

DATA HANDBOOK

Surface mounted
semiconductors

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Philips Semiconductors



PHILIPS

**Surface mounted
semiconductors****Contents**

PART A	page
SELECTION GUIDE	
General purpose transistors	4
High frequency transistors	8
Broadband transistors	8
Switching transistors	10
Power transistors for switching	12
Low-noise transistors	14
High-voltage transistors	14
Field-effect transistors	15
Special transistors	18
Trigger devices	18
Diodes	18
Variable capacitance diodes	20
Voltage regulator diodes	20
Transient suppression diodes	21
Rectifier diodes	21
Temperature sensors	22
TYPE NUMBER SURVEY (alphanumeric)	24
CONVERSION LIST (conventional to SMD type numbers)	40
MARKING LIST	46
GENERAL	
Tape and reel specification	55
Soldering recommendations	61
Thermal characteristics	67
Type designation	71
Rating systems	73
Transistor ratings	75
Letter symbols	79
S-parameters	85
DEVICE DATA (in alphanumeric sequence)	89

PART B	page
SELECTION GUIDE	
General purpose transistors	700
High frequency transistors	704
Broadband transistors	704
Switching transistors	706
Power transistors for switching	708
Low-noise transistors	710
High-voltage transistors	710
Field-effect transistors	711
Special transistors	714
Trigger devices	714
Diodes	714
Variable capacitance diodes	716
Voltage regulator diodes	716
Transient suppression diodes	717
Rectifier diodes	717
Temperature sensors	718
DEVICE DATA (in alphanumeric sequence)	721
ENVELOPES	1375

Selection guide

Surface mounted semiconductors

Selection guide

GENERAL PURPOSE TRANSISTORS in SOT23/SOT89*/SOT143**/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
NPN												
BC817	45	45	500	250	100	600	100	1	0.7	500/50	200	229
BC818	25	25	500	250	100	600	100	1	0.7	500/50	200	229
BC846	65	65	100	250	220	800	2	5	0.25	10/0.5	300	235
BC847	45	45	100	250	220	800	2	5	0.25	10/0.5	300	235
BC848	30	30	100	250	220	800	2	5	0.25	10/0.5	300	235
BC868*	20	20	1000	1000	85	375	500	1	0.5	1000/100	60	275
BCP54Δ	45	45	1000	1500	40	250	150	2	0.5	500/50	130	311
BCP55Δ	60	60	1000	1500	40	250	150	2	0.5	500/50	130	311
BCP56Δ	100	80	1000	1500	40	250	150	2	0.5	500/50	130	311
BCP68Δ	-	20	1000	1500	85	375	500	1	0.5	1000/100	60	315
BCV27	40	30	300	250	20000	-	100	5	1.0	100/0.1	220	329
BCV29*	40	30	500	1000	20000	-	100	5	1.0	100/0.1	220	333
BCV47	80	60	500	250	4000	-	10	5	1.0	100/0.1	220	329
BCV49*	80	60	500	1000	10000	-	100	5	1.0	100/0.1	220	333
BCV71	80	60	100	250	110	220	2	5	0.25	10/0.5	300	353
BCV72	80	60	100	250	200	450	2	5	0.25	10/0.5	300	353
BCW31	32	32	100	250	110	220	2	5	0.25	10/0.5	300	361
BCW32	32	32	100	250	200	450	2	5	0.25	10/0.5	300	361
BCW33	32	32	100	250	420	800	2	5	0.25	10/0.5	300	361
BCW60A	32	32	200	250	120	220	2	5	0.35	10/0.25	250	367
BCW60B	32	32	200	250	180	310	2	5	0.35	10/0.25	250	367
BCW60C	32	32	200	250	250	460	2	5	0.35	10/0.25	250	367
BCW60D	32	32	200	250	380	630	2	5	0.35	10/0.25	250	367
BCW71	50	45	100	250	110	220	2	5	0.25	10/0.5	300	381
BCW72	50	45	100	250	220	450	2	5	0.25	10/0.5	300	381
BCW81	50	45	100	250	450	800	2	5	0.25	10/0.5	300	387
BCX19	50	45	500	250	100	600	100	1	0.62	500/50	200	395
BCX20	30	25	500	250	100	600	100	1	0.62	500/50	200	395
BCX54*	45	45	1000	1000	45	250	150	2	0.5	500/50	130	403
BCX55*	60	60	1000	1000	40	160	150	2	0.5	500/50	130	403
BCX56*	100	80	1000	1000	40	160	150	2	0.5	500/50	130	403
BCX70G	45	45	200	250	120	220	2	5	0.35	10/0.25	250	407
BCX70H	45	45	200	250	180	310	2	5	0.35	10/0.25	250	407

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
NPN												
BCX70J	45	45	200	250	250	460	2	5	0.35	10/0.25	250	407
BCX70K	45	45	200	250	380	630	2	5	0.35	10/0.25	250	407
BSP40Δ	70	60	1000	1500	40	120	100	5	0.25	150/15	100	905
BSP41Δ	70	60	1000	1500	100	300	100	5	0.25	150/15	100	905
BSP42Δ	90	80	1000	1500	40	120	100	5	0.25	150/15	100	905
BSP43Δ	90	80	1000	1500	100	300	100	5	0.25	150/15	100	905
PMBT4401	60	40	600	250	100	300	150	1	0.75	500/50	250	1233
PMBT5550	160	140	600	300	60	250	10	5	0.25	50/5	200	1247
PMBT6428	60	50	200	350	250	650	-	-	0.2	10/0.5	300	1251
PMBT6429	55	45	200	350	500	1250	-	-	0.2	10/0.5	300	1251
PMBTA05	60	60	500	300	50	-	10	1	0.25	100/10	100	1255
PMBTA06	80	80	500	300	50	-	10	1	0.25	100/10	100	1255
PMBTA13	30	30	300	300	5000	-	10	5	1.5	100/0.1	125	1257
PMBTA14	30	30	300	300	10000	-	10	5	1.5	100/0.1	125	1257
PXT4401*	60	40	600	1000	100	300	150	1	0.75	500/50	250	1313
PXTA14*	30	30	300	1000	20000	-	100	5	1.5	100/0.1	125	1321
PXTA27*	-	60	500	1000	10000	-	100	5	1.5	100/0.1	125	1323
PZTA05Δ	60	60	500	1500	50	-	100	1	0.25	100/10	100	1347
PZTA06Δ	80	80	500	1500	50	-	100	1	0.25	100/10	100	1347
PZTA13Δ	30	30	300	1500	5000	-	10	5	1.5	100/0.1	125	1351
PZTA14Δ	30	30	300	1500	10000	-	10	5	1.5	100/0.1	125	1351
PZTA42Δ	300	300	500	1500	40	-	10	10	0.5	20/2	50	1353
PZTA43Δ	200	200	500	1500	40	-	10	10	0.5	20/2	50	1353
PNP												
BC807	45	45	500	250	100	600	100	1	0.7	500/50	100	223
BC808	25	25	500	250	100	600	100	1	0.7	500/50	100	223
BC856	65	65	100	250	75	475	2	5	0.3	10/0.5	150	257
BC857	45	45	100	250	75	800	2	5	0.3	10/0.5	150	257

Notes

* Types in SOT89 package.

** Types in SOT143 package.

Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE-sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
PNP												
BC858	30	30	100	250	75	800	2	5	0.3	10/0.5	150	257
BC869*	20	20	1000	1000	85	375	500	1	0.5	1000/100	60	281
BCP51Δ	45	45	1000	1500	40	250	150	2	0.5	500/50	50	307
BCP52Δ	60	60	1000	1500	40	250	150	2	0.5	500/50	50	307
BCP53Δ	100	80	1000	1500	40	250	150	2	0.5	500/50	50	307
BCP69Δ	-	25	1000	1500	85	375	500	1	0.5	1000/100	60	321
BCV26	40	30	250	350	20000	-	100	5	1.0	100/0.1	220	327
BCV28*	40	30	500	1000	20000	-	100	5	1.0	100/0.1	220	331
BCV46	80	60	250	300	4000	-	10	5	1.0	100/0.1	220	327
BCV48*	80	60	500	1000	10000	-	100	5	1.0	100/0.1	220	331
BCW29	32	32	100	250	120	260	2	5	0.3	10/0.5	150	355
BCW30	32	32	100	250	215	500	2	5	0.3	10/0.5	150	355
BCW61A	32	32	200	250	120	220	2	5	0.25	10/0.25	180	371
BCW61B	32	32	200	250	180	310	2	5	0.25	10/0.25	180	371
BCW61C	32	32	200	250	250	460	2	5	0.25	10/0.25	180	371
BCW61D	32	32	200	250	380	630	2	5	0.25	10/0.25	180	371
BCW69	50	45	100	250	120	260	2	5	0.3	10/0.5	150	375
BCW70	50	45	100	250	120	500	2	5	0.3	10/0.5	150	375
BCW89	80	60	100	250	120	260	2	5	0.3	10/0.5	150	389
BCX17	50	45	500	250	100	600	100	1	0.62	500/50	100	391
BCX18	30	25	500	250	100	600	100	1	0.62	500/50	100	391
BCX51*	45	45	1000	1000	40	250	150	2	0.5	500/50	50	399
BCX52*	60	60	1000	1000	40	160	150	2	0.5	500/50	50	399
BCX53*	100	80	1000	1000	40	160	150	2	0.5	500/50	50	399
BCX71G	45	45	200	250	120	220	2	5	0.25	10/0.25	180	411
BCX71H	45	45	200	250	180	310	2	5	0.25	10/0.25	180	411
BCX71J	45	45	200	250	250	460	2	5	0.25	10/0.25	180	411
BCX71K	45	45	200	250	380	630	2	5	0.25	10/0.25	180	411

Notes

* Types in SOT89 package.

** Types in SOT143 package.

Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
BSP30Δ	70	60	1000	1500	40	120	100	5	0.25	150/15	100	901
BSP31Δ	70	60	1000	1500	100	300	100	5	0.25	150/15	100	901
BSP32Δ	90	80	1000	1500	40	120	100	5	0.25	150/15	100	901
BSP33Δ	90	80	1000	1500	100	300	100	5	0.25	150/15	100	901
PMBT4403	40	40	600	250	100	300	150	2	0.75	500/50	200	1237
PMBTA55	60	60	500	250	50	-	10	1	0.25	100/10	50	1263
PMBTA56	80	80	500	250	50	-	10	1	0.25	100/10	50	1263
PMBTA63	30	30	500	250	5000	-	10	5	1.5	100/0.1	125	1265
PMBTA64	30	30	500	250	5000	-	10	5	1.5	100/0.1	125	1265
PXT4403*	40	40	600	1000	100	300	150	2	0.4	150/15	200	1317
PXTA64*	30	30	300	1000	20000	-	100	5	1.5	100/0.1	125	1325
PXTA77*	-	60	500	1000	10000	-	100	5	1.5	100/0.1	125	1327
PXTA92*	300	300	500	1500	40	-	10	10	0.5	20/2	50	1329
PXTA93*	200	200	500	1500	40	-	10	10	0.5	20/2	50	1329
PZTA55Δ	60	60	500	1500	50	-	100	1	0.25	100/10	50	1357
PZTA56Δ	80	80	500	1500	50	-	100	1	0.25	100/10	50	1357
PZTA63Δ	30	30	500	1500	10000	-	100	5	1.5	100/0.1	125	1361
PZTA64Δ	30	30	500	1500	10000	-	100	5	1.5	100/0.1	125	1361
PZTA92Δ	300	300	500	1500	40	-	10	10	0.5	20/2	50	1363
PZTA93Δ	200	200	500	1500	40	-	10	10	0.5	20/2	50	1363

Notes

- * Types in SOT89 package.
- ** Types in SOT143 package.
- Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

HIGH-FREQUENCY TRANSISTORS in SOT23

TYPE NUMBER	RATINGS				CHARACTERISTICS								PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	F typ. (dB)	at f (MHz)	f _T typ. (MHz)	C _{re} typ. (pF)	
					min.	max.							
NPN													
BF570	40	15	100	250	40	-	10	1	-	-	> 490	1.6	497
BF840	40	40	25	250	-	-	-	-	-	-	380	0.3	549
BF841	40	40	25	250	-	-	-	-	-	-	380	0.3	549
BFS18	30	20	20	250	35	125	1	10	4	100	200	0.85	839
BFS19	30	20	30	250	65	225	1	10	4	100	260	0.85	839
BFS20	30	20	25	250	40	85	7	10	-	-	450	-	845
PNP													
BF550	40	40	25	250	50	-	1	10	2	0.1	325	0.5	493
BF569	40	35	30	250	25	-	3	10	4.5	800	900	0.33	495
BF579	20	20	25	250	20	-	10	10	4.5	800	1350	0.46	501
BF660	40	30	25	250	30	-	3	10	-	-	650	0.65	513
BF824	30	30	25	250	-	-	-	-	3	100	450	0.1	543

BROADBAND TRANSISTORS in SOT23/SOT89*/SOT143**/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS								PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	d _{im} typ. (dB)	at f (MHz)	f _T typ. (GHz)	C _{re} typ. (pF)	
					min.	max.							
NPN													
BF747	30	20	50	150	40	250	2	10	-	-	1.2	0.5	523
BFG16AΔ	40	25	150	1000	25	-	50	5	-	-	1.5	1.8	591
BFG17A**	25	15	50	300	20	-	2	1	60	793.25	2.8	0.6	599
BFG25AX**	8	5	6.5	32	50	200	0.5	1	-	-	5	0.22	607
BFG33**	9	7	20	300	50	-	14	5	-	-	12	-	617
BFG33X**	9	7	20	300	50	-	14	5	-	-	12	-	617
BFG35Δ	25	18	150	1000	25	-	100	10	60	793.25	4	1.2	619
BFG67**	20	10	50	300	60	100	15	5	-	-	7.5	0.5	637
BFG67X**	20	10	50	300	60	-	15	5	-	-	7.5	0.5	637
BFG92A**	20	15	25	300	40	-	14	10	-	-	5	0.35	641
BFG92AX**	20	15	25	300	40	-	14	10	-	-	5	0.35	641
BFG93A**	15	12	35	300	40	-	30	5	-	-	6	0.6	647
BFG93AX**	15	12	35	300	40	-	30	5	-	-	6	0.6	647
BFG94Δ	15	12	60	700	45	-	30	5	60	793.25	6	0.5	653
BFG97Δ	20	15	100	1000	25	-	70	10	60	793.25	5.5	1.0	665

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS								PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	d _{im} typ. (dB)	at f (MHz)	f _T typ. (GHz)	C _{re} typ. (pF)	
					min.	max.							
NPN													
BFG135Δ	25	15	150	1000	80	-	100	10	60	793.25	7.0	1.2	675
BFG197**	20	10	100	300	40	-	50	5	-	-	7.5	0.85	687
BFG197X**	20	10	100	300	40	-	50	5	-	-	7.5	0.85	687
BFG198Δ	20	10	100	1000	40	-	50	5	60	793.25	8.0	0.8	721
BFQ17*	40	25	150	1000	25	-	150	5	-	-	1.2	1.9	731
BFQ18A	25	15	150	1000	25	-	100	10	60	793.25	3.6	1.2	737
BFQ19*	20	15	75	500	25	-	75	10	-	-	5.0	1.3	741
BFQ67	20	10	50	180	100	-	15	5	-	-	7.5	0.5	747
BFR53	18	10	50	250	25	-	50	5	60	217	2.0	0.9	767
BFR92	20	15	25	200	25	-	14	10	60	493.25	5.0	0.7	775
BFR92A	20	15	25	200	40	-	14	10	60	793.25	5.0	0.35	783
BFR93	15	12	35	200	25	-	30	5	60	493.25	5.0	0.8	795
BFR93A	15	12	35	250	40	-	30	5	60	793.25	5.0	0.6	803
BFR106	20	15	100	350	-	-	-	-	-	-	3.7	1.2	817
BFS17	25	15	25	250	20	150	2	1	45	217	1.3	0.65	827
BFS17A	25	15	25	300	20	150	2	1	-	-	2.8	0.6	833
BFT25	8	5	2.5	50	20	-	1	1	-	-	2.3	0.45	851
BFT25A	8	5	6.5	50	-	-	-	-	-	-	5	0.22	859
PNP													
BFG31Δ	20	15	100	1000	25	-	100	10	60	848.25	5	1.6	611
BFG55Δ	25	18	150	1000	25	-	100	10	60	848.25	4	1.7	631
BFQ149*	20	15	75	1000	20	-	50	10	-	-	4.2	1.7	751
BFT92	20	15	25	200	20	-	14	10	60	493.25	5	0.7	869
BFT93	15	12	35	200	20	-	30	5	60	493.25	5	1.0	875

Notes

- * Types in SOT89 package.
- ** Types in SOT143 package.
- Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

SWITCHING TRANSISTORS in SOT23/SOT89*/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS								PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} (V) max.	at I _C /I _B (mA)	t _{on} /t _{off} (ns) max.	at I _C /I _B (mA)	
					min.	max.							
NPN													
BSP50Δ	60	45	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	909
BSP51Δ	80	60	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	909
BSP52Δ	90	80	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	909
BSR13	60	30	800	250	100	300	150	10	1.6	500/50	35/285	150/-	991
BSR14	75	40	800	250	100	300	150	10	1.0	500/50	-	-	991
BSR17A	60	40	200	250	100	300	10	1	0.3	50/5	70/250	10/1	999
BSR40*	70	60	1000	1000	40	120	100	5	0.5	500/50	250/1000	100/5	1019
BSR41*	70	60	1000	1000	100	300	100	5	0.5	500/50	250/1000	100/5	1019
BSR42*	90	80	1000	1000	40	120	100	5	0.5	500/50	250/1000	100/5	1019
BSR43*	90	80	1000	1000	100	300	100	5	0.5	500/50	250/1000	100/5	1019
BSS64	120	80	100	250	20	80	10	1	0.2	50/15	-/1000	15/1	1033
BST50*	60	45	500	1000	1000	-	150	10	1.3	500/50	400/1500	500/0.5	1067
BST51*	80	60	500	1000	1000	-	150	10	1.3	500/50	400/1500	500/0.5	1067
BST52*	90	80	500	1000	1000	-	150	10	1.3	500/50	400/1500	500/0.5	1067
BSV52	20	12	100	250	40	120	10	1	0.2	50/5	12/18	10/3	1099
PMBT2222	60	30	600	250	100	300	150	10	0.4	150/15	10/225	150/-	1215
PMBT2222A	75	40	600	250	100	300	150	10	0.3	150/15	10/225	150/-	1215
PMBT2369	40	40	500	250	40	120	10	1	0.25	10/1	12/18	10/3	1219
PMBT3904	60	40	200	300	100	300	10	1	0.3	50/5	35/200	10/1	1225
PXT2222*	60	30	600	1000	100	300	150	10	0.4	150/15	10/225	150/15	1297
PXT2222A*	75	40	600	1000	100	300	150	10	0.4	150/15	10/225	150/15	1297
PXT3904*	60	40	200	1000	100	300	10	1	0.3	50/5	35/200	10/1	1305
PZT2222Δ	60	30	600	1500	100	300	150	10	0.4	150/15	-	-	1331
PZT2222AΔ	75	40	600	1500	100	300	150	10	0.3	150/10	10/225	150/15	1331
PZT3904Δ	60	40	200	1500	100	300	10	1	0.3	10/1	35/200	10/1	1339

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS								PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} (V) max.	at I _C /I _B (mA)	t _{on} /t _{off} (ns) max.	at I _C /I _B (mA)	
					min.	max.							
PNP													
BSP60Δ	60	45	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	913
BSP61Δ	80	60	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	913
BSP62Δ	90	80	500	1500	2000	-	500	10	1.3	500/0.5	400/1500	500/0.5	913
BSR12	15	15	100	250	30	120	50	1	0.45	100/10	20/30	30/3	985
BSR15	60	40	600	250	100	300	150	10	1.6	500/50	45/100	150/15	995
BSR16	60	60	600	250	100	300	150	10	1.6	500/50	45/100	150/15	995
BSR18A	40	40	200	250	100	300	10	1	0.4	50/5	70/300	10/1	1003
BSR30*	70	60	1000	1000	40	120	100	5	0.5	500/50	500/650	100/5	1015
BSR31*	70	60	1000	1000	100	300	100	5	0.5	500/50	500/650	100/5	1015
BSR32*	90	80	1000	1000	40	120	100	5	0.5	500/50	500/650	100/5	1015
BSR33*	90	80	1000	1000	100	300	100	5	0.5	500/50	500/650	100/5	1015
BSS63	110	100	100	250	30	-	25	1	0.25	25/2.5	-	-	1027
BST60*	60	45	500	1000	1000	-	150	10	1.3	500/0.5	400/1500	500/0.5	1071
BST61*	80	60	500	1000	1000	-	150	10	1.3	500/0.5	400/1500	500/0.5	1071
BST62*	90	80	500	1000	1000	-	150	10	1.3	500/0.5	400/1500	500/0.5	1071
PMBT2907	60	40	600	250	30	50	500	10	0.4	150/15	45/100	150/15	1221
PMBT2907A	60	60	600	250	30	50	500	10	0.4	150/15	45/100	150/15	1221
PMBT3906	40	40	200	250	100	300	10	1	0.25	10/1	35/225	10/1	1229
PXT2907*	60	40	600	1000	100	300	150	10	0.4	150/10	45/100	150/15	1301
PXT2907A*	60	60	600	1000	100	300	150	10	0.4	150/10	45/100	150/15	1301
PXT3906*	40	40	200	1000	100	300	10	1	0.25	10/1	35/225	10/1	1309
PZT2907Δ	60	40	600	1500	100	300	150	10	0.4	150/15	45/100	150/15	1335
PZT2907AΔ	60	60	600	1500	100	300	150	10	0.4	150/15	45/100	150/15	1335
PZT3906Δ	40	40	200	1500	100	300	10	1	0.4	50/5	35/225	10/1	1343

Notes

* Types in SOT89 package.

** Types in SOT143 package.

 Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

POWER TRANSISTORS FOR SWITCHING in SOT223

TYPE NUMBER	RATINGS				CHARACTERISTICS										PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (A)	P _{tot} (W)	h _{FE} min.	at I _C (A)	at V _{CE} (V)	V _{CE sat} (V) max.	at I _C (A)	at I _B (mA)	t _{on} max.	t _{off} max.	at I _C (A)	at I _B (mA)	
NPN															
BDS61	60	60	4	8	1000	1.5	3	1.6	1.5	6	2	8	1.5	6000	421
BDS61A	80	80	4	8	1000	1.5	3	1.6	1.5	6	2	8	1.5	6000	421
BDS61B	100	100	4	8	1000	1.5	3	1.6	1.5	6	2	8	1.5	6000	421
BDS61C	120	120	4	8	1000	1.5	3	1.6	1.5	6	2	8	1.5	6000	421
BDS77	100	80	3	8	30	2	2	1.8	6	600	1	3	2	200	427
BDS201	60	45	3	8	40	3	2	1.8	6	600	1	3	2	200	427
BDS203	60	60	3	8	30	2	2	1.8	6	600	1	3	2	200	427
BDS643	60	45	3	8	1000	3	3	1.8	5	50	2	10	3	12	439
BDS645	80	60	3	8	1000	3	3	1.8	5	50	2	10	3	12	439
BDS647	100	80	3	8	1000	3	3	1.8	5	50	2	10	3	12	439
BDS649	120	100	3	8	1000	3	3	1.8	5	50	1	10	3	12	439
BDS651	140	120	3	8	1000	3	3	1.8	5	50	2	10	3	12	439
BDS933	45	45	3	8	25	1	2	0.5	1	100	1	3	1	100	451
BDS935	60	60	3	8	25	1	2	0.5	1	100	1	3	1	100	451
BDS937	100	80	3	8	25	1	2	0.5	1	100	1	3	1	100	451
BDS939	120	100	3	8	25	1	2	0.5	1	100	1	3	1	100	451
BDS941	140	120	3	8	25	1	2	0.5	1	100	1	3	1	100	451
BDS943	22	22	3	8	50	2	1	0.5	2	200	-	-	-	-	463
BDS945	32	32	3	8	50	2	1	0.5	2	200	-	-	-	-	463
BDS947	45	45	3	8	40	0.25	1	0.5	2	200	-	-	-	-	463
BDS949	60	60	3	8	20	2	4	1	2	200	-	-	-	-	475
BDS951	80	80	3	8	20	2	4	1	2	200	-	-	-	-	475
BDS953	100	100	3	8	20	2	4	1	2	200	-	-	-	-	475
BDS955	120	120	3	8	20	2	4	1	2	200	-	-	-	-	475
PNP															
BDS60	60	60	4	8	1000	1.5	3	1.6	1.5	6	1.5	5	1.5	6000	415
BDS60A	80	80	4	8	1000	1.5	3	1.6	1.5	6	1.5	5	1.5	6000	415
BDS60B	100	100	4	8	1000	1.5	3	1.6	1.5	6	1.5	5	1.5	6000	415
BDS60C	120	120	4	8	1000	1.5	3	1.6	1.5	6	1.5	5	1.5	6000	415
BDS78	100	80	3	8	40	3	2	1.8	6	600	1	3	2	200	433
BDS202	60	45	3	8	40	3	2	1.8	6	600	1	3	2	200	433
BDS204	60	60	3	8	40	3	2	1.8	6	600	1	3	2	200	433
BDS644	60	45	3	8	1000	3	3	1.8	5	50	2	10	3	12	445
BDS646	80	60	3	8	1000	3	3	1.8	5	50	2	10	3	12	445

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS										PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (A)	P _{tot} (W)	h _{FE} min.	at I _C (A)	at V _{CE} (V)	V _{CE sat} (V) max.	at I _C (A)	at I _B (mA)	t _{on} max.	t _{off} max.	at I _C (A)	at I _B (mA)	
PNP															
BDS648	100	80	3	8	1000	3	3	1.8	5	50	2	10	3	12	445
BDS650	120	100	3	8	1000	3	3	1.8	5	50	2	10	3	12	445
BDS652	140	120	3	8	1000	3	3	1.8	5	50	2	10	3	12	445
BDS934	45	45	3	8	25	1	2	0.5	1	100	0.6	2.4	1	100	457
BDS936	60	60	3	8	25	1	2	0.5	1	100	0.6	2.4	1	100	457
BDS938	100	80	3	8	25	1	2	0.5	1	100	0.6	2.4	1	100	457
BDS940	120	100	3	8	25	1	2	0.5	1	100	0.6	2.4	1	100	457
BDS942	140	120	3	8	25	1	2	0.5	1	100	0.6	2.4	1	100	457
BDS944	22	22	3	8	50	2	1	0.5	2	200	-	-	-	-	469
BDS946	32	32	3	8	50	2	1	0.5	2	200	-	-	-	-	469
BDS948	45	45	3	8	40	2	1	0.5	2	200	-	-	-	-	469
BDS950	60	60	3	8	20	2	4	1	2	200	-	-	-	-	481
BDS952	80	80	3	8	20	2	4	1	2	200	-	-	-	-	481
BDS954	100	100	3	8	20	2	4	1	2	200	-	-	-	-	481
BDS956	120	120	3	8	20	2	4	1	2	200	-	-	-	-	481

Surface mounted semiconductors

Selection guide

LOW-NOISE TRANSISTORS in SOT23 (F > 4 dB at f = 1 kHz; B = 200 Hz)

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
NPN												
BC849	30	30	100	250	-	800	2	5	0.25	10/0.5	300	245
BC850	45	45	100	250	-	800	2	5	0.25	10/0.5	300	245
BCF32	32	32	100	250	200	450	2	5	0.25	10/0.5	300	293
BCF33	32	32	100	250	420	800	2	5	0.25	10/0.5	300	293
BCF81	50	45	100	250	420	800	2	5	0.25	10/0.5	300	305
PMBT5088	35	30	50	250	350	-	1	5	0.5	10/1	200	1241
PNP												
BC859	30	30	100	250	125	800	2	5	0.3	10/0.5	150	265
BC860	45	45	100	250	125	800	2	5	0.3	10/0.5	150	265
BCF29	32	32	100	250	120	260	2	5	0.3	10/0.5	150	287
BCF30	32	32	100	250	215	500	2	5	0.3	10/0.5	150	287
BCF70	50	45	100	250	215	500	2	5	0.3	10/0.5	150	299

HIGH-VOLTAGE TRANSISTORS in SOT23/SOT89*/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
NPN												
BF620*	300	-	50	1000	50	-	25	20	0.6	30/5	60	505
BF622*	250	250	50	1000	50	-	25	20	0.6	30/5	60	505
BF720Δ	300	-	50	1500	50	-	25	20	0.6	30/5	60	515
BF722Δ	250	250	50	1500	50	-	25	20	0.6	30/5	60	515
BF820	300	-	50	310	50	-	25	20	0.6	30/5	60	535
BF822	250	250	50	310	50	-	25	20	0.6	30/5	60	535
BSP19Δ	400	350	1000	1500	40	-	10	20	1.3	50/4	70	899
BSP20Δ	300	250	1000	1500	40	-	10	20	1.3	50/4	70	899
BSR19	160	140	600	350	60	250	10	5	0.25	50/5	100	1007
BSR19A	180	160	600	360	80	250	10	5	0.2	50/5	100	1007
BST39*	400	350	1000	1000	40	160	20	10	0.5	50/4	70	1063
BST40*	300	250	1000	1000	40	160	20	10	0.5	50/4	70	1063
PMBT5551	180	160	600	250	80	250	10	5	0.2	50/5	100	1249
PMBTA42	300	300	500	250	40	-	30	10	0.5	20/2	50	1259
PMBTA43	200	200	500	250	40	-	30	10	0.5	20/2	50	1259

Surface mounted semiconductors

Selection guide

HIGH-VOLTAGE TRANSISTORS in SOT23/SOT89*/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
PNP												
BF621*	300	-	20	1000	50	-	25	20	0.8	30/5	60	509
BF623*	250	250	20	1000	50	-	25	20	0.8	30/5	60	509
BF721Δ	300	-	50	1500	50	-	25	20	0.8	30/5	60	519
BF723Δ	250	250	50	1500	50	-	25	20	0.8	30/5	60	519
BF821	300	-	50	250	50	-	25	20	0.8	30/5	60	539
BF823	250	250	50	250	50	-	25	20	0.8	30/5	60	539
BSP15Δ	200	200	1000	1500	30	150	10	50	2.5	50/5	15	897
BSP16Δ	350	300	1000	1500	30	120	10	50	2.0	50/5	15	897
BSR20	130	120	600	250	40	180	10	5	0.5	50/5	100	1011
BSR20A	160	150	600	250	60	240	10	5	0.5	50/5	100	1011
BST15*	200	200	1000	1000	30	150	50	10	2.5	50/5	15	1059
BST16*	350	300	1000	1000	30	120	50	10	2.0	50/5	15	1059
PMBT5401	160	150	500	250	60	240	10	5	0.5	50/5	100	1245
PMBTA92	300	300	500	250	40	-	10	10	0.5	20/2	50	1267
PMBTA93	200	200	500	250	40	-	10	10	0.5	20/2	50	1267

Notes

- * Types in SOT89 package.
 ** Types in SOT143 package.
 Δ Types in SOT223 package.

FIELD-EFFECT TRANSISTORS in SOT23/SOT89*/SOT143**/SOT223Δ

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	$\pm V_{DS}$ (V)	$-V_{GSO}$ (V)	I_D (mA)	P_{tot} (mW)	$-I_{GSS}$ (nA) max.	I_{DSS} (mA)		$-V_{(P)GS}$ (V) max.	$ Y_{fs} $ (ms) min.	C_{rs} (pF) max.	V_n (μ V) max.	
						min.	max.					
BF510	20	-	30	250	10	0.7	3	0.8	2.5	0.4	-	487
BF511	20	-	30	250	10	2.5	7	1.5	4	0.4	-	487
BF512	20	-	30	250	10	6	12	2.2	6	0.4	-	487
BF513	20	-	30	250	10	10	18	3	7	0.4	-	487
BF989**	20	-	20	200	50	2	20	2.7	9.5	0.025	-	551
BF990A**	18	-	30	200	25	-	-	1.3	17	0.025	-	555
BF991**	20	-	20	200	50	4	25	2.5	10	0.020	-	559
BF992**	20	-	40	200	25	-	-	1.3	20	0.04	-	563

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	$\pm V_{DS}$ (V)	$-V_{GSO}$ (V)	I_D (mA)	P_{tot} (mW)	$-I_{GSS}$ (nA) max.	I_{DSS} (mA)		$-V_{(P)GS}$ (V) max.	$ Y_{fs} $ (ms) min.	C_{rs} (pF) max.	V_n (μ V) max.	
						min.	max.					
BF994S**	20	-	50	300	50	4	20	2.5	15	0.025	-	569
BF996S**	20	-	30	300	50	4	20	2.5	15	0.025	-	573
BF997**	20	-	30	300	10	2	20	2.5	15	0.025	-	577
BF998**	12	-	30	200	50	2	18	2.5	21	-	-	581
BFR30	25	25	10	250	0.2	4	10	5	1	1.5	0.5	757
BFR31	25	-	-	-	-	1	5	2.5	1.5	1.5	0.5	757
BFR101A**	30	30	10	200	5	0.2	1.5	1.0	1.2	-	-	815
BFR101B**	30	30	10	200	5	1	5	2.5	2.5	-	-	815
BFR200**	30	30	20	250	.003	0.2	3.5	-	1.3	-	-	823
BFT46	25	25	10	250	0.2	0.2	1.5	1.2	1.0	1.5	0.5	861
BSD22**	20	-	50	230	1	-	-	2.0	-	0.6	-	893
BSP103 Δ	35	20	700	1500	-	-	-	-	-	-	-	917
BSP105 Δ	60	20	500	1500	-	-	-	-	-	-	-	917
BSP106 Δ	60	20	425	1500	10	-	0.001	-	100	10	-	921
BSP107 Δ	200	20	200	1500	10	-	.00003	-	90	10	-	929
BSP108 Δ	80	20	500	1500	100	-	0.001	-	150	12	-	937
BSP109 Δ	90	20	450	1500	-	-	-	-	-	-	-	917
BSP110 Δ	80	20	325	1500	100	-	0.001	-	75	6	-	941
BSP120 Δ	200	20	250	1500	100	-	0.001	-	125	10	-	945
BSP121 Δ	200	20	350	1500	100	-	0.001	-	200	10	-	949
BSP126 Δ	250	20	350	1500	100	-	0.001	-	200	15	-	955
BSP205 Δ	60	20	275	1500	100	-	0.001	-	60	10	-	961
BSP206 Δ	60	20	350	1500	100	-	0.001	-	100	12	-	965
BSP220 Δ	200	20	225	1500	100	-	0.001	-	100	15	-	969
BSP225 Δ	250	20	225	1500	100	-	0.001	-	100	15	-	977
BSR56	40	40	-	250	1	50	-	10	-	5	-	1023
BSR57	40	40	-	250	1	20	100	6	-	5	-	1023
BSR58	40	40	-	250	1	8	80	4	-	5	-	1023
BSS83**	10	-	50	230	10	-	-	2	-	0.6	-	1037
BSS84	50	20	130	360	6000	-	0.06	-	50	-	-	1041
BSS87	200	20	280	1000	100	-	0.06	-	140	10	-	1045
BSS131	240	20	100	360	10	-	0.06	-	60	-	-	1049

Notes

* Types in SOT89 package.

** Types in SOT143 package.

 Δ Types in SOT223 package.

Surface mounted semiconductors

Selection guide

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	$\pm V_{DS}$ (V)	$-V_{GSO}$ (V)	I_D (mA)	P_{tot} (mW)	$-I_{GSS}$ (nA) max.	I_{DSS} (mA)		$-V_{(P)GS}$ (V) max.	$ Y_{fs} $ (ms) min.	C_{rs} (pF) max.	V_n (μ v) max.	
						min.	max.					
BSS192*	200	20	150	1000	100	-	0.06	-	60	15	-	1053
BST80*	80	20	500	1000	100	-	0.01	3.5	300	8	-	1075
BST82	80	20	175	300	100	-	0.001	3.5	150	3	-	1079
BST84*	200	20	250	1000	100	-	0.01	2.8	250	5	-	1083
BST86*	180	20	300	1000	100	-	0.01	2.4	250	6	-	1087
BST120*	60	20	300	1000	100	-	0.01	3.5	200	8	-	1091
BST122*	50	20	250	1000	100	-	0.01	3.5	125	8	-	1095
PMBF170	60	20	250	300	10	-	0.001	-	100	10	-	1191
PMBF4391	40	40	-	250	1	50	150	10	-	3.5	-	1195
PMBF4392	40	40	-	250	1	25	75	5	-	3.5	-	1195
PMBF4393	40	40	-	250	1	5	30	3	-	3.5	-	1195
PMBFJ108	25	25	-	250	3	80	-	-	-	15	-	1199
PMBFJ109	25	25	-	250	3	40	-	-	-	15	-	1199
PMBFJ110	25	25	-	250	3	10	-	-	-	15	-	1199
PMBFJ111	40	40	-	300	1	20	-	-	-	-	-	1205
PMBFJ112	40	40	-	300	1	5	-	-	-	-	-	1205
PMBFJ113	40	40	-	300	1	2	-	-	-	-	-	1205
PMBFJ174	30	30	-	300	1	20	135	10	-	4	-	1211
PMBFJ175	30	30	-	300	1	7	70	6	-	4	-	1211
PMBFJ176	30	30	-	300	1	2	35	4	-	4	-	1211
PMBFJ177	30	30	-	300	1	1.5	20	2.25	-	4	-	1211
2N7002	60	-	180	300	-	-	-	-	-	-	-	1365

Notes

* Types in SOT89 package.

** Types in SOT143 package.

Surface mounted semiconductors

Selection guide

SPECIAL TRANSISTORS IN SOT143

TYPE NUMBER	RATINGS				CHARACTERISTICS							PAGE
	V _{CBO} (V)	V _{CEO} (V)	I _C (mA)	P _{tot} (mW)	h _{FE}		at I _C (mA)	at V _{CE} (V)	V _{CE sat} max. (V)	at I _C /I _B (mA)	f _T typ. (MHz)	
					min.	max.						
PNP												
BCV62	30	30	100	250	100	800	2	5	0.65	100/5	150	339
BCV64	30	30	100	250	100	900	2	5	0.3	100/0.5	200	347
NPN												
BCV61	30	30	100	250	110	800	2	5	0.6	100/5	300	335
BCV63	30	30	100	250	100	900	2	5	0.65	100/5	200	343
NPN/PNP												
BCV65	30	30	100	250	75	800	2	5	0.3	10/0.5	100	351

TRIGGER DEVICES

TYPE	ENVELOPE	RATINGS		CHARACTERISTICS		PAGE
		V_{GA} (V) max.	I_A (mA) max.	I_P (μ A)	I_V (μ A)	
BRY61	SOT23	70	175	5/1	30/50	881
BRY62	SOT143	70	175	-	-	887

DIODES in SOT23/SOD80*/SOT143**

TYPE NUMBER	DESCRIPTION	RATINGS		CHARACTERISTICS				PAGE
		V_R (V)	I_F (mA)	t_{rr} max. (ns)	V_F (V)	at I_F (mA)	C_d max. (pF)	
BA423L*	band switch	20	50	-	0.9	50	2.5	89
BA682*	band switch	35	100	-	1	100	1.5	91
BA683*	band switch	35	100	-	1	100	1.5	91
BAS16	high-speed switch	75	250	6	1.25	150	2	93
BAS17	low-voltage stabilizer	-	250	-	0.87-0.96	100	140	97
BAS19	high-speed switch	100	200	50	1.25	200	5	101
BAS20	high-speed switch	150	200	50	1.25	200	5	101
BAS21	high-speed switch	200	200	50	1.25	200	5	101
BAS28**	fast switch double diode	75	250	6	1.25	150	2	109
BAS29	switch	90	250	50	1.25	400	35	113
BAS31	two diodes in series	90	250	50	1.25	400	35	113
BAS32*	high-speed switch	75	200	4	1	100	2	115
BAS32L*	high-speed switch	75	200	4	1	100	2	123

Surface mounted semiconductors

Selection guide

TYPE NUMBER	DESCRIPTION	RATINGS		CHARACTERISTICS				PAGE
		V _R (V)	I _F (mA)	t _{rr} max. (ns)	V _F (V)	at I _F (mA)	C _d max. (pF)	
BAS35	common diode double diode	90	250	50	1.25	400	35	113
BAS56**	ultra-high speed switch double diode	60	200	6	1.25	500	2.5	131
BAS85*	Schottky barrier	30	200	5	0.8	100	10	135
BAS86	Schottky barrier	50	200	4	0.9	100	-	139
BAT17	Schottky barrier	4	30	-	0.6	10	1	143
BAT18	band switch	35	100		1.2	100	1	147
BAT54	Schottky barrier	30	200	5	1	100	10	151
BAT54A;C;S	Schottky barrier	30	200	5	1	100	10	155
BAT74**	Schottky barrier double diode	30	200	5	1	100	10	157
BAV23**	two diodes	200	200	50	2.5	200	2.5	161
BAV70	common cathode double diode	70	250	6	1.25	150	1.5	163
BAV74	two diodes	50	250	4	1	100	2	167
BAV99	two diodes in series	70	250	6	1.25	150	1.5	171
BAV100*	general purpose	50	250	50	1.25	200	5	175
BAV101*	general purpose	100	250	50	1.25	200	5	175
BAV102*	general purpose	150	250	50	1.25	200	5	175
BAV103*	general purpose	200	250	50	1.25	200	5	175
BAV105*	ultra high speed	60	300	6	1.25	500	2.5	183
BAW56	common anode double diode	70	250	6	1.25	150	2	191
PMBD914	high speed switch	70	200	15	1	10	4	1179
PMBD6050	high speed switch	70	200	15	1.1	100	2.5	1183
PMBD7000	two diodes in series	100	200	15	1.1	100	1.5	1187
PMLL4148*	general purpose	75	200	4	1	10	4	1273
PMLL4150*	general purpose	50	300	6	1	200	2.5	1277
PMLL4151*	general purpose	50	200	2	1	50	2	1277
PMLL4153*	general purpose	50	200	2	0.88	20	2	1277
PMLL4446*	general purpose	75	200	4	1	20	4	1273
PMLL4448*	general purpose	70	200	4	1	100	4	1273

Notes

* Types in SOD80 package.

** Types in SOT143 package.

Surface mounted semiconductors

Selection guide

VARIABLE CAPACITANCE DIODES

TYPE NUMBER	ENVELOPE	RATINGS		CHARACTERISTICS					PAGE
		V_R (V)	I_F (mA)	C_d (pF)	at V_R (V)	C_d ratio ($f = 1$ MHz)	at V_R	r_D (Ω)	
BB215	SOD80	30	20	1.8 - 2.2	28	typ. 8.3	1/28	typ. 0.63	195
BB219	SOD80	30	20	2.6 - 3.2	28	12 - 15	1/28	typ. 0.7	197
BB240	SOD80	32	20	2.4 - 2.7	28	min. 14	0.5/28	max. 1	199
BB241	SOD80	32	20	2.5 - 3.0	28	min. 21	0.5/28	max. 2	201
BB249	SOD80	30	20	4 - 5	28	8 - 10	1/28	max. 0.6	203
BB804	SOT23	18	50	42 - 47.5	2	1.65 - 1.75	2/8	typ. 0.2	207
BBY31	SOT23	28	20	1.6 - 2	28	typ. 9.7	1/28	max. 1.2	209
BBY39	SOT23	30	20	1 - 2	28	min. 7.6	1/28	max. 0.75	213
BBY40	SOT23	28	20	3.8 - 4.8	28	8 - 12	1/28	max. 0.7	215
BBY42	SOT23	32	20	2.4 - 3	28	12 - 16	1/28	max. 1	219
BBY62	SOT143	28	20	1.6 - 2	28	typ. 9.7	1/28	max. 1.2	221

VOLTAGE REGULATOR DIODES

TYPE NUMBER	ENVELOPE	RATINGS					CHARACTERISTICS		PAGE
		VOLTAGE RANGE (V)	VOLTAGE TOLERANCE (%)	P_{tot} (mW)	I_{ZRM} (mA)	I_{FRM} (mA)	V_F max. (V)	at I_F (mA)	
BZD27	SOD87	7.5 to 510	5	2300	-	-	1.2	200	1125
BZV49	SOT89	2.4 to 75	5	1000	note 1	250	1	50	1131
BZV55	SOD80	2.4 to 75	2, 3, 5	500	-	250	0.9	10	1141
BZV80	SOD80	5.89 to 6.51	-	400	50	-	-	-	1155
BZV81	SOD80	5.89 to 6.51	-	400	50	-	-	-	1155
BZX84	SOT23	2.4 to 75	2.5	350	250	250	0.9	10	1161
PMLL5225B to PMLL5267B	SOD80	3.0 to 75	5	500	-	250	1.1	200	1281

Note

1. I_{ZRM} limited by $P_{ZRM\ max}$.

TRANSIENT SUPPRESSION DIODES

TYPE NUMBER	ENVELOPE	CHARACTERISTICS				PAGE
		V_R (V)	$V_{(CL)R}$ (V)	I_{RSM} (A)	P_{RSM} (W)	
BZD27	SOD87	6.2 to 430	11.3 to 707	13.3 to 0.21 note 1	150 note 1	1125

Note

1. Pulse according to IEC60-2, section 6: 10/1000 μ s exponential; $T_j = 25^\circ\text{C}$ prior to the pulse.

RECTIFIER DIODES

TYPE NUMBER	ENVELOPE	RATINGS					CHARACTERISTICS			PAGE
		$I_{F(AV)}$ (A)	V_{RRM} (V)	V_R (V)	I_{FRM} (A)	I_{FSM} (A)	t_{rr} (ns)	V_F (V)	at I_F (A)	
BYD17D	SOD87	1.5	200*	200	5.5	20	-	1.05	1	1107
BYD17G	SOD87	1.5	400*	400	5.5	20	-	1.05	1	1107
BYD17J	SOD87	1.5	600*	600	5.5	20	-	1.05	1	1107
BYD17K	SOD87	1.5	800*	800	5.5	20	-	1.05	1	1107
BYD17M	SOD87	1.5	1000*	1000	5.5	20	-	1.05	1	1107
BYD37D	SOD87	1.5	200	200	12	20	250	1.3	1	1115
BYD37G	SOD87	1.5	400	400	12	20	250	1.3	1	1115
BYD37J	SOD87	1.5	600	600	12	20	250	1.3	1	1115
BYD37K	SOD87	1.5	800	800	12	20	300	1.3	1	1115
BYD37M	SOD87	1.5	1000	1000	12	20	300	1.3	1	1115
BYD77A	SOD87	2.0	50	50	15	25	25	0.95	1	1121
BYD77B	SOD87	2.0	100	100	15	25	25	0.95	1	1121
BYD77C	SOD87	2.0	150	150	15	25	25	0.95	1	1121
BYD77D	SOD87	2.0	200	200	15	25	25	0.95	1	1121
BYD77E	SOD87	1.85	250	250	13	25	50	1.05	1	1121
BYD77F	SOD87	1.85	300	300	13	25	50	1.05	1	1121
BYD77G	SOD87	1.85	400	400	13	25	50	1.05	1	1121

Note

* V_{RRM}

TEMPERATURE SENSORS

TYPE NUMBER	TEMPERATURE RANGE °C	RESISTANCE R at T _{amb} (Ω) note 1	SENSOR CURRENT (mA)	PAGE
KTY85-110	-40 to 125	1000 ± 1%	1	1173
KTY85-120	-40 to 125	1000 ± 2%	1	1173
KTY85-150	-40 to 125	1000 ± 5%	1	1173

Note

1. T_{amb} = 25 °C.

Type number survey

Surface mounted semiconductors

Type number survey

In this alphanumeric list we present all surface mounted devices mentioned in this handbook.

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BA423L	SOD80	diode			89
BA682	SOD80	diode	BA482		91
BA683	SOD80	diode	BA483		91
BAS16	SOT23	diode	BAW62, 1N4148		93
BAS17	SOT23	diode	BA314		97
BAS19	SOT23	diode	BAV19		101
BAS20	SOT23	diode	BAV20		101
BAS21	SOT23	diode	BAV21		101
BAS28	SOT143	2 diodes	1N4148		109
BAS29	SOT23	diode	BAX12		113
BAS31	SOT23	2 diodes	BAX12		113
BAS32	SOD80	diode	1N4148		115
BAS32L	SOD80C	diode			123
BAS35	SOT23	2 diodes	BAX12		113
BAS56	SOT143	2 diodes	BAV10		131
BAS85	SOD80	diode			135
BAS86	SOD80	diode			139
BAT17	SOT23	diode	BA480		143
BAT18	SOT23	diode	BA482		147
BAT54	SOT23	diode	BAT85		151
BAT54A	SOT23	2 diodes	BAT85 (double)		155
BAT54C	SOT23	2 diodes	BAT85 (double)		155
BAT54S	SOT23	2 diodes	BAT85 (double)		155
BAT74	SOT143	2 diodes	BAT85		157
BAV23	SOT143	2 diodes	BAV21		161
BAV70	SOT23	2 diodes	BAW62, 1N4148 (double)		163
BAV74	SOT23	2 diodes			167
BAV99	SOT23	2 diodes	BAW62, 1N4148 (double)		171
BAV100	SOD80	diode	BAV10		175
BAV101	SOD80	diode	BAV19		175
BAV102	SOD80	diode	BAV20		175
BAV103	SOD80	diode	BAV21		175
BAV105	SOD80	diode	BAV10		183
BAW56	SOT23	diode	BAW62, 1N4148 (double)		191
BB215	SOD80	diode	BB405B		195
BB219	SOD80	diode	BB909		197

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BB240	SOD80	diode			199
BB241	SOD80	diode			201
BB249	SOD80	diode			203
BB804	SOT23	diode			207
BBY31	SOT23	diode	BB405		209
BBY39	SOT23	2 diodes			213
BBY40	SOT23	diode	BB809		215
BBY42	SOT23	diode			219
BBY62	SOT143	2 diodes			221
BC807	SOT23	pnp			223
BC807-16	SOT23	pnp	BC327-16	BC817-16	223
BC807-25	SOT23	pnp	BC327-25	BC817-25	223
BC807-40	SOT23	pnp	BC327-40	BC817-40	223
BC808	SOT23	pnp			223
BC808-16	SOT23	pnp	BC328-16	BC818-16	223
BC808-25	SOT23	pnp	BC328-25	BC818-25	223
BC808-40	SOT23	pnp	BC328-40	BC818-40	223
BC817	SOT23	npn			229
BC817-16	SOT23	npn	BC337-16	BC807-16	229
BC817-25	SOT23	npn	BC337-25	BC807-25	229
BC817-40	SOT23	npn	BC337-40	BC807-40	229
BC818	SOT23	npn			229
BC818-16	SOT23	npn	BC328-16	BC808-16	229
BC818-25	SOT23	npn	BC328-25	BC808-25	229
BC818-40	SOT23	npn	BC328-40	BC808-40	229
BC846	SOT23	npn			235
BC846A	SOT23	npn	BC546A	BC856A	235
BC846B	SOT23	npn	BC546B	BC856B	235
BC847	SOT23	npn			235
BC847A	SOT23	npn	BC547A, BC107A	BC857A	235
BC847B	SOT23	npn	BC547B, BC107B	BC857B	235
BC847C	SOT23	npn	BC547C	BC857C	235
BC848	SOT23	npn			235
BC848A	SOT23	npn	BC584A, BC108A	BC858A	235
BC848B	SOT23	npn	BC548B, BC108B	BC858B	235
BC848C	SOT23	npn	BC548C, BC108C	BC858C	235
BC849	SOT23	npn			245
BC849B	SOT23	npn	BC549B, BC109B	BC859B	245

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BC849C	SOT23	npn	BC549C, BC109C	BC859C	245
BC850	SOT23	npn			245
BC850B	SOT23	npn	BC550B, BCY59	BC860B	245
BC850C	SOT23	npn	BC550C, BCY59	BC860C	245
BC856	SOT23	pnp			257
BC856A	SOT23	pnp	BC556A	BC846A	257
BC856B	SOT23	pnp	BC556B	BC846C	257
BC857	SOT23	pnp			257
BC857A	SOT23	pnp	BC557A, BC177A	BC847A	257
BC857B	SOT23	pnp	BC557B, BC177B	BC847B	257
BC857C	SOT23	pnp	BC557C	BC847C	257
BC858	SOT23	pnp			257
BC858A	SOT23	pnp	BC558A, BC178A	BC848A	257
BC858B	SOT23	pnp	BC558B, BC158B	BC848B	257
BC858C	SOT23	pnp	BC558C	BC848C	257
BC859	SOT23	pnp			265
BC859A	SOT23	pnp	BC559A, BC179A, BCY78		265
BC859B	SOT23	pnp	BC559B, BCY79	BC849B	265
BC859C	SOT23	pnp	BC559C, BCY79	BC849C	265
BC860	SOT23	pnp			265
BC860A	SOT23	pnp	BC560A, BCY79		265
BC860B	SOT23	pnp	BC560B, BCY79	BC850B	265
BC860C	SOT23	pnp	BC560C, BCY79	BC850C	265
BC868	SOT89	npn	BC368, BD329	BC869	275
BC868-10	SOT89	npn			275
BC868-16	SOT89	npn			275
BC868-25	SOT89	npn			275
BC869	SOT89	pnp	BC369, BD330	BC868	281
BC869-10	SOT89	pnp			281
BC869-16	SOT89	pnp			281
BC869-25	SOT89	pnp			281
BCF29	SOT23	pnp	BC559A, BCY78, BC179		287
BCF30	SOT23	pnp	BC559B, BCY78	BCF32	287
BCF32	SOT23	npn	BC549B, BCY58, BC109	BCF30	293
BCF33	SOT23	npn	BC549C, BCY58		293
BCF70	SOT23	pnp	BC560B, BCY79		299
BCF81	SOT23	npn	BC550C		305
BCP51	SOT223	pnp		BCP54	307

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BCP51-10	SOT223	pnP		BCP54-10	307
BCP51-16	SOT223	pnP		BCP54-16	307
BCP52	SOT223	pnP		BCP55	307
BCP52-10	SOT223	pnP		BCP55-10	307
BCP52-16	SOT223	pnP		BCP55-16	307
BCP53	SOT223	pnP		BCP56	307
BCP53-10	SOT223	pnP		BCP56-10	307
BCP53-16	SOT223	pnP		BCP56-16	307
BCP54	SOT223	npn		BCP51	311
BCP54-10	SOT223	npn		BCP51-10	311
BCP54-16	SOT223	npn		BCP51-16	311
BCP55	SOT223	npn		BCP52	311
BCP55-10	SOT223	npn		BCP52-10	311
BCP55-16	SOT223	npn		BCP52-16	311
BCP56	SOT223	npn		BCP53	311
BCP56-10	SOT223	npn		BCP53-10	311
BCP56-16	SOT223	npn		BCP53-16	311
BCP68	SOT223	npn			315
BCP69	SOT223	pnP			321
BCV26	SOT23	pnP	BC516	BCV27	327
BCV27	SOT23	npn	BC517	BCV26	329
BCV28	SOT89	pnP		BCV29	331
BCV29	SOT89	npn		BCV28	333
BCV46	SOT23	pnP		BCV47	327
BCV47	SOT23	npn		BCV46	329
BCV48	SOT89	pnP		BCV49	331
BCV49	SOT89	npn		BVC48	333
BCV61	SOT143	npn		BCV62	335
BCV61A	SOT143	npn			335
BCV61B	SOT143	npn			335
BCV61C	SOT143	npn			335
BCV62	SOT143	pnP	BC557	BCV61	339
BCV62A	SOT143	pnP			339
BCV62B	SOT143	pnP			339
BCV62C	SOT143	pnP			339
BCV63	SOT143	npn		BCV64	343
BCV63B	SOT143	npn			343
BCV64	SOT143	pnP		BCV63	347

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BCV64B	SOT143	pn-p			347
BCV65	SOT143	pn-p			351
BCV65B	SOT143	npn			351
BCV71	SOT23	npn	BC546A	BCW89	353
BCV72	SOT23	npn	BC546B		353
BCW29	SOT23	pn-p	BC178A, BC558A	BCW31	355
BCW30	SOT23	pn-p	BC178B, BC558B	BCW32	355
BCW31	SOT23	npn	BC108A, BC548A	BCW29	361
BCW32	SOT23	npn	BC108B, BC548B	BCW30	361
BCW33	SOT23	npn	BC108C, BC548C		361
BCW60A	SOT23	npn	BC548A	BCW61A	367
BCW60B	SOT23	npn	BC548B	BCW61B	367
BCW60C	SOT23	npn	BC548B	BCW61C	367
BCW60D	SOT23	npn	BC548C	BCW61D	367
BCW61A	SOT23	pn-p	BC558A	BCW60A	371
BCW61B	SOT23	pn-p	BC558B	BCW60B	371
BCW61C	SOT23	pn-p	BC558B	BCW60C	371
BCW61D	SOT23	pn-p	BC558C	BCW60D	371
BCW69	SOT23	pn-p	BC557A	BCW71	375
BCW70	SOT23	pn-p	BC557B	BCW72	375
BCW71	SOT23	npn	BC547A	BCW69	381
BCW72	SOT23	npn	BC547B	BCW70	381
BCW81	SOT23	npn	BC547C		387
BCW89	SOT23	pn-p	BC556A	BCV71	389
BCX17	SOT23	pn-p	BC327	BCX19	391
BCX18	SOT23	pn-p	BC328	BCX20	391
BCX19	SOT23	npn	BC337	BCX17	395
BCX20	SOT23	npn	BC338	BCX18	395
BCX51	SOT89	pn-p	BC636, BD136	BCX54	399
BCX51-10	SOT89	pn-p		BCX54-10	399
BCX51-16	SOT89	pn-p		BCX54-16	399
BCX52	SOT89	pn-p	BC638, BD138	BCX55	399
BCX52-10	SOT89	pn-p		BCX55-10	399
BCX52-16	SOT89	pn-p		BCX55-16	399
BCX53	SOT89	pn-p	BC640, BD140	BCX56	399
BCX53-10	SOT89	pn-p		BXC56-10	399
BCX53-16	SOT89	pn-p		BCX56-16	399
BCX54	SOT89	npn	BC635, BD135	BCX51	403

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BCX54-10	SOT89	npn	BC637, BD137	BCX51-10	403
BCX54-16	SOT89	npn		BCX51-16	403
BCX55	SOT89	npn		BCX52	403
BCX55-10	SOT89	npn		BCX52-10	403
BCX55-16	SOT89	npn		BCX52-16	403
BCX56	SOT89	npn		BCX53	403
BCX56-10	SOT89	npn	BC639, BD139	BCX53-10	403
BCX56-16	SOT89	npn		BCX53-16	403
BCX70G	SOT23	npn		BCX71G	407
BCX70H	SOT23	npn		BCX71H	407
BCX70J	SOT23	npn		BCX71J	407
BCX70K	SOT23	npn		BCX71K	407
BCX71G	SOT23	pnp	BC107A, BC547A BC107B, BC547B BC107B, BC547B BC107C, BC547C BC177A, BC557A BC177B, BC557B BC177B, BC557B BC557C	BCX70G	411
BCX71H	SOT23	pnp		BCX70H	411
BCX71J	SOT23	pnp		BCX70J	411
BCX71K	SOT23	pnp		BCX70K	411
BDS60	SOT223	pnp		BDS61	415
BDS60A	SOT223	pnp		BDS61A	415
BDS60B	SOT223	pnp		BDS61B	415
BDS60C	SOT223	pnp		BDS61C	415
BDS61	SOT223	npn		BDS60	421
BDS61A	SOT223	npn		BDS60A	421
BDS61B	SOT223	npn		BDS60B	421
BDS61C	SOT223	npn		BDS60C	421
BDS77	SOT223	npn		BDS78	427
BDS78	SOT223	pnp		BDS77	433
BDS201	SOT223	npn		BDS202	427
BDS202	SOT223	pnp		BDS201	433
BDS203	SOT223	npn		BDS204	427
BDS204	SOT223	pnp		BDS203	433
BDS643	SOT223	npn		BDS644	439
BDS644	SOT223	pnp		BDS643	445
BDS645	SOT223	npn		BDS646	439
BDS646	SOT223	pnp		BDS645	445
BDS647	SOT223	npn		BDS648	439
BDS648	SOT223	pnp		BDS647	445
BDS649	SOT223	npn		BDS650	439
BDS650	SOT223	pnp		BDS649	445

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BDS651	SOT223	nnp		BDS652	439
BDS652	SOT223	pnp		BDS651	445
BDS933	SOT223	nnp		BDS934	451
BDS934	SOT223	pnp		BDS933	457
BDS935	SOT223	nnp		BDS936	451
BDS936	SOT223	pnp		BDS935	457
BDS937	SOT223	nnp		BDS938	451
BDS938	SOT223	pnp		BDS937	457
BDS939	SOT223	nnp		BDS940	451
BDS940	SOT223	pnp		BDS939	457
BDS941	SOT223	nnp		BDS942	451
BDS942	SOT223	pnp		BDS941	457
BDS943	SOT223	nnp		BDS944	463
BDS944	SOT223	pnp		BDS943	469
BDS945	SOT223	nnp		BDS946	463
BDS946	SOT223	pnp		BDS945	469
BDS947	SOT223	nnp		BDS948	463
BDS948	SOT223	pnp		BDS947	469
BDS949	SOT223	nnp		BDS950	475
BDS950	SOT223	pnp		BDS949	481
BDS951	SOT223	nnp		BDS952	475
BDS952	SOT223	pnp		BDS951	481
BDS953	SOT223	nnp		BDS954	475
BDS954	SOT223	pnp		BDS953	481
BDS955	SOT223	nnp		BDS956	475
BDS956	SOT223	pnp		BDS955	481
BF510	SOT23	FET	BF410A		487
BF511	SOT23	FET	BF410B		487
BF512	SOT23	FET	BF410C		487
BF513	SOT23	FET	BF410D		487
BF550	SOT23	pnp	BF450		493
BF569	SOT23	pnp	BF970		495
BF570	SOT23	nnp	BF370		497
BF579	SOT23	pnp	BF979		501
BF620	SOT89	nnp	BF420, BF471, BF871	BF621	505
BF621	SOT89	pnp	BF421, BF472, BF872	BF620	509
BF622	SOT89	nnp	BF422, BF469, BF869	BF623	505
BF623	SOT89	pnp	BF423, BF470, BF870	BF622	509

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BF660	SOT23	pn-p	BF606A		513
BF720	SOT223	npn			515
BF721	SOT223	pn-p			519
BF722	SOT223	npn			515
BF723	SOT223	pn-p			519
BF747	SOT23	npn			523
BF820	SOT23	npn	BF420	BF821	535
BF821	SOT23	pn-p	BF421	BF820	539
BF822	SOT23	npn	BF422	BF823	535
BF823	SOT23	pn-p	BF423	BF822	539
BF824	SOT23	pn-p	BF324		543
BF840	SOT23	npn	BF240		549
BF841	SOT23	npn	BF241		549
BF989	SOT143	FET	BF960		551
BF990A	SOT143	FET	BF980A		555
BF991	SOT143	FET	BF981		559
BF992	SOT143	FET	BF982		563
BF994S	SOT143	FET	BF964S		569
BF996S	SOT143	FET	BF966S		573
BF997	SOT143	FET	BF965		577
BF998	SOT143	FET			581
BFG16A	SOT223	npn			591
BFG17A	SOT143	npn			599
BFG25AX	SOT143	npn			607
BFG31	SOT223	pn-p			611
BFG33	SOT143	npn			617
BFG33X	SOT143	npn			617
BFG35	SOT223	npn	BFQ34T, BFG34	BFG55	619
BFG55	SOT223	pn-p		BFG35	631
BFG67	SOT143	npn	BFG65		637
BFG67X	SOT143	npn			637
BFG92A	SOT143	npn			641
BFG92AX	SOT143	npn			641
BFG93A	SOT143	npn			647
BFG93AX	SOT143	npn			647
BFG94	SOT223	npn			653
BFG97	SOT223	npn	BFR96		665
BFG135	SOT223	npn	BFQ135		675

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BFG197	SOT143	npn			687
BFG197X	SOT143	npn			687
BFG198	SOT223	npn	BFG195		721
BFQ17	SOT89	npn	BFW16A		731
BFQ18A	SOT89	npn	BFQ34		737
BFQ19	SOT89	npn	BFR96		741
BFQ67	SOT23	npn	BFQ65		747
BFQ149	SOT89	pnp			751
BFR30	SOT23	FET	BFW11, BF245		757
BFR31	SOT23	FET	BFW12, BF245		757
BFR53	SOT23	npn	BFW30, BFW93		767
BFR92	SOT23	npn	BFR90	BFT92	775
BFR92A	SOT23	npn	BFR90		783
BFR93	SOT23	npn	BFR91	BFT93	795
BFR93A	SOT23	npn	BFR91		803
BFR101A	SOT143	FET			815
BFR101B	SOT143	FET			815
BFR106	SOT23	npn			817
BFR200	SOT143	FET			823
BFS17	SOT23	npn	BFY90, BFW92		827
BFS17A	SOT23	npn			833
BFS18	SOT23	npn	BF495		839
BFS19	SOT23	npn	BF494		839
BFS20	SOT23	npn	BF199		845
BFT25	SOT23	npn	BFT24		851
BFT25A	SOT23	npn			859
BFT46	SOT23	FET	BFW13, BF245		861
BFT92	SOT23	pnp	BFQ51; 52	BFR92	869
BFT93	SOT23	pnp	BFQ23; 24	BFR93	875
BRY61	SOT23	Pnpn	BRY56, BRY39		881
BRY62	SOT89	Pnpn	BRY39		887
BSD22	SOT89	FET			893
BSP15	SOT223	pnp	BSP19		897
BSP16	SOT223	pnp	BSP20		897
BSP19	SOT223	npn	BSP15		899
BSP20	SOT223	npn	BSP16		899
BSP30	SOT223	pnp			901
BSP31	SOT223	pnp			901

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BSP32	SOT223	pn-p	BSP60 BSP61 BSP62	BSP50 BSP51 BSP52	901
BSP33	SOT223	pn-p			901
BSP40	SOT223	npn			905
BSP41	SOT223	npn			905
BSP42	SOT223	npn			905
BSP43	SOT223	npn			905
BSP50	SOT223	npn			909
BSP51	SOT223	npn			909
BSP52	SOT223	npn			909
BSP60	SOT223	pn-p			913
BSP61	SOT223	pn-p			913
BSP62	SOT223	pn-p			913
BSP103	SOT223	FET			917
BSP105	SOT223	FET			917
BSP106	SOT223	FET			921
BSP107	SOT223	FET			929
BSP108	SOT223	FET			937
BSP109	SOT223	FET			917
BSP110	SOT223	FET			941
BSP120	SOT223	FET			945
BSP121	SOT223	FET			949
BSP126	SOT223	FET			955
BSP205	SOT223	FET	2N2894A 2N2222, PH2222 2N2222A, PH2222A 2N2907, PH2907 2N2907A, PH2907A 2N3904 2N3906 2N5550 2N5551 2N5400 2N5401 2N4030	BSV52 BSR15 BSR16 BSR13 BSR14 BSR18A BSR17A BSR20 BSR20A BSR19 BSR19A BSR40	961
BSP206	SOT223	FET			965
BSP220	SOT223	FET			969
BSP225	SOT223	FET			977
BSR12	SOT23	pn-p			985
BSR13	SOT23	npn			991
BSR14	SOT23	npn			991
BSR15	SOT23	pn-p			995
BSR16	SOT23	pn-p			995
BSR17A	SOT23	npn			999
BSR18A	SOT23	pn-p			1003
BSR19	SOT23	npn			1007
BSR19A	SOT23	npn			1007
BSR20	SOT23	pn-p			1011
BSR20A	SOT23	pn-p			1011
BSR30	SOT89	pn-p			1015

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BSR31	SOT89	pn-p	2N4032	BSR41	1015
BSR32	SOT89	pn-p	2N4031	BSR42	1015
BSR33	SOT89	pn-p	2N4033	BSR43	1015
BSR40	SOT89	npn	BSX466	BSR30	1019
BSR41	SOT89	npn	BSX4616	BSR31	1019
BSR42	SOT89	pn-p	2N3020	BSR32	1019
BSR43	SOT89	npn	2N3019	BSR33	1019
BSR56	SOT23	FET	2N4856		1023
BSR57	SOT23	FET	2N4857		1023
BSR58	SOT23	FET	2N4858		1023
BSS63	SOT23	pn-p	BSS68	BSS64	1027
BSS64	SOT23	npn	BSS38	BSS33	1033
BSS83	SOT143	FET			1037
BSS84	SOT23	FET			1041
BSS87	SOT89	FET			1045
BSS131	SOT23	FET			1049
BSS192	SOT89	FET			1053
BST15	SOT89	pn-p	2N5415	BST40	1059
BST16	SOT89	pn-p	2N5416	BST39	1059
BST39	SOT89	npn	2N3439	BST16	1063
BST40	SOT89	npn	2N3440	BST15	1063
BST50	SOT89	npn	BSR50, BSS50, BDX42		1067
BST51	SOT89	npn	BSR51, BSS51, BDX43		1067
BST52	SOT89	npn	BSR52, BSS52, BDX44		1067
BST60	SOT89	pn-p	BSR60, BSS60, BDX45		1071
BST61	SOT89	pn-p	BSR61, BSS61, BDX46		1071
BST62	SOT89	pn-p	BSR62, BSS62, BDX47		1071
BST80	SOT89	FET	BST70A		1075
BST82	SOT23	FET	BST72A		1079
BST84	SOT89	FET	BST74A		1083
BST86	SOT89	FET	BST76A		1087
BST120	SOT89	FET			1091
BST122	SOT89	FET			1095
BSV52	SOT23	npn	PH2369, BSX20	BSR12	1099
BYD17D	SOD87	diode	BYD13D		1107
BYD17G	SOD87	diode	BYD13G	BYD17J	1107
BYD17J	SOD87	diode	BYD13J		1107
BYD17K	SOD87	diode	BYD13K		1107

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
BYD17M	SOD87	diode	BYD13M		1107
BYD37D	SOD87	diode	BYD33D		1115
BYD37G	SOD87	diode	BYD33G		1115
BYD37J	SOD87	diode	BYD33J		1115
BYD37K	SOD87	diode	BYD33K		1115
BYD37M	SOD87	diode	BYD33M		1115
BYD77A	SOD87	diode	BYD73A		1121
BYD77B	SOD87	diode	BYD73B		1121
BYD77C	SOD87	diode	BYD73C		1121
BYD77D	SOD87	diode	BYD73D		1121
BYD77E	SOD87	diode	BYD73E		1121
BYD77F	SOD87	diode	BYD73F		1121
BYD77G	SOD87	diode	BYD73G		1121
BZD27	SOD87	diode			1125
BZV49	SOT89	diode	BZV85		1131
BZV55	SOD80	diode	BZX79, BZX55		1141
BZV80	SOD80	diode			1155
BZV81	SOD81	diode			1155
BZV87	SOD80	diode			1157
BZX84	SOT23	diode	BZX79, BZX55		1161
KTY85-110	SOD80	sensor			1173
KTY85-120	SOD80	sensor			1173
KTY85-150	SOD80	sensor			1173
PMBD914	SOT23	diode			1179
PMBD6050	SOT23	diode			1183
PMBD7000	SOT23	diode			1187
PMBF170	SOT23	FET			1191
PMBF4391	SOT23	FET	2N4391		1195
PMBF4392	SOT23	FET	2N4392		1195
PMBF4393	SOT23	FET	2N4393		1195
PMBFJ108	SOT23	FET			1199
PMBFJ109	SOT23	FET			1199
PMBFJ110	SOT23	FET			1199
PMBFJ111	SOT23	FET			1205
PMBFJ112	SOT23	FET			1205
PMBFJ113	SOT23	FET			1205
PMBFJ174	SOT23	FET			1211
PMBFJ175	SOT23	FET			1211

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
PMBFJ176	SOT23	FET			1211
PMBFJ177	SOT23	FET			1211
PMBT2222	SOT23	npn	2N2222, PM2222	PMBT2907	1215
PMBT2222A	SOT23	npn	2N2222A, PM2222A	PMBT2907A	1215
PMBT2369	SOT23	npn			1219
PMBT2907	SOT23	pnp	2N2907, PM2907	PMBT2222	1221
PMBT2907A	SOT23	pnp	2N2907A, PM2907A	PMBT2222A	1221
PMBT3904	SOT23	npn	2N3904	PMBT3906	1225
PMBT3906	SOT23	pnp	2N3906	PMBT3904	1229
PMBT4401	SOT23	npn			1233
PMBT4403	SOT23	pnp			1237
PMBT5088	SOT23	npn			1241
PMBT5401	SOT23	pnp			1245
PMBT5550	SOT23	npn			1247
PMBT5551	SOT23	npn			1249
PMBT6428	SOT23	npn	2N6428		1251
PMBT6429	SOT23	npn	2N6429		1251
PMBTA05	SOT23	npn	MPSA05	PMBTA55	1255
PMBTA06	SOT23	npn	MPSA06	PMBTA56	1255
PMBTA13	SOT23	npn	MPSA13	PMBTA63	1257
PMBTA14	SOT23	npn	MPSA14	PMBTA64	1257
PMBTA42	SOT23	npn	MPSA42	PMBTA94	1259
PMBTA43	SOT23	npn	MPSA43	PMBTA93	1259
PMBTA55	SOT23	npn	MPSA55	PMBTA05	1263
PMBTA56	SOT23	npn	MPSA56	PMBTA06	1263
PMBTA63	SOT23	pnp	MPSA63	PMBTA13	1265
PMBTA64	SOT23	pnp	MPSA63	PMBTA14	1265
PMBTA92	SOT23	pnp	MPSA92	PMBTA42	1267
PMBTA93	SOT23	pnp	MPSA93	PMBTA43	1267
PMBZ5226B -PMBZ5257B	SOT23	diode			1269
PMLL4148	SOD80	diode			1273
PMLL4446	SOD80	diode			1273
PMLL4448	SOD80	diode			1273
PMLL4150	SOD80	diode			1277
PMLL4151	SOD80	diode			1277
PMLL4153	SOD80	diode			1277
PMLL5225B -PMLL5267B	SOD80	diode	1N5225B -1N5267B		1281

Surface mounted semiconductors

Type number survey

TYPE NUMBER	PACKAGE	DEVICE TYPE	NEAREST CONVENTIONAL TYPE(S)	COMPLEMENT	PAGE
PRLL4001	SOD87	diode	2N3904 2N3906		1285
PRLL4002	SOD87	diode			1285
PRLL5817	SOD87	diode			1289
PRLL5818	SOD87	diode			1289
PRLL5819	SOD87	diode			1289
PXT2222	SOT89	npn		PXT2907	1297
PXT2222A	SOT89	npn		PXT2907A	1297
PXT2907	SOT89	pnP		PXT2222	1301
PXT2907A	SOT89	pnP		PXT2222A	1301
PXT3904	SOT89	npn		PXT3906	1305
PXT3906	SOT89	pnP		PXT3904	1309
PXT4401	SOT89	npn		PXT4403	1313
PXT4403	SOT89	pnP		PXT4401	1317
PXTA14	SOT89	npn		PXTA64	1321
PXTA27	SOT89	npn		PXTA77	1323
PXTA64	SOT89	pnP		PXTA14	1325
PXTA77	SOT89	pnP		PXTA27	1327
PXTA92	SOT89	pnP			1329
PXTA93	SOT89	pnP			1329
PZT2222	SOT223	npn		PZT2907	1331
PZT2222A	SOT223	npn		PZT2907A	1331
PZT2907	SOT223	pnP		PZT2222	1335
PZT2907A	SOT223	pnP		PZT222A	1335
PZT3904	SOT223	npn			1339
PZT3906	SOT223	pnP			1343
PZTA05	SOT223	npn			1347
PZTA06	SOT223	npn			1347
PZTA13	SOT223	npn		PZTA63	1351
PZTA14	SOT223	pnP		PZTA64	1351
PZTA42	SOT223	npn			1353
PZTA43	SOT223	npn			1353
PZTA55	SOT223	pnP			1357
PZTA56	SOT223	pnP			1357
PZTA63	SOT223	pnP		PZTA13	1361
PZTA64	SOT223	pnP		PZTA14	1361
PZTA92	SOT223	pnP			1363
PZTA93	SOT223	pnP			1363
2N7002	SOT23	FET			1365

Conversion list

CONVERSION LIST

(conventional type number to SMD type number)

conven. ¹	micro. ²	conven. ¹	micro. ²	conven. ¹	micro. ²
BA243	BAT18	BC177	BC857	BC546B	BC846B
BA314	BAS17		BCW69/70		BCV72
BA480	BAT17	BC177A	BC857A	BC547	BC847
BA481	BAT17		BCW69		BCW71/72/81
BA482	BA682	BC177B	BC857B	BC547A	BC847A
BA483	BA683		BCW70		BCW71
BAT85	BAT54	BC178	BC858	BC547B	BC847B
	BAT74		BCW29/30		BCW72
BAV10	BAS56	BC178A	BC858A	BC547C	BC847C
BAV18	BAV100		BCW29		BCW81
BAV19	BAS19	BC178B	BC858B	BC548	BC848
	BAV101		BCW30		BCW31-33
BAV20	BAS20	BC179	BC859	BC548A	BC848A
	BAV102		BCF29/30		BCW31
BAV21	BAS21	BC179A	BC859A	BC548B	BC848B
BAW62	BAS16		BCF29		BCW32
	BAS28	BC179B	BC859B	BC548C	BC848C
	BAS32		BCF30		BCW33
	BAV70	BC200/01	BC859B	BC549	BC849
	BAV99		BCF29		BCF32-33
	BAW56	BC200/02	BC859B/C	BC549B	BC849B
BAX12	BAS29		BCF29/30		BCF32
	BAS31	BC200/03	BC859C	BC549C	BC849C
	BAS35		BCF30		BCF33
BB405	BBY31	BC327	BC807	BC550	BC850
BB809	BBY40		BCX17		BCF81
BC107	BC847	BC327-16	BC807-16	BC550B	BC850B
	BCW71/72	BC327-25	BC807-25	BC550C	BC850C
BC107A	BC847A	BC327-40	BC807-40	BC556	BC856
	BCW71	BC327A			BCW89
BC107B	BC847B	BC328	BC808	BC556A	BC856A
	BCW72	BC328-16	BC808-16		BCW89
BC108	BC848	BC328-25	BC808-25	BC556B	BC856B
	BCW31-33	BC328-40	BC808-40	BC557	BC857
BC108A	BC848A	BC337	BC817		BCW69/70
	BCW31		BCX19	BC557A	BC857A
BC108B	BC848B	BC337-16	BC817-16		BCW69
	BCW32	BC337-25	BC817-25	BC557B	BC857B
BC109	BC849	BC337-40	BC817-40		BCW70
	BCF32/33	BC338	BC818	BC557C	BC857C
BC109B	BC849B		BCX20	BC558	BC858
	BCF32	BC338-16	BC818-16		BCW29/30
BC109C	BC849C	BC338-25	BC818-25	BC558A	BC858A
	BCFC33	BC338-40	BC818-40		BCW29
BC146/01	BC849B	BC368	BC868	BC558B	BC858B
	BCF32	BC369	BC869		BCW30
BC146/02	BC849B/C	BC516	BCV26	BC558C	BC858C
	BCF32/33	BC517	BCV27	BC559	BC859
BC146/03	BC849C	BC546	BC846		BCF29/30
	BCF33		BCV71/72	BC559A	BC859A
BC156	BCV26	BC546A	BC846A		BCF29
BC157	BCV27		BCV71		

¹ = conventional type

² = microminiature type

CONVERSION LIST

conven. ¹	micro. ²	conven. ¹	micro. ²	conven. ¹	micro. ²
BC559B	BC859B	BCY57	BC849	BD136	BCX51
	BCF30		BCF32/33		BCP54
BC559C	BC859C	BCY58	BC849	BD136-10	BCX51-10
BC560	BC860		BCW60 fam.		BCP51-10
	BCF70	BCY58-VII	BCW60A	BD136-16	BCX51-16
BC560A	BC860A	BCY58-VIII	BC849B		BCP51-16
BC560B	BC860B		BCW60B	BD137	BCX55
	BCF70	BCY58-IX	BC849B		BCP55
BC560C	BC860C		BCW60C	BD137-10	BCX55-10
BC635	BCX54	BCY58-X	BC849C		BCP55-10
	BCP54		BCW60D	BD137-16	BCX55-16
BC635-10	BCX54-10	BCY59	BC850		BCP55-16
	BCP54-10		BCX70 fam.	BD138	BCX52
BC635-16	BCX54-16	BCY59-VII	BCX70G		BCP52
	BCP54-16	BCY59-VIII	BC850B	BD138-10	BCX52-10
BC636	BCX51		BCX70H		BCP52-10
	BCP51	BCY59-IX	BC850B	BD138-16	BCX52-16
BC636-10	BCX51-10		BCX70J		BCP52-16
	BCP51-10	BCY59-X	BC850C	BD139	BCX56
BC636-16	BCX51-16		BCX70K		BCP56
	BCP51-16	BCY65	BCV71	BD139-10	BCX56-10
BC637	BCX55		BCV72		BCP56-10
	BCP55	BCY70	BC860	BD139-16	BCX56-16
BC637-10	BCX55-10		BCF70		BCP56-16
	BCP55-10	BCY71	BC860	BD140	BCX53
BC637-16	BCX55-16		BCF70		BCP53
	BCP55-16	BCY72	BC859	BD140-10	BCX53-10
BC638	BCX52		BCF29/30		BCP53-10
	BCP52	BCY78	BC859	BD140-16	BCX53-16
BC638-10	BCX52-10		BCW61 fam.		BCP53-16
	BCP52-10	BCY78-VII	BC859A	BDX42	BST50
BC638-16	BCX52-16		BCW61A		BSP50
	BCP52-16	BCY78-VIII	BCY859A/B	BDX43	BST51
BC639	BCX56		BCW61B		BSP51
	BCP56	BCY78-IX	BC859B	BDX44	BST52
BC639-10	BCX56-10		BCW61C		BSP52
	BCP56-10	BCY78-X	BV859C	BDX45	BST60
BC639-16	BCX56-16		BCW61D		BSP60
	BCP56-16	BCY79	BC860	BDX46	BST61
BC640	BCX53		BCX71 fam.		BSP61
	BCP53	BCY79-VII	BC860A	BDX47	BST61
BC640-10	BCX53-10		BCX71G		BSP61
	BCP53-10	BCY79-VIII	BC860A/B	BF199	BFS20
BC640-16	BCX53-16		BCX71H	BF240	BF840
	BCP53-16	BCY79-IX	BC860B	BF241	BF841
BCX58	BCW60		BCX71J	BF324	BF824
BCX59	BCX70	BD135	BCX54	BF370	BSV52
BCX78	BCW61		BCP54		BF570
BCX79	BCX71	BD135-10	BCX54-10	BF410A	BF510
BCY56	BC850B		BCP54-10	BF410B	BF511
	BCF70	BD135-16	BCX54-16	BF410C	BF512
			BCP54-16	BF410D	BF513

¹ = conventional type

² = microminiature type

CONVERSION LIST

conven. ¹	micro. ²	conven. ¹	micro. ²	conven. ¹	micro. ²
BF419	BST40	BF970	BF569	BFY55	BSR40
BF420	BF620	BF970A	BF569		BSP40
	BF720	BF979	BF579	BFY90	BFS17
	BF820	BF980	BF990	BR101	BRV62
BF421	BF621	BF981	BF991	BRV39	BRV62
	BF721	BF982	BF992	BRV56	BRV61
	BF821	BFQ65	BFQ67	BSR50	BST50
BF422	BF622	BFQ23	BFT93		BSP50
	BF722	BFQ24	BFT93	BSR51	BST51
	BF822	BFQ34	BFQ18A		BSP51
BF423	BF623		BF935	BSR52	BST52
	BF723	BFQ34T	BFQ18A		BSP52
	BF823		BF935	BSR60	BST60
BF450	BF550	BFQ51	BFT92		BSP60
BF457	BST40	BFQ52	BFT92	BSR61	BST61
BF458	BST40	BFQ65	BFQ67		BSP61
BF459	BST39	BFR54	BSV52	BSR62	BST62
BF469	BF622	BFR90	BFR92A		BSP62
	BF722	BFR91	BFR93A	BSS38	BSS64
BF470	BF623	BFR96	BFQ19	BSS50	BST50
	BF723		BF927		BSP50
BF471	BF620	BFR96S	BFQ19	BSS51	BST51
	BF720		BF927		BSP51
BF472	BF621	BFT24	BFT25	BSS52	BST52
	BF721	BFT44	BST16		BSP52
			BSP16	BSS60	BST60
BF483	BF720		BST15/16		BSP60
BF484	BF723	BFT45	BSP15/16	BSS61	BST61
BF486	BF721				BSP61
BF494	BFS19	BFW11	BFR30	BSS62	BST62
BF494B	BFS19	BFW12	BFR31		BSP62
BF495	BFS18	BFW13	BFT46	BSS68	BSS63
BF459C	BFS18	BFW16A	BFQ17	BSV15	BSR30/31
BF459D	BFS18	BFW30	BFR53		BSP30/31
BF606A	BF660	BFW92	BFS17	BSV15-6	BSR30
BF819	BST40	BFW93	BFR53		BSP30
	BSP20	BFX29	BSR16	BSV15-10	BSR30/31
BF857	BST40	BFX30	BSR16		BSP30/31
	BSP20	BFX84	BSR40	BSV15-16	BSR31
BF858	BST40		BSP40		BSP31
	BSP20	BFX85	BSR41	BSV16	BSR30/31
BF859	BST39		BSP41		BSP30/31
BF869	BF622	BFX86	BSR41	BSV16-6	BSR30
	BF722		BSP41		BSP30
BF870	BF623	BFX87	BSR16	BSV16-10	BSR30/31
	BF723	BFX88	BSR15		BSP30/31
BF871	BF620	BFY50	BSR40	BSV16-16	BSR31
	BF720		BSP40		BSP31
BF872	BF621	BFY51	BSR40	BSV17	BSR32/33
	BF721		BSP40		BSP32/33
BF926	BF660	BFY52	BSR40	BSV17-6	BSR32
BF960	BF989		BSP40		BSP32
BF964	BF994				
	BF994S				
BF966	BF996				
	BF996S				

¹ = conventional type
² = microminiature type

CONVERSION LIST

conven. ¹	micro. ²	conven. ¹	micro. ²	conven. ¹	micro. ²
BSV17-10	BSR32/33 BSP32/33	PH2907A PN2222	BSR16 PMBT2222	2N3019 2N3020	BSR43 BSR42
BSX20	BSV52		BSR13	2N3053	BSR40/41
BSX45	BSR40/41 BSP40/41	PN2222A	PMBT 2222A BSR14	2N3904	BSR17A PMBT3904
BSX45-6	BSR40 BSP40	PN2369	PMBT 2369 BSV52	2N3906	BSR18A PMBT3906
BSX45-10	BSR40/41 BSP40/41	PN2369A PN2907	PMBT 2369A PMBT2907	2N4030 2N4031	BSR30 BSR32
BSX45-16	BSR41 BSP41	PM2907A	BSR15 PMBT2907A	2N4032 2N4033	BSR31 BSR33
BSX46	BSR40/41 BSP40/41		BSR16 BST39	2N4124 2N4400	BSR18 A PMBT4400
BSX46-6	BSR40 BSP40	PN3439 PN3440	BSP19 BST40	2N4401 2N4402	PMBT4401 PMBT4402
BSX46-10	BSR40/41		BSP20	2N4403	PMBT4403
BSX46-16	BSR41	PN5415	BST15	2N4856	BSR56
BSX47	BSR42/43		BSP15	2N4857	BSR57
BSX47-6	BSR42	PN5416	BST16	2N4858	BSR58
BSX47-10	BSR42-43		BSP16	2N5086	PMBT5086
BSY95A	BSV52	1N4148	BAS16	2N5087	PMBT5087
BZX55	BZX84		BAV90	2N5088	PMBT5088
BZX79	BZX84 BZV55		BAV99 BAW56	2N5415 2N5416	BST15 BST16
BZV85	BZV49	1N5225B	PMLL5225B	2N6428	PMBT6428
MPS6513	BC848A	to	to	2N6429	PMBT6429
MPS6514	BC848A	1N5267B	PMLL5267B		
MPS6515	BC848B	2N894A	BSR12		
MPS6517	BC858A	2N929	BC850		
MPS6518	BC858A	2N930	BNC850		
MPS6519	BC858B		BCF81		
MPS6520	BC859B	2N1613	BDSR40		
MPS6521	BC859C	2N1711	BSR41		
MPS6522	BC859B	2N1893	BSR42		
MPS6523	BC859C	2N2219	BSR13		
MPSA05	PMBTA05	2N2219A	BSR14		
MPSA06	PMBTA06	2N2222	BSR13		
MPSA13	PMBTA13		PMBT2222		
MPSA14	PMBTA14	2N2222A	BSR14		
MPSA42	PMBTA42		PMBT2222A		
MPSA43	PMBTA43	2N2297	BSR40		
MPSA55	PMBTA55	2N2368	BSV52		
MPSA56	PMBTA56	2N2369	BSV52		
MPSA63	PMBTA63	2N2369A	BSV52		
MPSA64	PMPTA64	2N2483	BC850B		
MPSA92	PMBTA92	2N2484	BC850B/C		
MPSA93	PMBTA93	2N2905	BSR15		
PH2222	BSR13	2N2905A	BSR16		
PH2222A	BSR14	2N2907	BSR15		
PH2369	BSV52		PMBT2907		
PH2907	BSR15	2N2907A	BSR16		
			PMBT2907A		

¹ = conventional type

² = microminiature type

Marking list

Surface mounted semiconductors

Marking

MARKING LIST

Types in SOT23, SOT89 and SOT143 envelopes are marked with a code as listed in the following

tables. The actual type number and data code are on the packing.

An exception to this is the BZV49 series. The envelope number is

shown in those cases where the same marking code applies to more than one type number.

MARK	TYPE NO.
A1p	BAW56
A2p	BAT18
A3p	BAT17
A4p	BAV70
A5p	BRY61
A51	BRY62
A6p	BAS16
A7p	BAV99
A91	BAS17
AAp	BCW60A
AA	BCX51
ABp	BCW60B
ACp	BCW60C
AC	BCX51-10
ADp	BCW60D
AD	BCX51-16
AE	BCX52
AGp	BCX70G
AG	BCX52-10
AHp	BCX70H
AH	BCX53
AJp	BCX70J
AKp	BCX70K
AK	BCX53-10
AL	BCX53-16
AM	BCX52-16
AMp	BSS64
AR1	BSR40
AR2	BSR41
AR3	BSR42
AR4	BSR43
AS1	BST50
AS2	BST51
AS3	BST52
AT1	BST39

MARK	TYPE NO.
AT2	BST40
B2p	BSV52
B5p	BSR12
B26	BF570
BAp	BCW61A
BA	BCX54
BBp	BCW61B
BCp	BCW61C
BC	BCX54-10
BDp	BCW61D
BD	BCX54-16
BE	BCX55
BGp	BCX71G
BG	BCX55-10
BHp	BCX71H
BH	BCX56
BJp	BCX71J
BKp	BCX71K
BK	BCX56-10
BL	BCX56-16
BM	BCX55-16
BMp	BSS63
BR1	BSR30
BR2	BSR31
BR3	BSR32
BR4	BSR33
BS1	BST60
BS2	BST61
BS3	BST62
BT1	BST15
BT2	BST16
C1p	BCW29
C2p	BCW30
C7p	BCF29
C8p	BCF30

Surface mounted semiconductors

Marking

MARK	TYPE NO.
C91	BCV62
C92	BCV62A
C93	BCV62B
C94	BCV62C
C95	BCV64
C96	BCV64B
CAC	BC868
CBC	BC868-10
CCC	BC868-16
CDC	BC868-25
CEC	BC869
CGC	BC869-10
D1p	BCW31
D2p	BCW32
D3p	BCW33
D7p	BCF32
D8p	BCF33
D95	BCV63
D96	BCV63B
DA	BF622
DB	BF623
DC	BF620
DF	BF621
E1p	BFS17
F1p	BFS18
F2p	BFS19
F8p	BF824
FA	BFQ17
FB	BFQ19
FDp	BCV26
FEp	BCV46
FFp	BCV27
FF	BFQ18A
FGp	BCV47
G1p	BFS20
H1p	BCW69
H2p	BCW70
H3p	BCW89
H7p	BCF70
JAp	BAV74

MARK	TYPE NO.
JPp	BAS19
JRp	BAS20
JSp	BAS21
JTp	BAS28
K1p	BCW71
K2p	BCW72
K3p	BCW81
K7p	BCV71
K8p	BCV72
K9p	BCF81
KM	BST80
KN	BST84
KO	BST86
L20	BAS29
L21	BAS31
L22	BAS35
L30	BAV23
L4p	BAT54
L41	BAT74
L42	BAT54A
L43	BAT54C
L44	BAT54S
L51	BAS56
LEp	BF660
LAp	BF550
LHp	BF569
LJp	BF579
LM	BST120
LN	BST122
LOp	BSR174
LPp	BSR175
LQp	BSR176
LRp	BSR177
M1p	BFR30
M2p	BFR31
M3p	BFT46
M31	BSD20
M32	BSD22
M4p	BSR56
M5p	BSR57

Surface mounted semiconductors

Marking

MARK	TYPE NO.	MARK	TYPE NO.
M6p	BSR58	p1Q	PMBT5088
M74	BSS83	p1Y	PMBT3903
M87	BF990A	p2P	BFR92A
M91	BF991	p2A	PMBT3906
M92	BF992		(SOT23)
M97	BFR101A		PXT3906
M98	BFR101B		(SOT89)
MAp	BF989	p2B	PMBT2907
MGp	BF994S		(SOT23)
MKp	BF997		PXT2907
MWp	BF996S		(SOT89)
N1p	BFR53	p2D	PMBTA92
NCp	BF840	p2E	PMBTA93
NDp	BF841	p2F	PMBT2907A
P1p	BFR92		(SOT23)
p1A	PMBT3904		PXT2907A
	(SOT23)		(SOT89)
	PXT3904	p2H	PMBTA55
	(SOT89)	p2L	PMBT5401
p1B	PMBT2222	p2G	PMBTA56
	(SOT23)	p2T	PMBT4403
	PXT2222		(SOT23)
	(SOT89)		PXT4403
p1D	PMBTA42		(SOT89)
p1E	PMBTA43	p2V	PBMTA63
p1F	PMBT5550	p2V	PBMTA64
p1H	PMBTA05		(SOT23)
p1J	PMBT2369		PXTA64
p1G	PMBTA06		(SOT89)
p1K	PMBT6428	p2X	PMBT4401
p1L	PMBT6429		(SOT23)
p1M	PMBTA13		PXT4401
p1N	PMBTA14		(SOT89)
	(SOT23)	p6J	PMBF4391
	PXTA14	p6K	PMBF4392
	(SOT89)	p6G	PMBF4393
p1P	PMBT2222A	p6S	PMBFJ176
	(SOT23)	p6W	PMBFJ175
	PXT2222A	p6X	PMBFJ174
	(SOT89)	p6Y	PMBFJ177

Surface mounted semiconductors

Marking

MARK	TYPE NO.
pG1	PMBT5551
R1p	BFR93
R2p	BFR93A
SF	BB804
S1p	BBY31
S2	BBY40
S4	BBY62
S6p	BF510
S7p	BF511
S8p	BF512
S9p	BF513
S12	BBY39
S13	BBY42
T1p	BCX17
T2p	BCX18
T7p	BSR15
T8p	BSR16
T9p	BSR18
T35	BSR20
T36	BSR20A
T92	BSR18A
U1p	BCX19
U2p	BCX20
U7p	BSR13
U8p	BSR14
U9p	BSR17
U35	BSR19
U36	BSR19A
U92	BSR17A
V1p	BFT25
V2p	BFQ67
V3	BFG67
V12	BFG67X
W1p	BFT92
X1p	BFT93
Y1	BZX84-C11
Y2	BZX84-C12
Y3	BZX84-C13
Y4	BZX84-C15
Y5	BZX84-C16

MARK	TYPE NO.
Y6	BZX84-C18
Y7	BZX84-C20
Y8	BZX84-C22
Y9	BZX84-C24
Y10	BZX84-C27
Y11	BZX84-C30
Y12	BZX84-C33
Y13	BZX84-C36
Y14	BZX84-C39
Y15	BZX84-C43
Y16	BZX84-C47
Y17	BZX84-C51
Y18	BZX84-C56
Y19	BZX84-C62
Y20	BZX84-C68
Y21	BZX84-C75
Z1	BZX84-C4V7
Z2	BZX84-C5V1
Z3	BZX84-C5V6
Z4	BZX84-C6V2
Z5	BZX84-C6V8
Z6	BZX84-C7V5
Z7	BZX84-C8V2
Z8	BZX84-C9V1
Z9	BZX84-C10
Z11	BZX84-C2V4
Z12	BZX84-C2V7
Z13	BZX84-C3V0
Z14	BZX84-C3V3
Z15	BZX84-C3V6
Z16	BZX84-C3V9
Z17	BZX84-C4V3
O2p	BST82
1Ap	BC846A
1Bp	BC846B
1Dp	BC846
1Ep	BC847A
1Fp	BC847B
1Gp	BC847C
1Hp	BC847

Surface mounted semiconductors

Marking

MARK	TYPE NO.	MARK	TYPE NO.
1Jp	BC848A (SOT23)	3Y0	BZV49-C3V0
1Jp	BCV61A (SOT143)	3Y3	BZV49-C3V3
1Kp	BC848B (SOT23)	3Y6	BZV49-C3V6
1Kp	BCV61B (SOT143)	3Y9	BZV49-C3V9
1Lp	BC848C (SOT23)	4Ap	BC859A
1Lp	BCV61C (SOT143)	4Bp	BC859B
1Mp	BC848 (SOT23)	4Cp	BC859C
1Mp	BCV61 (SOT143)	4Dp	BC859
1Vp	BF820	4Ep	BC860A
1Wp	BF821	4Fp	BC860B
1Xp	BF822	4Gp	BC860C
1Yp	BF823	4Hp	BC860
2Bp	BC849B	4Y3	BZV49-C4V3
2Cp	BC849C	4Y7	BZV49-C4V7
2Dp	BC849	5Ap	BC807-16
2Fp	BC850B	5Bp	BC807-25
2Gp	BC850C	5Cp	BC807-40
2Hp	BC850	5Dp	BC807
2Y4	BZV49-C2V4	5Ep	BC808-16
2Y7	BZV49-C2V7	5Fp	BC808-25
3Ap	BC856A	5Gp	BC808-40
3Bp	BC856B	5Hp	BC808
3BR	BC856BR	5Y1	BZV49-C5V1
3Dp	BC856	5Y6	BZV49-C5V6
3Ep	BC857A	6Ap	BC817-16
3Fp	BC857B	6Bp	BC817-25
3Jp	BC858A	6Cp	BC817-40
3Gp	BC857C	6Dp	BC817
3Hp	BC857	6Ep	BC818-16
3Kp	BC858B	6Fp	BC818-25
3Lp	BC858C	6Gp	BC818-40
3Mp	BC858	6Hp	BC818
		6Y2	BZV49-C6V2
		6Y8	BZV49-C6V8
		7Y5	BZV49-C7V5
		8Y2	BZV49-C8V2
		9Y1	BZV49-C9V1
		10Y	BZV49-C10
		11Y	BZV49-C11
		12Y	BZV49-C12

Surface mounted semiconductors

Marking

MARK	TYPE NO.
13Y	BZV49-C13
15Y	BZV49-C15
16Y	BZV49-C16
18Y	BZV49-C18
20Y	BZV49-C20
22Y	BZV49-C22
24Y	BZV49-C24
27Y	BZV49-C27
30Y	BZV49-C30
33Y	BZV49-C33
36Y	BZV49-C36
39Y	BZV49-C39
43Y	BZV49-C43
47Y	BZV49-C47
51Y	BZV49-C51
56Y	BZV49-C56
62Y	BZV49-C62
68Y	BZV49-C68
75Y	BZV49-C75
97p	BCV65
98p	BCV65B

General

Packing
Soldering recommendations
Thermal characteristics
Type designation code
Rating systems
Letter symbols
S-parameters

TAPE AND REEL SPECIFICATION

Semiconductors in SOT23 and SOT143 encapsulations can be delivered in reel packing for automatic placement on hybrid circuits and printed-circuit boards. The devices are placed with the mounting side downwards in compartments.

Separate reel packing for SOT89, SOD87, SOT223 and SOD80 encapsulations are given in Figs 2 to 5 respectively.

The configuration of the reel and flange is given in Fig. 6.

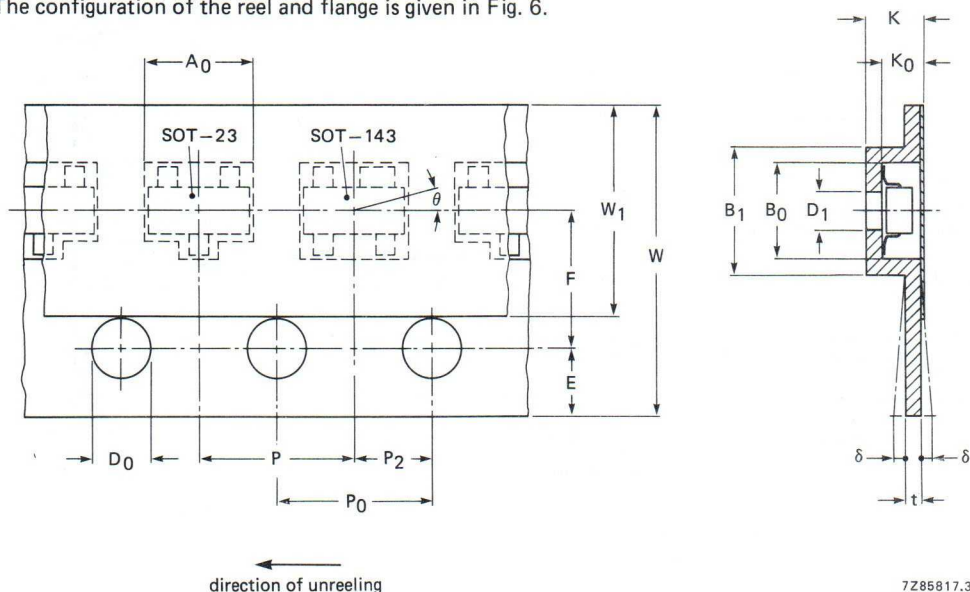
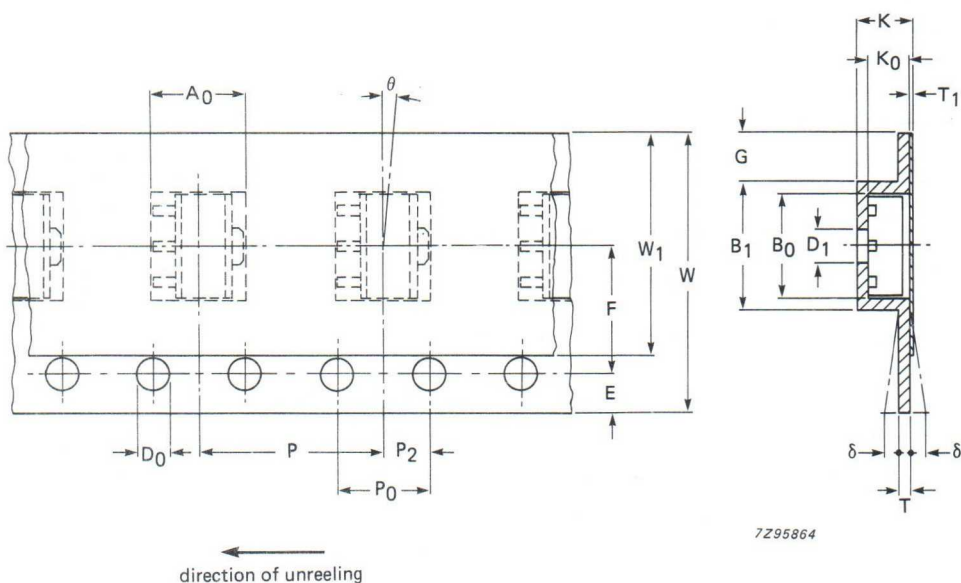


Fig.1 Configuration of bandolier. Dimensions in mm.

Compartment				Centre line dimensions			
length	A ₀	component length	+0,2	length direction	P ₂	2,0	± 0,05
width	B ₀	component width	+0,2	width direction	F	3,5	± 0,05
depth	K ₀		0,95	Fixing tape			
width outside	B ₁		3,3	width	W ₁	5,5	± 0,25
pitch	P		4,0	thickness	—	0,1	max.
deviation	Θ		15°	Carrier tape			
hole diameter	D ₁		1	width	W	8,0	± 0,2
Sprocket hole				bending	δ	0,3	max.
diameter	D ₀		1,5	thickness	t	0,4	max.
pitch	P ₀		4,0	Overall thickness			
distance	E		1,75		K	1,5	max.
cumulative (10)							
pitch error			± 0,1				

Semiconductors in SOT89 encapsulations can also be delivered in reel packing for automatic placement on hybrid circuits and printed-circuit boards. The devices are placed with the mounting side downwards in compartments.



7Z95864

Fig.2 Configuration of bandolier. Dimensions in mm.

Compartment			tol.			Centre line dimensions			tol.		
length	A_0	component length				length direction	P_2	2,0	$\pm 0,05$		
width	B_0	component width				width direction	F	5,5	$\pm 0,1$		
depth	K_0	component depth				Fixing tape					
width outside	B_1	5,7		max.		width	W_1	9,5		max.	
pitch	P	8,0		$\pm 0,1$		thickness	T_1	0,1		max.	
deviation	Θ	$\pm 5^\circ$		max.		Carrier tape					
hole diam.	D_1	1,5		min.		width	W	12		$\pm 0,2$	
Sprocket hole						bending	δ	0,3		max.	
diameter	D_0	1,5		$+0,1$		thickness	T	0,4		max.	
pitch	P_0	4,0		$\pm 0,1$		Overall thickness					
distance	E	1,75		$\pm 0,1$		distance	K	2,4		max.	
cumulative (10)											
pitch error				$\pm 0,1$						min.	

Semiconductors in SOD87 encapsulations can also be delivered in reel packing for automatic placement on hybrid circuits and printed-circuit boards. The devices are placed with the mounting side downwards in compartments. Total number of devices per reel is 2000.

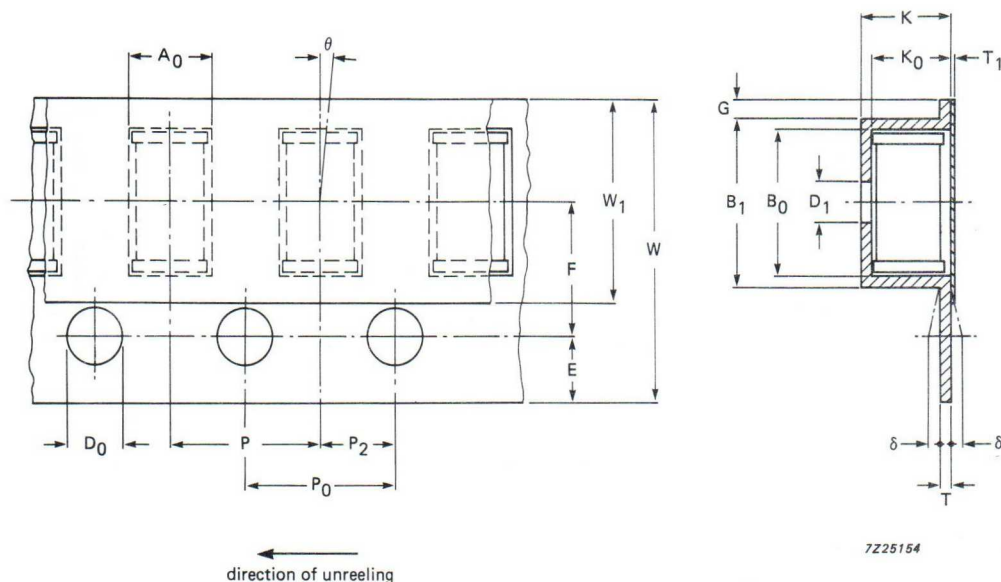


Fig.3 Configuration of bandolier. Dimensions in mm.

Note: Testing of SOD87 devices is not possible in this tape. Total number of devices per reel is 2000.

Compartment				Centre line dimensions			
length	A ₀	2.1	+ 0.3	length direction	P ₂	2.0	± 0.05
width	B ₀	3.8	min.	width direction	F	3.5	± 0.1
depth	K ₀	2.1	+ 0.3	Fixing tape			
width outside	B ₁	4.5	max.	width	W ₁	5.5	max.
pitch	P	4.0	± 0.1	thickness	T ₁	0.1	max
deviation	θ	± 5°	max.	Carrier tape			
hole diameter	D ₁	1.0	+ 0.1	width	W	8	± 0.2
Sprocket hole				bending	δ	0.3	max.
diameter	D ₀	1.5	+ 0.1	thickness	T	0.4	max.
pitch	P ₀	4.0	± 0.1	Overall thickness			
distance	E	1.75	± 0.1		K	2.5	max.
cumulative (10)							
pitch error			± 0.1				

Semiconductors in SOT223 encapsulations can also be delivered in reel packing for automatic placement on hybrid circuits and printed-circuit boards. The devices are placed with the mounting side downwards in compartments.

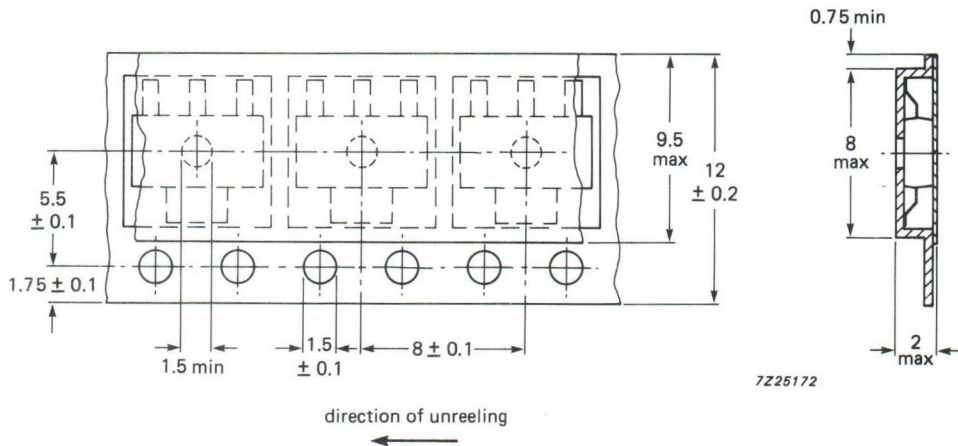


Fig.4 Configuration of bandolier. Dimensions in mm.

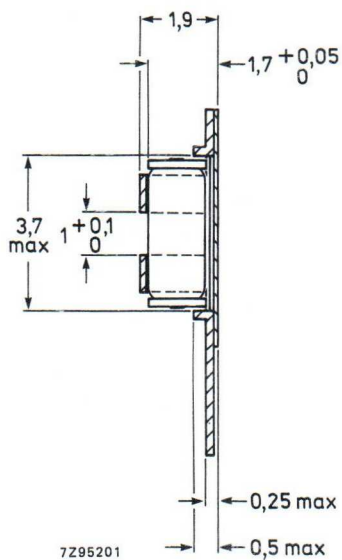
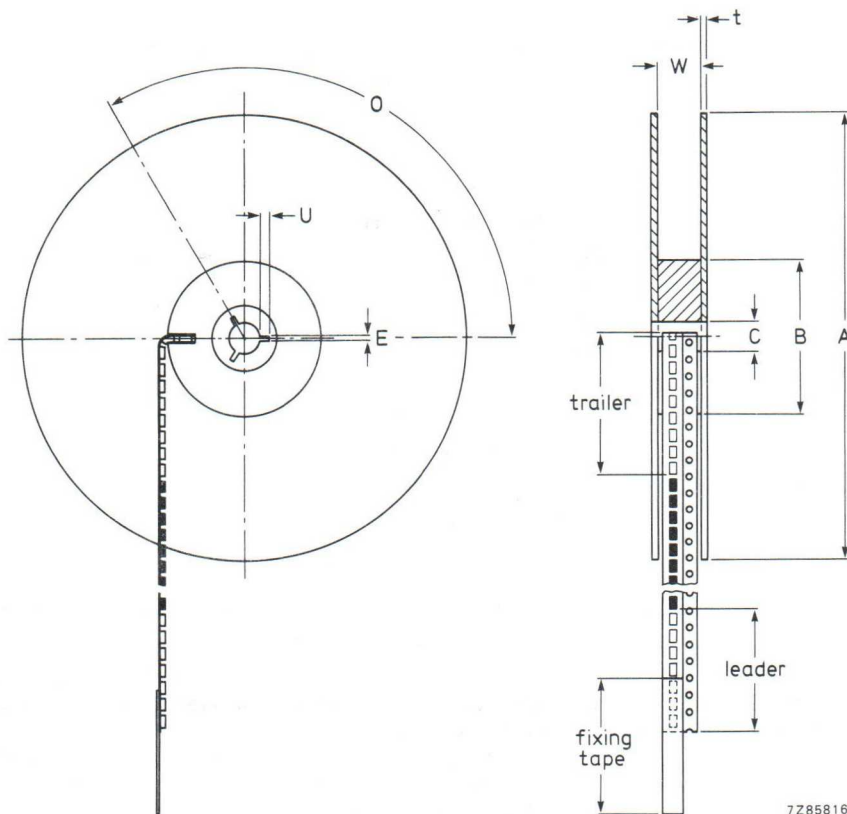


Fig.5 Cross-sectional view of bandolier with **SOD80** devices.

Note: Testing of SOD80 devices is possible in this tape. The cathode is directed towards the sprocket hole. The total number of devices per reel is 2500.



7Z85816

Fig.6 Configuration of reel and flange (dimensions in mm).

Flange			tol.
diameter	A	180	+0 -2
thickness	t	1,5	+0,5 -0,1
space between flanges	W	9,5	± 0,5

Hub			tol.
diameter	B	62	± 1,5
spindle hole	C	12,75	+0,15 -0
key slit			
width	E	2	± 0,5
depth	U	4	± 0,5
location	O	120	degrees

Amount of devices per reel

The bandolier of a 180 mm reel contains at least 3000 devices with no more than 15 empty compartments (0,5%). Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.

The carrier tape (leader) starts with at least 75 empty positions (equivalent to 300 mm); the covering foil is at least 300 mm. In order to fix the carrier tape a self-adhesive tape of 20 to 50 mm is applied.

At the end of the bandolier (trailer) at least 75 empty positions (equivalent to a length of 300 mm) and 300 mm foil. For fixing onto the reel a self-adhesive tape of 20 to 50 mm is applied.

SOLDERING RECOMMENDATIONS

SMD devices are ideally suited for placement onto thick and thin film substrates and printed boards. To assure reliable and consistent connections particular attention should be paid to:

1. Flux

A non-active flux is recommended. Where active fluxes are employed, great care in subsequent substrate cleaning must be exercised.

2. Metal-alloy solder or solder paste

Correct choice of solder alloy or solder paste to be employed e.g. 62% Sn, 36% Pb, 2% Ag or 60% Sn/40% Pb. Any paste used should contain at least 85% metal dry weight.

3. Soldering temperature

This will vary according to the actual method employed.

REFLOW SOLDERING

The preferred technique for mounting microminiature components on hybrid thick and thin-film is the method of reflow soldering.

The tags of SOT23, SOT143 and SOT89 envelopes are pre-tinned and the best results are obtained if a similar solder is applied to the corresponding soldering areas on the substrate. This can be done by either dipping the substrate in a solder bath or by screen printing a solder paste.

The maximum temperature of the leads or tab during the soldering cycle should not exceed 285 °C. The most economic method of soldering is a process in which all different components are soldered simultaneously for example SOT23, SOT143 or SOT89 devices, capacitors and resistors.

Having first been fluxed, all components are positioned on the substrate. The slight adhesive force of the flux is sufficient to keep the components in place. Solder paste contains a flux and has therefore good inherent adhesive properties which eases positioning of the components.

With the components in position the substrate is heated to a point where the solder begins to flow. This can be done on a heating plate or on a conveyor belt running through an infrared tunnel. The maximum allowed temperature of the plastic body of a device must be kept below 280 °C during the soldering cycle. For further temperature behaviour during the soldering process see Figs 2 and 3.

The surface tension of the liquid solder tends to draw the tags of the device towards the centre of the soldering area and has thus a correcting affect on slight mispositionings. However, if the layout leaves something to be desired the same effect can result in undesirable shifts; particularly if the soldering areas on the substrate and the components are not concentrically arranged. This problem can be solved using a standard contact pattern, which leaves sufficient scope for the self-positioning effect (see Figs 4 to 9).

After cooling the connections may be visually inspected and, where necessary, repaired with a light soldering iron. Finally any remaining flux must be removed carefully.

WAVE SOLDERING

The normal (dual) wave soldering process can also be applied to SOD80, SOT23, SOD87 and SOT143 envelopes. We do not recommend SOT89 to be used with wave soldering process.

IMMERSION SOLDERING

Where a complete substrate or printed circuit board is immersed in solder:

- The temperature of the soldering bath should not exceed 280 °C.
- The duration of the soldering cycle should not exceed 10 seconds.
- Forced cooling may be applied (see Fig. 1).

HAND SOLDERING

It is possible to solder microminiature devices with a light hand-held soldering iron, but this method has obvious drawbacks and should therefore be restricted to laboratory use and/or incidental repairs on production circuits.

- It is time-consuming and expensive.
- The device cannot be positioned accurately and therefore the connecting tags may come into contact with the substrate and damage it.
- There is a great risk of breaking either substrate or even internal connections inside the encapsulation.
- The envelope may be damaged by the iron.

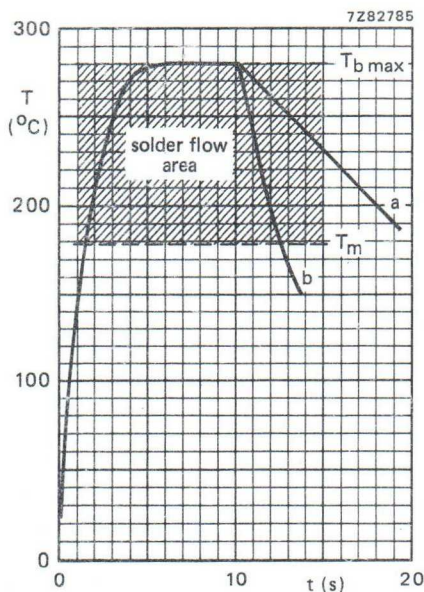


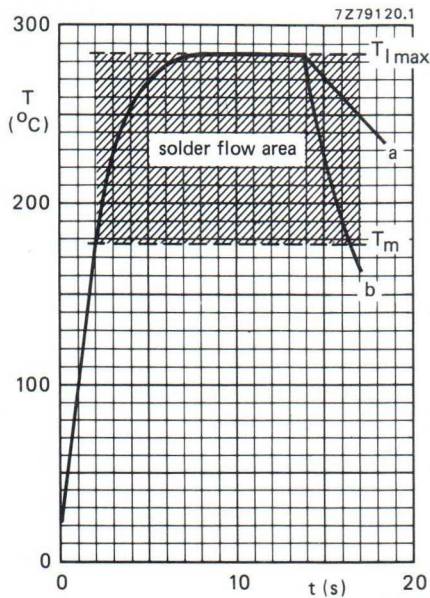
Fig.1 Device temperature during *immersion* soldering.

Maximum time of immersion in soldering bath is 10 seconds at an ambient temperature of 25 °C.

a = free convection cooling; b = forced cooling.

$T_{b \text{ max}}$ = maximum bath temperature (280 °C).

T_m = melting temperature of solder (179 °C).



- a = free convection cooling
- b = permissible forced cooling
- $T_{I\max}$ = maximum lead or tab temperature = 285 °C
- T_m = melting point of the solder is 179 °C
- T_{amb} = 25 °C

Time of heat supply:
without preheating max. 14 s
with preheating max. 10 s
Maximum time of preheating 45 s

Fig.2 Reflow soldering without preheating.

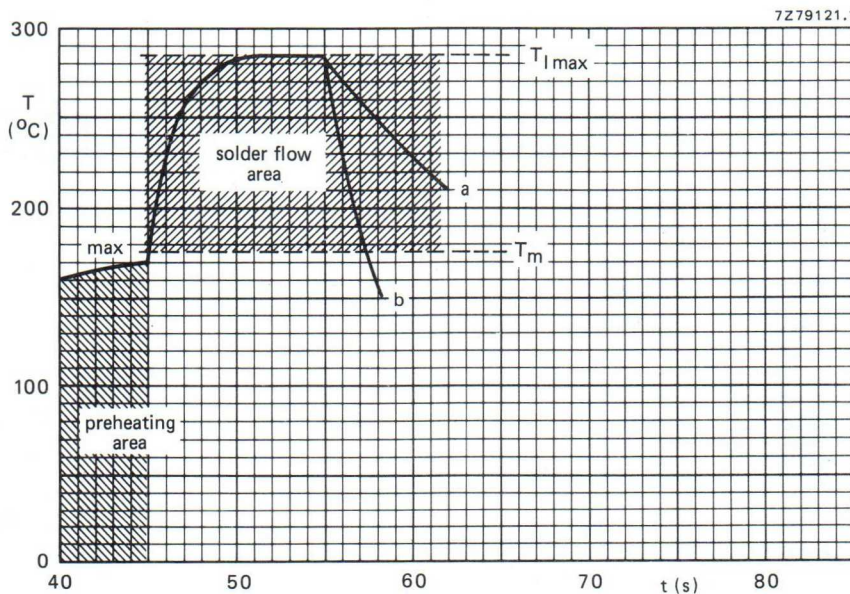


Fig.3 Reflow soldering with preheating.

SOLDERING RECOMMENDATIONS

Minimum required dimensions of metal connection pads on hybrid thick and thin-film substrates.

Dimensions in mm

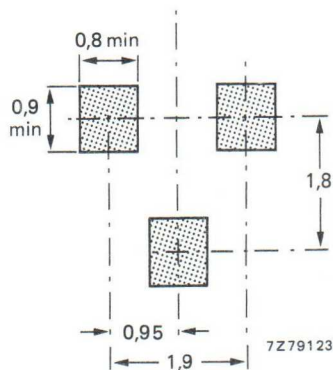


Fig.4 SOT23 pattern.

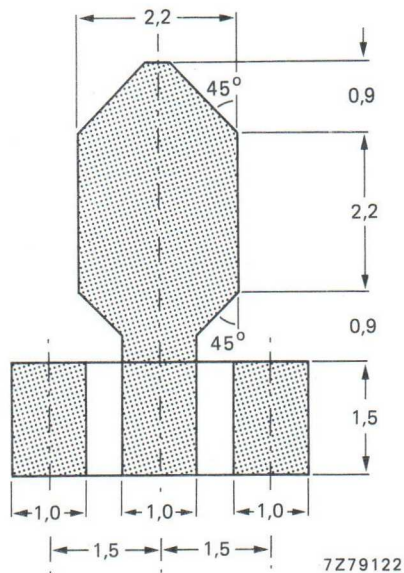


Fig.5 SOT89 pattern.

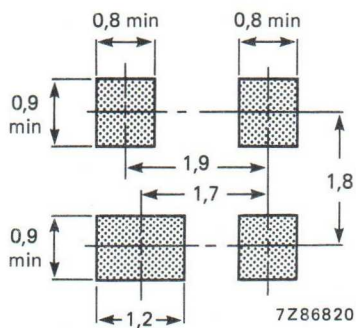


Fig.6 SOT143 pattern.

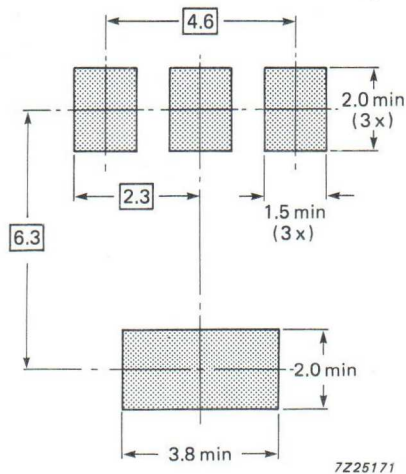


Fig.7 SOT223 pattern.

Minimum required dimensions of metal connection pads on hybrid thick and thin-film substrates.

Dimensions in mm

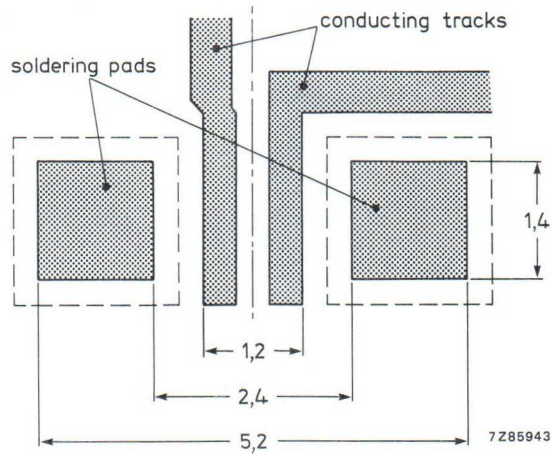


Fig.8 SOD80 pattern.

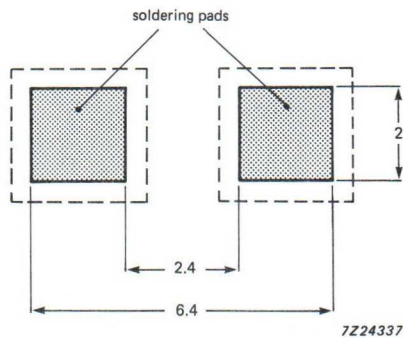
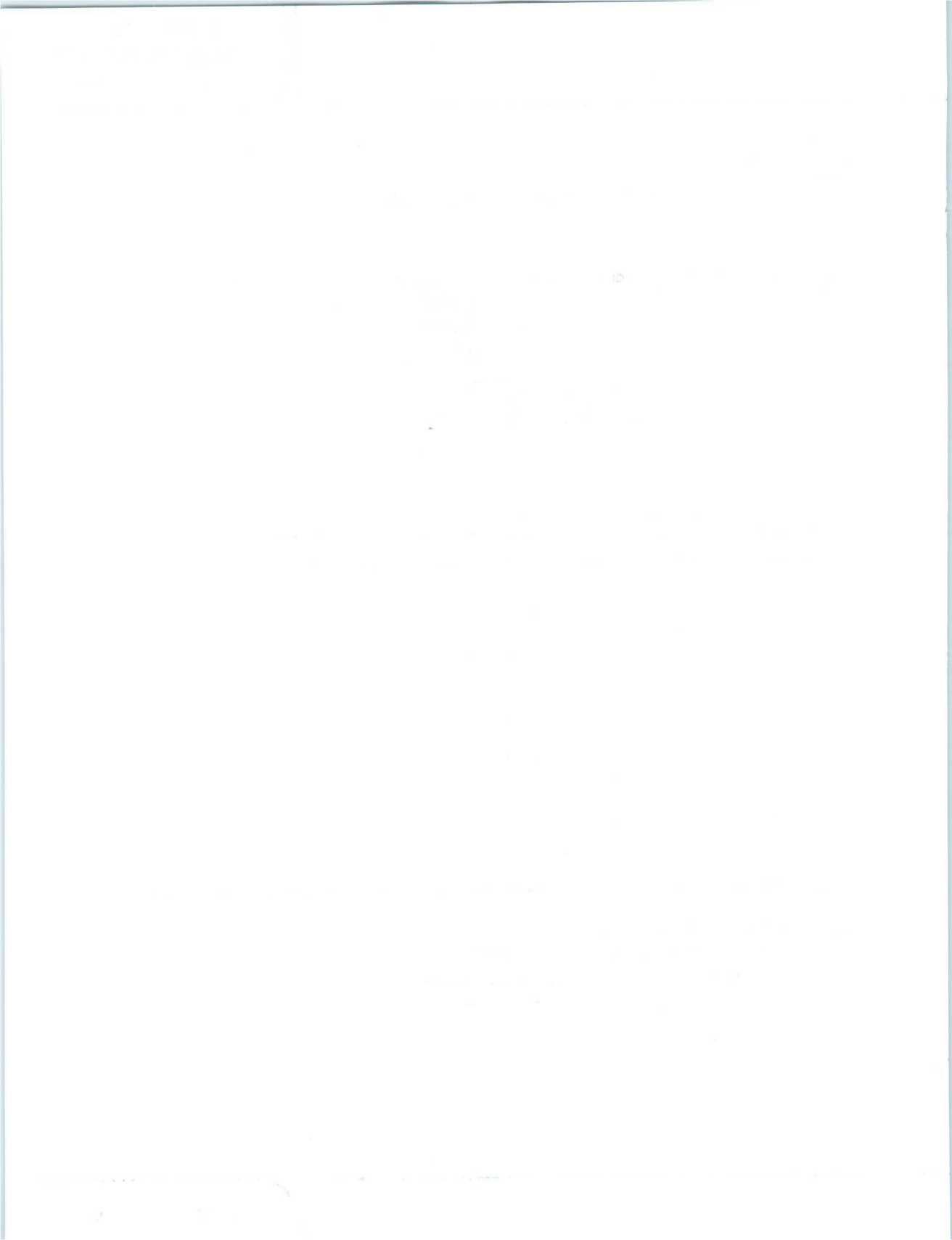


Fig. 9 SOD87 pattern.



THERMAL CHARACTERISTICS

The heat generated in a semiconductor chip normally flows by various paths to the surroundings (ambient).

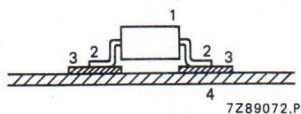


Fig.1.

1. Heat radiation from the envelope to ambient (1).

This heat transfer can be neglected when the envelope is mounted on a substrate or printed board.

2. Heat transmission via leads (2) soldering points (3) and substrate (4).

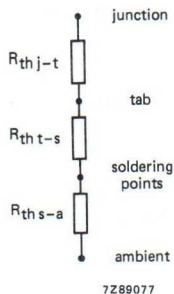


Fig.2 Thermal behaviour of heat flow when the device is mounted on a substrate or printed board.

$R_{th\ j-t}$ = Thermal resistance from junction to tab.

$R_{th\ t-s}$ = Thermal resistance from tab to soldering points.

$R_{th\ s-a}$ = Thermal resistance from soldering points to ambient.

Internal $R_{th} = R_{th\ j-t} + R_{th\ t-s} = 320\ K/W$ (SOT23/143).

Heat transfer from soldering points to ambient (Fig.3)

This depends on the shape and material of tracks and substrate. In Figures 4 to 8 standard mounting conditions are given to set up the maximum power ratings for SOT23, SOT143, SOT89, SOD87 and SOT223 encapsulations.

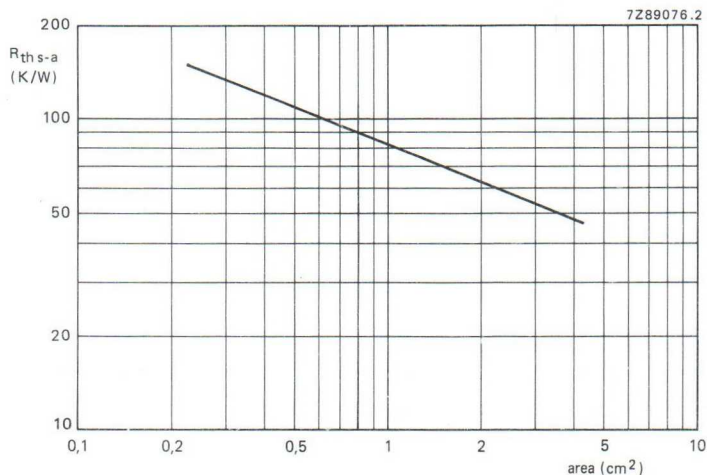


Fig.3 Heat transfer from soldering points to ambient.

Ceramic substrate

The $R_{th\ s-a}$ depends on the size of the ceramic substrate due to good conductive properties.

Printed board

$R_{th\ s-a} = 150\text{ K/W}$ for SOT23 and SOT143 envelopes mounted on a printed board.

$P_{tot} = 250\text{ mW}$ for SOT23 and SOT143 envelopes mounted on a printed board.

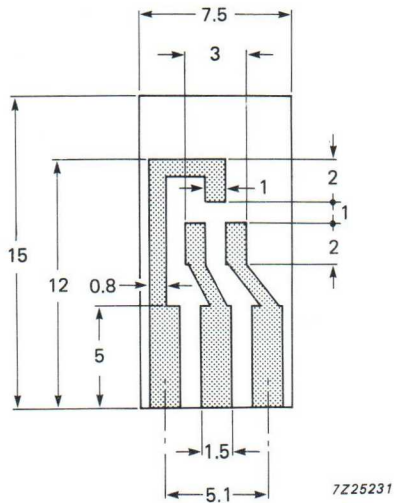


Fig.4 Test circuit for SOT23.

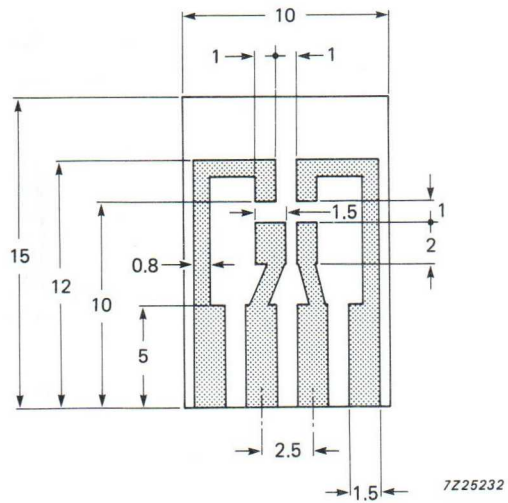


Fig.5 Test circuit for SOT143.

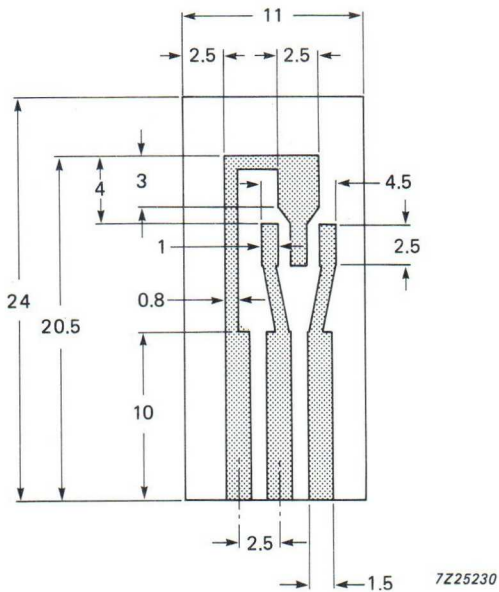


Fig.6 Test circuit for SOT89.

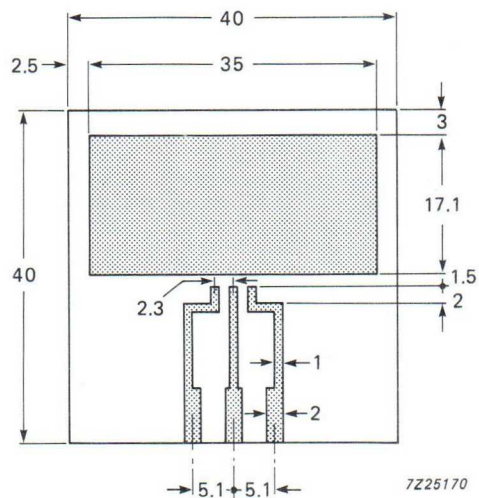


Fig.7 Test circuit for SOT223.

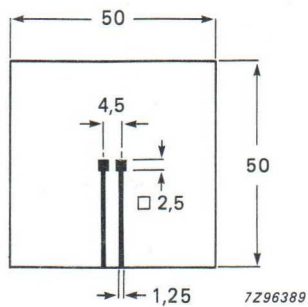


Fig.8 Test circuit for SOD87.

PRO ELECTRON TYPE DESIGNATION CODE
FOR SEMICONDUCTOR DEVICES

This type designation code applies to discrete semiconductor devices — as opposed to integrated circuits —, multiples of such devices and semiconductor chips.

“Although not all type numbers accord with the Pro Electron system, the following explanation is given for the ones that do.”

A basic type number consists of:

TWO LETTERS FOLLOWED BY A SERIAL NUMBER

FIRST LETTER

The first letter gives information about the material used for the active part of the devices.

- A. GERMANIUM or other material with band gap of 0,6 to 1,0 eV.
- B. SILICON or other material with band gap of 1,0 to 1,3 eV.
- C. GALLIUM-ARSENIDE or other material with band gap of 1,3 eV or more.
- R. COMPOUND MATERIALS (e.g. Cadmium-Sulphide).

SECOND LETTER

The second letter indicates the function for which the device is primarily designed.

- A. DIODE; signal, low power
- B. DIODE; variable capacitance
- C. TRANSISTOR; low power, audio frequency ($R_{th j-mb} > 15 \text{ K/W}$)
- D. TRANSISTOR; power, audio frequency ($R_{th j-mb} \leq 15 \text{ K/W}$)
- E. DIODE; tunnel
- F. TRANSISTOR; low power, high frequency ($R_{th j-mb} > 15 \text{ K/W}$)
- G. MULTIPLE OF DISSIMILAR DEVICES — MISCELLANEOUS; e.g. oscillator
- H. DIODE; magnetic sensitive
- L. TRANSISTOR; power, high frequency ($R_{th j-mb} \leq 15 \text{ K/W}$)
- N. PHOTO-COUPLER
- P. RADIATION DETECTOR; e.g. high sensitivity phototransistor
- Q. RADIATION GENERATOR; e.g. light-emitting diode (LED)
- R. CONTROL AND SWITCHING DEVICE; e.g. thyristor, low power ($R_{th j-mb} > 15 \text{ K/W}$)
- S. TRANSISTOR; low power, switching ($R_{th j-mb} > 15 \text{ K/W}$)
- T. CONTROL AND SWITCHING DEVICE; e.g. thyristor, power ($R_{th j-mb} \leq 15 \text{ K/W}$)
- U. TRANSISTOR; power, switching ($R_{th j-mb} \leq 15 \text{ K/W}$)
- X. DIODE: multiplier, e.g. varactor, step recovery
- Y. DIODE; rectifying, booster
- Z. DIODE; voltage reference or regulator (transient suppressor diode, with third letter W)

SERIAL NUMBER

Three figures, running from 100 to 999, for devices primarily intended for consumer equipment.*
One letter (Z, Y, X, etc.) and two figures, running from 10 to 99, for devices primarily intended for industrial/professional equipment.*

This letter has no fixed meaning except W, which is used for transient suppressor diodes.

VERSION LETTER

It indicates a minor variant of the basic type either electrically or mechanically. The letter never has a fixed meaning, except letter R, indicating reverse voltage, e.g. collector to case or anode to stud.

SUFFIX

Sub-classification can be used for devices supplied in a wide range of variants called associated types. Following sub-coding suffixes are in use:

1. VOLTAGE REFERENCE and VOLTAGE REGULATOR DIODES: *ONE LETTER and ONE NUMBER*

The LETTER indicates the nominal tolerance of the Zener (regulation, working or reference) voltage

A. 1% (according to IEC 63: series E96)

B. 2% (according to IEC 63: series E48)

C. 5% (according to IEC 63: series E24)

D. 10% (according to IEC 63: series E12)

E. 20% (according to IEC 63: series E6)

The number denotes the typical operating (Zener) voltage related to the nominal current rating for the whole range.

The letter 'V' is used instead of the decimal point.

2. TRANSIENT SUPPRESSOR DIODES: *ONE NUMBER*

The NUMBER indicates the maximum recommended continuous reversed (stand-off) voltage V_R . The letter 'V' is used as above.

3. CONVENTIONAL and CONTROLLED AVALANCHE RECTIFIER DIODES and THYRISTORS: *ONE NUMBER*

The NUMBER indicates the rated maximum repetitive peak reverse voltage (V_{RRM}) or the rated repetitive peak off-state voltage (V_{DRM}), whichever is the lower. Reversed polarity is indicated by letter R, immediately after the number.

4. RADIATION DETECTORS: *ONE NUMBER*, preceded by a hyphen (—)

The NUMBER indicates the depletion layer in μm . The resolution is indicated by a version LETTER.

5. ARRAY OF RADIATION DETECTORS and GENERATORS: *ONE NUMBER*, preceded by a stroke (/).

The NUMBER indicates how many basic devices are assembled into the array.

* When these serial numbers are exhausted the serial number for consumer types may be extended to four figures, and that for industrial types to three figures.

RATING SYSTEMS

The rating systems described are those recommended by the International Electrotechnical Commission (IEC) in its Publication 134.

DEFINITIONS OF TERMS USED

Electronic device. An electronic tube or valve, transistor or other semiconductor device.

Note

This definition excludes inductors, capacitors, resistors and similar components.

Characteristic. A characteristic is an inherent and measurable property of a device. Such a property may be electrical, mechanical, thermal, hydraulic, electro-magnetic, or nuclear, and can be expressed as a value for stated or recognized conditions. A characteristic may also be a set of related values, usually shown in graphical form.

Bogey electronic device. An electronic device whose characteristics have the published nominal values for the type. A bogey electronic device for any particular application can be obtained by considering only those characteristics which are directly related to the application.

Rating. A value which establishes either a limiting capability or a limiting condition for an electronic device. It is determined for specified values of environment and operation, and may be stated in any suitable terms.

Note

Limiting conditions may be either maxima or minima.

Rating system. The set of principles upon which ratings are established and which determine their interpretation.

Note

The rating system indicates the division of responsibility between the device manufacturer and the circuit designer, with the object of ensuring that the working conditions do not exceed the ratings.

ABSOLUTE MAXIMUM RATING SYSTEM

Absolute maximum ratings are limiting values of operating and environmental conditions applicable to any electronic device of a specified type as defined by its published data, which should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking no responsibility for equipment variations, environmental variations, and the effects of changes in operating conditions due to variations in the characteristics of the device under consideration and of all other electronic devices in the equipment.

The equipment manufacturer should design so that, initially and throughout life, no absolute maximum value for the intended service is exceeded with any device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, equipment control adjustment, load variations, signal variation, environmental conditions, and variations in characteristics of the device under consideration and of all other electronic devices in the equipment.

DESIGN MAXIMUM RATING SYSTEM

Design maximum ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking responsibility for the effects of changes in operating conditions due to variations in the characteristics of the electronic device under consideration.

The equipment manufacturer should design so that, initially and throughout life, no design maximum value for the intended service is exceeded with a bogey device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, variation in characteristics of all other devices in the equipment, equipment control adjustment, load variation, signal variation and environmental conditions.

DESIGN CENTRE RATING SYSTEM

Design centre ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under normal conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device in average applications, taking responsibility for normal changes in operating conditions due to rated supply voltage variation, equipment component variation, equipment control adjustment, load variation, signal variation, environmental conditions, and variations in the characteristics of all electronic devices.

The equipment manufacturer should design so that, initially, no design centre value for the intended service is exceeded with a bogey electronic device in equipment operating at the stated normal supply voltage.

TRANSISTOR RATINGS

The ratings are presented as voltage, current, power and temperature ratings. The list of these ratings and their definitions is given as follows:

Transistor voltage ratings

Collector to base voltage ratings

- V_{CBmax} The maximum permissible instantaneous voltage between collector and base terminals. The collector voltage is negative with respect to base in PNP transistors and positive with respect to base in NPN types.
- $V_{CBmax} (I_E = 0)$ The maximum permissible instantaneous voltage between collector and base terminals, when the emitter terminal is open circuited.

Emitter to base voltage ratings

- V_{EBmax} The maximum permissible instantaneous reverse voltage between emitter and base terminal. The emitter voltage is negative with respect to base for PNP transistor and positive with respect to base for NPN types.
- $V_{EBmax} (I_C = 0)$ The maximum permissible instantaneous reverse voltage between emitter and base terminals when the collector terminal is open circuited.

Collector to emitter voltage ratings

- V_{CEmax} The maximum permissible instantaneous voltage between collector and emitter terminals. The collector voltage is negative with respect to emitter in PNP transistors and positive with respect to emitter in NPN types. This rating is very dependent on circuit conditions and collector current and it is necessary to refer to the curve of V_{CE} versus I_C for the appropriate circuit condition in order to obtain the correct rating.
- $V_{CEmax} (Cut-off)$ The maximum permissible instantaneous voltage between collector and emitter terminals when the emitter current is reduced to zero by means of a reverse emitter base voltage, i.e. the base voltage is normally positive with respect to emitter for PNP transistor and negative with respect to emitter for NPN types.

NOTE: The term "cut-off" is sometimes replaced by $V_{BE} > x$ volts, or $\frac{R_B}{R_E} \leq y$ which are equivalent conditions under which the device may be cut-off.

- $V_{CEmax} (I_C = x \text{ mA})$ The maximum permissible instantaneous voltage between collector and emitter terminals when the collector current is at a high value, often the max. rated value.
- $V_{CEmax} (I_B = 0)$ The maximum permissible instantaneous voltage between collector and emitter terminals when the base terminal is open circuited or when a very high resistance is in series with the base terminal. Special care must be taken to ensure that thermal runaway due to excessive collector leakage current does not occur in this condition.

Due to the current dependency of V_{CE} it is usual to present this information as a voltage rating chart which is a curve of collector current versus collector to emitter voltage (see Fig. 1).

TRANSISTOR RATINGS

This curve is divided into two areas:

A permissible area of operation under all conditions of base drive provided the dissipation rating is not exceeded (area 1) and an area where operation is allowable under certain specified conditions (area 2). To assist in determining the rating in this second area, further curves are provided relating the voltage rating to external circuit conditions, for example:

$$\frac{R_B}{R_E}, R_B, Z_{Bg}, V_{BE}, I_B \text{ or } \frac{V_{BB}}{R_B}.$$

An example of this type of curve is given in Fig. 2 as V_{CE} versus $\frac{R_B}{R_E}$ for two different values of collector current.

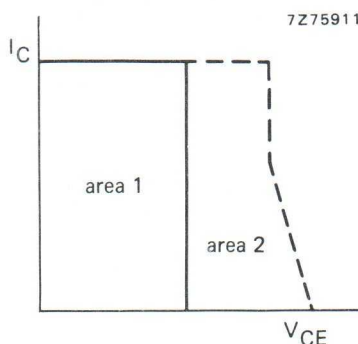


Fig. 1.

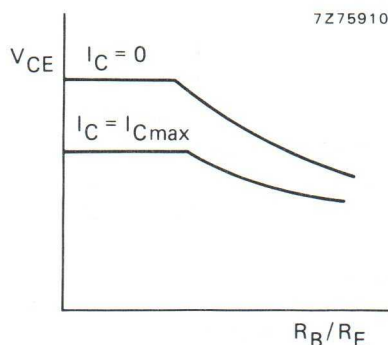


Fig. 2.

It should be noted that when R_E is shunted by a capacitor, the collector voltage V_{CE} during switching must be restricted to a value which does not rely on the effect of R_E .

In the case of an inductive load and when an energy rating is given, it may be permissible to operate outside the rated area provided the specified energy rating is not exceeded.

Transistor current ratings

Collector current ratings

I_{Cmax} The maximum permissible collector current. Without further qualification, the d.c. value is implied.

$I_{C(AV)max}$ The maximum permissible average value of the total collector current

I_{CM} The maximum permissible instantaneous value of the total collector current.

Emitter current ratings

I_{Emax} The maximum permissible emitter current. Without further qualification, the d.c. value is implied.

$I_{E(AV)max}$ The maximum permissible average value of the total emitter current.

$I_{ER(AV)max}$ The maximum permissible average value of the total emitter current when operating in the reverse emitter-base breakdown region.

I_{EM} The maximum permissible instantaneous value of the total emitter current.

I_{ERM} The maximum permissible instantaneous value of the total reverse emitter current allowable in the reverse breakdown region.

Base current ratings

I_{Bmax}	The maximum permissible base current. Without further qualification, the d.c. value is implied.
$I_{B(AV)max}$	The maximum permissible average value of the total base current.
$I_{BR(AV)max}$	The maximum permissible average value of the total reverse base current allowable in the reverse breakdown region.
I_{BM}	The maximum permissible instantaneous value of the total base current. The rating also includes the switch off current.
I_{BRM}	The maximum permissible instantaneous value of the total reverse current allowable in the reverse breakdown region.

Transistor power ratings

$P_{tot \max}$: The total maximum permissible continuous power dissipation in the transistor and includes both the collector-base dissipation and the emitter-base dissipation. Under steady state conditions the total power is given by the expression:

$$P_{tot} = V_{CE} \times I_C + V_{BE} \times I_B.$$

In order to distinguish between "steady state" and "pulse" conditions the terms "steady state power (P_S)" and "pulse power (P_P)" are often used. The permissible total power dissipation is dependent upon temperature and its relationship is shown by means of a chart as shown in Fig. 3.

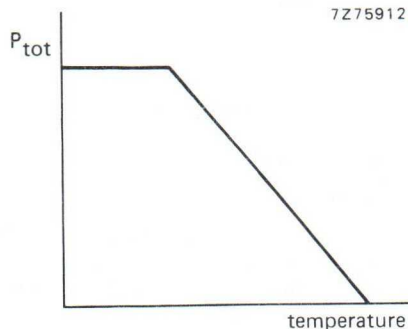


Fig. 3.

The temperature may be ambient, case or mounting base temperatures. Where a cooling clip or a heatsink is attached to the device, the allowable power dissipation is also dependent on the efficiency of the heatsink.

The efficiency of this clip or heatsink is measured in terms of its thermal resistance (R_{th}) normally expressed in degrees kelvin per watt (K/W). For mounting base rated devices, the added effect of the contact resistance ($R_{th i}$) must be taken into account.

The effect of heatsinks of various thermal resistance and contact resistance is often included in the above chart.

TRANSISTOR RATINGS

Thus for any heatsink of known thermal resistance and any given ambient temperature, the maximum permissible power dissipation can be established. Alternatively, knowing the power dissipation which will occur and the ambient temperature, the necessary heatsink thermal resistance can be calculated.

A general expression from which the total permissible steady state power dissipation can be calculated is:

$$P_{\text{tot}} = \frac{T_j - T_{\text{amb}}}{R_{\text{th j-a}}}$$

where $R_{\text{th j-a}}$ is the thermal resistance from the transistor junction to the ambient. For case rated or mounting base rated devices, the thermal resistance $R_{\text{th j-a}}$ is made up of the thermal resistance junction to case or mounting base ($R_{\text{th j-mb}}$), the contact thermal resistance ($R_{\text{th i}}$) and the heatsink thermal resistance $R_{\text{th h}}$.

For the calculation of pulse power operation P_p , the maximum pulse power is obtained by the aid of a chart as shown in Fig. 4.

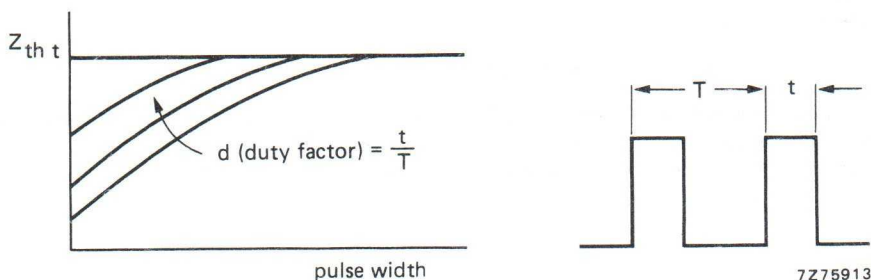


Fig. 4.

The general expression from which the maximum pulse power dissipation can be calculated is:

$$P_p = \frac{T_j - T_{\text{amb}} - P_s \times R_{\text{th j-a}}}{Z_{\text{th t}} + d (R_{\text{th c-a}})}$$

where $Z_{\text{th t}}$ and d are given in the above chart and $R_{\text{th c-a}}$ is the thermal resistance between case and ambient for case rated device. For mounting base rated device, it is equal to $R_{\text{th h}} + R_{\text{th i}}$ and is zero for free air rated device because the effect of the temperature rise of the case over the ambient for a pulse train is already included in $Z_{\text{th t}}$.

Temperature ratings

$T_{j\text{max}}$	The maximum permissible junction temperature which is used as the basis for the calculation of power ratings. Unless otherwise stated, the continuous value is implied.
$T_{j\text{max}}$ (continuous operation)	The maximum permissible continuous value.
$T_{j\text{max}}$ (intermittent operation)	The maximum permissible instantaneous junction temperature usually allowed for a total duration of 200 hours.
T_{mb}	The temperature of the surface making contact with a heatsink. This is confined to devices where a flange or stud for fixing onto a heatsink forms an integral part of the envelope.
T_{case}	The temperature of the envelope. This is confined to devices to which may be attached a clip-on cooling fin.

LETTER SYMBOLS FOR TRANSISTORS AND SIGNAL DIODES

based on IEC Publication 148

LETTER SYMBOLS FOR CURRENTS, VOLTAGES AND POWERS

Basic letters

The basic letters to be used are:

I, i = current
 V, v = voltage
 P, p = power.

Lower-case basic letters shall be used for the representation of instantaneous values which vary with time.

In all other instances upper-case basic letters shall be used.

Subscripts

A, a	Anode terminal
(AV), (av)	Average value
B, b	Base terminal, for MOS devices: Substrate
(BR)	Breakdown
C, c	Collector terminal
D, d	Drain terminal
E, e	Emitter terminal
F, f	Forward
G, g	Gate terminal
K, k	Cathode terminal
M, m	Peak value
O, o	As third subscript: The terminal not mentioned is open circuited
R, r	As first subscript: Reverse. As second subscript: Repetitive. As third subscript: With a specified resistance between the terminal not mentioned and the reference terminal.
(RMS), (rms)	Root-mean-square value
S, s	{ As first or second subscript: Source terminal (for FETS only) As second subscript: Non-repetitive (not for FETS) As third subscript: Short circuit between the terminal not mentioned and the reference terminal
X, x	Specified circuit
Z, z	Replaces R to indicate the actual working voltage, current or power of voltage reference and voltage regulator diodes.

Note: No additional subscript is used for DC values.

Upper-case subscripts shall be used for the indication of:

- a) continuous (DC) values (without signal)
Example I_B
- b) instantaneous total values
Example i_B
- c) average total values
Example $I_{B(AV)}$
- d) peak total values
Example I_{BM}
- e) root-mean-square total values
Example $I_{B(RMS)}$

Lower-case subscripts shall be used for the indication of values applying to the varying component alone:

- a) instantaneous values
Example i_b
- b) root-mean-square values
Example $I_{b(rms)}$
- c) peak values
Example I_{bm}
- d) average values
Example $I_{b(av)}$

Note: If more than one subscript is used, subscript for which both styles exist shall either be all upper-case or all lower-case.

Additional rules for subscripts

Subscripts for currents

Transistors: If it is necessary to indicate the terminal carrying the current, this should be done by the first subscript (conventional current flow from the external circuit into the terminal is positive).

Examples: I_B , i_B , i_b , I_{bm}

Diodes: To indicate a forward current (conventional current flow into the anode terminal) the subscript F or f should be used; for a reverse current (conventional current flow out of the anode terminal) the subscript R or r should be used.

Examples: I_F , I_R , i_F , $I_{f(rms)}$

Subscripts for voltages

Transistors: If it is necessary to indicate the points between which a voltage is measured, this should be done by the first two subscripts. The first subscript indicates the terminal at which the voltage is measured and the second the reference terminal or the circuit node. Where there is no possibility of confusion, the second subscript may be omitted.

Examples: V_{BE} , v_{BE} , v_{be} , V_{bem}

Diodes: To indicate a forward voltage (anode positive with respect to cathode), the subscript F or f should be used; for a reverse voltage (anode negative with respect to cathode) the subscript R or r should be used.

Examples: V_F , V_R , v_F , V_{rm}

Subscripts for supply voltages or supply currents

Supply voltages or supply currents shall be indicated by repeating the appropriate terminal subscript.

Examples: V_{CC} , I_{EE}

Note: If it is necessary to indicate a reference terminal, this should be done by a third subscript

Example: V_{CCE}

Subscripts for devices having more than one terminal of the same kind

If a device has more than one terminal of the same kind, the subscript is formed by the appropriate letter for the terminal followed by a number; in the case of multiple subscripts, hyphens may be necessary to avoid misunderstanding.

Examples: I_{B2} = continuous (DC) current flowing into the second base terminal
 V_{B2-E} = continuous (DC) voltage between the terminals of second base and emitter

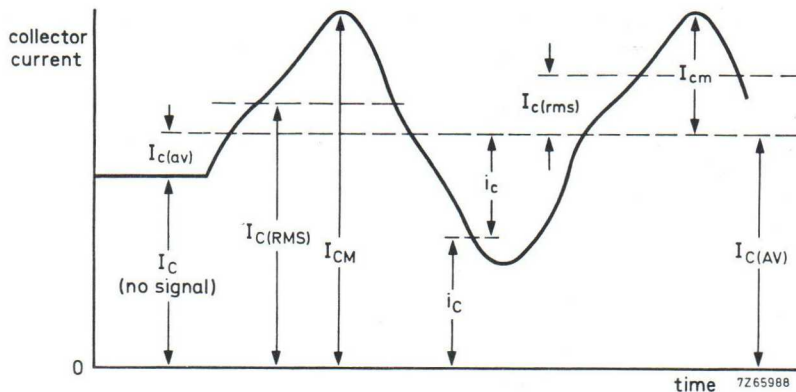
Subscripts for multiple devices

For multiple unit devices, the subscripts are modified by a number preceding the letter subscript; in the case of multiple subscripts, hyphens may be necessary to avoid misunderstanding.

Examples: I_{2C} = continuous (DC) current flowing into the collector terminal of the second unit
 V_{1C-2C} = continuous (DC) voltage between the collector terminals of the first and the second unit.

Application of the rules

The figure below represents a transistor collector current as a function of time. It consists of a continuous (DC) current and a varying component.



LETTER SYMBOLS FOR ELECTRICAL PARAMETERS

Definition

For the purpose of this Publication, the term "electrical parameter" applies to four-pole matrix parameters, elements of electrical equivalent circuits, electrical impedances and admittances, inductances and capacitances.

Basic letters

The following is a list of the most important basic letters used for electrical parameters of semiconductor devices.

B, b = susceptance; imaginary part of an admittance

C = capacitance

G, g = conductance; real part of an admittance

H, h = hybrid parameter

L = inductance

R, r = resistance; real part of an impedance

X, x = reactance; imaginary part of an impedance

Y, y = admittance;

Z, z = impedance;

Upper-case letters shall be used for the representation of:

- a) electrical parameters of external circuits and of circuits in which the device forms only a part;
- b) all inductances and capacitances.

Lower-case letters shall be used for the representation of electrical parameters inherent in the device (with the exception of inductances and capacitances).

Subscripts

General subscripts

The following is a list of the most important general subscripts used for electrical parameters of semiconductor devices:

F, f	= forward; forward transfer
I, i (or 1)	= input
L, l	= load
O, o (or 2)	= output
R, r	= reverse; reverse transfer
S, s	= source

Examples: Z_S , h_f , h_F

The upper-case variant of a subscript shall be used for the designation of static (d.c.) values.

Examples : h_{FE} = static value of forward current transfer ratio in common-emitter configuration (DC current gain)

R_E = DC value of the external emitter resistance

Note: The static value is the slope of the line from the origin to the operating point on the appropriate characteristic curve, i.e. the quotient of the appropriate electrical quantities at the operating point.

The lower-case variant of a subscript shall be used for the designation of small-signal values.

Examples: h_{fe} = small-signal value of the short-circuit forward current transfer ratio in common-emitter configuration

$Z_e = R_e + jX_e$ = small-signal value of the external impedance

Note: If more than one subscript is used, subscripts for which both styles exist shall either be all upper-case or all lower-case

Examples: h_{FE} , y_{RE} , h_{fe}

Subscripts for four-pole matrix parameters

The first letter subscript (or double numeric subscript) indicates input, output, forward transfer or reverse transfer

$$\begin{array}{l} \text{Examples: } h_i \text{ (or } h_{11}) \\ h_o \text{ (or } h_{22}) \\ h_f \text{ (or } h_{21}) \\ h_r \text{ (or } h_{12}) \end{array}$$

A further subscript is used for the identification of the circuit configuration. When no confusion is possible, this further subscript may be omitted.

$$\text{Examples: } h_{fe} \text{ (or } h_{21c}), h_{FE} \text{ (or } h_{21E})$$

Distinction between real and imaginary parts

If it is necessary to distinguish between real and imaginary parts of electrical parameters, no additional subscripts should be used. If basic symbols for the real and imaginary parts exist, these may be used.

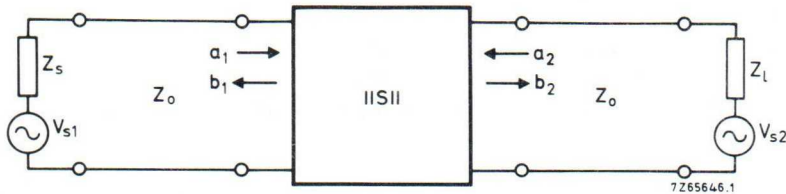
$$\begin{array}{l} \text{Examples: } Z_i = R_i + jX_i \\ y_{fe} = g_{fe} + jb_{fe} \end{array}$$

If such symbols do not exist or if they are not suitable, the following notation shall be used:

$$\begin{array}{l} \text{Examples: } \text{Re}(h_{ib}) \text{ etc. for the real part of } h_{ib} \\ \text{Im}(h_{ib}) \text{ etc. for the imaginary part of } h_{ib} \end{array}$$

SCATTERING PARAMETERS

In distinction to the conventional h, y and z-parameters, s-parameters relate to traveling wave conditions. The figure below shows a two-port network with the incident and reflected waves a_1 , b_1 , a_2 and b_2 .



$$a_1 = \frac{V_{i1}}{\sqrt{Z_0}}$$

$$a_2 = \frac{V_{i2}}{\sqrt{Z_0}}$$

1)

$$b_1 = \frac{V_{r1}}{\sqrt{Z_0}}$$

$$b_2 = \frac{V_{r2}}{\sqrt{Z_0}}$$

Z_0 = characteristic impedance of the transmission line in which the two-port is connected.

V_i = incident voltage

V_r = reflected (generated) voltage

The four-pole equations for s-parameters are:

$$b_1 = s_{11}a_1 + s_{12}a_2$$

$$b_2 = s_{21}a_1 + s_{22}a_2$$

Using the subscripts i for 11, r for 12, f for 21 and o for 22, it follows that:

$$s_i = s_{11} = \left. \frac{b_1}{a_1} \right|_{a_2 = 0}$$

$$s_r = s_{12} = \left. \frac{b_1}{a_2} \right|_{a_1 = 0}$$

$$s_f = s_{21} = \left. \frac{b_2}{a_1} \right|_{a_2 = 0}$$

$$s_o = s_{22} = \left. \frac{b_2}{a_2} \right|_{a_1 = 0}$$

1) The squares of these quantities have the dimension of power.

S-PARAMETERS

The s-parameters can be named and expressed as follows:

$s_i = s_{11}$ = Input reflection coefficient.

The complex ratio of the reflected wave and the incident wave at the input, under the conditions $Z_1 = Z_0 = 50 \Omega$ and $V_{s2} = 0$.

$s_r = s_{12}$ = Reverse transmission coefficient.

The complex ratio of the generated wave at the input and the incident wave at the output, under the conditions $Z_s = Z_0 = 50 \Omega$ and $V_{s1} = 0$.

$s_f = s_{21}$ = Forward transmission coefficient.

The complex ratio of the generated wave at the output and the incident wave at the input, under the conditions $Z_1 = Z_0 = 50 \Omega$ and $V_{s2} = 0$.

$s_o = s_{22}$ = Output reflection coefficient.

The complex ratio of the reflected wave and the incident wave at the output, under the conditions $Z_s = Z_0 = 50 \Omega$ and $V_{s1} = 0$.

Device data

SILICON AM BAND SWITCHING DIODE FOR SURFACE MOUNTING

The BA423L is a switching diode intended for band switching in AM radio receivers.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with lead/tin plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20 V
Forward current (DC)	I_F	max.	50 mA
Junction temperature	T_J	max.	100 °C
Diode capacitance at $f = 1$ MHz $V_R = 3$ V	C_d	<	2.5 pF
Series resistance at $f = 1$ MHz $I_F = 10$ mA	r_s	<	1.2 Ω

MECHANICAL DATA

Dimensions in mm

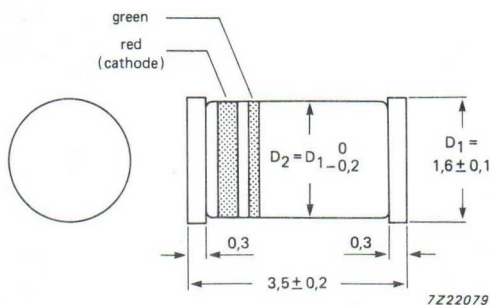


Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20 V
Forward current (DC)	I_F	max.	50 mA
Storage temperature range	T_{stg}		-65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient on a ceramic
substrate of 8 mm x 10 mm x 0.7 mm
(see soldering recommendations SOD-80)

R_{thj-a}	max.	400 K/W
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CHARACTERISTICS

 $T_{amb} = 25\text{ °C}$ unless otherwise specified

Forward voltage

$I_F = 50\text{ mA}$

V_F	<	0.9 V
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Reverse current

$V_R = 20\text{ V}$

$V_R = 20\text{ V}; T_j = 125\text{ °C}$

I_R	<	100 nA
	<	5.0 μA

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 3\text{ V}$

C_d	<	2.5 pF
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Series resistance at $f = 1\text{ MHz}$

$I_F = 10\text{ mA}$

r_s	<	1.2 Ω
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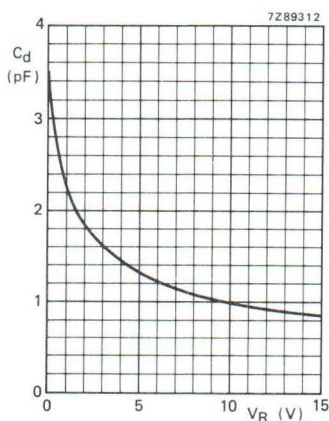


Fig. 2 Diode capacitance as a function of continuous reverse voltage;
 $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$;
typical values.

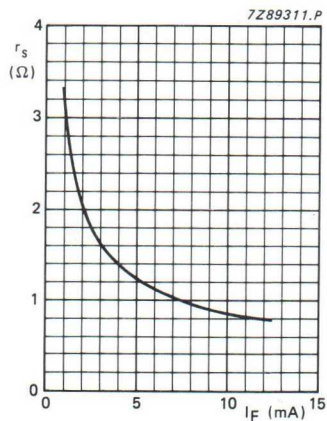


Fig. 3 Series resistance as a function of forward current;
 $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$;
typical values.

BAND-SWITCHING DIODES FOR SURFACE MOUNTING

Switching diodes in a SOD-80 envelope, intended for band switching in v.h.f. television tuners. A special feature of these diodes is their low capacitance.

These SM diodes are leadless diodes in an hermetically sealed micro-miniature glass envelope with tin-plated metal discs at each end. They are suitable for Automatic Placement and as such they can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

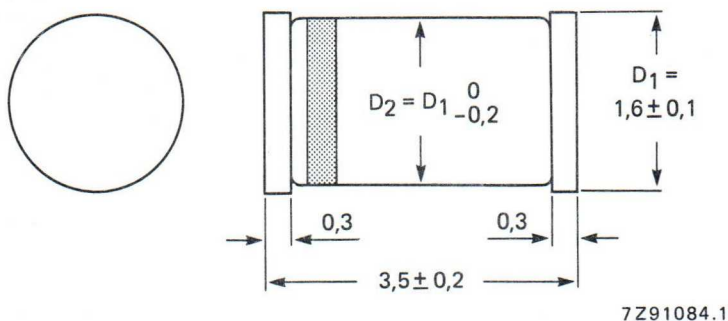
QUICK REFERENCE DATA

			BA682	BA683	
Continuous reverse voltage	V_R	max.	35	35	V
Forward current (d.c.)	I_F	max.	100	100	mA
Junction temperature	T_j	max.	150	150	°C
Diode capacitance $V_R = 3 \text{ V}; f = 1 \text{ MHz}$	C_d	<	1,25	1,2	pF
Series resistance at $f = 200 \text{ MHz}$					
$I_F = 3 \text{ mA}$	r_D	<	0,7	1,2	Ω
$I_F = 10 \text{ mA}$		<	0,5	0,9	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a red band.

The BA683 cathode has an additional orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}		-65 to +150	°C
Junction temperature	T_j		150	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0,6	K/mW
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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

Forward voltage

$I_F = 100\text{ mA}$

V_F	<	1,0	V
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Reverse current

$V_R = 20\text{ V}$

$V_R = 20\text{ V}; T_{amb} = 75\text{ °C}$

I_R	<	50	nA
	<	1	μA

	BA682	BA683	
--	-------	-------	--

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 1\text{ V}$

$V_R = 3\text{ V}$

C_d	<	1,5	1,5	pF
	<	1,25	1,2	pF

Series resistance at $f = 200\text{ MHz}$

$I_F = 3\text{ mA}$

$I_F = 10\text{ mA}$

r_D	<	0,7	1,2	Ω
	<	0,5	0,9	Ω

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

Silicon epitaxial high-speed diode in a microminiature plastic envelope. It is intended for high-speed switching in hybrid thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Repetitive peak forward current	I_{FRM}	max.	500 mA
Junction temperature	T_j	max.	150 °C
Forward voltage at $I_F = 50$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	45 pC

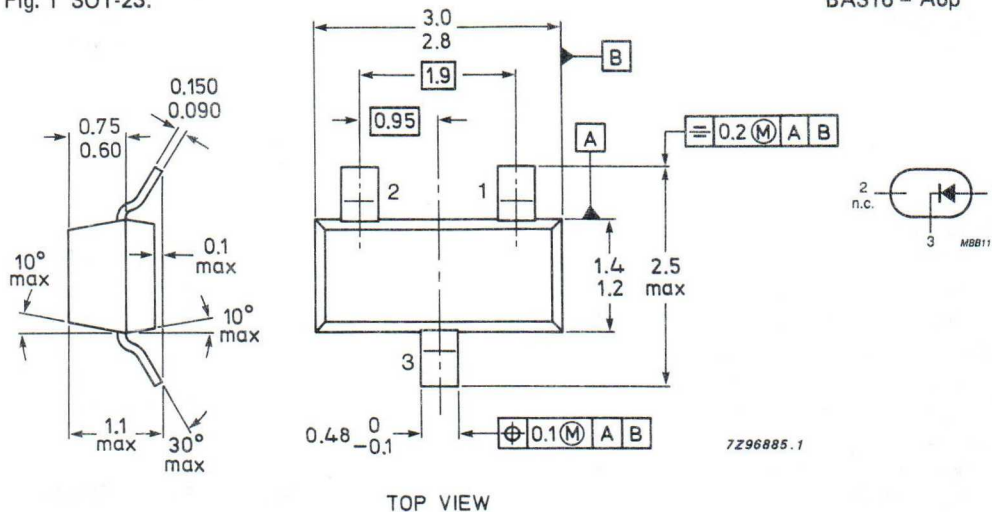
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-23.

BAS16 = A6p



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Average rectified forward current* (averaged over any 20 ms period) up to $T_{amb} = 25^\circ\text{C}$	$I_F(AV)$	max.	250 mA
Forward current (DC)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	500 mA
Non-repetitive peak forward current (per crystal) $t = 1\ \mu\text{s}$	I_{FSM}	max.	2 A
$t = 1\ \text{ms}$	I_{FSM}	max.	1 A
$t = 1\ \text{s}$	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		-65 to $+150^\circ\text{C}$
Junction temperature	T_j	max.	150°C

THERMAL RESISTANCE**

From junction to ambient [▲]	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified.

Forward voltage			
$I_F = 1\ \text{mA}$	V_F	<	715 mV
$I_F = 10\ \text{mA}$	V_F	<	855 mV
$I_F = 50\ \text{mA}$	V_F	<	1000 mV
$I_F = 150\ \text{mA}$	V_F	<	1250 mV
Reverse current			
$V_R = 25\ \text{V}; T_j = 150^\circ\text{C}$	I_R	<	30 μA
$V_R = 75\ \text{V}$	I_R	<	1 μA
$V_R = 75\ \text{V}; T_j = 150^\circ\text{C}$	I_R	<	50 μA
Diode capacitance			
$V_R = 0; f = 1\ \text{MHz}$	C_d	<	2 pF
Forward recovery voltage (see also Fig. 2) when switched to $I_F = 10\ \text{mA}; t_p = 20\ \text{ns}$	V_{fr}	<	1,75 V
Reverse recovery time (see also Fig. 3) when switched from $I_F = 10\ \text{mA}$ to $I_R = 10\ \text{mA};$ $R_L = 100\ \Omega$; measured at $I_R = 1\ \text{mA}$	t_{rr}	<	6 ns
Recovery charge (see also Fig. 4) when switched from $I_F = 10\ \text{mA}$ to $V_R = 5\ \text{V};$ $R_L = 500\ \Omega$	Q_s	<	45 pC

* Measured under pulse conditions. $t_p \leq 0,5\ \text{ms}$. $I_F(AV) = 150\ \text{mA}$, $t(AV) \leq 1\ \text{ms}$, for sinusoidal operation.** See *Thermal characteristics*.

▲ Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

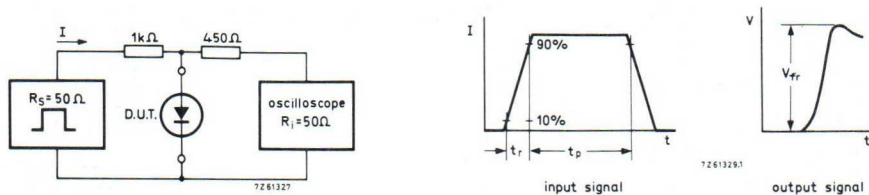


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: forward pulse rise time = $t_r = 20$ ns; forward current pulse duration $t_p = 120$ ns; duty factor = $\delta = 0,01$.

Oscilloscope: rise time = $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

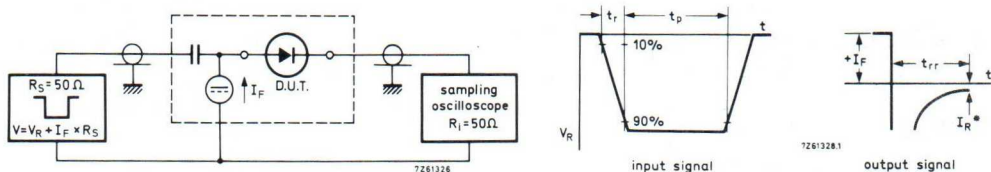


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: reverse pulse rise time = $t_r = 0,6$ ns; reverse pulse duration = $t_p = 100$ ns; duty factor = $\delta = 0,05$.
* t_{rr} up to $I_R = 1$ mA.

Oscilloscope: rise time = $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

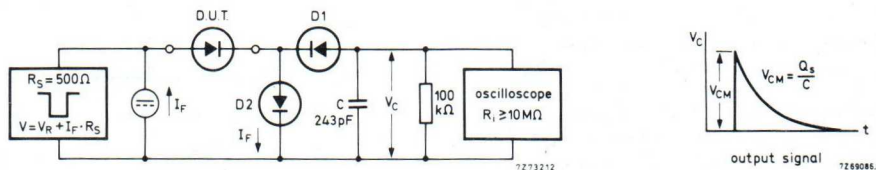


Fig. 4 Recovery charge test circuit and waveform.

D1 = BAW62; D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal

Rise time of the reverse pulse

Reverse pulse duration

Duty factor

$$\begin{aligned} t_r &= 2 \text{ ns} \\ t_p &= 400 \text{ ns} \\ \delta &= 0,02 \end{aligned}$$

Circuit capacitance $C \leq 7$ pF (C = oscilloscope input capacitance + parasitic capacitance).

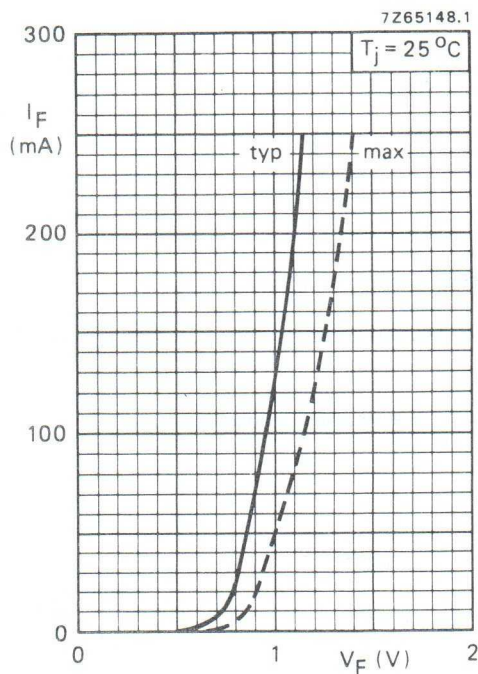


Fig. 5.

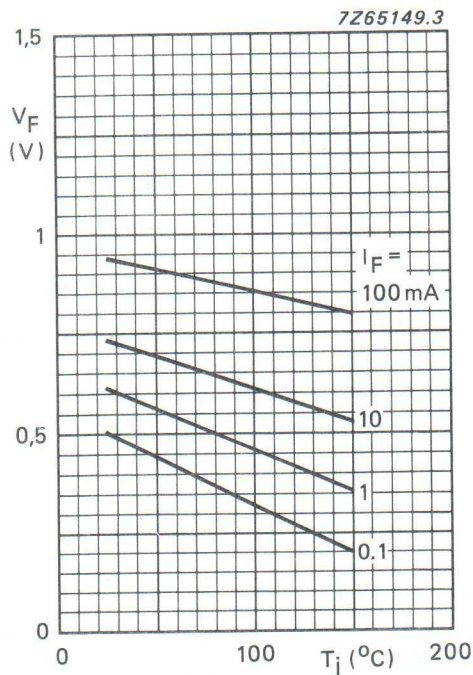


Fig. 6 Typical values.

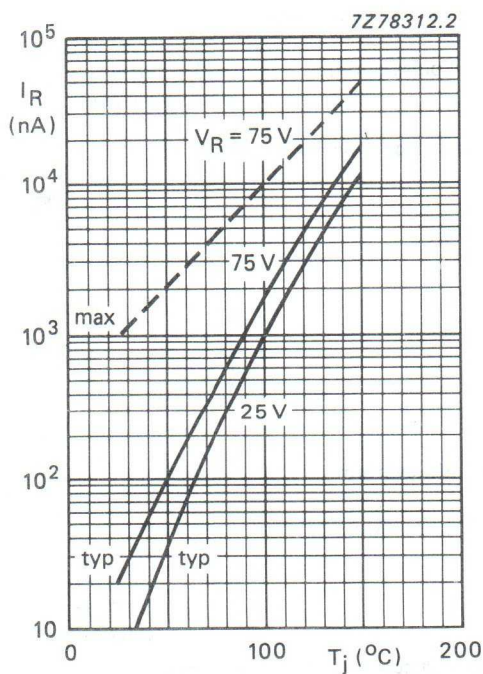


Fig. 7.

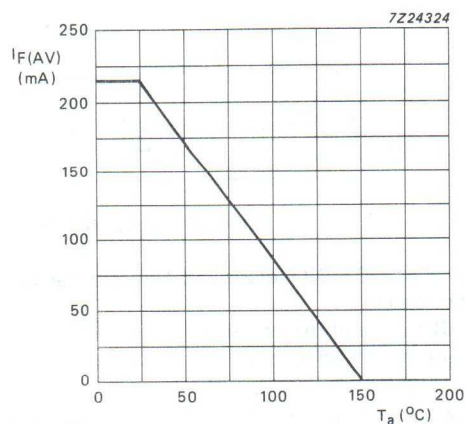


Fig. 8 Current derating curve.

LOW VOLTAGE STABISTOR

Silicon planar epitaxial diode in SOT-23 envelope. This diode is intended for low voltage stabilizing e.g. bias stabilizer in class-B output stages, clipping, clamping and meter protection.

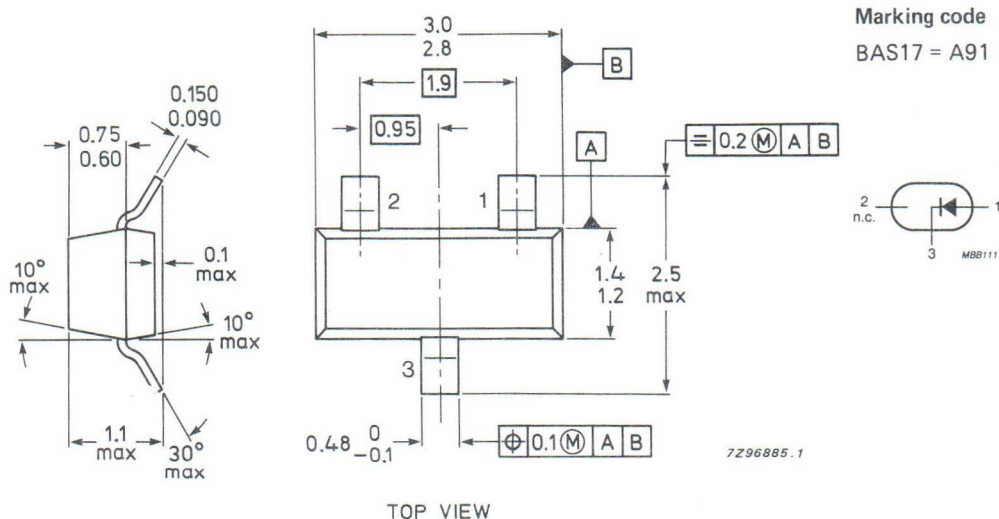
QUICK REFERENCE DATA

Repetitive peak forward current	I_{FRM}	max.	250 mA
Storage temperature	T_{stg}	-65 to + 150	°C
Junction temperature	T_j	max.	150 °C
Forward voltage			
$I_F = 0,1$ mA	V_F	580 to 660	mV
$I_F = 1,0$ mA	V_F	665 to 745	mV
$I_F = 10$ mA	V_F	750 to 830	mV
$I_F = 100$ mA	V_F	870 to 960	mV
Diode capacitance			
$V_R = 0$; $f = 1$ MHz	C_d	<	140 pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.



See also chapter *Soldering Recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current *	I_{FRM}	max.	250 mA
Storage temperature	T_{stg}	-65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS **

From junction to ambient *	$R_{th\ j-t}$	=	420 K/W
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CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage

 $I_F = 0,1\text{ mA}$ V_F 580 to 660 mV $I_F = 1,0\text{ mA}$ V_F 665 to 745 mV $I_F = 5,0\text{ mA}$ V_F 725 to 805 mV $I_F = 10\text{ mA}$ V_F 750 to 830 mV $I_F = 100\text{ mA}$ V_F 870 to 960 mV

Reverse current

 $V_R = 4\text{ V}$ I_R < 5 μA

Temperature coefficient

 $I_F = 1\text{ mA}$ S_F typ. -1,8 mV/K

Diode capacitance

 $V_R = 0$; $f = 1\text{ MHz}$ C_d < 140 pF

* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.

** See *Thermal characteristics*.

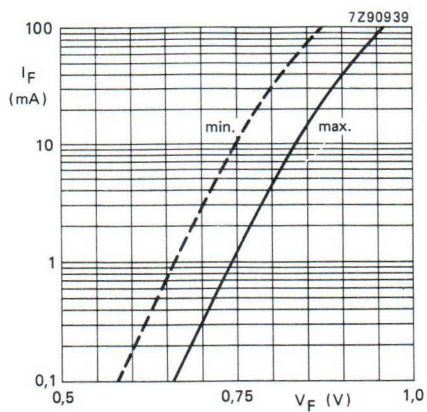


Fig. 2 Forward current as a function of forward voltage.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

Silicon epitaxial high-speed diodes in a microminiature plastic envelope. They are intended for switching and general purposes.

QUICK REFERENCE DATA

			BAS19	BAS20	BAS21	
Continuous reverse voltage	V_R	max.	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250	V
Repetitive peak forward current	I_{FRM}	max.		625		mA
Junction temperature	T_j	max.		150		°C
Forward voltage at $I_F = 100$ mA	V_F	<		1		V
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$ measured at $I_R = 3$ mA	t_{rr}	<		50		ns

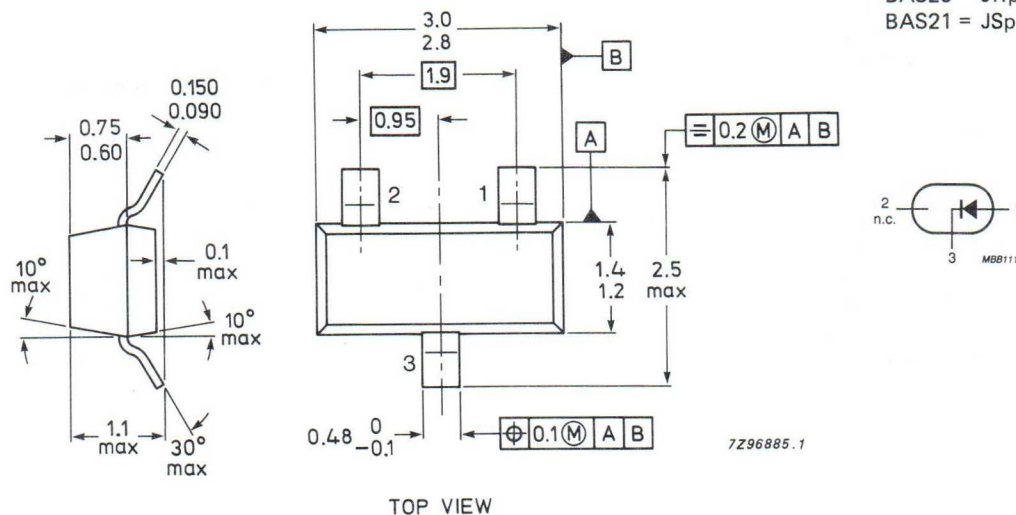
MECHANICAL DATA

Dimensions in mm

Marking code

BAS19 = JPP
BAS20 = JRp
BAS21 = JSp

Fig. 1 SOT-23.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAS19	BAS20	BAS21
Continuous reverse voltage	V_R	max.	100	150	200 V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250 V
Non-repetitive peak forward current (per crystal)					
$t = 1 \mu s$	I_{FSM}	max.		2,5	A
$t = 1 s$	I_{FSM}	max.		0,5	A
Average rectified forward current (1) (averaged over any 20 ms period)	$I_{F(AV)}$	max.		200	mA
Forward current (DC) up to $T_{amb} = 25^\circ C^*$	I_F	max.		200	mA
Repetitive peak forward current	I_{FRM}	max.		625	mA
Storage temperature range	T_{stg}			-65 to + 150	$^\circ C$
Junction temperature	T_j	max.		150	$^\circ C$
Total power dissipation up to $T_{amb} = 25^\circ C$	P_{tot}	max.		200	mW

THERMAL RESISTANCE **

From junction to ambient* $R_{th j-a} = 430 \text{ K/W}$

CHARACTERISTICS

$T_j = 25^\circ C$ unless otherwise specified.

Forward voltage					
$I_F = 100 \text{ mA}$	V_F		<	1,0	V
$I_F = 200 \text{ mA}$	V_F		<	1,25	V
Reverse breakdown voltage (1)					
BAS19; $I_R = 100 \mu A$	$V_{(BR)R}$		>	120	V
BAS20; $I_R = 100 \mu A$	$V_{(BR)R}$		>	200	V
BAS21; $I_R = 100 \mu A$ (2)	$V_{(BR)R}$		>	250	V
Reverse current					
$V_R = V_{Rmax}$	I_R		<	100	nA
$V_R = V_{Rmax}; T_j = 150^\circ C$	I_R		<	100	μA
Differential resistance					
$I_F = 10 \text{ mA}$	r_{diff}		typ.	5	Ω

(1) Measured under pulse conditions; Pulse time = $t_p \leq 0,3 \text{ ms}$.

(2) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited to 275 V.

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** See *Thermal characteristics*.

Diode capacitance

$$V_R = 0; f = 1 \text{ MHz}$$

$$C_d < 5 \text{ pF}$$

Reverse recovery time (see Figs 2 and 3)

when switched from $I_F = 30 \text{ mA}$ to $I_R = 30 \text{ mA}$; $R_L = 100 \Omega$; measured at $I_R = 3 \text{ mA}$

$$t_{rr} < 50 \text{ ns}$$

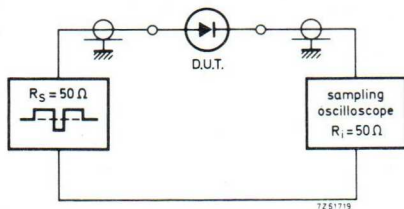
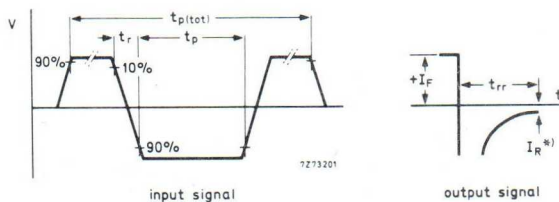


Fig. 2 Test circuit.

Fig. 3 Waveforms; $I_R = 3 \text{ mA}$.

Input signal

total pulse duration

$$t_p(\text{tot}) = 2 \mu\text{s}$$

duty factor

$$\delta = 0,0025$$

rise time of reverse pulse

$$t_r = 0,6 \text{ ns}$$

reverse pulse duration

$$t_p = 100 \text{ ns}$$

Oscilloscope

rise time

$$t_r = 0,35 \text{ ns}$$

circuit capacitance*

$$C < 1 \text{ pF}$$

*C = oscilloscope input capacitance + parasitic capacitance.

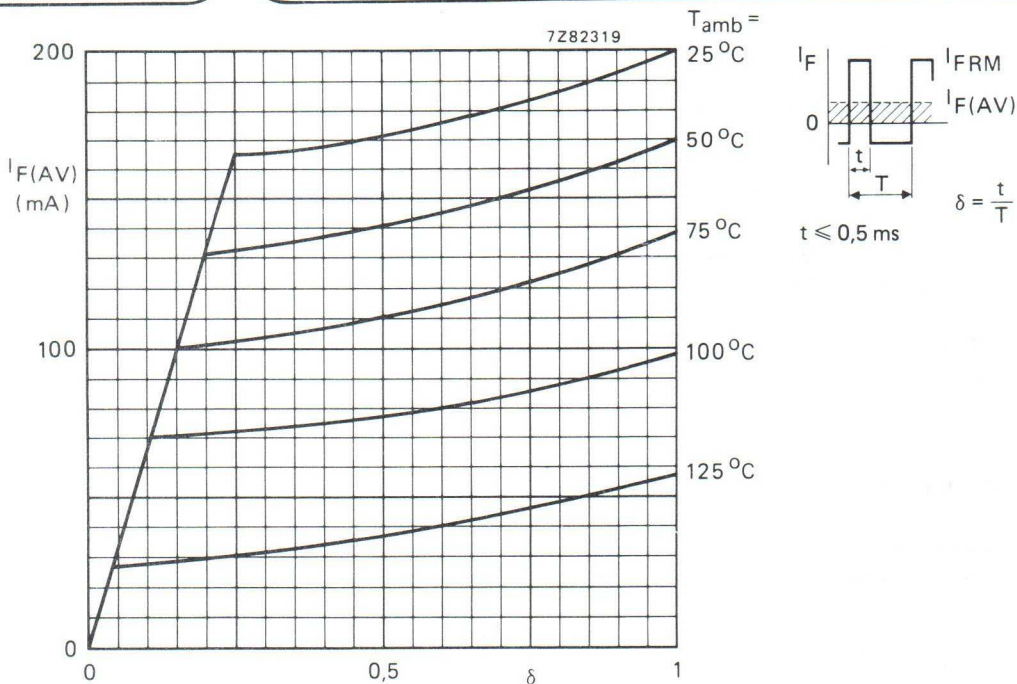


Fig. 4 BAS19; maximum permissible average rectified forward current for pulse operation as a function of the duty factor at $V_R = 100$ V.

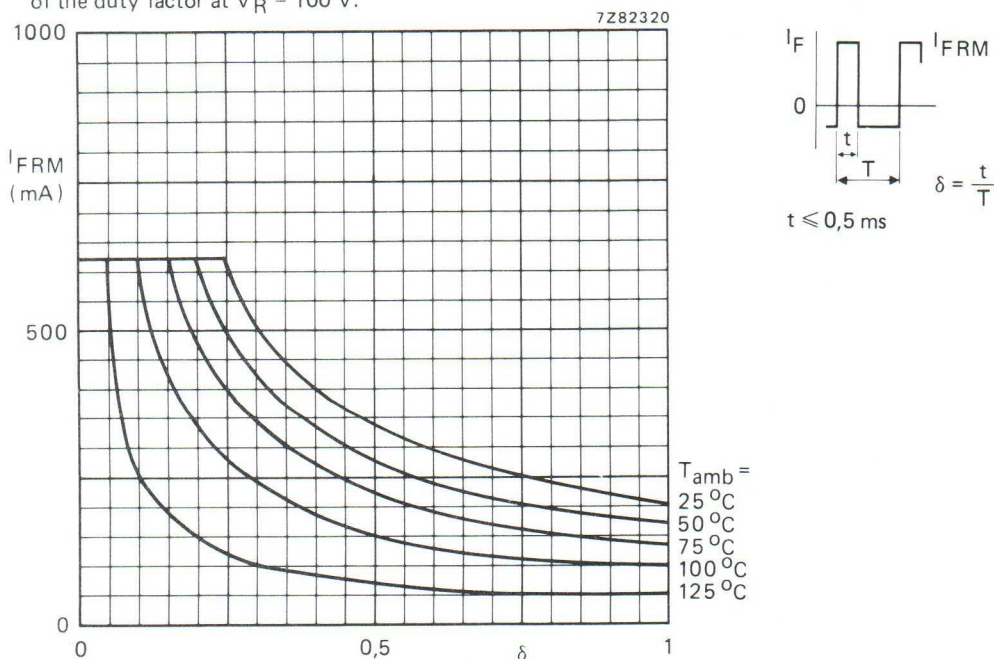


Fig. 5 BAS19; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor at $V_R = 100$ V.

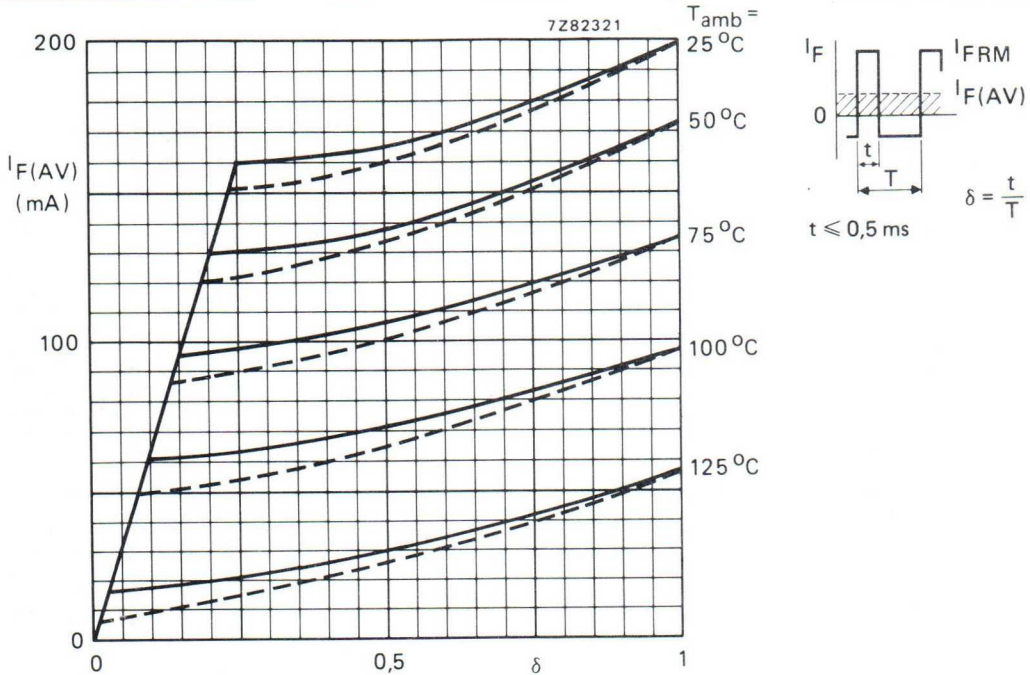


Fig. 6 BAS20/21; maximum permissible average rectified forward current for pulse operation as a function of the duty factor.

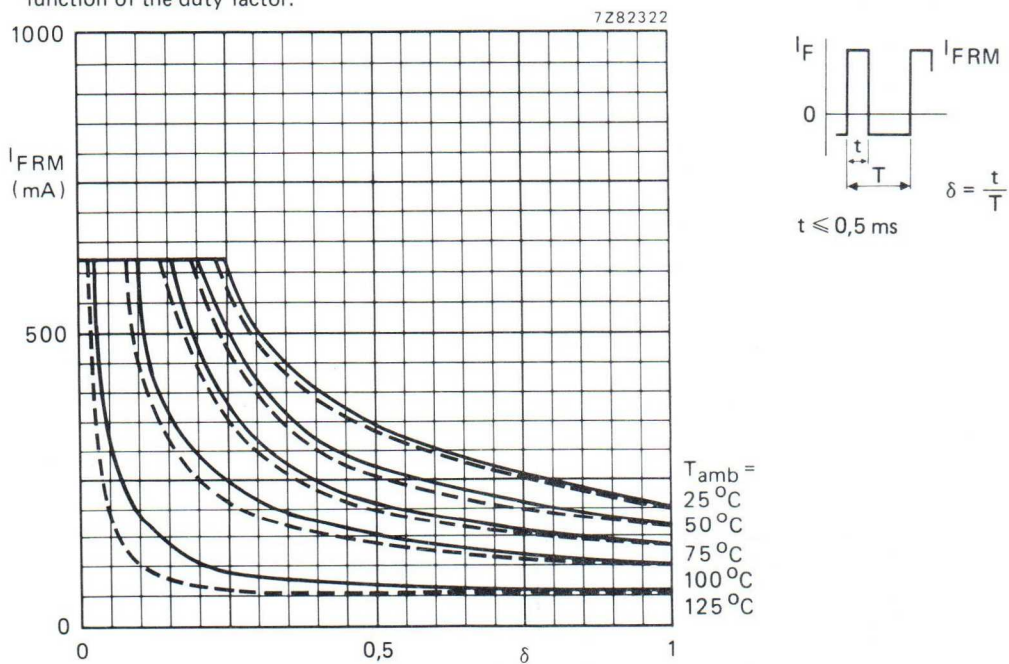


Fig. 7 BAS20/21; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor.

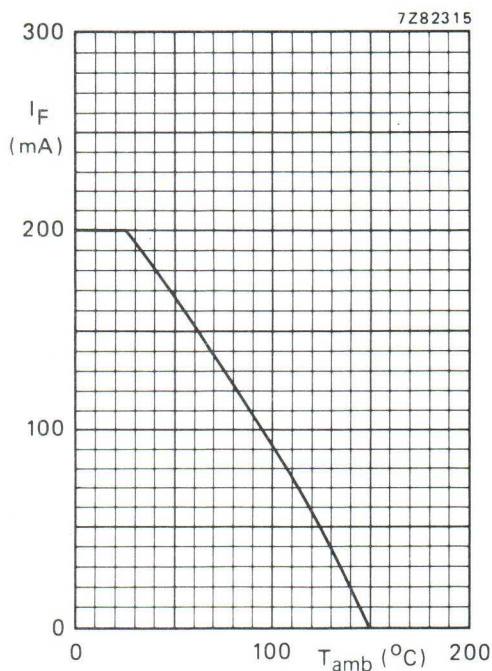


Fig. 8.

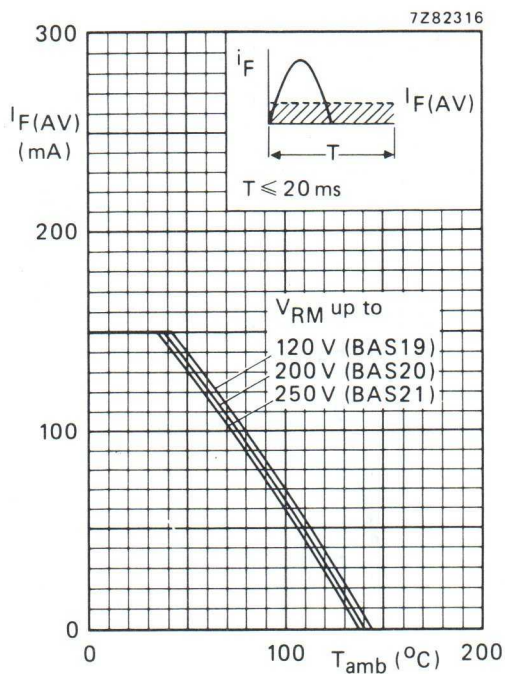


Fig. 9.

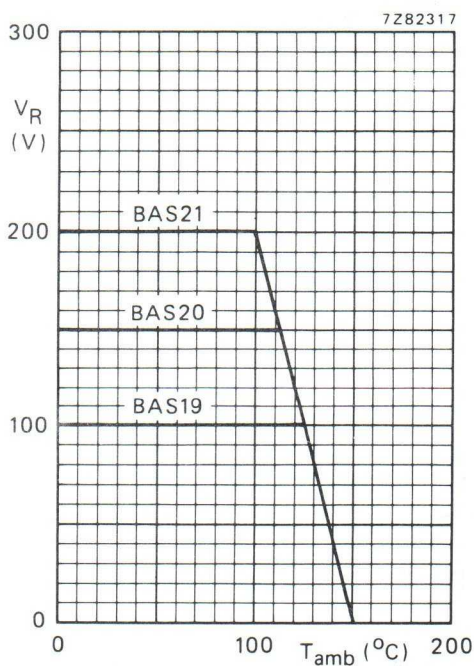


Fig. 10.

Fig. 8 Maximum permissible continuous forward current as a function of the ambient temperature.

Fig. 9 Maximum permissible average rectified forward current as a function of the ambient temperature.

Fig. 10 Maximum permissible continuous reverse voltage as a function of the ambient temperature.

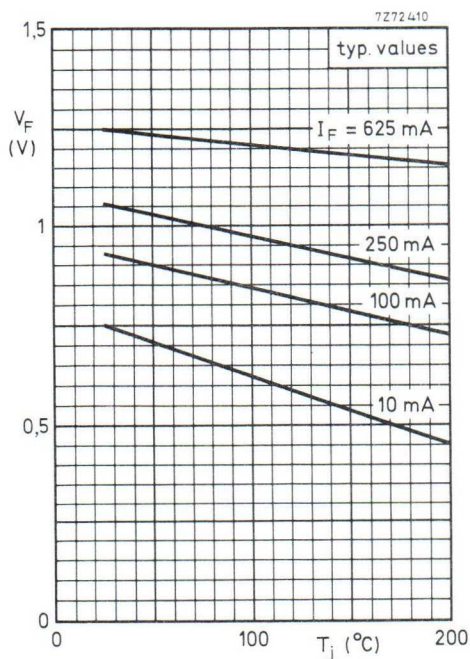
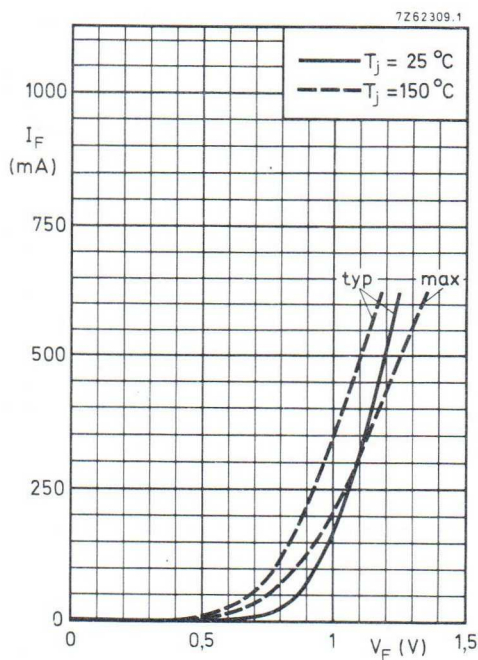
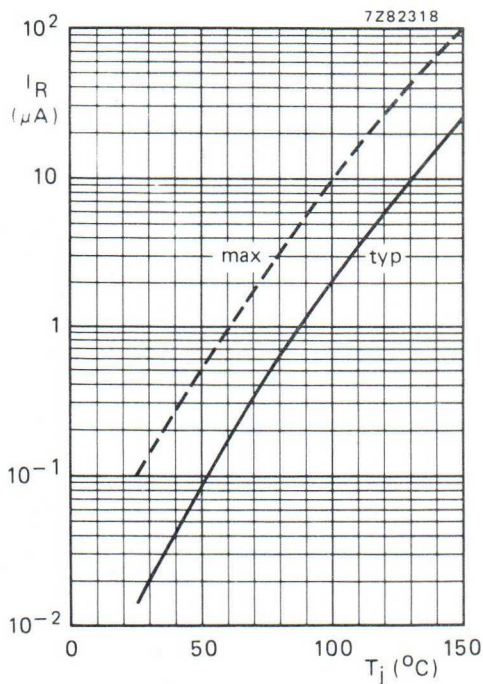


Fig. 11 Continuous reverse current as a function of the junction temperature.

Fig. 12 Forward current as a function of forward voltage.

Fig. 13 Forward voltage as a function of the junction temperature.

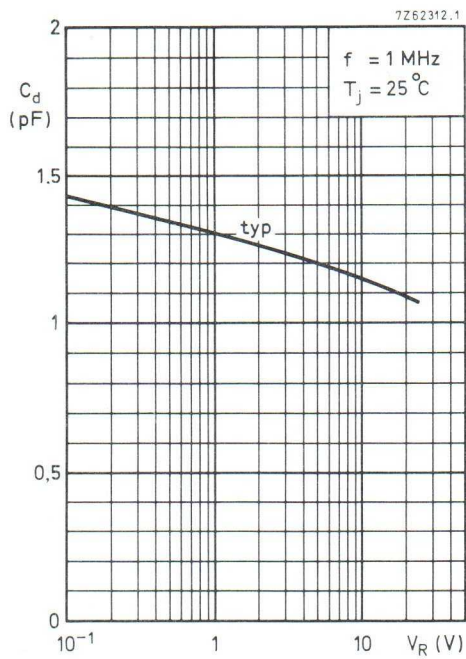


Fig. 14.

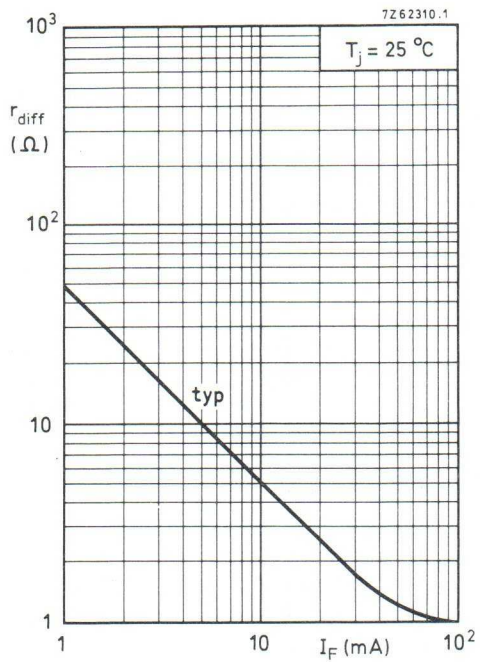


Fig. 15.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The BAS28 consists of two separate diodes in one microminiature envelope intended for surface mounting.

It concerns fast-switching general-purpose diodes.

QUICK REFERENCE DATA

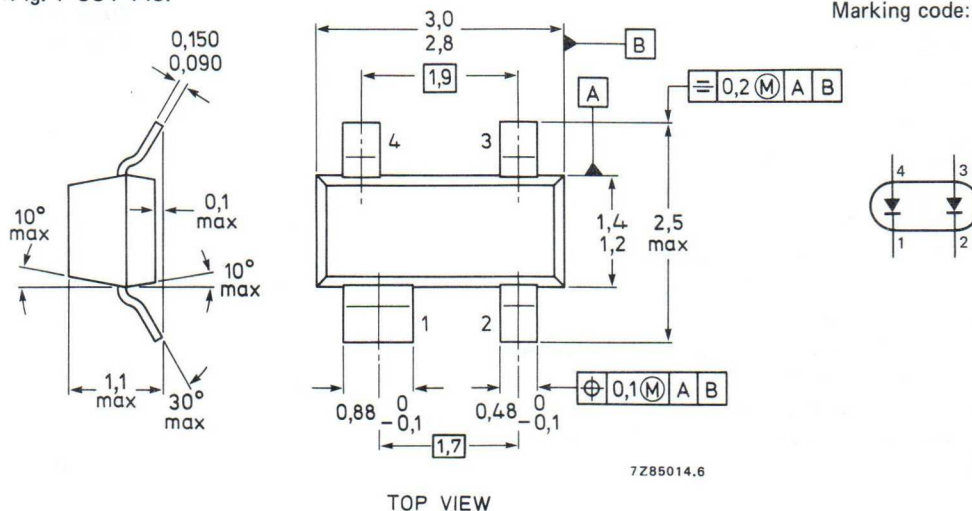
Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Repetitive peak forward current	I_{FRM}	max.	250 mA
Junction temperature	T_j	max.	150 °C
Forward voltage at $I_F = 50$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$, measured at $I_R = 1$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	45 pC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code: JTp



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Average rectified forward current* (averaged over any 20 ms period) up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	$I_{F(AV)}$	max.	215 mA
Forward current (DC)	I_F	max.	215 mA
Repetitive peak forward current	I_{FRM}	max.	215 mA
Non-repetitive peak forward current (per crystal) $t = 1\text{ }\mu\text{s}$	I_{FSM}	max.	2 A
$t = 1\text{ ms}$	I_{FSM}	max.	1 A
$t = 1\text{ s}$	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		$-65\text{ to }+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient **	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Forward voltage

$I_F = 1\text{ mA}$	V_F	<	715 mV
$I_F = 10\text{ mA}$	V_F	<	855 mV
$I_F = 50\text{ mA}$	V_F	<	1000 mV
$I_F = 150\text{ mA}$	V_F	<	1250 mV

Reverse current

$V_R = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	I_R	<	30 μA
$V_R = 75\text{ V}$	I_R	<	1 μA
$V_R = 75\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	I_R	<	50 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	<	2 pF
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Forward recovery voltage (see also Fig. 2)

when switched to $I_F = 10\text{ mA}; t_p = 20\text{ ns}$	V_{fr}	<	1,75 V
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Reverse recovery time (see also Fig. 3)

when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA};$ $R_L = 100\text{ }\Omega$; measured at $I_R = 1\text{ mA}$	t_{rr}	<	6 ns
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Recovery charge (see also Fig. 4)

when switched from $I_F = 10\text{ mA}$ to $V_R = 5\text{ V};$ $R_L = 500\text{ }\Omega$	Q_s	<	45 pC
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* Measured under pulse conditions. $t_p \leq 0,5\text{ ms}$. $I_{F(AV)} = 150\text{ mA}$, $t_{(av)} \leq 1\text{ ms}$, for sinusoidal operation.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

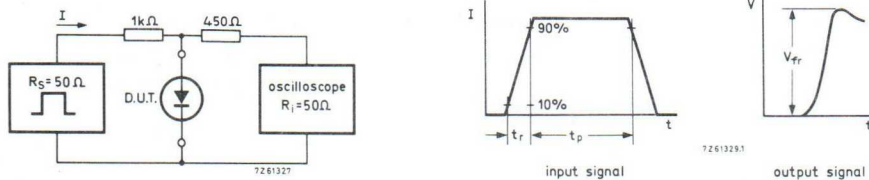


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: forward pulse rise time $t_r = 20$ ns; forward current pulse duration $t_p = 120$ ns; duty factor $= 0,01$.

Oscilloscope: rise time $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance).

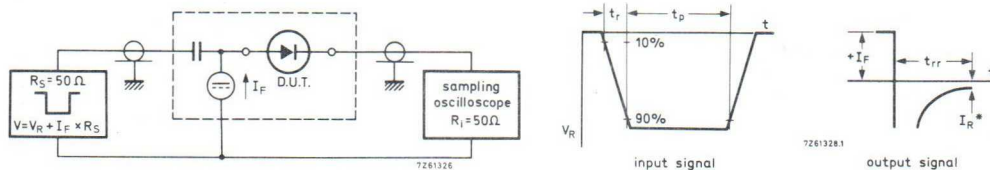


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: reverse pulse rise time $t_r = 0,6$ ns; reverse pulse duration $t_p = 100$ ns; duty factor $= 0,05$.
* t_{rr} up to $I_R = 1$ mA.

Oscilloscope: rise time $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance).

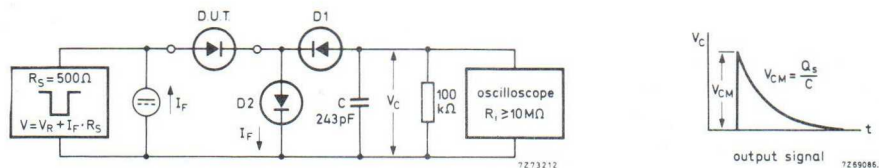


Fig. 4 Recovery charge test circuit and waveform.

D1 = BAW62; D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal

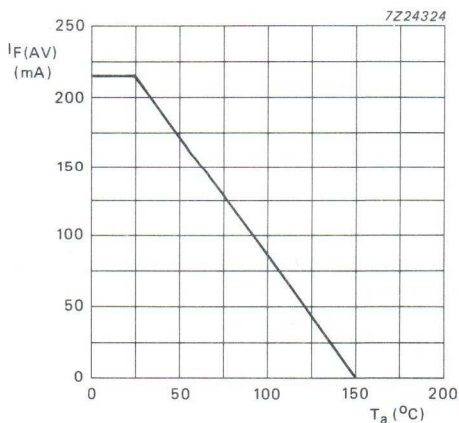
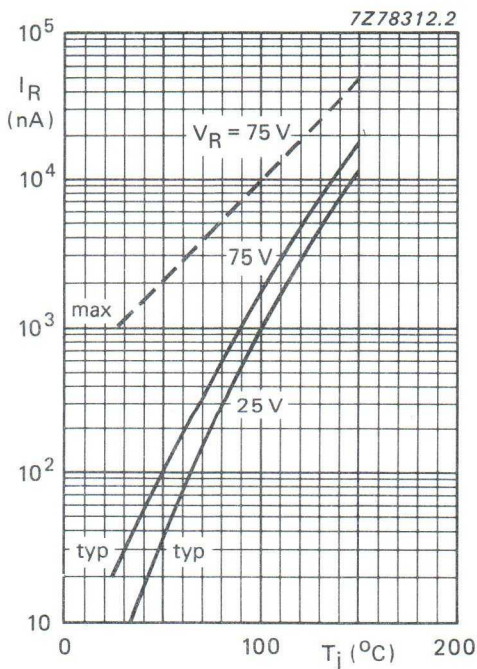
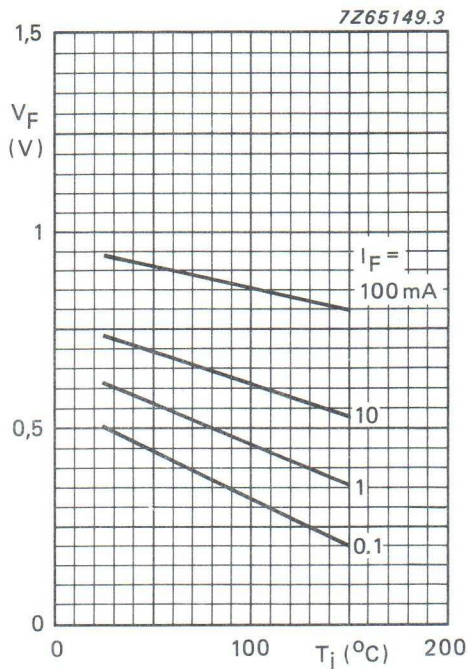
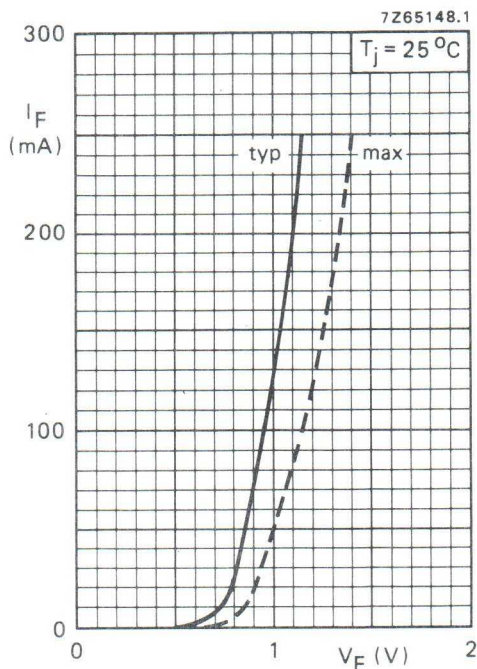
Rise time of the reverse pulse

Reverse pulse duration

Duty factor

$$\begin{aligned} t_r &= 2 \text{ ns} \\ t_p &= 400 \text{ ns} \\ \delta &= 0,02 \end{aligned}$$

Circuit capacitance $C \leq 7$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance).



RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	90 V
Repetitive peak forward current	I_{FRM}	max.	600 mA
Repetitive peak reverse current	I_{RRM}	max.	600 mA
Average rectified forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Non-repetitive peak forward current $t = 1 \mu s$; $T_j = 25^\circ C$ prior to surge; per crystal $t = 1 s$; $T_j = 25^\circ C$ prior to surge; per crystal	I_{FSM}	max.	3 A 0,75 A
Forward current (DC)	I_F	max.	250 mA
Repetitive peak reverse energy $t_p \geq 50 \mu s$; $f \leq 20 \text{ Hz}$; $T_j = 25^\circ C$	E_{RRM}	max.	5,0 mJ
Storage temperature	T_{stg}		$-65 \text{ to } +150^\circ C$
Junction temperature	T_j	max.	150 $^\circ C$

THERMAL RESISTANCE*

From junction to ambient**	R_{thj-a}	=	430 K/W
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CHARACTERISTICS (per diode)

$T_j = 25^\circ C$ unless otherwise specified

Forward voltage			
$I_F = 10 \text{ mA}$	V_F	<	0,75 V
$I_F = 50 \text{ mA}$	V_F	<	0,84 V
$I_F = 100 \text{ mA}$	V_F	<	0,90 V
$I_F = 200 \text{ mA}$	V_F	<	1,00 V
$I_F = 400 \text{ mA}$	V_F	<	1,25 V
Reverse current			
$V_R = 90 \text{ V}$	I_R	<	100 nA
$V_R = 90 \text{ V}$; $T_j = 150^\circ C$	I_R	<	100 μA
Reverse avalanche breakdown voltage			
$I_R = 1 \text{ mA}$	$V_{(BR)R}$		120 to 175 V
Diode capacitance			
$V_R = 0$; $f = 1 \text{ MHz}$	C_d	<	35 pF
Reverse recovery time when switched from $I_F = 30 \text{ mA}$ to $I_R = 30 \text{ mA}$; $R_L = 100 \Omega$; measured at $I_R = 3 \text{ mA}$	t_{rr}	<	50 ns

* See Thermal Characteristics.

** When mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

HIGH-SPEED SILICON DIODE FOR SURFACE MOUNTING

The BAS32 is a planar epitaxial high-speed diode designed for fast logic applications.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

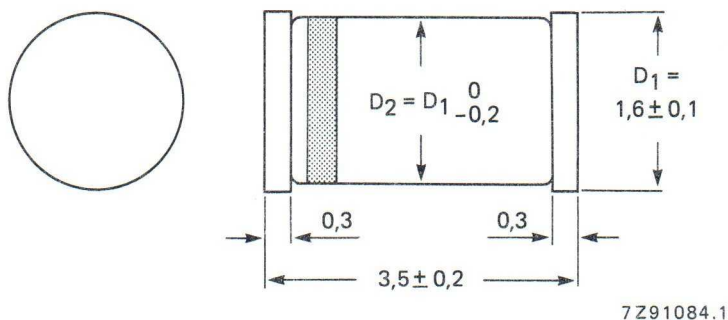
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	75 V
Repetitive peak forward current	I_{FRM}	max.	450 mA
Junction temperature	T_j	max.	200 °C
Forward voltage $I_F = 100$ mA	V_F	<	1 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	4 ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	75 V*
Average rectified forward current	$I_F(AV)$	max.	150 mA**
Forward current (d.c.)	I_F	max.	200 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current			
$t = 1 \mu s$	I_{FSM}	max.	2000 mA
$t = 1 s$	I_{FSM}	max.	500 mA
Storage temperature	T_{stg}		-65 to + 200 °C
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th j-a}$	=	600 K/W
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CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltages

$I_F = 5\text{ mA}$	V_F	0,62 to 0,75 V
$I_F = 100\text{ mA}$	V_F	< 1,00 V
$I_F = 100\text{ mA}; T_j = 100\text{ °C}$	V_F	< 0,93 V

Reverse currents

$V_R = 20\text{ V}$	I_R	< 25 nA
$V_R = 20\text{ V}; T_j = 150\text{ °C}$	I_R	< 50 μA
$V_R = 75\text{ V}$	I_R	< 5 μA
$V_R = 75\text{ V}; T_j = 150\text{ °C}$	I_R	< 100 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	< 2 pF
-----------------------------	-------	--------

Forward recovery voltage when switched to

$I_F = 50\text{ mA}; t_r = 20\text{ ns}$	V_{fr}	< 2,5 V
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* Measured at zero life time at $I_R = 100\text{ }\mu A; V_R > 100\text{ V}$.

** For sinusoidal operation see Fig. 6. For pulse operation see Figs 4 and 5.

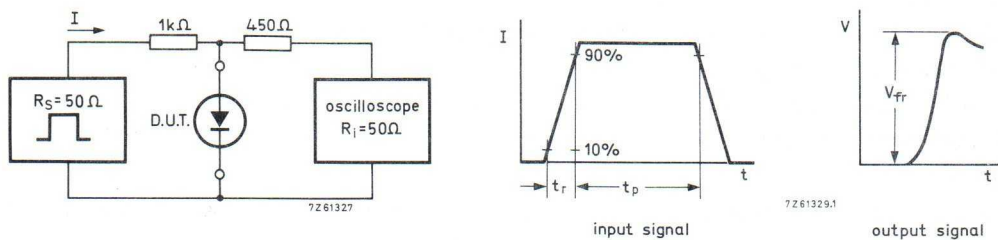


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal : Rise time of the forward pulse $t_r = 20 \text{ ns}$
 Forward current pulse duration $t_p = 120 \text{ ns}$
 Duty factor $\delta = 0,01$

Oscilloscope: Rise time $t_r = 0,35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Reverse recovery time when switched from
 $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \Omega$;
 measured at $I_R = 1 \text{ mA}$

$$t_{rr} < 4 \text{ ns}$$

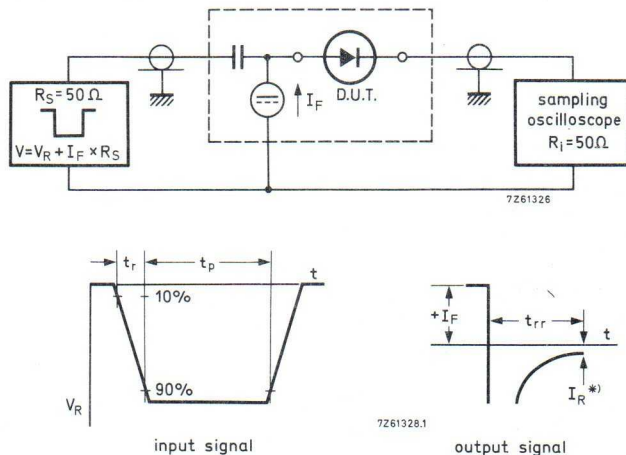


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal : Rise time of the reverse pulse $t_r = 0,6 \text{ ns}$
 Reverse pulse duration $t_p = 100 \text{ ns}$
 Duty factor $\delta = 0,05$

* $I_R = 1 \text{ mA}$

Oscilloscope: Rise time $t_r = 0,35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

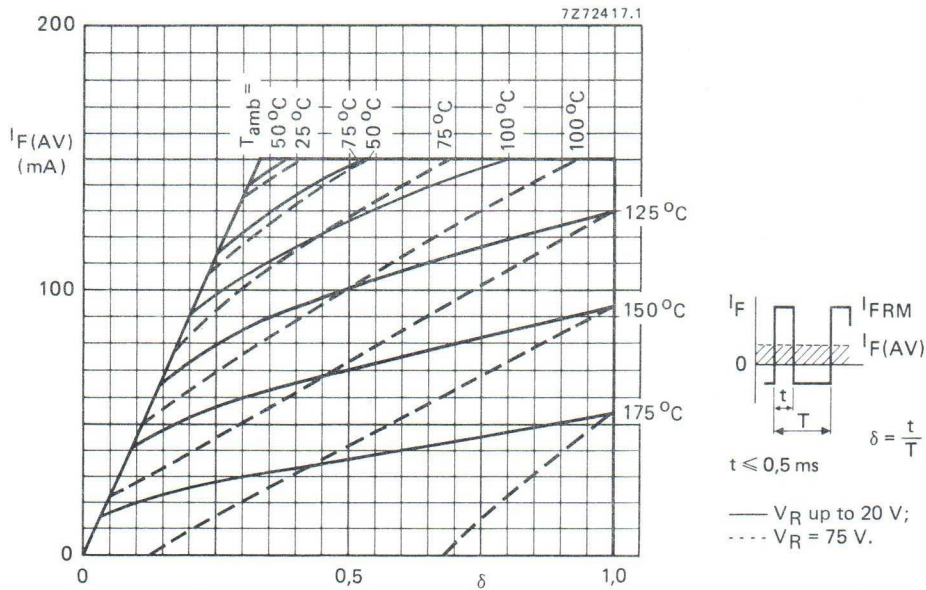


Fig. 4 Maximum permissible average rectified forward current versus duty factor (pulse operated).

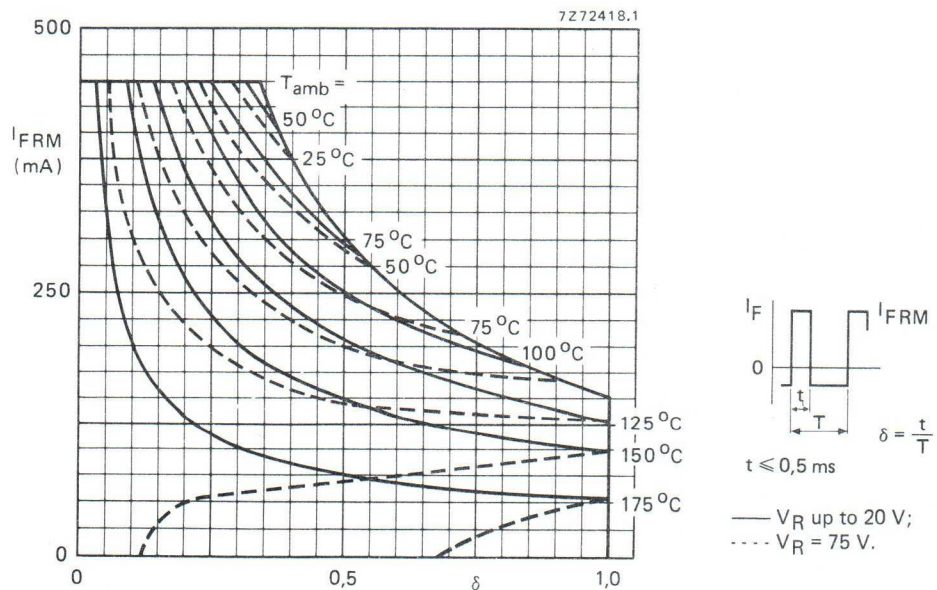


Fig. 5 Maximum permissible repetitive peak forward current versus duty factor (pulse operated).

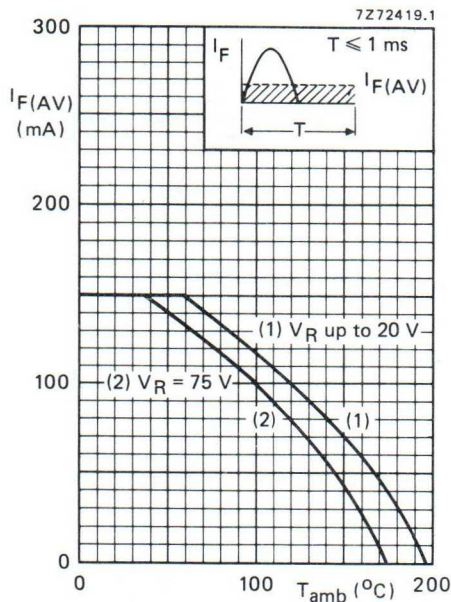


Fig. 6 Maximum permissible average rectified forward current versus ambient temperature.

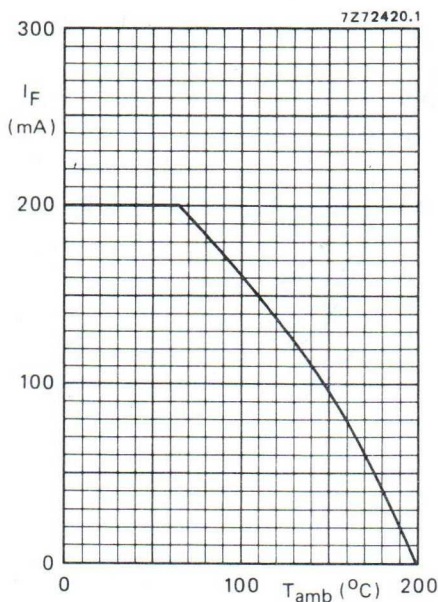


Fig. 7 Maximum permissible continuous forward current versus ambient temperature.

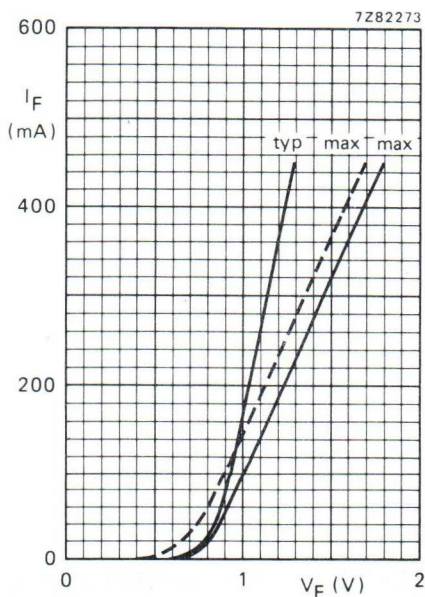


Fig. 8 Forward current versus forward voltage;
— $T_j = 25^{\circ}C$; --- $T_j = 175^{\circ}C$.

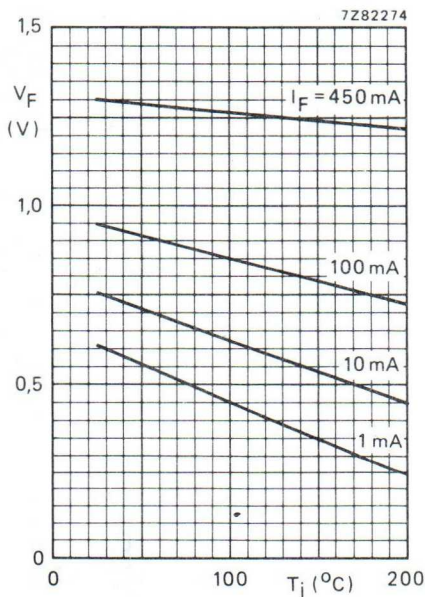


Fig. 9 Forward voltage versus junction temperature; typical values.

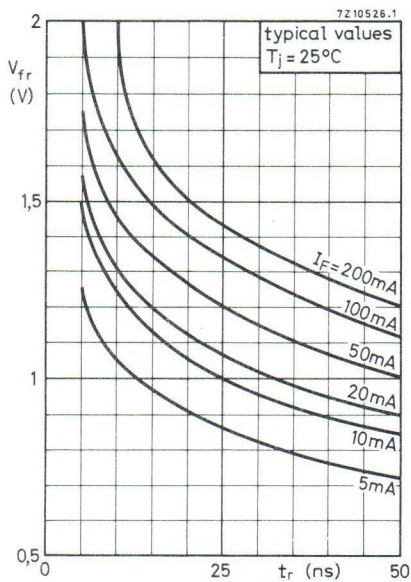


Fig. 10 Forward recovery voltage versus rise time.

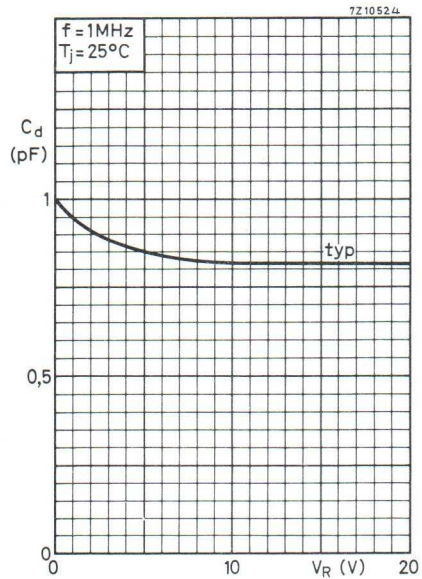


Fig. 11 Diode capacitance versus reverse voltage.

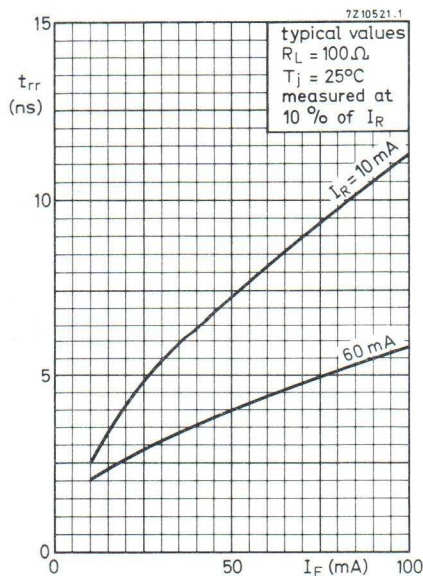


Fig. 12 Reverse recovery time versus forward current.

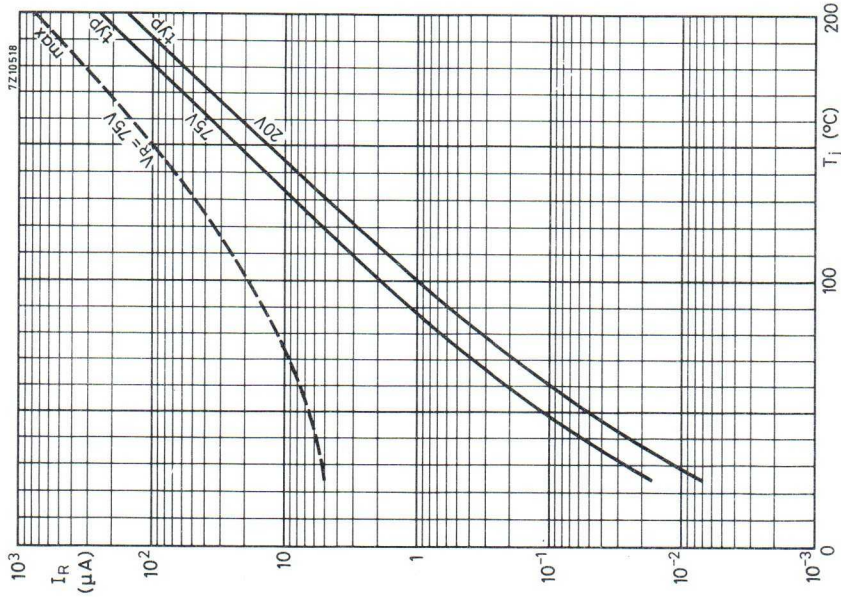


Fig. 14 Reverse current versus junction temperature.

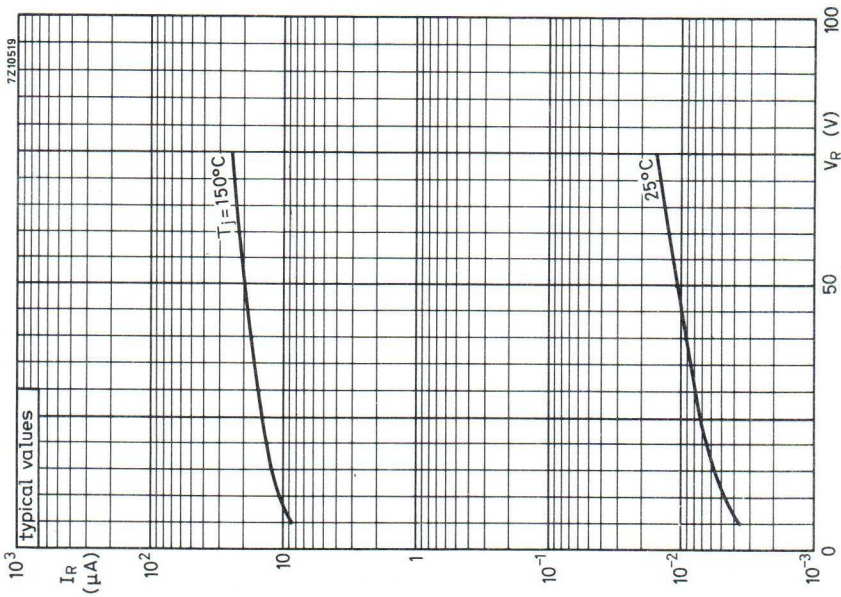


Fig. 13 Reverse current versus reverse voltage.

HIGH-SPEED SILICON DIODE FOR SURFACE MOUNTING

The BAS32L is a planar epitaxial high-speed diode designed for fast logic applications.

This SM diode is a leadless diode in a hermetically sealed SOD-80C glass envelope with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	75 V
Repetitive peak forward current	I_{FRM}	max.	450 mA
Junction temperature	T_j	max.	200 °C
Forward voltage $I_F = 100$ mA	V_F	<	1.0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	4.0 ns

MECHANICAL DATA

Dimensions in mm

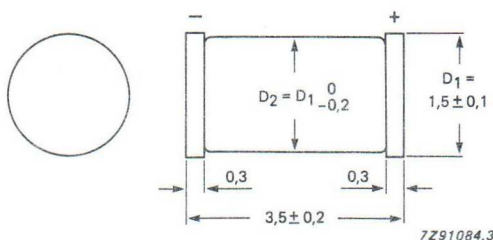


Fig. 1 SOD-80C.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	75 V
Average rectified forward current *	$I_F(AV)$	max.	150 mA
Forward current (DC)	I_F	max.	200 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current			
$t = 1 \mu s$	I_{FSM}	max.	2000 mA
$t = 1 s$	I_{FSM}	max.	500 mA
Storage temperature range	T_{stg}		-65 to + 200 °C
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th j-a}$	=	600 K/W
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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

Forward voltages

$I_F = 5\text{ mA}$	V_F	0.62 to 0.75 V
$I_F = 100\text{ mA}$	V_F	< 1.0 V
$I_F = 100\text{ mA}; T_j = 100\text{ °C}$	V_F	< 0.93 V

Reverse breakdown voltage

$I_R = 100\text{ }\mu A$	$V_{(BRR)}$	> 100 V
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Reverse currents

$V_R = 20\text{ V}$	I_R	< 25 nA
$V_R = 20\text{ V}; T_j = 150\text{ °C}$	I_R	< 50 μA
$V_R = 75\text{ V}$	I_R	< 5.0 μA
$V_R = 75\text{ V}; T_j = 150\text{ °C}$	I_R	< 100 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	< 2.0 pF
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Forward recovery voltage when switched to

$I_F = 50\text{ mA}; t_r = 20\text{ ns}$	V_{fr}	< 2.5 V
--	----------	---------

* For sinusoidal operation see Fig. 6. For pulse operation see Figs 4 and 5.

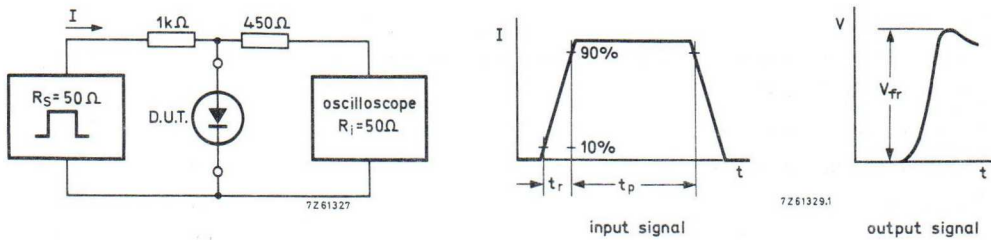


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal : Rise time of the forward pulse $t_r = 20 \text{ ns}$
 Forward current pulse duration $t_p = 120 \text{ ns}$
 Duty factor $\delta = 0.01$

Oscilloscope: Rise time $t_r = 0.35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Reverse recovery time when switched from
 $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \Omega$;
 measured at $I_R = 1 \text{ mA}$

$$t_{rr} < 4 \text{ ns}$$

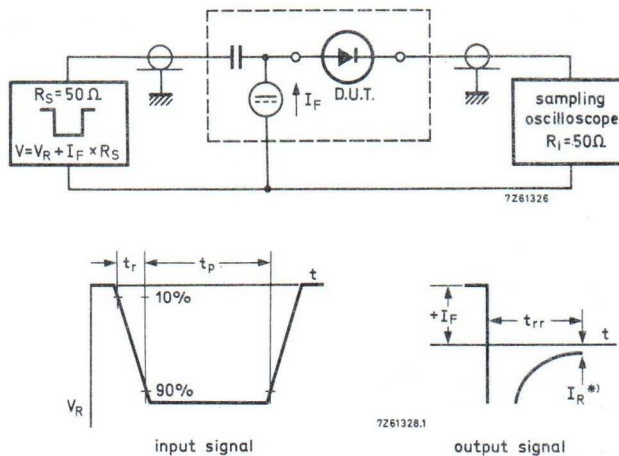


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal : Rise time of the reverse pulse $t_r = 0.6 \text{ ns}$
 Reverse pulse duration $t_p = 100 \text{ ns}$
 Duty factor $\delta = 0.05$

* $I_R = 1 \text{ mA}$

Oscilloscope: Rise time $t_r = 0.35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

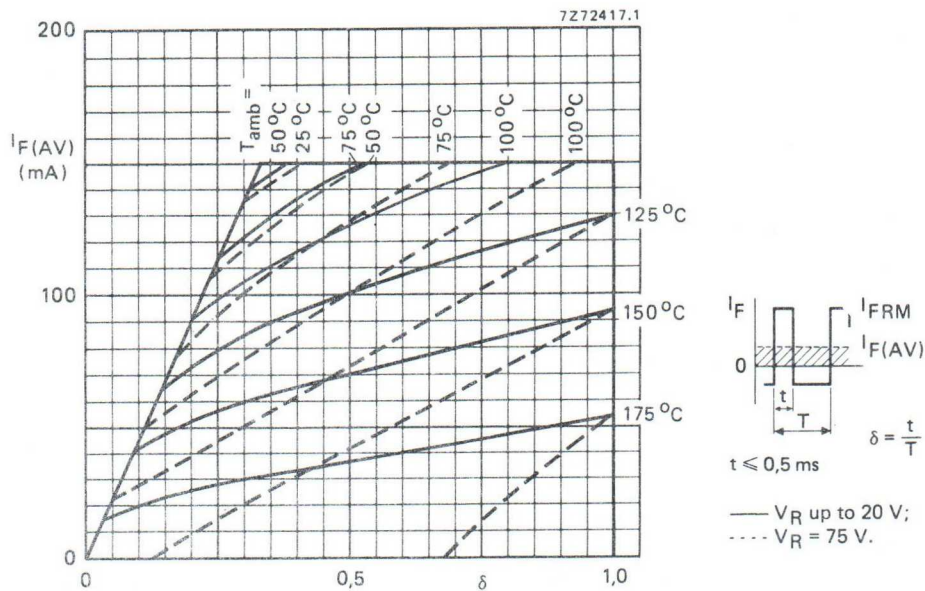


Fig. 4 Maximum permissible average rectified forward current as a function of duty factor (pulse operated).

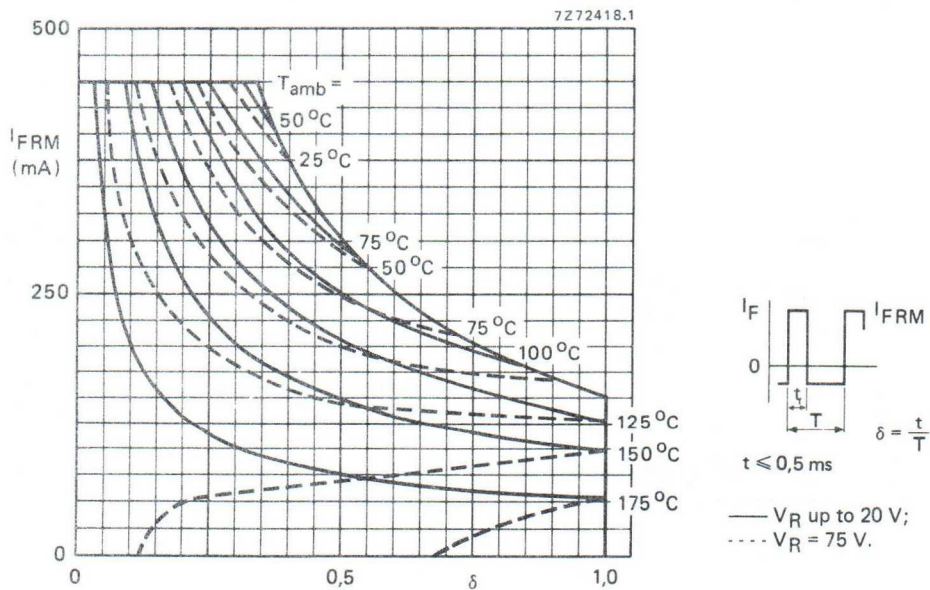


Fig. 5 Maximum permissible repetitive peak forward current as a function of duty factor (pulse operated).

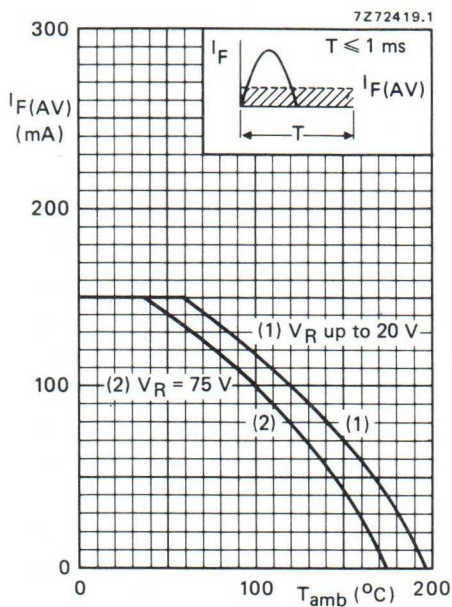


Fig. 6 Maximum permissible average rectified forward current as a function of ambient temperature.

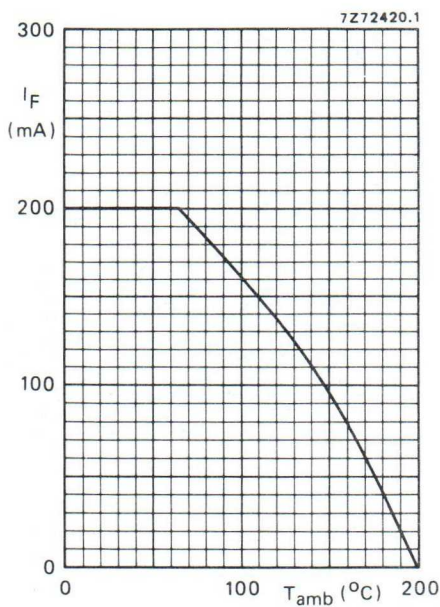


Fig. 7 Maximum permissible continuous forward current as a function of ambient temperature.

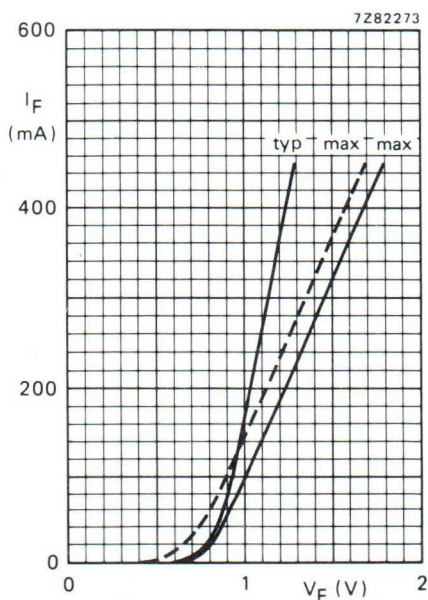


Fig. 8 Forward current as a function of forward voltage; — $T_j = 25$ °C; --- $T_j = 175$ °C.

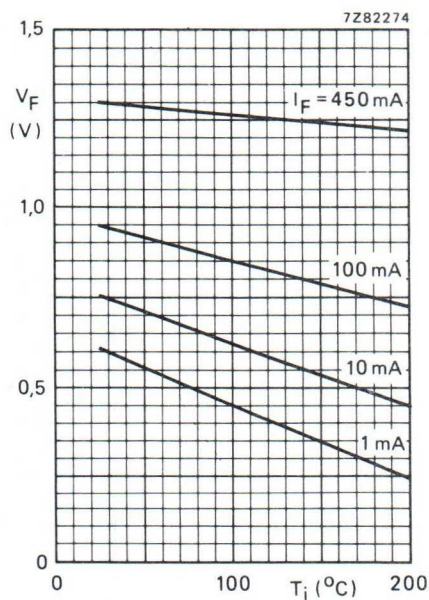


Fig. 9 Forward voltage as a function of junction temperature; typical values.

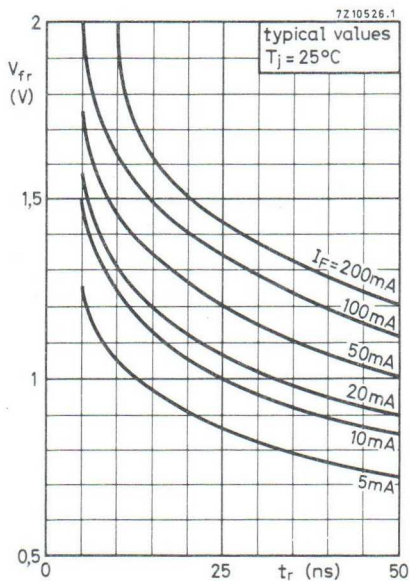


Fig. 10 Forward recovery voltage as a function of rise time.

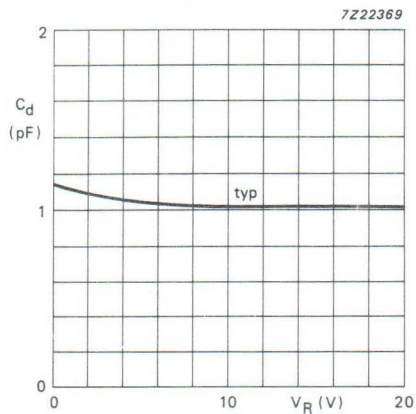


Fig. 11 Diode capacitance as a function of reverse voltage.

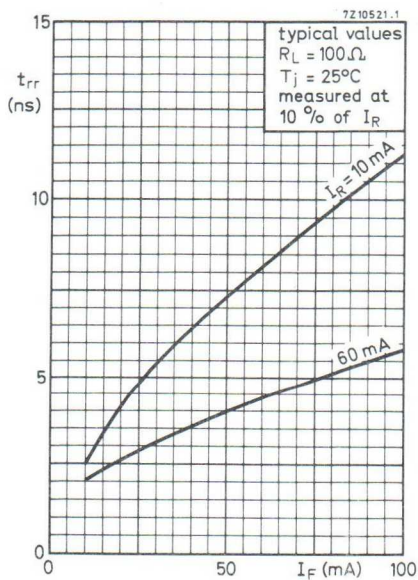


Fig. 12 Reverse recovery time as a function of forward current.

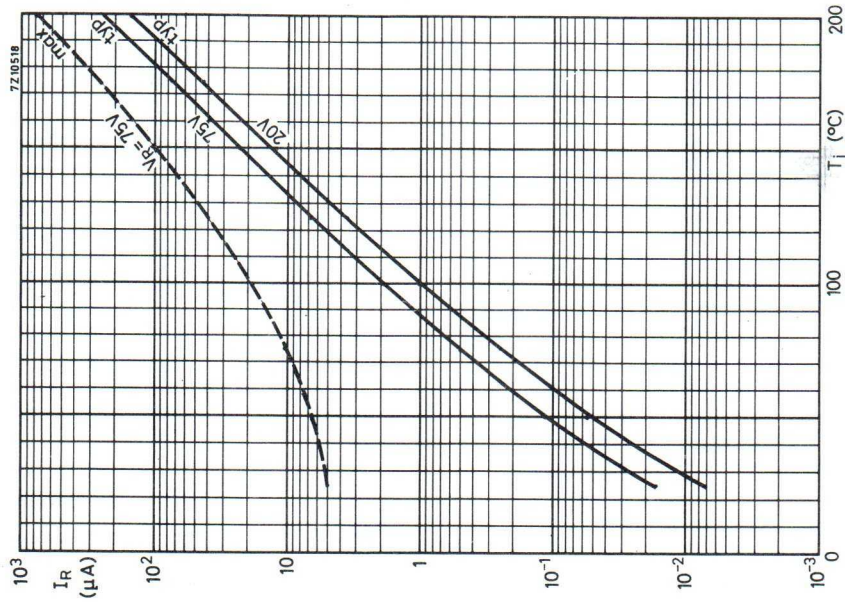


Fig. 14 Reverse current as a function of junction temperature.

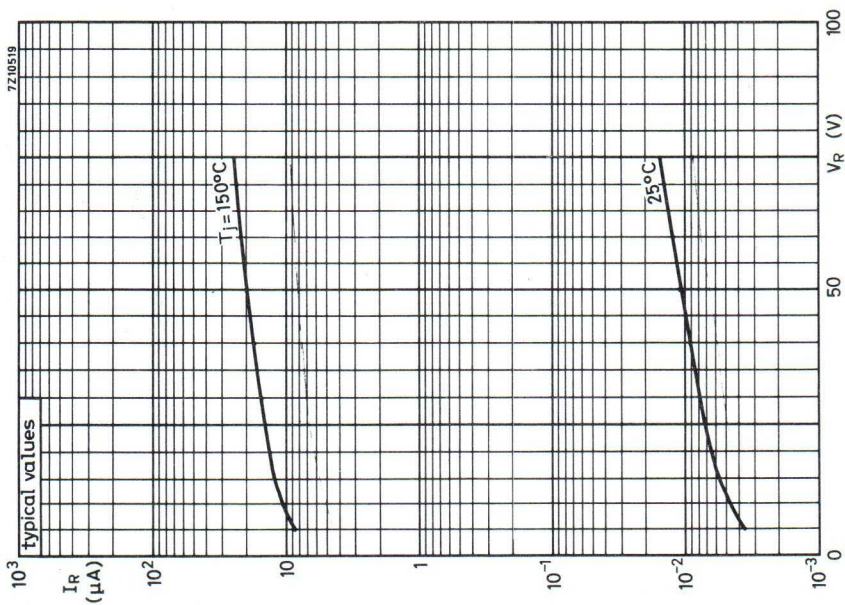


Fig. 13 Reverse current as a function of reverse voltage.

SILICON PLANAR EPITAXIAL ULTRA-HIGH SPEED DIODE

The BAS56 consists of two separate planar epitaxial ultra-high speed, high conductance diodes in one microminiature plastic envelope intended for surface mounting.

The device is primarily intended for core gating in very fast memories using the Surface Mounted Devices (SMD) technology.

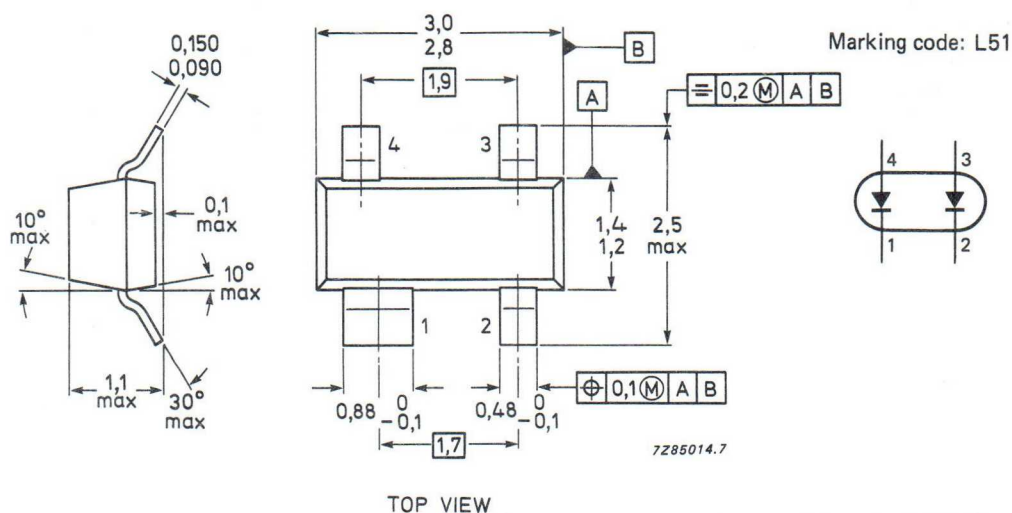
QUICK REFERENCE DATA

			single diode	series connection
Continuous reverse voltage	V_R	max.	60	120 V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120 V
Forward current	I_F	max.	200	150 mA
Repetitive peak forward current	I_{FRM}	max.	600	430 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	300	mW
Reverse recovery time when switched from $I_F = 400\text{ mA}$ to $I_R = 400\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 40\text{ mA}$	t_{rr}	<	6	ns

MECHANICAL DATA

Fig. 1 SOT-143.

Dimensions in mm



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection
Continuous reverse voltage	V_R	max.	60	120 V
Repetitive peak reverse voltage*	V_{RRM}	max.	60	120 V
Forward current	I_F	max.	200	150 mA
Repetitive peak forward current	I_{FRM}	max.	600	430 mA
Non-repetitive peak forward current (per crystal)				
$t = 1 \mu s$	I_{FSM}	max.	2000	mA
$t = 1 s$	I_{FSM}	max.	500	mA
Total power dissipation**				
up to $T_{amb} = 25^\circ C$	P_{tot}	max.	300	mW
Storage temperature range	T_{stg}		-65 to +150	$^\circ C$
Junction temperature	T_j	max.	150	$^\circ C$

THERMAL RESISTANCE

From junction to ambient**

$$R_{th\ j-a} = 430 \text{ K/W}$$

CHARACTERISTICS, per diode $T_j = 25^\circ C$ unless otherwise specified

Forward voltage

$I_F = 10 \text{ mA}$

$V_F < 0,75 \text{ V}$

$I_F = 200 \text{ mA}$

$V_F < 1,00 \text{ V}$

$I_F = 200 \text{ mA}; T_j = 100^\circ C$

$V_F < 0,95 \text{ V}$

$I_F = 500 \text{ mA}$

$V_F < 1,25 \text{ V}$

Reverse current

$V_R = 60 \text{ V}$

$I_R < 100 \text{ nA}$

$V_R = 60 \text{ V}; T_j = 150^\circ C$

$I_R < 100 \mu A$

Diode capacitance

$V_R = 0; f = 1 \text{ MHz}$

$C_d < 2,5 \text{ pF}$

* Measured at zero life time at $I_R = 10 \mu A$; $V_R = 75 \text{ V}$.

** Mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm.

Forward recovery voltage when switched to

$$I_F = 400 \text{ mA}; t_{r1} = 30 \text{ ns}$$

$$I_F = 400 \text{ mA}; t_{r2} = 100 \text{ ns}$$

$$V_{fr} < \begin{matrix} 120 & \text{V} \\ 1,5 & \text{V} \end{matrix}$$

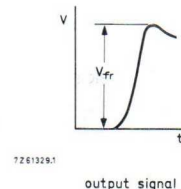
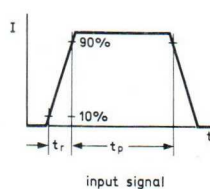
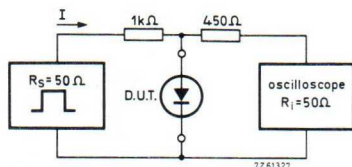


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: 1st rise time of the forward pulse
2nd rise time of the forward pulse
Forward current pulse duration
Duty factor

$$\begin{matrix} t_{r1} & = & 30 & \text{ns} \\ t_{r2} & = & 100 & \text{ns} \\ t_p & = & 300 & \text{ns} \\ \delta & = & 0,01 & \end{matrix}$$

Oscilloscope: Rise time
Input capacitance

$$\begin{matrix} t_r & = & 0,35 & \text{ns} \\ C_i & \leq & 1 & \text{pF} \end{matrix}$$

Circuit capacitance $C \leq 20 \text{ pF}$ ($C = C_i + \text{parasitic capacitance}$)

Reverse recovery time when switched
from $I_F = 400 \text{ mA}$ to $I_R = 400 \text{ mA}$;
 $R_L = 100 \Omega$; measured at $I_R = 40 \text{ mA}$

$$t_{rr} < 6 \text{ ns}$$

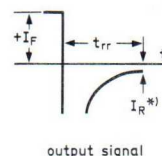
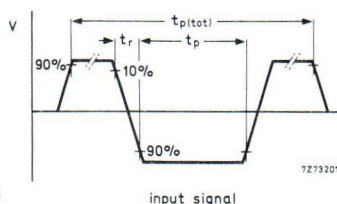
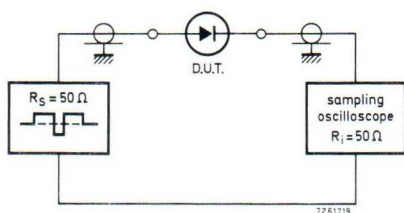


Fig. 3 Test circuits and waveforms; reverse recovery time.

* $I_R = 40 \text{ mA}$

Input signal: Total pulse duration
Duty factor
Rise time of the reverse pulse
Reverse pulse duration

$$\begin{matrix} t_{p(\text{tot})} & = & 0,2 & \mu\text{s} \\ \delta & = & 0,0025 & \\ t_r & = & 0,6 & \text{ns} \\ t_p & = & 30 & \text{ns} \\ t_r & = & 0,35 & \text{ns} \end{matrix}$$

Oscilloscope: Rise time

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Recovery charge when switched from
 $I_F = 10 \text{ mA}$ to $V_R = 5 \text{ V}$; $R_L = 500 \Omega$

$Q_s < 50 \text{ pC}$

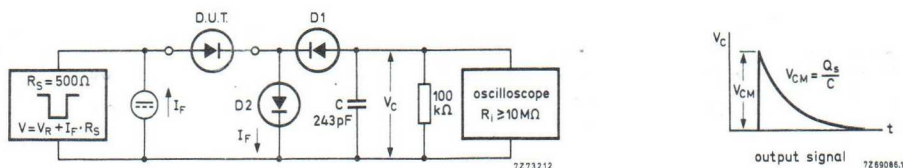


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA

Input signal: Rise time of the reverse pulse

Reverse pulse duration

Duty factor

$<$	200	ps
$=$	2	ns
$=$	400	ns
$=$	0,02	

Circuit capacitance $C \leq 7 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

SCHOTTKY BARRIER DIODE

Schottky Barrier diode with an integrated protection ring against extremely high static discharges.
This diode, in a SOD-80 envelope, is intended for applications where a very low forward voltage is required.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Forward current (d.c.)	I_F	max.	200 mA
Peak forward current	I_{FM}	max.	300 mA
Junction temperature	T_j	max.	125 °C
Forward voltage $I_F = 10 \text{ mA}$	V_F	<	400 mV
Diode capacitance	C_d	<	10 pF

MECHANICAL DATA

Dimensions in mm

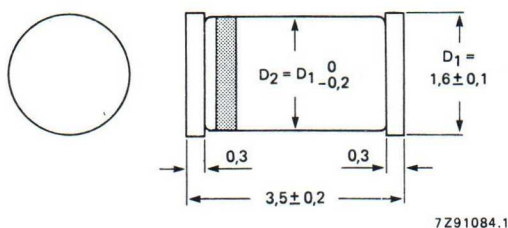


Fig. 1 SOD-80.

The cathode is indicated by a grey band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30 V
Forward current			
d.c.	I_F	max.	200 mA
peak value		max.	300 mA
peak value; $t_p < 1$ s	I_{FM}	max.	600 mA
Average rectified forward current (see Fig. 2)	$I_{F(AV)}$	max.	200 mA
Storage temperature	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	125 °C

CHARACTERISTICS

$T_{amb} = 25$ °C unless otherwise specified

Forward voltage*

$I_F = 0,1$ mA	V_F	<	240 mV
$I_F = 1$ mA		<	320 mV
$I_F = 10$ mA	V_F	<	400 mV
$I_F = 30$ mA		<	500 mV
$I_F = 100$ mA	V_F	typ.	500 mV
		max.	800 mV

Reverse current

$V_R = 25$ V	I_R	<	2,0 µA
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Reverse breakdown voltage

$I_R = 10$ µA	$V_{(BR)R}$	>	30 V
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Diode capacitance

$V_R = 1$ V; $f = 1$ MHz	C_d	<	10 pF
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Reverse recovery time when switched

from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ measured at $I_R = 1$ mA	t_{rr}	<	5,0 ns
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* Temperature coefficient

$I_F = 1$ mA	S_F	typ.	-0,2 %/K
$I_F = 15$ mA		typ.	-0,04 %/K

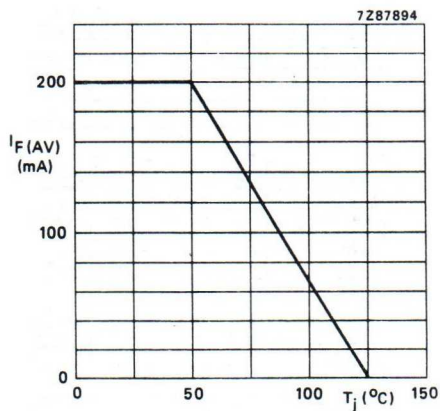


Fig. 2 Power derating curve;
typical values.

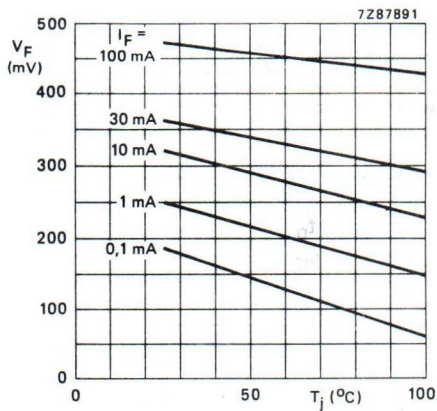


Fig. 3 Forward voltage as a function
of temperature; typical values.

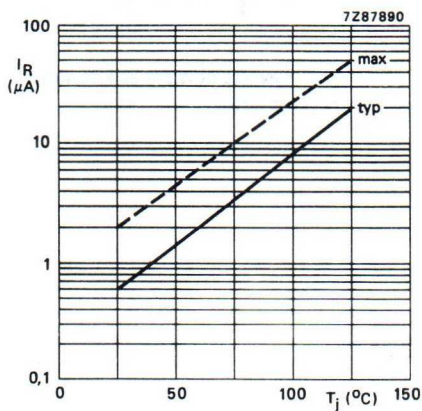


Fig. 4 Reverse current as a function of
temperature; $V_R = 25\text{ V}$;
typical values.

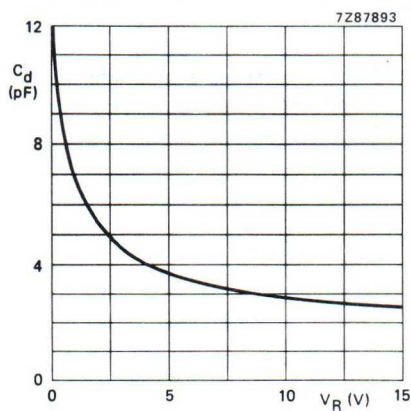


Fig. 5 Diode capacitance as a
function of reverse voltage;
 $f = 1\text{ MHz}$; typical values.

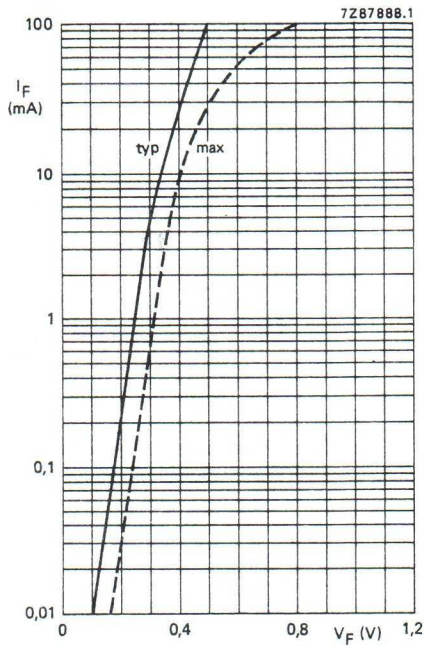


Fig. 6 Forward current as a function of forward voltage.

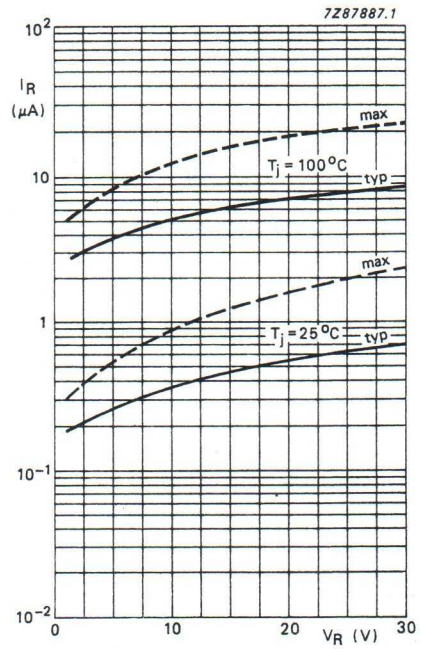


Fig. 7 Reverse current as a function of reverse voltage.

SCHOTTKY BARRIER DIODE

Schottky Barrier diode with an integrated protection ring against extremely high static discharges. This diode, in a SOD80 envelope, is intended for applications where a very low forward voltage is required.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	50	V
Forward current (DC)	I_F	max.	200	mA
Peak forward current	I_{FM}	max.	250	mA
Junction temperature	T_j	max.	125	°C
Forward voltage $I_F = 10 \text{ mA}$	V_F	max.	450	mV
Diode capacitance	C_d	max.	8	pF

MECHANICAL DATA

Dimensions in mm

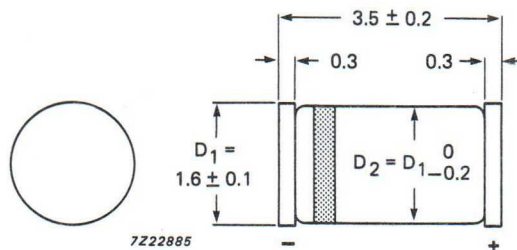


Fig.1 SOD80.

The cathode is indicated by coloured band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	50	V
Forward current				
DC	I_F	max.	200	mA
peak value		max.	250	mA
peak value; $t_p < 1$ s	I_{FM}	max.	500	mA
Average rectified forward current (see Fig. 2)	$I_{F(AV)}$	max.	200	mA
Storage temperature range	T_{stg}	—65 to +150		°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient when mounted on a printed circuit board at a lead length of 4 mm

$R_{th\ j-a}$	=	320	K/W
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CHARACTERISTICS $T_{amb} = 25$ °C unless otherwise specified

Forward voltage (note 1)

 $I_F = 0.1$ mA $I_F = 1$ mA $I_F = 10$ mA $I_F = 30$ mA $I_F = 100$ mA

V_F	max.	300	mV
	max.	380	mV
	max.	450	mV
	max.	600	mV
	typ.	600	mV
	max.	900	mV

Reverse current

 $V_R = 40$ V

I_R	max.	5	μA
-------	------	---	----

Reverse breakdown voltage

 $I_R = 10$ μA

$V_{(BR)R}$	min.	50	V
-------------	------	----	---

Diode capacitance

 $V_R = 1$ V; $f = 1$ MHz

C_d	max.	8	pF
-------	------	---	----

Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω; measured at $I_R = 1$ mA

t_{rr}	max.	4	ns
----------	------	---	----

Note

1. Temperature coefficient

 $I_F = 1$ mA $I_F = 15$ mA

S_F	typ.	—0.2	%/K
	typ.	—0.04	%/K

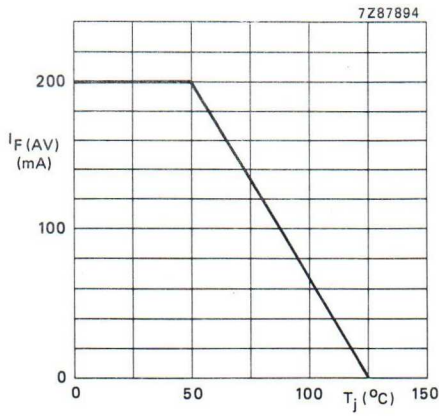


Fig. 2 Derating curve.

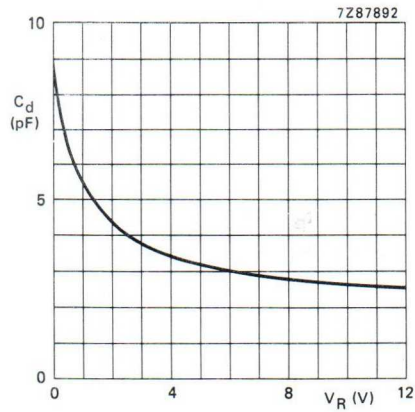
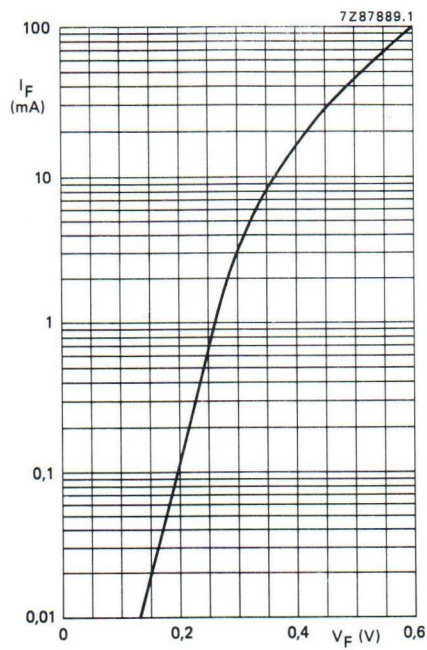
Fig. 3 $f = 1$ MHz; typ. values.

Fig. 4 Typical values.

SCHOTTKY BARRIER DIODE

Silicon epitaxial diode in a microminiature plastic envelope. Intended for u.h.f. mixer and fast switching applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	4 V
Forward current (d.c.)	I_F	max.	30 mA
Junction temperature	T_j	max.	100 °C
Forward voltage at $I_F = 10$ mA	V_F	<	600 mV
Diode capacitance at $V_R = 0$; $f = 1$ MHz	C_d	<	1,0 pF
Noise figure at $f = 900$ MHz	F	<	8,0 dB

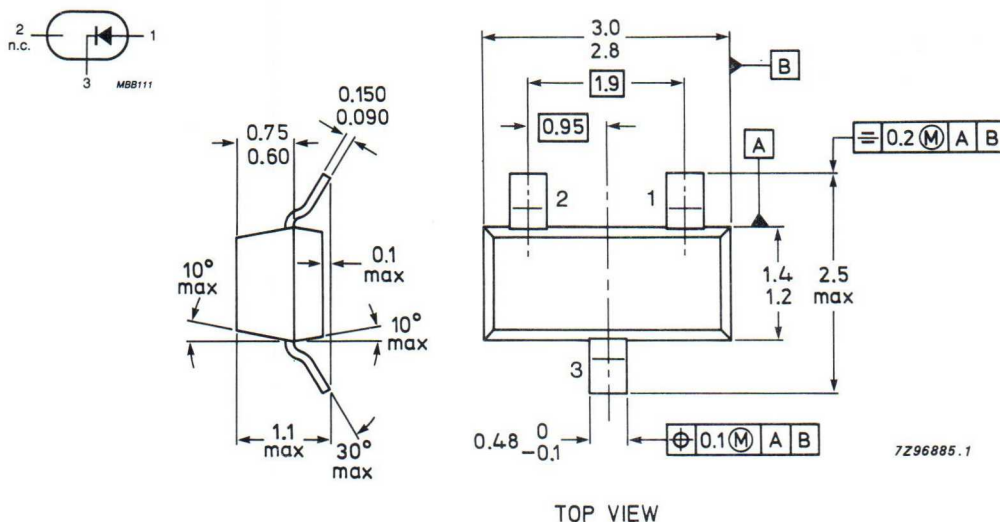
MECHANICAL DATA

Dimensions in mm

Marking code

BAT17 = A3p

Fig.1 SOT-23.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	4 V
Forward current (d.c.) **	I_F	max.	30 mA
Storage temperature	T_{stg}		-65 to +100 °C
Junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

$$V_R = 3\text{ V}$$

$$I_R < 0,25\text{ }\mu\text{A}$$

$$V_R = 3\text{ V}; T_{amb} = 60\text{ °C}$$

$$I_R < 1,25\text{ }\mu\text{A}$$

Reverse breakdown voltage

$$I_R = 10\text{ }\mu\text{A}$$

$$V_{(BR)R} > 4\text{ V}$$

Forward voltage

$$I_F = 0,1\text{ mA}$$

$$V_F < 350\text{ mV}$$

$$I_F = 1,0\text{ mA}$$

$$V_F < 450\text{ mV}$$

$$I_F = 10\text{ mA}$$

$$V_F < 600\text{ mV}$$

Diode capacitance

$$V_R = 0; f = 1\text{ MHz}$$

$$C_d < 1,0\text{ pF}$$

Noise figure at $f = 900\text{ MHz}$ ▲

$$F < 8,0\text{ dB}$$

Series resistance at $f = 1\text{ kHz}$

$$I_F = 5\text{ mA}$$

$$r_D < 15\text{ }\Omega$$

* See *Thermal characteristics*.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ The local oscillator is adjusted for a diode current of 2 mA. I.F. amplifier noise $F_{if} = 1,5\text{ dB}$; $f = 35\text{ MHz}$.

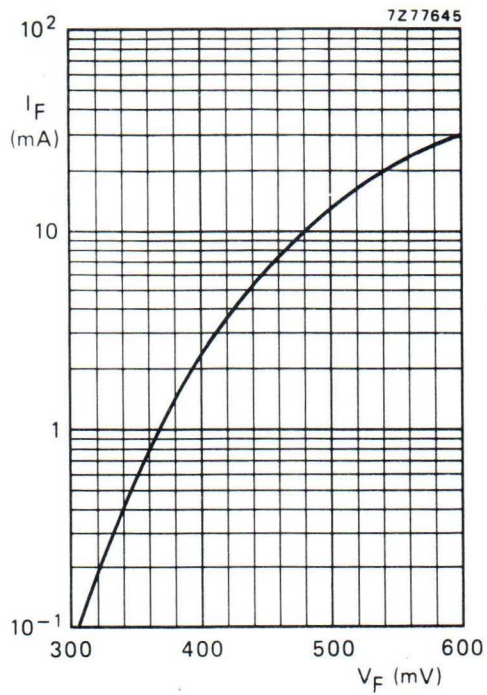


Fig. 2 Typical values.

SILICON PLANAR DIODE

Band switching diode in a microminiature plastic envelope. Intended for thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	35 V
Forward current (d.c.)	I_F	max.	100 mA
Junction temperature	T_j	max.	100 °C
Diode capacitance at $f = 1$ MHz $V_R = 20$ V	C_d	typ. <	0,8 pF 1,0 pF
Series resistance at $f = 200$ MHz $I_F = 5$ mA	r_D	typ. <	0,5 Ω 0,7 Ω

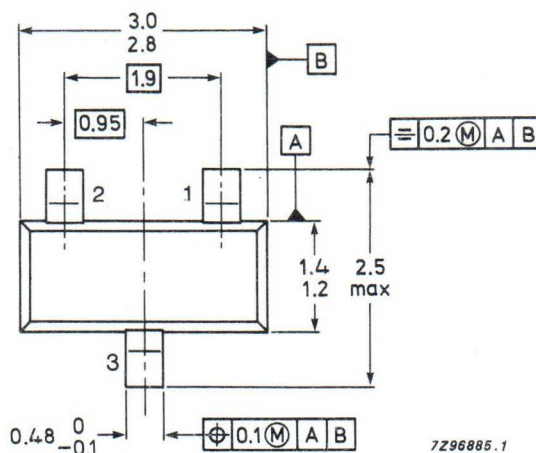
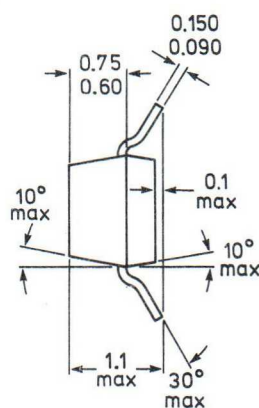
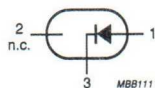
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-23.

BAT18 = A2



TOP VIEW

7296885.1

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35 V
Forward current (d.c.)	I_F	max.	100 mA
Storage temperature	T_{stg}	—55 to + 125 °C	
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage at $I_F = 100\text{ mA}$	V_F	<	1,2 V
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Reverse current

$V_R = 20\text{ V}$	I_R	<	100 nA
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$V_R = 20\text{ V}; T_j = 60\text{ °C}$	I_R	<	1 μA
---	-------	---	-----------------

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 20\text{ V}$	C_d	typ.	0,8 pF
		<	1,0 pF

Series resistance at $f = 200\text{ MHz}$

$I_F = 5\text{ mA}$	r_D	typ.	0,5 Ω
		<	0,7 Ω

* See *Thermal characteristics*.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

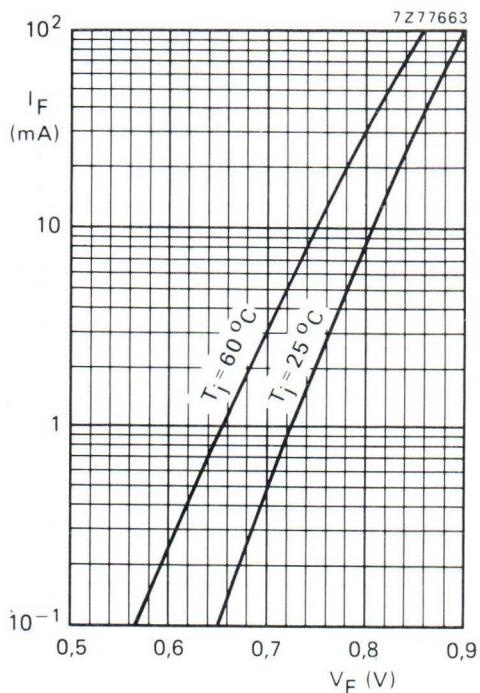


Fig. 2 Typical values.

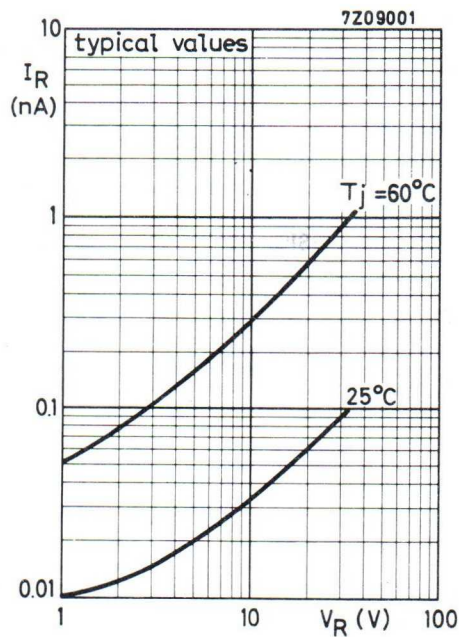


Fig. 3.

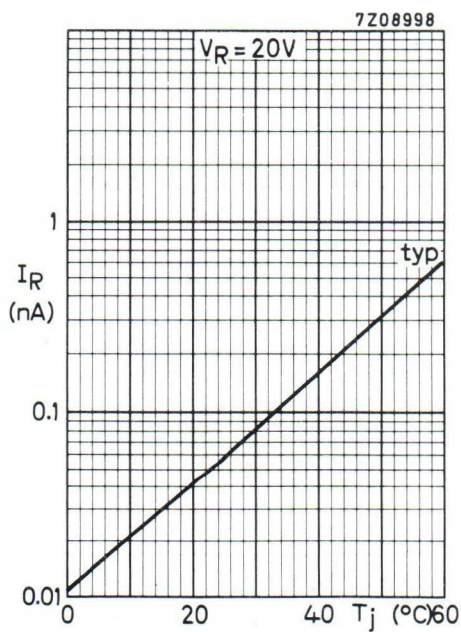


Fig. 4.

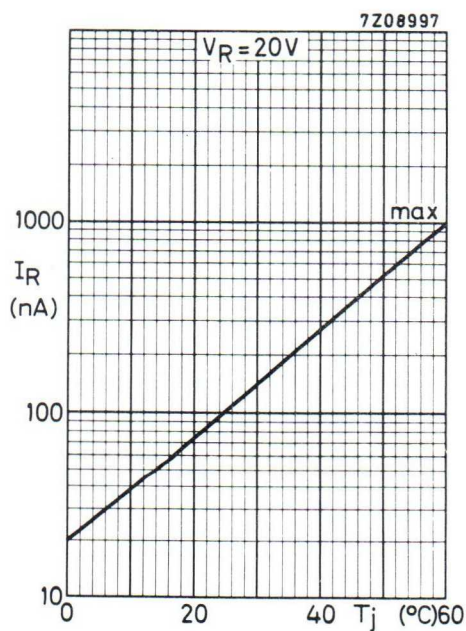


Fig. 5.

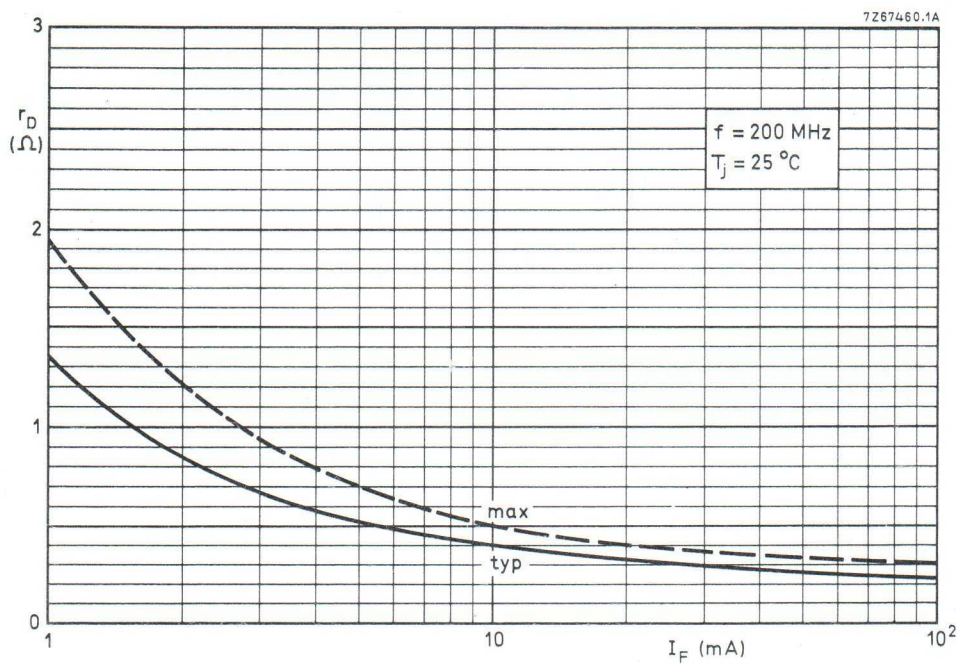


Fig. 6.

SCHOTTKY BARRIER DIODE

Silicon epitaxial Schottky barrier diode with an integrated p-n junction protection ring in a micro-miniature SOT-23 envelope intended for surface mounting.

The diode features especially a low forward voltage.

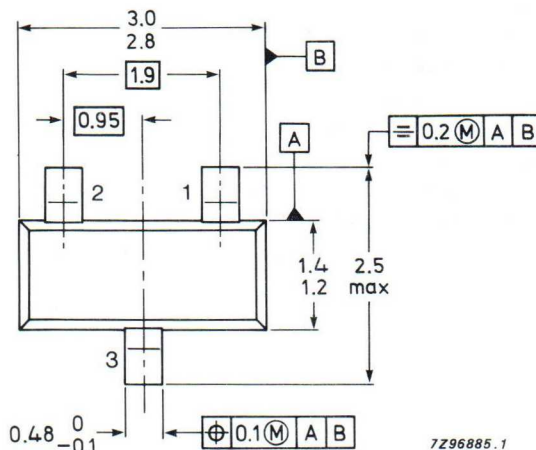
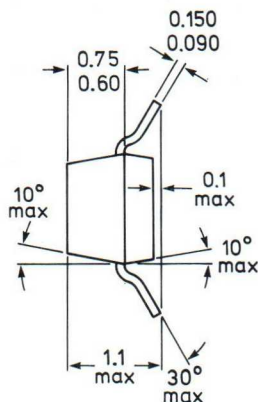
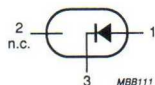
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	200	mA
Forward voltage at $I_F = 10$ mA	V_F	max.	400	mV
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230	mW
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA	t_{rr}	$\leq$	5	ns
Junction temperature	T_j	max.	125	°C

Fig. 1 SOT-23

Dimensions in mm

Marking code: L4p



TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.) see Fig. 2	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	300	mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230	mW
Storage temperature	T_{stg}	—55 to +150		°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm

$R_{th\ j-a}$	=	430	K/W
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CHARACTERISTICS $T_{amb} = 25$ °C unless otherwise specified

Forward voltage

$I_F = 0,1$ mA	V_F	$\leq$	240	mV
$I_F = 1$ mA*	V_F	$\leq$	320	mV
$I_F = 10$ mA	V_F	$\leq$	400	mV
$I_F = 30$ mA*	V_F	$\leq$	500	mV
$I_F = 100$ mA	V_F	=	500	mV
	V_F	<	1000	mV

Reverse current

$V_R = 25$ V	I_R	$\leq$	2	μ A
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Reverse breakdown voltage

$V_{(BR)R}$	>	30	V
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Diode capacitance

$V_R = 1$ V; $f = 1$ MHz	C_d	$\leq$	10	pF
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Reverse recovery time when switched from

$I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA	t_{rr}	$\leq$	5	ns
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* Temperature coefficient of forward voltage:

—0,6 %/K at $I_F = 1$ mA—0,3 %/K at $I_F = 30$ mA

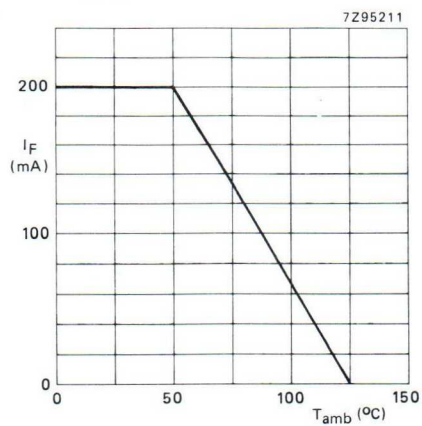


Fig. 2 Derating curve maximum ambient temperature.

DEVELOPMENT DATA

This data sheet contains advance information and specifications are subject to change without notice.

BAT54A; C; S

SUPERSEDES DATA OF JUNE 1989

SCHOTTKY BARRIER DIODE

Silicon epitaxial Schottky Barrier double diodes with an integrated p-n junction protection ring in a microminiature SOT-23 envelope intended for surface mounting.

The diodes feature an especially low forward voltage.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Forward current (DC)	I_F	max.	200 mA
Forward voltage at $I_F = 10$ mA	V_F	max.	400 mV
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$; measured at $I_R = 1$ mA	t_{rr}	<	5 ns
Junction temperature	T_j	max.	125 °C

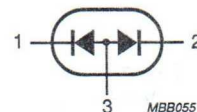
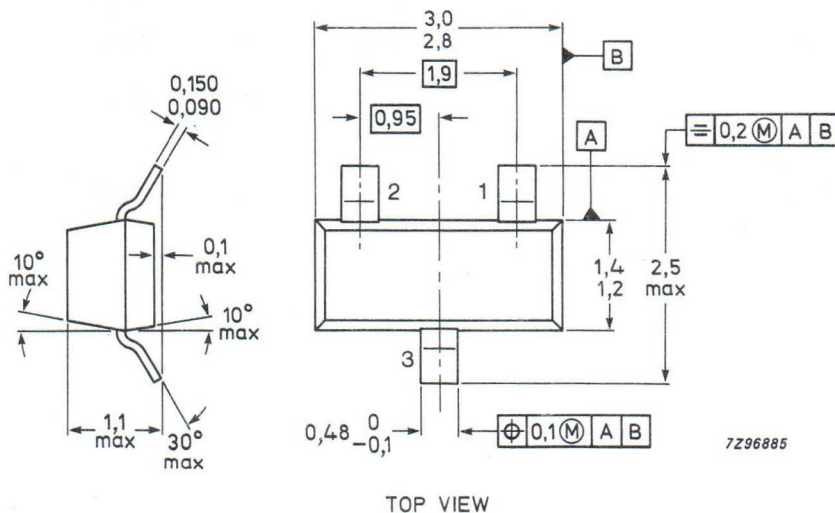
Marking code:

BAT54A = L42

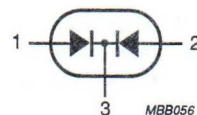
BAT54C = L43

BAT54S = L44

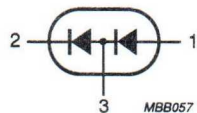
Dimensions in mm



BAT54A



BAT54C



BAT54S

Fig. 1 SOT-23.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak reverse voltage	V_{RRM}	max.	30 V
Forward current (DC)	I_F	max.	200 mA
Repetitive peak forward current	I_{FRM}	max.	300 mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600 mA
Storage temperature	T_{stg}		-50 to + 150 °C
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE

From junction to ambient; mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm

R_{thj-a}	=	430 K/W
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CHARACTERISTICS $T_{amb} = 25$ °C unless otherwise specified

Forward voltage

$I_F = 0,1$ mA	V_F	max.	240 mV
$I_F = 1$ mA	V_F	max.	320 mV
$I_F = 10$ mA	V_F	max.	400 mV
$I_F = 30$ mA	V_F	max.	500 mV
$I_F = 100$ mA	V_F	typ.	500 mV
		max.	1000 mV

Reverse current

$V_R = 25$ V	I_R	<	2 μ A
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Reverse breakdown voltage

$V_{(BR)R}$	>	30 V
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Diode capacitance

$V_R = 1$ V; $f = 1$ MHz	C_d	<	10 pF
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Reverse recovery time when switched

from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$; measured at $I_R = 1$ mA	t_{rr}	<	5 ns
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SCHOTTKY BARRIER DIODE

Two separate silicon epitaxial Schottky barrier diodes with an integrated p-n junction protection ring in one microminiature SOT-143 envelope, intended for surface mounting (SMD technology).

The device features a low forward voltage drop.

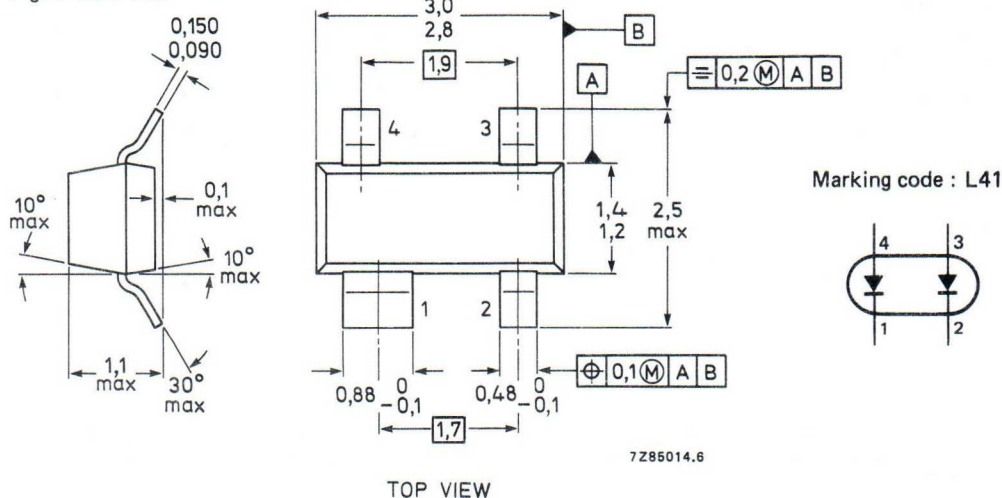
QUICK REFERENCE DATA

			single diode	double-diode operation
Continuous reverse voltage	V_R	max.	30	30 V
Continuous reverse voltage series connection	V_R	max.	—	60 V
Forward current	I_F	max.	200	110 mA
Repetitive peak forward current	I_{FRM}	max.	300	200 mA
Non-repetitive peak forward current	I_{FSM}	max.	600	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	230	mW
Reverse recovery time when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$	t_{rr}	$\leq$	5	ns

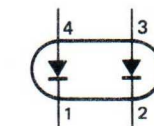
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.



Marking code : L41



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	double-diode operation
Continuous reverse voltage	V_R	max.	30	30 V
Continuous reverse voltage series connection	V_R	max.	—	60 V
Forward current (see Fig. 2)	I_F	max.	200	110* mA
Repetitive peak forward current	I_{FRM}	max.	300	200 mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm

$R_{th\ j-a}$	430	K/W
---------------	-----	-----

CHARACTERISTICS, per diode

 $T_{amb} = 25$ °C unless otherwise specified

Forward voltage

 $I_F = 0,1$ mA $I_F = 1$ mA** $I_F = 10$ mA $I_F = 30$ mA** $I_F = 100$ mA

V_F	$\leq$	240	mV
V_F	$\leq$	320	mV
V_F	$\leq$	400	mV
V_F	$\leq$	500	mV
V_F	$=$	500	mV
V_F	$<$	1000	mV

Reverse current

 $V_R = 25$ V

I_R	$\leq$	2	μ A
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Reverse breakdown voltage

$V_{(BR)R}$	$>$	30	V
-------------	-----	----	---

Diode capacitance

 $V_R = 1$ V; $f = 1$ MHz

C_d	$\leq$	10	pF
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Reverse recovery time when switched from

 $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ;
measured at $I_R = 1$ mA

t_{rr}	$\leq$	5	ns
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* If both diodes are in forward operation at the same moment, total device current max. 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current max. 200 mA.

** Temperature coefficient of forward voltage: $-0,6\%/K$ at $I_F = 1$ mA.

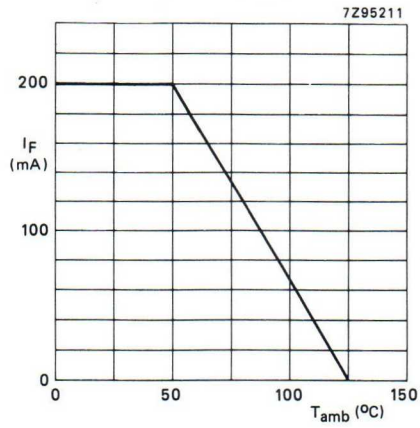


Fig. 2 Derating curve maximum ambient temperature.



SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The BAV23 consists of two separate planar epitaxial high-speed diodes in one microminiature plastic envelope intended for surface mounting.

The device is designed for switching and general applications where high breakdown voltages are required.

QUICK REFERENCE DATA

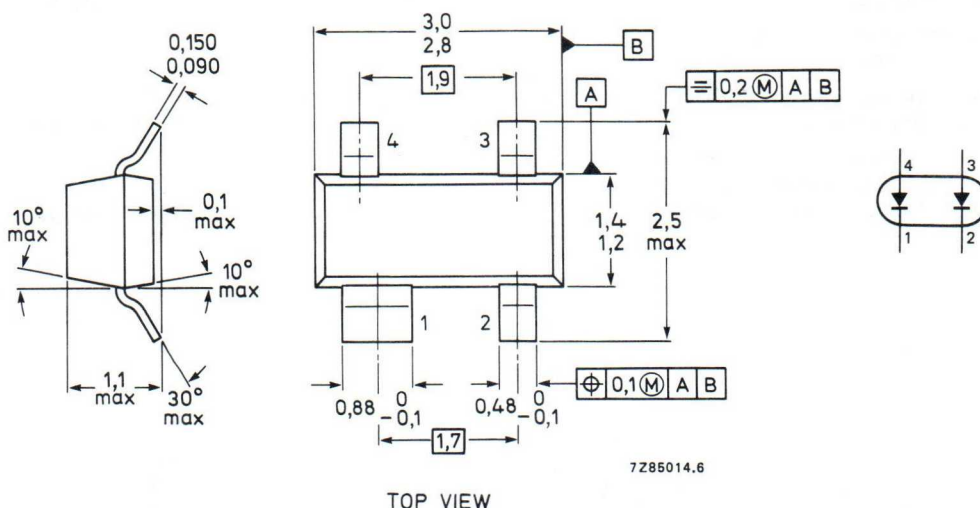
		single diode	series connection
Continuous reverse voltage	V_R max.	200	400 V
Repetitive peak reverse voltage	V_{RRM} max.	250	500 V
Average forward current	$I_{F(AV)}$ max.	200	120 mA
Repetitive peak forward current	I_{FRM} max.	625	450 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot} max.	300	mW
Reverse recovery time when switched from $I_F = 30\text{ mA}$ to $I_R = 30\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 3\text{ mA}$	t_{rr} <	50	ns

MECHANICAL DATA

Fig. 1 SOT-143.

Dimensions in mm

Marking code: L30



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection
Continuous reverse voltage	V_R	max.	200	400 V
Repetitive peak reverse voltage	V_{RRM}	max.	250	500 V
Average forward current	$I_F(AV)$	max.	200	120 mA
Repetitive peak forward current	I_{FRM}	max.	625	450 mA
Non-repetitive peak forward current $t = 1 \mu s$;	I_{FSM}	max.	2,5	1,5 A
Total power dissipation up to $T_{amb} = 25^\circ C$	P_{tot}	max.	300	mW
Storage temperature	T_{stg}		-65 to +150	$^\circ C$
Junction temperature	T_j	max.	150	$^\circ C$

THERMAL RESISTANCEFrom junction to ambient on a ceramic
substrate of 8 mm x 10 mm x 0,6 mm

R_{thj-a}	430	K/W
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CHARACTERISTICS $T_j = 25^\circ C$ unless otherwise specified

Forward voltage

 $I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$

		single diode	series connection
V_F	<	1000	2000 mV
	<	1250	2500 mV

Reverse current

 $V_R = V_{Rmax}$

I_R	<	100	100 nA
-------	---	-----	--------

Reverse breakdown voltage

 $I_R = 100 \mu A$

$V_{(BR)R}$	>	250	500 V
-------------	---	-----	-------

Differential forward resistance

 $I_F = 10 \text{ mA}$

r_f	typ.	5	10 Ω
-------	------	---	-------------

Diode capacitance

 $V_R = 0$; $f = 1 \text{ MHz}$

C_d	<	5	2,5 pF
-------	---	---	--------

Reverse recovery time when switched

from $I_F = 30 \text{ mA}$ to $I_R = 30 \text{ mA}$; $R_L = 100 \Omega$; measured at $I_R = 3 \text{ mA}$

t_{rr}	<	50	50 ns
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SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAV70 consists of two diodes in a microminiature plastic envelope. The cathodes are commoned and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Repetitive peak forward current	I_{FRM}	max.	450 mA
Junction temperature	T_j	max.	150 °C
Forward voltage at $I_F = 50$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	45 pC

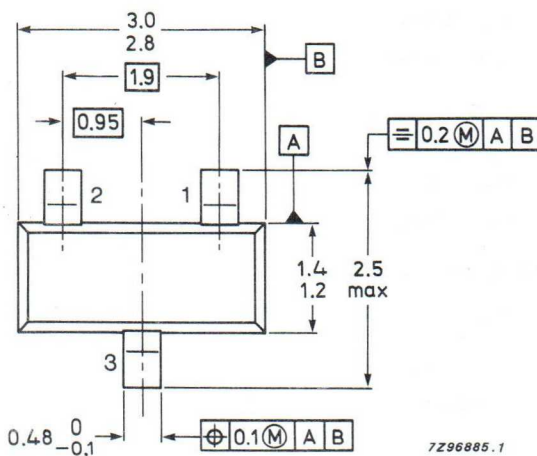
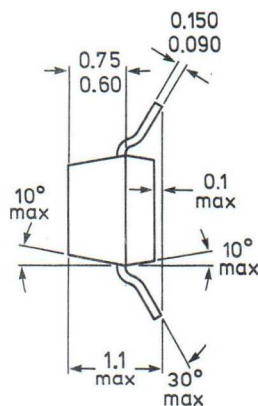
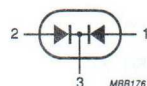
MECHANICAL DATA

Fig. 1 SOT-23.

Dimensions in mm

Marking code

BAV70 = A4_p



TOP VIEW

7296885.1

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current* (averaged over any 20 ms period)	$I_{F(AV)}$	max.	215 mA
Forward current (DC)	I_F	max.	215 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current (per crystal)			
$t = 1 \mu s$	I_{FSM}	max.	2 A
$t = 1 ms$	I_{FSM}	max.	1 A
$t = 1 s$	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient **	R_{thj-a}	=	430 K/W
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CHARACTERISTICS (per diode) $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage

$I_F = 1\text{ mA}$	V_F	<	715 mV
$I_F = 10\text{ mA}$	V_F	<	855 mV
$I_F = 50\text{ mA}$	V_F	<	1000 mV
$I_F = 150\text{ mA}$	V_F	<	1250 mV

Reverse current

$V_R = 25\text{ V}; T_j = 150\text{ °C}$	I_R	<	60 μA
$V_R = 70\text{ V}$	I_R	<	2.5 μA
$V_R = 70\text{ V}; T_j = 150\text{ °C}$	I_R	<	100 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	<	1,5 pF
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Forward recovery voltage when switched to

$I_F = 10\text{ mA}; t_r = 20\text{ ns}$ see Fig. 2	V_{fr}	<	1,75 V
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* Measured under pulse conditions : pulse time $t_p \leq 0,5\text{ ms}$.For sinusoidal operation $I_{F(AV)} = 150\text{ mA}$; averaging time $t_{(AV)} \leq 1\text{ ms}$.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

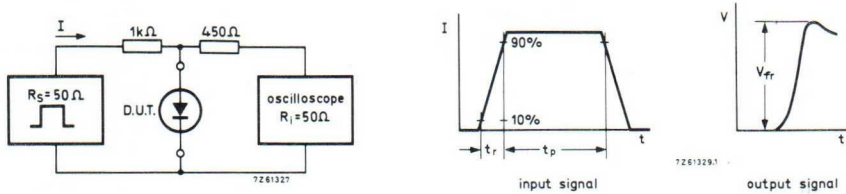


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal : Rise time of the forward pulse $t_r = 20$ ns; Forward current pulse duration $t_p = 120$ ns;

Duty factor $\delta = 0,01$

Oscilloscope : Rise time $t_r = 0,35$ ns

Circuit capacitance $C \leq 1$ pF ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Reverse recovery time when switched from

$I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$;

measured at $I_R = 1$ mA see Fig. 3

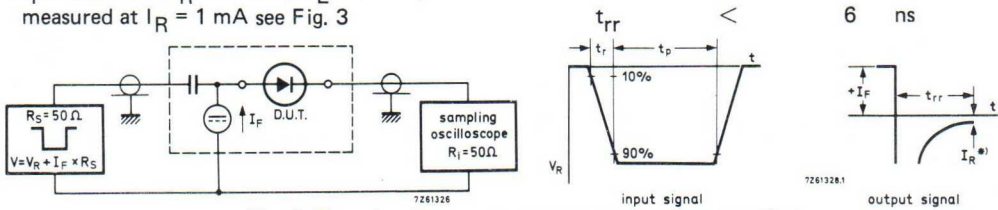


Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal : Rise time of the reverse pulse $t_r = 0,6$ ns; reverse pulse

duration $t_p = 100$ ns; duty factor $\delta = 0,05$

Oscilloscope : Rise time $t_r = 0,35$ ns

Circuit capacitance $C \leq 1$ pF ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Recovery charge when switched from

$I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$ see Fig. 4

$Q_s < 45$ pC

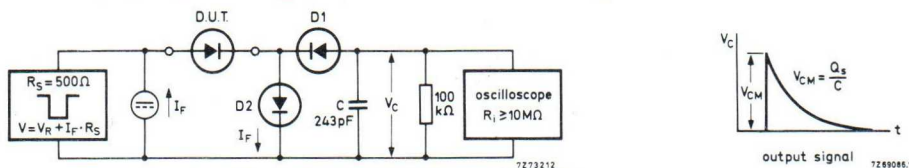


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal : Rise time of the reverse pulse = $t_r = 2$ ns; Reverse pulse duration = $t_p = 400$ ns;

Duty factor = $\delta = 0,02$

Circuit capacitance $C \leq 7$ pF ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

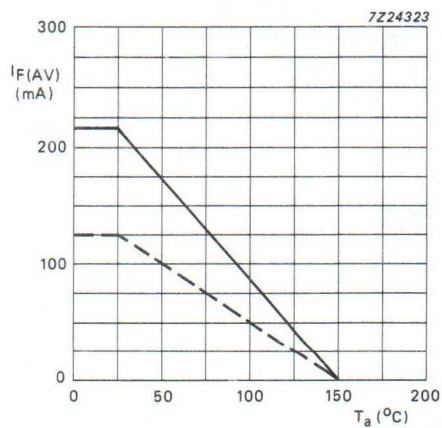
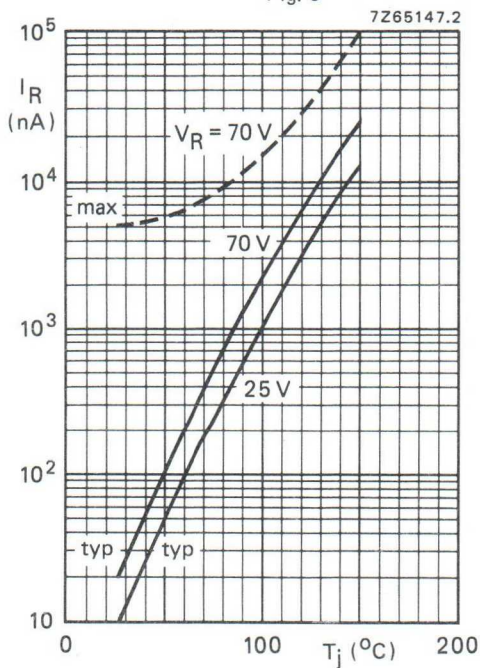
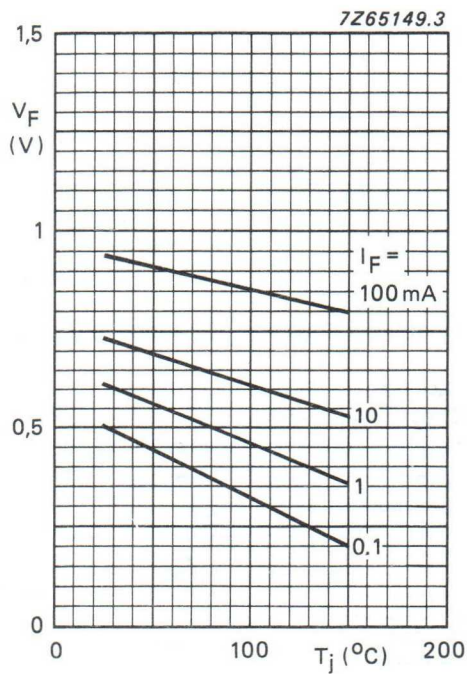
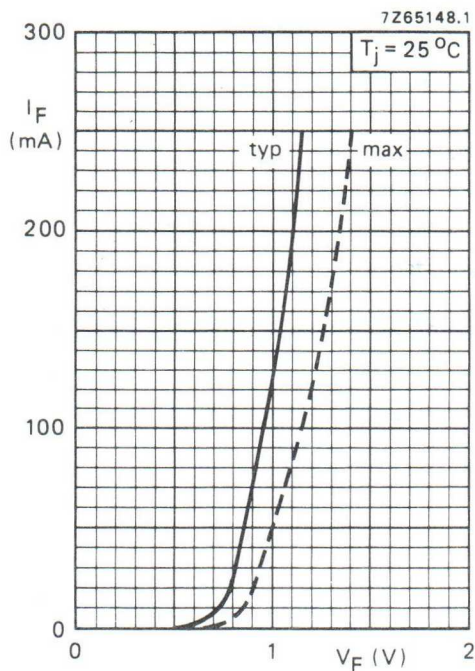


Fig. 8 — single diode
 - - - double diode, equally loaded.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The device consists of two diodes in a microminiature plastic envelope. The cathodes are commoned and the device is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	50 V
Repetitive peak reverse voltage	V_{RRM}	max.	50 V
Repetitive peak forward current	I_{FRM}	max.	250 mA
Junction temperature	T_j	max.	150 °C
Forward voltage $I_F = 100 \text{ mA}$	V_F	$\leq$	1,0 V
Reverse recovery time when switched from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \Omega$; measured at $I_R = 1 \text{ mA}$	t_{rr}	$\leq$	4 ns

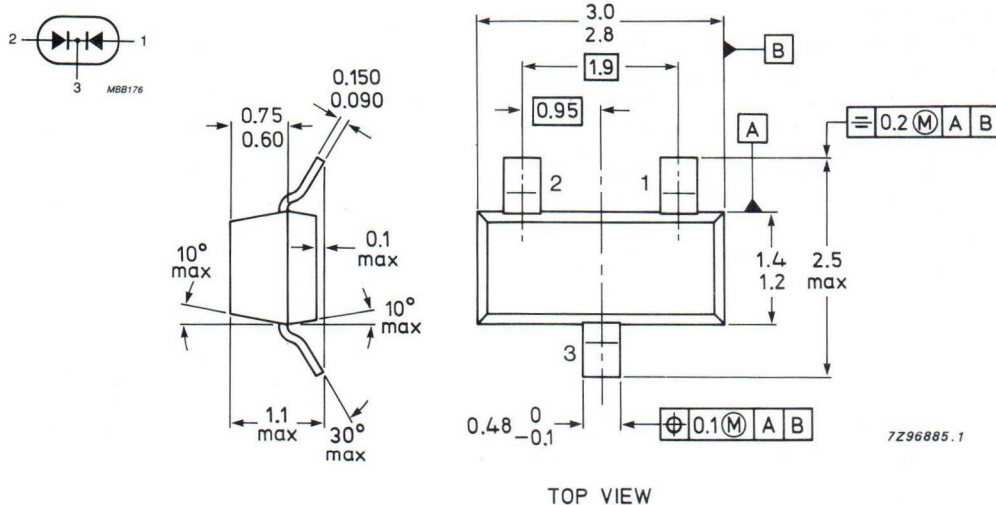
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAV74 = JAp



RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	50 V
Repetitive peak reverse voltage	V_{RRM}	max.	50 V
Average rectified forward current (averaged over any 20 ms period; $t_p = 10$ ms)	$I_F(AV)$	max.	250 mA
Forward current (d.c. or average)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Non-repetitive peak forward current $t = 1 \mu s$	I_{FSM}	max.	4,5 A
Total power dissipation up to $T_{amb} = 25^\circ C$	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		-65 to $+150^\circ C$
Junction temperature	T_j	max.	$150^\circ C$

THERMAL RESISTANCE*

From junction to ambient**	$R_{th j-a}$	max.	430 K/W
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CHARACTERISTICS $T_{amb} = 25^\circ C$ unless otherwise specified

Breakdown voltage at $I_R = 100 \mu A$	$V_{(BR)R}$	$\geq$	50 V
Forward voltage $I_F = 100$ mA	V_F	$\leq$	1,0 V
Reverse currents $V_R = 50$ V $V_R = 50$ V; $T_{amb} = 150^\circ C$	I_R	$\leq$ $\leq$	0,1 μA 100 μA
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA See Fig. 2	t_{rr}	$\leq$	4 ns
Diode capacitance at $V_R = 0$; $f = 1$ MHz	C_d	$\leq$	2 pF

* See Thermal Characteristics.

** When mounted on ceramic substrate of 8 mm x 10 mm x 0,7 mm.

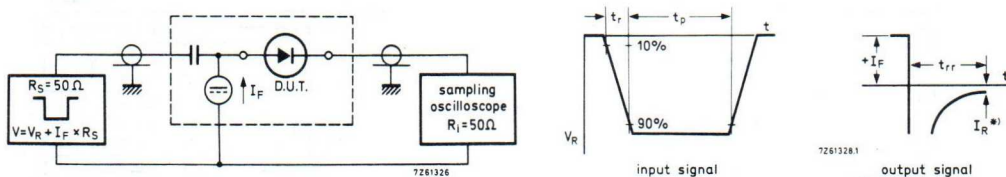


Fig. 2 Reverse recovery time test circuit and waveforms.

* $I_R = 1 \text{ mA}$

Input signal : Rise time of the reverse pulse $t_r = 0,6 \text{ ns}$
 Reverse pulse duration $t_p = 100 \text{ ns}$
 Duty factor $\delta = 0,05$

Oscilloscope : Rise time $t_r = 0,35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

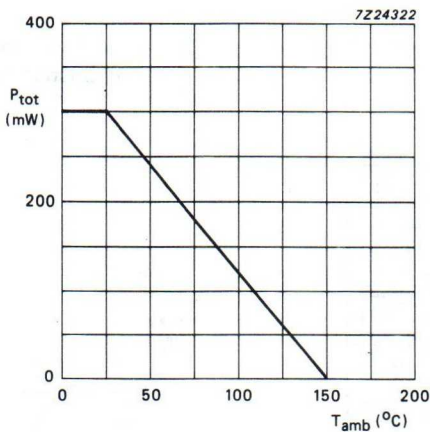


Fig. 3 Power derating curve.

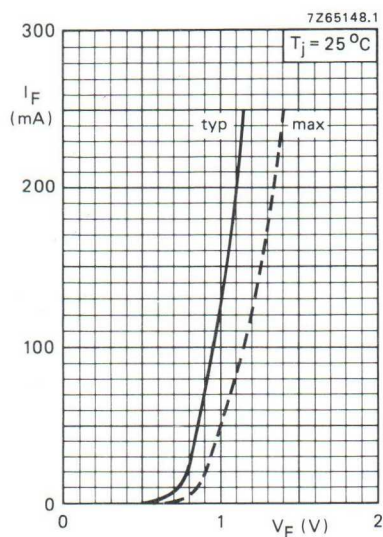


Fig. 4 Forward current as a function of forward voltage.

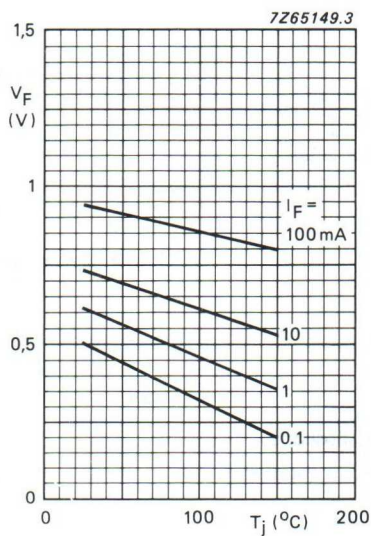


Fig. 5 Forward voltage as a function of junction temperature.

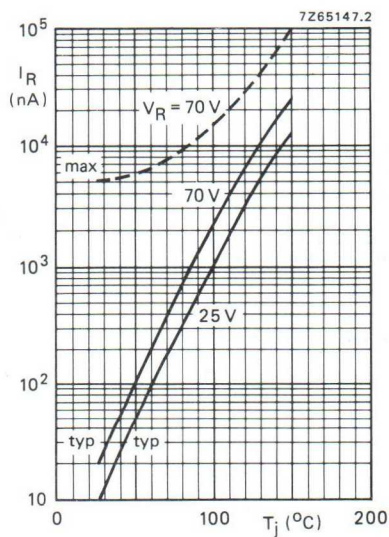


Fig. 6 Reverse current as a function of junction temperature.

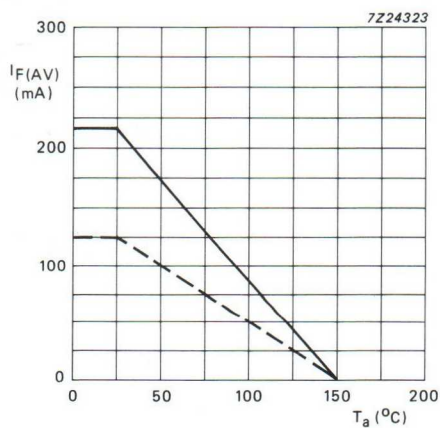


Fig. 7 Average current as a function of ambient temperature: — single diode; - - - double diode, equally loaded.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAV99 consists of two diodes in a microminiature plastic envelope. The diodes are connected in series and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Repetitive peak forward current	I_{FRM}	max.	450 mA
Junction temperature	T_j	max.	150 °C
Forward voltage at $I_F = 50$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	45 pC

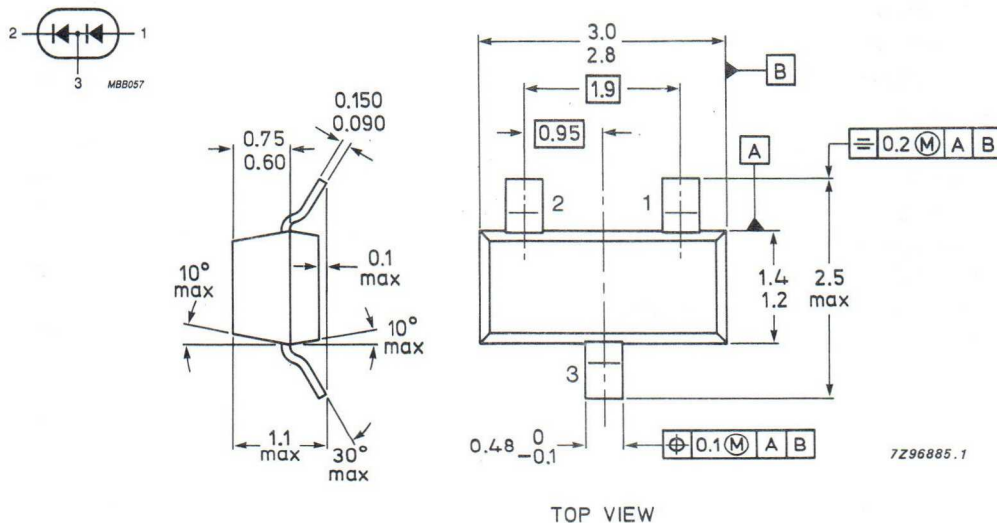
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-23.

BAV99 = A7p



See also *Soldering recommendations*.

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current* (averaged over any 20 ms period)	$I_{F(AV)}$	max.	215 mA
Forward current (d.c.)	I_F	max.	215 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current (per crystal)			
$t = 1 \mu s$	I_{FSM}	max.	2 A
$t = 1 ms$	I_{FSM}	max.	1 A
$t = 1 s$	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE**

From junction to ambient [▲]	$R_{th j-a}$	=	430 K/W
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CHARACTERISTICS (per diode) $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage

$I_F = 1\text{ mA}$	V_F	<	715 mV
$I_F = 10\text{ mA}$	V_F	<	855 mV
$I_F = 50\text{ mA}$	V_F	<	1000 mV
$I_F = 150\text{ mA}$	V_F	<	1250 mV

Reverse current

$V_R = 25\text{ V}; T_j = 150\text{ °C}$	I_R	<	30 μA
$V_R = 70\text{ V}$	I_R	<	2,5 μA
$V_R = 70\text{ V}; T_j = 150\text{ °C}$	I_R	<	50 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	<	1,5 pF
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Forward recovery voltage when switched to

$I_F = 10\text{ mA}; t_r = 20\text{ ns}$	V_{fr}	<	1,75 V
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* Measured under pulse conditions: pulse time $t_p \leq 0,5\text{ ms}$.For sinusoidal operation $I_{F(AV)} = 150\text{ mA}$; averaging time $t_{(av)} \leq 1\text{ ms}$.** See *Thermal characteristics*.[▲] Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

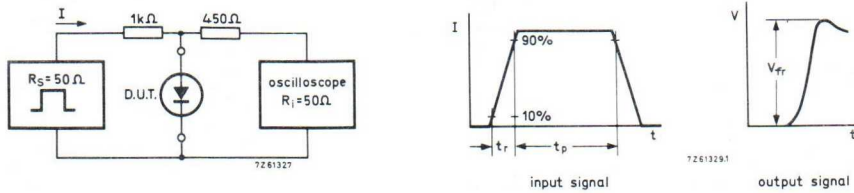


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse $t_r = 20$ ns;
Forward current pulse duration = $t_p = 120$ ns. Duty factor = $\delta = 0,01$.

Oscilloscope: Rise time $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

Reverse recovery time when switched from
 $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$;
measured at $I_R = 1$ mA

$$t_{rr} < 6 \text{ ns}$$

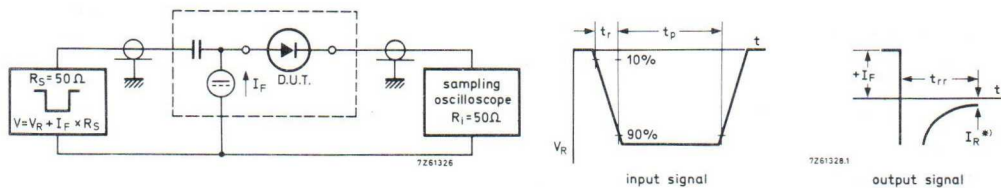


Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal: Rise time of the reverse pulse $t_r = 0,6$ ns
Reverse pulse duration $t_p = 100$ ns. Duty factor $\delta = 0,05$.

*) $I_R = 1$ mA

Oscilloscope: Rise time $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF (C = oscilloscope input capacitance + parasitic capacitance).

Recovery charge when switched from
 $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$

$$Q_s < 45 \text{ pC}$$

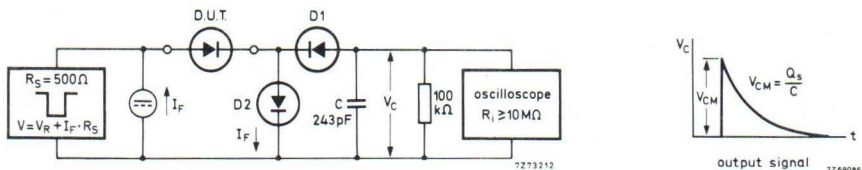


Fig. 4 Test and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps; D1 = BAW62.

Input signal: Rise time of the reverse pulse $t_r = 2$ ns
Reverse pulse duration $t_p = 400$ ns. Duty factor $\delta = 0,02$.

Circuit capacitance $C \leq 7$ pF (C = oscilloscope input capacitance + parasitic capacitance).

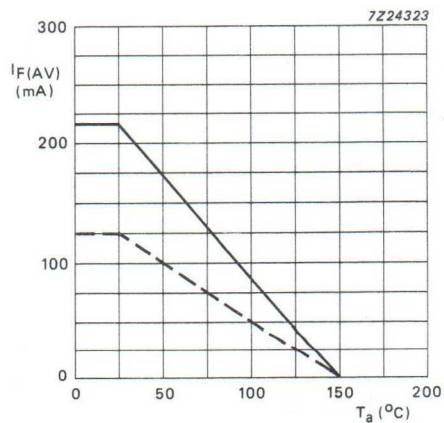
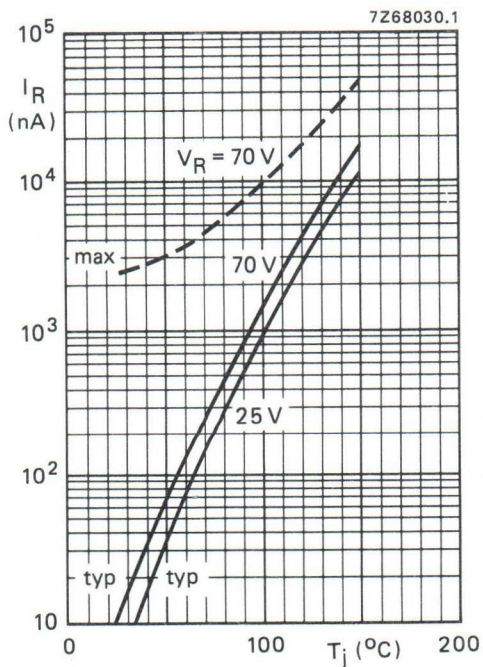
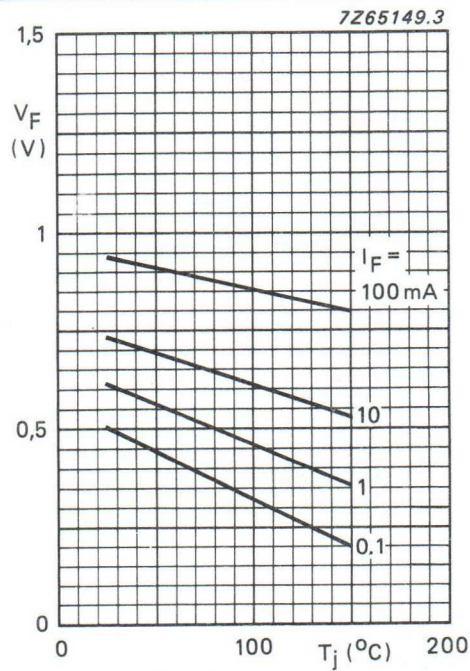
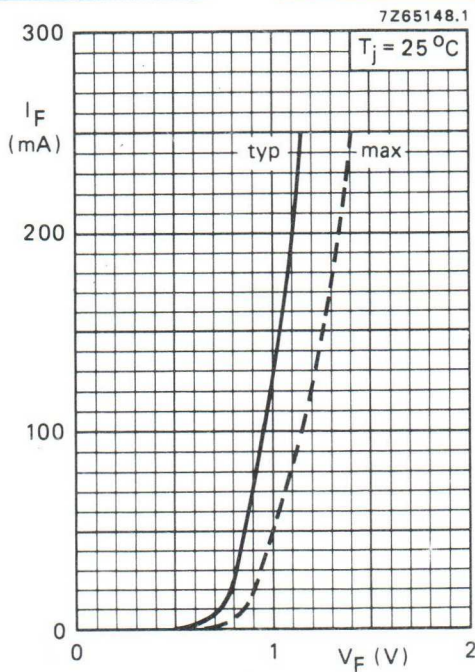


Fig. 8 — single diode
 ---- double diode; equally loaded.

GENERAL PURPOSE DIODES FOR SURFACE MOUNTING

Silicon planar epitaxial diodes; intended for switching and general purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

The SM DIODE is a leadless diode in an hermetically sealed glass envelope with tin plated metal discs at each end. It is suitable for Automatic Placement and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

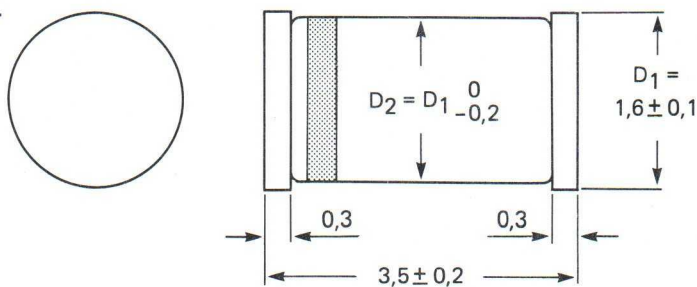
QUICK REFERENCE DATA

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Forward current (d.c.)	I_F	max.			250		mA
Junction temperature	T_j	max.			175		°C
Thermal resistance from junction to ambient	$R_{th j-a}$	=			375		K/W
Forward voltage at $I_F = 100$ mA	V_F	<			1,0		V
Reverse current at $V_R = V_{Rmax}$	I_R	<			100		nA
Diode capacitance at $V_R = 0$; $f = 1$ MHz	C_d	typ. <			1,5 5,0		pF pF
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$; measured at $I_R = 3$ mA	t_{rr}	<			50		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



7 Z91084.1

The BAV100 cathode is indicated by a green and a black band.
 The BAV101 cathode is indicated by a green and a brown band.
 The BAV102 cathode is indicated by a green and a red band.
 The BAV103 cathode is indicated by a green and an orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	200	250	V
Average rectified forward current	$I_F(AV)$	max.	250				mA ¹⁾
Forward current (d.c.)	I_F	max.	250				mA
Repetitive peak forward current	I_{FRM}	max.	625				mA
Non-repetitive peak forward current							
$t < 1$ s; $T_j = 25$ °C	I_{FSM}	max.	1				A
$t = 1$ μs; $T_j = 25$ °C	I_{FSM}	max.	5				A
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	400				mW
Storage temperature	T_{stg}		-65 to +175				°C
Junction temperature	T_j	max.	175				°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	375	K/W
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CHARACTERISTICS $T_j = 25$ °C unless otherwise specified

Forward voltage							
$I_F = 100$ mA	V_F	<	1,0				V
$I_F = 200$ mA	V_F	<	1,25				V
Reverse breakdown voltage			BAV100	BAV101	BAV102	BAV103	
$I_R = 100$ μA	$V(BR)R$	>	60	120	200	250	V ²⁾
Reverse current							
$V_R = V_{Rmax}$	I_R	<	100				nA
$V_R = V_{Rmax}$; $T_j = 150$ °C	I_R	<	100				μA
Differential resistance							
$I_F = 10$ mA	r_{diff}	typ.	5				Ω
Diode capacitance							
$V_R = 0$; $f = 1$ MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100$ Ω; measured at $I_R = 3$ mA	t_{rr}	<	50				ns

¹⁾ For sinusoidal operation see Figs 7 to 10. For pulse operation see Figs 3 to 6.²⁾ At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited at 275 V.

Test circuit and waveforms:

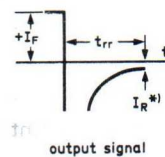
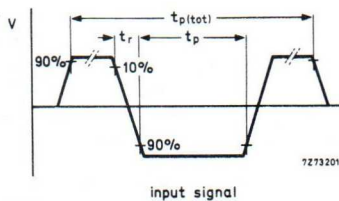
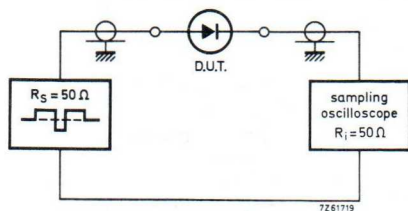


Fig. 2.

*) $I_R = 3 \text{ mA}$

Input signal:	Total pulse duration	$t_p(\text{tot})$	=	$2 \text{ } \mu\text{s}$
	Duty factor	δ	=	$0,0025$
	Rise time of the reverse pulse	t_r	=	$0,6 \text{ ns}$
	Reverse pulse duration	t_p	=	100 ns
Oscilloscope:	Rise time	t_r	=	$0,35 \text{ ns}$
Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)				

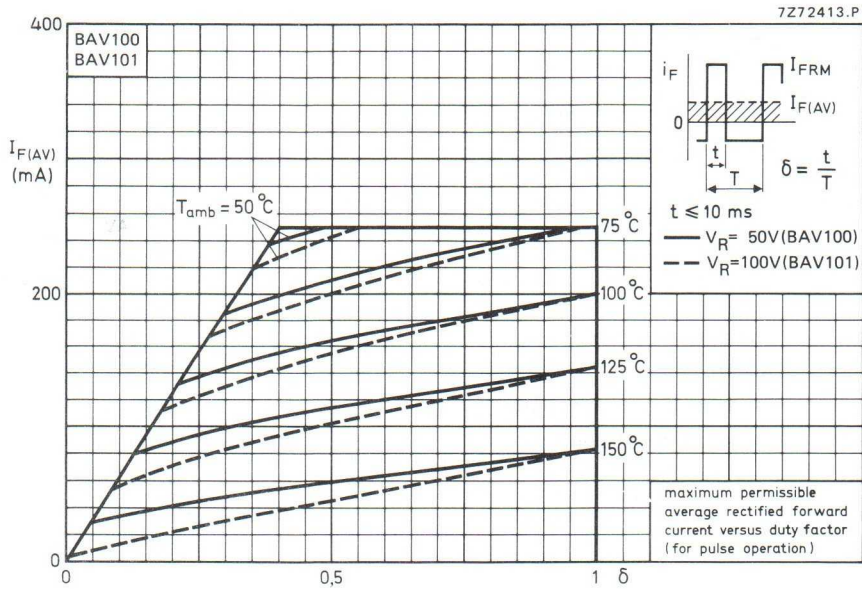


Fig. 3.

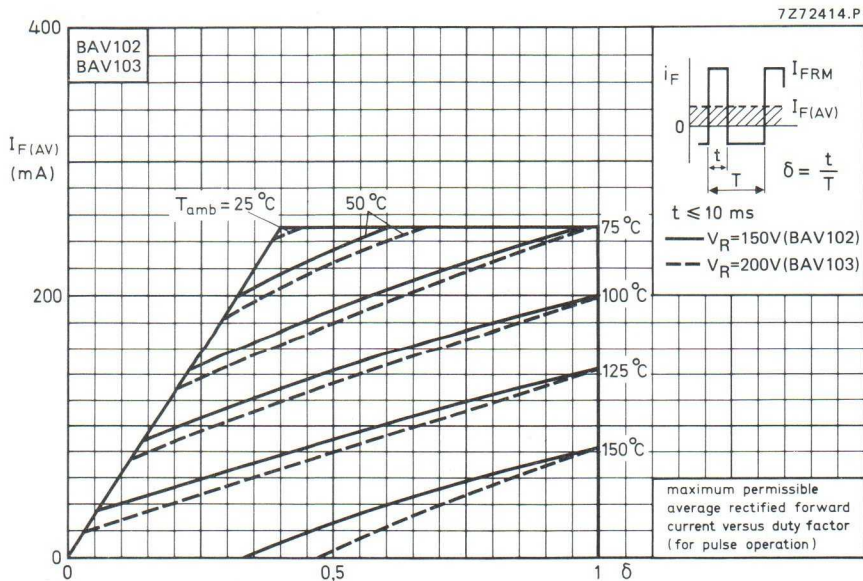


Fig. 4.

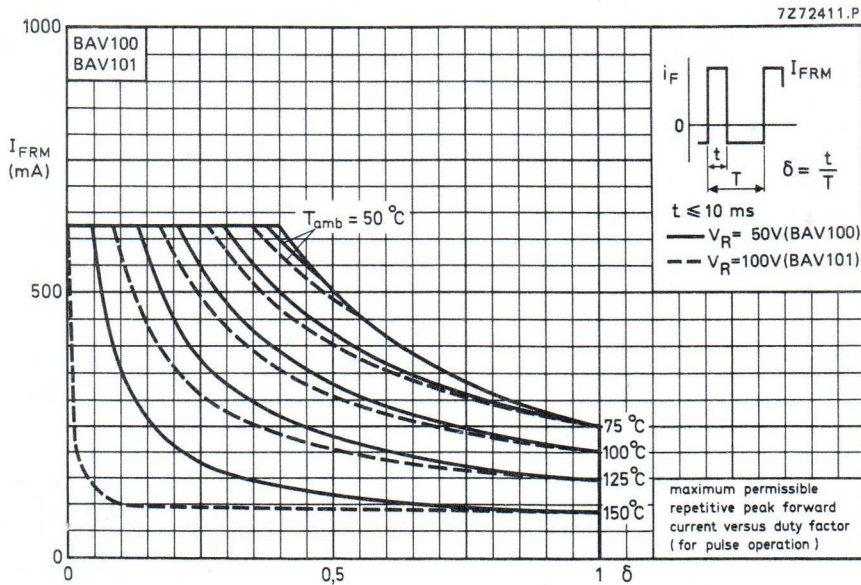


Fig. 5.

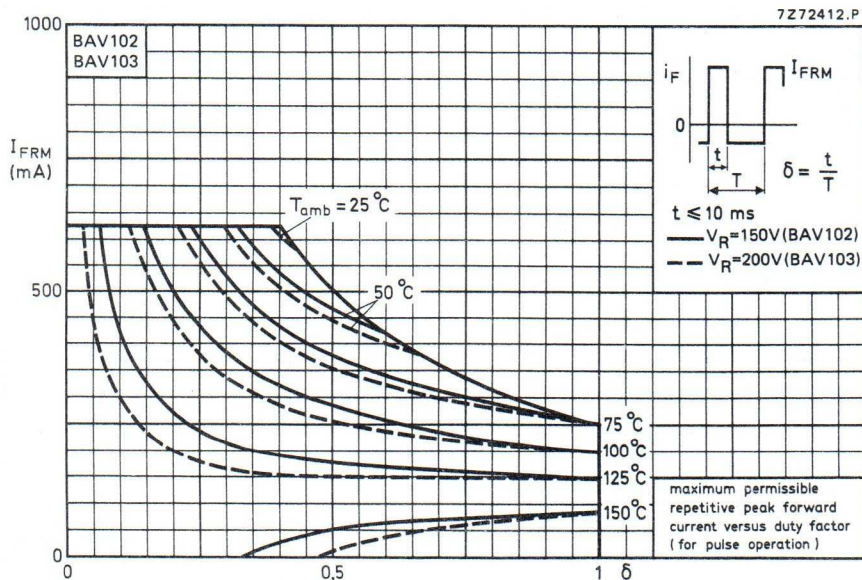


Fig. 6.

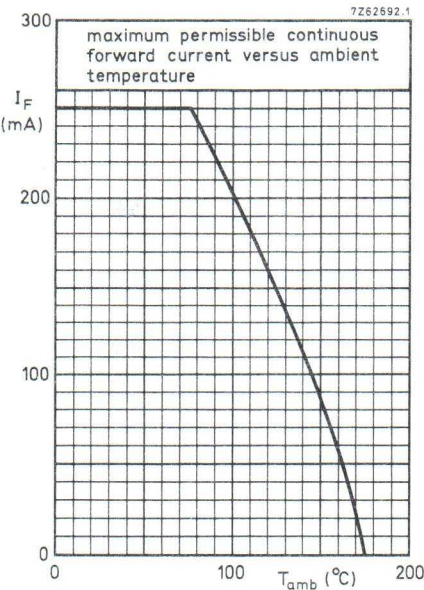


Fig. 7.

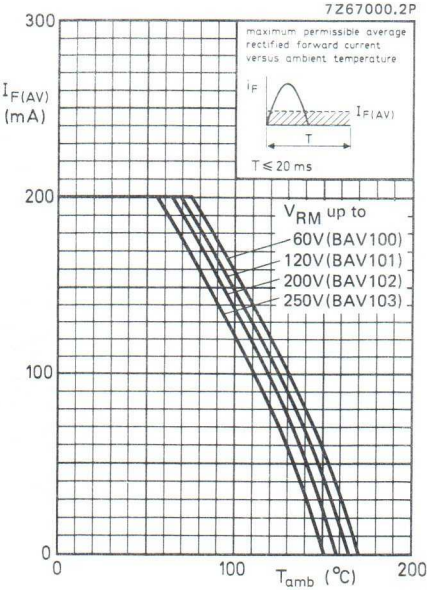


Fig. 8.

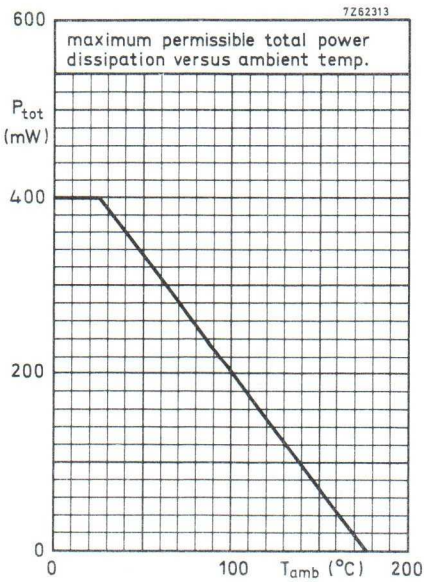


Fig. 9.

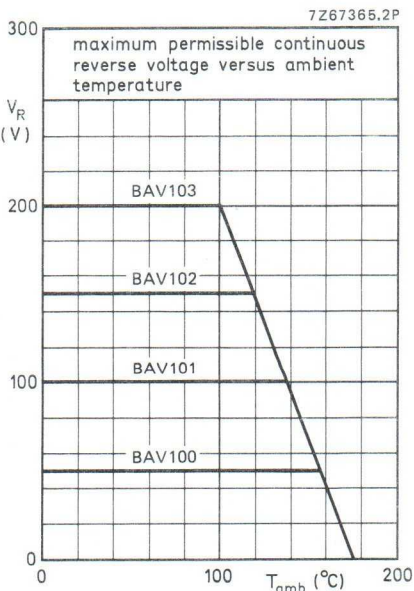


Fig. 10.

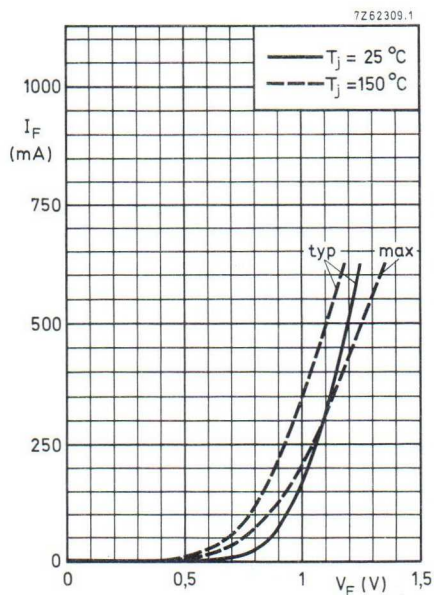


Fig. 11.

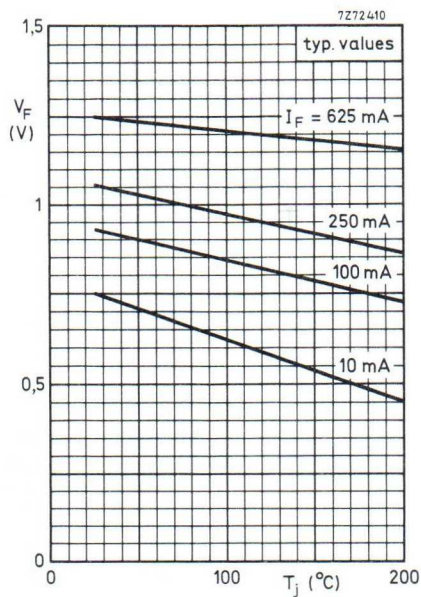


Fig. 12.

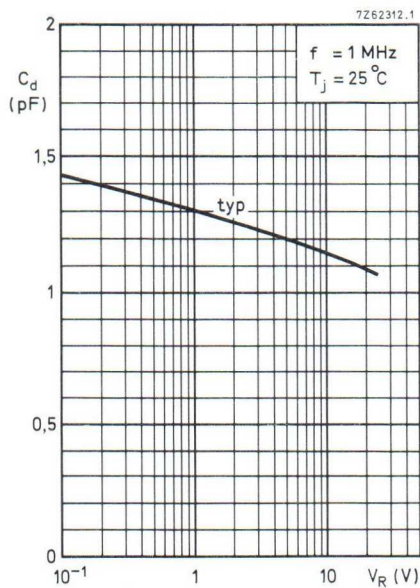


Fig. 13.

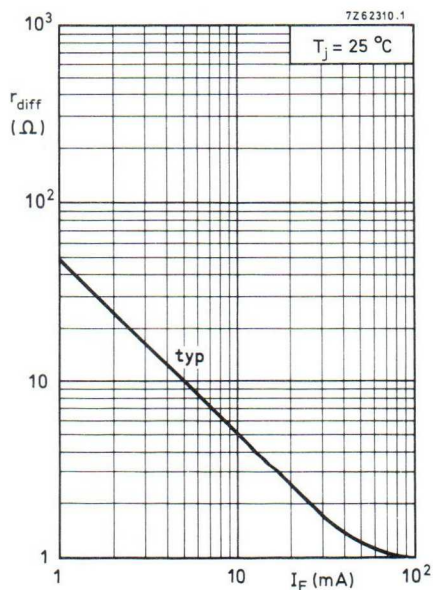


Fig. 14.

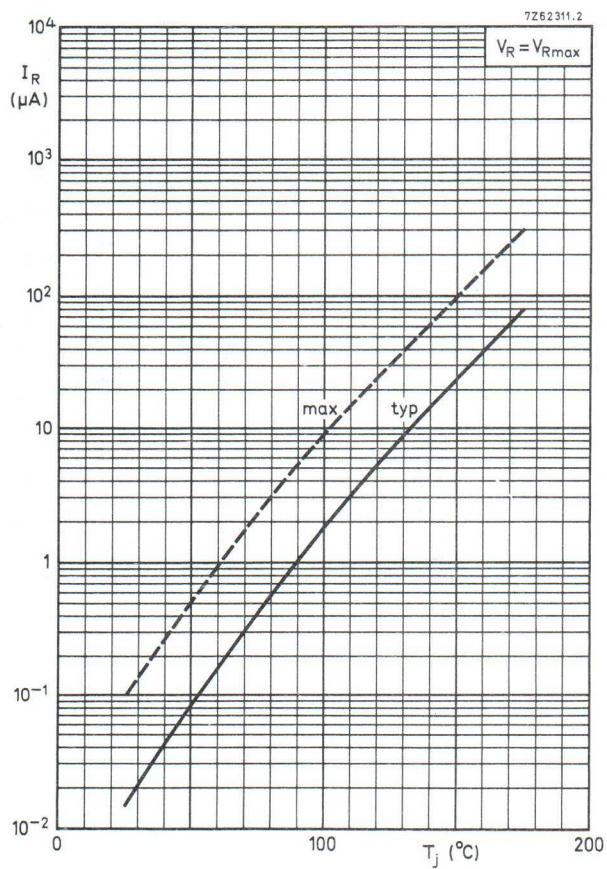


Fig. 15.

ULTRA HIGH-SPEED DIODE

Silicon planar epitaxial, ultra-high speed, high conductance diode in a SOD-80 envelope.

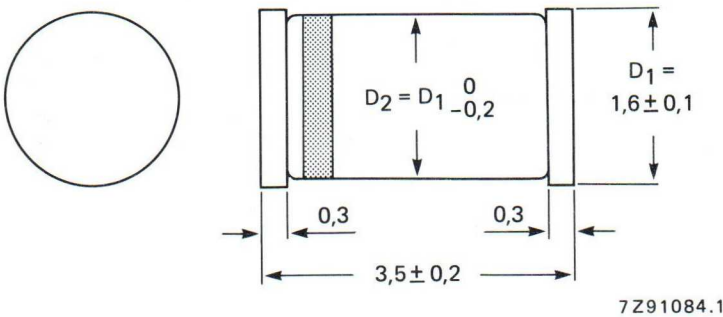
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	60 V
Repetitive peak reverse voltage	V_{RRM}	max.	60 V
Repetitive peak forward current	I_{FRM}	max.	600 mA
Junction temperature	T_j	max.	200 °C
Forward voltage at $I_F = 200$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 400$ mA to $I_R = 400$ mA; $R_L = 100 \Omega$; measured at $I_R = 40$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	50 pC

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



A green band indicates the cathode side and identifies the type BAV105.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	60 V
Repetitive peak reverse voltage	V_{RRM}	max.	60 V
Average rectified forward current	$I_F(AV)$	max.	300 mA
Forward current	I_F	max.	300 mA
Repetitive peak forward current	I_{FRM}	max.	600 mA
Non-repetitive peak forward current			
$t = 1 \mu s$	I_{FSM}	max.	4000 mA
$t = 1 s$		max.	1000 mA
Storage temperature	T_{stg}	-65 to + 175 °C	
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

From junction to ambient	$R_{th j-a}$	375 K/W
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CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage

$I_F = 10\text{ mA}$	V_F	<	0,75 V
$I_F = 200\text{ mA}$		<	1,00 V
$I_F = 200\text{ mA}; T_j = 100\text{ °C}$	V_F	<	0,95 V
$I_F = 500\text{ mA}$		<	1,25 V

Reverse current

$V_R = 60\text{ V}$	I_R	<	100 nA
$V_R = 60\text{ V}; T_j = 100\text{ °C}$		<	100 μA

Diode capacitance

$V_R = 0; f = 1\text{ MHz}$	C_d	<	2,5 pF
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Forward recovery voltage when switched to

$I_F = 400\text{ mA}; t_r1 = 30\text{ ns}$	V_{fr}	<	2,0 V
$I_F = 400\text{ mA}; t_r2 = 100\text{ ns}$ (see Fig. 2)		<	1,5 V

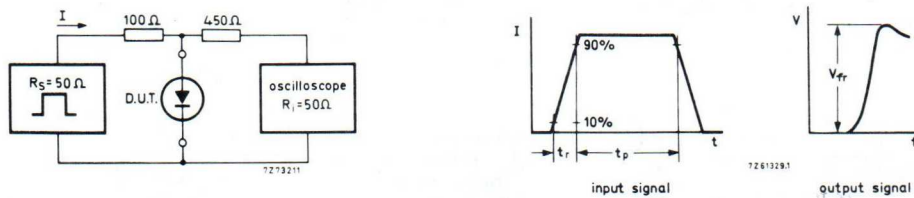


Fig. 2 Test circuit and waveforms; forward recovery voltage.

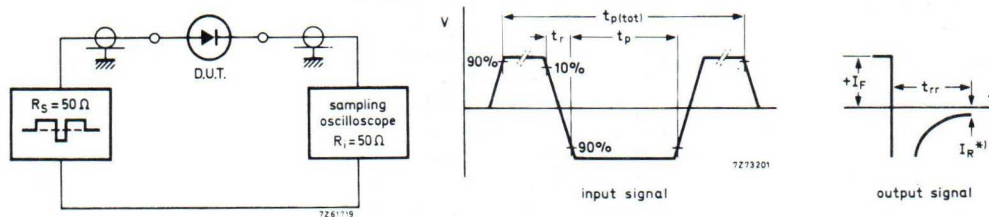
Input signal: 1st rise time of the forward pulse $t_{r1} = 30 \text{ ns}$
 2nd rise time of the forward pulse $t_{r2} = 100 \text{ ns}$
 Forward current pulse duration $t_p = 300 \text{ ns}$
 Duty factor $\delta = 0,01$

Oscilloscope: Rise time $t_r = 0,35 \text{ ns}$
 Input capacitance $C_i = 1 \text{ pF}$

Circuit capacitance $C \leq 20 \text{ pF}$ ($C = C_i + \text{parasitic capacitance}$)

Reverse recovery time when switched
 from $I_F = 400 \text{ mA}$ to $I_R = 400 \text{ mA}$;
 $R_L = 100 \Omega$; measured at $I_R = 40 \text{ mA}$
 (see Fig. 3)

$$t_{rr} < 6 \text{ ns}$$



*) $I_R = 40 \text{ mA}$

Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal: Total pulse duration $t_{p(\text{tot})} = 0,2 \mu\text{s}$
 Duty factor $\delta = 0,0025$
 Rise time of the reverse pulse $t_r = 0,6 \text{ ns}$
 Reverse pulse duration $t_p = 30 \text{ ns}$

Oscilloscope: Rise time $t_r = 0,35 \text{ ns}$

Circuit capacitance $C \leq 1 \text{ pF}$ ($C = \text{oscilloscope input capacitance} + \text{parasitic capacitance}$)

Recovery charge when switched from

$I_F = 10 \text{ mA}$ to $V_R = 5 \text{ V}$; $R_L = 500 \Omega$
(see Fig. 4)

$$Q_s < 50 \text{ pC}$$

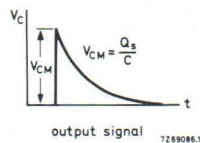
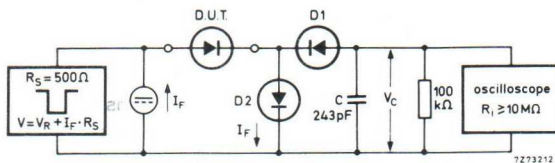


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA: $< 200 \text{ ps}$

Input signal: Rise time of the reverse pulse

$$t_r = 2 \text{ ns}$$

Reverse pulse duration

$$t_p = 400 \text{ ns}$$

Duty factor

$$\delta = 0,02$$

Circuit capacitance $C \leq 7 \text{ pF}$ (C = oscilloscope input capacitance + parasitic capacitance)

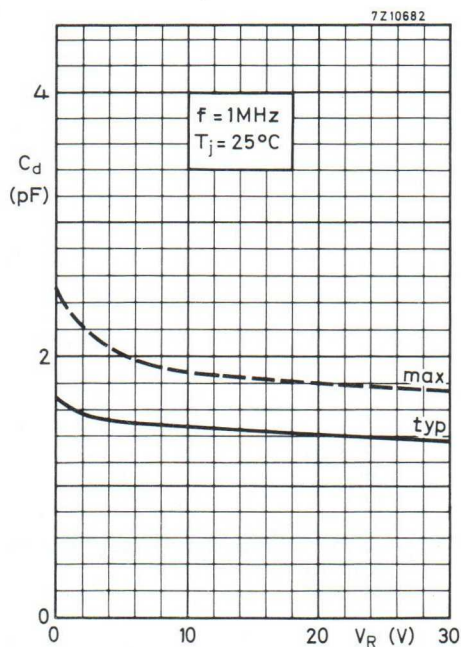


Fig. 5.

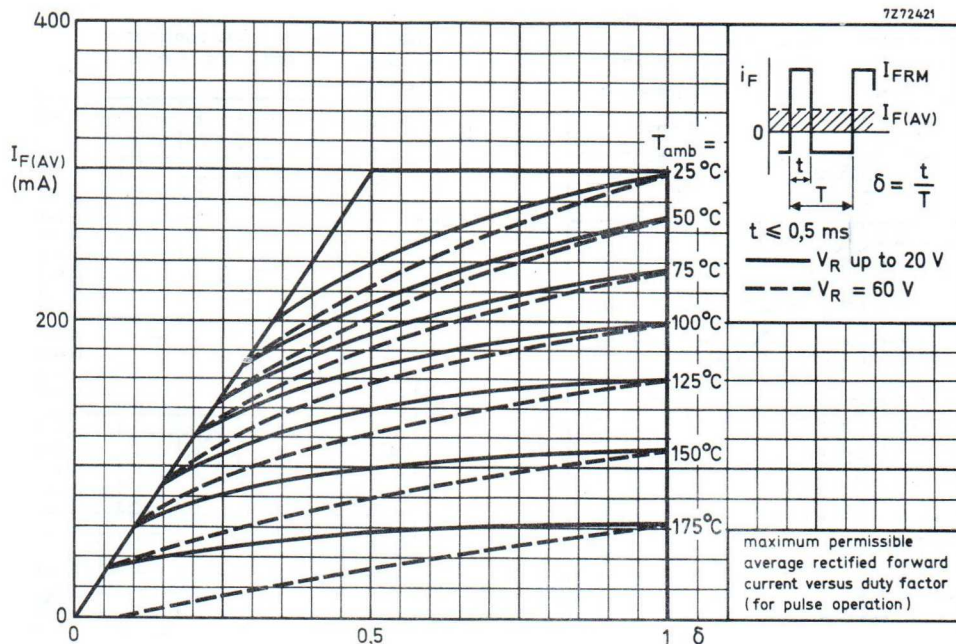


Fig. 6.

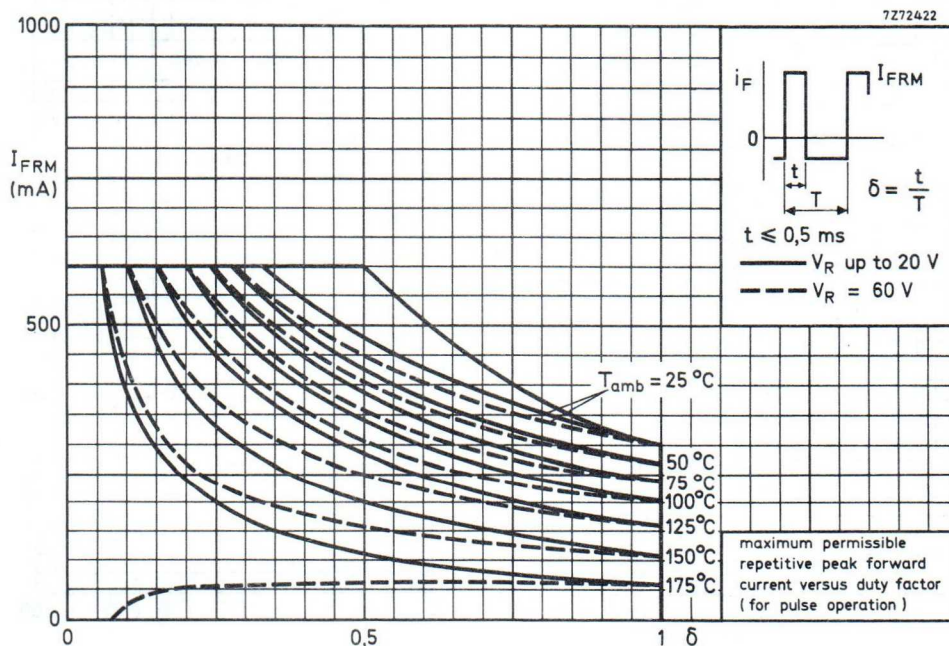


Fig. 7.

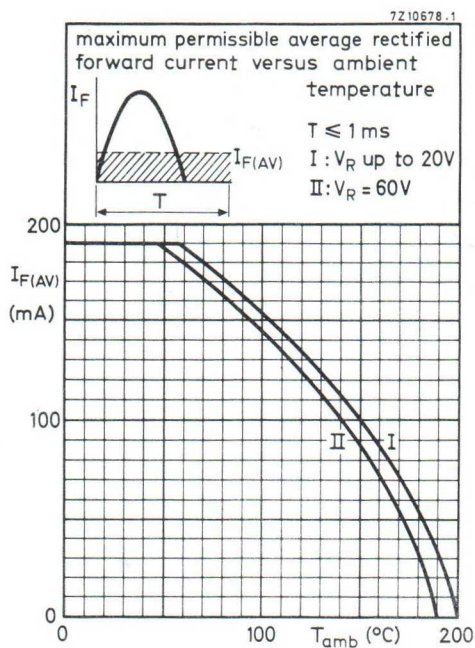


Fig. 8.

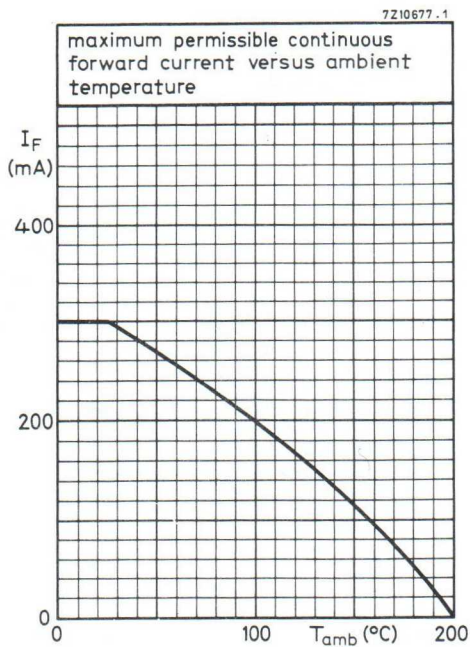


Fig. 9.

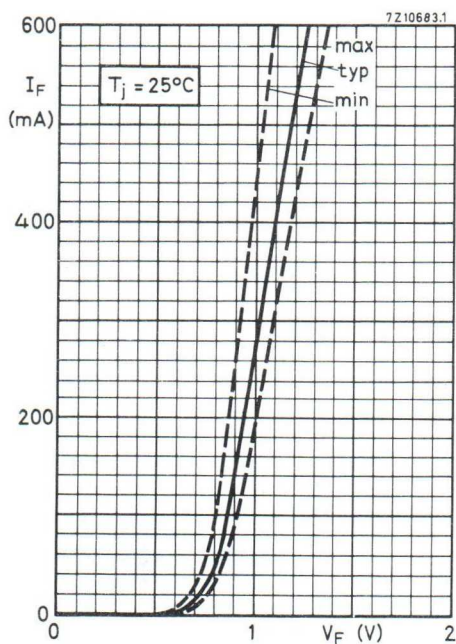


Fig. 10.

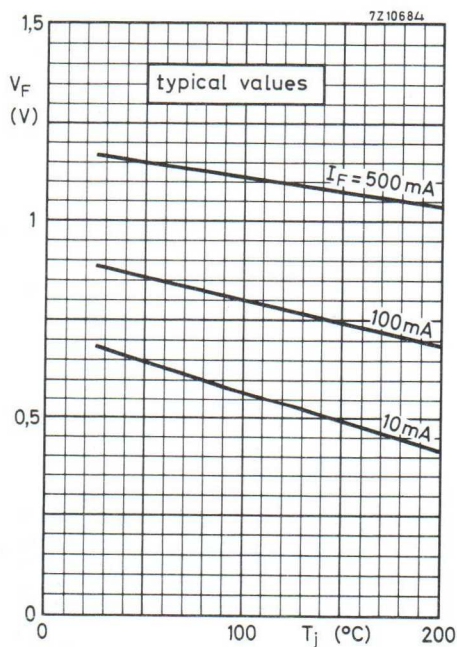


Fig. 11.

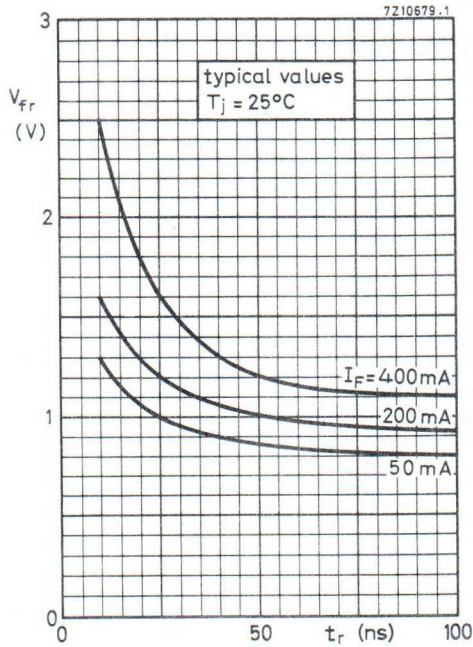


Fig. 12.

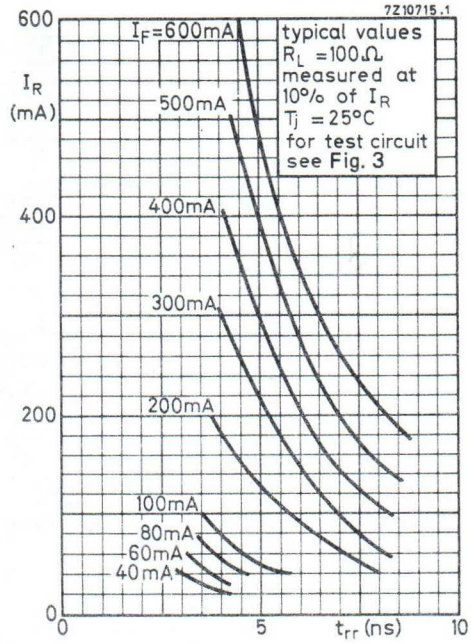


Fig. 13.

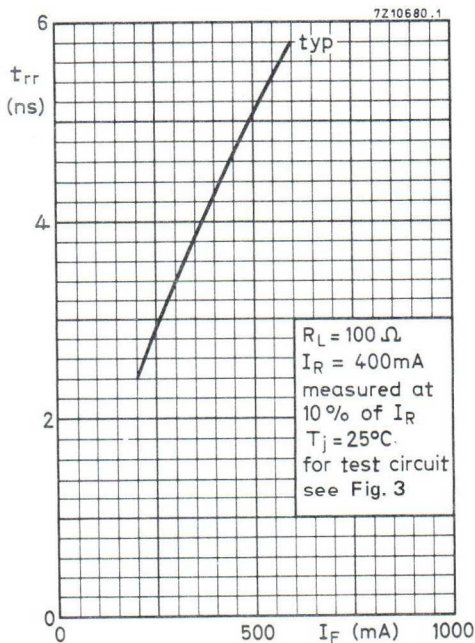


Fig. 14.

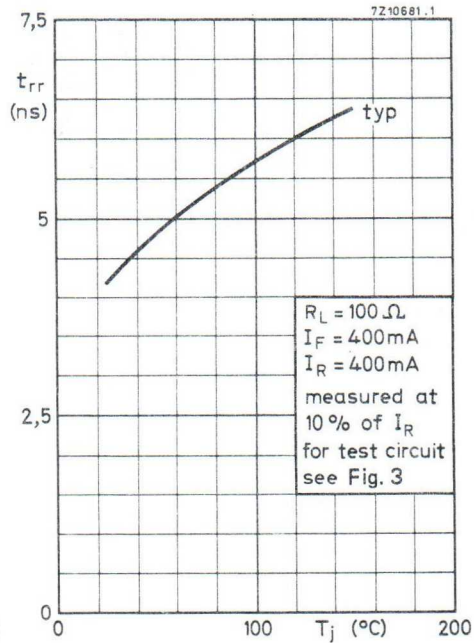


Fig. 15.

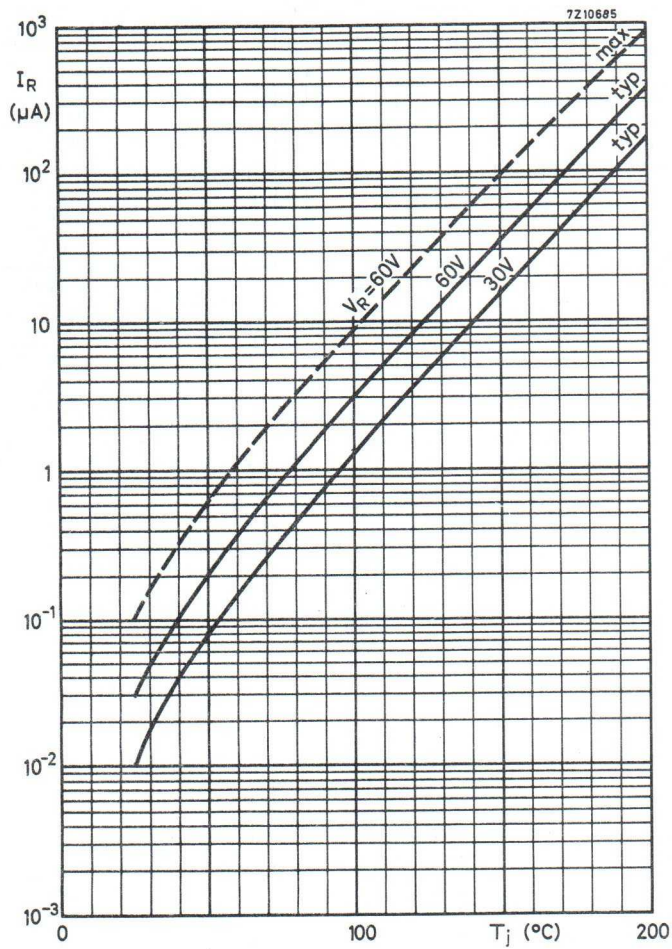


Fig. 16.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAW56 consists of two diodes in a microminiature plastic envelope. The anodes are commoned and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Repetitive peak forward current	I_{FRM}	max.	450 mA
Junction temperature	T_j	max.	150 °C
Forward voltage at $I_F = 50$ mA	V_F	<	1,0 V
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA	t_{rr}	<	6 ns
Recovery charge when switched from $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$	Q_s	<	45 pC

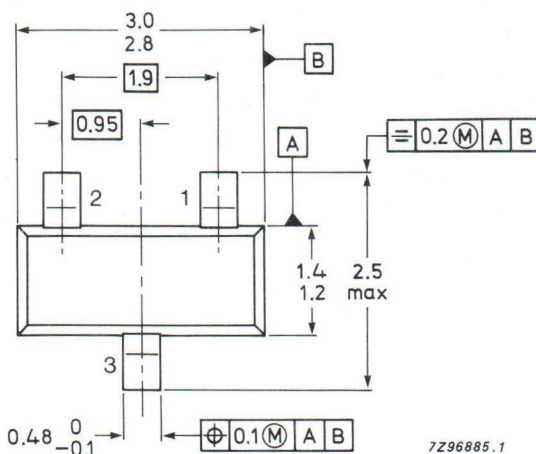
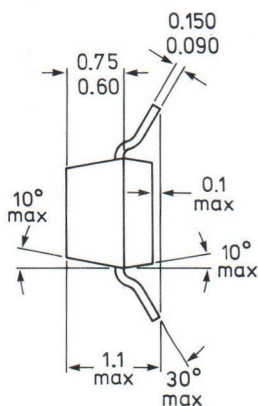
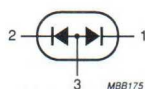
MECHANICAL DATA

Fig. 1 SOT-23.

Dimensions in mm

Marking code

BAW56 = A1p



TOP VIEW

See also *Soldering recommendations*.

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current* (averaged over any 20 ms period)	$I_F(AV)$	max.	215 mA
Forward current (DC)	I_F	max.	215 mA
Repetitive peak forward current	I_{FRM}	max.	450 mA
Non-repetitive peak forward current (per crystal)			
$t = 1 \mu s$	I_{FSM}	max.	2 A
$t = 1 ms$	I_{FSM}	max.	1 A
$t = 1 s$	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE**

From junction to ambient**	$R_{th j-t}$	=	430 K/W
From tab to soldering points	$R_{th t-s}$	=	2 x 280 K/W
From soldering points to ambient ▲	$R_{th s-a}$	=	2 x 90 K/W

CHARACTERISTICS (per diode) $T_j = 25\text{ °C}$ unless otherwise specified

Forward voltage			
$I_F = 1\text{ mA}$	V_F	<	715 mV
$I_F = 10\text{ mA}$	V_F	<	855 mV
$I_F = 50\text{ mA}$	V_F	<	1000 mV
$I_F = 150\text{ mA}$	V_F	<	1250 mV
Reverse current			
$V_R = 25\text{ V}; T_j = 150\text{ °C}$	I_R	<	30 μA
$V_R = 70\text{ V}$	I_R	<	2,5 μA
$V_R = 70\text{ V}; T_j = 150\text{ °C}$	I_R	<	50 μA
Diode capacitance			
$V_R = 0; f = 1\text{ MHz}$	C_d	<	2 pF
Forward recovery voltage when switched to $I_F = 10\text{ mA}; t_r = 20\text{ ns}$ see Fig. 2	V_{fr}	<	1,75 V

* Measured under pulse conditions: pulse time $t_p \leq 0,5\text{ ms}$.For sinusoidal operation $I_F(AV) = 150\text{ mA}$; averaging time $t(AV) \leq 1\text{ ms}$.** See *Thermal characteristics*.

▲ Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

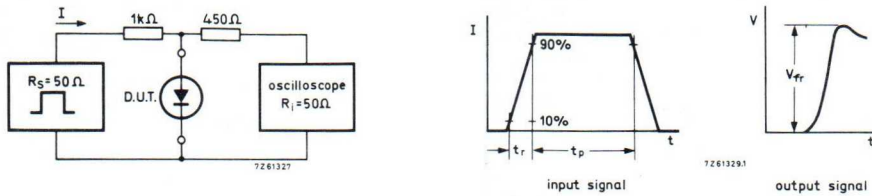


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse $t_r = 20$ ns

Forward current pulse duration $t_p = 120$ ns. Duty factor $\delta = 0,01$

Oscilloscope: Rise time $t_r = 0,35$ ns.

Circuit capacitance $C \leq 1$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
 $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$;
 measured at $I_R = 1$ mA see Fig. 3

$$t_{rr} < 6 \text{ ns}$$

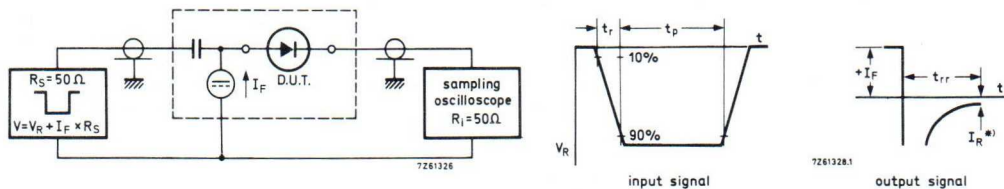


Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal: Rise time of the reverse pulse $t_r = 0,6$ ns

Reverse pulse duration $t_p = 100$ ns. Duty factor $\delta = 0,05$.

Oscilloscope: Rise time $t_r = 0,35$ ns

Circuit capacitance $C \leq 1$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from
 $I_F = 10$ mA to $V_R = 5$ V; $R_L = 500 \Omega$ see Fig. 4

$$Q_s < 45 \text{ pC}$$

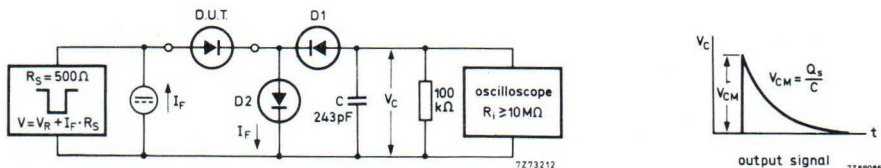


Fig. 4 Test circuit and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps. D1 = BAW62.

Input signal: Rise time of the reverse pulse $t_r = 2$ ns

Reverse pulse duration $t_p = 400$ ns. Duty factor $\delta = 0,02$

Circuit capacitance $C \leq 7$ pF ($C =$ oscilloscope input capacitance + parasitic capacitance).

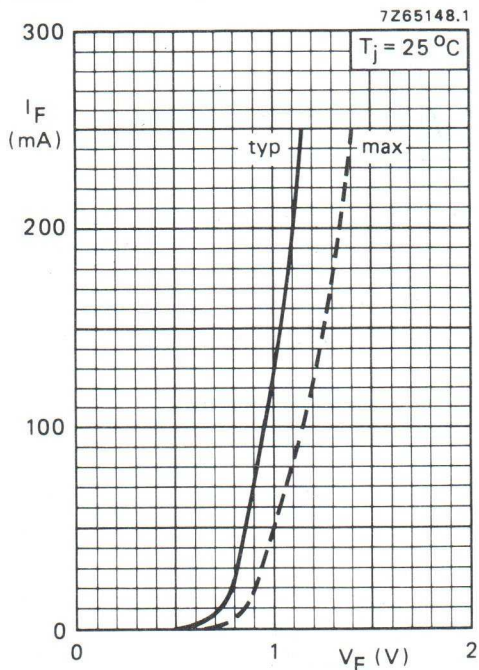


Fig. 5.

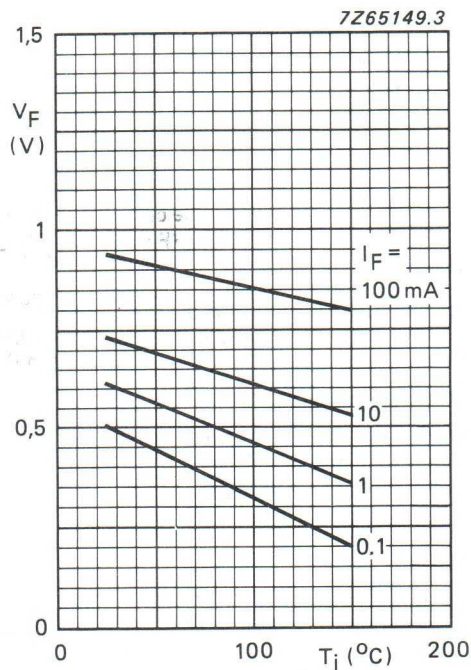


Fig. 6 Typical values.

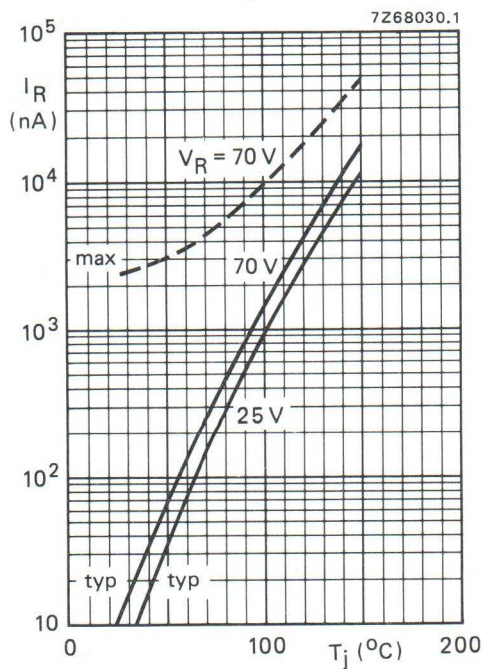
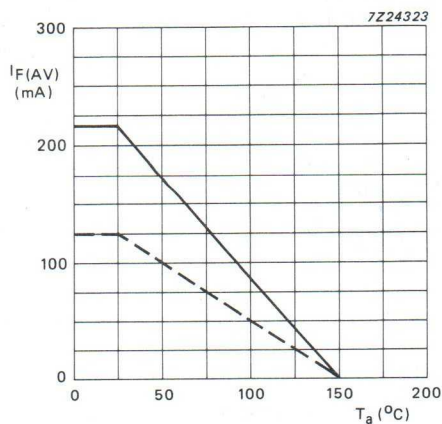


Fig. 7.

Fig. 8 — single diode;
----- double diode, equally loaded.

UHF VARIABLE CAPACITANCE DIODE

The BB215 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for application in UHF tuners. The leadless SOD-80 encapsulation is intended for surface mounting.

The diode features a capacitance characteristic with a good linearity.

Diodes are supplied in matched sets and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

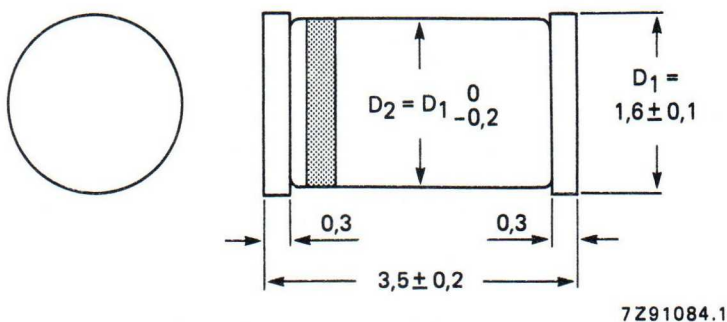
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Reverse current $V_R = 28 \text{ V}$	I_R	<	10 nA
Diode capacitance at $f = 500 \text{ kHz}$ $V_R = 28 \text{ V}$	C_d		1,8 to 2,2 pF
Capacitance ratio at $f = 500 \text{ kHz}$	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$	>	7,6
Series resistance at $f = 470 \text{ MHz}$ V_R is that value at which $C_d = 9 \text{ pF}$	r_s	<	0,75 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a white band on the body and a second green band indicates the BB215 type.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		-55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

 $V_R = 28\text{ V}$ $V_R = 28\text{ V}; T_{amb} = 85\text{ °C}$

I_R	<	10 nA
	<	200 nA

Diode capacitance at $f = 500\text{ kHz}$ $V_R = 1\text{ V}$

C_d	typ.	17 pF
	<	18 pF

 $V_R = 28\text{ V}$

C_d		1,8 to 2,2 pF
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Capacitance ratio at $f = 500\text{ kHz}$

$\frac{C_d(V_R = 1\text{ V})}{C_d(V_R = 28\text{ V})}$	>	7,6
	typ.	8,3

Series resistance

at $f = 470\text{ MHz}$ and at that value
of V_R at which $C_d = 9\text{ pF}$

r_s	typ.	0,63 Ω
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VHF VARIABLE CAPACITANCE DIODE

The BB219 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for electronic tuning in VHF television tuners for C.A.T.V. applications. The SOD-80 envelope is suitable for surface mounting.

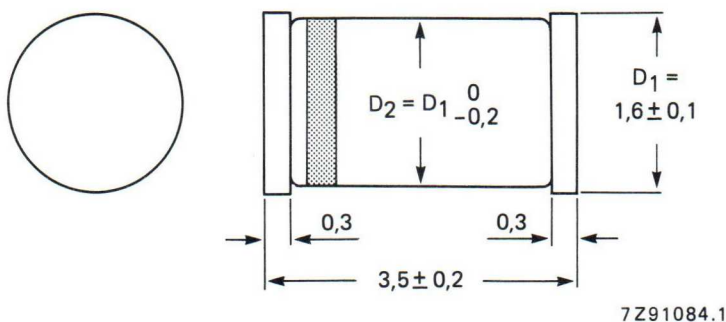
QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	30 V
Reverse current $V_R = 28$ V	I_R	<	10 nA
Diode capacitance at $f = 1$ MHz $V_R = 1$ V $V_R = 28$ V	C_d	>	31 pF 2,6 to 3,2 pF
Capacitance ratio at $f = 1$ MHz	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$		12 to 15
Series resistance at $f = 100$ MHz V_R is that value at which $C_d = 30$ pF	r_s	typ. <	0,7 Ω 0,9 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a white band on the body.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		-55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0,6 K/mW
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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

$V_R = 28\text{ V}$

I_R	<	10 nA
	<	200 nA

$V_R = 28\text{ V}; T_{amb} = 85\text{ °C}$

Diode capacitance at $f = 0,5\text{ MHz}$

$V_R = 1\text{ V}$

C_d	>	31 pF
C_d		2,6 to 3,2 pF

$V_R = 28\text{ V}$

Capacitance ratio at $f = 1\text{ MHz}$

$\frac{C_d(V_R = 1\text{ V})}{C_d(V_R = 28\text{ V})}$		12 to 15
--	--	----------

Series resistance

at $f = 100\text{ MHz}$ and at that value
of V_R at which $C_d = 30\text{ pF}$

r_s	typ.	0,7 Ω
	<	0,9 Ω

Tolerance of capacitance difference

between two diodes at $V_R = 1\text{ to }28\text{ V}$

$\frac{\Delta C}{C}$	<	2,5 %
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VHF VARIABLE CAPACITANCE DIODE

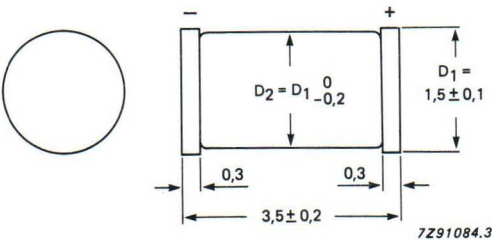
The BB240 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band B up to 460 MHz in all-band tuners.
The diode is encapsulated in the hermetically sealed glass envelope SOD-80 suitable for surface mounting.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32 V
Reverse current $V_R = 28\text{ V}$	I_R	<	10 nA
Diode capacitance at $f = 1\text{ MHz}$ $V_R = 0.5\text{ V}$ $V_R = 28\text{ V}$	C_d	>	38 pF 2.4 to 2.7 pF
Capacitance ratio at $f = 1\text{ MHz}$ $C_d(V_R = 0.5\text{ V})$ $C_d(V_R = 28\text{ V})$		>	14
Series resistance at $f = 100\text{ MHz}$ V_R is that value at which $C_d = 40\text{ pF}$	r_s	<	1.0 Ω

MECHANICAL DATA

Dimensions in mm



The cathode is indicated by a green band on the body.

Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature range	T_{stg}		-55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	R_{thj-a}	=	0.6 K/W
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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

$V_R = 28\text{ V}$

$V_R = 28\text{ V}; T_{amb} = 85\text{ °C}$

I_R	<	10 nA
	<	200 nA

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 0.5\text{ V}$

$V_R = 28\text{ V}$

C_d	>	38 pF
		2.4 to 2.7 pF

Capacitance ratio at $f = 1\text{ MHz}$

$C_d (V_R = 0.5\text{ V})$	>	14
$C_d (V_R = 28\text{ V})$		

Series resistance

at $f = 100\text{ MHz}$ and at that valueof V_R at which $C_d = 40\text{ pF}$

r_s	<	1.0 Ω
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Tolerance of capacitance difference

between two diodes at $V_R = 1\text{ to }28\text{ V}$

$\frac{\Delta C}{C}$	<	2.5 %
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VHF VARIABLE CAPACITANCE DIODE

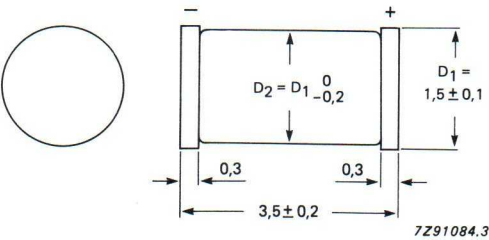
The BB241 is a VHF variable capacitance diode in planar technology with a very high capacitance ratio intended for VHF-band A up to 160 MHz in all-band tuners.
The diode is encapsulated in the hermetically sealed glass envelope SOD-80 suitable for surface mounting.

QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	32 V
Reverse current $V_R = 28\text{ V}$	I_R	<	10 nA
Diode capacitance at $f = 1\text{ MHz}$ $V_R = 0.5\text{ V}$ $V_R = 28\text{ V}$	C_d	>	63 pF 2.5 to 3.0 pF
Capacitance ratio at $f = 1\text{ MHz}$	$C_d (V_R = 0.5\text{ V})$ $C_d (V_R = 28\text{ V})$	>	21
Series resistance at $f = 100\text{ MHz}$ V_R is that value at which $C_d = 40\text{ pF}$	r_s	<	2.0 Ω

MECHANICAL DATA

Dimensions in mm



The cathode is indicated by a black band on the body.

Fig. 1 SOD-80.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	32 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature range	T_{stg}		-55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	0.6 K/W
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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

 $V_R = 28\text{ V}$ $V_R = 28\text{ V}; T_{amb} = 85\text{ °C}$

I_R	<	10 nA
	<	200 nA

Diode capacitance at $f = 1\text{ MHz}$ $V_R = 0.5\text{ V}$ $V_R = 28\text{ V}$

C_d	>	63 pF
C_d		2.5 to 3.0 pF

Capacitance ratio at $f = 1\text{ MHz}$

$C_d (V_R = 0.5\text{ V})$	>	21
$C_d (V_R = 28\text{ V})$		

Series resistance

at $f = 100\text{ MHz}$ and at that valueof V_R at which $C_d = 40\text{ pF}$

r_s	<	2.0 Ω
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Tolerance of capacitance difference

between two diodes at $V_R = 1\text{ to }28\text{ V}$

$\frac{\Delta C}{C}$	<	2.5 %
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SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BB249 is a variable capacitance diode in a miniature glass envelope intended for electronic tuning in v.h.f. television tuners with extended band I (FCC and OIRT-norm).

Diodes are supplied in matched sets (minimum 120 pieces and divisible by 12) and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

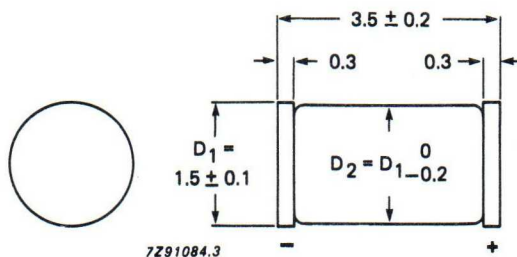
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	28 V
Reverse current at $V_R = 28$ V	I_R	max.	10 nA
Diode capacitance at $f = 500$ kHz $V_R = 1$ V	C_d		39 to 46 pF
$V_R = 28$ V	C_d		4,0 to 5,0 pF
Capacitance ratio at $f = 500$ kHz	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$		8 to 10
Series resistance at $f = 200$ MHz V_R is that value at which $C_d = 25$ pF	r_s	max.	0,6 Ω

MECHANICAL DATA

Dimensions in mm

Fig.1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		-55 to + 150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air

$$R_{th\ j-a} = 0,6\ K/mW$$

CHARACTERISTICS $T_{amb} = 25\ ^\circ C$ unless otherwise specified

Reverse current

$V_R = 28\ V$

I_R max. 10 nA

$V_R = 28\ V; T_{amb} = 85\ ^\circ C$

I_R max. 200 nA

Diode capacitance at $f = 500\ kHz$

$V_R = 1\ V$

C_d 39 to 46 pF

$V_R = 28\ V$

C_d 4,0 to 5,0 pF

Capacitance ratio at $f = 500\ kHz$

$$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)} = 8\ to\ 10$$

Series resistance at $f = 200\ MHz$ V_R is that value at which $C_d = 25\ pF$

r_s max. 0,6 Ω

Relative capacitance difference

between two diodes; $V_R = 0,5\ to\ 28\ V$

$$\frac{\Delta C}{C} \text{ max. } 3\ \%$$

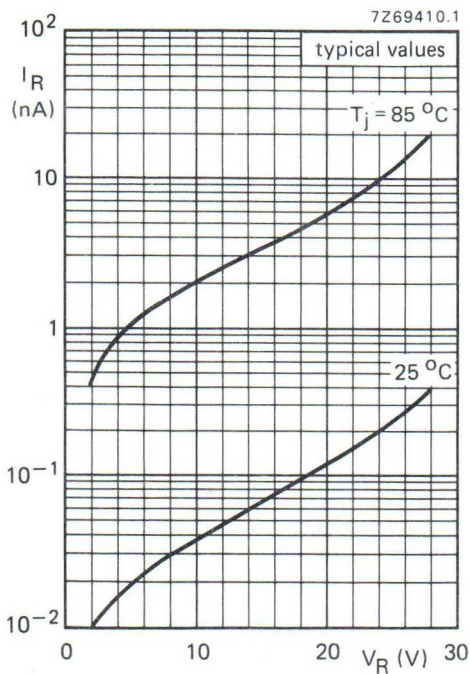
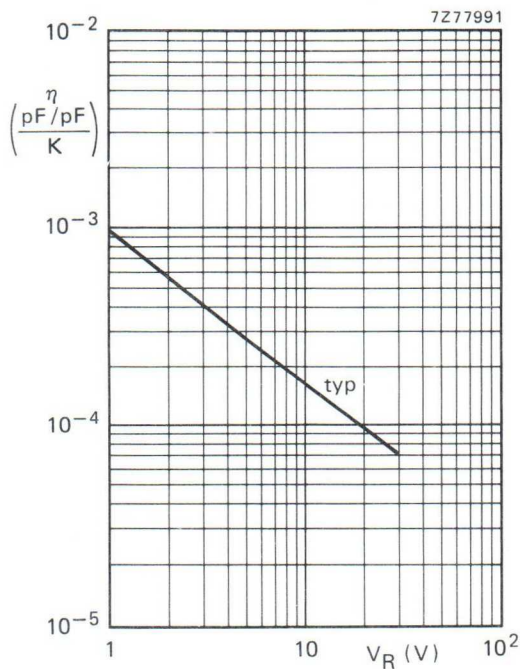
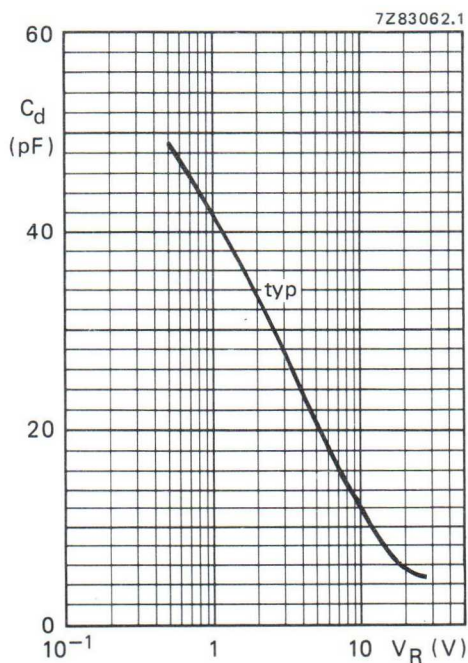
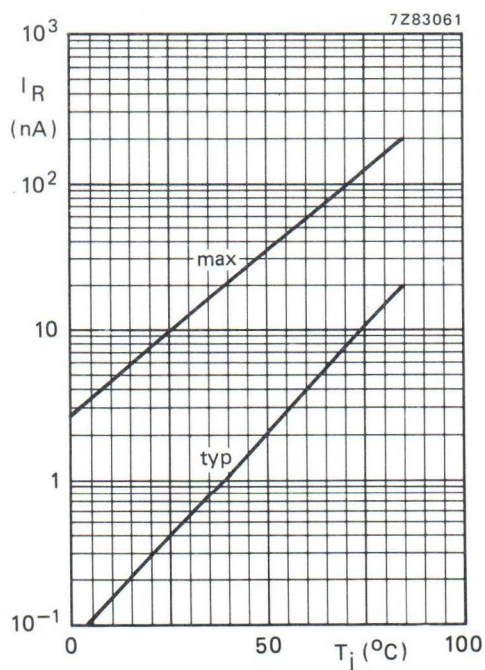


Fig. 2 Typical values.

Fig. 3 Temperature coefficient of the diode capacitance; $T_{\text{amb}} = 0$ to $85\text{ }^{\circ}\text{C}$.Fig. 4 $f = 500\text{ kHz}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$.Fig. 5 $V_R = 28\text{ V}$.

VHF VARIABLE CAPACITANCE DOUBLE DIODE

The BB804 is a variable capacitance double diode in planar technology with common cathode in a plastic SOT23 envelope. It is intended for FM tuning especially for car radios.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	18 V
Repetitive peak reverse voltage	V_{RRM}	max.	20 V
Forward current (DC)	I_F	max.	50 mA
Operating junction temperature	T_j	max.	100 °C
Reverse current	I_R	max.	20 nA
Diode capacitance at $f = 1$ MHz $V_R = 2$ V	C_d		42 to 47.5 pF
Capacitance ratio at $f = 1$ MHz	$\frac{C_d (V_R = 2 \text{ V})}{C_d (V_R = 8 \text{ V})}$		1.65 to 1.75
Series resistance at $f = 100$ MHz V_R is that value at which $C_d = 38$ pF	r_s	typ.	0.20 Ω

MECHANICAL DATA

Dimensions in mm

Marking SF

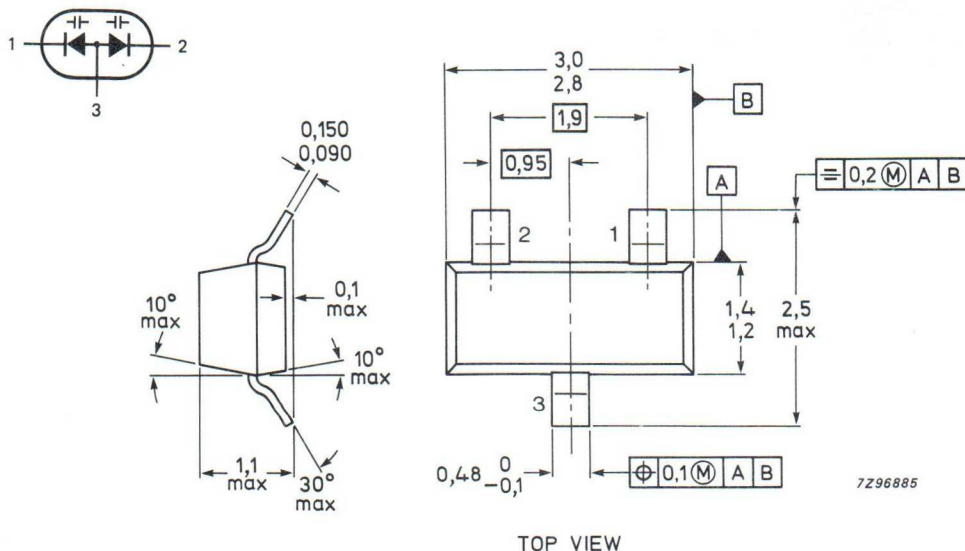


Fig.1 SOT23.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	18 V
Forward current (DC)	I_F	max.	50 mA
Repetitive peak reverse voltage	V_{RRM}	max.	20 V
Storage temperature range	T_{stg}		-55 to + 100 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCEFrom junction to ambient mounted on a
ceramic substrate of 8 mm x 10 mm x 0.7 mm

$$R_{th\ j-a} = 430\ K/W$$

CHARACTERISTICS $T_j = 25\ ^\circ C$ unless otherwise specified

Reverse current

$V_R = 16\ V$

$V_R = 16\ V; T_{amb} = 60\ ^\circ C$

$$I_R < 20\ nA$$

$$< 200\ nA$$

Diode capacitance at $f = 1.0\ MHz$

$V_R = 2\ V$

red 0

yellow 1

white 2

green 3

blue 4

$$C_d \quad 42\ \text{to}\ 43.5\ pF$$

$$C_d \quad 43\ \text{to}\ 44.5\ pF$$

$$C_d \quad 44\ \text{to}\ 45.5\ pF$$

$$C_d \quad 45\ \text{to}\ 46.5\ pF$$

$$C_d \quad 46\ \text{to}\ 47.5\ pF$$

Capacitance ratio at $f = 1\ MHz$

$$\frac{C_d(V_R = 2\ V)}{C_d(V_R = 8\ V)} \quad 1.65\ \text{to}\ 1.75$$

Series resistance

at $f = 100\ MHz$, V_R is that valueat which $C_d = 38\ pF$

$$r_s \quad \text{typ.} \quad 0.20\ \Omega$$

VARIABLE CAPACITANCE DIODE

Silicon planar variable capacitance diode in a microminiature envelope. It is intended for electronic tuning applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Reverse voltage	V_R	max.	28 V
Reverse current at $V_R = 28$ V	I_R	<	50 nA
Diode capacitance at $f = 1$ MHz $V_R = 28$ V	C_d		1,6 to 2,0 pF
Capacitance ratio at $f = 1$ MHz	$\frac{C_d (V_R = 1 \text{ V})}{C_d (V_R = 28 \text{ V})}$	typ.	9,7
Series resistance at $f = 470$ MHz $V_R =$ that value at which $C_d = 9$ pF	r_D	<	1,2 Ω

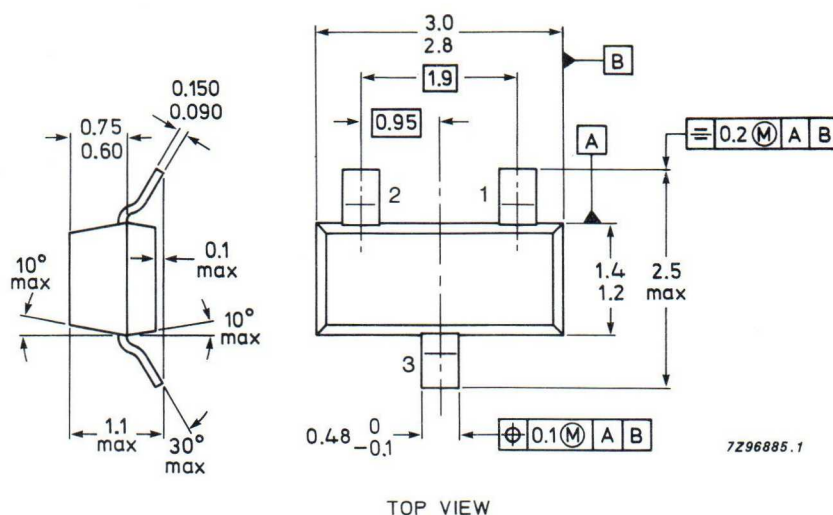
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-23.

BBY31 = S1p



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)**	I_F	max.	20 mA
Storage temperature	T_{stg}		-65 to + 100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified

Reverse current

$V_R = 28\text{ V}$

$I_R < 50\text{ nA}$

$V_R = 28\text{ V}; T_j = 85\text{ °C}$

$I_R < 1000\text{ nA}$

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 1\text{ V}$

$C_d \text{ typ. } 17,5\text{ pF}$

$V_R = 28\text{ V}$

$C_d \text{ } 1,6 \text{ to } 2,0\text{ pF}$

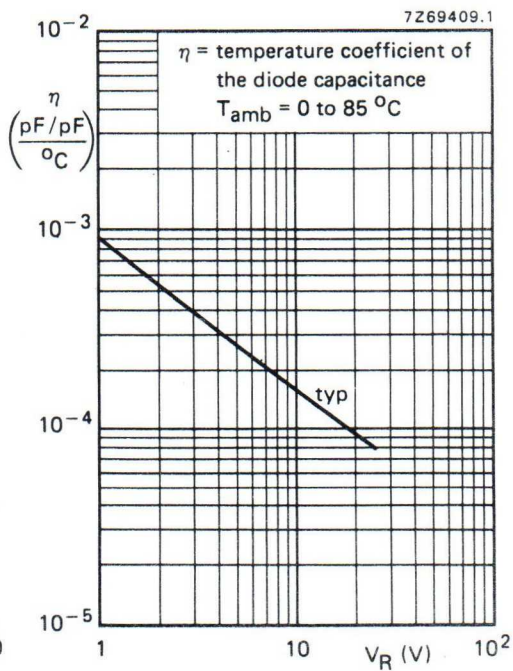
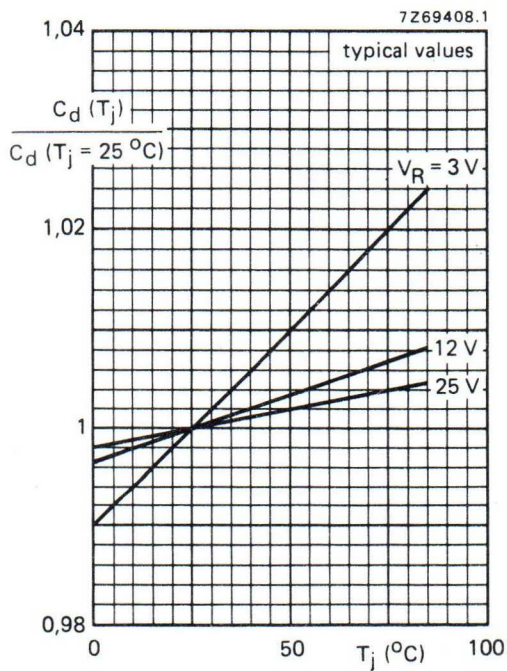
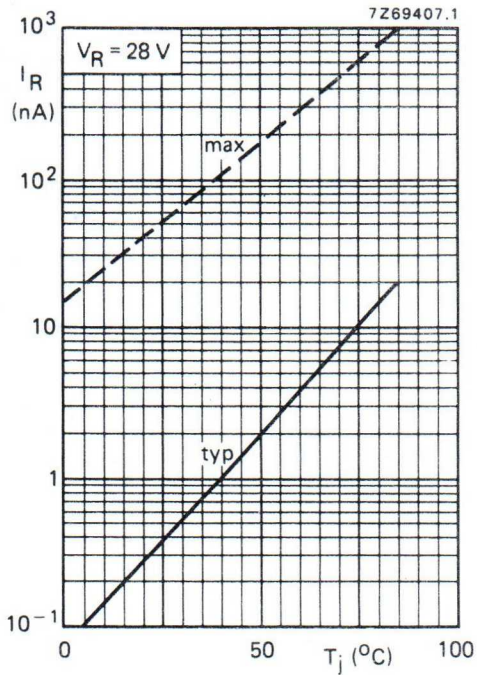
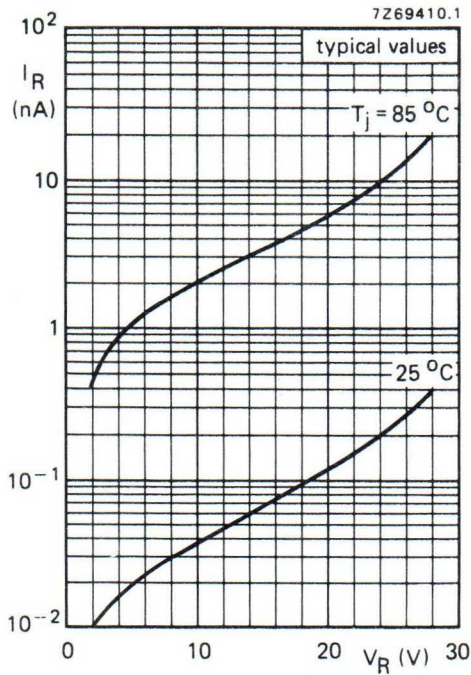
Capacitance ratio at $f = 1\text{ MHz}$

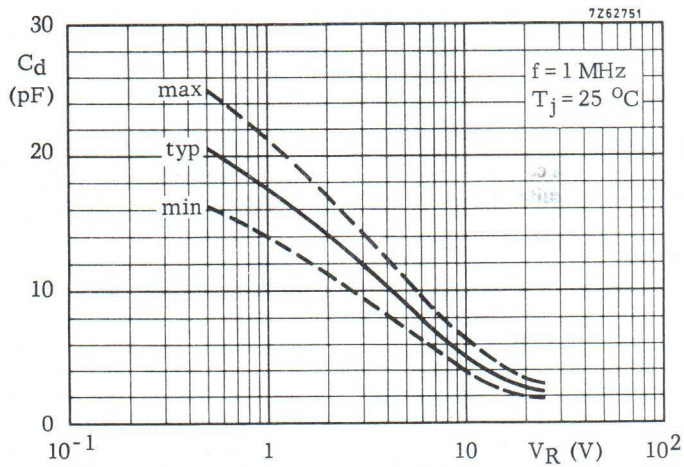
$$\frac{C_d(V_R = 1\text{ V})}{C_d(V_R = 28\text{ V})} \text{ typ. } 9,7$$

Series resistance at $f = 470\text{ MHz}$ and at that value of V_R at which $C_d = 9\text{ pF}$

$r_D < 1,2\text{ }\Omega$

* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.





DOUBLE VARIABLE CAPACITANCE DIODE

The BBY39 is a double variable capacitance diode with a common cathode and mounted in a micro-miniature envelope (SOT-23), suitable for surface mounting. The two diodes in one envelope are matched.

The device is intended for application in electronic tuners in satellite TV systems.

QUICK REFERENCE DATA

For each diode:

Continuous reverse voltage

V_R max. 30 V

Operating junction temperature

T_j max. 85 °C

Reverse current

I_R < 10 nA

$V_R = 28$ V

Diode capacitance at $f = 1$ MHz

C_d 1,6 to 2,0 pF

$V_R = 28$ V

Capacitance ratio at $f = 1$ MHz

$\frac{C_d (V_R = 1 \text{ V})}{C_d (V_R = 28 \text{ V})} > 8,0$

Series resistance at $f = 470$ MHz

V_R is that value at which $C_d = 9$ pF

r_s < 1,2 Ω

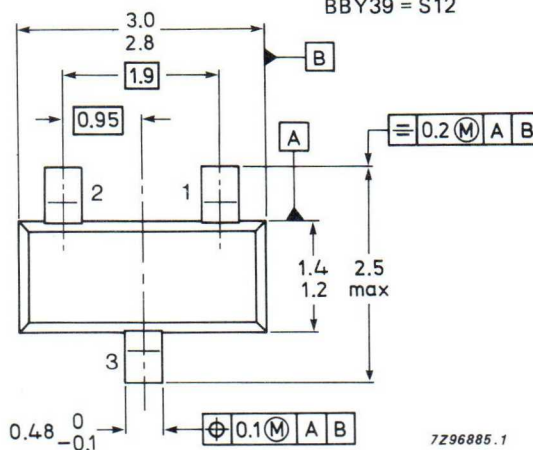
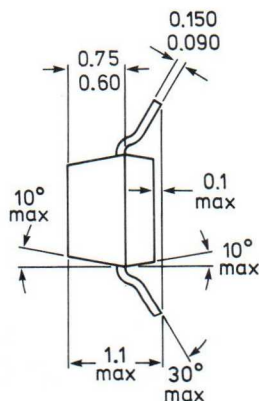
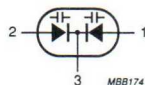
MECHANICAL DATA

Fig. 1 SOT-23.

Dimensions in mm

Marking code:

BBY39 = S12



TOP VIEW

7296885.1

RATINGS (for each diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		-65 to +100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient *	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS (for each diode) $T_j = 25\text{ °C}$ unless otherwise specified

Reverse current

$V_R = 28\text{ V}$

$V_R = 28\text{ V}; T_j = 85\text{ °C}$

I_R	<	10 nA
	<	100 nA

Diode capacitance at $f = 1\text{ MHz}$

$V_R = 1\text{ V}$

$V_R = 28\text{ V}$

C_d	typ.	17.5 pF
C_d		1.6 to 2.0 pF

Capacitance ratio at $f = 1\text{ MHz}$

$\frac{C_d(V_R = 1\text{ V})}{C_d(V_R = 28\text{ V})}$	>	8.0
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Series resistance

at $f = 470\text{ MHz}$ and that value
of V_R at which $C_d = 9\text{ pF}$

r_s	<	1.2 Ω
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* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BBY40 is a variable capacitance diode in a plastic envelope intended for electronic tuning in VHF television tuners with extended band I (FCC and OIRT-norm).

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	28 V
Reverse current at $V_R = 28$ V	I_R	<	10 nA
Diode capacitance at $f = 1$ MHz $V_R = 1$ V	C_d		39 to 46 pF
$V_R = 28$ V	C_d		3.8 to 4.8 pF
Capacitance ratio at $f = 1$ MHz	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$		8 to 12
Series resistance at $f = 200$ MHz V_R is that value at which $C_d = 25$ pF	r_S	<	0.7 Ω

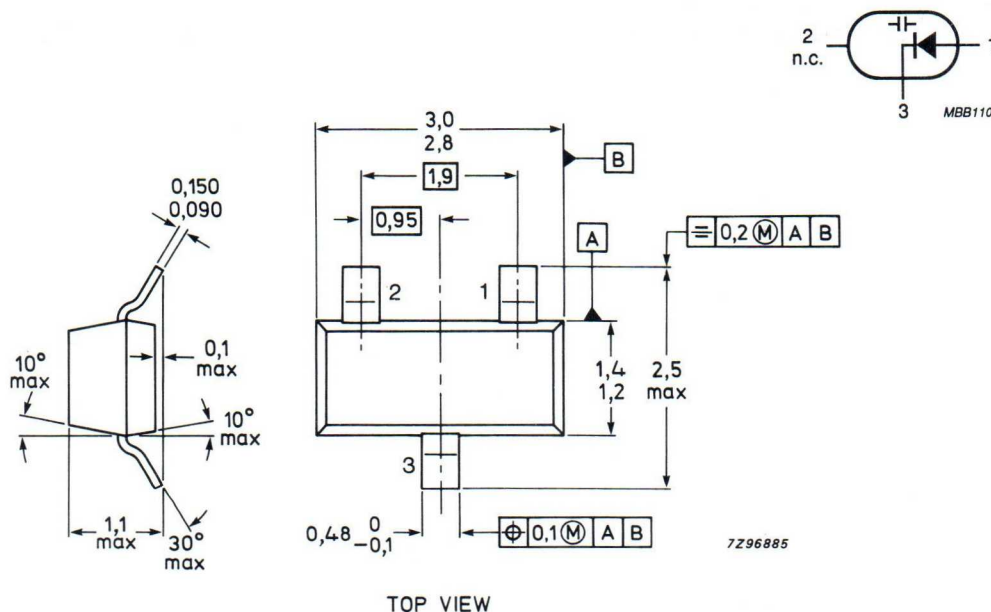
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-23.

BBY40 = S2



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (repetitive peak value)	V_{RRM}	max.	30 V
Forward current (DC)	I_F	max.	20 mA
Storage temperature	T_{stg}		-55 to +100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified

Reverse current

 $V_R = 28\text{ V}$

I_R	typ.	0.1 nA
	<	10 nA

 $V_R = 28\text{ V}; T_{amb} = 60\text{ °C}$

I_R	<	100 nA
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Diode capacitance at $f = 1\text{ MHz}$ $V_R = 1\text{ V}$

C_d		39 to 46 pF
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 $V_R = 3\text{ V}$

C_d	typ.	29.0 pF
-------	------	---------

 $V_R = 28\text{ V}$

C_d		3.8 to 4.8 pF
-------	--	---------------

Capacitance ratio at $f = 1\text{ MHz}$

$\frac{C_d(V_R = 1\text{ V})}{C_d(V_R = 28\text{ V})}$		8 to 12
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Series resistance at $f = 200\text{ MHz}$ V_R is that value at which $C_d = 25\text{ pF}$

r_s	<	0.7 Ω
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* Mounted on a ceramic substrate of 7 mm x 5 mm x 0.5 mm.

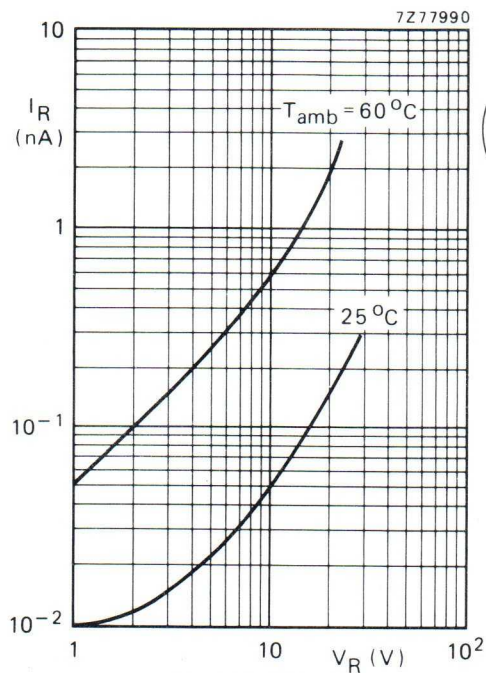
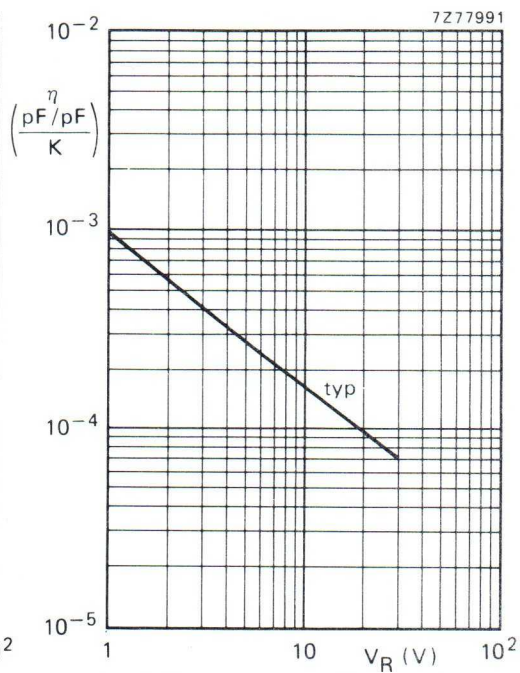
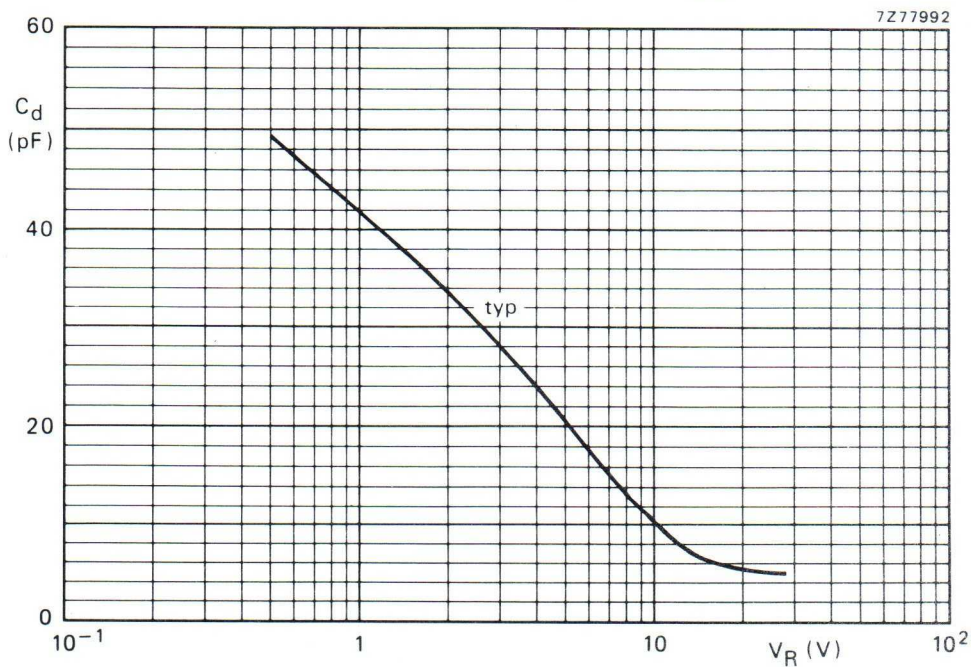


Fig. 2 Typical values

Fig. 3 Temperature coefficient of the diode capacitance; $T_{amb} = 0$ to 85°C .Fig. 4 $f = 1$ MHz; $T_{amb} = 25^\circ\text{C}$.

V.H.F. VARIABLE CAPACITANCE DIODE

The BBY42 is a variable capacitance diode in a microminiature plastic envelope SOT-23. It is intended for use in v.h.f. TV tuners and CATV applications using SMD technology.

QUICK REFERENCE DATA

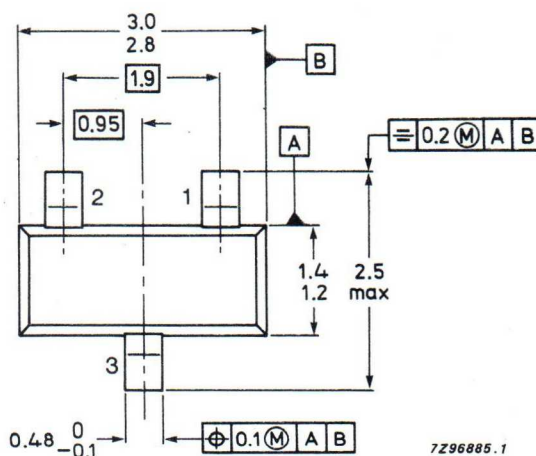
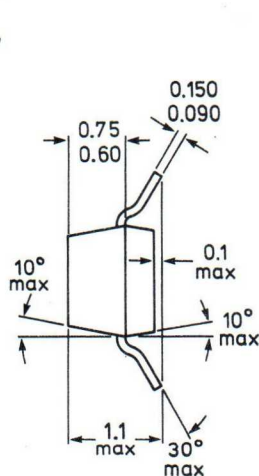
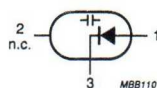
Reverse voltage, peak value	V_{RM}	max. 32 V
Reverse current $V_R = 28$ V	I_R	max. 10 nA
Diode capacitance at $f = 1$ MHz $V_R = 28$ V	C_d	2,4 to 3,0 pF
Capacitance ratio at $f = 1$ MHz	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$	12 to 16
Series resistance at $f = 100$ MHz V_R is that value at which $C_d = 30$ pF	r_s	typ. 0,9 Ω max. 1,0 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code: S13



TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage (peak value)	V_{RM}	max.	32 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		-65 to + 100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient and
mounted on a ceramic substrate of
8 mm x 10 mm x 0,7 mm

R_{thj-a}	=	430 K/W
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CHARACTERISTICS $T_j = 25$ °C unless otherwise specified

Reverse current

$V_R = 28$ V

$V_R = 28$ V; $T_j = 85$ °C

I_R	<	10 nA
	<	200 nA

Diode capacitance at $f = 1$ MHz

$V_R = 1$ V

$V_R = 3$ V

$V_R = 28$ V

C_d	>	31 pF
C_d	typ.	24 pF
C_d		2,4 to 3,0 pF

Capacitance ratio at $f = 1$ MHz

$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$	12 to 16
--	----------

Series resistance at $f = 100$ MHzand at that value of V_R atwhich $C_d = 30$ pF

r_s	typ.	0,9 Ω
	<	1,0 Ω

DOUBLE VARIABLE CAPACITANCE DIODE

The BBY62 is a double variable capacitance diode and mounted in a microminiature envelope (SOT-143).

The device is intended for application in electronic tuners using SMD technology.

QUICK REFERENCE DATA

For each diode:

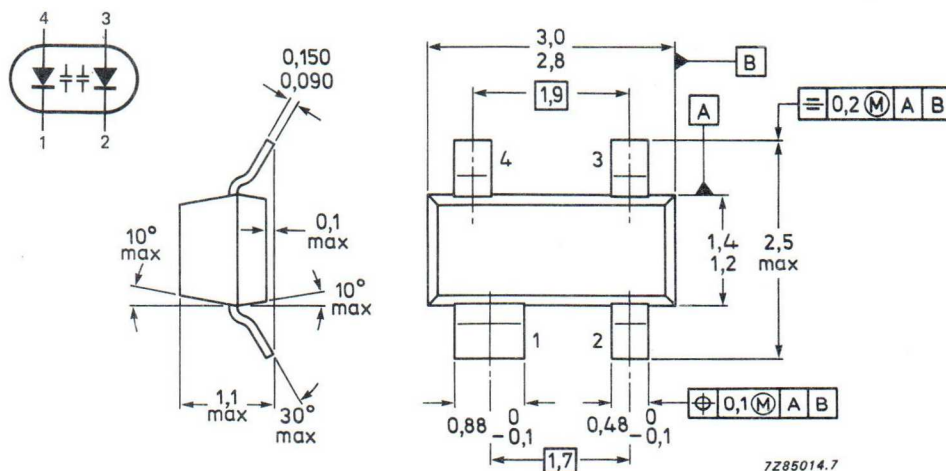
Continuous reverse voltage	V_R	max. 28 V
Reverse current $V_R = 28 \text{ V}$	I_R	< 50 nA
Diode capacitance at $f = 1 \text{ MHz}$ $V_R = 28 \text{ V}$	C_d	1,6 to 2,0 pF
Capacitance ratio at $f = 1 \text{ MHz}$	$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})}$	typ. 9,7
Series resistance at $f = 470 \text{ MHz}$ V_R is that value at which $C_d = 9 \text{ pF}$	r_s	< 1,2 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code: S4



TOP VIEW

RATINGS (for each diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		-65 to + 100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient and mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm

$$R_{thj-a} = 430 \text{ K/W}$$

CHARACTERISTICS (for each diode)

$T_j = 25 \text{ °C}$ unless otherwise specified

Reverse current

$$V_R = 28 \text{ V}$$

$$V_R = 28 \text{ V}; T_j = 85 \text{ °C}$$

$$I_R < 50 \text{ nA}$$

$$< 1 \text{ } \mu\text{A}$$

Diode capacitance at $f = 1 \text{ MHz}$

$$V_R = 1 \text{ V}$$

$$V_R = 28 \text{ V}$$

$$C_d \text{ typ. } 17,5 \text{ pF}$$

$$C_d \text{ } 1,6 \text{ to } 2,0 \text{ pF}$$

Capacitance ratio at $f = 1 \text{ MHz}$

$$\frac{C_d(V_R = 1 \text{ V})}{C_d(V_R = 28 \text{ V})} \text{ typ. } 9,7$$

Series resistance at $f = 470 \text{ MHz}$ and at that value of V_R at which $C_d = 9 \text{ pF}$

$$r_s < 1,2 \text{ } \Omega$$

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film hybrid circuits.

N-P-N complements are BC817; R and BC818; R respectively.

QUICK REFERENCE DATA

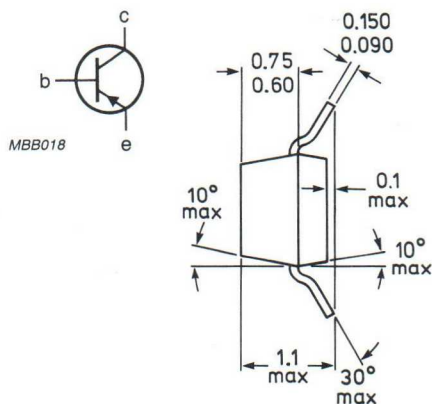
		BC807	BC808
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$ max.	50	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	45	25 V
Collector current (peak value)	$-I_{CM}$ max.	1000	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot} max.	250	mW
Junction temperature	T_j max.	150	$^\circ\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T typ.	100	MHz

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

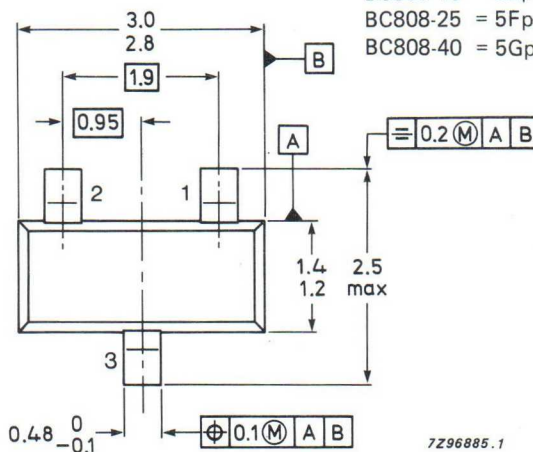
- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm

Marking code:

- BC807 = 5Dp
- BC807-16 = 5Ap
- BC807-25 = 5Bp
- BC807-40 = 5Cp
- BC808 = 5Hp
- BC808-16 = 5Ep
- BC808-25 = 5Fp
- BC808-40 = 5Gp



7296885.1

TOP VIEW

Reverse pinning types are available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BC807	BC808
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$ max.	50	30 V
Collector-emitter voltage (open base) $-I_C = 10 \text{ mA}$	$-V_{CEO}$ max.	45	25 V
Emitter-base voltage (open collector)	$-V_{EBO}$ max.	5	5 V
Collector current (DC)	$-I_C$ max.	500	mA
Collector current (peak value)	$-I_{CM}$ max.	1000	mA
Emitter current (peak value)	I_{EM} max.	1000	mA
Base current (DC)	$-I_B$ max.	100	mA
Base current (peak value)	$-I_{BM}$ max.	200	mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$ *	P_{tot} max.	250	mW
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction temperature	T_j max.	150	$^\circ\text{C}$

THERMAL RESISTANCE*

From junction to ambient	$R_{tj \text{ j-a}}$ =	500	K/W
--------------------------	------------------------	-----	-----

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

 $I_E = 0; -V_{CB} = 20\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$ $-I_{CBO}$ max. 100 nA $I_E = 0; -V_{CB} = 20\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $-I_{CBO}$ max. 5 μA

Emitter cut-off current

 $I_C = 0; V_{EB} = 5\text{ V}$ $-I_{EBO}$ max. 10 μA

Base emitter voltage *

 $-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$ $-V_{BE}$ max. 1,2 V

Saturation voltage

 $-I_C = 500\text{ mA}; -I_B = 50\text{ mA}$ $-V_{CEsat}$ max. 700 mV

D.C. current gain

 $-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$ h_{FE} min. 40 $-I_C = 100\text{ mA}; -V_{CE} = 1\text{ V}; \text{BC807; BC808}$ h_{FE} 100 to 600

BC807-16 |

BC808-16 |

 h_{FE} 100 to 250

BC807-25 |

BC808-25 |

 h_{FE} 160 to 400

BC807-40 |

BC808-40 |

 h_{FE} 250 to 600Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$ f_T typ. 100 MHzCollector capacitance at $f = 1\text{ MHz}$ $I_E = I_e = 0; -V_{CB} = 10\text{ V}$ C_C typ. 8 pF* $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

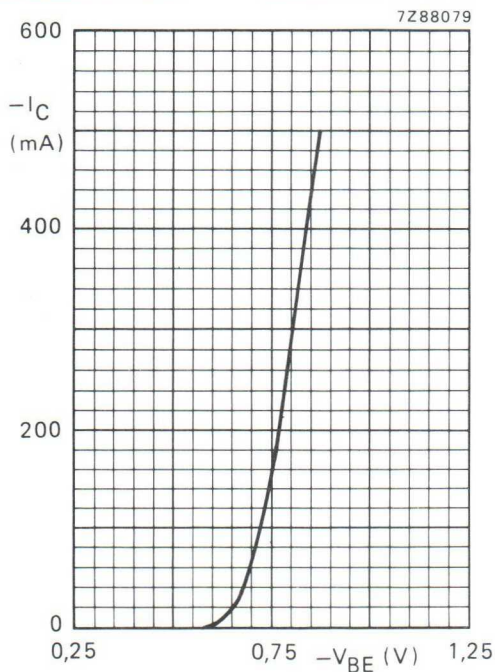


Fig. 2 $-V_{CE} = 1 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$.
Typical values.

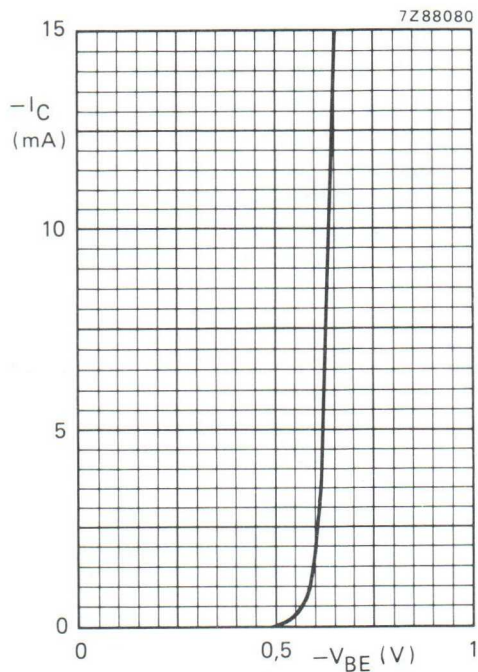


Fig. 3 $-V_{CE} = 5 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$.
Typical values.

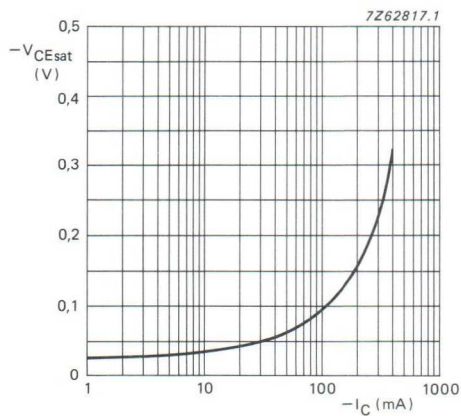


Fig. 4 typical values.

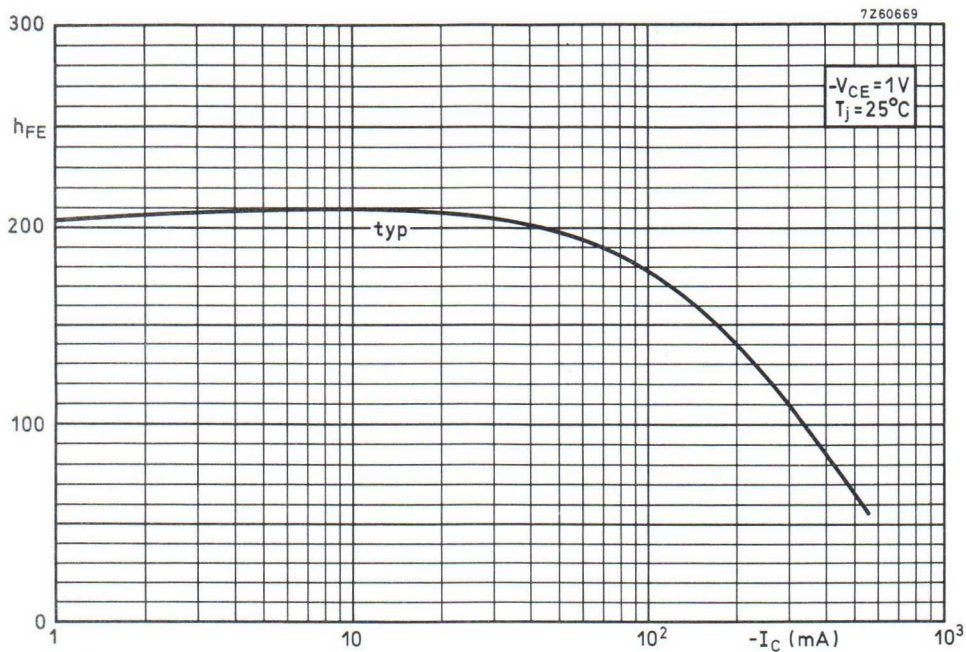


Fig. 5 D.C. current gain.

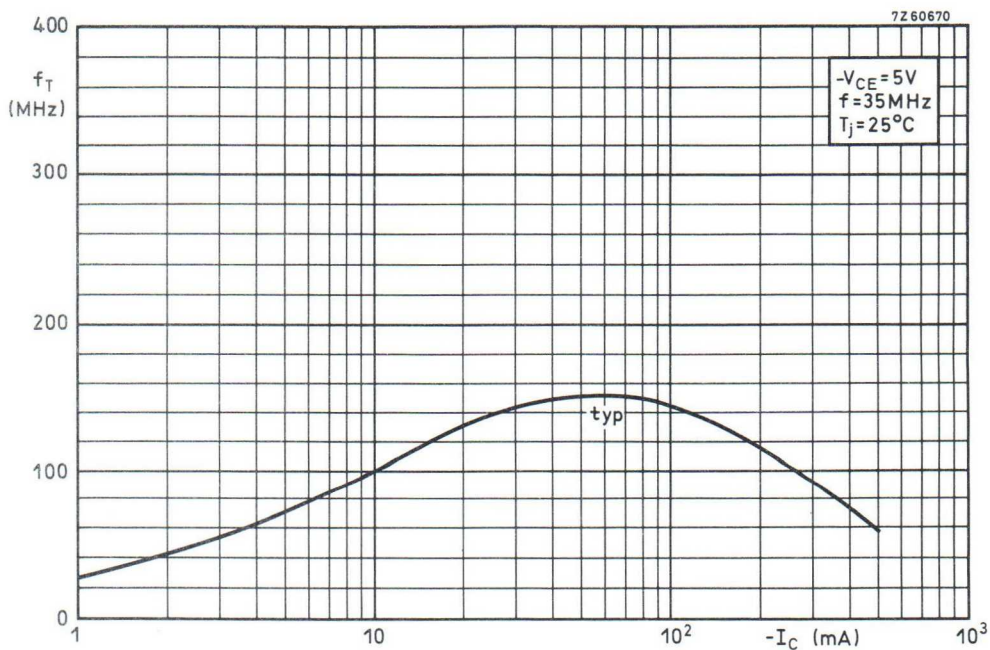


Fig. 6 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film hybrid circuits.

P-N-P complements are BC807; R and BC808; R respectively.

QUICK REFERENCE DATA

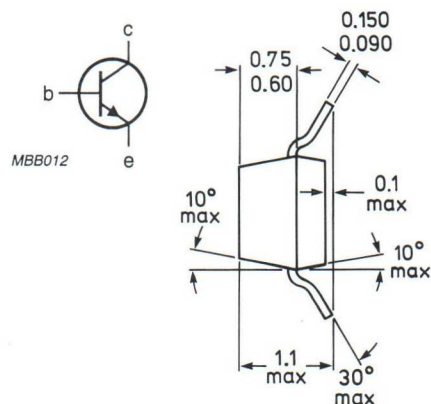
		BC817	BC818
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max. 50	30 V
Collector-emitter voltage (open base)	V_{CEO}	max. 45	25 V
Collector current (peak value)	I_{CM}	max. 1000	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max. 250	mW
Junction temperature	T_j	max. 150	$^{\circ}\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ. 200	MHz

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

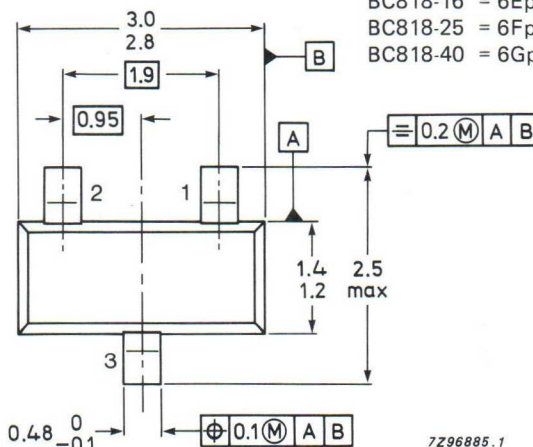
- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm

Marking code:

BC817 = 6Dp
 BC817-16 = 6Ap
 BC817-25 = 6Bp
 BC817-40 = 6Cp
 BC818 = 6Hp
 BC818-16 = 6Ep
 BC818-25 = 6Fp
 BC818-40 = 6Gp



TOP VIEW

Reverse pinning types are available on request.
 See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BC817	BC818
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max. 50	30 V
Collector-emitter voltage (open base) $I_C = 10$ mA	V_{CEO}	max. 45	25 V
Emitter-base voltage (open collector)	V_{EBO}	max. 5	5 V
Collector current (d.c.)	I_C	max. 500	mA
Collector current (peak value)	I_{CM}	max. 1000	mA
Emitter current (peak value)	$-I_{EM}$	max. 1000	mA
Base current (d.c.)	I_B	max. 100	mA
Base current (peak value)	I_{BM}	max. 200	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max. 250	mW
Storage temperature	T_{stg}	-65 to + 150	°C
Junction temperature	T_j	max. 150	°C

THERMAL RESISTANCE

From junction to ambient*

$$R_{th\ j-a} = 500\ K/W$$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

 $I_E = 0; V_{CB} = 20\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$ $I_{CBO} < 100\text{ nA}$ $I_E = 0; V_{CB} = 20\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $I_{CBO} < 5\text{ }\mu\text{A}$

Emitter cut-off current

 $I_C = 0; V_{EB} = 5\text{ V}$ $I_{EBO} < 10\text{ }\mu\text{A}$

Base emitter voltage *

 $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$ $V_{BE} < 1,2\text{ V}$

Saturation voltage

 $I_C = 500\text{ mA}; I_B = 50\text{ mA}$ $V_{CEsat} < 700\text{ mV}$

D.C. current gain

 $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$ $h_{FE} > 40$ $I_C = 100\text{ mA}; V_{CE} = 1\text{ V}; \text{BC817; BC818}$ $h_{FE} 100\text{ to }600$

BC817-16 }

BC818-16 }

 $h_{FE} 100\text{ to }250$

BC817-25 }

BC818-25 }

 $h_{FE} 160\text{ to }400$

BC817-40 }

BC818-40 }

 $h_{FE} 250\text{ to }600$ Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$ $f_T \text{ typ. } 200\text{ MHz}$ Collector capacitance at $f = 1\text{ MHz}$ $I_E = I_e = 0; V_{CB} = 10\text{ V}$ $C_c \text{ typ. } 5\text{ pF}$ * V_{BE} decreases by about 2 mV/K with increasing temperature.

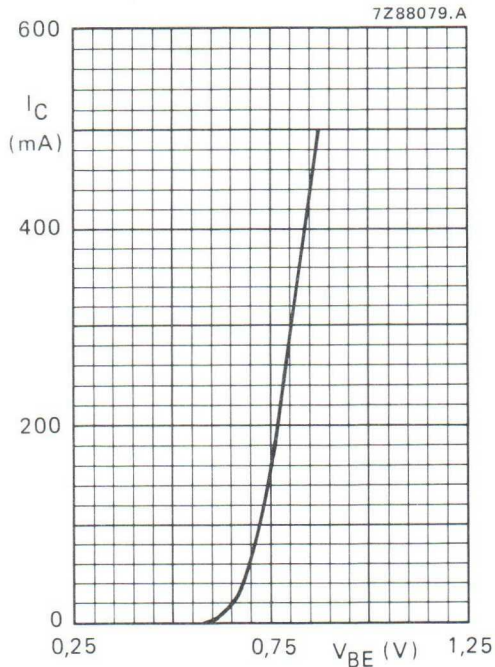


Fig. 2 $V_{CE} = 1$ V; $T_j = 25$ °C. Typical values.

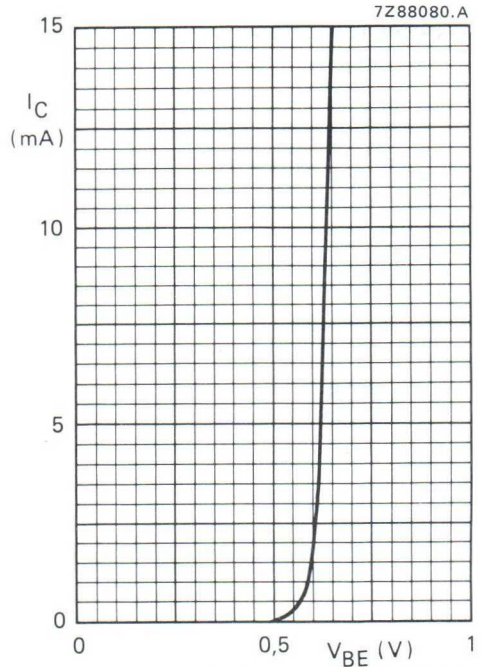


Fig. 3 $V_{CE} = 5$ V; $T_j = 25$ °C. Typical values.

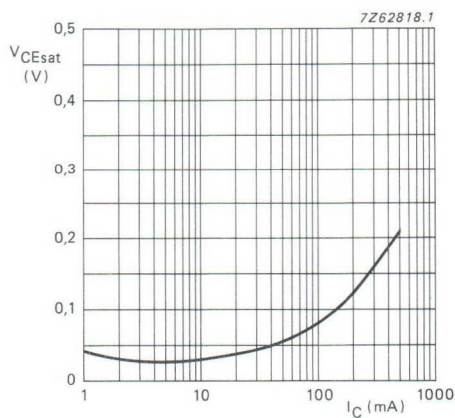


Fig. 4 $I_C/I_B = 10$; $T_j = 25$ °C.

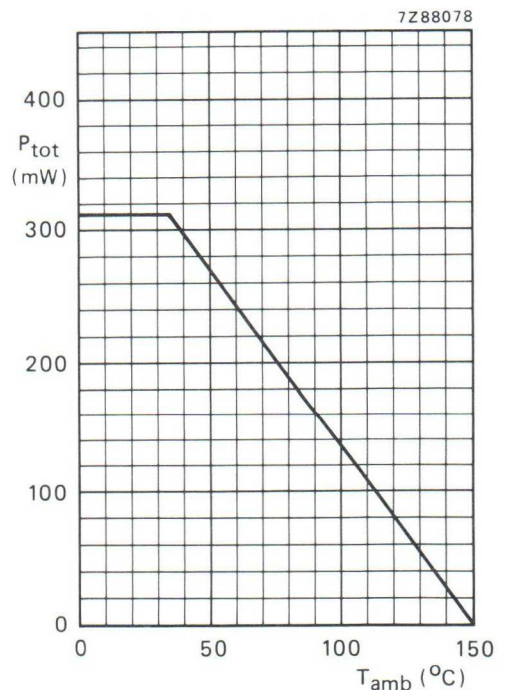


Fig. 5 Power derating curve.

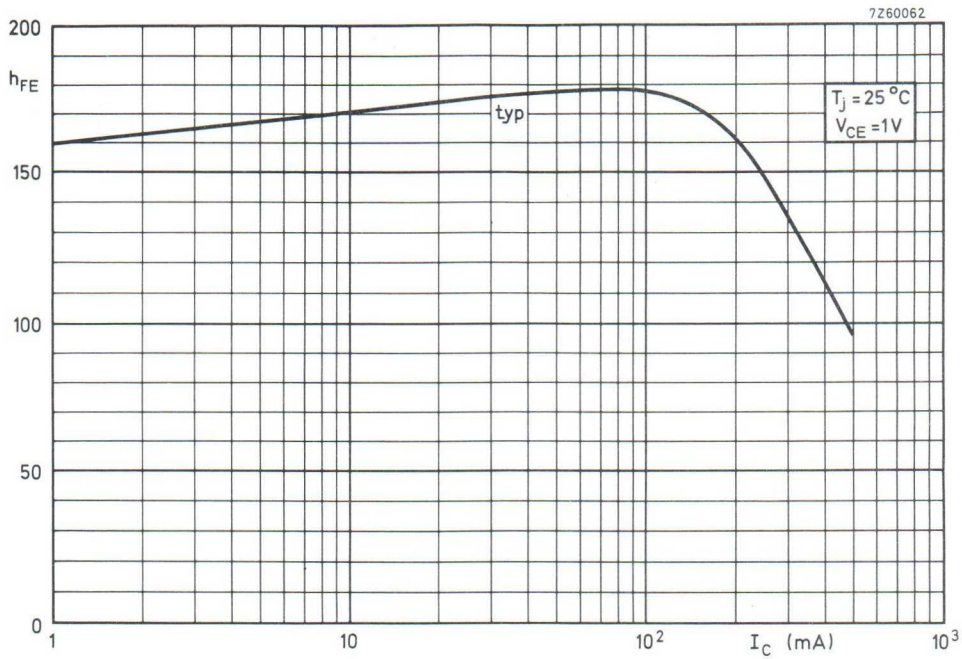


Fig. 6 D.C. current gain.

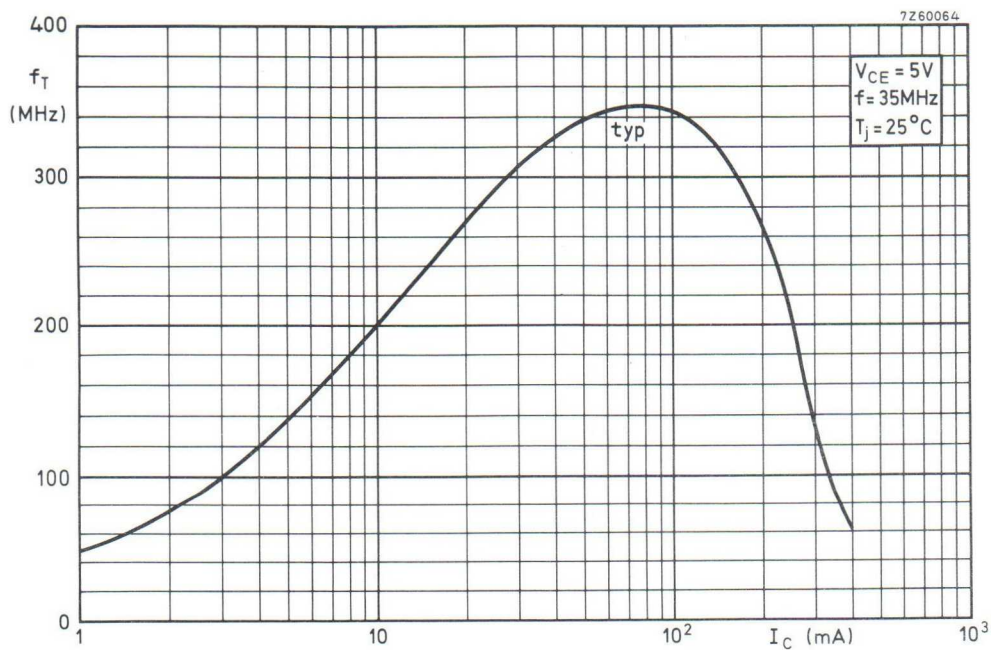


Fig. 7 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

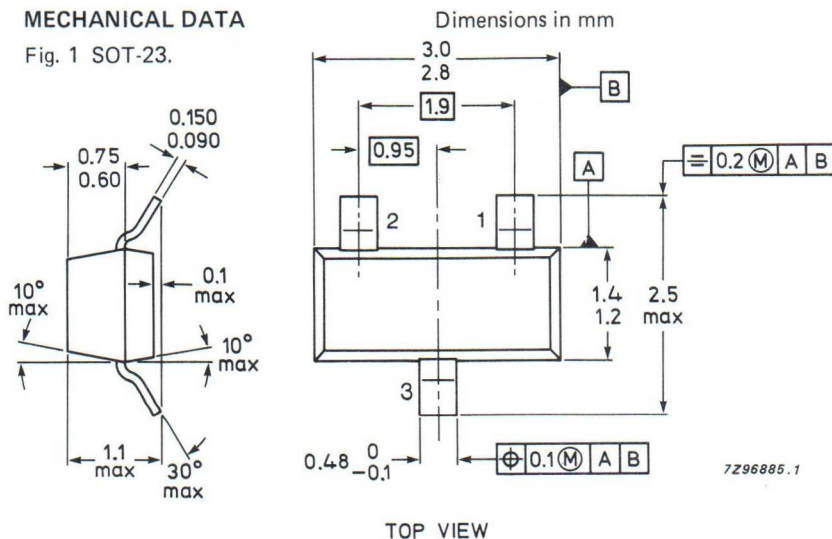
General purpose n-p-n transistors in a plastic SOT-23 variant, especially suitable for use in driver stages of audio amplifiers in thick and thin-film hybrid circuits.

QUICK REFERENCE DATA

			BC846	BC847	BC848	
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	80	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	65	45	30	V
Collector current (peak value)	I_{CM}	max.	200	200	200	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250	250	250	mW
Junction temperature	T_j	max.	150	150	150	$^\circ\text{C}$
Small-signal current gain						
$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; f = 1\text{ kHz}$	h_{fe}	$>$	125	125	125	
		$<$	500	900	900	
Transition frequency						
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	300	300	300	MHz
Noise figure at $R_S = 2\text{ k}\Omega$						
$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$						
$f = 1\text{ kHz}; B = 200\text{ Hz}$	F	typ.	2	2	2	dB

MECHANICAL DATA

Fig. 1 SOT-23.

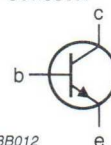


Marking code:

BC846	= 1Dp
BC846A	= 1Ap
BC846B	= 1Bp
BC847	= 1Hp
BC847A	= 1Ep
BC847B	= 1Fp
BC847C	= 1Gp
BC848	= 1Mp
BC848A	= 1Jp
BC848B	= 1Kp
BC848C	= 1Lp

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



Reverse pinning types are available on request.

See also *Soldering recommendations*.

MBB012

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC846	BC847	BC848	
Collector-base voltage (open emitter)	V_{CBO}	max.	80	50	30	V
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	80	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	65	45	30	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6	6	5	V
Collector current (d.c.)	I_C	max.	100			mA
Collector current (peak value)	I_{CM}	max.	200			mA
Emitter current (peak value)	$-I_{EM}$	max.	200			mA
Base current (peak value)	I_{BM}	max.	200			mA
Total power dissipation* up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250			mW
Storage temperature	T_{stg}		-65 to $+150$			$^{\circ}\text{C}$
Junction temperature	T_j	max.	150			$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th\ j-a} = 500\text{ K/W}$$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 30\text{ V}$

$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$

Base-emitter voltage*

$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$

$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$

Saturation voltage**

$I_C = 10\text{ mA}; I_B = 0,5\text{ mA}$

$I_C = 100\text{ mA}; I_B = 5\text{ mA}$

Collector capacitance at $f = 1\text{ MHz}$

$I_E = I_e = 0; V_{CB} = 10\text{ V}$

Transition frequency at $f = 35\text{ MHz}$

$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$

$I_{CBO} < 15\text{ nA}$

$I_{CBO} < 5\text{ }\mu\text{A}$

$V_{BE} \text{ typ. } 660\text{ mV}$
 $580\text{ to } 700\text{ mV}$

$V_{BE} < 770\text{ mV}$

$V_{CEsat} \text{ typ. } 90\text{ mV}$
 $< 250\text{ mV}$

$V_{BEsat} \text{ typ. } 700\text{ mV}$

$V_{CEsat} \text{ typ. } 200\text{ mV}$
 $< 600\text{ mV}$

$V_{BEsat} \text{ typ. } 900\text{ mV}$

$C_c \text{ typ. } 2,5\text{ pF}$

$f_T \text{ typ. } 300\text{ MHz}$

* V_{BE} decreases by about 2 mV/K with increasing temperature.** V_{BEsat} decreases by about $1,7\text{ mV/K}$ with increasing temperature.

Small signal current gain at $f = 1 \text{ kHz}$

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

		BC846	BC847	BC848
h_{fe}	$>$	125	125	125
	$<$	500	900	900

Noise figure at $R_S = 2 \text{ k}\Omega$

$I_C = 200 \mu\text{A}; V_{CE} = 5 \text{ V};$
 $f = 1 \text{ kHz}; B = 200 \text{ Hz}$

F	typ.	2	2	2	dB
	$<$	10	10	10	dB

BC846A	BC846B	
BC847A	BC847B	BC847C
BC848A	BC848B	BC848C

D.C. current gain

$I_C = 10 \mu\text{A}; V_{CE} = 5 \text{ V}$

h_{FE}	typ.	90	150	270
----------	------	----	-----	-----

$>$	110	200	420
-----	-----	-----	-----

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

h_{FE}	typ.	180	290	520
	$<$	220	450	800

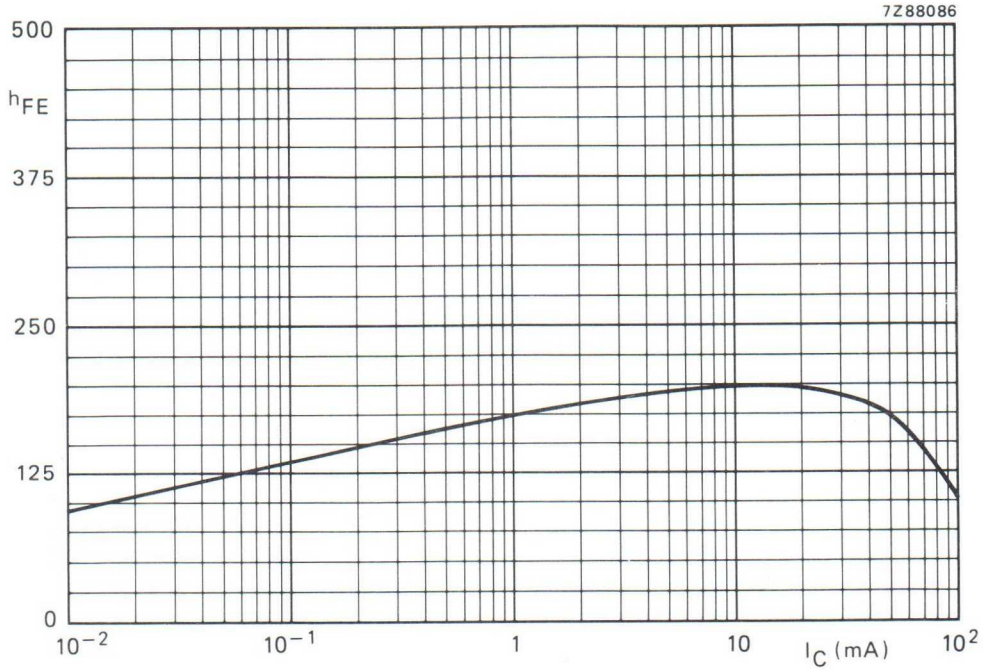


Fig. 3 Typical D.C. current gain for A-selections. $V_{CE} = 5$ V; $T_j = 25$ °C.

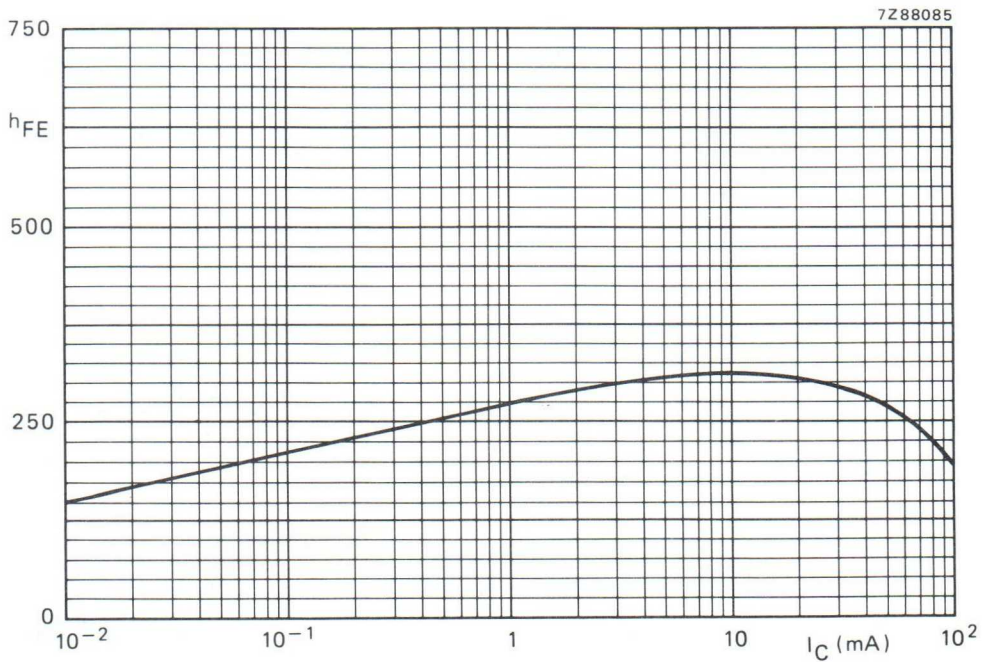


Fig. 4 Typical D.C. current gain for B-selections. $V_{CE} = 5$ V; $T_j = 25$ °C.

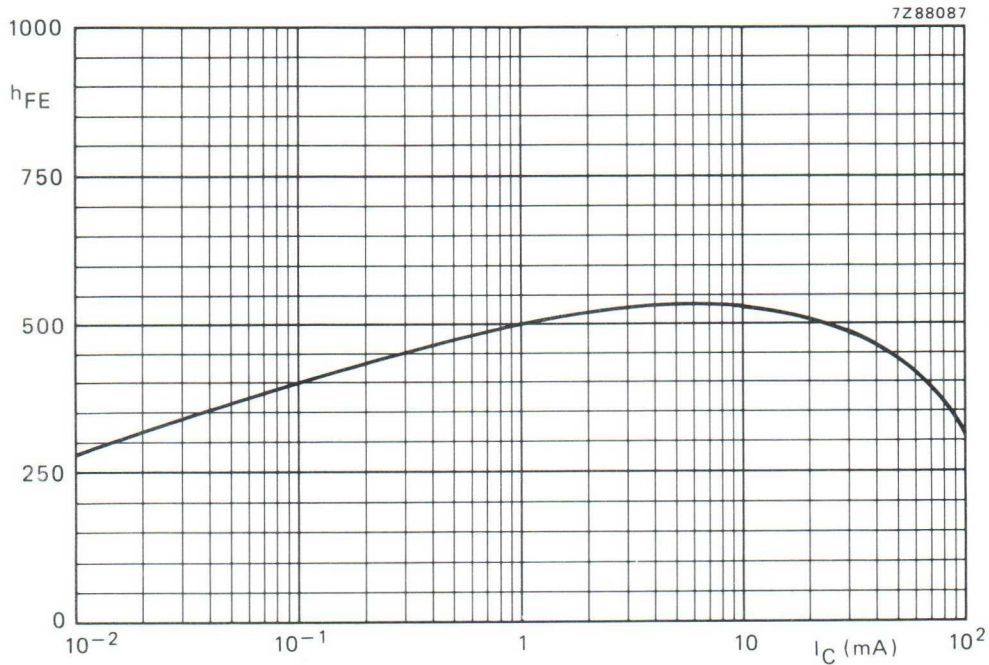


Fig. 5 Typical D.C. current gain for C-selections. $V_{CE} = 5$ V; $T_j = 25^\circ\text{C}$.

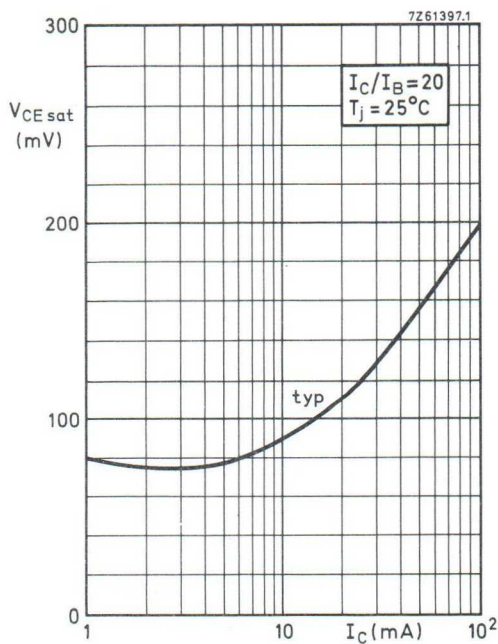


Fig. 6 Typical values.

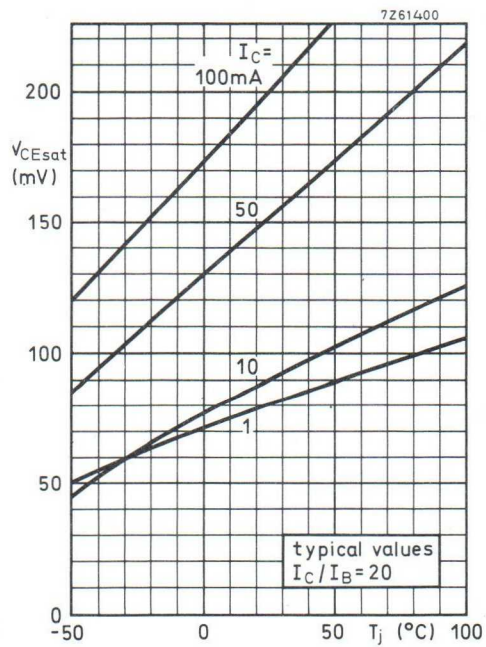


Fig. 7 Typical values.

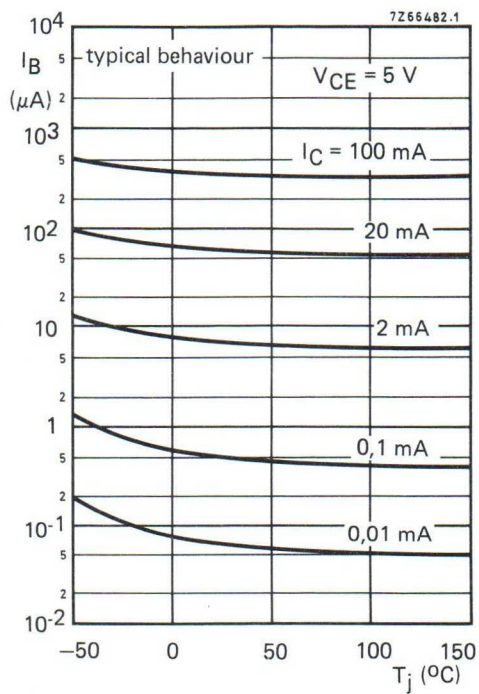


Fig. 8 Typical behaviour of base current versus junction temperature.

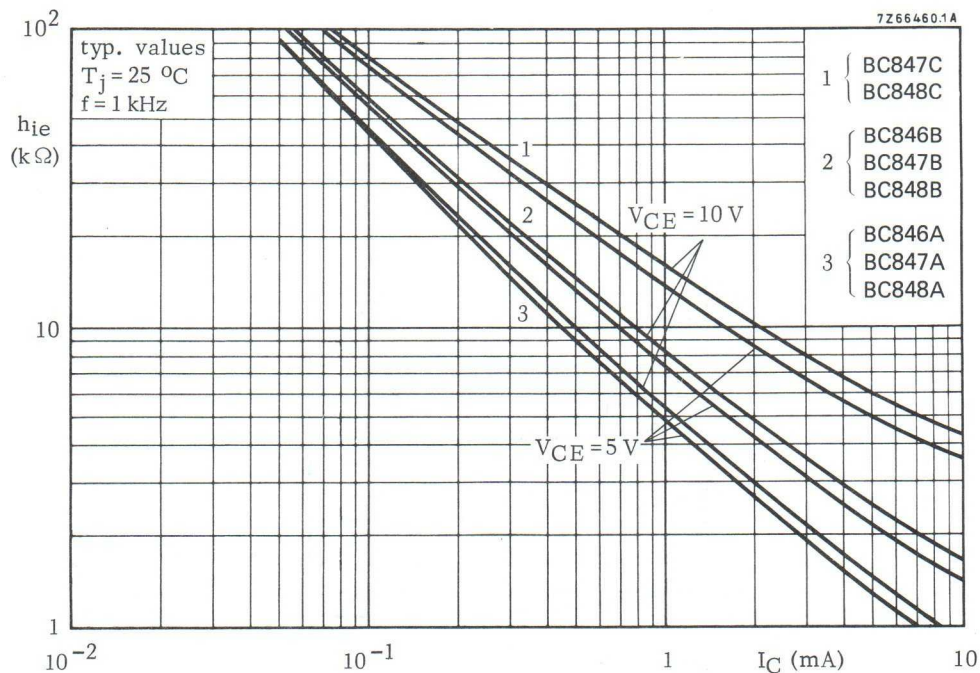


Fig. 9 Input impedance. 1 = C selections; 2 = B selections; 3 = A selections.

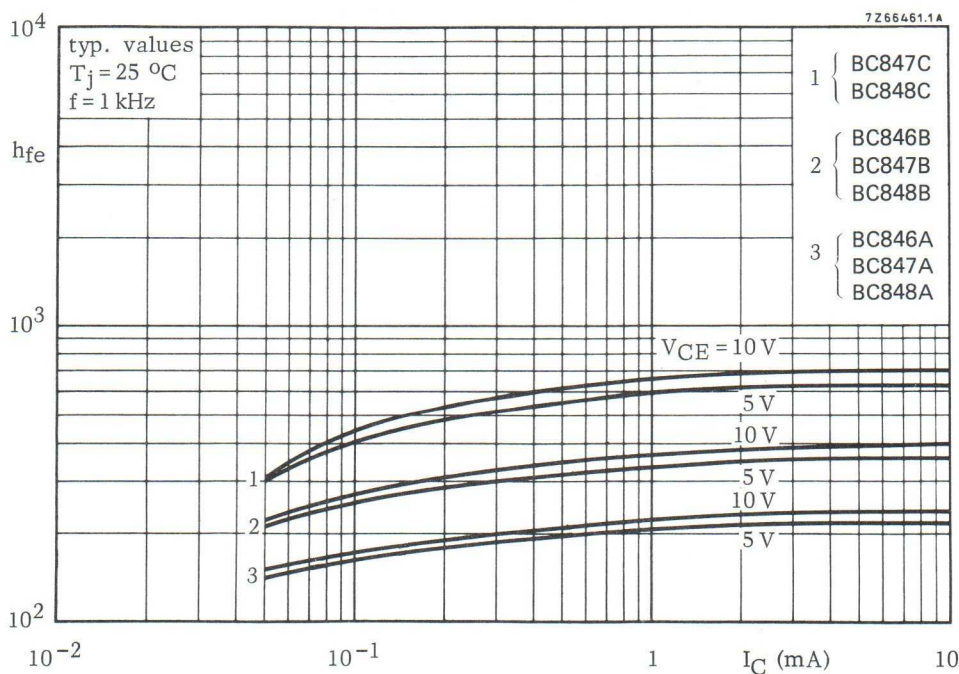


Fig. 10 Small signal current gain. 1 = C-; 2 = B- and 3 = A-selections.

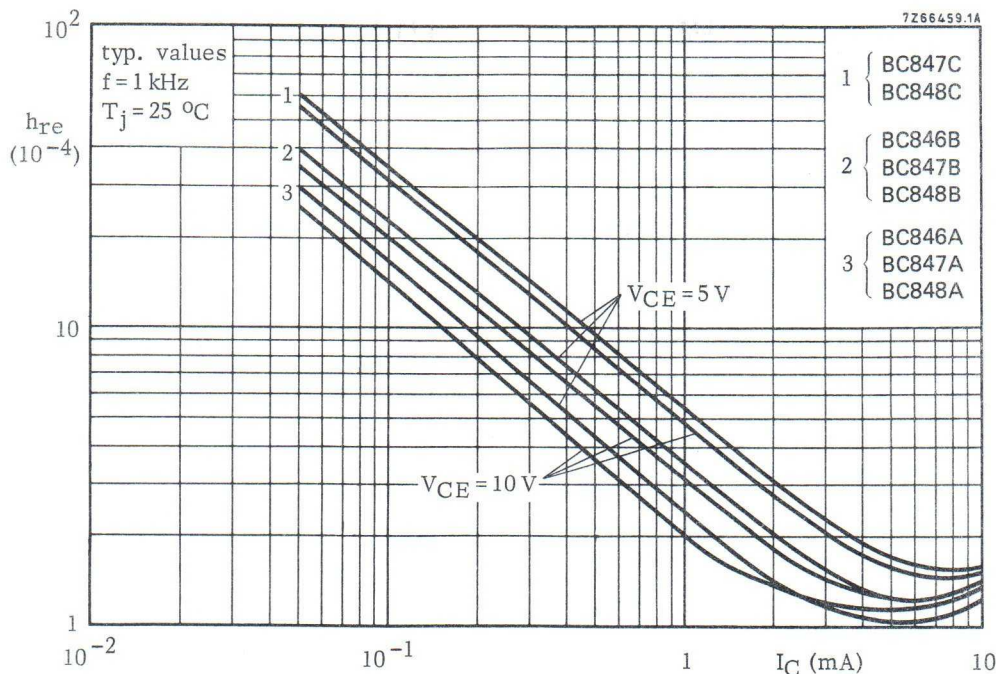


Fig. 11 Reverse voltage transfer ratio. 1 = C-; 2 = B- and 3 = A-selections.

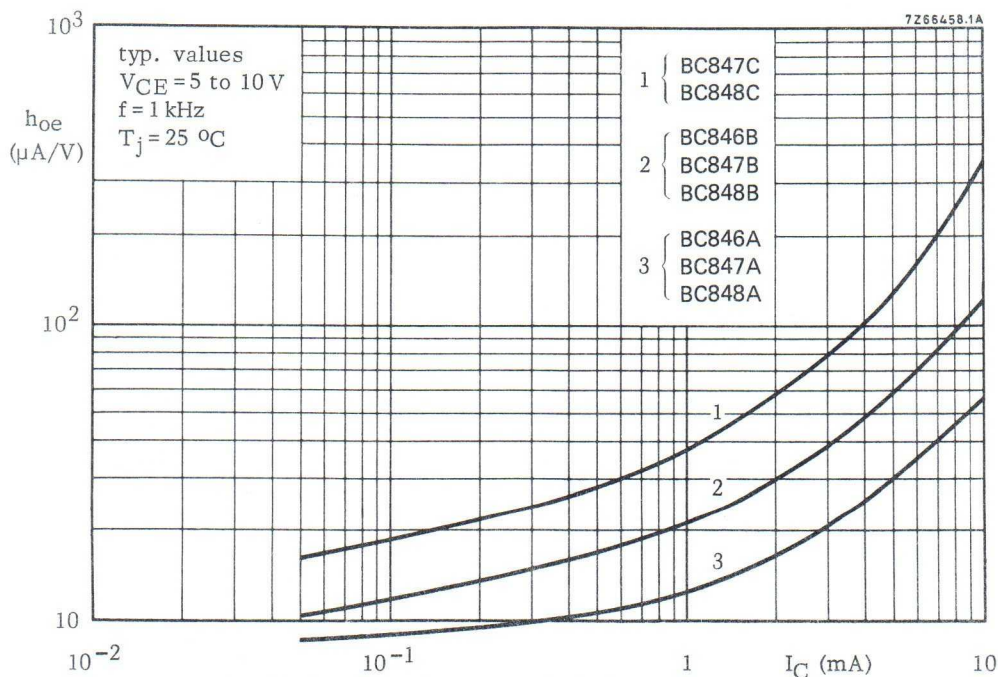


Fig. 12 Output admittance. 1 = C-; 2 = B- and 3 = A-selections.

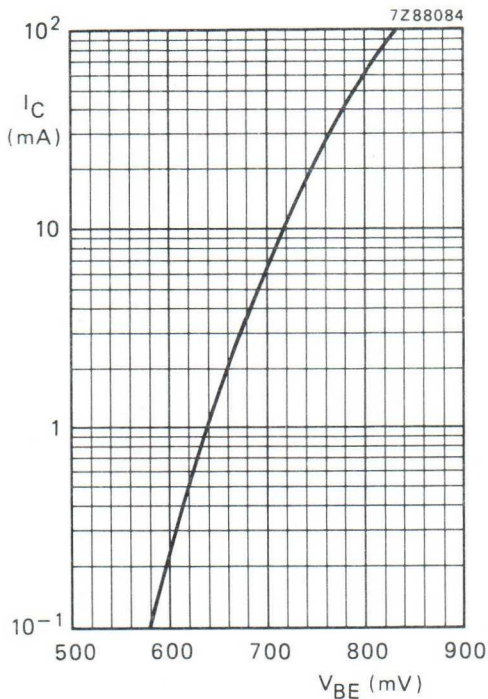


Fig. 13 Typical values at $V_{CE} = 5\text{ V}$; $T_j = 25^\circ\text{C}$.

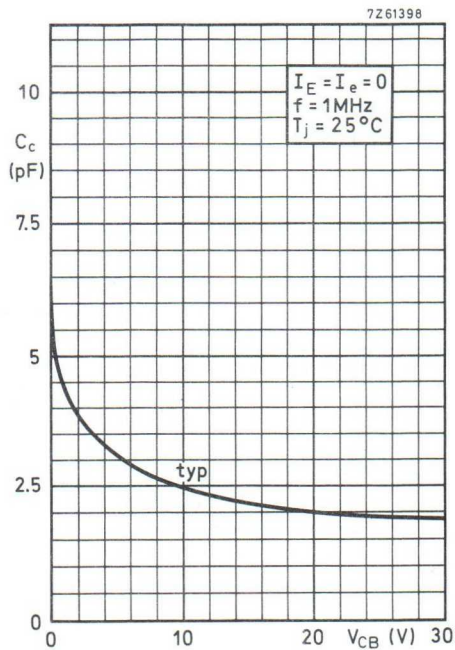


Fig. 14 Typical values.

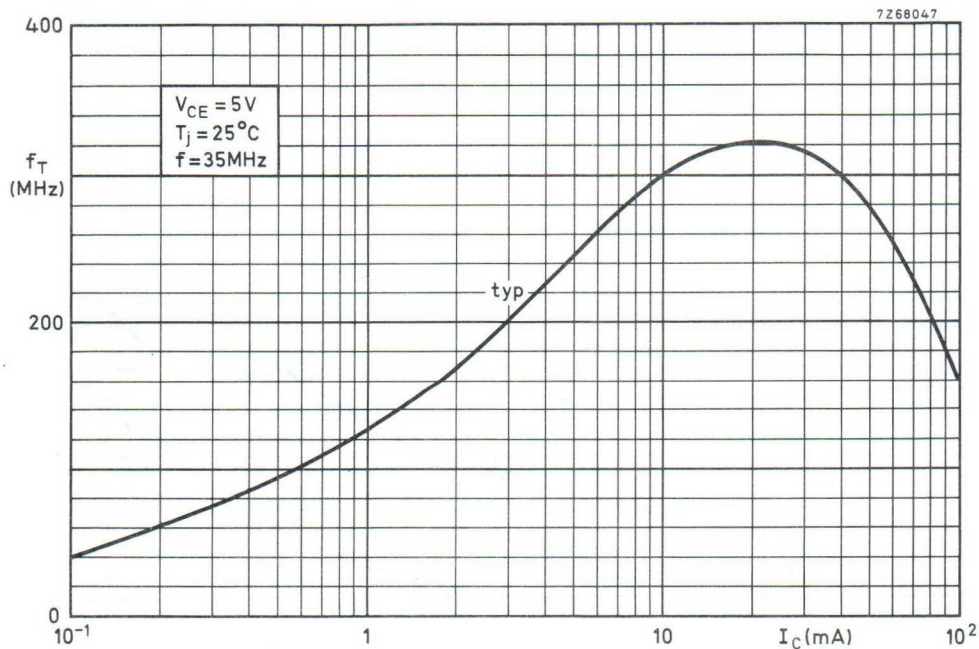


Fig. 15 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

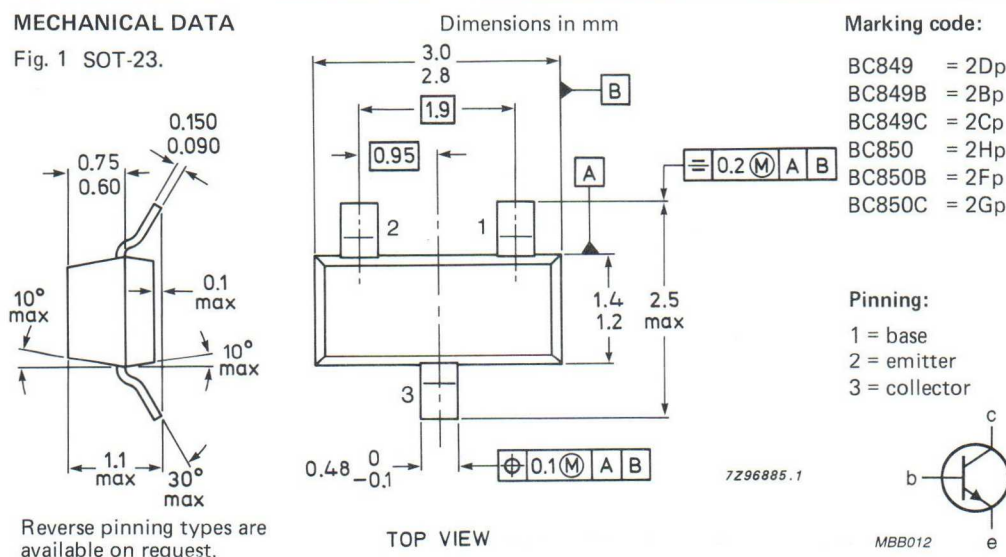
N-P-N transistors in a plastic SOT-23 envelope, primarily intended for low-noise input stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment in thick and thin-film hybrid circuits.

QUICK REFERENCE DATA

			BC849	BC850	
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	30	50	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	45	V
Collector current (peak value)	I_{CM}	max.	200	200	mA
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	P_{tot}	max.	250	250	mW
Junction temperature	T_j	max.	150	150	$^{\circ}\text{C}$
Small-signal current gain	h_{fe}	$>$	240	240	
$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; f = 1\text{ kHz}$		$<$	900	900	
Transition frequency	f_T	typ.	300	300	MHz
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$					
Noise figure at $R_S = 2\text{ k}\Omega$	F	typ.	1,4	1,4	dB
$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$		$<$	4	3	dB
$f = 30\text{ Hz to } 15\text{ kHz}$					
$f = 1\text{ kHz}; B = 200\text{ Hz}$	F	typ.	1,2	1	dB
$f = 10\text{ Hz to } 50\text{ Hz}$ (equivalent noise voltage)	V_n	$<$	—	0,135	μV

MECHANICAL DATA

Fig. 1 SOT-23.



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC849	BC850	
Collector-base voltage (open emitter)	V_{CBO}	max.	30	50	V
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	30	50	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	45	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	V
Collector current (d.c.)	I_C	max.	100		mA
Collector current (peak value)	I_{CM}	max.	200		mA
Emitter current (peak value)	$-I_{EM}$	max.	200		mA
Base current (peak value)	I_{BM}	max.	200		mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250		mW
Storage temperature	T_{stg}		-65 to + 150		$^{\circ}\text{C}$
Junction temperature	T_j	max.	150		$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$R_{th\ j-a} = 500\text{ K/W}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 30\text{ V}$

$I_{CBO} < 15\text{ nA}$

$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$

$I_{CBO} < 5\text{ }\mu\text{A}$

Base emitter voltage*

$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$

$V_{BE} \text{ typ. } 660\text{ mV}$
 $580\text{ to } 700\text{ mV}$

$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$

$V_{BE} < 770\text{ mV}$

Saturation voltages**

$I_C = 10\text{ mA}; I_B = 0,5\text{ mA}$

$V_{CEsat} \text{ typ. } 90\text{ mV}$
 $< 250\text{ mV}$

$V_{BEsat} \text{ typ. } 700\text{ mV}$

$V_{CEsat} \text{ typ. } 200\text{ mV}$

$< 600\text{ mV}$

$V_{BEsat} \text{ typ. } 900\text{ mV}$

$I_C = 100\text{ mA}; I_B = 5\text{ mA}$

$C_c \text{ typ. } 2,5\text{ pF}$

Collector capacitance at $f = 1\text{ MHz}$

$I_E = I_e = 0; V_{CB} = 10\text{ V}$

Transition frequency at $f = 35\text{ MHz}$

$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$

$f_T \text{ typ. } 300\text{ MHz}$

* V_{BE} decreases by about 2 mV/K with increasing temperature.** V_{BEsat} decreases by about $1,7\text{ mV/K}$ with increasing temperature.

BC849
BC850

Small signal current gain at $f = 1 \text{ kHz}$

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

Noise figure at $R_S = 2 \text{ k}\Omega$

$I_C = 200 \text{ }\mu\text{A}; V_{CE} = 5 \text{ V}$

$f = 30 \text{ Hz to } 15 \text{ kHz}$

$f = 1 \text{ kHz}; B = 200 \text{ Hz}$

Equivalent noise voltage at $R_S = 2 \text{ k}\Omega$

$I_C = 200 \text{ }\mu\text{A}; V_{CE} = 5 \text{ V}$

$f = 10 \text{ Hz to } 50 \text{ Hz}; T_{\text{amb}} = 25 \text{ }^\circ\text{C}$

D.C. current gain

$I_C = 10 \text{ }\mu\text{A}; V_{CE} = 5 \text{ V}$

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

		BC849	BC850		
h_{fe}	$>$	240	240		
	$<$	900	900		
F	typ.	1,4	1,4		dB
	$<$	4	3		dB
F	typ.	1,2	1		dB
	$<$	4	4		dB
V_N	max.	—	0,135		μV
		BC849B	BC849C		
		BC850B	BC850C		
h_{FE}	typ.	150	270		
	$>$	200	420		
h_{FE}	typ.	290	520		
	$<$	450	800		

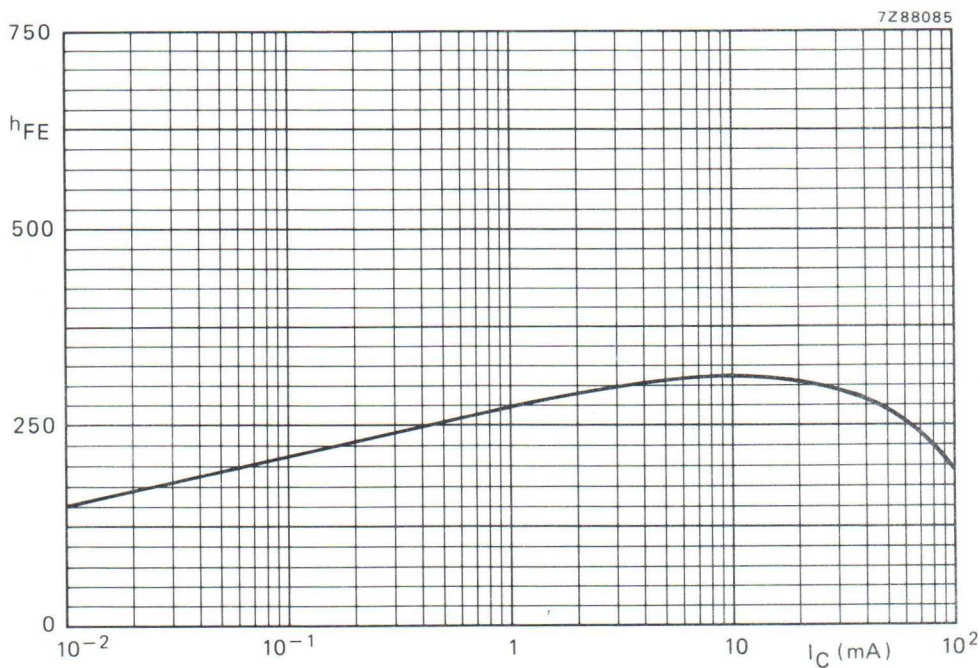


Fig. 3 Typical D.C. current gain B selections. $V_{CE} = 5$ V; $T_j = 25$ °C.

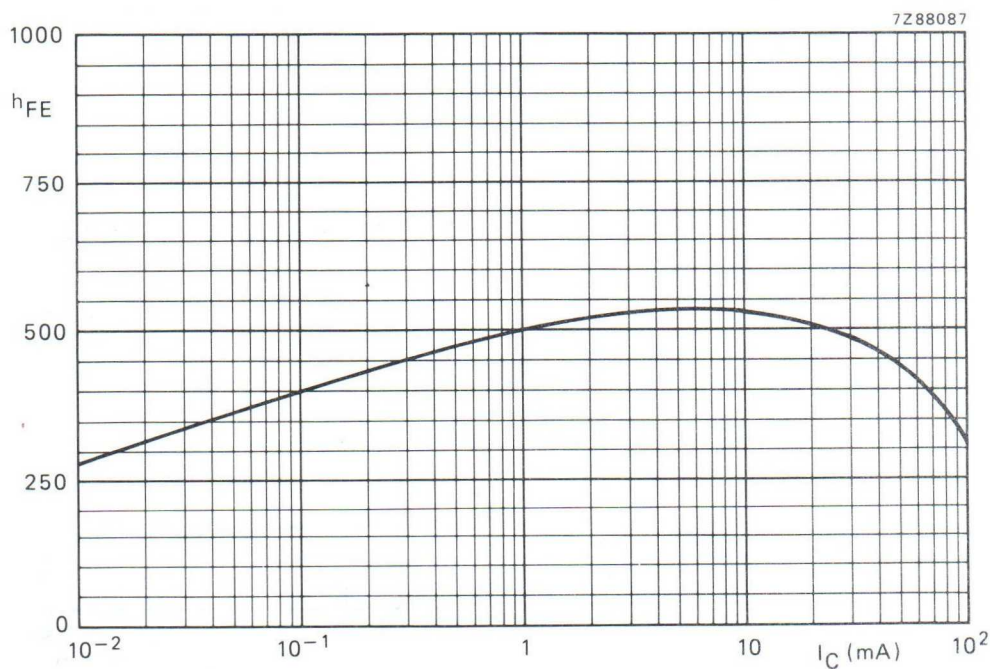


Fig. 4 Typical D.C. current gain C selections. $V_{CE} = 5$ V; $T_j = 25$ °C.

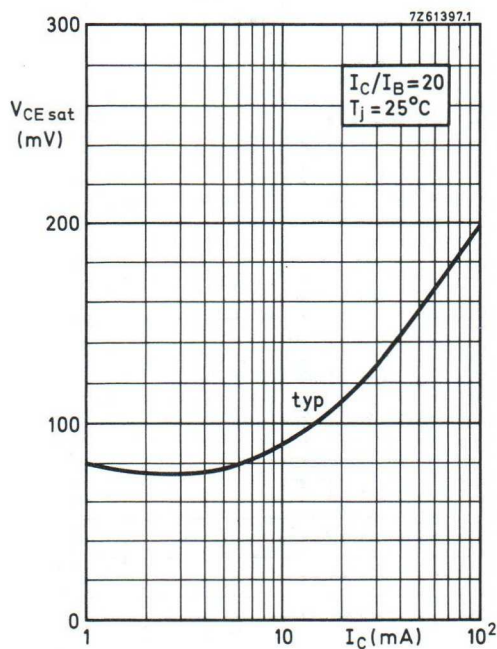


Fig. 5 Typical values.

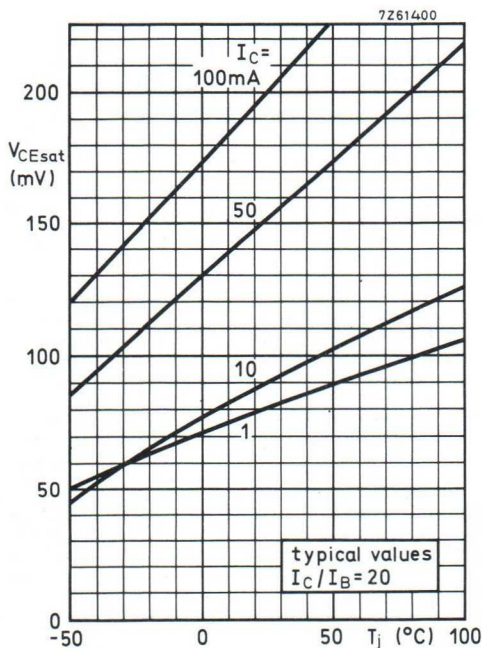


Fig. 6 Typical values; $I_C/I_B = 20$.

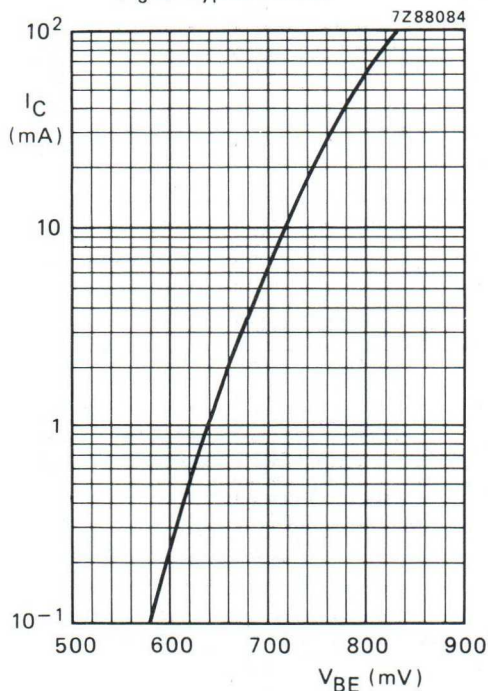


Fig. 7 Typical values V_{BE} . $V_{CE} = 5 V$; $T_j = 25^\circ C$.

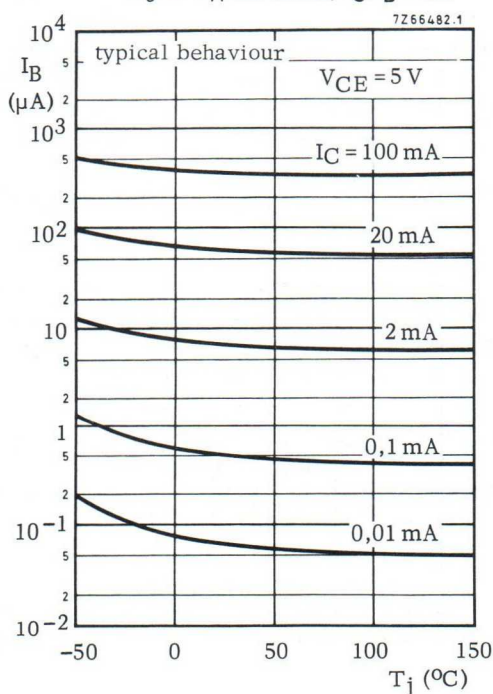


Fig. 8 Typical values.

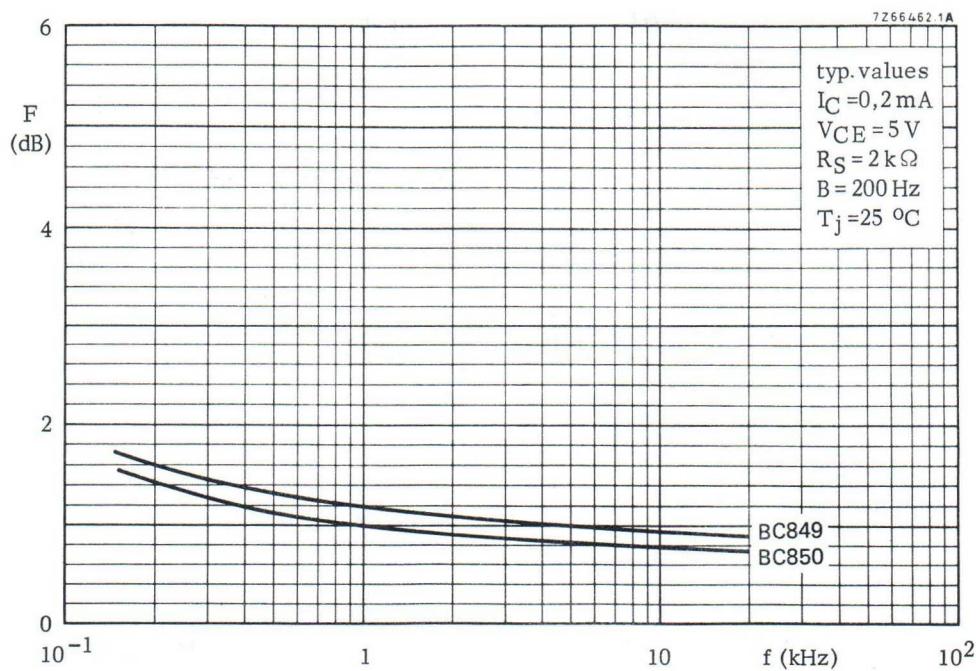


Fig. 9.

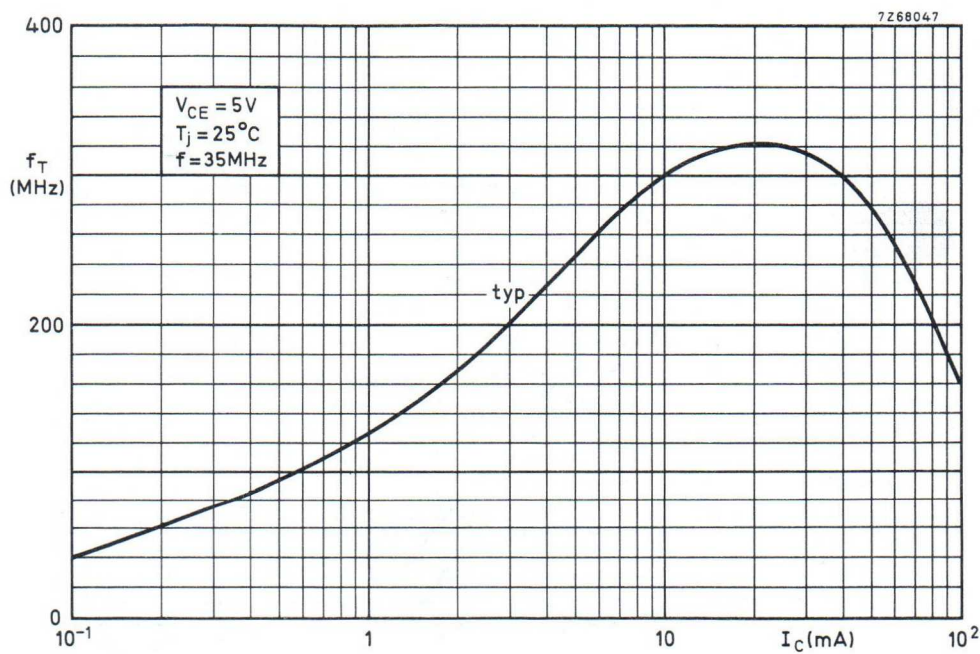


Fig. 10.

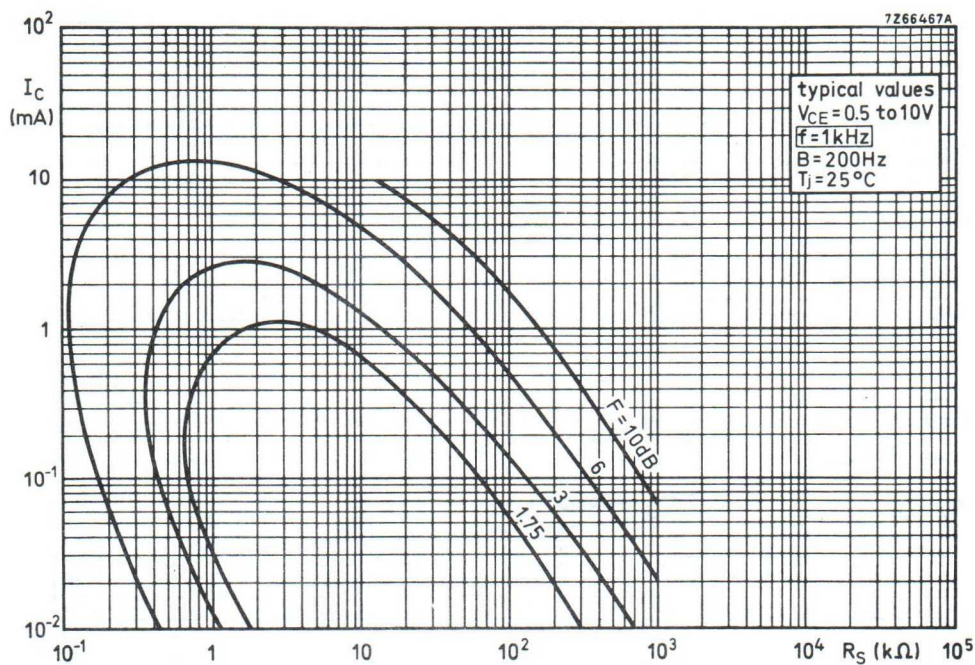


Fig. 11 Curves of constant noise figure for BC849.

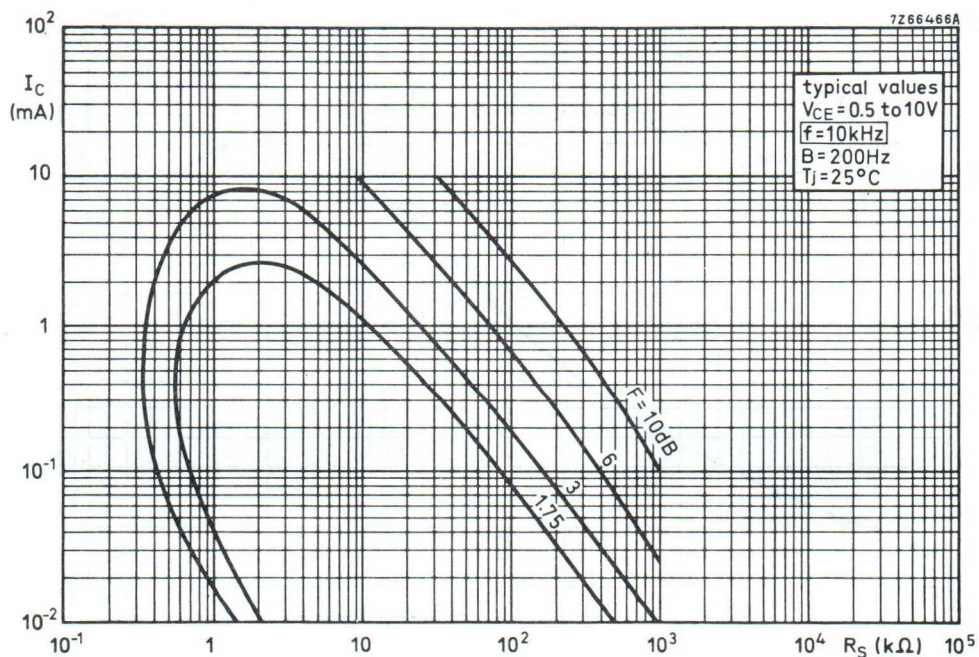


Fig. 12 Curves of constant noise figure for BC849.

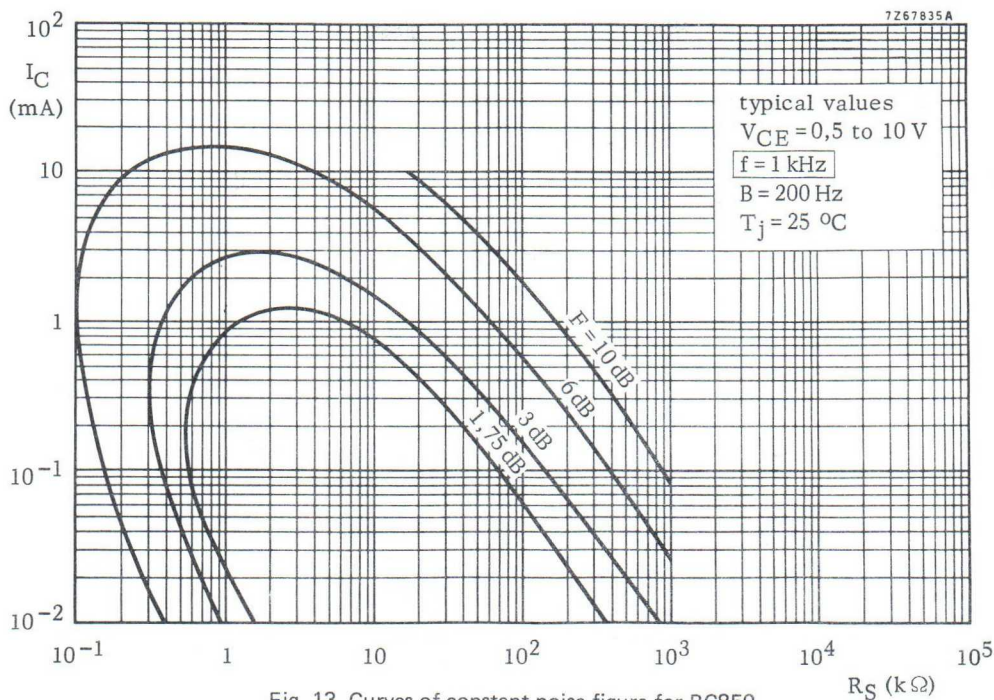


Fig. 13 Curves of constant noise figure for BC850.

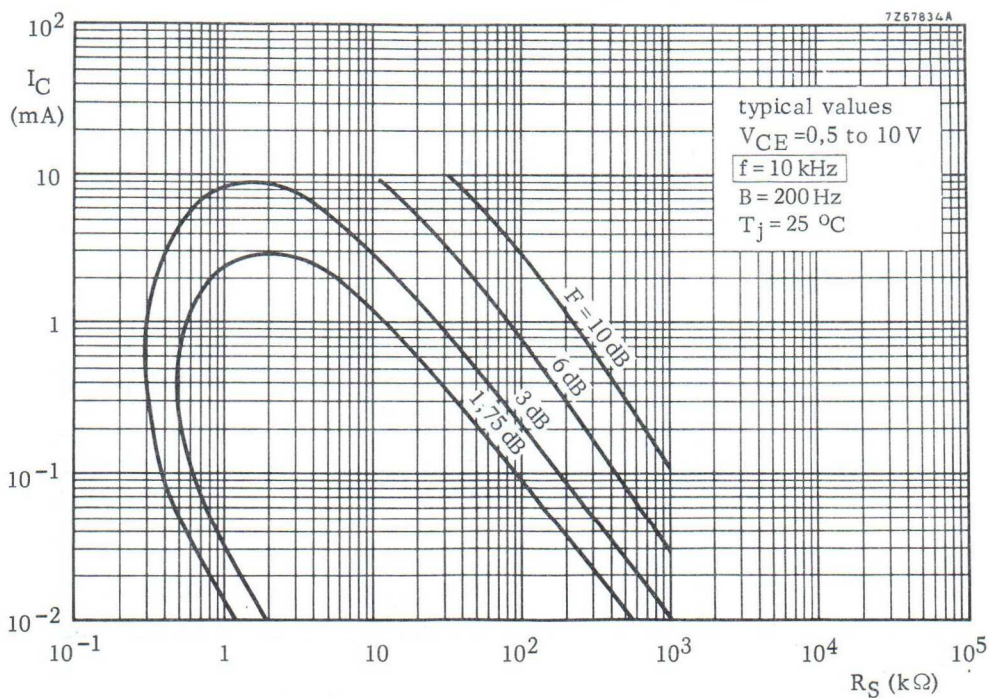


Fig. 14 Curves of constant noise figure for BC850.

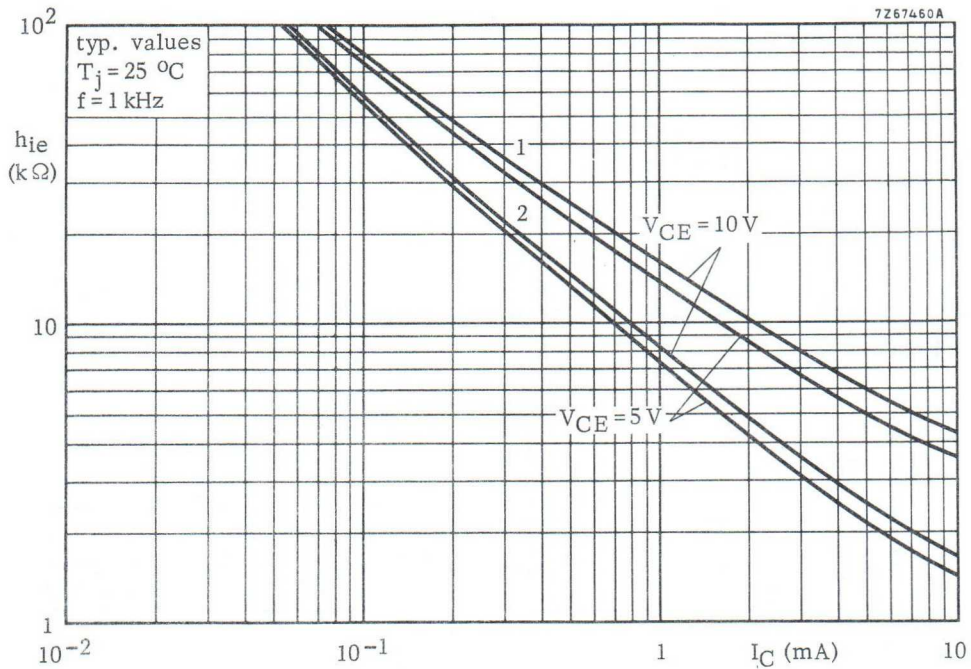


Fig. 15 Typical values. 1 = C selections; 2 = B selections.

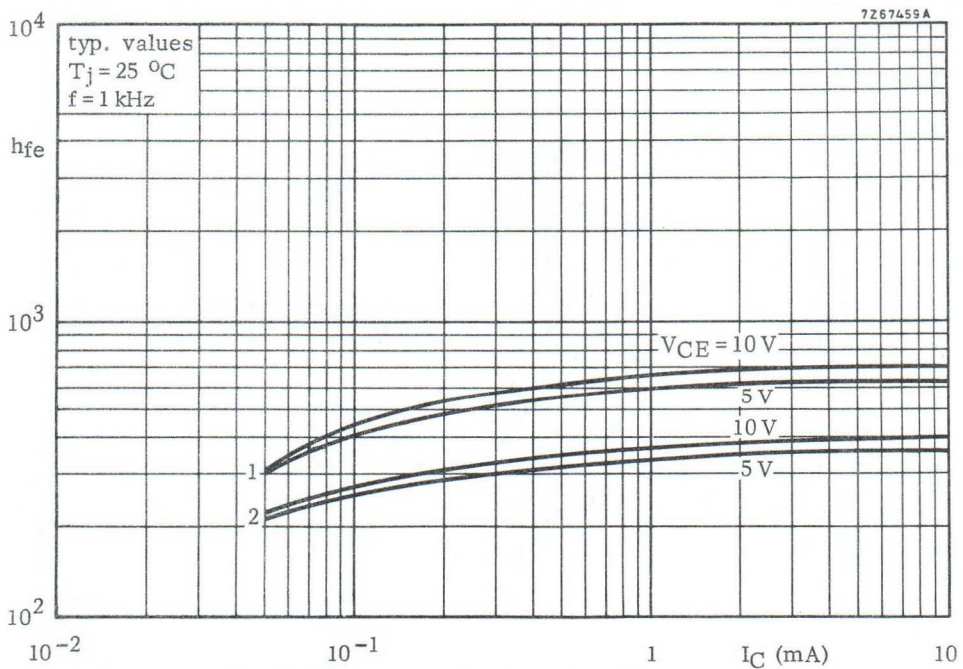


Fig. 16 Typical values. 1 = C selections; 2 = B selections.

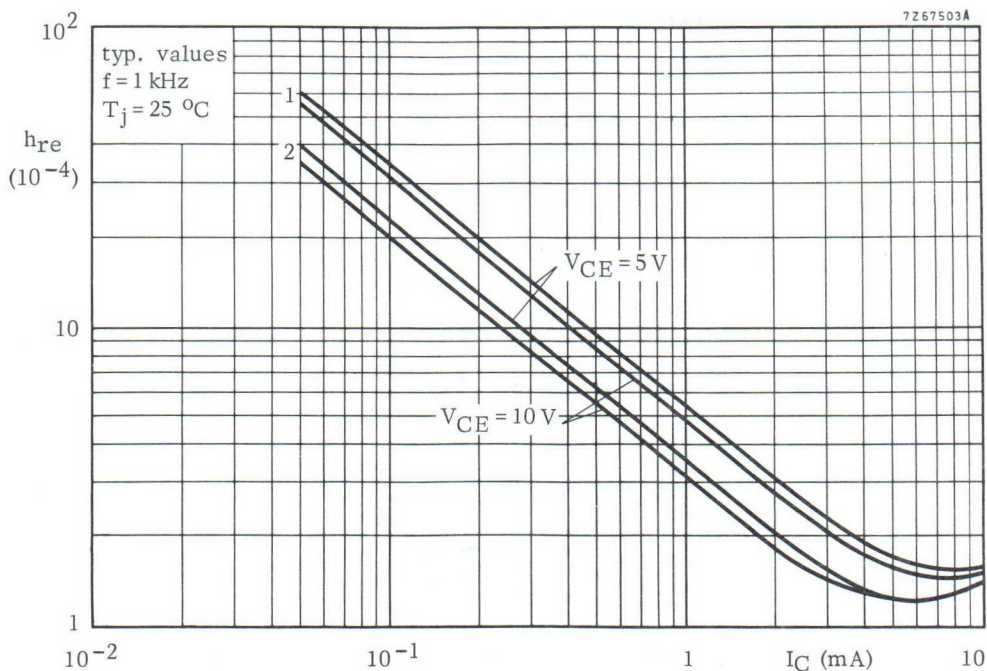


Fig. 17 Typical values. 1 = C selections; 2 = B selections.

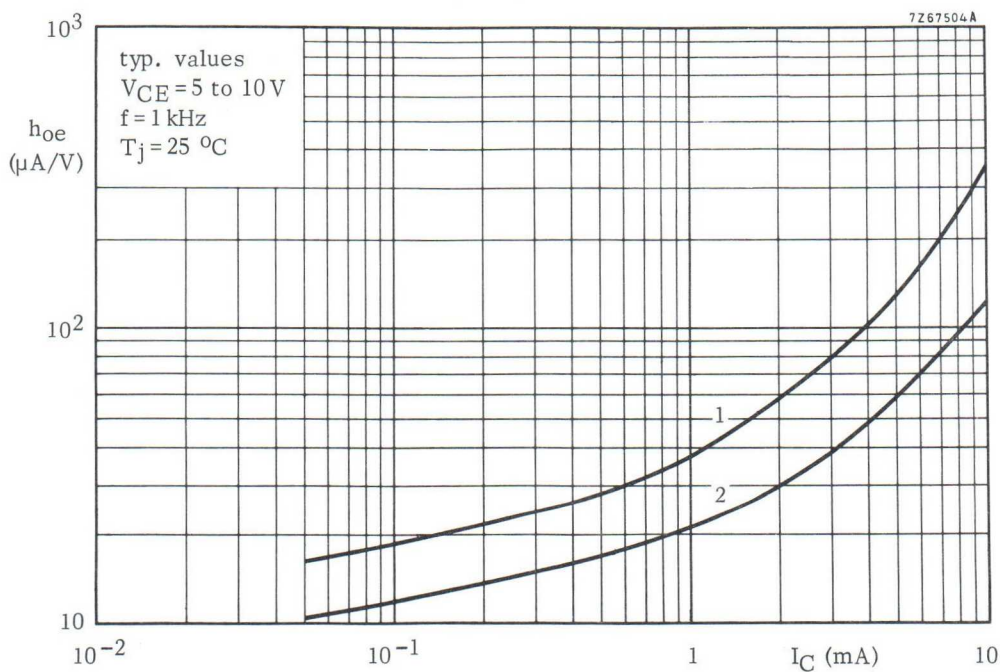


Fig. 18 Typical values. 1 = C selections; 2 = B selections.

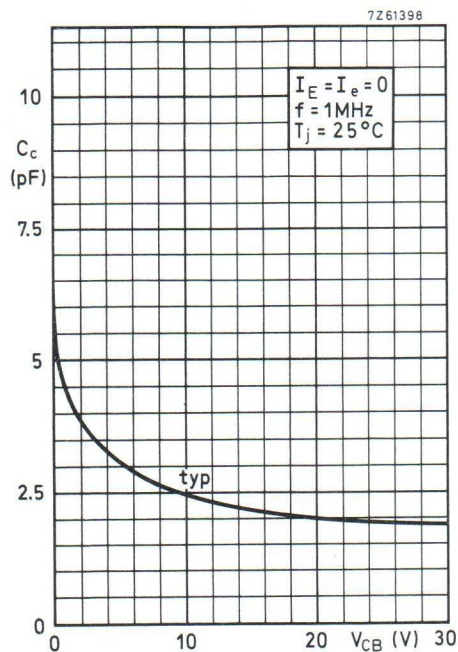


Fig. 19 Typical values.

SILICON PLANAR EPITAXIAL TRANSISTORS

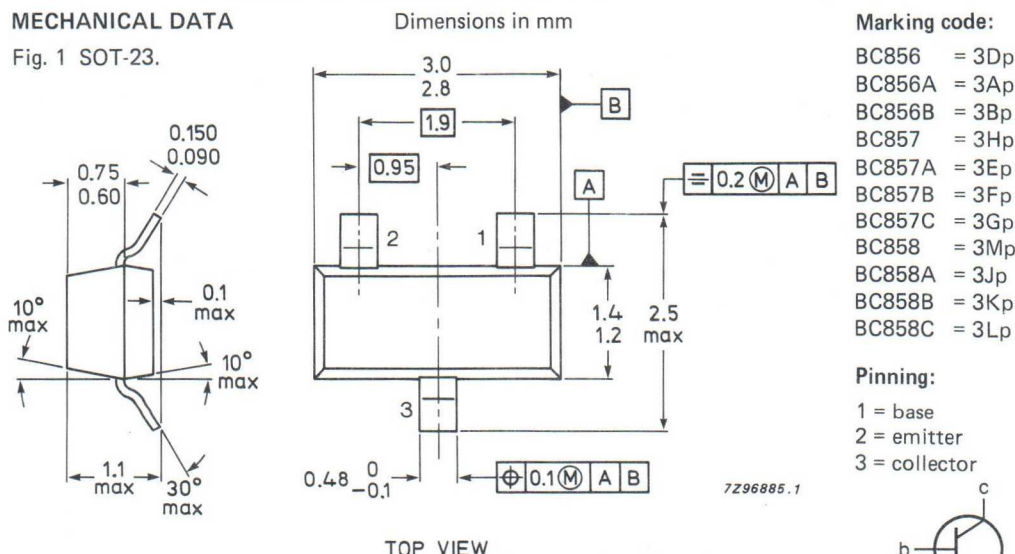
P-N-P transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film circuits.

QUICK REFERENCE DATA

		BC856	BC857	BC858
Collector-emitter voltage (+ $V_{BE} = 1\text{ V}$)	$-V_{CEX}$	max. 80	50	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max. 65	45	30 V
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to $T_{amb} = 60\text{ °C}$	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	150	°C
Small-signal current gain $-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}; f = 1\text{ kHz}$	h_{fe}		75 to 900	
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T	typ.	150	MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V}$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	F	<	10	dB

MECHANICAL DATA

Fig. 1 SOT-23.



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC856	BC857	BC858
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80	50	30 V
Collector-emitter voltage (+ $V_{BE} = 1$ V)	$-V_{CEX}$	max.	80	50	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	65	45	30 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5 V
Collector current (d.c.)	$-I_C$	max.		100	mA
Collector current (peak value)	$-I_{CM}$	max.		200	mA
Emitter current (peak value)	I_{EM}	max.		200	mA
Base current (peak value)	$-I_{BM}$	max.		200	mA
Total power dissipation ** up to $T_{amb} = 60$ °C	P_{tot}	max.		250	mW
Storage temperature	T_{stg}			-65 to +150	°C
Junction temperature	T_j	max.		150	°C

THERMAL CHARACTERISTICS *

$$T_j = P \times (R_{th j-t} + R_{th t-s} + R_{th s-a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th j-t}$	=	60	K/W
From tab to soldering points	$R_{th t-s}$	=	280	K/W
From soldering points to ambient **	$R_{th s-a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Collector cut-off current

$I_E = 0$; $-V_{CB} = 30$ V; $T_j = 25$ °C	$-I_{CBO}$	typ.	1	nA
		<	15	nA
$T_j = 150$ °C	$-I_{CBO}$	<	4	μA

Base-emitter voltage [▲]

$-I_C = 2$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	typ.	650	mV
			600 to 750	mV
$-I_C = 10$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	<	820	mV

[▲] $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

* See *Thermal characteristics*.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Saturation voltages *

 $-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$

$-V_{CEsat}$	typ.	75 mV
	<	300 mV

 $-I_C = 100 \text{ mA}; -I_B = 5 \text{ mA}$

$-V_{BEsat}$	typ.	700 mV
$-V_{CEsat}$	typ.	250 mV
	<	650 mV
$-V_{BEsat}$	typ.	850 mV

Knee voltage

 $-I_C = 10 \text{ mA}; -I_B = \text{value for which}$ $-I_C = 11 \text{ mA at } -V_{CE} = 1 \text{ V}$

$-V_{CEK}$	typ.	250 mV
	<	600 mV

Collector capacitance at $f = 1 \text{ MHz}$ $I_E = I_e = 0; -V_{CB} = 10 \text{ V}$

C_C	typ.	4,5 pF
-------	------	--------

Transition frequency at $f = 35 \text{ MHz}$ $-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$

f_T	typ.	150 MHz
-------	------	---------

Small-signal current gain at $f = 1 \text{ kHz}$ $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

h_{fe}	75 to 900
----------	-----------

Noise figure at $R_S = 2 \text{ k}\Omega$ $-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$ $f = 1 \text{ kHz}; B = 200 \text{ Hz}$

F	typ.	2 dB
	<	10 dB

D.C. current gain

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

BC856/857

BC858

BC856A/857A/858A

BC856B/857B/858B

BC857C/858C

h_{FE}	75 to 800
h_{FE}	75 to 800
h_{FE}	125 to 250
h_{FE}	220 to 475
h_{FE}	420 to 800

* $-V_{BEsat}$ decreases by about 1,7 mV/K with increasing temperature.

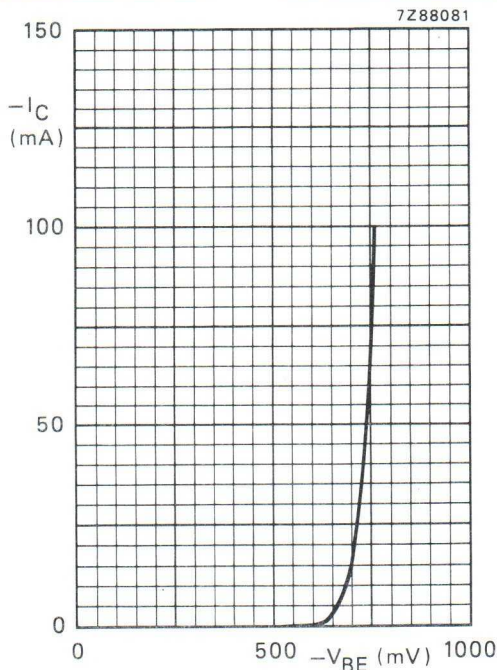


Fig. 3 Typical values. $-V_{CE} = 5 \text{ V}$; $T_j = 25^\circ \text{C}$.

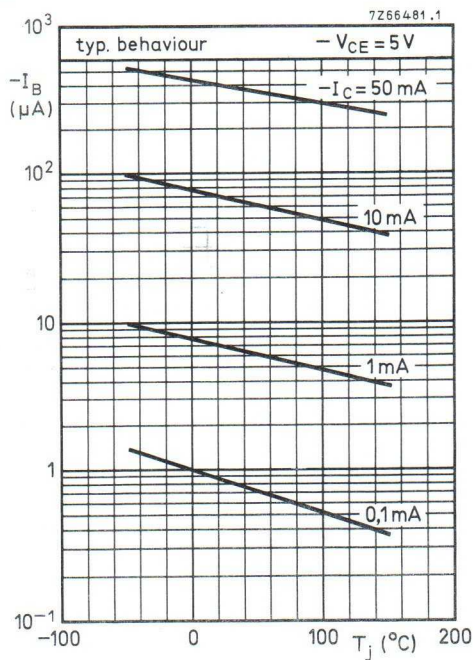


Fig. 4 Typical values.

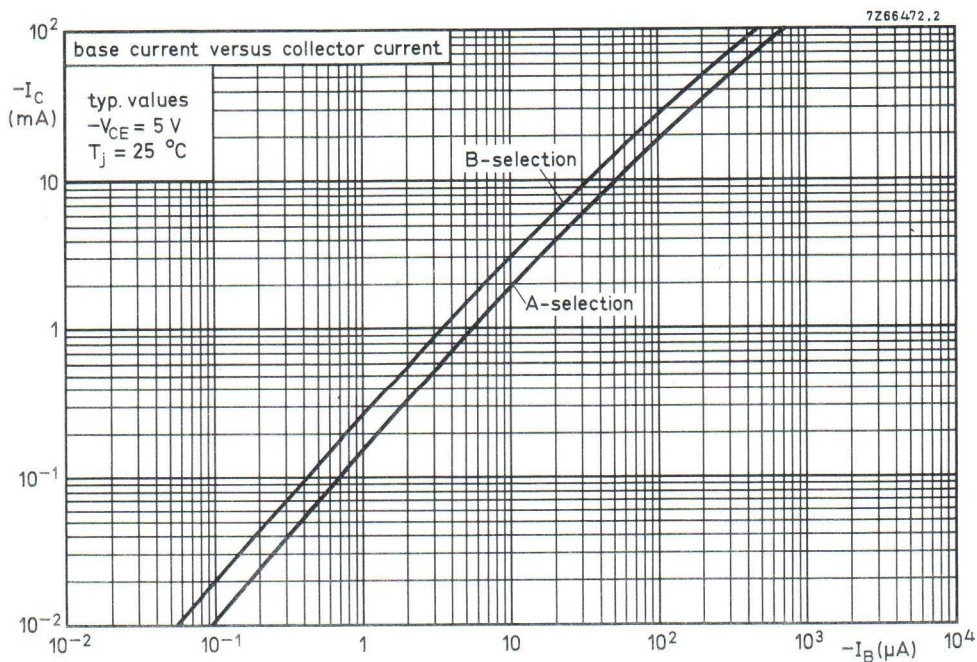


Fig. 5.

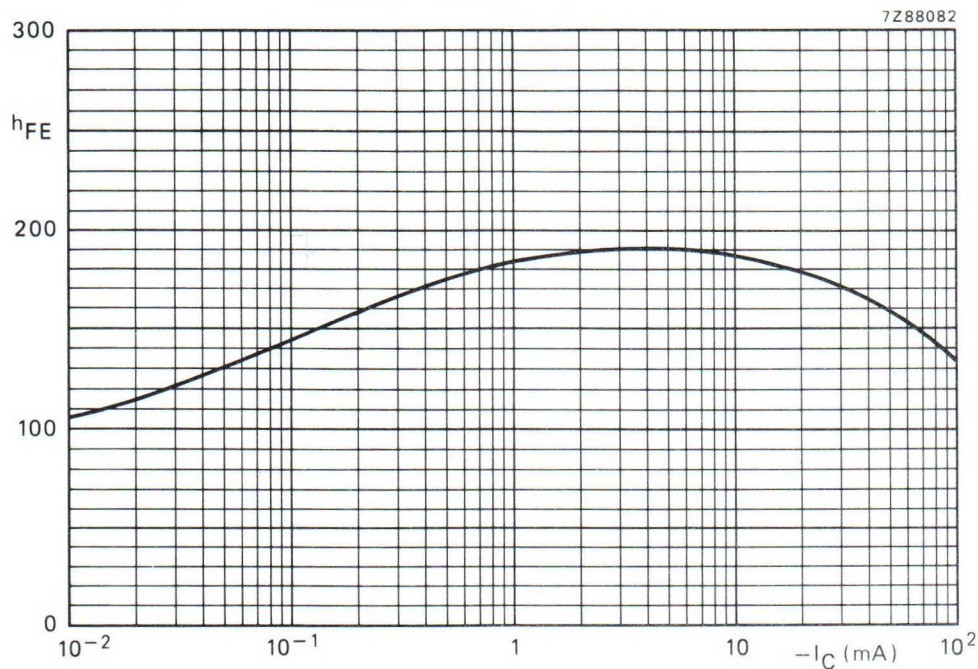


Fig. 6 Typical values D.C. current gain A-selections. $-V_{CE} = 5\text{ V}$; $T_j = 25^\circ\text{C}$.

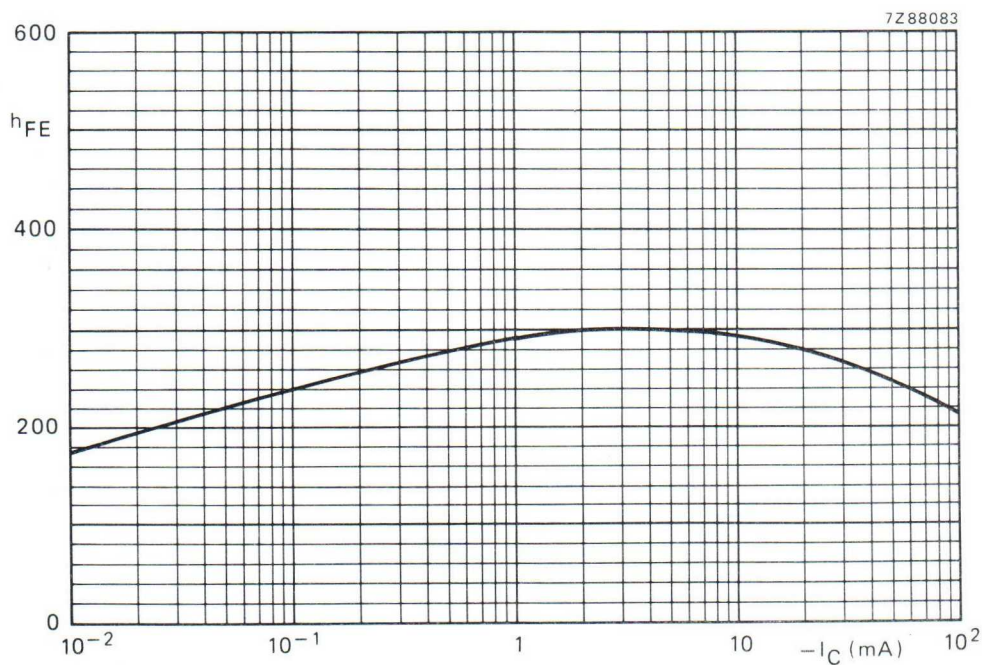


Fig. 7 Typical values D.C. current gain B-selections. $-V_{CE} = 5\text{ V}$; $T_j = 25^\circ\text{C}$.

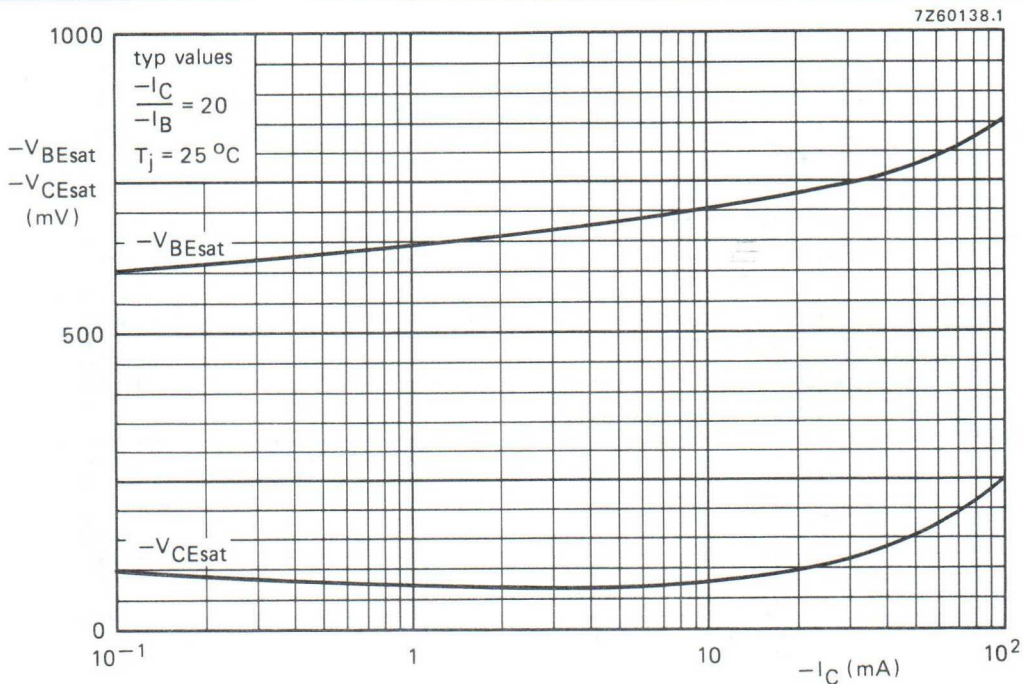


Fig. 8 Typical values base-emitter and collector-emitter saturation voltage.

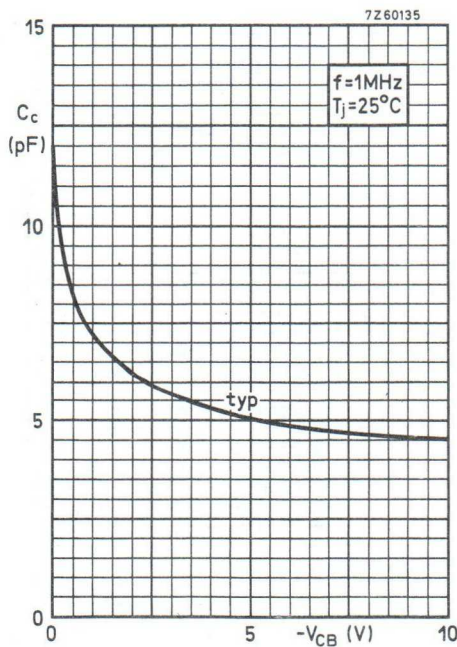


Fig. 9 Typical values.

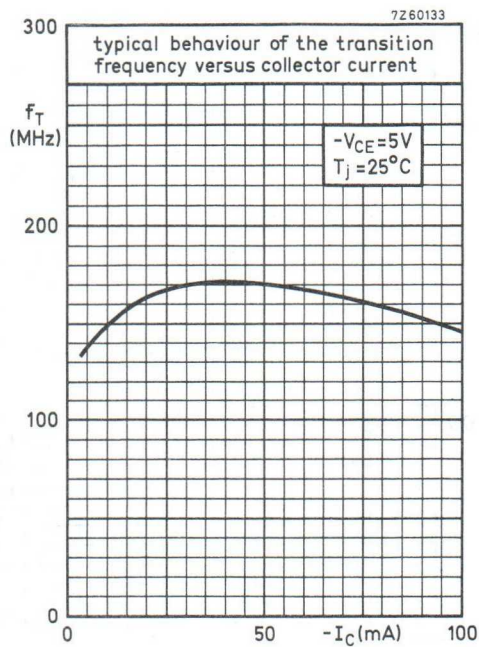


Fig. 10 Typical values. $f = 35\text{ MHz}$.

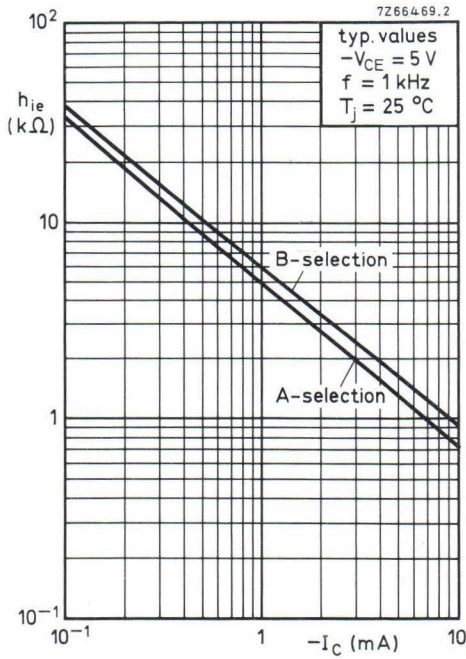


Fig. 11.

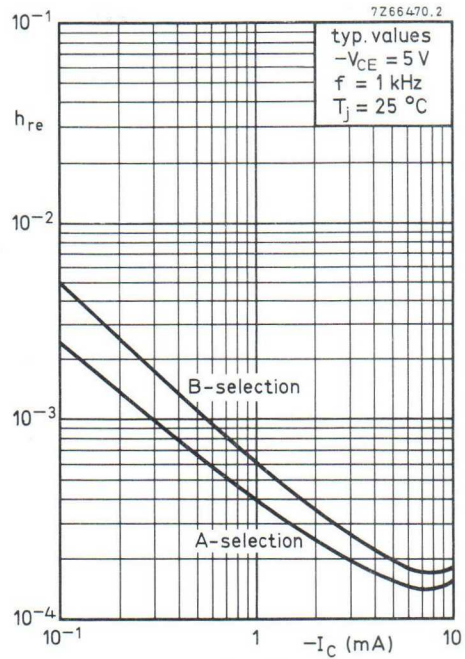


Fig. 12.

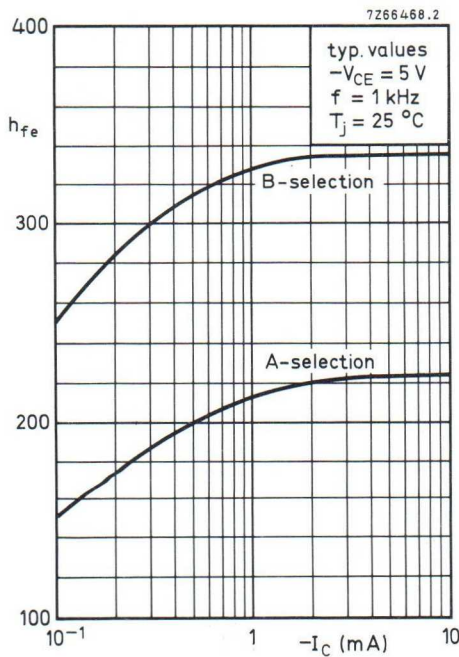


Fig. 13.

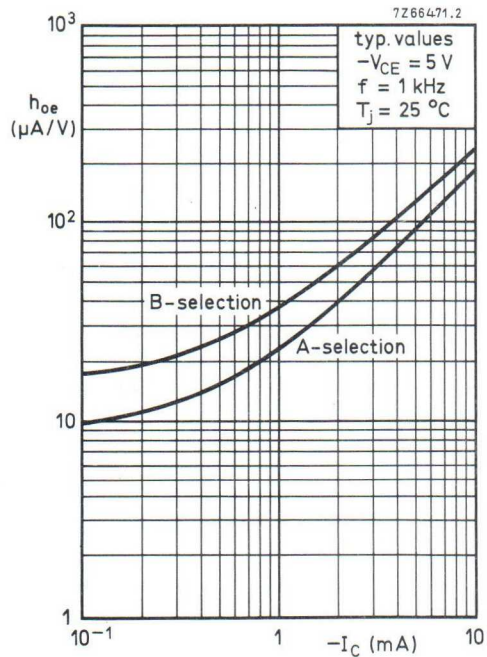


Fig. 14.

100

100

100

100

100

100

100

100

100

100

100

100

100

SILICON PLANAR EPITAXIAL TRANSISTORS

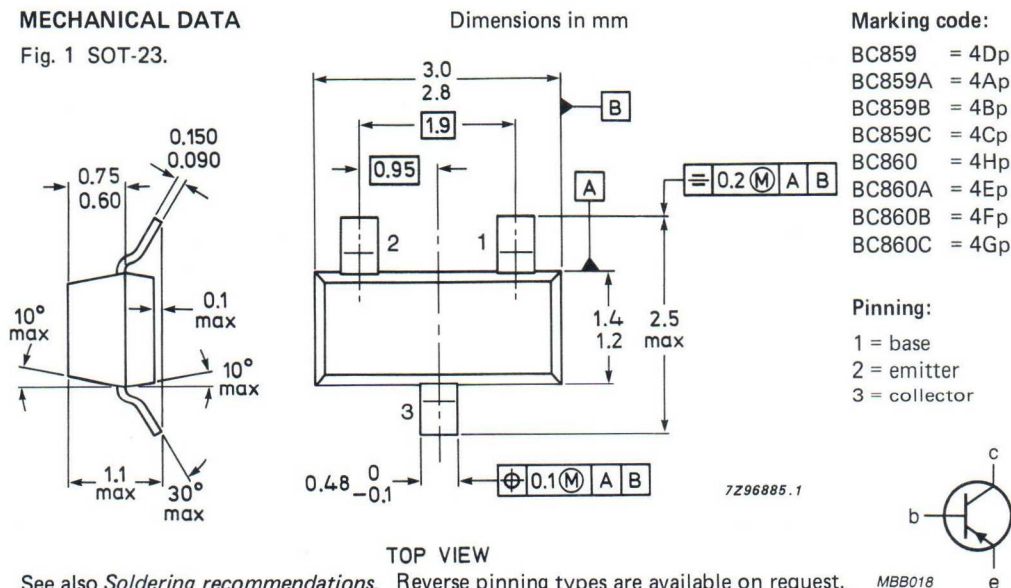
P-N-P transistors in a plastic SOT-23 envelope, primarily intended for low-noise input stages in tape recorders, hi-fi amplifiers and other audio frequency equipment in thick and thin-film hybrid circuits.

QUICK REFERENCE DATA

			BC859	BC860	
Collector-emitter voltage (+ V _{BE} = 1 V)	−V _{CEX}	max.	30	50	V
Collector-emitter voltage (open base)	−V _{CEO}	max.	30	45	V
Collector current (peak value)	−I _{CM}	max.	200	200	mA
Total power dissipation up to T _{amb} = 60 °C	P _{tot}	max.	250	250	mW
Junction temperature	T _j	max.	150	150	°C
Small-signal current gain					
−I _C = 2 mA; −V _{CE} = 5 V; f = 1 kHz	h _{fe}	>	125	125	
		<	900	900	
Transition frequency					
−I _C = 10 mA; −V _{CE} = 5 V	f _T	typ.	150	150	MHz
Noise figure at R _s = 2 kΩ					
−I _C = 200 μA; −V _{CE} = 5 V					
f = 30 Hz to 15 kHz	F	typ.	1,2	1	dB
		<	4	3	dB
f = 1 kHz; B = 200 Hz	F	<	4	4	dB

MECHANICAL DATA

Fig. 1 SOT-23.



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC859	BC860	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	50	V
Collector-emitter voltage (+ $V_{BE} = 1$ V)	$-V_{CEX}$	max.	30	50	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	45	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	100		mA
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Emitter current (peak value)	I_{EM}	max.	200		mA
Base current (peak value)	$-I_{BM}$	max.	200		mA
Total power dissipation up to $T_{amb} = 60$ °C**	P_{tot}	max.	250		mW
Storage temperature	T_{stg}		-65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS*

$$T_j = P_x (R_{th\ j-t} + R_{th\ t-s} + R_{th\ s-a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\ j-t}$	=	60	K/W
From tab to soldering points	$R_{th\ t-s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s-a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 30$ V; $T_j = 25$ °C	$-I_{CBO}$	typ.	1	nA
		<	15	nA
$T_j = 150$ °C	$-I_{CBO}$	<	4	μA

Base-emitter voltage ▲

$-I_C = 2$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	typ.	650	mV
			600 to 750	mV
$-I_C = 10$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	<	820	mV

* See *Thermal characteristics*.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Saturation voltages* $-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$

$-V_{CEsat}$	typ.	75	mV
	<	300	mV

$-V_{BEsat}$	typ.	700	mV
--------------	------	-----	----

 $-I_C = 100 \text{ mA}; -I_B = 5 \text{ mA}$

$-V_{CEsat}$	typ.	250	mV
	<	650	mV

$-V_{BEsat}$	typ.	850	mV
--------------	------	-----	----

Collector capacitance at $f = 1 \text{ MHz}$ $I_E = I_e = 0; -V_{CB} = 10 \text{ V}$

C_c	typ.	4,5	pF
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Transition frequency at $f = 35 \text{ MHz}$ $-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$

f_T	typ.	150	MHz
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Small-signal current gain at $f = 1 \text{ kHz}$ $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

h_{fe}	125 to 900
----------	------------

Noise figure at $R_S = 2 \text{ k}\Omega$ $-I_C = 200 \text{ }\mu\text{A}; -V_{CE} = 5 \text{ V}$ $f = 30 \text{ Hz to } 15 \text{ kHz}$

		BC859	BC860	
F	typ.	1,2	1	dB
	<	4	3	dB

 $f = 1 \text{ kHz}; B = 200 \text{ Hz}$

F	typ.	1	1	dB
	<	4	4	dB

Equivalent noise voltage at $R_S = 2 \text{ k}\Omega$ $-I_C = 200 \text{ }\mu\text{A}; -V_{CE} = 5 \text{ V}$ $f = 10 \text{ Hz to } 50 \text{ Hz}; T_{amb} = 25 \text{ }^\circ\text{C}$

V_n	<	—	0,11	μV
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D.C. current gain $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; \text{ total range}$

A selections

h_{FE}	125 to 800
----------	------------

B selections

h_{FE}	125 to 250
----------	------------

C selections

h_{FE}	220 to 475
----------	------------

h_{FE}	420 to 800
----------	------------

* $-V_{BEsat}$ decreases by about $1,7 \text{ mV/K}$ with increasing temperature.

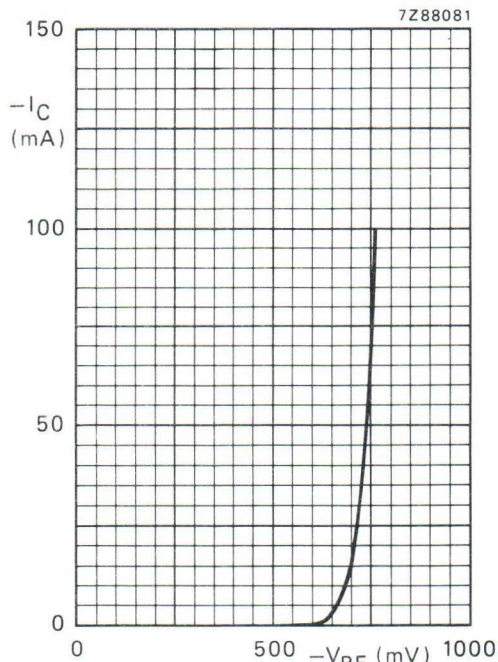


Fig. 3 Typical values. $-V_{CE} = 5\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$.

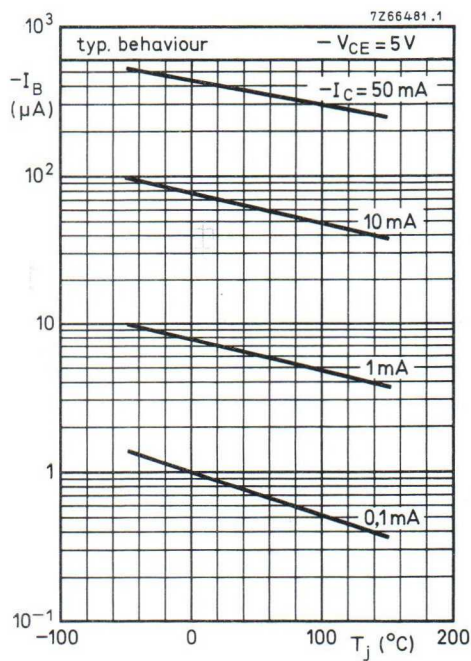


Fig. 4 Typical values.

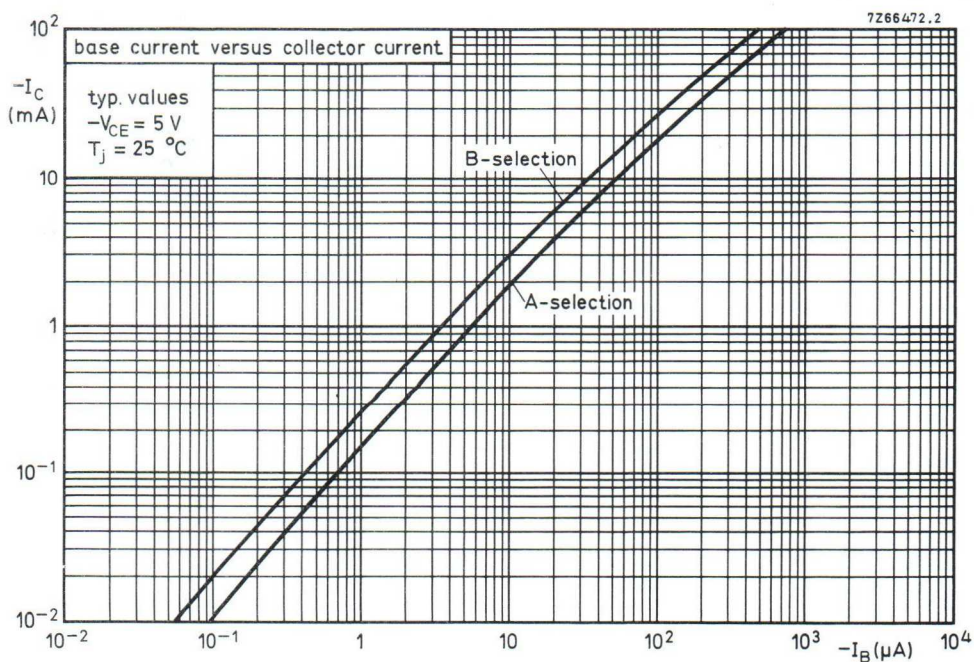


Fig. 5.

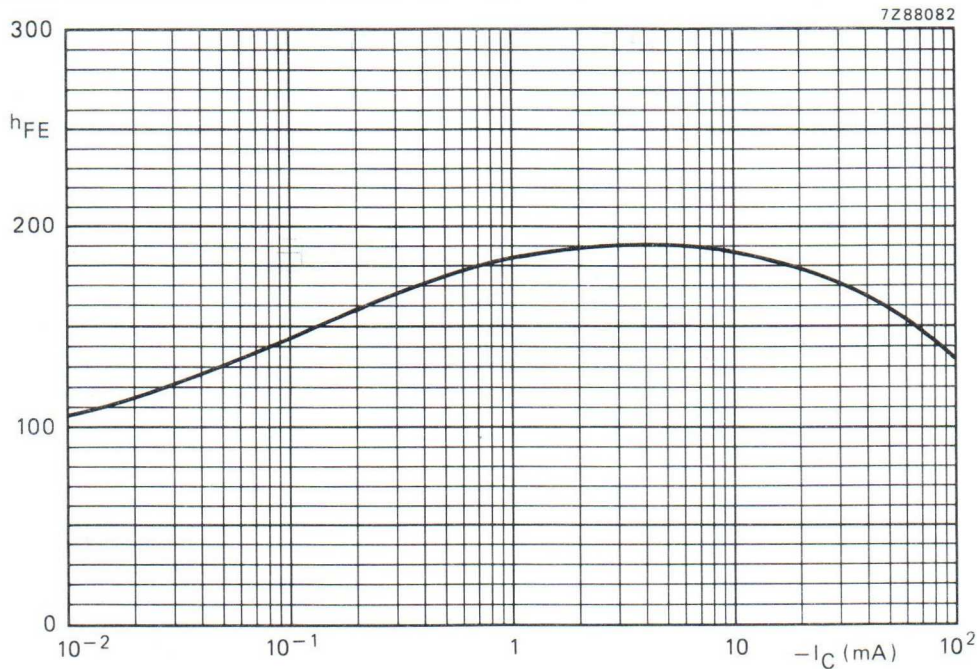


Fig. 6 Typical values. D.C. current gain A-selections. $-V_{CE} = 5$ V; $T_j = 25$ °C.

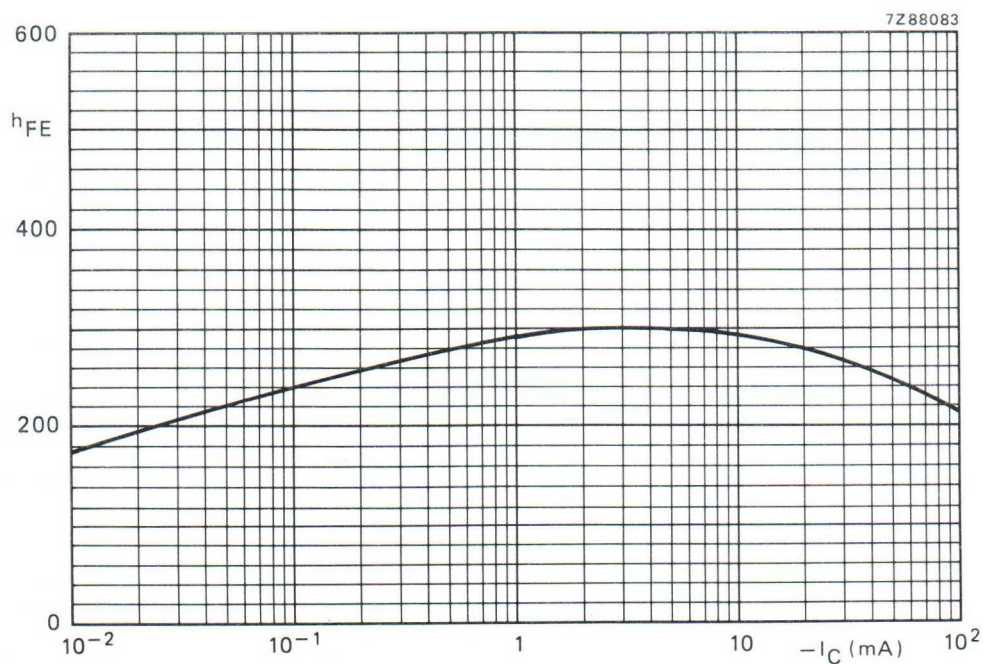


Fig. 7 Typical values. D.C. current gain B-selections. $-V_{CE} = 5$ V; $T_j = 25$ °C.

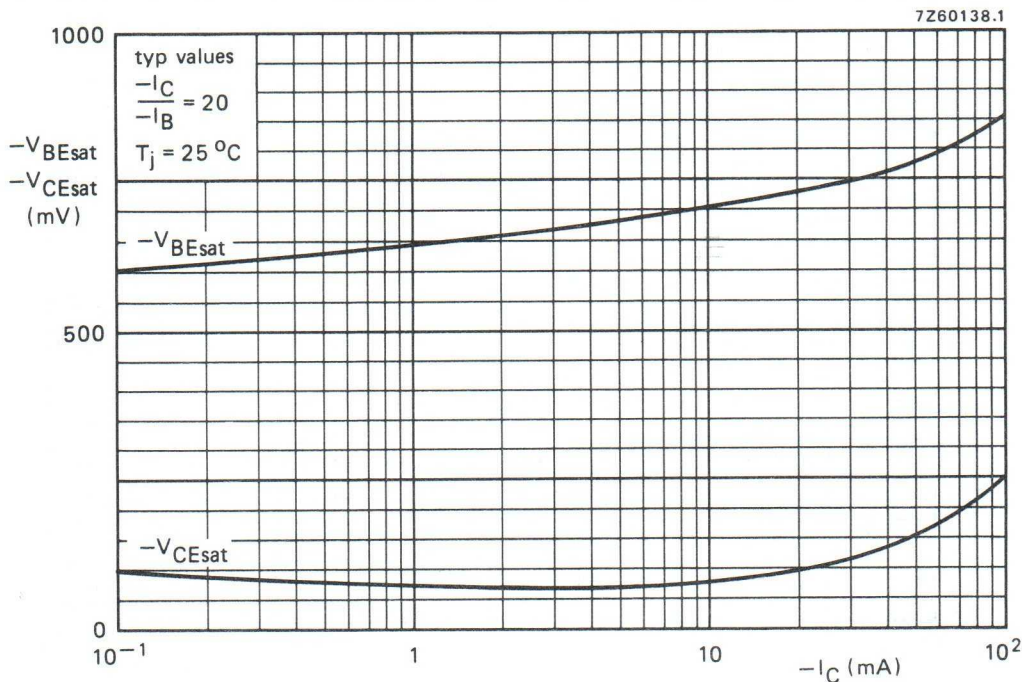


Fig. 8 Typical values base-emitter and collector-emitter saturation voltage.

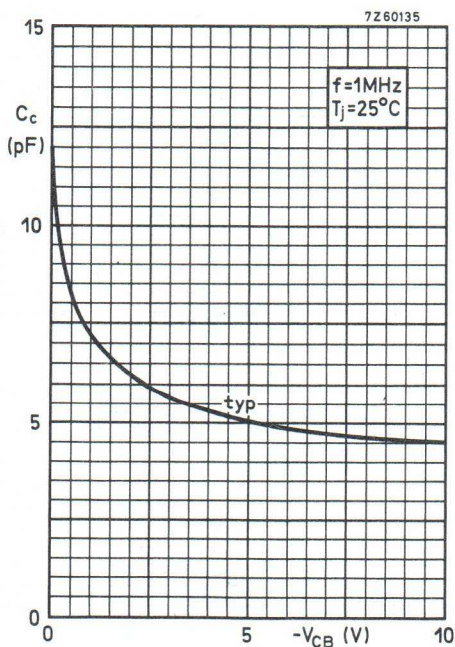


Fig. 9 Typical values.

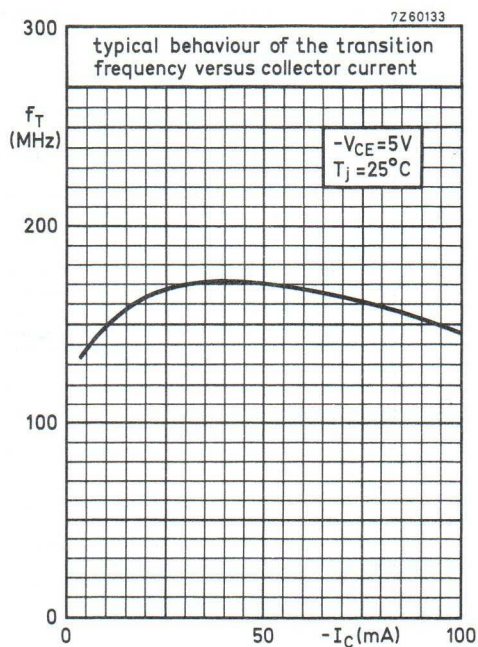


Fig. 10 Typical values. $f = 35\text{ MHz}$.

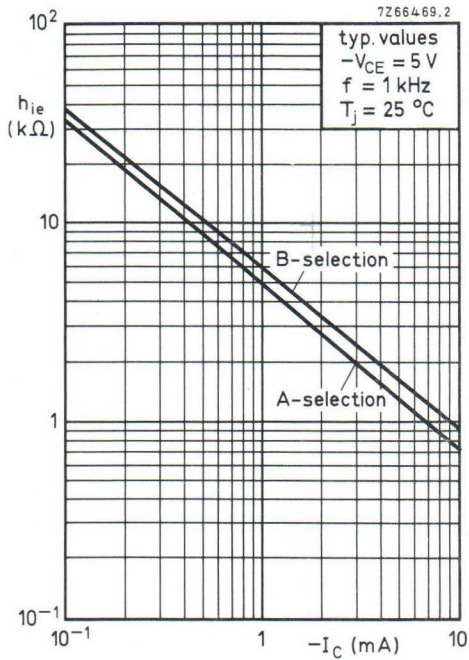


Fig. 11 Typical values.

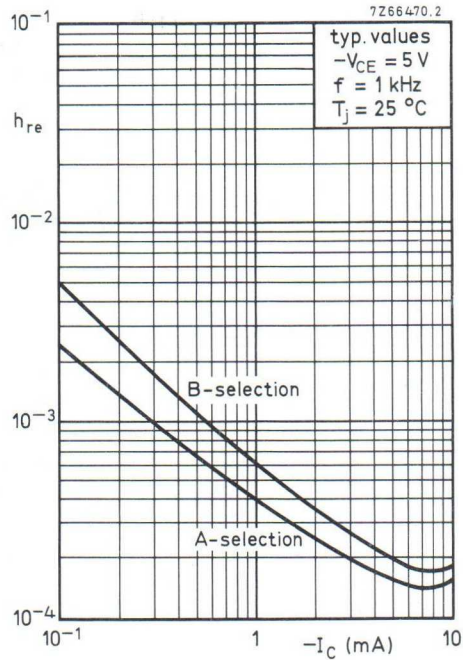


Fig. 12 Typical values.

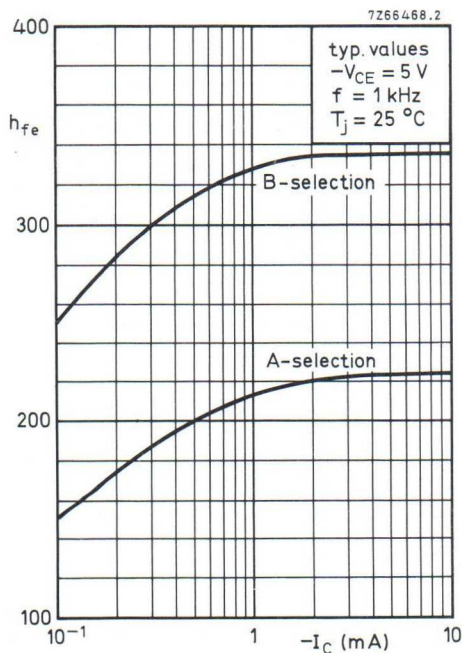


Fig. 13 Typical values.

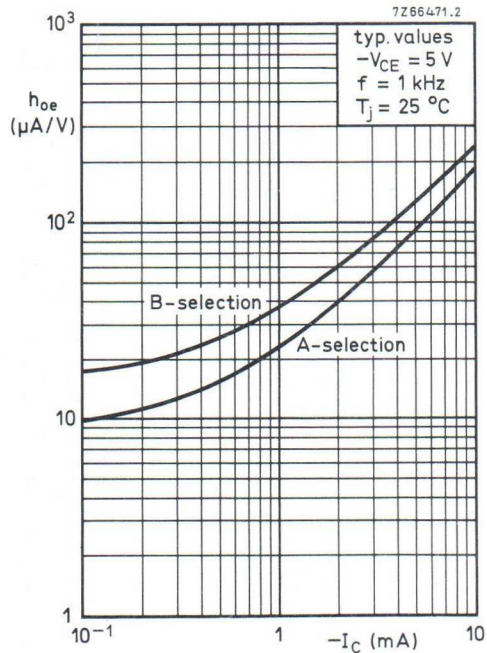


Fig. 14 Typical values.

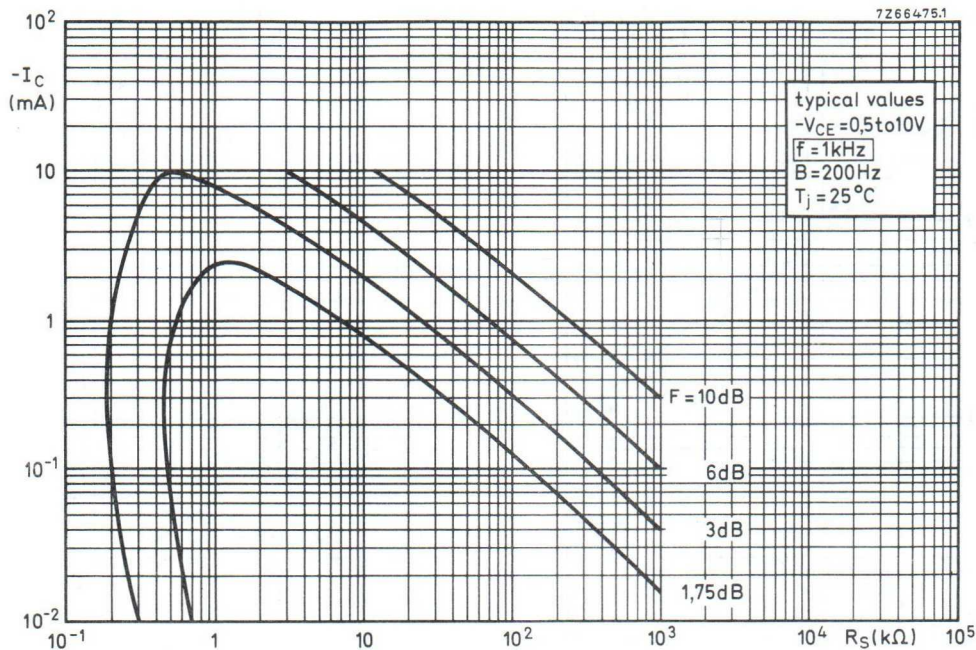


Fig. 15 Curves of constant noise figure at $f = 1 \text{ kHz}$.

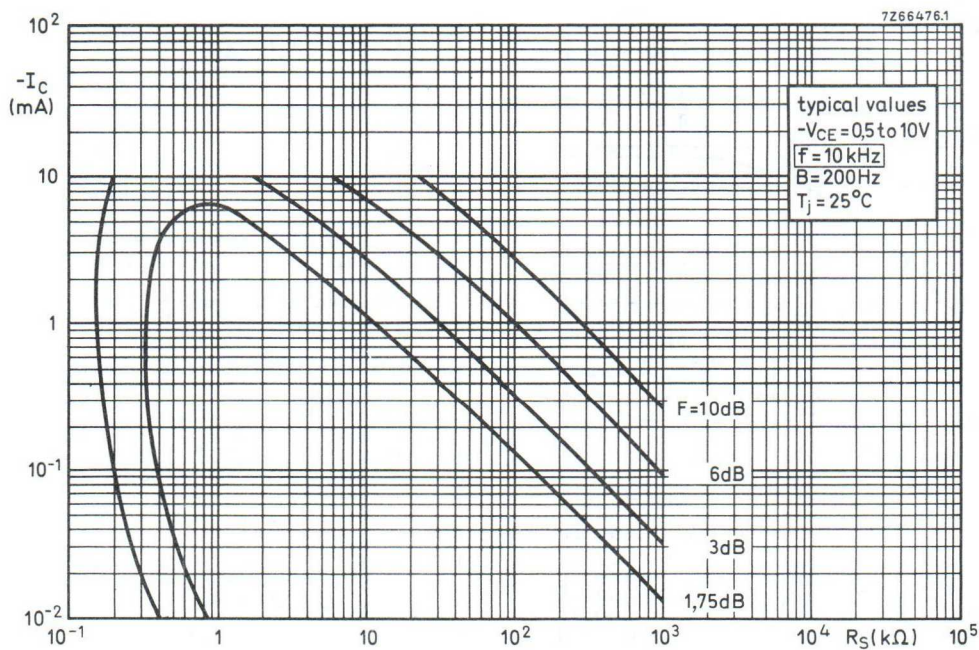


Fig. 16 Curves of constant noise figure at $f = 10 \text{ kHz}$.

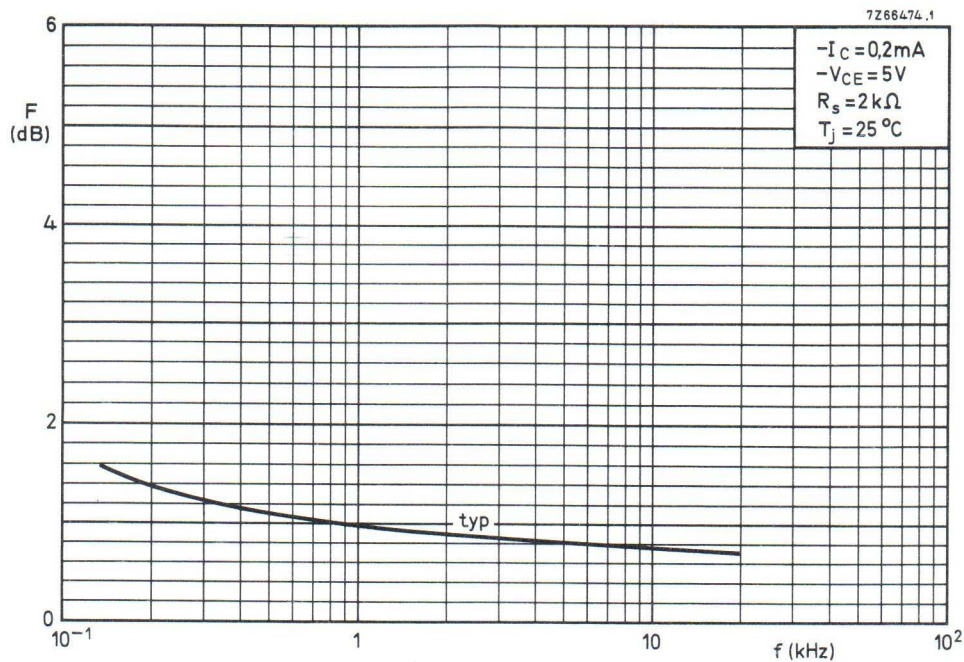


Fig. 17 Typical values noise figure.

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor in a microminiature plastic envelope intended for low-voltage, high-current l.f. applications. BC868/BC869 is the matched complementary pair suitable for class-B audio output stages up to 3 W.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	20 V
Collector current (peak value)	I_{CM}	max.	2 A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	1 W
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}		85 to 375
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	60 MHz

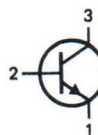
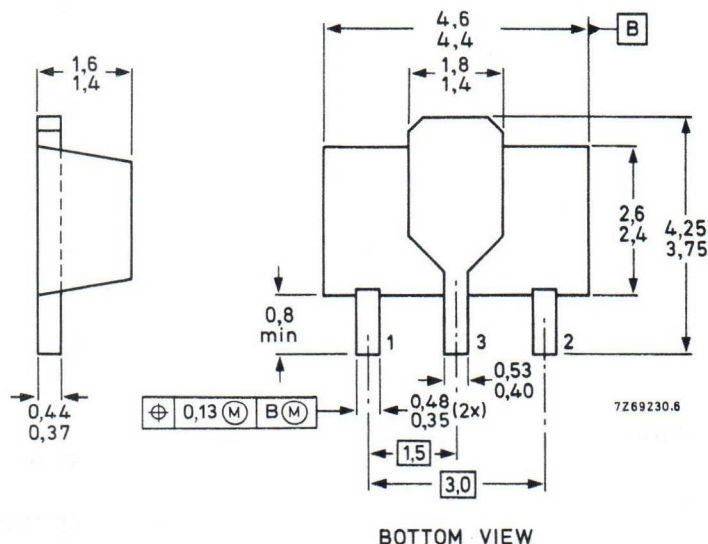
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-89.

BC868 = CAC
BC868-10 = CBC
BC868-16 = CCC
BC868-25 = CDC



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	20 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	1 A
Collector current (peak value)	I_{CM}	max.	2 A
Base current (d.c.)	I_B	max.	100 mA
Base current (peak value)	I_{BM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1 W
Storage temperature	T_{stg}		-65 to + 150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j-a}$	=	125 K/W
From junction to tab	$R_{th\ j-t}$	=	10 K/W

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current			
$I_E = 0; V_{CB} = 25\text{ V}$	I_{CBO}	<	10 μA
$I_E = 0; V_{CB} = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	I_{CBO}	<	1 mA
Emitter cut-off current			
$I_C = 0; V_{EB} = 5\text{ V}$	I_{EBO}	<	10 μA
Base-emitter voltage			
$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	V_{BE}	typ.	0,62 V
$I_C = 1\text{ A}; V_{CE} = 1\text{ V}$	V_{BE}	<	1 V
Collector-emitter saturation voltage			
$I_C = 1\text{ A}; I_B = 100\text{ mA}$	V_{CEsat}	<	0,5 V
DC current gain			
$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	BC8681	h_{FE}	50
DC current gain			
$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$	BC868	h_{FE}	> 50
$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	BC868	h_{FE}	85 to 375
	BC868-10	h_{FE}	$\leq$ 160
	BC868-16	h_{FE}	100 to 250
	BC868-25	h_{FE}	$\geq$ 160
$I_C = 1\text{ A}; V_{CE} = 1\text{ V}$	BC868	h_{FE}	> 60
Collector capacitance at $f = 450\text{ kHz}$			
$I_E = I_e = 0; V_{CB} = 5\text{ V}$	C_c	typ.	27 pF
Transition frequency at $f = 35\text{ MHz}$			
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	60 MHz

* Mounted on a ceramic substrate, area = 2,5 cm²; thickness = 0,7 mm.

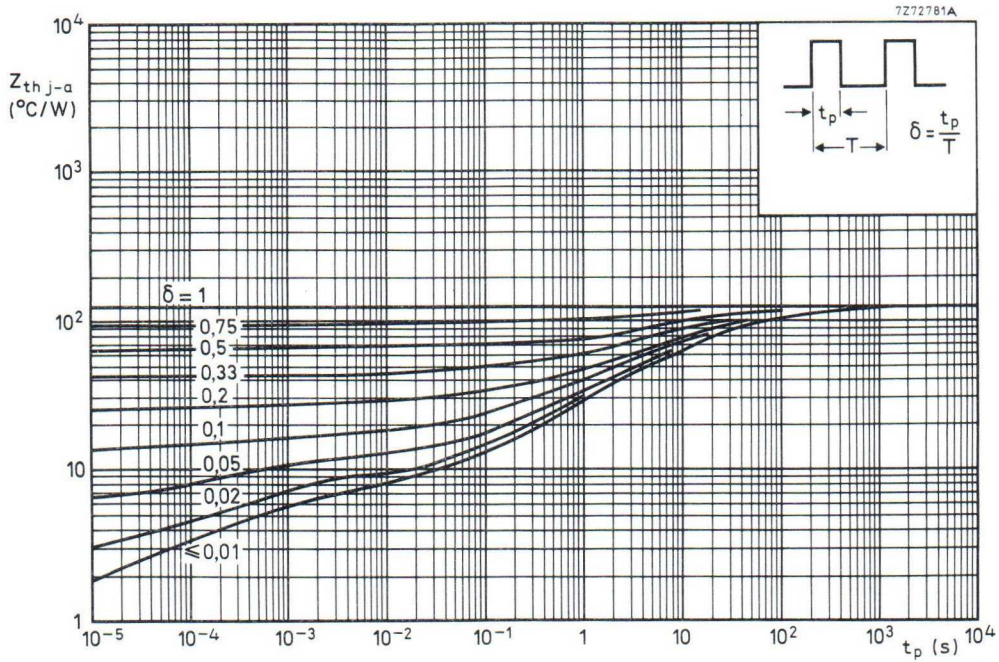


Fig. 2 Pulse power rating chart.

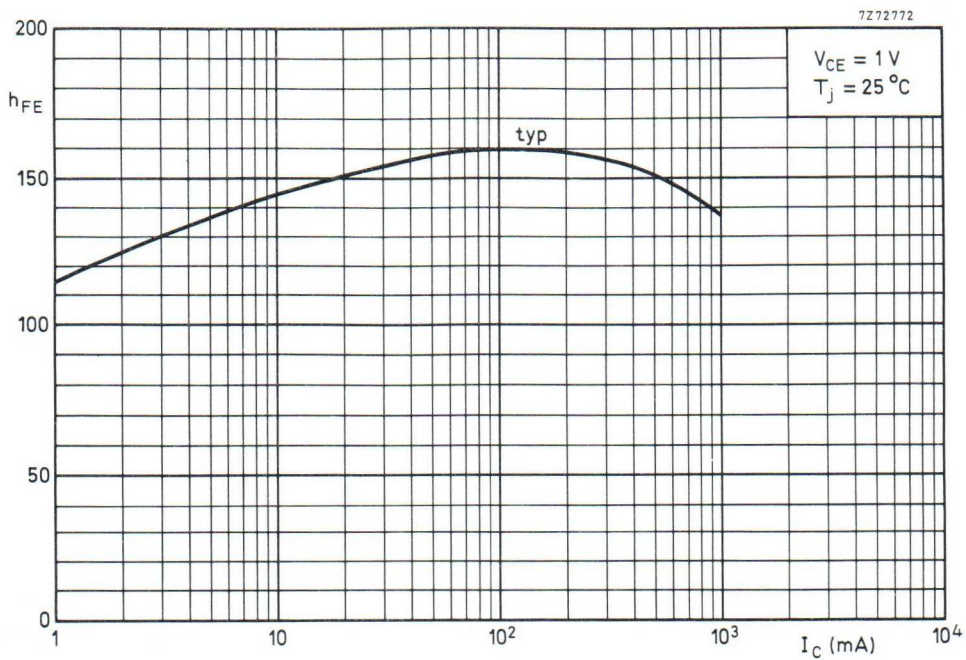


Fig. 3 D.C. current gain.

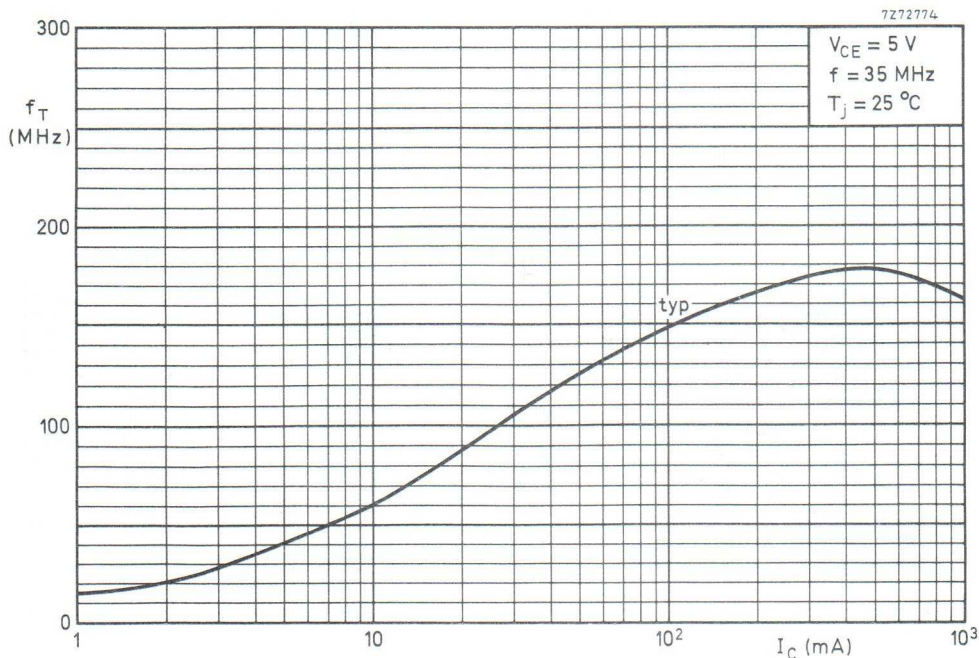


Fig. 4 Typical values transition frequency as a function of collector current.

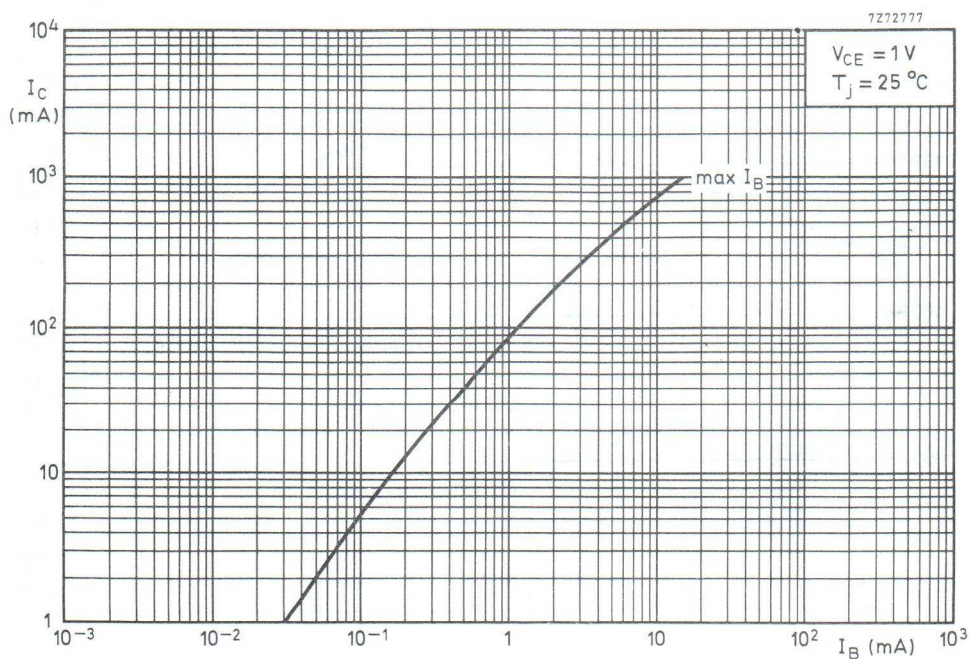


Fig. 5 Typical values collector current as a function of maximum base current.

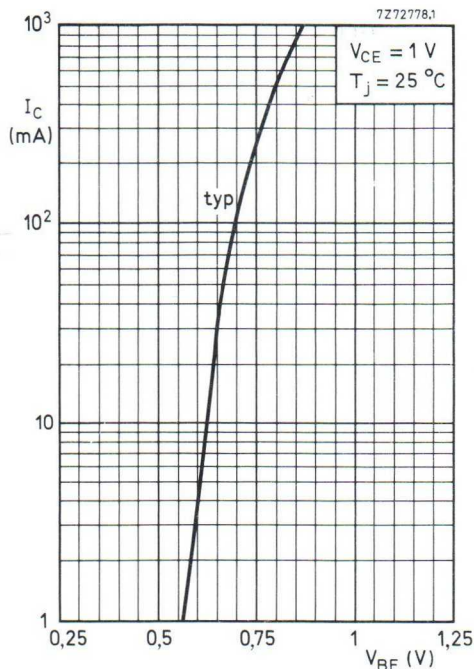


Fig. 6 Typical values collector current as a function of base-emitter voltage.

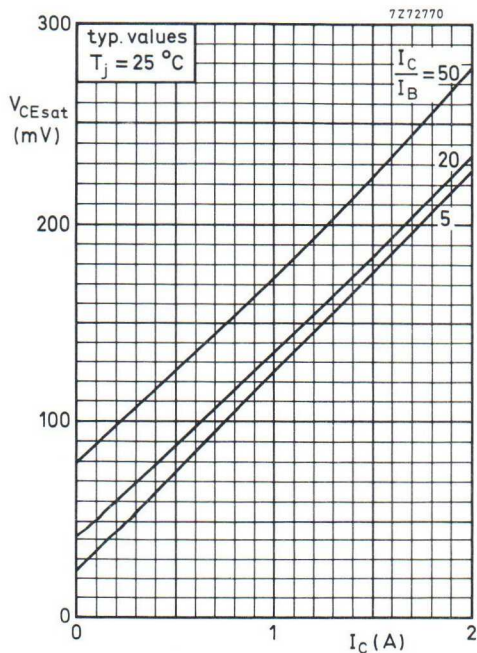


Fig. 7 Collector-emitter saturation voltage as a function of collector current.

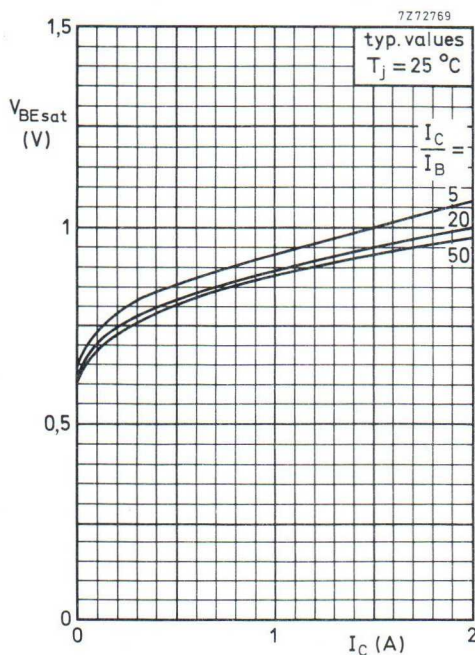


Fig. 8 Base-emitter saturation voltage as a function of collector current.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a plastic microminiature envelope, intended for low-voltage, high-current l.f. applications. BC868/BC869 is the matched complementary pair suitable for class-B audio output stages up to 3 W.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	25 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20 V
Collector current (peak value)	$-I_{CM}$	max.	2 A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	1 W
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain	h_{FE}	85 to 375	
Transition frequency at $f = 35\text{ MHz}$	f_T	typ.	60 MHz
$-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$			
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$			

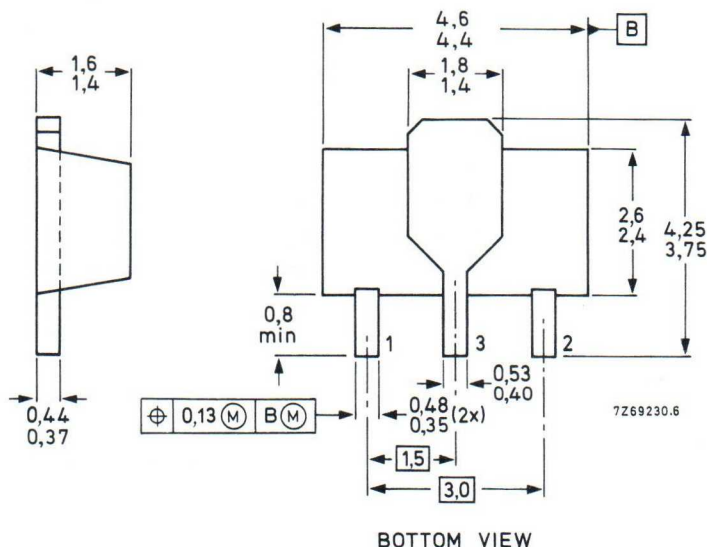
MECHANICAL DATA

Dimensions in mm

Marking code

Fig. 1 SOT-89.

BC869 = CEC
BC869-10 = CGC



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	25 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	1 A
Collector current (peak value)	$-I_{CM}$	max.	2 A
Base current (d.c.)	$-I_B$	max.	100 mA
Base current (peak value)	$-I_{BM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1 W
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j-a}$	=	125 K/W
From junction to tab	$R_{th\ j-t}$	=	10 K/W

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

 $I_E = 0; -V_{CB} = 25\text{ V}$ $-I_{CBO} < 10\text{ }\mu\text{A}$ $I_E = 0; -V_{CB} = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $-I_{CBO} < 1\text{ mA}$

Emitter cut-off current

 $I_C = 0; -V_{EB} = 5\text{ V}$ $-I_{EBO} < 10\text{ }\mu\text{A}$

Base-emitter voltage

 $-I_C = 5\text{ mA}; -V_{CE} = 10\text{ V}$ $-V_{BE}$ typ. 0,62 V $-I_C = 1\text{ A}; -V_{CE} = 1\text{ V}$ $-V_{BE} < 1\text{ V}$

Collector-emitter saturation voltage

 $-I_C = 1\text{ A}; -I_B = 100\text{ mA}$ $-V_{CEsat} < 0,5\text{ V}$

D.C. current gain

 $-I_C = 5\text{ mA}; -V_{CE} = 10\text{ V}$ BC869 $h_{FE} > 50$ $-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$ BC869 h_{FE} 85 to 375BC869-10 $h_{FE} \leq 160$ BC869-16 h_{FE} 100 to 250BC869-25 $h_{FE} \geq 160$ BC869 $h_{FE} > 60$ $-I_C = 1\text{ A}; -V_{CE} = 1\text{ V}$ Collector capacitance at $f = 450\text{ kHz}$ $I_E = I_E = 0; -V_{CB} = 5\text{ V}$ C_c typ. 45 pFTransition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$ f_T typ. 60 MHz* Mounted on a ceramic substrate, area = $2,5\text{ cm}^2$; thickness = 0,7 mm.

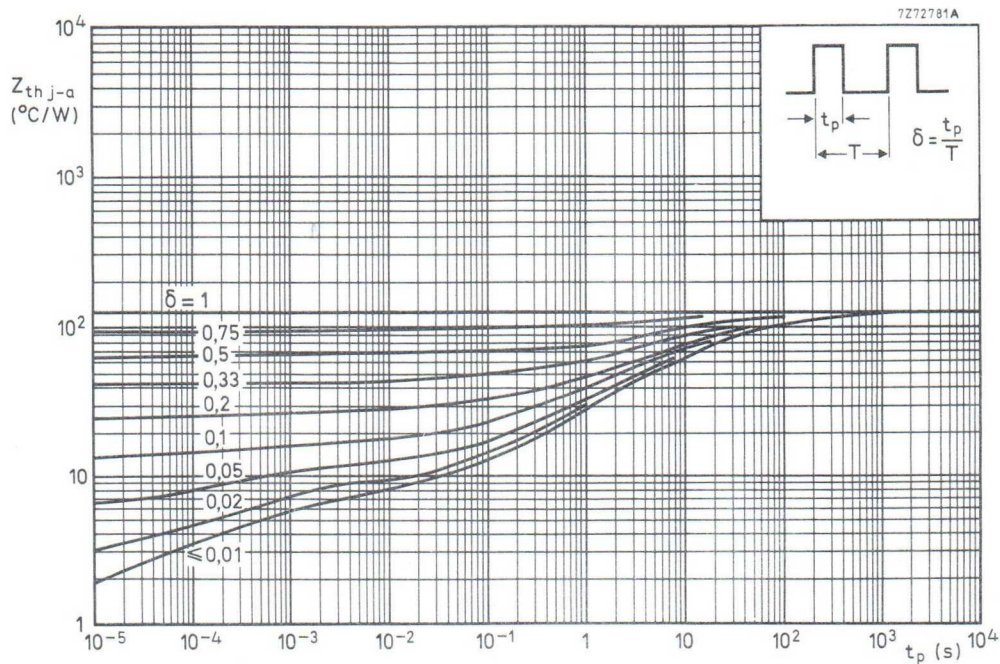


Fig. 2 Pulse power rating chart.

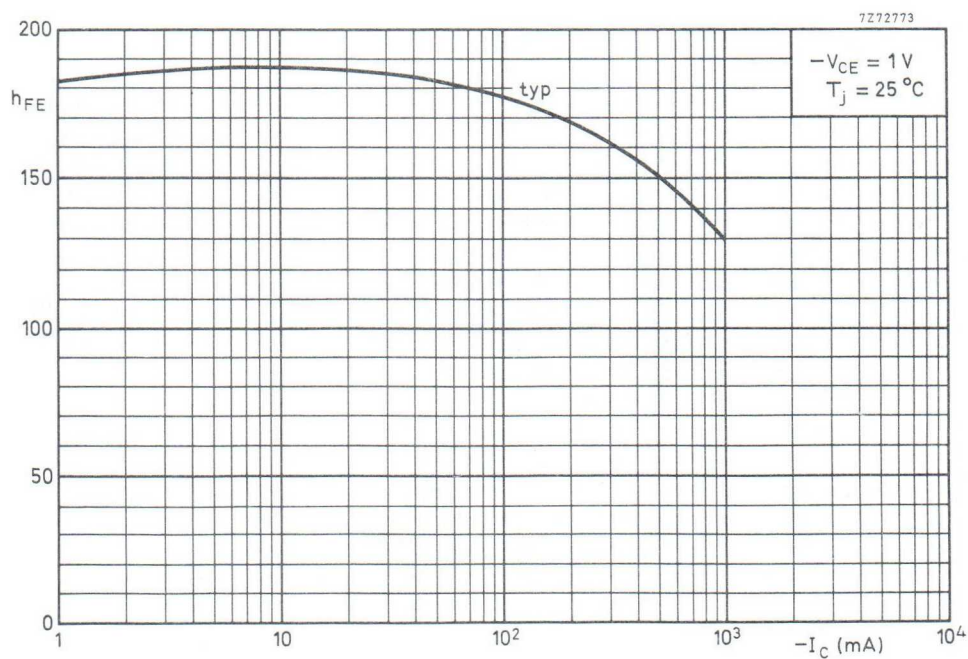


Fig. 3 D.C. current gain.

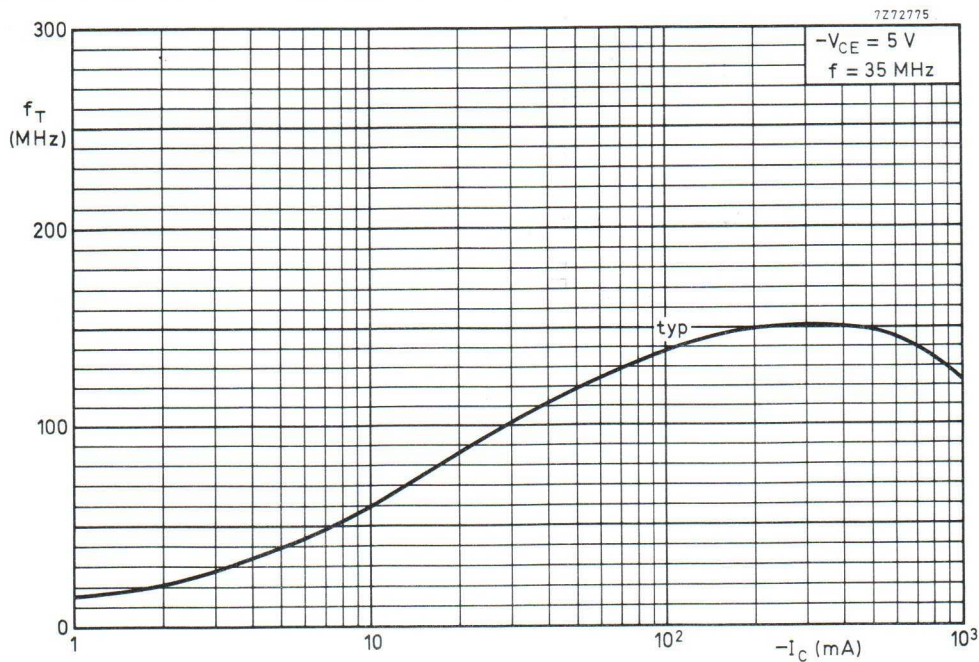


Fig. 4 Typical values transition frequency as a function of collector current.

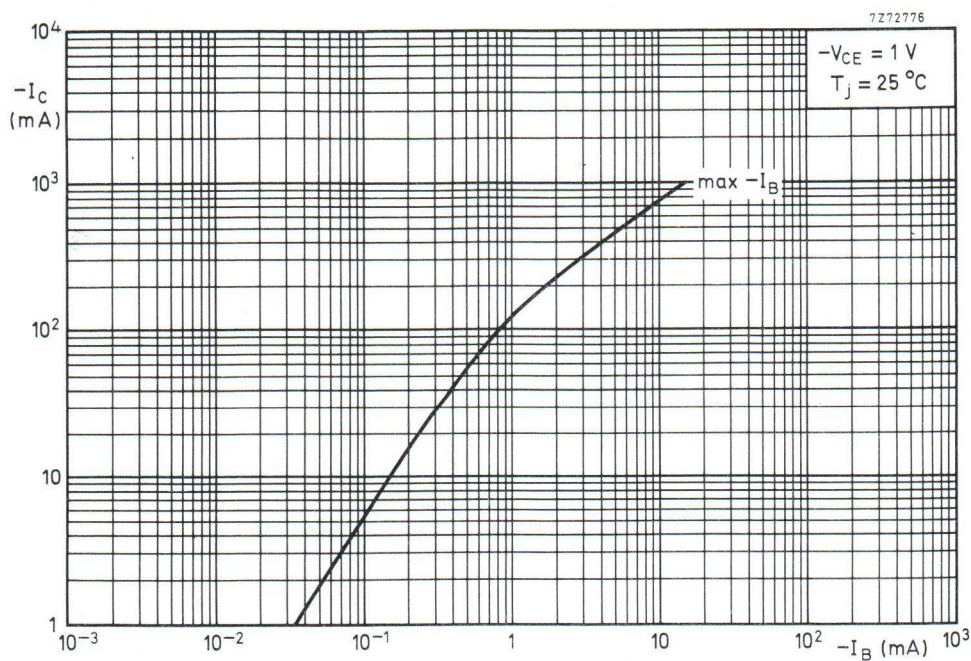


Fig. 5 Typical values collector current as a function of maximum base current.

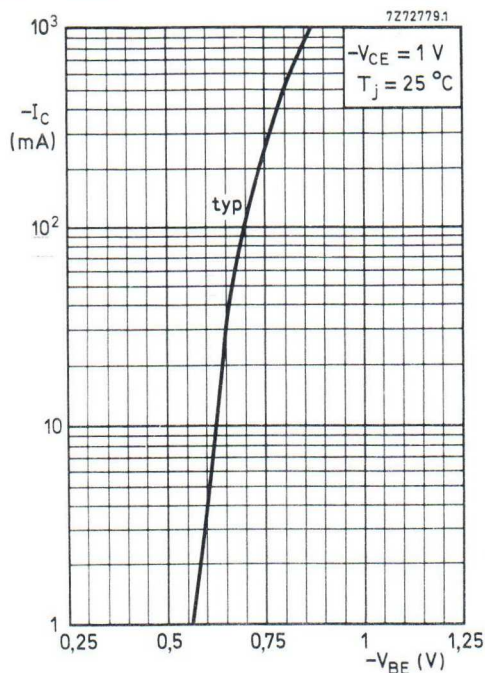


Fig. 6 Typical values collector current as a function of base-emitter voltage.

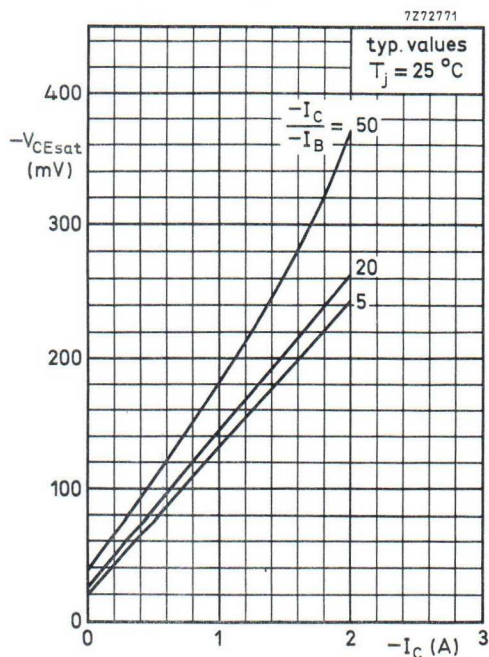


Fig. 7 Collector-emitter saturation voltage as a function of collector current.

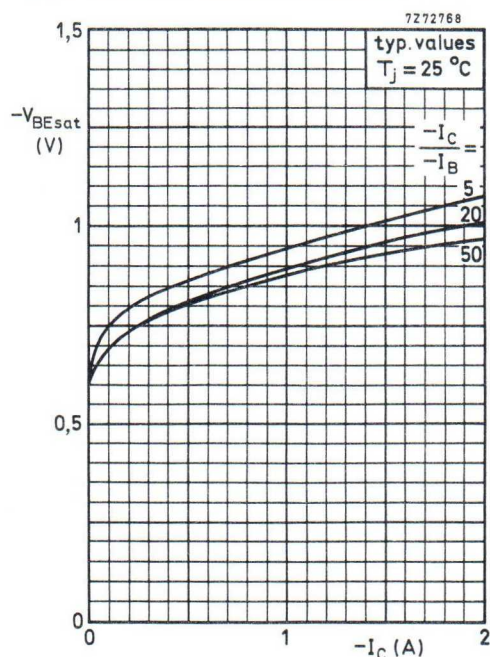


Fig. 8 Base-emitter saturation voltage as a function of collector current.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base) $-I_C = 2$ mA	$-V_{CEO}$	max.	32 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25$ °C**	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Collector cut-off current

$I_E = 0$; $-V_{CB} = 32$ V

$-I_{CBO} < 100$ nA

$I_E = 0$; $-V_{CB} = 32$ V; $T_j = 100$ °C

$-I_{CBO} < 10$ µA

Base-emitter voltage

$-I_C = 2$ mA; $-V_{CE} = 5$ V

$-V_{BE} 600$ to 750 mV

Saturation voltages

$-I_C = 10$ mA; $-I_B = 0,5$ mA

$-V_{CEsat}$ typ. 80 mV
< 300 mV

$-V_{BEsat}$ typ. 720 mV

$-I_C = 50$ mV; $-I_B = 2,5$ mA

$-V_{CEsat}$ typ. 150 mV

$-V_{BEsat}$ typ. 810 mV

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$-I_C = 10 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

		BCF29	BCF30
h_{FE}	typ.	90	150
	$>$	120	215
	$<$	260	500
C_C	typ.	4,5	pF
f_T	typ.	150	MHz
F	$<$	4	dB
	typ.	1	dB

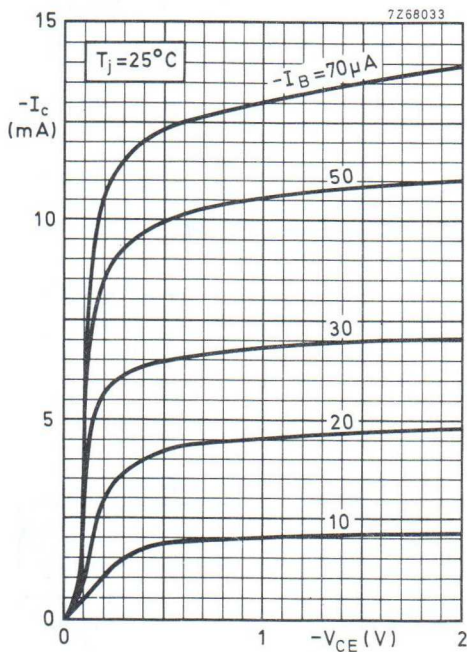


Fig. 2

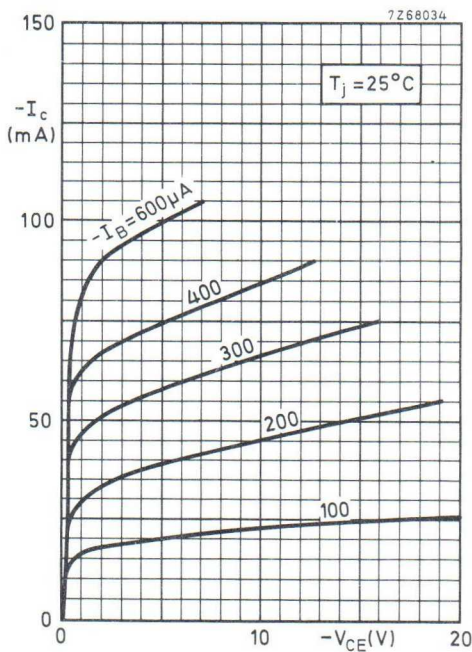


Fig. 3

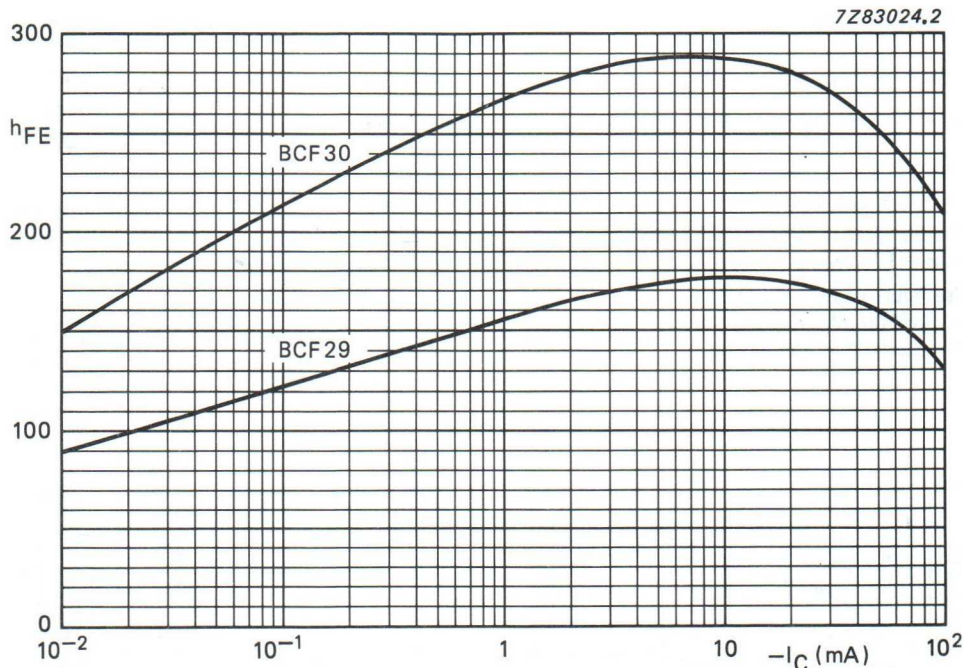


Fig. 4 Typical values of d.c. current gain. $-V_{CE} = 5$ V; $T_j = 25^\circ\text{C}$.

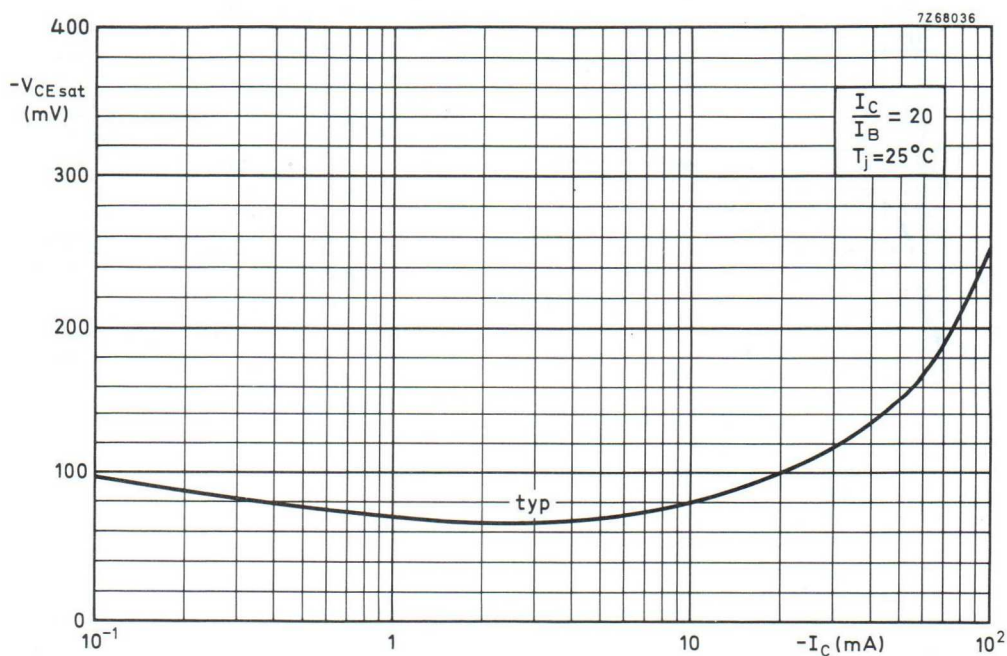


Fig. 5

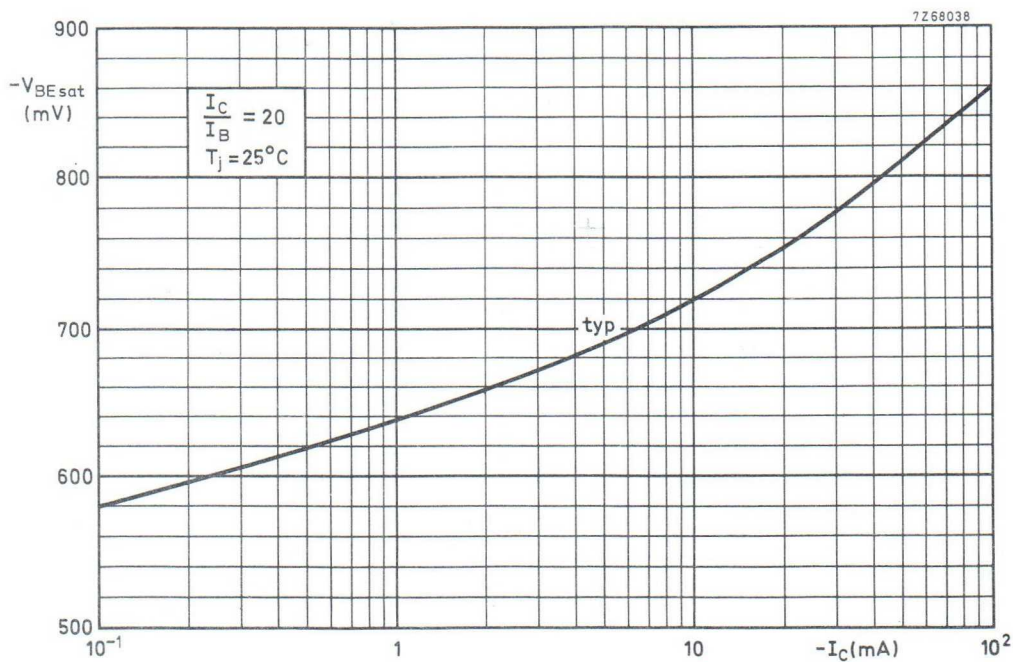


Fig. 6

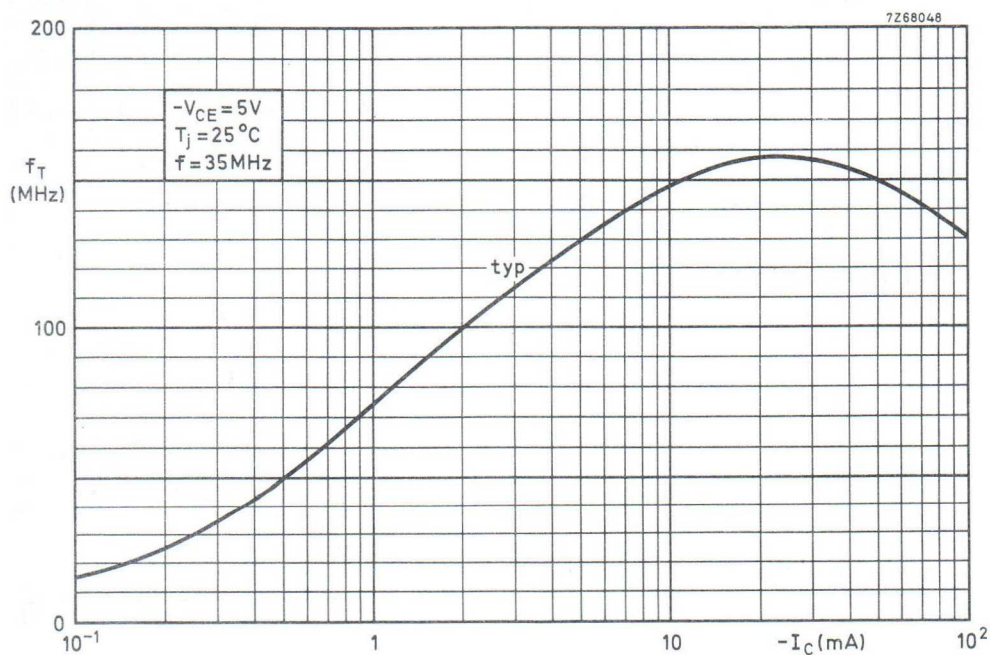


Fig. 7

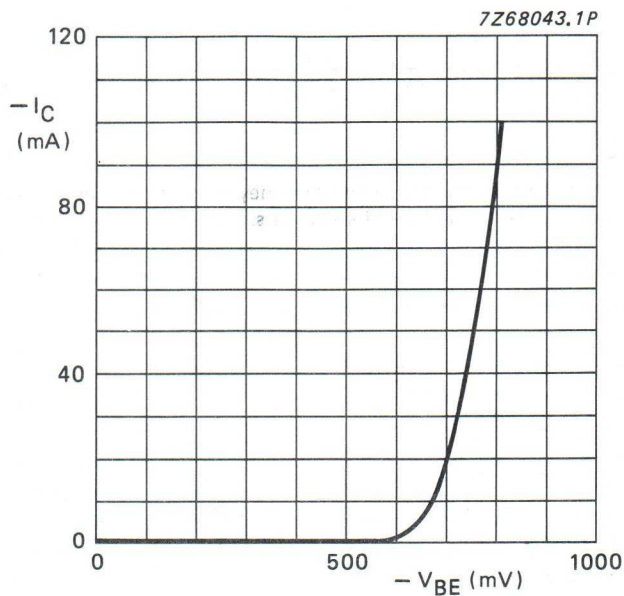


Fig. 8 $-V_{CE} = 5$ V; $T_j = 25^\circ\text{C}$; typical values.

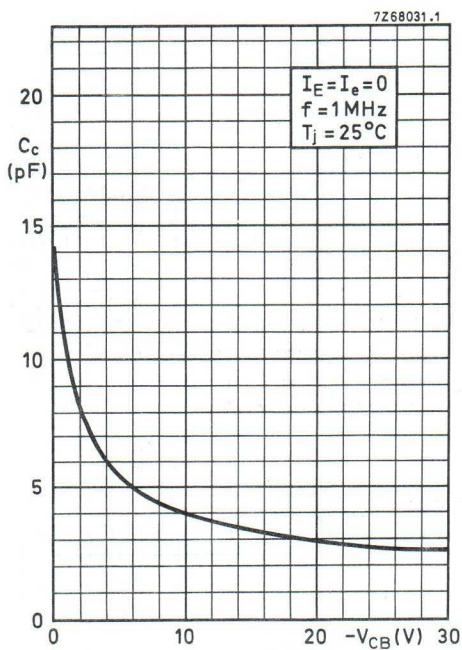


Fig. 9

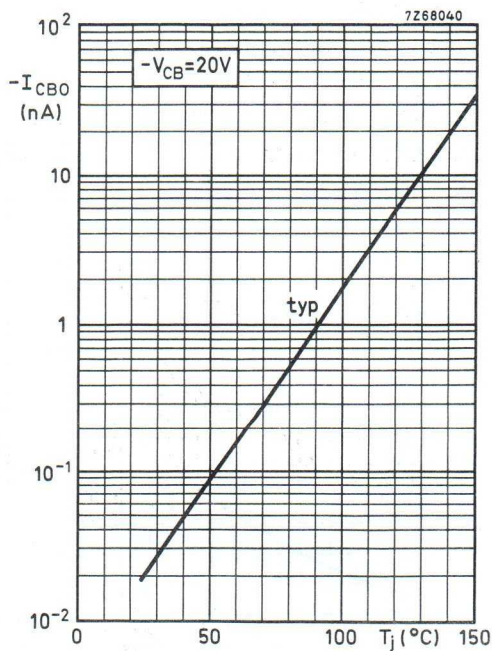


Fig. 10

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope. They are intended for low level, low noise general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

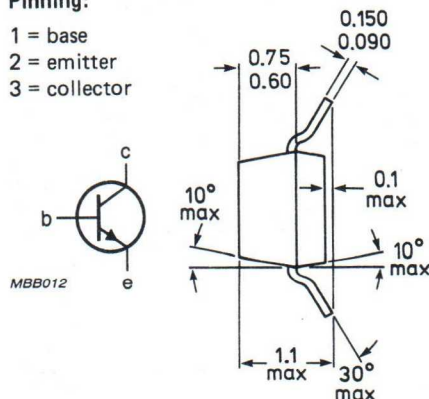
		BCF32	BCF33
D.C. current gain at $T_j = 25^\circ\text{C}$ $I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$	h_{FE}	$\begin{matrix} > 200 \\ < 450 \end{matrix}$	$\begin{matrix} 420 \\ 800 \end{matrix}$
Collector-base voltage (open emitter)	V_{CBO}	max. 32	V
Collector-emitter voltage (open base)	V_{CEO}	max. 32	V
Collector current (peak value)	I_{CM}	max. 200	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max. 250	mW
Junction temperature	T_j	max. 150	$^\circ\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ. 300	MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$	F	< 4	dB

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

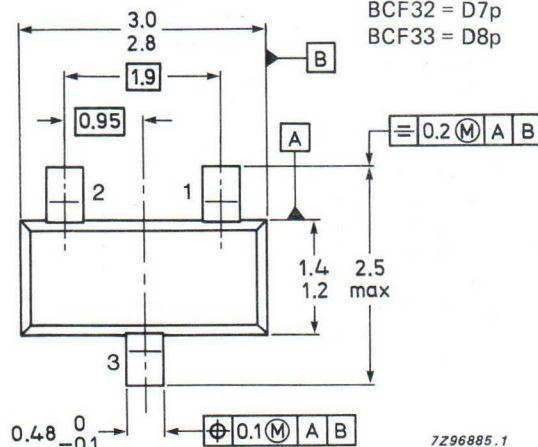
- 1 = base
2 = emitter
3 = collector



Dimensions in mm

Marking code

BCF32 = D7p
BCF33 = D8p



7Z96885.1

Reverse pinning types are available on request.
See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	32 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	32 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}^{**}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	-65 to + 150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th \text{ j-a}} = 500 \text{ K/W}$$

CHARACTERISTICS

$T_j = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$$I_E = 0; V_{CB} = 32 \text{ V}$$

$$I_E = 0; V_{CB} = 32 \text{ V}; T_j = 100 \text{ }^{\circ}\text{C}$$

I_{CBO}	<	100 nA
I_{CBO}	<	10 μA

Base-emitter voltage

$$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$$

$$V_{BE} \quad 550 \text{ to } 700 \text{ mV}$$

Saturation voltages

$$I_C = 10 \text{ mA}; I_B = 0,5 \text{ mA}$$

V_{CEsat}	typ.	120 mV
	<	250 mV

$$I_C = 50 \text{ mA}; I_B = 2,5 \text{ mA}$$

V_{BEsat}	typ.	750 mV
V_{CEsat}	typ.	210 mV
V_{BEsat}	typ.	850 mV

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$I_C = 10 \mu\text{A}; V_{CE} = 5 \text{ V}$$

$$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$I_C = 200 \mu\text{A}; V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

		BCF32	BCF33
h_{FE}	typ.	150	270
	$>$	200	420
h_{FE}	$<$	450	800
C_c	typ.	2,5 pF	
f_T	typ.	300 MHz	
F	$<$	4 dB	
	typ.	1,2 dB	

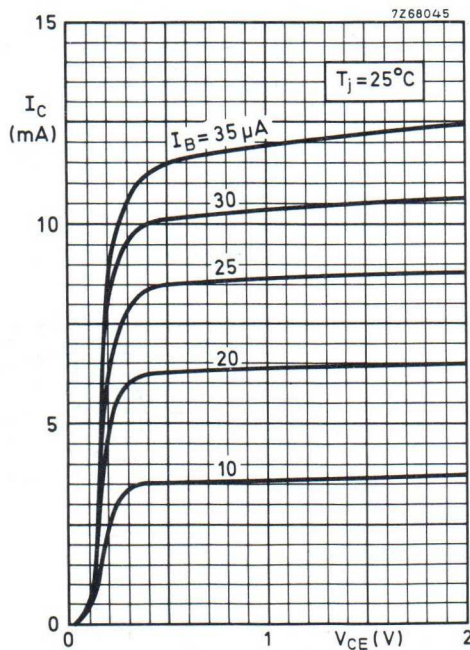


Fig. 2

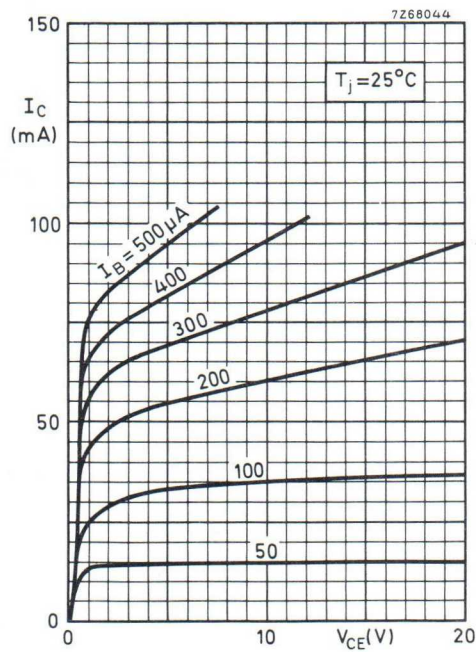


Fig. 3

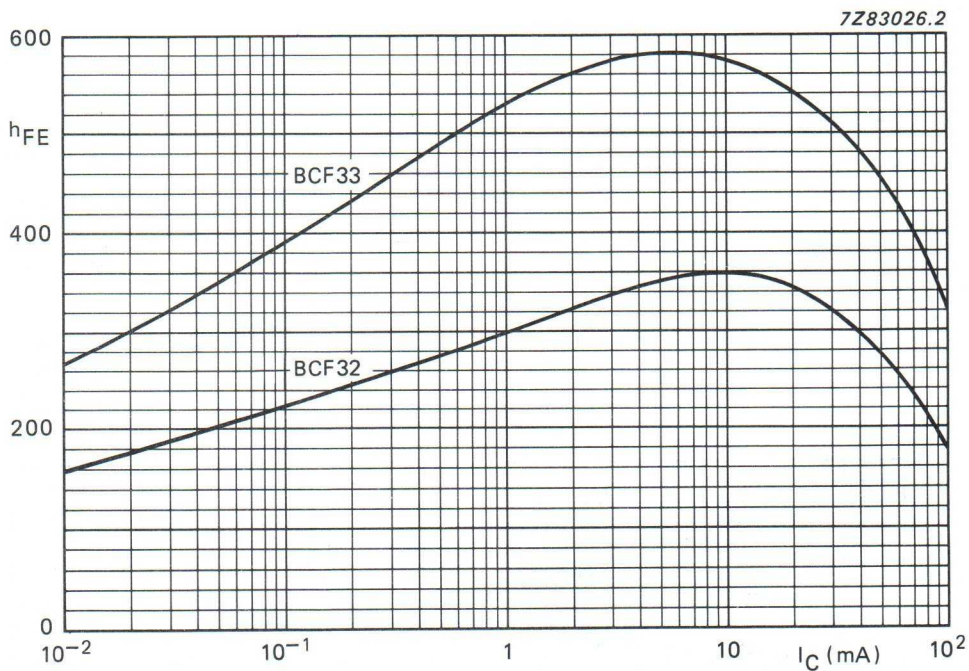


Fig. 4 Typical values d.c. current gain. $V_{CE} = 5\text{ V}$; $T_j = 25^\circ\text{C}$.

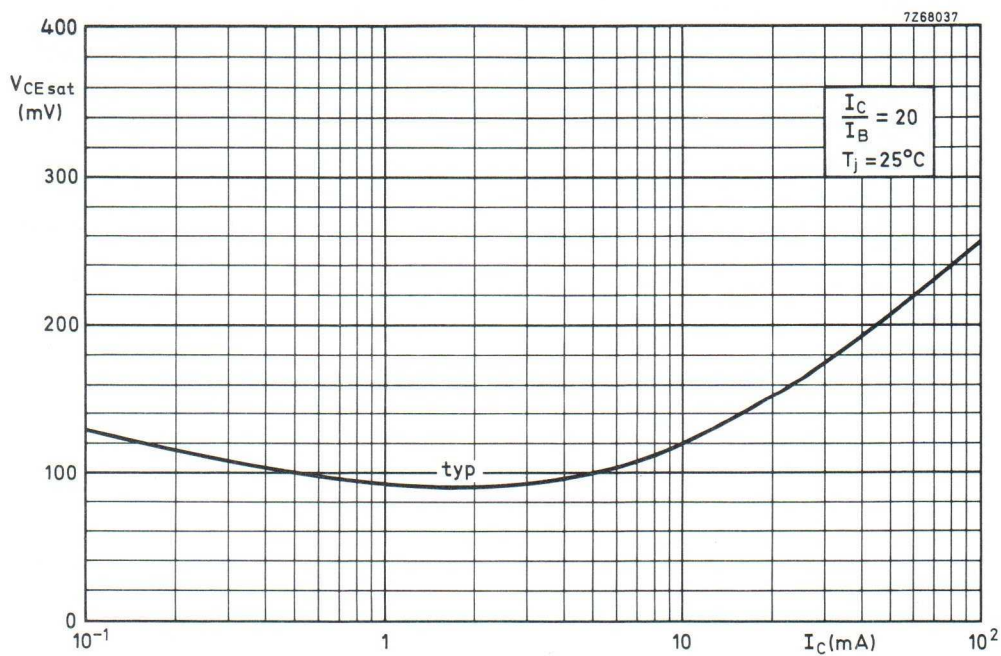


Fig. 5

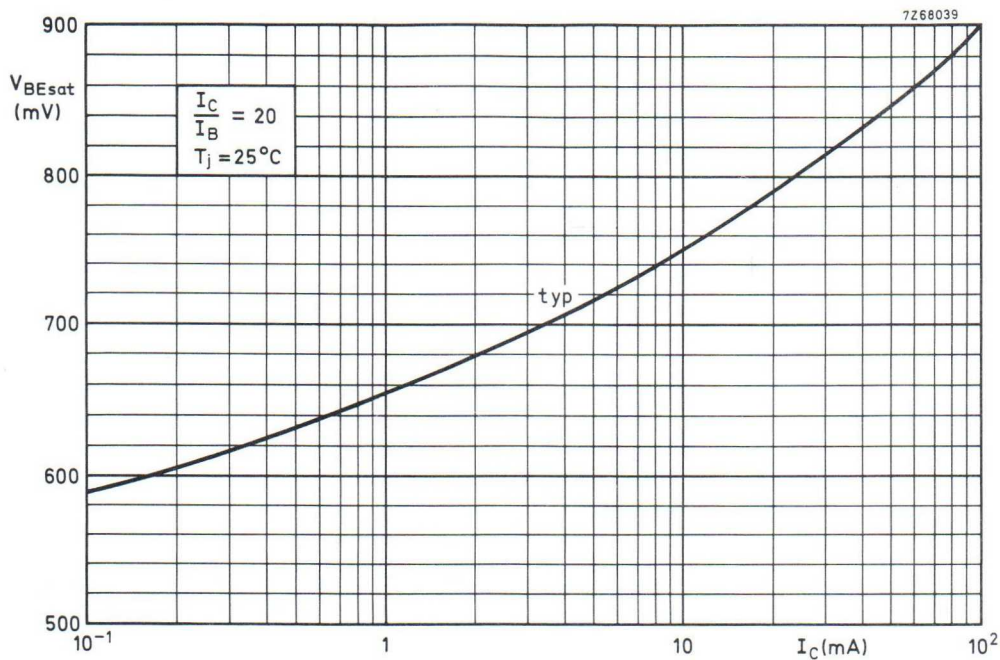


Fig. 6

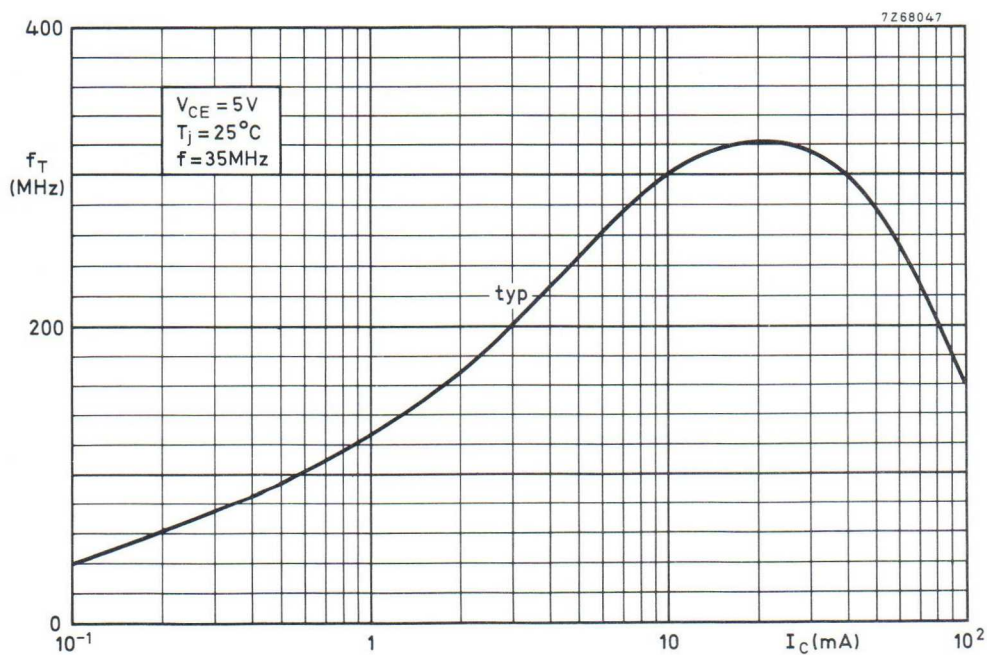


Fig. 7

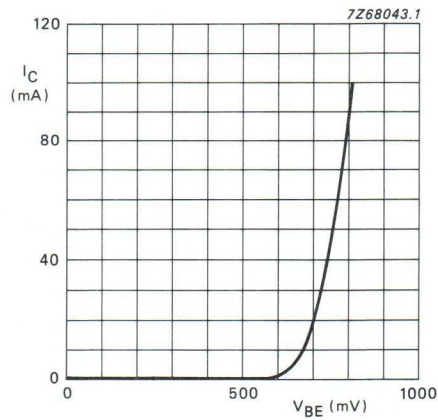


Fig. 8 $V_{CE} = 5$ V; $T_j = 25$ °C; typical values.

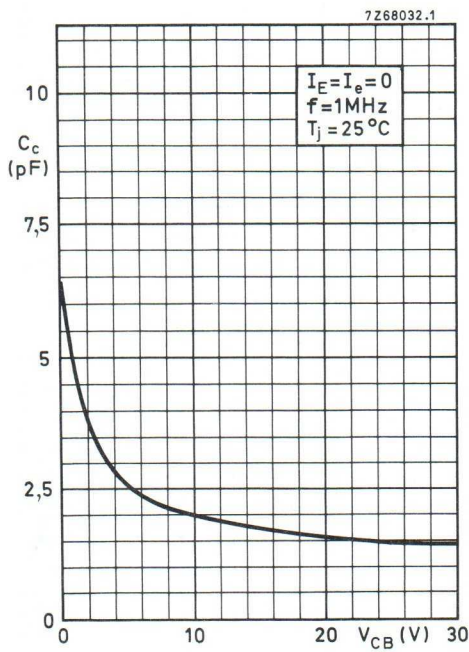


Fig. 9

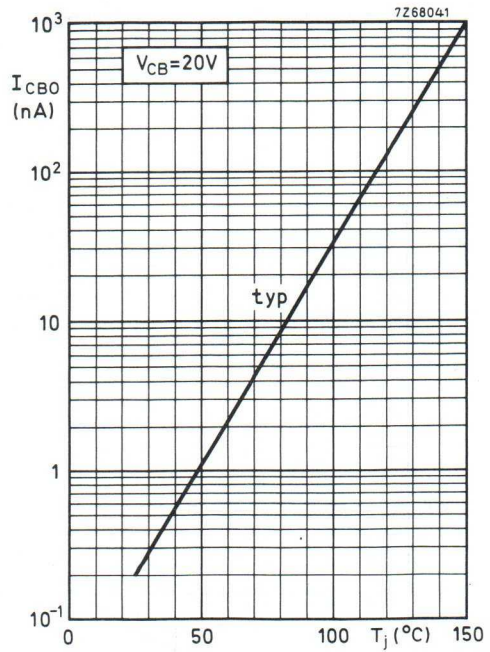


Fig. 10

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level, low noise applications in thick and thin-film circuits.

QUICK REFERENCE DATA

D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$

$-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$

h_{FE}	$>$	215
	$<$	500

Collector-base voltage (open emitter)

$-V_{CBO}$	max.	50 V
------------	------	------

Collector-emitter voltage (open base)

$-V_{CEO}$	max.	45 V
------------	------	------

Collector current (peak value)

$-I_{CM}$	max.	200 mA
-----------	------	--------

Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$

P_{tot}	max.	250 mW
-----------	------	--------

Junction temperature

T_j	max.	150 $^{\circ}\text{C}$
-------	------	------------------------

Transition frequency at $f = 35\text{ MHz}$

$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$

f_T	typ.	150 MHz
-------	------	---------

Noise figure at $R_S = 2\text{ k}\Omega$

$-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V};$

$f = 1\text{ kHz}; B = 200\text{ Hz}$

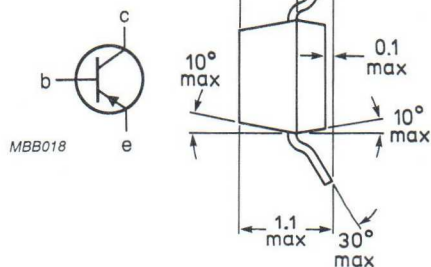
F	$<$	4 dB
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MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

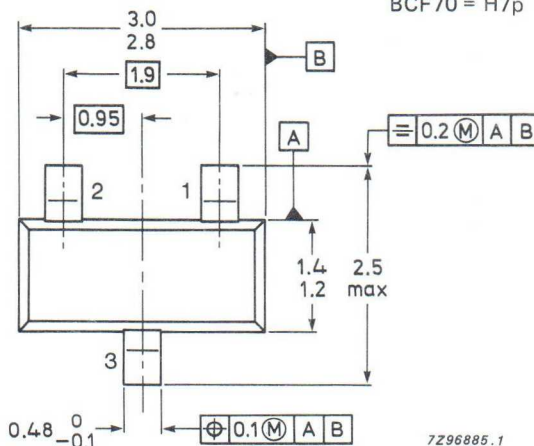
- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm

Marking code

BCF70 = H7p



TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	50 V
Collector-emitter voltage (open base) $-I_C = 2$ mA	$-V_{CEO}$	max.	45 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*

$$R_{th\ j-a} = 500\ K/W$$

CHARACTERISTICS $T_j = 25$ °C unless otherwise specified $I_E = 0$; $-V_{CB} = 20$ V; $T_j = 25$ °C $T_j = 100$ °C

$$-I_{CBO} < 100\ nA$$

$$-I_{CBO} < 10\ \mu A$$

Base-emitter voltage

 $-I_C = 2$ mA; $-V_{CE} = 5$ V; $T_j = 25$ °C

$$-V_{BE} \quad 600\ \text{to}\ 750\ mV$$

Saturation voltages

 $-I_C = 10$ mA; $-I_B = 0,5$ mA

$$-V_{CEsat} \quad \begin{matrix} \text{typ.} & 80\ mV \\ < & 300\ mV \end{matrix}$$

$$-V_{BEsat} \quad \text{typ.} \quad 720\ mV$$

$$-V_{CEsat} \quad \text{typ.} \quad 150\ mV$$

$$-V_{BEsat} \quad \text{typ.} \quad 810\ mV$$

 $-I_C = 50$ mA; $-I_B = 2,5$ mA

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$-I_C = 10 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

$$h_{FE} \quad \text{typ.} \quad 150$$

$$h_{FE} \quad > \quad 215$$

$$h_{FE} \quad < \quad 500$$

$$C_c \quad \text{typ.} \quad 4,5 \text{ pF}$$

$$f_T \quad \text{typ.} \quad 150 \text{ MHz}$$

$$F \quad < \quad 4 \text{ dB}$$

$$\text{typ.} \quad 1 \text{ dB}$$

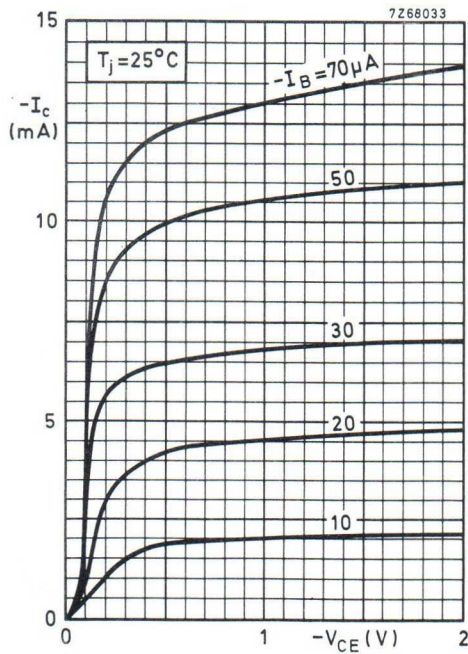


Fig. 2

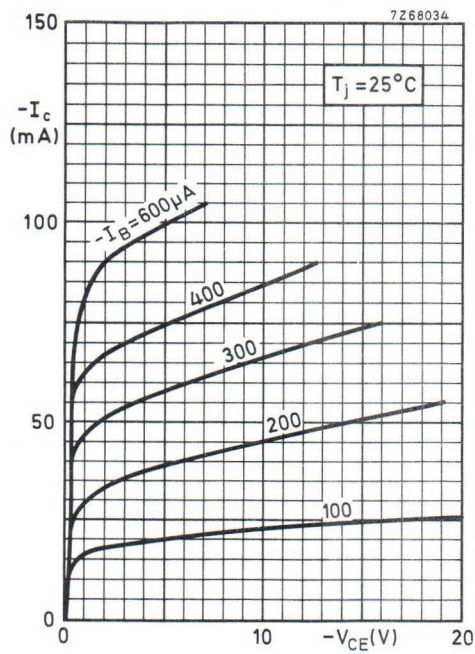


Fig. 3

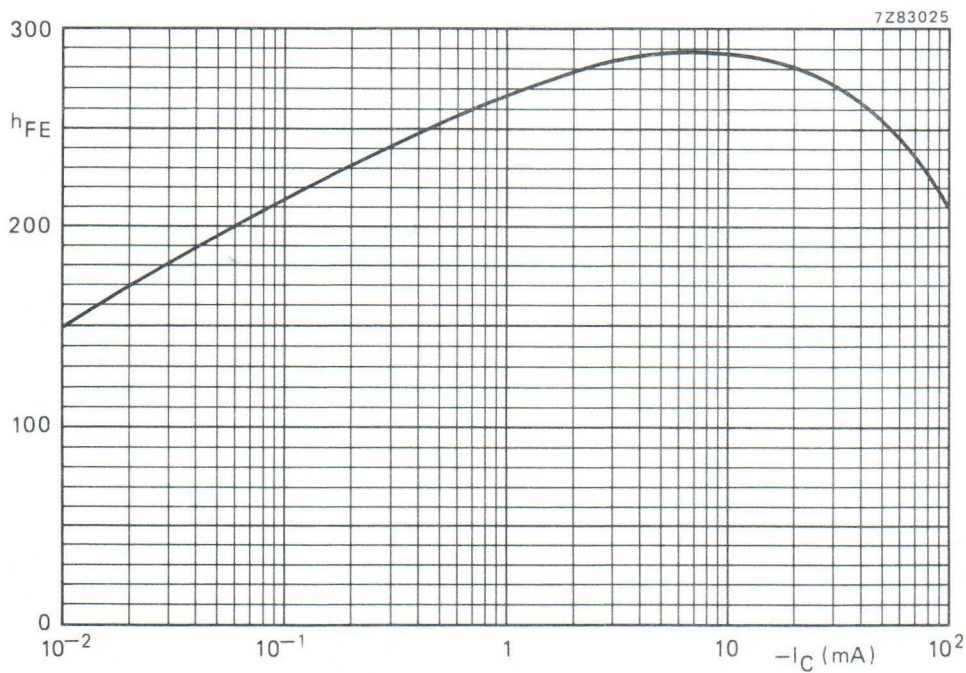


Fig. 4 Typical values of d.c. current gain. $-V_{CE} = 5$ V; $T_j = 25^\circ\text{C}$.

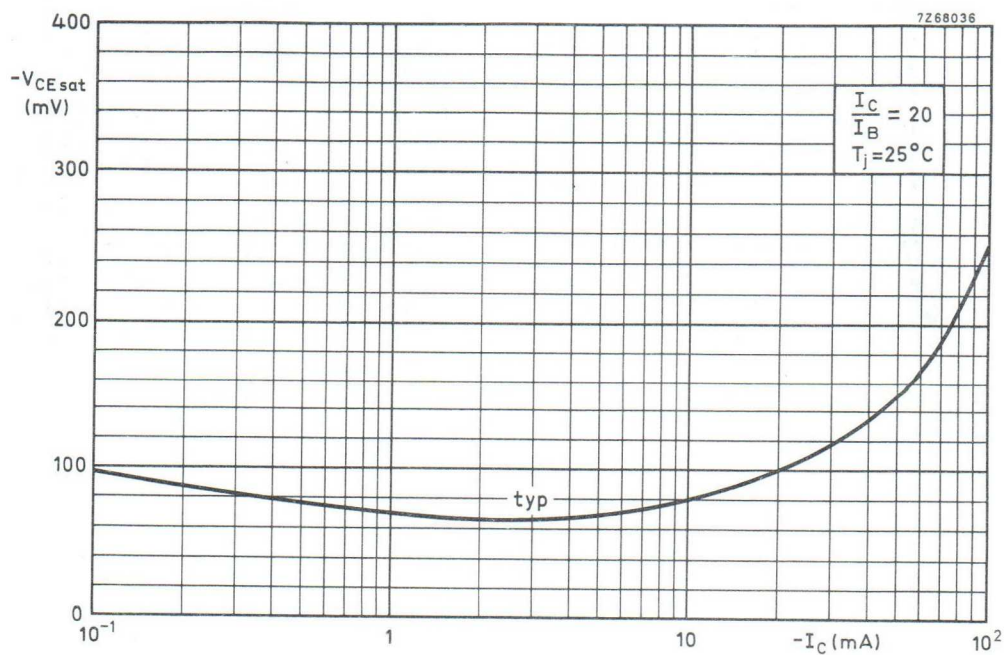


Fig. 5

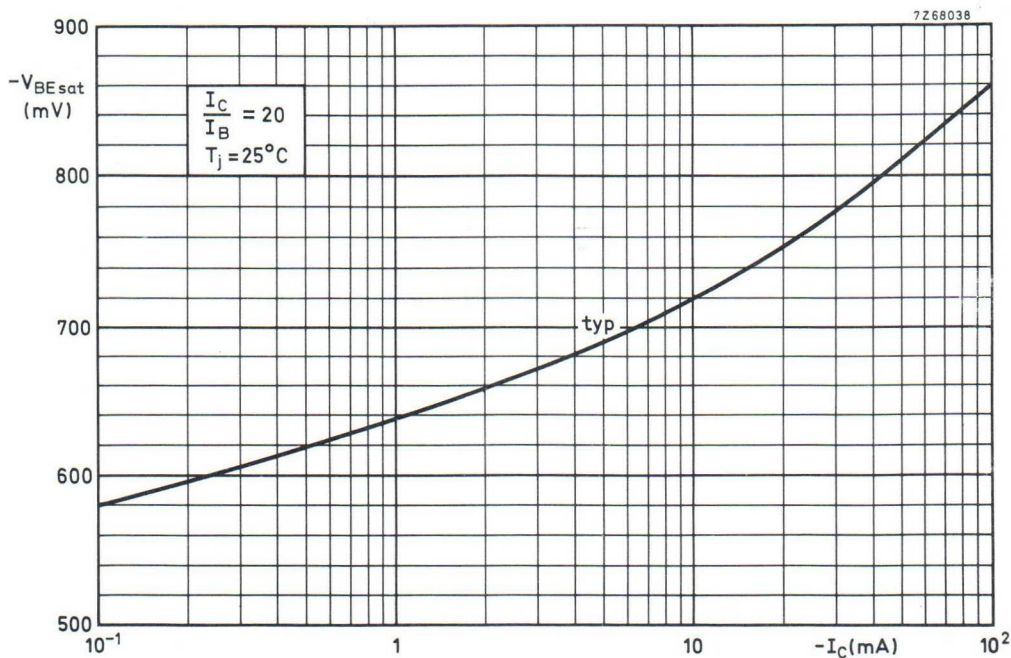


Fig. 6

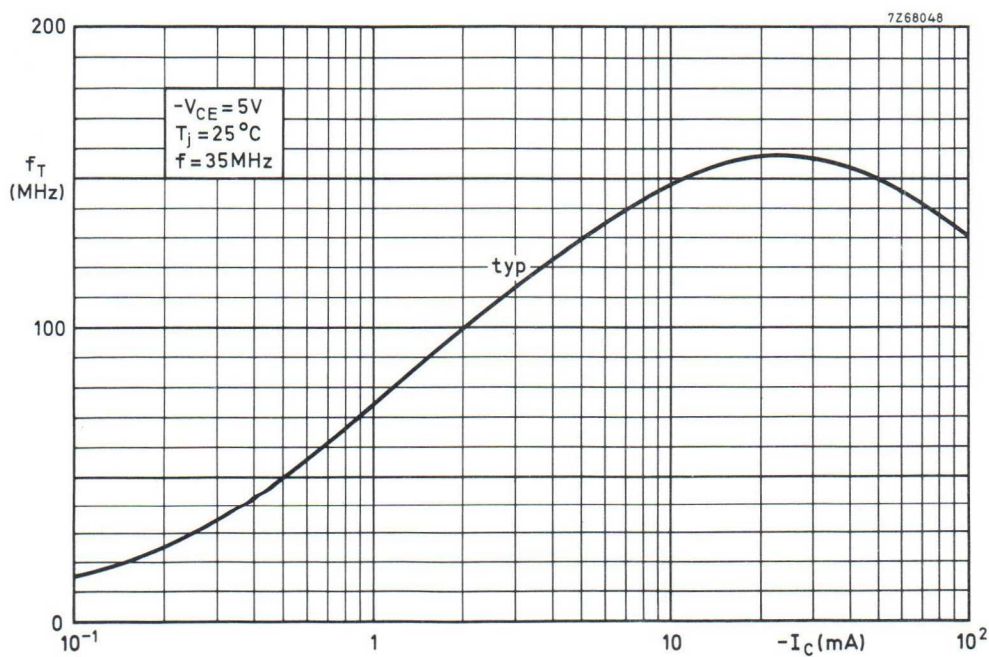


Fig. 7

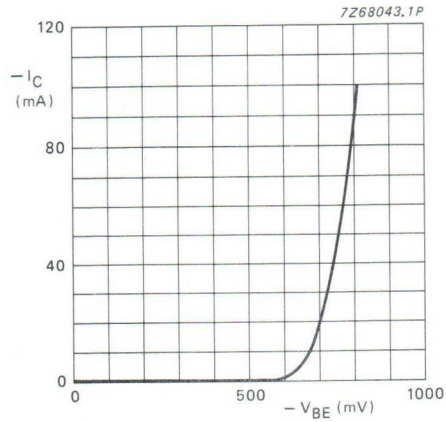


Fig. 8 $-V_{CE} = 5$ V; $T_j = 25^\circ\text{C}$; typical values.

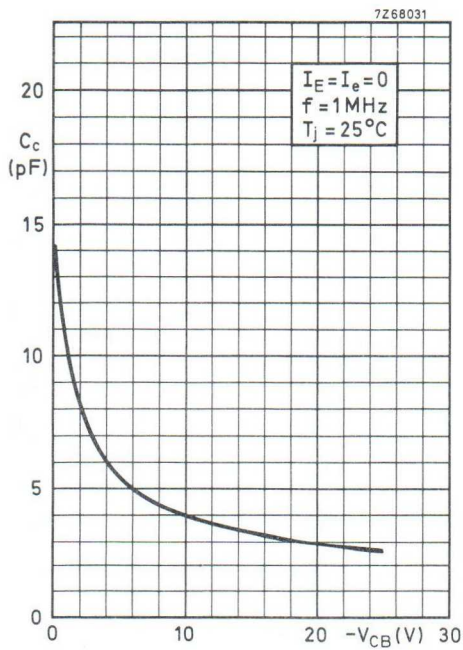


Fig. 9

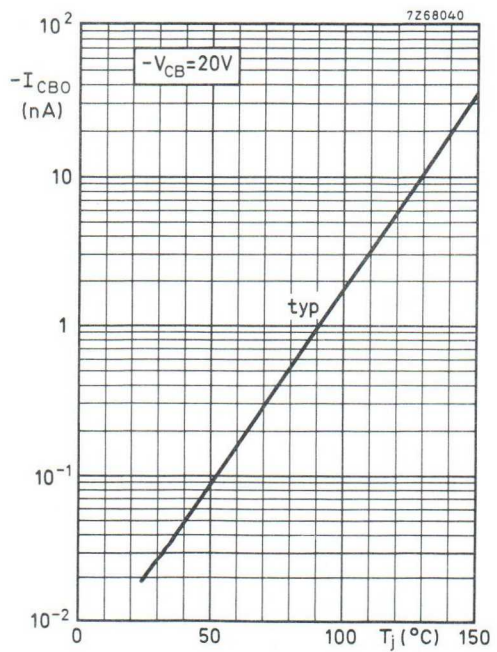


Fig. 10

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level, low noise general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45 V
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$ $I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$	h_{FE}	>	420
		<	800
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ.	300 MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$	F	<	4 dB

MECHANICAL DATA

Fig. 1 SOT-23.

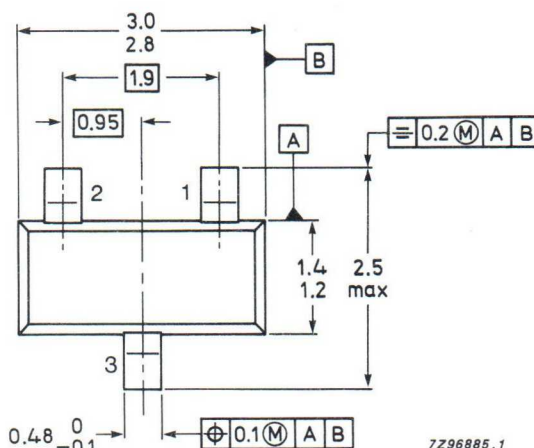
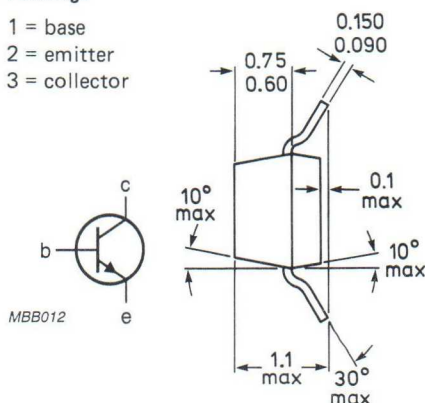
Dimensions in mm

Marking code

BCF81 = K9p

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	45 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}^{**}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		$-65 \text{ to } +150 \text{ }^\circ\text{C}$
Junction temperature	T_j	max.	150 $^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	500 K/W
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CHARACTERISTICS $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

 $I_E = 0; V_{CB} = 20 \text{ V}$ $I_{CBO} < 100 \text{ nA}$ $I_E = 0; V_{CB} = 20 \text{ V}; T_j = 100 \text{ }^\circ\text{C}$ $I_{CBO} < 10 \text{ } \mu\text{A}$

Base emitter voltage

 $I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$ $V_{BE} \quad 550 \text{ to } 700 \text{ mV}$

Saturation voltages

 $I_C = 10 \text{ mA}; I_B = 0,5 \text{ mA}$

V_{CEsat}	typ.	120 mV
	<	250 mV

 $I_C = 50 \text{ mA}; I_B = 2,5 \text{ mA}$

V_{BEsat}	typ.	750 mV
V_{CEsat}	typ.	210 mV
V_{BEsat}	typ.	850 mV

D.C. current gain

 $I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

h_{FE}	>	420
	<	800

Collector capacitance at $f = 1 \text{ MHz}$ $I_E = I_e = 0; V_{CB} = 10 \text{ V}$ $C_c \quad \text{typ.} \quad 2,5 \text{ pF}$ Transition frequency at $f = 35 \text{ MHz}$ $I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$ $f_T \quad \text{typ.} \quad 300 \text{ MHz}$ Noise figure at $R_S = 2 \text{ k}\Omega$ $I_C = 200 \text{ } \mu\text{A}; V_{CE} = 5 \text{ V}$ $f = 1 \text{ kHz}; B = 200 \text{ Hz}$

F	<	4 dB
	typ.	1,2 dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCP51	BCP52	BCP53
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	45	60	100 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	60	80 V
Collector-emitter voltage ($R_{BE} = 1 \text{ k}\Omega$)	$-V_{CER}$	max.	45	60	100 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5 V
Collector current (DC)	$-I_C$	max.		1,0	A
Collector current (peak value)	$-I_{CM}$	max.		1,5	A
Base current (DC)	$-I_B$	max.		0,1	A
Base current (peak value)	$-I_{BM}$	max.		0,2	A
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}^*$	P_{tot}	max.		1,5	W
Storage temperature range	T_{stg}			-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.		150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to collector tab	$R_{th j-tab}$	=		10	K/W
From junction to ambient*	$R_{th j-a}$	=		83,3	K/W

CHARACTERISTICS

 $T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current					
$I_E = 0; -V_{CB} = 30 \text{ V}$	$-I_{CBO}$	<		100	nA
$I_E = 0; -V_{CB} = 30 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	$-I_{CBO}$	<		10	μA
Emitter cut-off current					
$I_C = 0; -V_{EB} = 5 \text{ V}$	$-I_{EBO}$	<		10	μA
Base-emitter voltage					
$-I_C = 500 \text{ mA}; -V_{CE} = 2 \text{ V}$	$-V_{BE}$	<		1	V
Saturation voltage					
$-I_C = 500 \text{ mA}; -I_B = 50 \text{ mA}$	$-V_{CEsat}$	<		0,5	V
DC current gain					
$-I_C = 5 \text{ mA}; -V_{CE} = 2 \text{ V}$	h_{FE}	>		25	
$-I_C = 150 \text{ mA}; -V_{CE} = 2 \text{ V}$	h_{FE}			40 to 250	
$-I_C = 500 \text{ mA}; -V_{CE} = 2 \text{ V}$	h_{FE}	>		25	
Transition frequency at $f = 35 \text{ MHz}$					
$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	f_T	typ.		50	MHz

* Device mounted on an epoxy printed circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

CHARACTERISTICS (continued)

DC current gain

 $I_C = 150 \text{ mA}; -V_{CE} = 2 \text{ V}$ h_{FE}

>

<

BCP51-10	BCP51-16
52-10	52-16
53-10	53-16
63	100
160	250

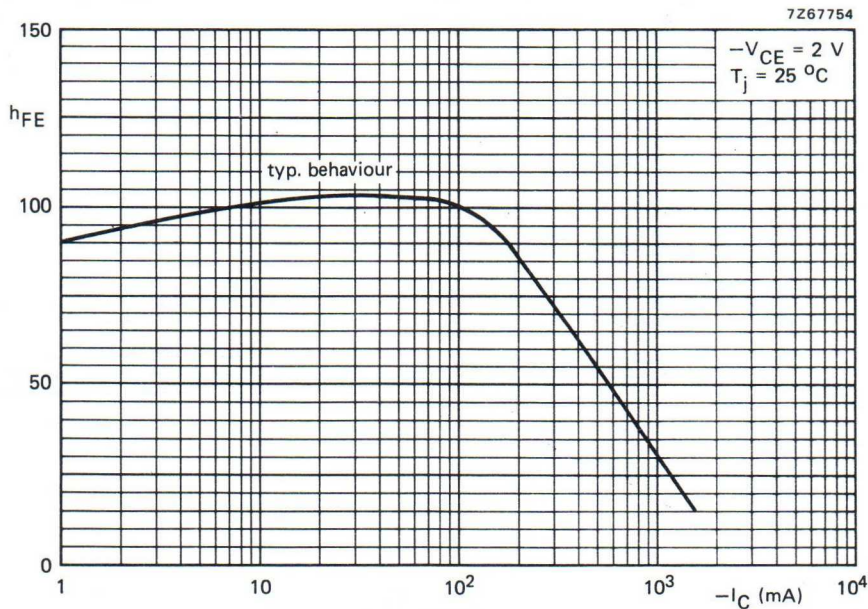
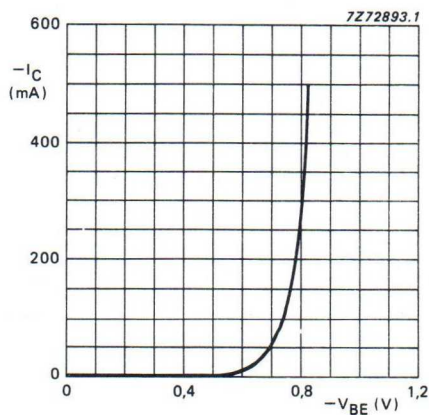


Fig. 2.

Fig. 3 $-V_{CE} = 2 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; typical values.

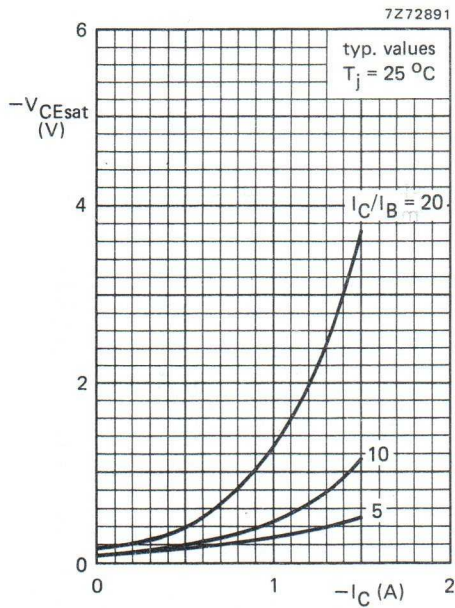


Fig. 4.

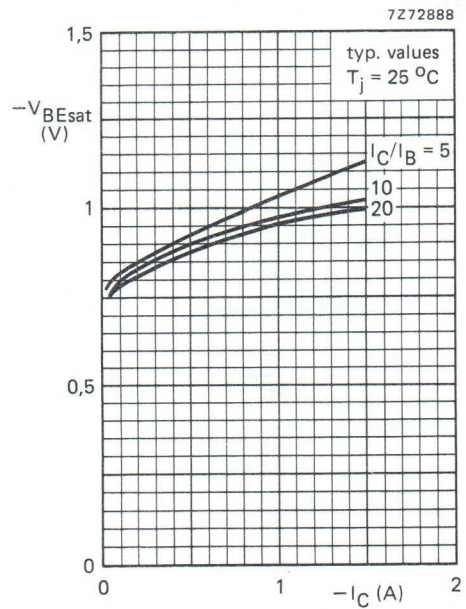


Fig. 5.

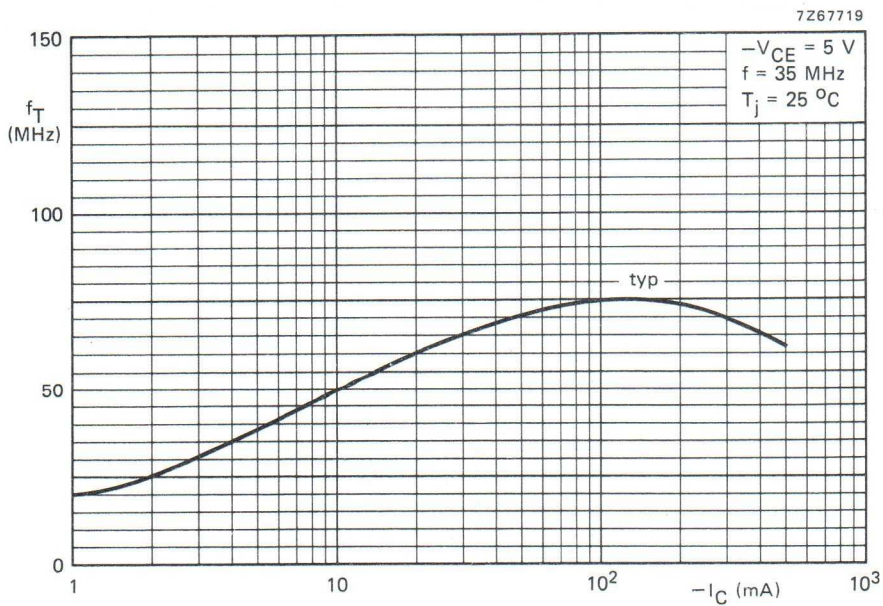


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTORS

Medium power npn transistors in a miniature plastic envelope intended for applications in thick and thin-film circuits. They are general purpose transistors, primarily designed for audio amplifier output stages.

PNP complements are BCP51, BCP52 and BCP53 respectively.

QUICK REFERENCE DATA

	BCP54	BCP55	BCP56
Collector-base voltage (open emitter)	V_{CBO} max. 45	60	100 V
Collector-emitter voltage (open base)	V_{CEO} max. 45	60	80 V
Collector-emitter voltage ($R_{BE} = 1\text{ k}\Omega$)	V_{CER} max. 45	60	100 V
Collector current (peak value)	I_{CM} max.	1,5	A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot} max.	1,5	W
Junction temperature	T_j max.	150	$^{\circ}\text{C}$
DC current gain	h_{FE}	40 to 250	
Transition frequency at $f = 35\text{ MHz}$	f_T typ.	130	MHz
$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$			
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$			

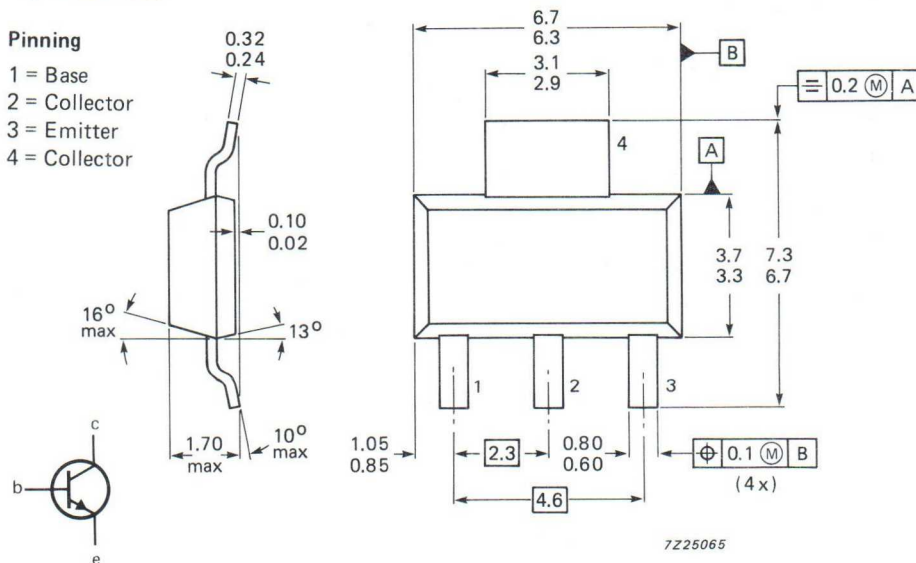
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter
- 4 = Collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCP54	BCP55	BCP56
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	100 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	60	80 V
Collector-emitter voltage ($R_{BE} = 1 \text{ k}\Omega$)	V_{CER}	max.	45	60	100 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	5 V
Collector current (DC)	I_C	max.		1,0	A
Collector current (peak value)	I_{CM}	max.		1,5	A
Base current (DC)	I_B	max.		0,1	A
Base current (peak value)	I_{BM}	max.		0,2	A
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}^*$	P_{tot}	max.		1,5	W
Storage temperature range	T_{stg}		-65 to +150		$^\circ\text{C}$
Junction temperature	T_j	max.		150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	83,3	K/W
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CHARACTERISTICS

 $T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current					
$I_E = 0; V_{CB} = 30 \text{ V}$	I_{CBO}	<		100	nA
$I_E = 0; V_{CB} = 30 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	I_{CBO}	<		10	μA
Emitter cut-off current					
$I_C = 0; V_{EB} = 5 \text{ V}$	I_{EBO}	<		10	μA
Base-emitter voltage					
$I_C = 500 \text{ mA}; V_{CE} = 2 \text{ V}$	V_{BE}	<		1	V
Saturation voltage					
$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	V_{CEsat}	<		0,5	V
DC current gain					
$I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}$	h_{FE}	>		25	
$I_C = 150 \text{ mA}; V_{CE} = 2 \text{ V}$	h_{FE}			40 to 250	
$I_C = 500 \text{ mA}; V_{CE} = 2 \text{ V}$	h_{FE}	>		25	
Transition frequency at $f = 35 \text{ MHz}$					
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	f_T	typ.		130	MHz

* Device mounted on an epoxy printed circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

CHARACTERISTICS (continued)

DC current gain

 $I_C = 150 \text{ mA}; V_{CE} = 2 \text{ V}$ h_{FE}

>

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BCP54-10	BCP54-16
55-10	55-16
56-10	56-16
63	100
160	250

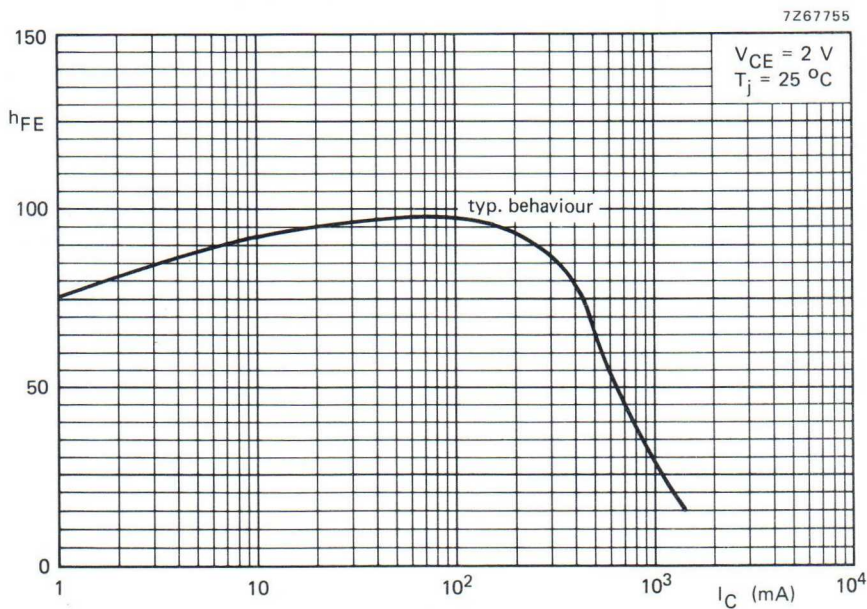
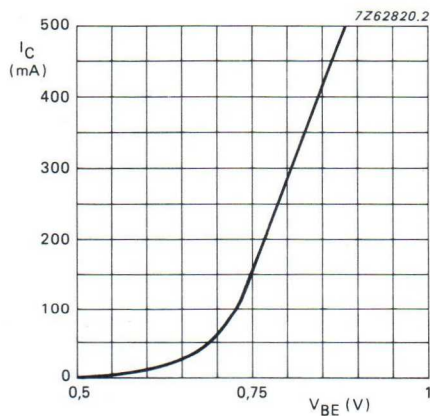


Fig. 2.

Fig. 3 $V_{CE} = 2 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; typical values.

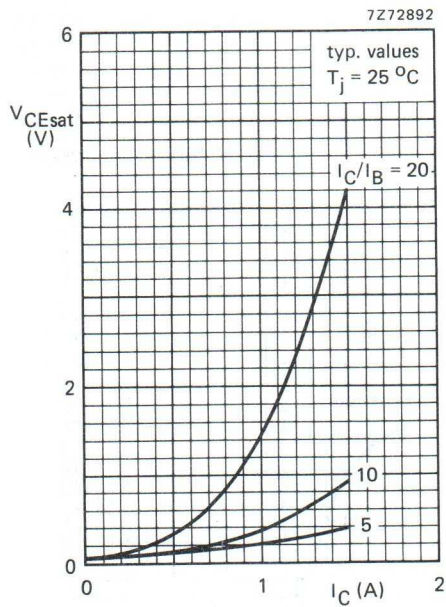


Fig. 4.

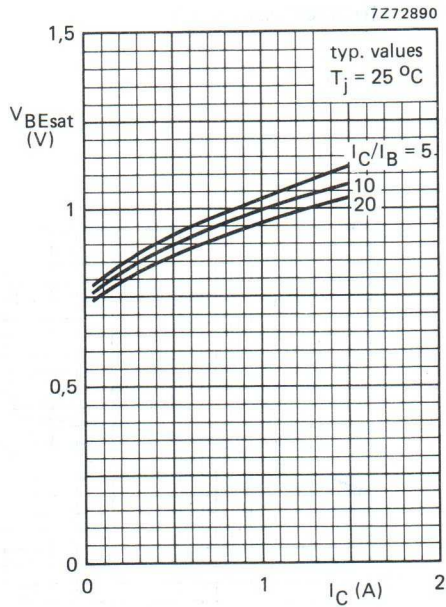


Fig. 5.

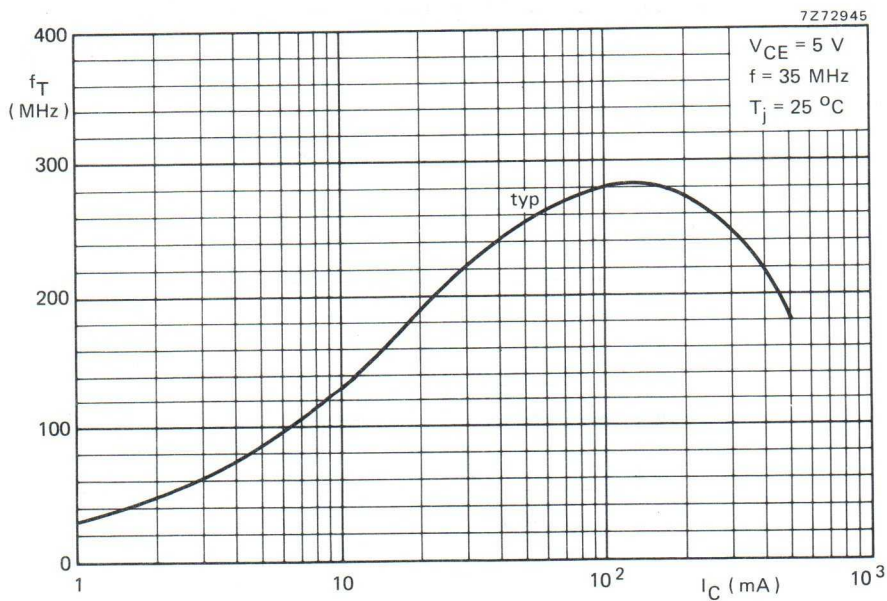


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTOR

NPN transistor in a microminiature plastic envelope intended for low-voltage, high-current LF applications.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	20 V
Collector current (peak value)	I_{CM}	max.	2 A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	1,5 W
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
DC current gain $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}		85 to 375
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	60 MHz

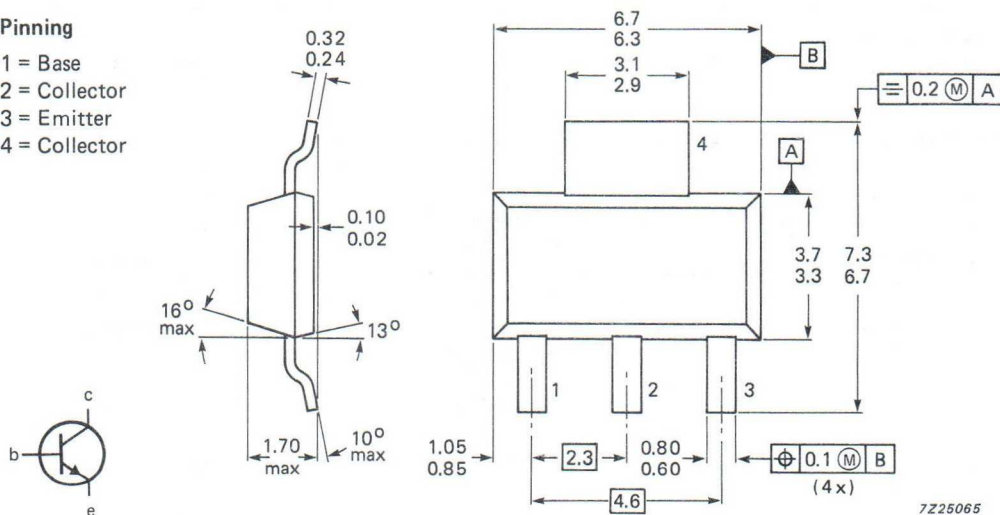
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter
- 4 = Collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	20 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (DC)	I_C	max.	1 A
Collector current (peak value)	I_{CM}	max.	2 A
Base current (DC)	I_B	max.	100 mA
Base current (peak value)	I_{BM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1,5 W
Storage temperature range	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j-a}$	=	83,3 K/W
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CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

 $I_E = 0; V_{CB} = 25\text{ V}$ $I_{CBO} < 10\text{ }\mu\text{A}$ $I_E = 0; V_{CB} = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$ $I_{CBO} < 1\text{ mA}$

Emitter cut-off current

 $I_C = 0; V_{EB} = 5\text{ V}$ $I_{EBO} < 10\text{ }\mu\text{A}$

Base-emitter voltage

 $I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$ V_{BE} typ. 0,62 V $I_C = 1\text{ A}; V_{CE} = 1\text{ V}$ $V_{BE} < 1\text{ V}$

Collector-emitter saturation voltage

 $I_C = 1\text{ A}; I_B = 100\text{ mA}$ $V_{CEsat} < 0,5\text{ V}$

DC current gain

 $I_C = 5\text{ mA}; V_{CE} = 10\text{ V}$ BCP68 $h_{FE} > 50$ $I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$ BCP68 h_{FE} 85 to 375BCP68-10 $h_{FE} \leq 160$ BCP68-16 h_{FE} 100 to 250BCP68-25 $h_{FE} \geq 250$ BCP68 $h_{FE} > 60$ $I_C = 1\text{ A}; V_{CE} = 1\text{ V}$ Collector capacitance at $f = 450\text{ kHz}$ $I_E = I_B = 0; V_{CB} = 5\text{ V}$ C_c typ. 27 pFTransition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$ f_T typ. 60 MHz

* Device mounted on an epoxy printed-circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

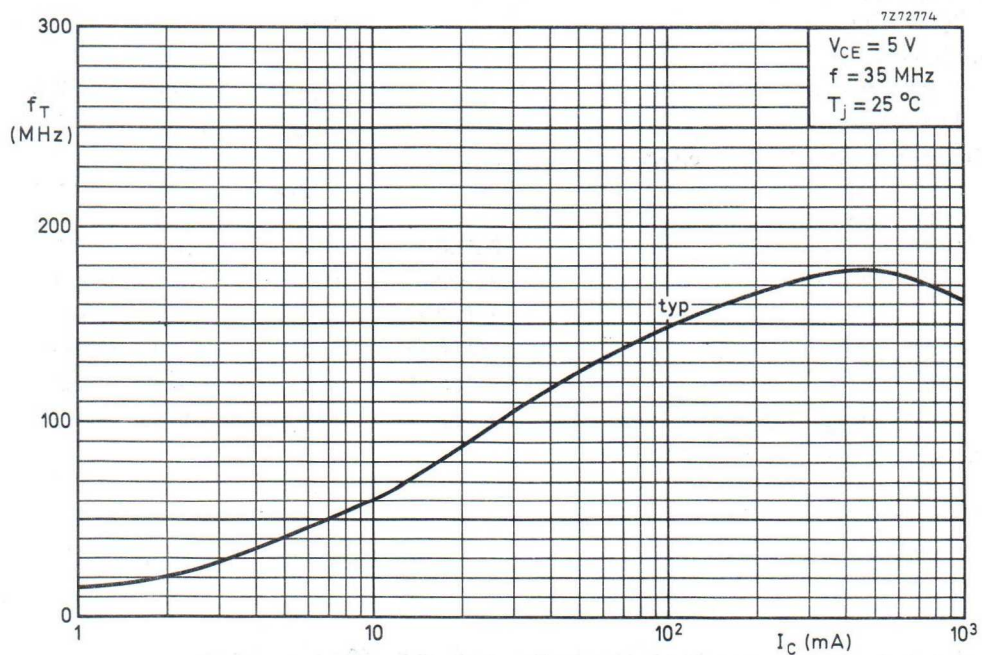
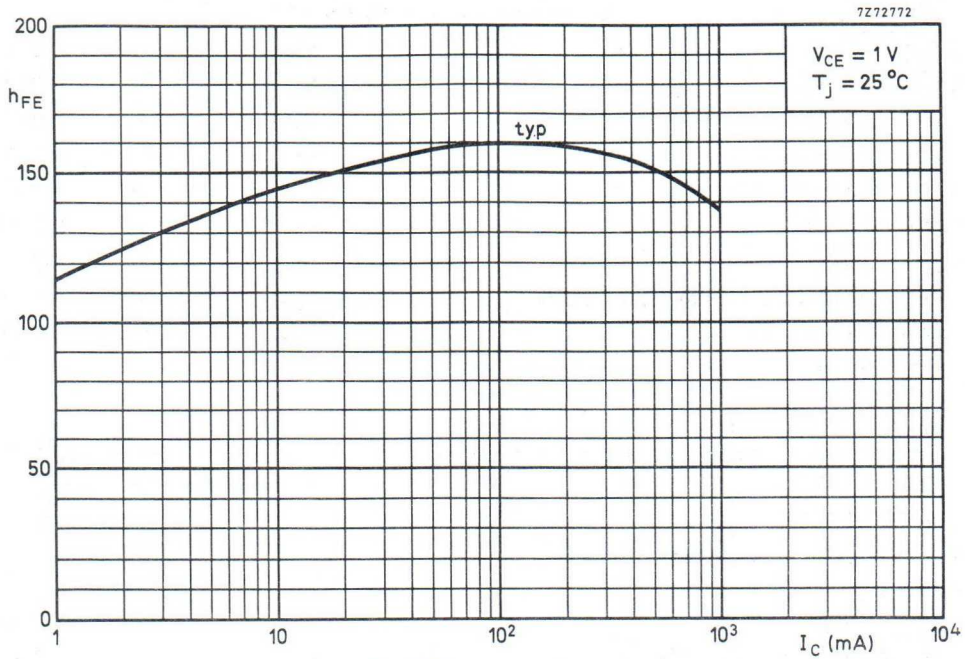


Fig.3 Typical values transition frequency as a function of collector current.

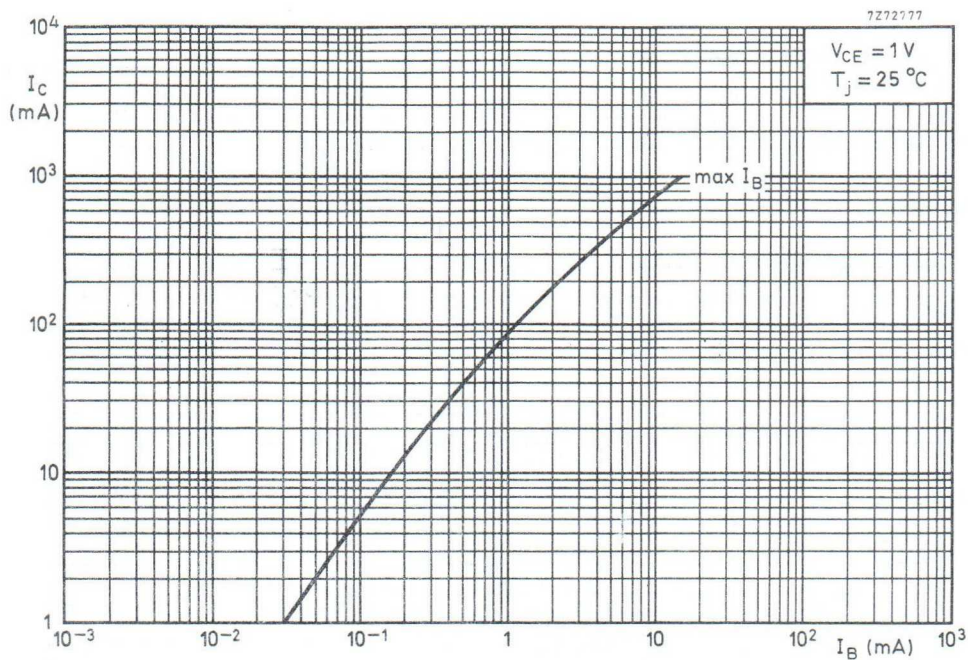


Fig.4 Typical values collector current as a function of maximum base current.

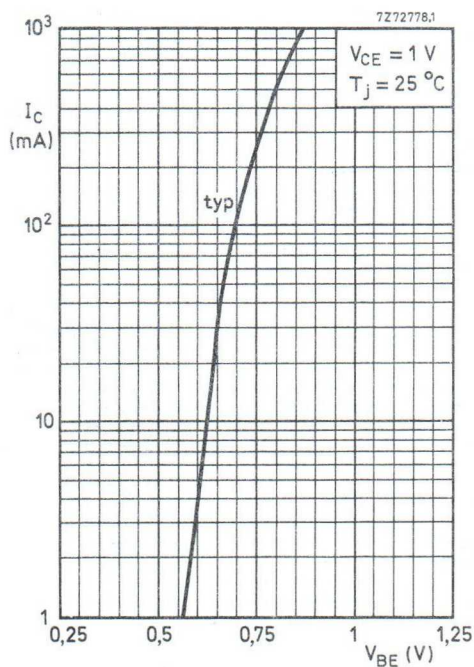


Fig.5 Typical values collector current as a function of base-emitter voltage.

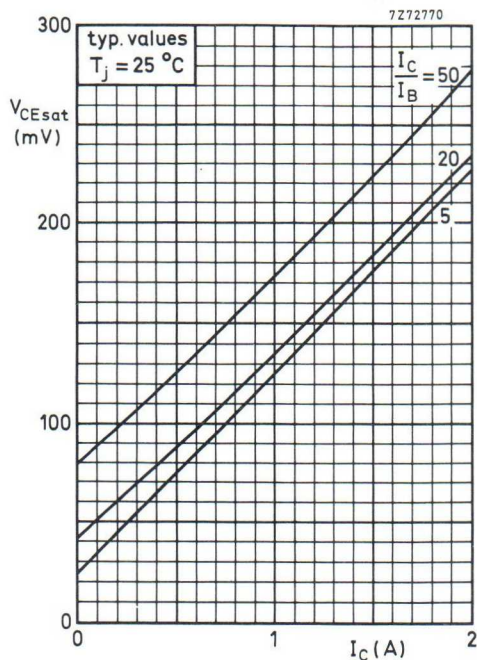


Fig.6 Collector-emitter saturation voltage as a function of collector current.

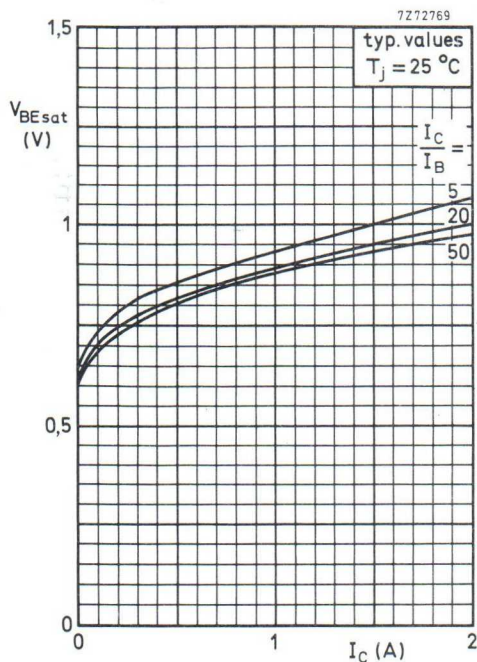
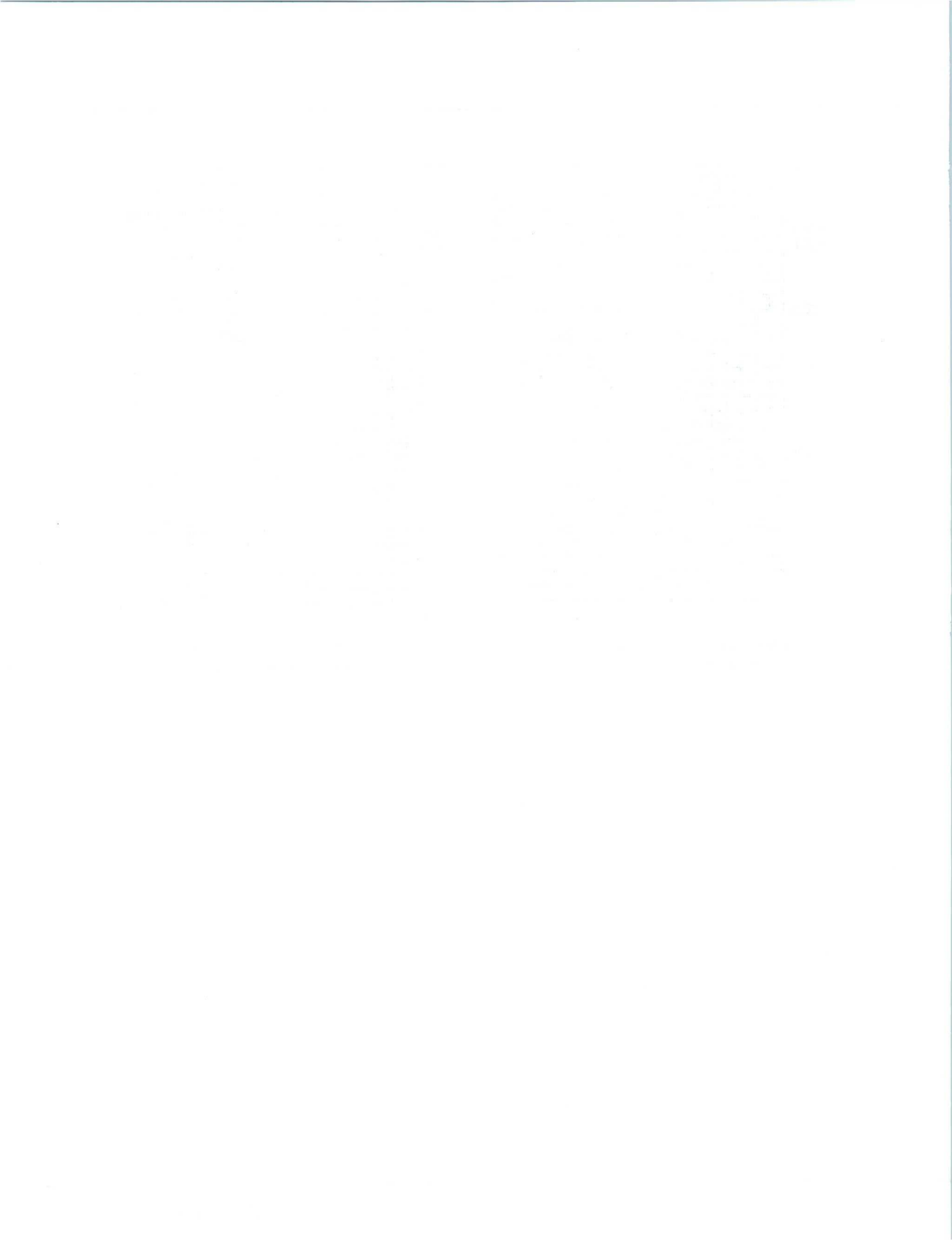


Fig.7 Base-emitter saturation voltage as a function of collector current.



SILICON PLANAR EPITAXIAL TRANSISTOR

PNP transistor in a plastic microminiature envelope, intended for low-voltage, high-current LF applications.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$ max.	25 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	20 V
Collector current (peak value)	$-I_{CM}$ max.	2 A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot} max.	1,5 W
Junction temperature	T_j max.	150 $^{\circ}\text{C}$
DC current gain	h_{FE}	85 to 375
Transition frequency at $f = 35\text{ MHz}$	f_T typ.	60 MHz
$-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$		
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$		

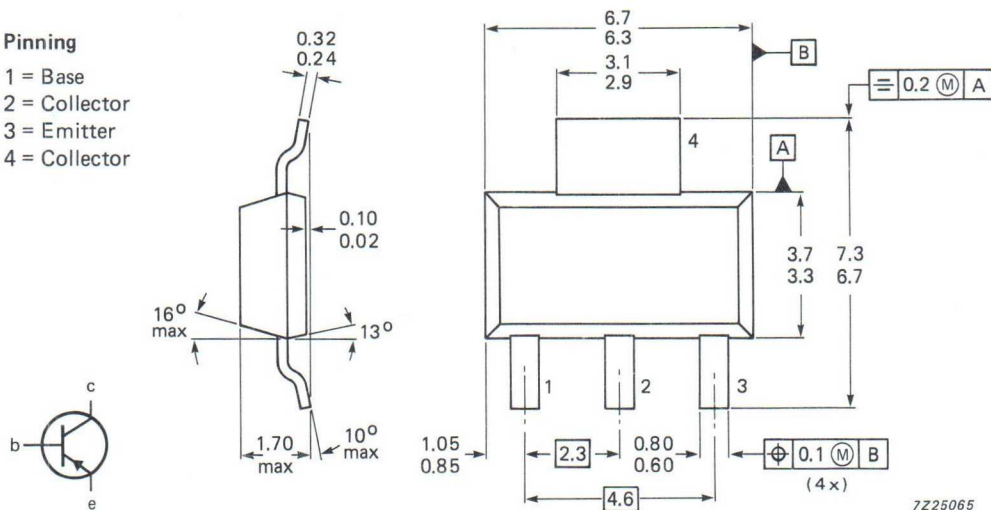
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter
- 4 = Collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	25 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (DC)	$-I_C$	max.	1 A
Collector current (peak value)	$-I_{CM}$	max.	2 A
Base current (DC)	$-I_B$	max.	100 mA
Base current (peak value)	$-I_{BM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1,5 W
Storage temperature range	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	83,3 K/W
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CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current			
$I_E = 0; -V_{CB} = 25\text{ V}$	$-I_{CBO}$	<	10 μA
$I_E = 0; -V_{CB} = 25\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	$-I_{CBO}$	<	1 mA
Emitter cut-off current			
$I_C = 0; -V_{EB} = 5\text{ V}$	$-I_{EBO}$	<	10 μA
Base-emitter voltage			
$-I_C = 5\text{ mA}; -V_{CE} = 10\text{ V}$	$-V_{BE}$	typ.	0,62 V
$-I_C = 1\text{ A}; -V_{CE} = 1\text{ V}$	$-V_{BE}$	<	1 V
Collector-emitter saturation voltage			
$-I_C = 1\text{ A}; -I_B = 100\text{ mA}$	$-V_{CEsat}$	<	0,5 V
DC current gain			
$-I_C = 5\text{ mA}; -V_{CE} = 10\text{ V}$	BCP69 h_{FE}	>	50
$-I_C = 500\text{ mA}; -V_{CE} = 1\text{ V}$	BCP69 h_{FE}		85 to 375
	BCP69-10 h_{FE}	$\leq$	160
	BCP69-16 h_{FE}		100 to 250
	BCP69-25 h_{FE}	$\geq$	250
	BCP69 h_{FE}	>	60
Collector capacitance at $f = 450\text{ kHz}$	C_c	typ.	45 pF
Transition frequency at $f = 35\text{ MHz}$	f_T	typ.	60 MHz

* Device mounted on an epoxy printed-circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

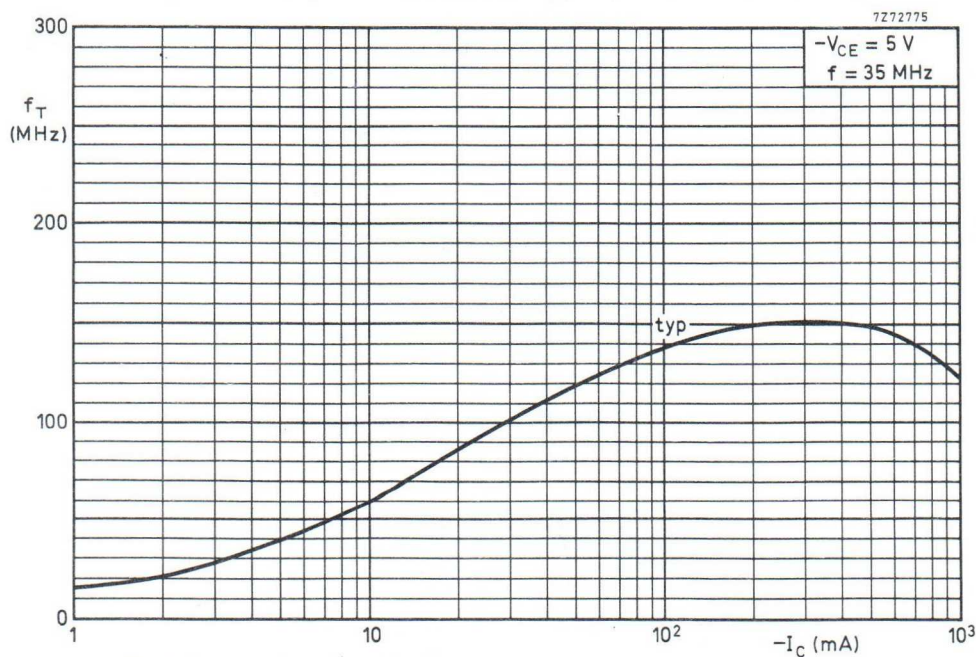
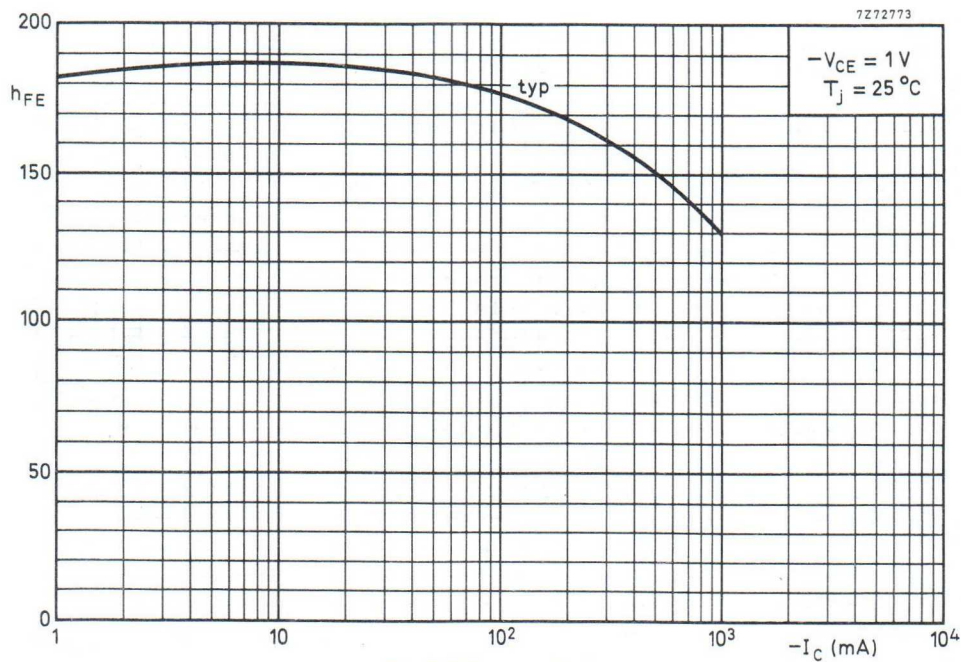


Fig.3 Typical values transition frequency as a function of collector current.

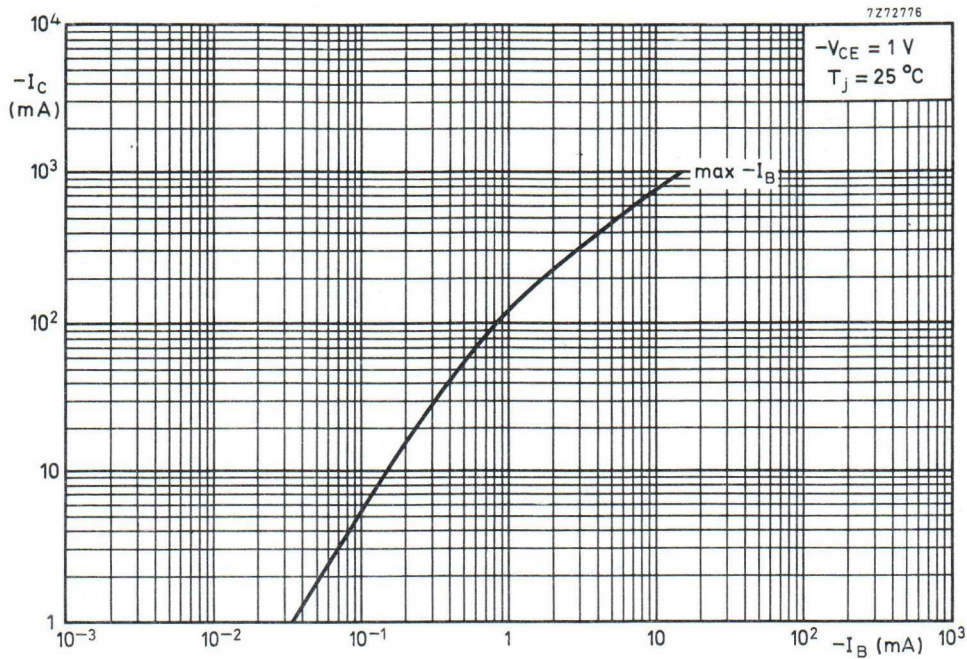


Fig.4 Typical values collector current as a function of maximum base current.

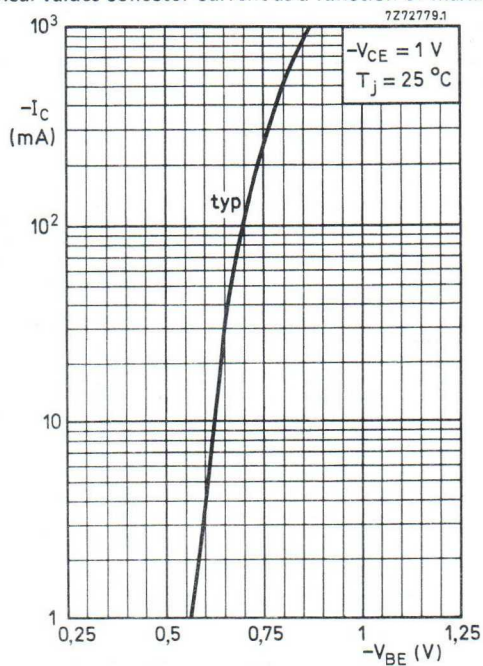


Fig.5 Typical values collector current as a function of base-emitter voltage.

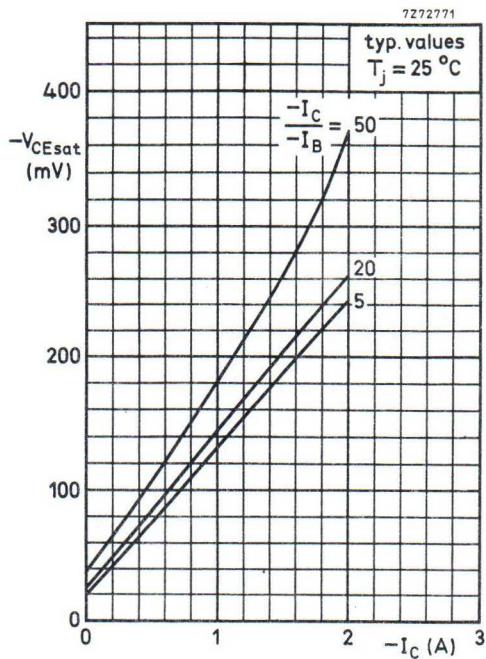


Fig.6 Collector-emitter saturation voltage as a function of collector current.

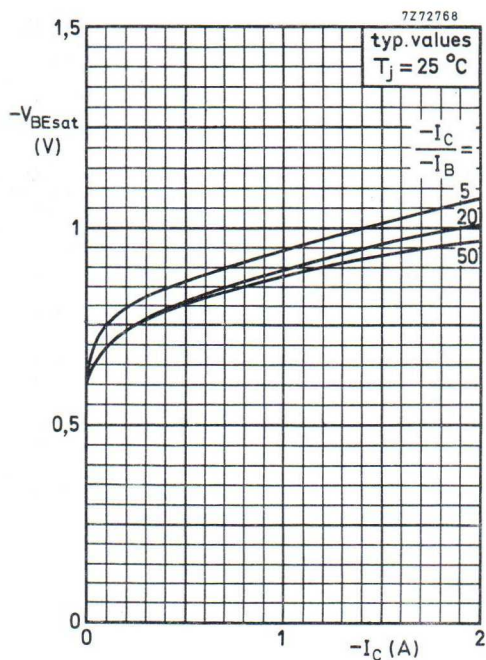


Fig.7 Base-emitter saturation voltage as a function of collector current.

SILICON PLANAR DARLINGTON TRANSISTOR

P-N-P silicon planar darlington transistor in a plastic SOT23 envelope.
N-P-N complement is BCV27/47.

QUICK REFERENCE DATA

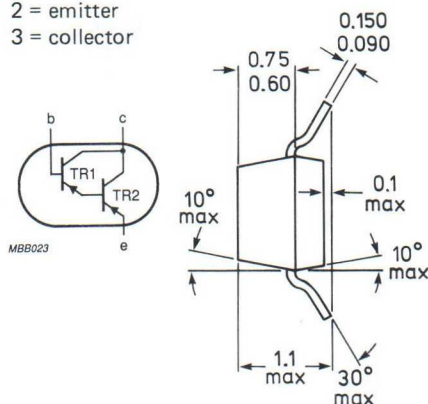
		BCV26	BCV46
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	30	60 V
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	40	80 V
Collector current	$-I_C$ max.	300	500 mA
DC current gain			
$-I_C = 1 \text{ mA}; -V_{CE} = 5 \text{ V}$	$h_{FE} >$	4 000	2 000
$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	$h_{FE} >$	10 000	4 000
$-I_C = 100 \text{ mA}; -V_{CE} = 5 \text{ V}$	$h_{FE} >$	20 000	10 000
Junction temperature	T_j max.	150	$^{\circ}\text{C}$
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	P_{tot} max.	250	mW
Collector-emitter saturation voltage			
$-I_C = 100 \text{ mA}; -I_B = 0.1 \text{ mA}$	$-V_{CEsat}$ max.	1.0	V
Transition frequency at $f = 100 \text{ MHz}$			
$-I_C = 30 \text{ mA}; -V_{CE} = 5 \text{ V}$	f_T typ.	220	MHz

MECHANICAL DATA

Fig. 1 SOT23

Pinning:

- 1 = base
2 = emitter
3 = collector

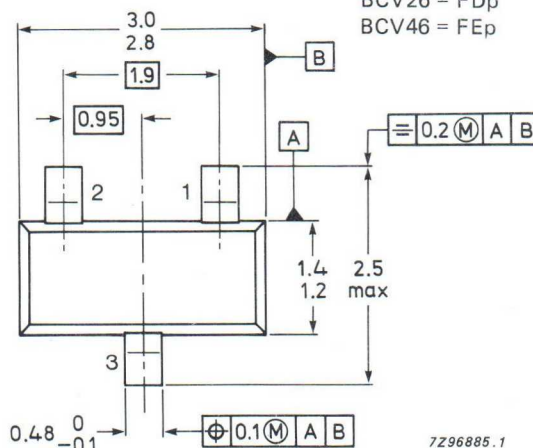


Dimensions in mm

Marking code:

BCV26 = FDp

BCV46 = FEp



TOP VIEW

7Z96885.1

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCV26	BCV46
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	60 V
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	80 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	10	10 V
Collector current	$-I_C$	max.	300	500 mA
Collector current (peak value)	$-I_{CM}$	max.	800	mA
Base current	$-I_B$	max.	100	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	250	mW
Storage temperature	T_s		-65 to +150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	max.	500	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

			BCV26	BCV46
Collector-base current				
$-V_{CBO} = 30\text{ V}$	$-I_{CBO}$	max.	0.1	0.1 μA
Emitter-base current				
$-V_{EB} = 10\text{ V}$	$-I_{EBO}$	max.	0.1	0.1 μA
Collector-emitter break-down voltage				
$-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	min.	30	60 V
Collector-base breakdown voltage				
$I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	min.	40	80 V
Emitter-base breakdown voltage				
$-I_E = 100\text{ nA}$	$-V_{(BR)EBO}$	min.	10	10 V
DC current gain				
$-I_C = 1\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	4 000	2 000
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	10 000	4 000
$-I_C = 100\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	20 000	10 000
Collector-emitter saturation voltage				
$-I_C = 100\text{ mA}; -I_B = 0.1\text{ mA}$	$-V_{CEsat}$	max.	1.0	V
Base-emitter saturation voltage				
$-I_C = 100\text{ mA}; -I_B = 0.1\text{ mA}$	$-V_{BEsat}$	max.	1.5	V
Transition frequency at $f = 100\text{ MHz}$				
$-I_C = 30\text{ mA}; -V_{CE} = 5\text{ V}$	f_T	typ.	220	MHz
Collector capacitance at $f = 1\text{ MHz}$				
$I_E = 0; -V_{CB} = 30\text{ V}$	C_c	typ.	3.5	pF

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

SILICON PLANAR DARLINGTON TRANSISTOR

N-P-N silicon planar darlington transistor in a plastic SOT23 envelope.

P-N-P complement is BCV26/46.

QUICK REFERENCE DATA

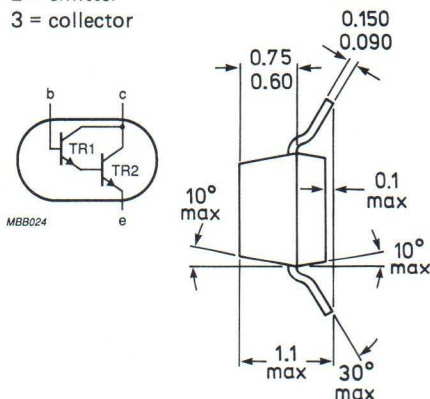
		BCV27	BCV47
Collector-emitter voltage (open base)	V_{CEO} max.	30	60 V
Collector-base voltage (open emitter)	V_{CBO} max.	40	80 V
Collector current	I_C max.	300	500 mA
DC current gain			
$I_C = 1 \text{ mA}; V_{CE} = 5 \text{ V}$	$h_{FE} >$	4 000	2 000
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	$h_{FE} >$	10 000	4 000
$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V}$	$h_{FE} >$	20 000	10 000
Junction temperature	T_j max.	150	$^{\circ}\text{C}$
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	P_{tot} max.	250	mW
Collector-emitter saturation voltage			
$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	V_{CEsat} max.	1.0	V
Transition frequency at $f = 100 \text{ MHz}$			
$I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}$	f_T typ.	220	MHz

MECHANICAL DATA

Fig. 1 SOT23

Pinning:

- 1 = base
2 = emitter
3 = collector

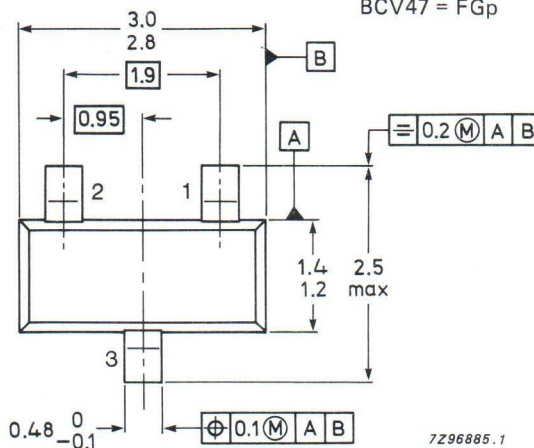


Dimensions in mm

Marking code:

BCV27 = FFp

BCV47 = FGp



TOP VIEW

7296885.1

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCV27	BCV47
Collector-emitter voltage (open base)	V_{CEO}	max.	30	60 V
Collector-base voltage (open emitter)	V_{CBO}	max.	40	80 V
Emitter-base voltage (open collector)	V_{EBO}	max.	10	10 V
Collector current	I_C	max.	300	500 mA
Collector current (peak value)	I_{CM}	max.	800	mA
Base current	I_B	max.	100	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	250	mW
Storage temperature	T_s		-65 to +150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	max.	500	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

			BCV27	BCV47
Collector-base current $V_{CBO} = 30\text{ V}$	I_{CBO}	max.	0.1	0.1 μA
Emitter-base current $V_{EB} = 10\text{ V}$	I_{EBO}	max.	0.1	0.1 μA
Collector-emitter break-down voltage $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	min.	30	60 V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	min.	40	80 V
Emitter-base breakdown voltage $I_E = 100\text{ nA}$	$V_{(BR)EBO}$	min.	10	10 V
DC current gain $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	4 000	2 000
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	10 000	4 000
$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	20 000	10 000
Collector-emitter saturation voltage $I_C = 100\text{ mA}; I_B = 0.1\text{ mA}$	V_{CEsat}	max.	1.0	V
Base-emitter saturation voltage $I_C = 100\text{ mA}; I_B = 0.1\text{ mA}$	V_{BEsat}	max.	1.5	V
Transition frequency at $f = 100\text{ MHz}$ $I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	220	MHz
Collector capacitance at $f = 1\text{ MHz}$ $I_E = 0; V_{CB} = 30\text{ V}$	C_C	typ.	3.5	pF

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

SMALL-SIGNAL DARLINGTON TRANSISTOR

PNP small-signal darlington transistors, housed in a microminiature envelope (SOT89).

NPN complementary types are BCV29/49.

QUICK REFERENCE DATA

			BCV28	BCV48
Collector-base voltage	$-V_{CBO}$	max.	40	80 V
Collector-emitter voltage	$-V_{CEO}$	max.	30	60 V
Emitter-base voltage	$-V_{EBO}$	max.	10	10 V
Collector current (DC)	$-I_C$	max.	500	500 mA
DC current gain				
$-I_C = 1 \text{ mA}; -V_{CE} = 5 \text{ V}$	h_{FE}	min.	4000	2000
$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	h_{FE}	min.	10000	4000
$-I_C = 100 \text{ mA}; -V_{CE} = 5 \text{ V}$	h_{FE}	min.	20000	10000
$-I_C = 500 \text{ mA}; -V_{CE} = 5 \text{ V}$	h_{FE}	min.	4000	2000
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1.0	W
Transition frequency at $f = 100 \text{ MHz}$ $-I_C = 30 \text{ mA}; -V_{CE} = 5 \text{ V}$	f_T	typ.	220	MHz

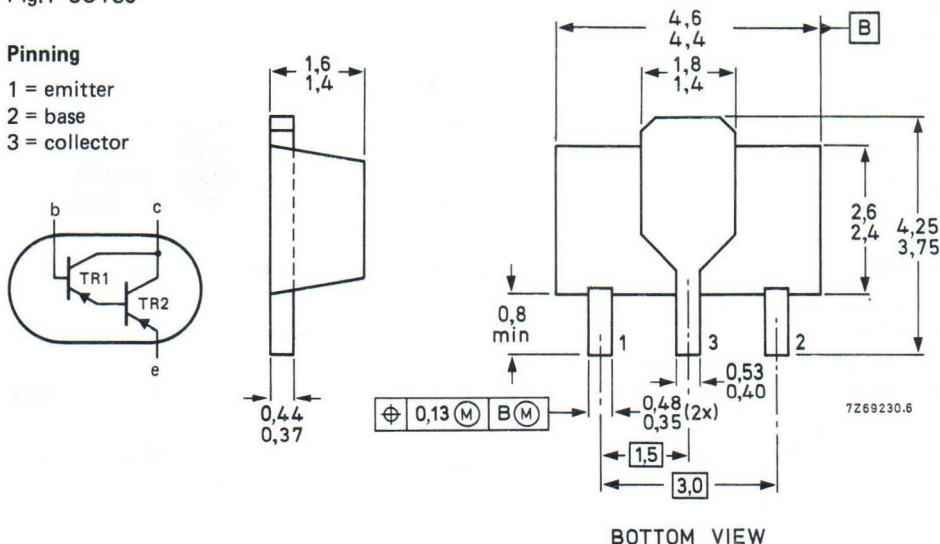
MECHANICAL DATA

Dimensions in mm

Fig.1 SOT89

Pinning

- 1 = emitter
- 2 = base
- 3 = collector



* Mounted on a ceramic substrate; area = 2.5 cm²; thickness = 0.7 mm.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCV28	BCV48
Collector-base voltage	$-V_{CBO}$	max.	40	80 V
Collector-emitter voltage	$-V_{CEO}$	max.	30	60 V
Emitter-base voltage	$-V_{EBO}$	max.	10	10 V
Collector current (DC)	$-I_C$	max.	500	500 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ *	P_{tot}	max.	1.0	W
Storage temperature range	T_{stg}		$-65\text{ to }+150\text{ }^{\circ}\text{C}$	
Junction temperature	T_j	max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	125	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

			BCV28	BCV48
Collector-emitter breakdown voltage $-I_C = 10\text{ mA}$	$-V_{(BR)CES}$	min.	30	60 V
Collector-base breakdown voltage $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	min.	40	80 V
Emitter-base breakdown voltage $-I_E = 0.1\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	min.	10	10 V
Emitter-base cut-off current $-V_{BE} = 4\text{ V}; I_C = 0$	$-I_{EBO}$	max.	0.1	0.1 μA
Collector-base cut-off current $-V_{CB} = 30/60\text{ V}; I_E = 0$	$-I_{CBO}$	max.	0.1	0.1 μA
DC current gain $-I_C = 1\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	4000	2000
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	10000	4000
$-I_C = 100\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	20000	10000
$-I_C = 500\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	min.	4000	2000
Collector-emitter saturation voltage $-I_C = 100\text{ mA}; -I_B = 0.1\text{ mA}$	$-V_{CEsat}$	max.	1.0	V
Base-emitter saturation voltage $-I_C = 100\text{ mA}; -I_B = 0.1\text{ mA}$	$-V_{BEsat}$	max.	1.5	V
Transition frequency at $f = 100\text{ MHz}$ $-I_C = 30\text{ mA}; -V_{CE} = 5\text{ V}$	f_T	typ.	220	MHz
Output capacitance $-V_{CB} = 30\text{ V}; I_E = 0$	C_{ob}	typ.	3.5	pF

* Mounted on a ceramic substrate; area = 2.5 cm^2 ; thickness = 0.7 mm.

SMALL-SIGNAL DARLINGTON TRANSISTOR

NPN small-signal darlington transistors, housed in a microminiature envelope (SO89).

PNP complementary types are BCV28/48.

QUICK REFERENCE DATA

		BCV29	BCV49
Collector-base voltage	V_{CBO} max.	40	80 V
Collector-emitter voltage	V_{CEO} max.	30	60 V
Emitter-base voltage	V_{EBO} max.	10	10 V
Collector current (DC)	I_C max.	500	500 mA
DC current gain			
$I_C = 1 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} min.	4000	2000
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} min.	10000	4000
$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} min.	20000	10000
$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} min.	4000	2000
Total power dissipation up to $T_{amb} = 25^\circ\text{C}^*$	P_{tot} max.	1.0	W
Transition frequency at $f = 100 \text{ MHz}$ $I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}$	f_T typ.	220	MHz

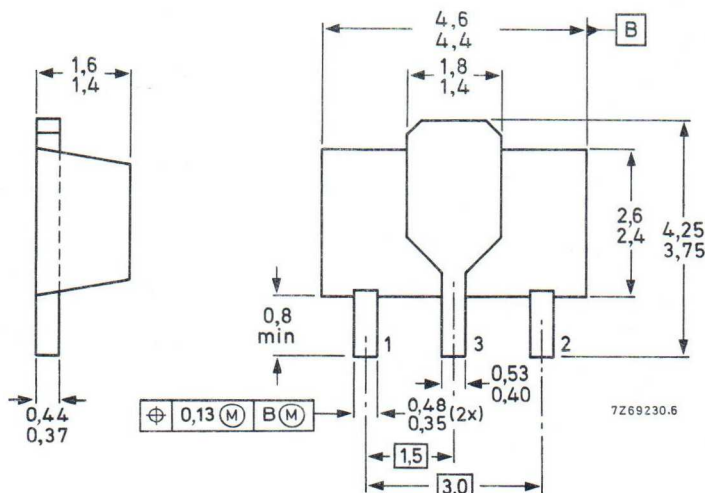
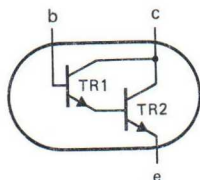
MECHANICAL DATA

Dimensions in mm

Fig.1 SOT89.

Pinning

- 1 = emitter
- 2 = base
- 3 = collector



BOTTOM VIEW

* Mounted on a ceramic substrate; area = 2.5 cm^2 ; thickness = 0.7 mm.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCV29	BCV49
Collector-base voltage	V_{CBO}	max.	40	80 V
Collector-emitter voltage	V_{CEO}	max.	30	60 V
Emitter-base voltage	V_{EBO}	max.	10	10 V
Collector current (DC)	I_C	max.	500	500 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	1.0	W
Storage temperature range	T_{stg}		-65 to + 150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\,j-a}$	=	125	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

			BCV29	BCV49
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$	$V_{(BR)CES}$	min.	30	60 V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	min.	40	80 V
Emitter-base breakdown voltage $I_E = 0.1\text{ }\mu\text{A}$	$V_{(BR)EBO}$	min.	10	10 V
Emitter-base cut-off current $V_{BE} = 4\text{ V}; I_C = 0$	I_{EBO}	max.	0.1	0.1 μA
Collector-base cut-off current $V_{CB} = 30/60\text{ V}; I_E = 0$	I_{CBO}	max.	0.1	0.1 μA
DC current gain $I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	4000	2000
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	10000	4000
$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	20000	10000
$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	4000	2000
Collector-emitter saturation voltage $I_C = 100\text{ mA}; I_B = 0.1\text{ mA}$	V_{CEsat}	max.	1.0	1.0 V
Base-emitter saturation voltage $I_C = 100\text{ mA}; I_B = 0.1\text{ mA}$	V_{BEsat}	max.	1.5	1.5 V
Transition frequency at $f = 100\text{ MHz}$ $I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	220	MHz
Output capacitance $V_{CB} = 30\text{ V}; I_E = 0$	C_{ob}	typ.	3.5	pF

* Mounted on a ceramic substrate; area = 2.5 cm^2 ; thickness = 0.7 mm.

SILICON PLANAR EPITAXIAL TRANSISTOR

Double n-p-n transistor, in SOT-143 plastic envelope, designed for use in applications where the working point must be independent of temperature.

Owing to application of two similar crystals of one slice this device has a good thermal coupling and V_{BE} matching. Special interconnection of the two transistor crystals allows the device to be used as a current mirror and the separated emitter leads allow connection to different sources.

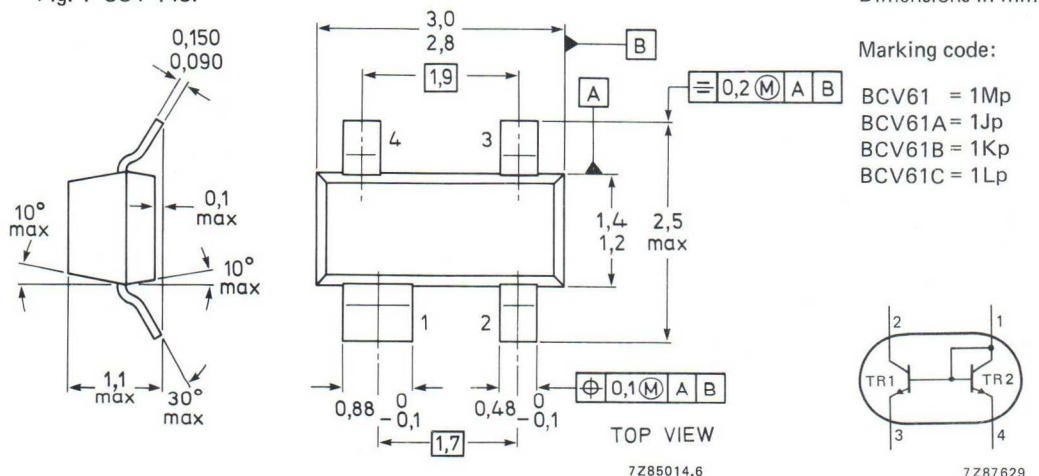
A similar device in p-n-p configuration is the BCV62.

QUICK REFERENCE DATA

Collector-emitter voltage (open base) regarding transistor T1	V_{CEO}	max.	30 V
Collector-base voltage (open emitter) regarding transistor T1	V_{CBO}	max.	30 V
Collector current d.c.	I_C	max.	100 mA
peak	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

MECHANICAL DATA

Fig. 1 SOT-143.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base) regarding transistor T1	V_{CEO}	max.	30 V
Collector-base voltage (open emitter) regarding transistor T1	V_{CBO}	max.	30 V
Base current (transistor T1) peak value	I_{BM1}	max.	200 mA
Emitter-base voltage	V_{EBS}	max.	6 V
Collector current d.c.	I_C	max.	100 mA
peak	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ when mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Storage temperature	T_{stg}		-65 to +150 $^{\circ}\text{C}$

THERMAL RESISTANCE

Device mounted on a ceramic substrate of
8 mm x 10 mm x 0,7 mm
from junction to ambient

$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Transistor T1

Collector cut-off current

$I_E = 0$; $V_{CB} = 30\text{ V}$

$I_E = 0$; $V_{CB} = 30\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$

I_{CBO}	<	15 nA
	<	5 μA

Base-emitter voltage

$I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$

V_{BE}	typ.	660 mV*
		580 to 700 mV*

$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$

V_{BE}	<	770 mV*
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Saturation voltages

$I_C = 10\text{ mA}$; $I_B = 0,5\text{ mA}$

V_{CEsat}	typ.	90 mV
	<	250 mV

V_{BEsat}	typ.	700 mV**
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$I_C = 100\text{ mA}$; $I_B = 5\text{ mA}$

V_{CEsat}	typ.	200 mV
	<	600 mV

V_{BEsat}	typ.	900 mV**
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* Decreasing 2 mV/ $^{\circ}\text{C}$ with increasing temperature.

** Decreasing 1,7 mV/ $^{\circ}\text{C}$ with increasing temperature.

Transition frequency at $f = 35$ MHz $I_C = 10$ mA; $V_{CE} = 5$ V f_T typ. 300 MHzCollector capacitance at $f = 1$ MHz $I_E = I_E = 0$; $V_{CB} = 10$ V C_c typ. 2,5 pFNoise figure at $R_S = 2$ k Ω $I_C = 200$ μ A; $V_{CE} = 5$ V $f = 1$ kHz; $B = 200$ Hz F typ. 2 dB
< 10 dB

D.C. current gain

 $I_C = 100$ μ A; $V_{CE} = 5$ V $I_C = 2$ mA; $V_{CE} = 5$ V h_{FE} > 100
 h_{FE} 110 to 800

Input impedance

 $I_C = 2$ mA; $V_{CE} = 5$ V; $f = 1$ kHz h_{ie} typ. 5 k Ω

Reverse voltage transfer ratio

 $I_C = 2$ mA; $V_{CE} = 5$ V; $f = 1$ kHz h_{re} typ. 2×10^{-4}

Small signal current gain

 $I_C = 2$ mA; $V_{CE} = 5$ V; $f = 1$ kHz h_{fe} 100 to 900

Output admittance

 $I_C = 2$ mA; $V_{CE} = 5$ V; $f = 1$ kHz h_{oe} typ. 30 μ S**Transistor T2**

Base-emitter forward voltage

 $I_E = 250$ mA $I_E = 10$ μ A V_{BES} < 1,8 V
> 400 mV

Matching of transistor T1 and transistor T2

at $I_{E2} = 0,5$ mA and $V_{CE1} = 5$ V $T_{amb} = 25$ $^{\circ}$ C $T_{amb} = 150$ $^{\circ}$ C I_{C1}/I_{C2} 0,7 to 1,3
 I_{C1}/I_{C2} 0,7 to 1,3

Thermal coupling of transistor T1 and Transistor T2*

T1 : $V_{CE} = 5$ V

Maximum current for thermal

stability of I_{C1} I_{E2} typ. 5 mA
min. 110

D.C. current gain

 $I_C = 2$ mA; $V_{CE} = 5$ V

BCV61A

 h_{FE} max. 220
min. 200

BCV61B

 h_{FE} max. 450
min. 420

BCV61C

 h_{FE} max. 800* Without emitter resistor and device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
(See Fig. 2)

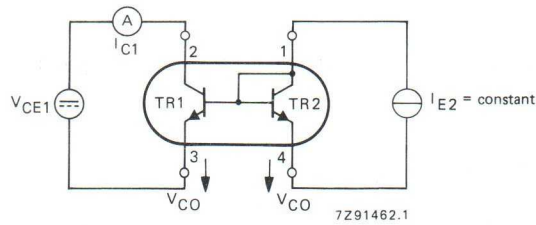


Fig. 2 Test circuit current matching.

Note: Voltage drop at contacts: $V_{CO} < \frac{2}{3} U_T \triangleq 16 \text{ mV}$.

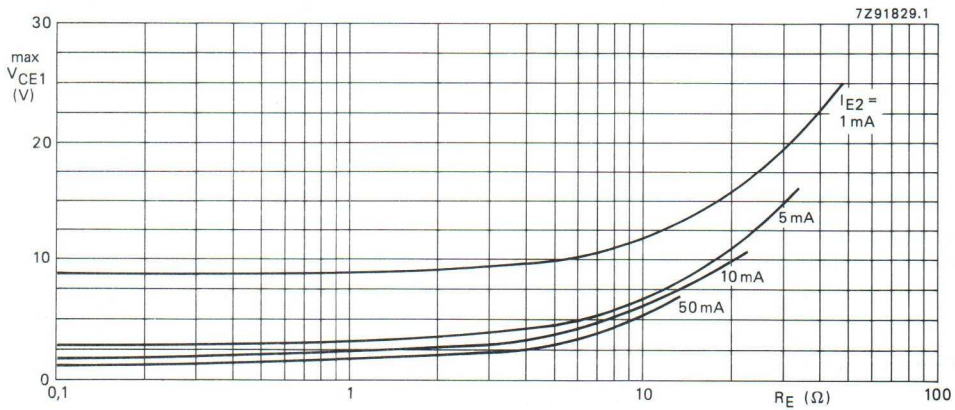


Fig. 3 Characteristic for determination of max. V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $\frac{I_{C1}}{I_{E2}} = 1,3$ (see Fig. 4).

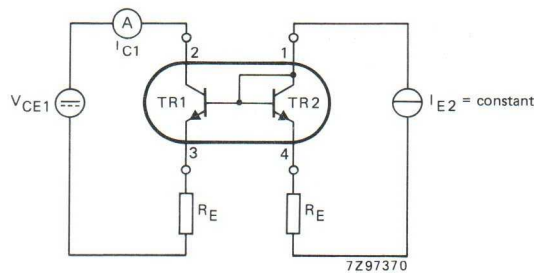


Fig. 4 BCV61 with emitter resistors.

SILICON PLANAR EPITAXIAL TRANSISTOR

Double p-n-p transistor, in SOT-143 plastic envelope, designed for use in applications where the working point must be independent of temperature.

Owing to application of two similar crystals of one slice this device has a good thermal coupling and V_{BE} matching. Special interconnection of the two transistor crystals allows the device to be used as a current mirror and the separated emitter leads allow connection to different sources.

A similar device in n-p-n configuration is the BCV61.

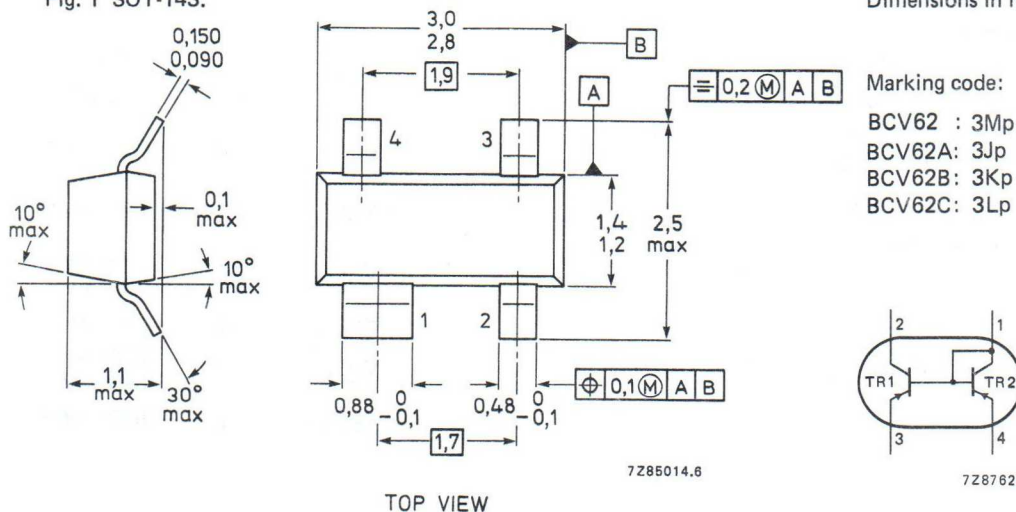
QUICK REFERENCE DATA

Collector-emitter voltage (open base) regarding transistor T1	$-V_{CEO}$	max	30 V
Collector-base voltage (open emitter) regarding transistor T1	$-V_{CBO}$	max.	30 V
Collector current d.c.	$-I_C$	max.	100 mA
peak	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

MECHANICAL DATA

Fig. 1 SOT-143.

Dimensions in mm



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base) regarding transistor T1	$-V_{CEO}$	max.	30 V
Collector-base voltage (open emitter) regarding transistor T1	$-V_{CBO}$	max.	30 V
Base current (transistor T1) peak value	$-I_{BM1}$	max.	200 mA
Emitter-base voltage	$-V_{EBS}$	max.	6 V
Collector current d.c.	$-I_C$	max.	100 mA
peak	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$ when mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Storage temperature	T_{stg}		-65 to + 150 $^\circ\text{C}$

THERMAL RESISTANCE

Device mounted on a ceramic substrate of
8 mm x 10 mm x 0,7 mm
from junction to ambient

$$R_{th\ j-a} = 500\ \text{K/W}$$

CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

Transistor T1

Collector cut-off current $-I_E = 0; -V_{CB} = 30\ \text{V}$	$-I_{CBO}$	<	15 nA
$-I_E = 0; -V_{CB} = 30\ \text{V}; T_j = 150^\circ\text{C}$		<	5 μA
Base-emitter voltage $-I_C = 2\ \text{mA}; -V_{CE} = 5\ \text{V}$	$-V_{BE}$	typ.	650 mV*
			600 to 750 mV*
$-I_C = 10\ \text{mA}; -V_{CE} = 5\ \text{V}$	$-V_{BE}$	<	820 mV*
Saturation voltages $-I_C = 10\ \text{mA}; -I_B = 0,5\ \text{mA}$	$-V_{CEsat}$	typ.	75 mV
		<	300 mV
	$-V_{BEsat}$	typ.	700 mV**
	$-V_{CEsat}$	typ.	250 mV
		<	650 mV
$-I_C = 100\ \text{mA}; -I_B = 5\ \text{mA}$	$-V_{BEsat}$	typ.	850 mV**

* Decreasing 2 mV/ $^\circ\text{C}$ with increasing temperature.

** Decreasing 1,7 mV/ $^\circ\text{C}$ with increasing temperature.

Transition frequency at $f = 35 \text{ MHz}$ $-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$ f_T typ. 150 MHzCollector capacitance at $f = 1 \text{ MHz}$ $I_E = i_e = 0; -V_{CB} = 10 \text{ V}$ C_C typ. 4,5 pFNoise figure at $R_S = 2 \text{ k}\Omega$ $-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$ F typ. 2 dB $f = 1 \text{ kHz}; B = 200 \text{ Hz}$

< 10 dB

D.C. current gain

 $-I_C = 100 \mu\text{A}; -V_{CE} = 5 \text{ V}$ h_{FE} > 100 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$ h_{FE} 100 to 800

Input impedance

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; f = 1 \text{ kHz}$ h_{ie} typ. 3 k Ω

Reverse voltage transfer ratio

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; f = 1 \text{ kHz}$ h_{re} typ. 3×10^{-4}

Small signal current gain

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; f = 1 \text{ kHz}$ h_{fe} 100 to 900

Output admittance

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; f = 1 \text{ kHz}$ h_{oe} typ. 50 μS **Transistor T2**

Base-emitter forward voltage

 $-I_E = 250 \text{ mA}$ $-V_{BES}$ < 1,5 V
> 400 mV $-I_E = 10 \mu\text{A}$

Matching of transistor T1 and transistor T2

at $I_{E2} = 0,5 \text{ mA}$ and $V_{CE1} = 5 \text{ V}$ $T_{amb} = 25^\circ\text{C}$ I_{C1}/I_{C2} 0,7 to 1,3 $T_{amb} = 150^\circ\text{C}$ I_{C1}/I_{C2} 0,7 to 1,3

Thermal coupling of transistor T1 and transistor T2*

T1 : $-V_{CE} = 5 \text{ V}$ Maximum current for thermal
stability of $-I_{C1}$ I_{E2} typ. 5 mA
min. 125

D.C. current gain

 $-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

BCV62A

 h_{FE} max. 250
min. 220

BCV62B

 h_{FE} max. 475
min. 420

BCV62C

 h_{FE} max. 800* Without emitter resistor and device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
(see Fig. 2)

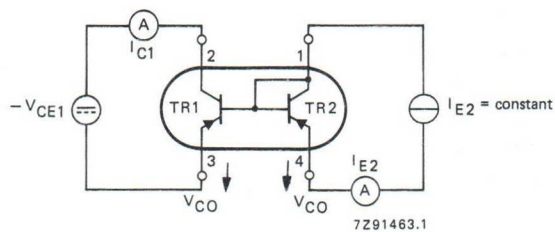


Fig. 2 Test circuit current matching.

Note: Voltage drop at contacts: $V_{CO} < \frac{2}{3} U_T \triangleq 16 \text{ mV}$.

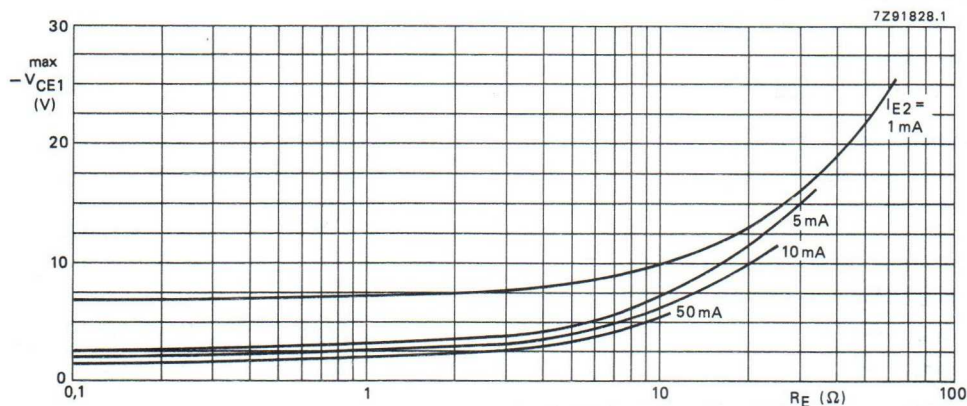


Fig. 3 Characteristic for determination of max. V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $\frac{I_{C1}}{I_{E2}} = 1,3$ (see Fig. 4).

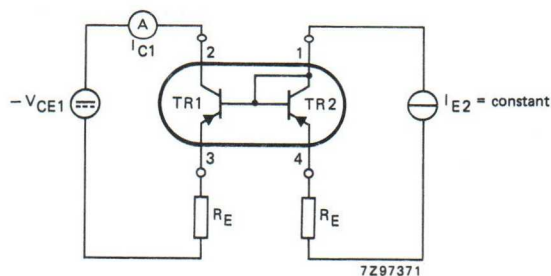


Fig. 4 BCV62 with emitter resistors.

SILICON PLANAR TRANSISTOR

Double N-P-N transistor in a plastic SOT-143 envelope. Intended for Schmitt-trigger applications.
P-N-P complement is the BCV64.

QUICK REFERENCE DATA

	transistor	T1	T2
Collector-emitter voltage (open base)	V_{CEO} max.	30	6 V
Collector-base voltage (open emitter)	V_{CBO} max.	30	6 V
Collector current	I_C max.	100	mA
Junction temperature	T_j max.	150	°C
Total power dissipation up to $T_{amb} = 25\text{ °C}$	P_{tot} max.	250	mW
Collector-emitter saturation voltage $I_C = 10\text{ mA}; I_B = 0,5\text{ mA}$	V_{CEsat} max.	300	mV
Small signal current gain	h_{fe}	100 to 900	
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T typ.	200	— MHz

MECHANICAL DATA

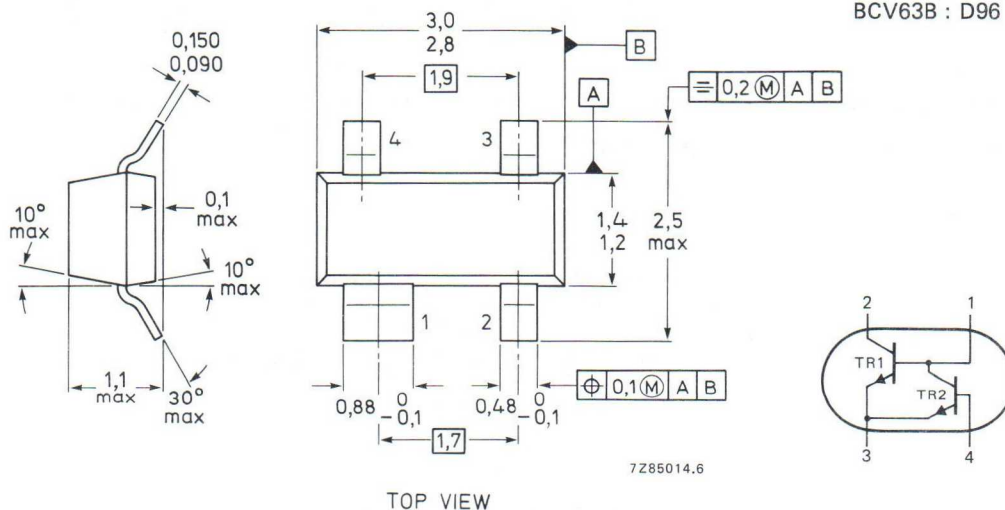
Fig. 1 SOT-143.

Dimensions in mm

Marking code

BCV63 : D95

BCV63B : D96



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

	transistor	T1	T2
Collector-emitter voltage (open base)	V_{CEO} max.	30	6 V
Collector-base voltage (open emitter)	V_{CBO} max.	30	6 V
Emitter-base voltage (open collector)	V_{EBO} max.	6	V
Collector current (d.c.)	I_C max.	100	mA
Collector current (peak value)	I_{CM} max.	200	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot} max.	250	mW
Storage temperature	T_s	-65 to +150 $^{\circ}\text{C}$	
Junction temperature	T_j max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$R_{th\ j-a}$ max.	500	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

	transistor	T1	T2
Collector cut-off current $I_E = 0; V_{CBO} = 30\text{ V}$	I_{CBO} max.	15	15 nA
$I_E = 0; V_{CBO} = 30\text{ V}$ $T_j = 150\text{ }^{\circ}\text{C}$	I_{CBO} max.	5	5 μA
Saturation voltage** $I_C = 10\text{ mA}; I_B = 0,5\text{ mA}$	V_{CEsat} typ.	75	75 mV
	V_{CEsat} max.	300	300 mV
	V_{BEsat} typ.	700	700 mV
$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	V_{CEsat} typ.	250	250 mV
	V_{CEsat} max.	650	— mV
	V_{BEsat} typ.	850	— mV
Base-emitter voltage ▲ $I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	V_{BE} min.	600	— mV
	V_{BE} typ.	650	— mV
	V_{BE} max.	750	— mV
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	V_{BE} max.	820	— mV
$I_C = 2\text{ mA}; V_{CE} = 700\text{ mV}$	V_{BE} typ.		700 mV
Collector capacitance at $f = 1\text{ MHz}$ $I_E = i_e = 0; V_{CE} = 10\text{ V}$	C_c typ.	4	— pF
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T typ.	200	— MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** V_{BEsat} decreases by approx 1,7 mV/K with increasing temperature.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Small signal current gain at $f = 1 \text{ kHz}$

$I_C = 2 \text{ mA}$; T1 : $V_{CE} = 5 \text{ V}$

T2 : $V_{CE} = 700 \text{ mV}$

Transistor 1

D.C. current gain

$I_C = 2 \text{ mA}$; $V_{CE} = 5 \text{ V}$

Transistor 2

D.C. current gain

$I_C = 2 \text{ mA}$; $V_{CE} = 700 \text{ mV}$

	h_{fe}	100 to 900
	BCV63	BCV63B
h_{FE}		
min.	110	200
max.	800	450

Group selection will be done on T1. Due to matched crystals h_{FE} values for T2 are the same as T1.

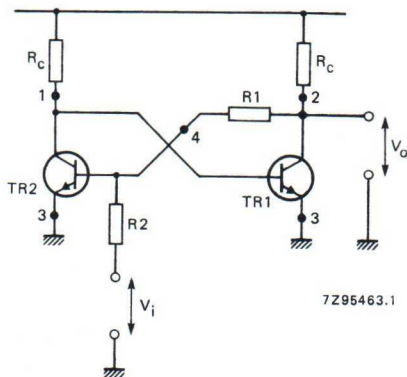


Fig. 2 Schmitt-trigger application.

SILICON PLANAR TRANSISTOR

Double P-N-P transistor in a plastic SOT-143 envelope. Intended for Schmitt-trigger applications.
N-P-N complement is the BCV63.

QUICK REFERENCE DATA

	transistor	T1	T2
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	30	6 V
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	30	6 V
Collector current	$-I_C$ max.	100	mA
Junction temperature	T_j max.	150	°C
Total power dissipation up to $T_{amb} = 25\text{ °C}$	P_{tot} max.	250	mW
Collector-emitter saturation voltage $-I_C = 10\text{ mA}; -I_B = 0,5\text{ mA}$	$-V_{CEsat}$ max.	300	mV
Small signal current gain	h_{fe}	100 to 900	
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T typ.	200	— MHz

MECHANICAL DATA

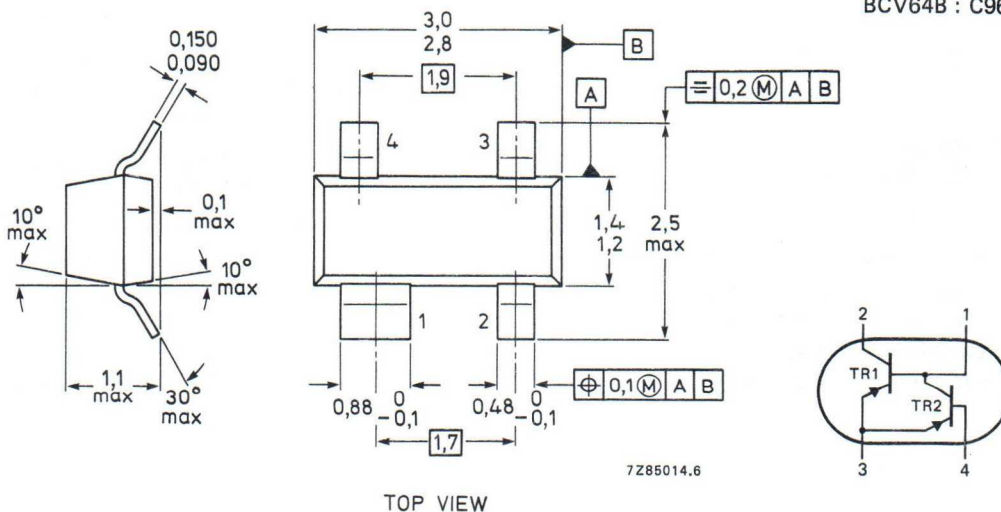
Fig. 1 SOT-143.

Dimensions in mm

Marking code

BCV64 : C95

BCV64B : C96



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

	transistor	T1	T2
Collector-emitter voltage (open base)	$-V_{CE0}$ max.	30	6 V
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	30	6 V
Emitter-base voltage (open collector)	$-V_{EBO}$ max.	6	6 V
Collector current (d.c.)	$-I_C$ max.	6	mA
Collector current (peak value)	$-I_{CM}$ max.	200	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot} max.	250	mW
Storage temperature	T_s	-65 to +150 $^{\circ}\text{C}$	
Junction temperature	T_j max.	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$ max.	500	K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

	transistor	T1	T2
Collector cut-off current $-I_E = 0; -V_{CBO} = 30\text{ V}$	$-I_{CBO}$ max.	15	15 nA
$-I_E = 0; -V_{CBO} = 30\text{ V}$ $T_j = 150\text{ }^{\circ}\text{C}$	$-I_{CBO}$ max.	5	5 μA
Saturation voltage** $-I_C = 10\text{ mA}; -I_B = 0,5\text{ mA}$	$-V_{CEsat}$ typ.	75	75 mV
	$-V_{CEsat}$ max.	300	300 mV
	$-V_{BEsat}$ typ.	700	700 mV
$-I_C = 100\text{ mA}; -I_B = 5\text{ mA}$	$-V_{CEsat}$ typ.	250	250 mV
	$-V_{CEsat}$ max.	650	— mV
	$-V_{BEsat}$ typ.	850	— mV
Base-emitter voltage ▲ $-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$	$-V_{BE}$ typ.	650 600/750	— mV — mV
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	$-V_{BE}$ max.	820	— mV
$-I_C = 2\text{ mA}; -V_{CE} = 700\text{ mV}$	$-V_{BE}$ typ.		700 mV
Collector capacitance at $f = 1\text{ MHz}$ $-I_E = i_e = 0; -V_{CE} = 10\text{ V}$	C_c typ.	4	— pF
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T typ.	200	— MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** V_{BEsat} decreases by approx 1,7 mV/K with increasing temperature.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Small signal current gain at $f = 1 \text{ kHz}$

$-I_C = 2 \text{ mA}$; T1 : $-V_{CE} = 5 \text{ V}$

T2 : $-V_{CE} = 700 \text{ mV}$

Transistor 1

D.C. current gain

$-I_C = 2 \text{ mA}$; $-V_{CE} = 5 \text{ V}$

Transistor 2

D.C. current gain

$-I_C = 2 \text{ mA}$; $-V_{CE} = 700 \text{ mV}$

	h_{fe}	
	BCV64	BCV64B
h_{FE}	min. 110	220
	max. 800	475

Group selection will be done on T1. Due to matched crystals h_{FE} values for T2 are the same as T1.

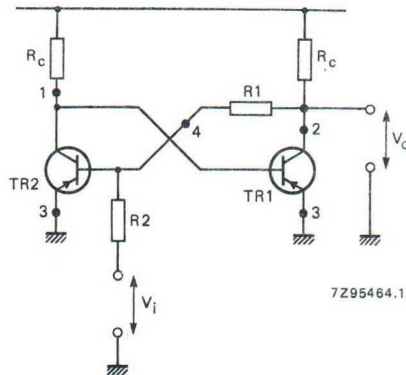


Fig. 2 Schmitt-trigger application.

SILICON PLANAR TRANSISTORS

A matched pair of P-N-P and N-P-N crystal, based on the BC557 and BC547, in a microminiature SOT-143 envelope.

Complementary crystals give advantages in P.C.B. layout using S.M.D. technology.

QUICK REFERENCE DATA

Collector-emitter voltage (open base)	V_{CEO}	max.	30 V
Collector-base voltage (open emitter)	V_{CBO}	max.	30 V
Collector current (DC)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

MECHANICAL DATA

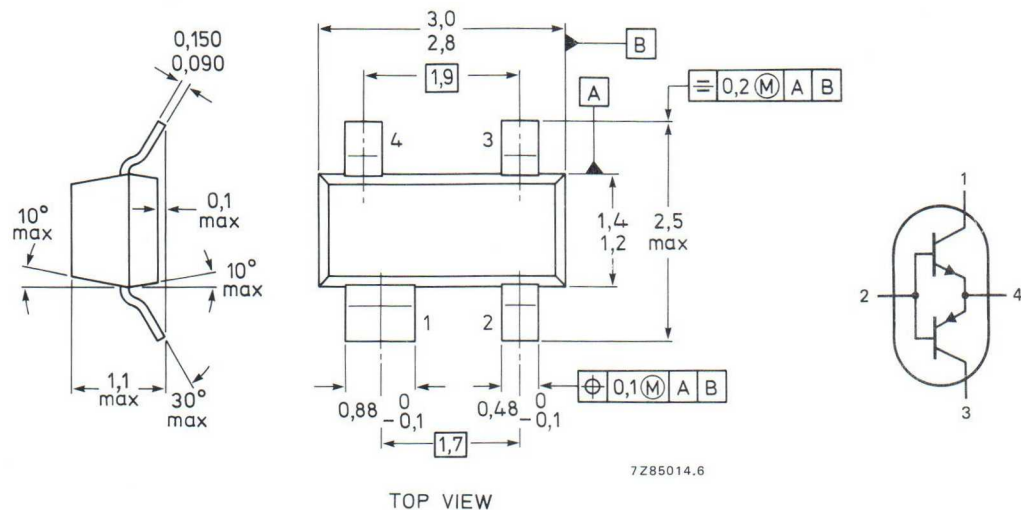
Fig. 1 SOT-143.

Dimensions in mm

Marking code

BCV65: 97p

BCV65B: 98p



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Per transistor:

Collector-emitter voltage (open base)	V_{CEO}	max.	30 V
Collector-base voltage (open emitter)	V_{CBO}	max.	30 V
Collector current (DC)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation (per device) up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_s		-65 to + 150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	R_{thj-a}	max.	500 K/W
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CHARACTERISTICS

Per transistor:

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

Collector cut-off current

$I_E = 0; V_{CB} = 30\text{ V}$	I_{CBO}	max.	15 nA
$I_E = 0; V_{CB} = 30\text{ V}$ $T_j = 150\text{ }^{\circ}\text{C}$	I_{CBO}	max.	5 μA

Base-emitter voltage**

$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	V_{BE}	typ.	650 mV
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	V_{BE}	max.	580 to 750 mV 820 mV

Saturation voltage[▲]

$I_C = 10\text{ mA}; I_B = 0,5\text{ mA}$	V_{CEsat}	typ.	90 mV
	V_{CEsat}	max.	300 mV
	V_{BEsat}	typ.	700 mV
$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	V_{CEsat}	typ.	250 mV
	V_{CEsat}	max.	650 mV
	V_{BEsat}	typ.	900 mV

D.C. current gain

$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$

		BCV65	BCV65B
h_{FE}	min.	75	200
h_{FE}	max.	800	475

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

▲ V_{BEsat} decreases by approx. 1,7 mV/K with increasing temperature.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

D.C. current gain at $T_j = 25^\circ\text{C}$

$I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Collector current (peak value)

Total power dissipation up to $T_{\text{amb}} = 25^\circ\text{C}$

Junction temperature

Transition frequency at $f = 35\text{ MHz}$

$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$

Noise figure at $R_S = 2\text{ k}\Omega$

$I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$;

$f = 1\text{ kHz}$; $B = 200\text{ Hz}$

		BCV71	BCV72
h_{FE}	$>$	110	200
	$<$	220	450
V_{CBO}	max.	80	V
V_{CEO}	max.	60	V
I_{CM}	max.	200	mA
P_{tot}	max.	250	mW
T_j	max.	150	$^\circ\text{C}$
f_T	typ.	300	MHz
F	$<$	10	dB

MECHANICAL DATA

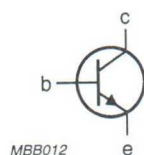
Fig. 1 SOT-23.

Pinning:

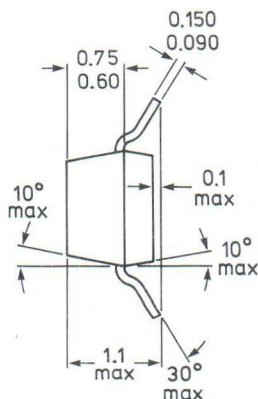
1 = base

2 = emitter

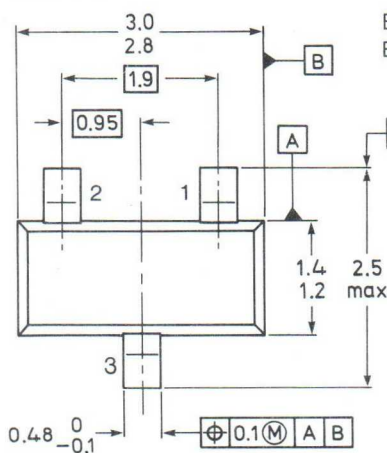
3 = collector



MBB012



Dimensions in mm



Marking code

BCV71 = K7p

BCV72 = K8p

7Z96885.1

TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	80 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	60 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		$-65 \text{ to } +150 \text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 20 \text{ V}$	I_{CBO}	<	100 nA
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$I_E = 0; V_{CB} = 20 \text{ V}; T_j = 100 \text{ }^{\circ}\text{C}$	I_{CBO}	<	10 μA
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Base emitter voltage

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	V_{BE}		550 to 700 mV
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Saturation voltages

$I_C = 10 \text{ mA}; I_B = 0,5 \text{ mA}$	V_{CEsat}	typ.	120 mV
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		<	250 mV
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	V_{BEsat}	typ.	750 mV
--	-------------	------	--------

	V_{CEsat}	typ.	210 mV
--	-------------	------	--------

	V_{BEsat}	typ.	850 mV
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D.C. current gain

$I_C = 10 \text{ } \mu\text{A}; V_{CE} = 5 \text{ V}$	h_{FE}	typ.	BCV71	BCV72
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		>	90	150
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$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE}	<	110	200
--	----------	---	-----	-----

		<	220	450
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Collector capacitance at $f = 1 \text{ MHz}$

$I_E = I_e = 0; V_{CB} = 10 \text{ V}$	C_c	typ.	2,5	pF
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Transition frequency at $f = 35 \text{ MHz}$

$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	f_T	typ.	300	MHz
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Noise figure at $R_S = 2 \text{ k}\Omega$

$I_C = 200 \text{ } \mu\text{A}; V_{CE} = 5 \text{ V}$	F	<	10	dB
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$f = 1 \text{ kHz}; B = 200 \text{ Hz}$				
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* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

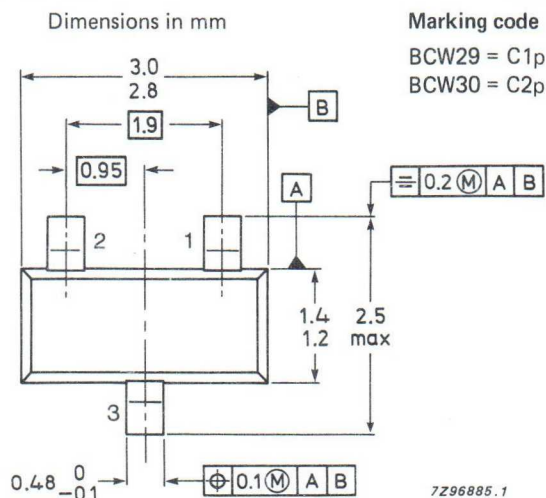
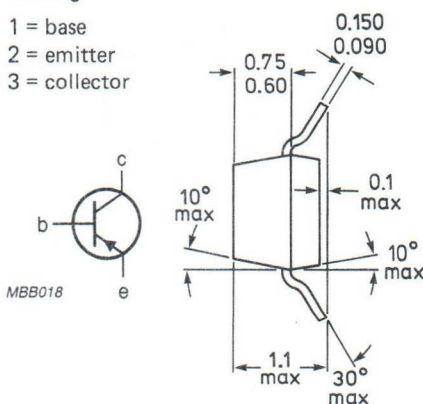
		BCW29	BCW30
D.C. current gain at $T_j = 25^\circ\text{C}$ $-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$	$h_{FE} >$	120	215
	$h_{FE} <$	260	500
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	32	V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	32	V
Collector current (peak value)	$-I_{CM}$ max.	200	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot} max.	250	mW
Junction temperature	T_j max.	150	$^\circ\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T typ.	150	MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V};$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	F	< 10	dB

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base) $-I_C = 2 \text{ mA}$	$-V_{CEO}$	max.	32 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		$-65 \text{ to } +150 \text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 32 \text{ V}$

$-I_{CBO} < 100 \text{ nA}$

$I_E = 0; -V_{CB} = 32 \text{ V}; T_j = 100 \text{ }^{\circ}\text{C}$

$-I_{CBO} < 10 \text{ } \mu\text{A}$

Base-emitter voltage

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

$-V_{BE} \quad 600 \text{ to } 750 \text{ mV}$

Saturation voltages

$-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$

$-V_{CEsat} \text{ typ. } 80 \text{ mV}$
 $< 300 \text{ mV}$

$-V_{BEsat} \text{ typ. } 720 \text{ mV}$

$-I_C = 50 \text{ mA}; -I_B = 2,5 \text{ mA}$

$-V_{CEsat} \text{ typ. } 150 \text{ mV}$
 $-V_{BEsat} \text{ typ. } 810 \text{ mV}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$-I_C = 10 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Collector-capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

	BCW29	BCW30
h_{FE}	typ. 90	150
h_{FE}	> 120	215
h_{FE}	< 260	500
C_c	typ. 4,5	pF
f_T	typ. 150	MHz
F	$<$	10 dB

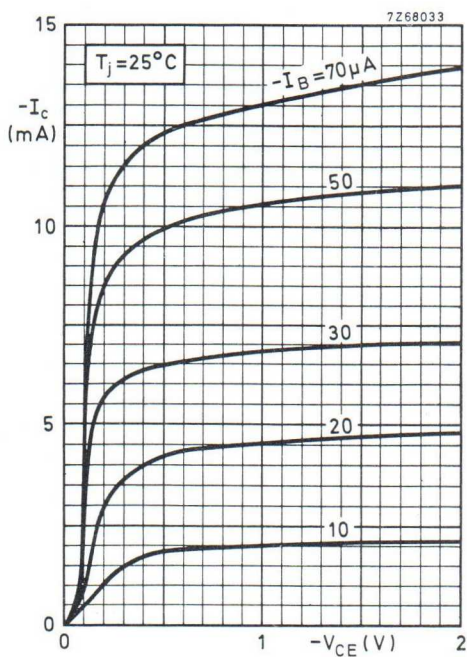


Fig. 2

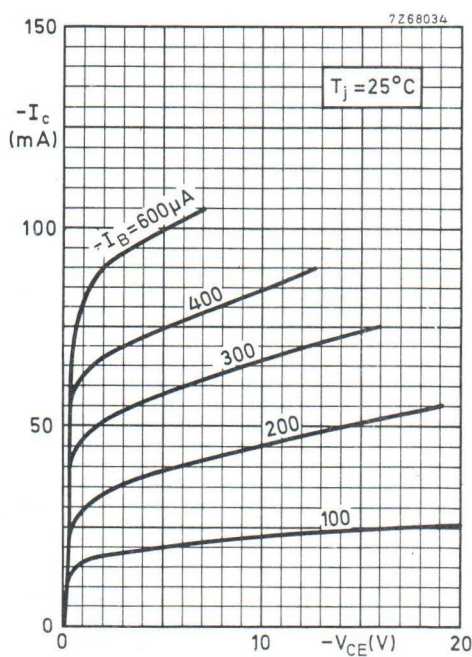


Fig. 3

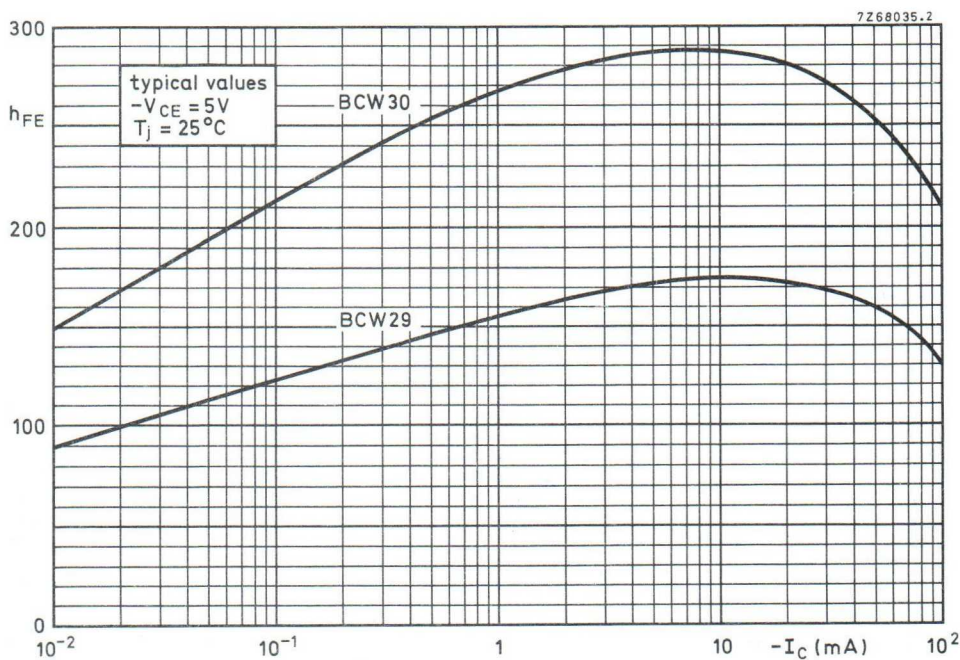


Fig. 4

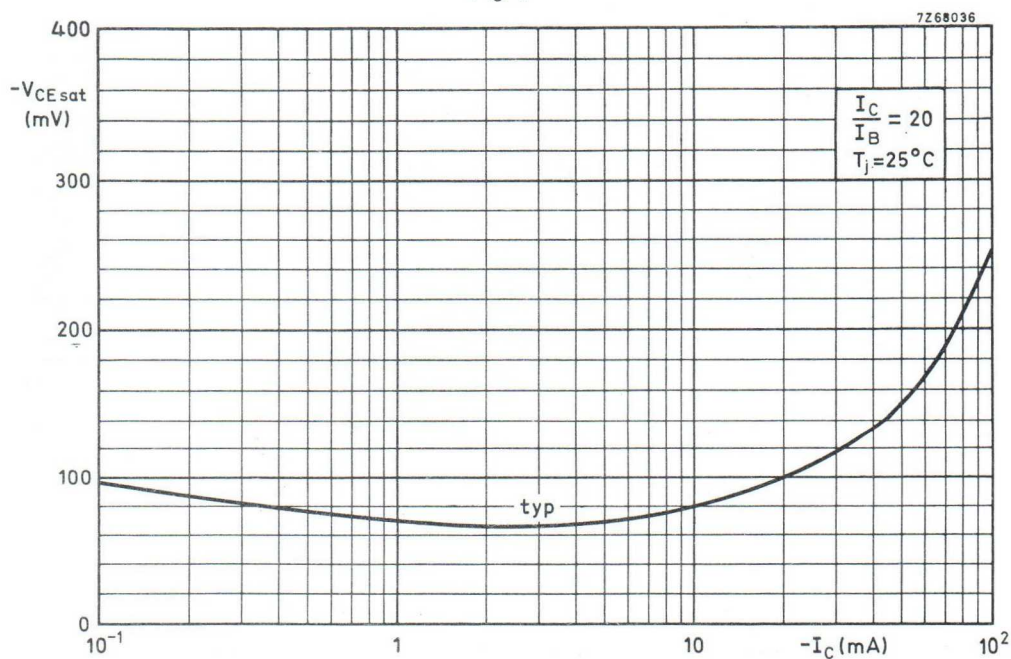


Fig. 5

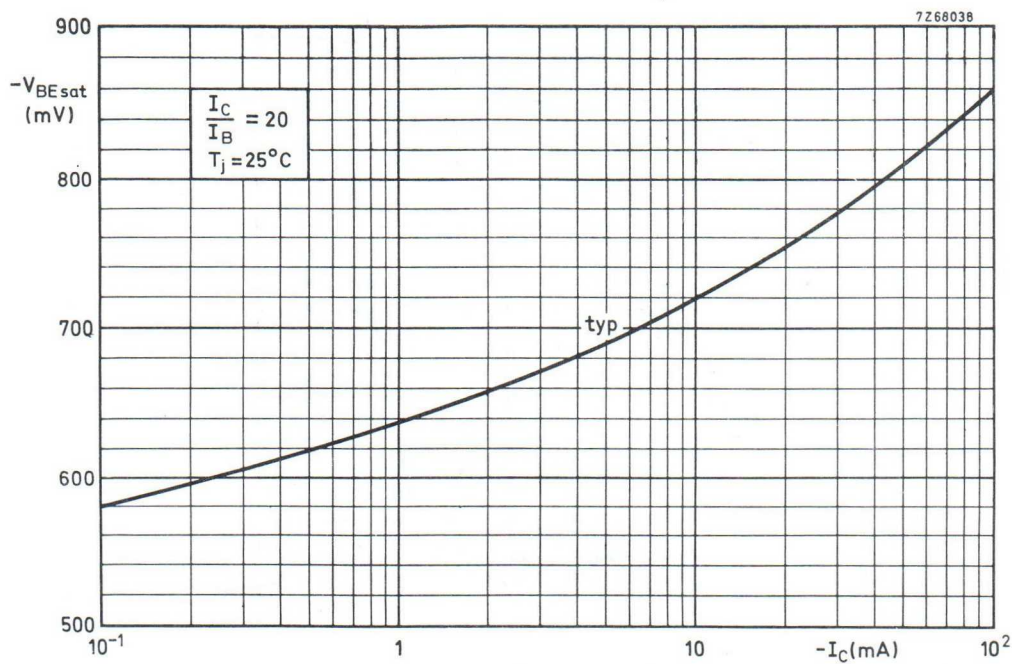


Fig. 6

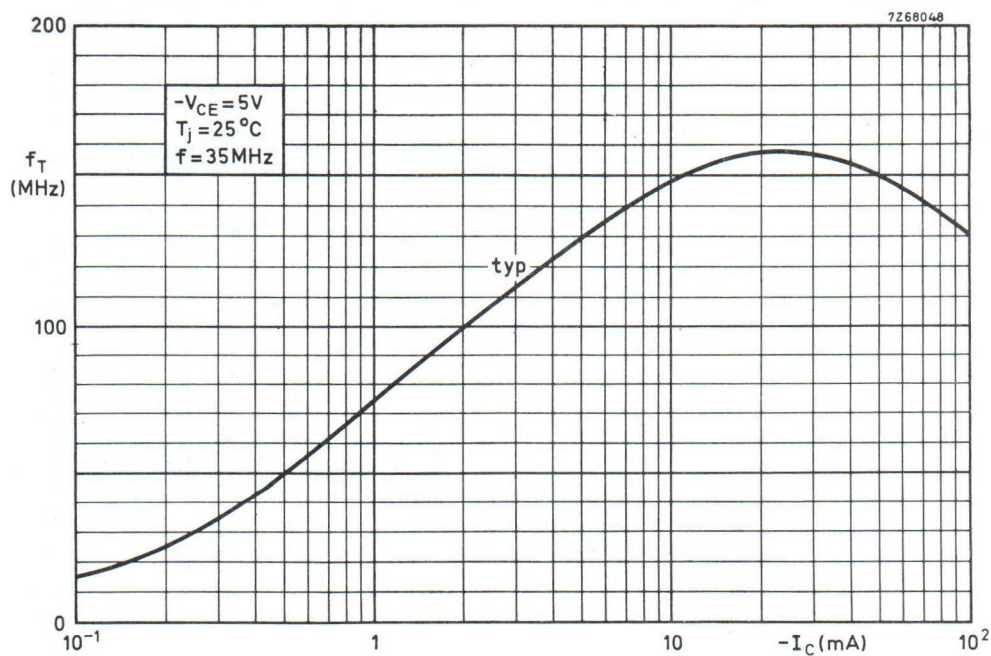


Fig. 7

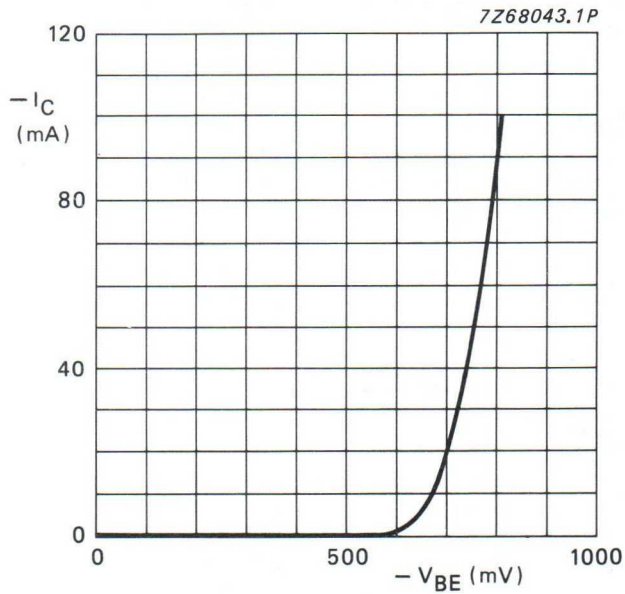


Fig. 8 $V_{CE} = 5\text{ V}$; $T_j = 25^\circ\text{C}$; typical values.

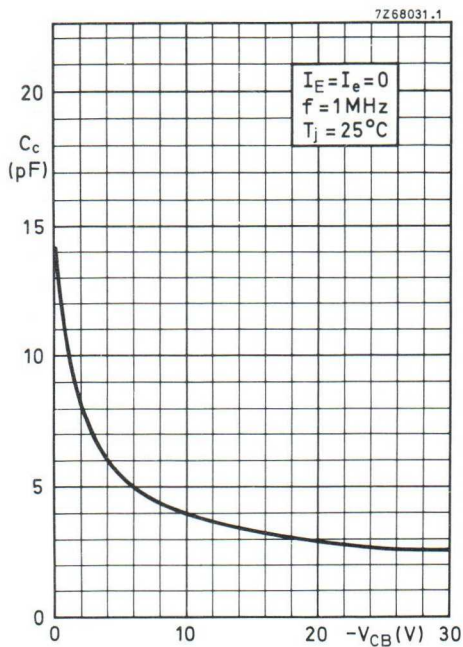


Fig. 9

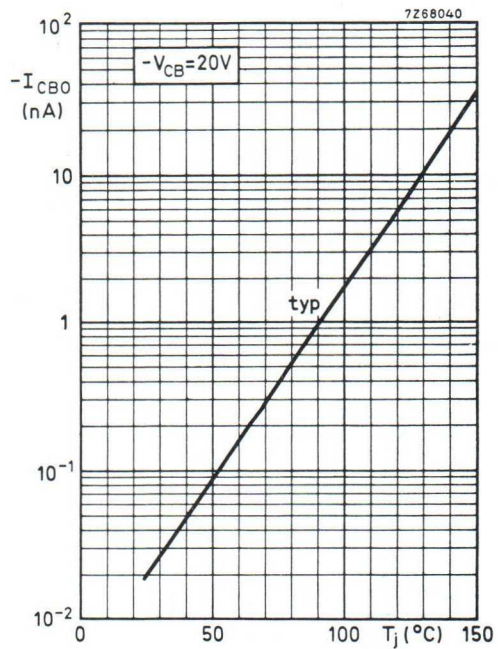


Fig. 10

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	V_{CBO}	max.	32 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	32 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to +150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 32 \text{ V}$

$I_{CBO} < 100 \text{ nA}$

$I_E = 0; V_{CB} = 32 \text{ V}; T_j = 100 \text{ }^{\circ}\text{C}$

$I_{CBO} < 10 \text{ } \mu\text{A}$

Base-emitter voltage

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

$V_{BE} \quad 550 \text{ to } 700 \text{ mV}$

Saturation voltages

$I_C \text{ 10 mA}; I_B = 0,5 \text{ mA}$

$V_{CEsat} \text{ typ. } 120 \text{ mV}$
 $< 250 \text{ mV}$

$V_{BEsat} \text{ typ. } 750 \text{ mV}$

$I_C = 50 \text{ mA}; I_B = 2,5 \text{ mA}$

$V_{CEsat} \text{ typ. } 210 \text{ mV}$
 $V_{BEsat} \text{ typ. } 850 \text{ mV}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$$

$$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$I_C = 200 \mu\text{A}; V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

	BCW31	BCW32	BCW33
h_{FE} typ.	90	150	270
$h_{FE} >$	110	200	420
$h_{FE} <$	220	450	800
C_C	typ.	2,5	pF
f_T	typ.	300	MHz
F	$<$	10	dB

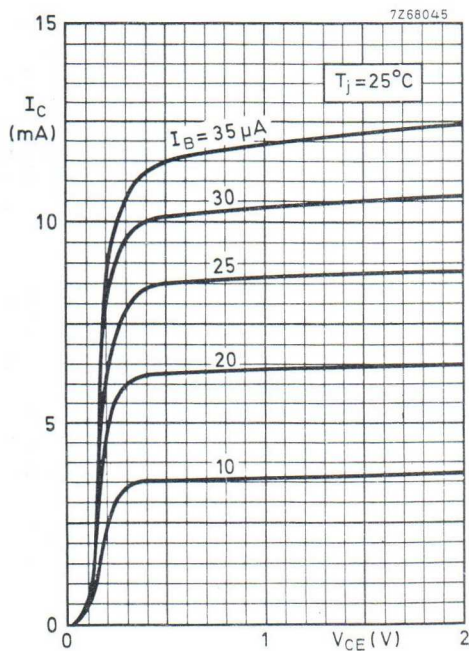


Fig. 2

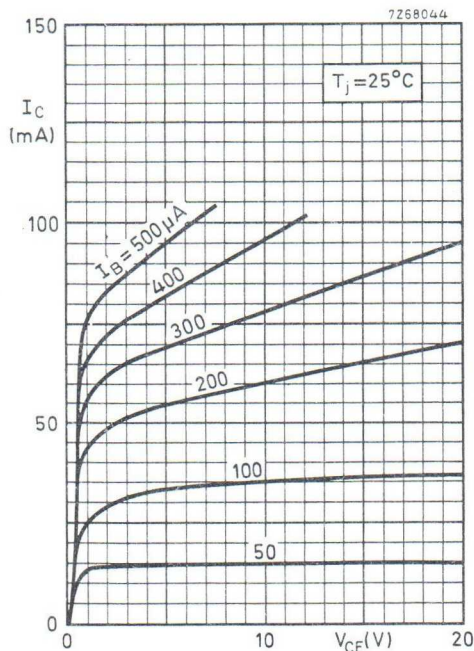


Fig. 3

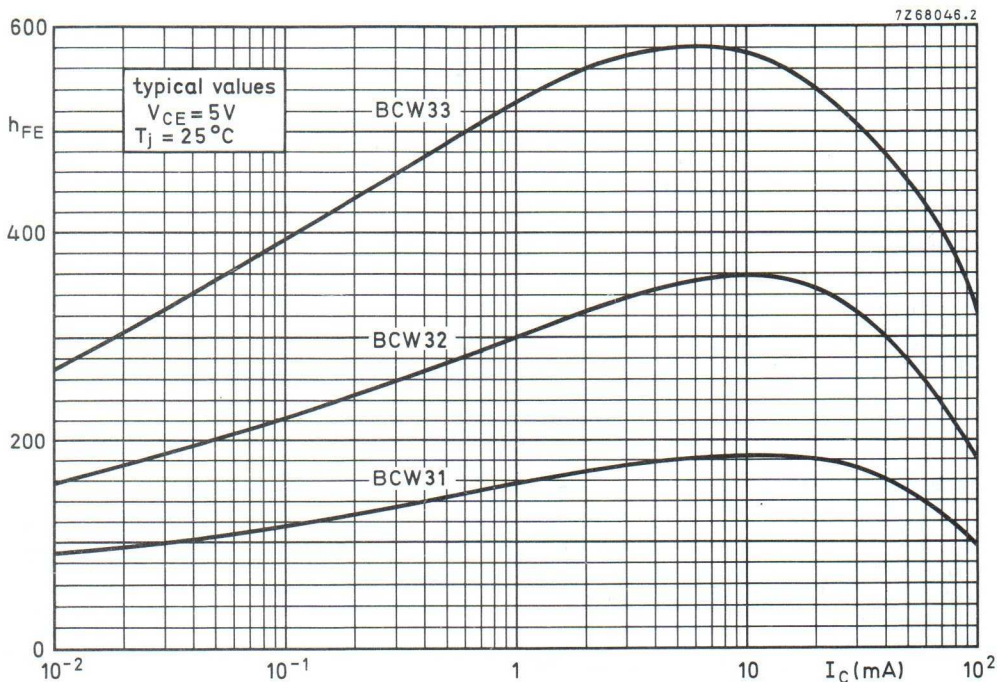


Fig. 4

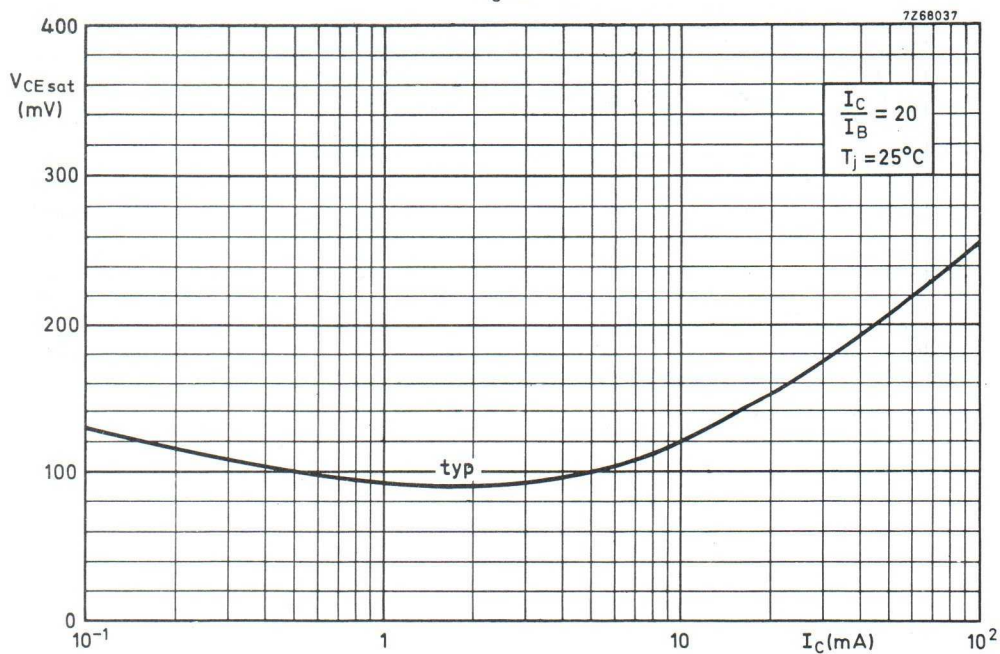


Fig. 5

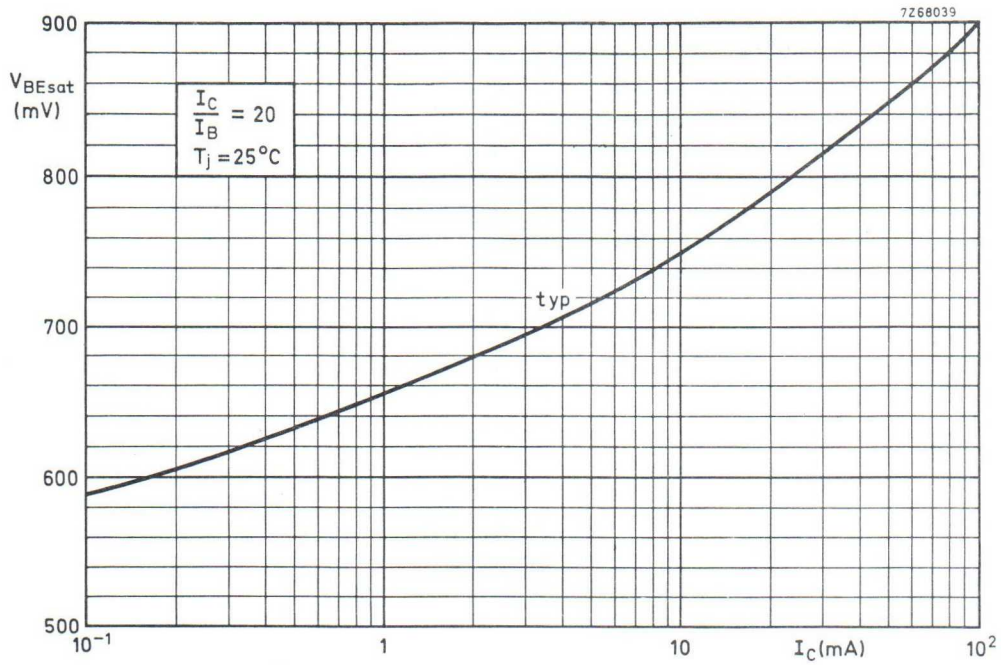


Fig. 6

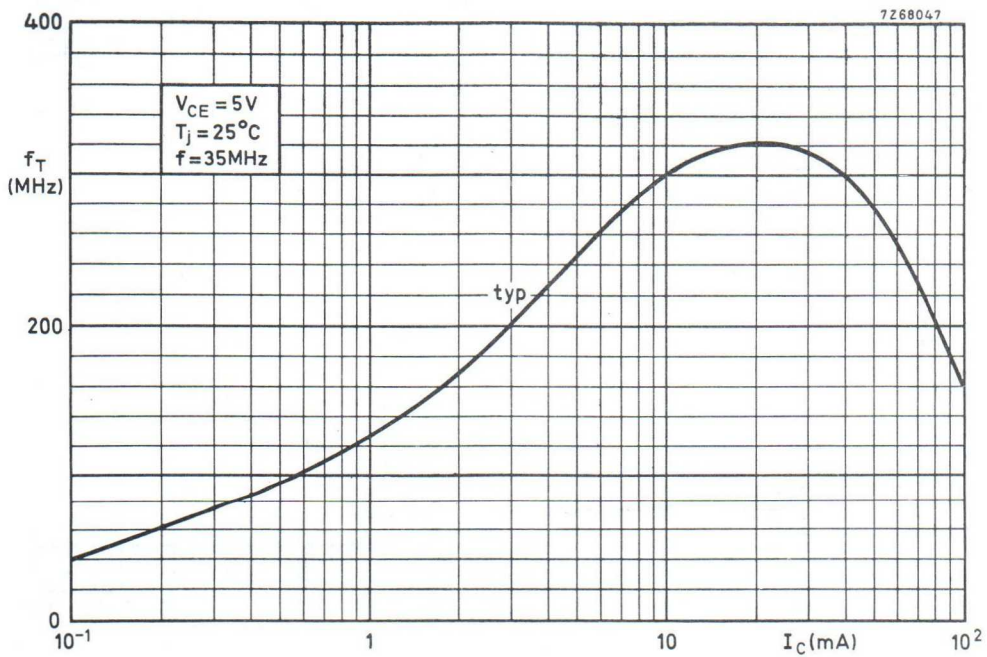


Fig. 7

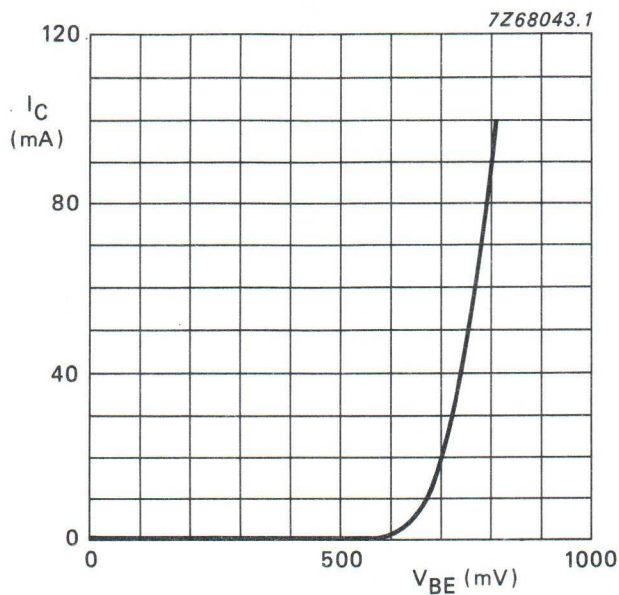


Fig. 8 $V_{CE} = 5 \text{ V}$; $T_j = 25^\circ\text{C}$; typical values.

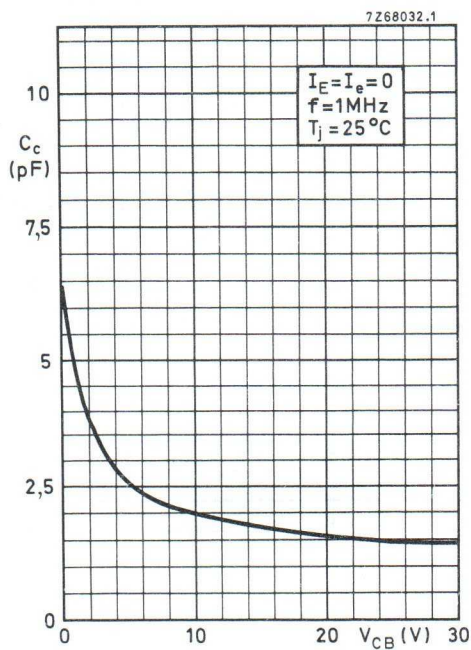


Fig. 9

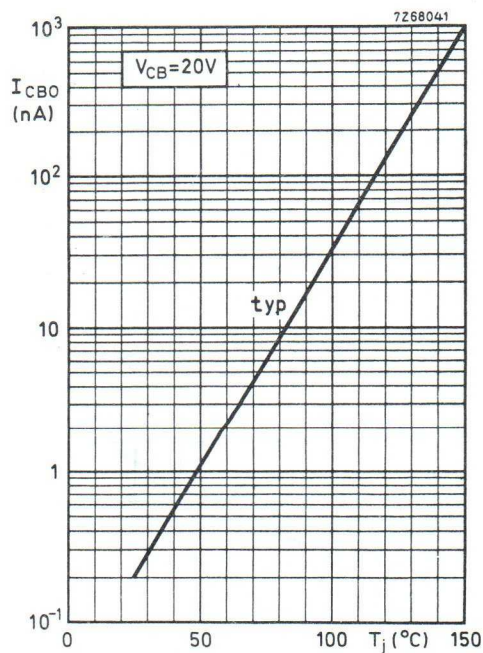


Fig. 10

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	32 V
Collector-emitter voltage (open base)	V_{CEO}	max.	32 V
Collector current (d.c.)	I_C	max.	200 mA
Total power dissipation	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 °C
Transition frequency at $f = 100$ MHz $V_{CE} = 5$ V; $I_C = 10$ mA	f_T	typ.	250 MHz
Noise figure at $f = 1$ kHz $V_{CE} = 5$ V; $I_C = 200$ μ A; $B = 200$ Hz	F	typ.	2 dB

MECHANICAL DATA

Dimensions in mm

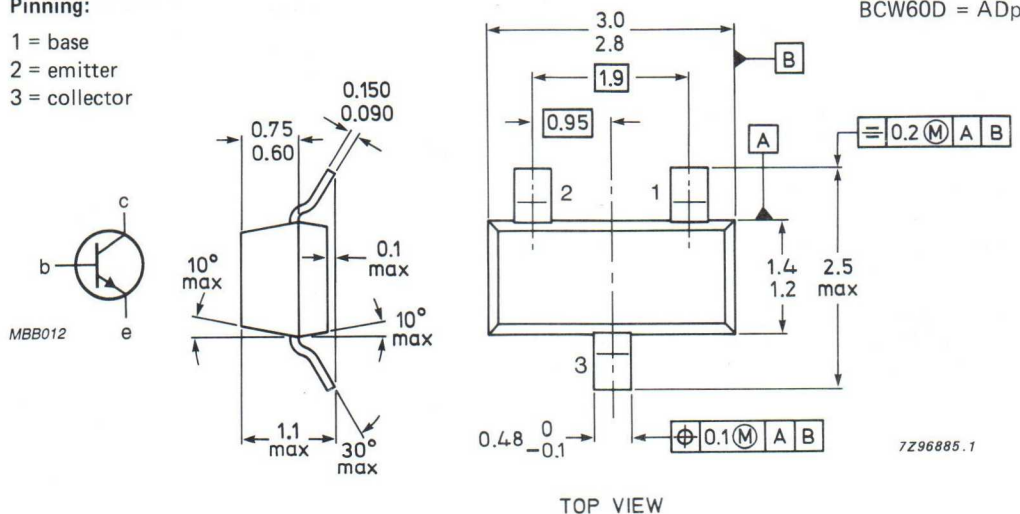
Marking code

Fig. 1 SOT-23.

BCW60A = AAp
BCW60B = ABp
BCW60C = ACp
BCW60D = ADp

Pinning:

- 1 = base
2 = emitter
3 = collector



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	32 V
Collector-emitter voltage (open base)	V_{CEO}	max.	32 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	200 mA
Base current	I_B	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th\ j-a} = 500\text{ K/W}$$

CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector-emitter cut-off current

$V_{BE} = 0; V_{CE} = 32\text{ V}$

$I_{CES} < 20\text{ nA}$

$V_{BE} = 0; V_{CE} = 32\text{ V}; T_{amb} = 150\text{ }^{\circ}\text{C}$

$I_{CES} < 20\text{ }\mu\text{A}$

Emitter-base cut-off current

$I_C = 0; V_{EB} = 4\text{ V}$

$I_{EBO} < 20\text{ nA}$

Saturation voltages

at $I_C = 10\text{ mA}; I_B = 0,25\text{ mA}$

$V_{CEsat} 0,05\text{ to }0,35\text{ V}$

$V_{BEsat} 0,6\text{ to }0,85\text{ V}$

at $I_C = 50\text{ mA}; I_B = 1,25\text{ mA}$

$V_{CEsat} 0,1\text{ to }0,55\text{ V}$

$V_{BEsat} 0,7\text{ to }1,05\text{ V}$

Transition frequency at $f = 100\text{ MHz}$ ▲

$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$

$$f_T > 125\text{ MHz}$$

$$\text{typ. } 250\text{ MHz}$$

Collector capacitance at $f = 1\text{ MHz}$

$I_E = I_e = 0; V_{CB} = 10\text{ V}$

$C_C \text{ typ. } 2,5\text{ pF}$

Emitter capacitance at $f = 1\text{ MHz}$

$I_C = I_c = 0; V_{EB} = 0,5\text{ V}$

$C_e \text{ typ. } 8\text{ pF}$

Noise figure at $R_S = 2\text{ k}\Omega$

$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; f = 1\text{ kHz}; B = 200\text{ Hz}$

$$F \text{ typ. } 2\text{ dB}$$

$$< 6\text{ dB}$$

* Mounted on a ceramic substrate of $8\text{ mm} \times 10\text{ mm} \times 0,7\text{ mm}$.

▲ Measured under pulse conditions.

		BCW60A	60B	60C	60D
D.C. current gain					
$V_{CE} = 5 \text{ V}; I_C = 10 \mu\text{A}$	$h_{FE} >$	—	20	40	100
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}$	$h_{FE} >$	120	180	250	380
	$h_{FE} <$	220	310	460	630
$V_{CE} = 1 \text{ V}; I_C = 50 \text{ mA}$	$h_{FE} >$	50	70	90	100
Input impedance					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{ie} typ.	2,7	3,6	4,5	7,5 $k\Omega$
Reverse voltage transfer ratio					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{re} typ.	1,5	2	2	$3 \cdot 10^{-4}$
Small-signal current gain					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{fe} typ.	200	260	330	520
Output admittance					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{oe} typ.	18	24	30	50 μs
Base-emitter voltage					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}$	V_{BE} typ.	0,55 to 0,75			V
			0,65		V
$V_{CE} = 5 \text{ V}; I_C = 10 \mu\text{A}$	V_{BE} typ.		0,52		V
$V_{CE} = 1 \text{ V}; I_C = 50 \text{ mA}$	V_{BE} typ.		0,78		V

Switching times

$I_{Con} = 10 \text{ mA}$; $I_{Bon} = -I_{Boff} = 1 \text{ mA}$
 $V_{CC} = 10 \text{ V}$; $R_L = 990 \Omega$

turn-on time ($t_d + t_r$)

t_{on} typ. 85 ns
 $< 150 \text{ ns}$

turn-off time ($t_s + t_f$)

t_{off} typ. 480 ns
 $< 800 \text{ ns}$

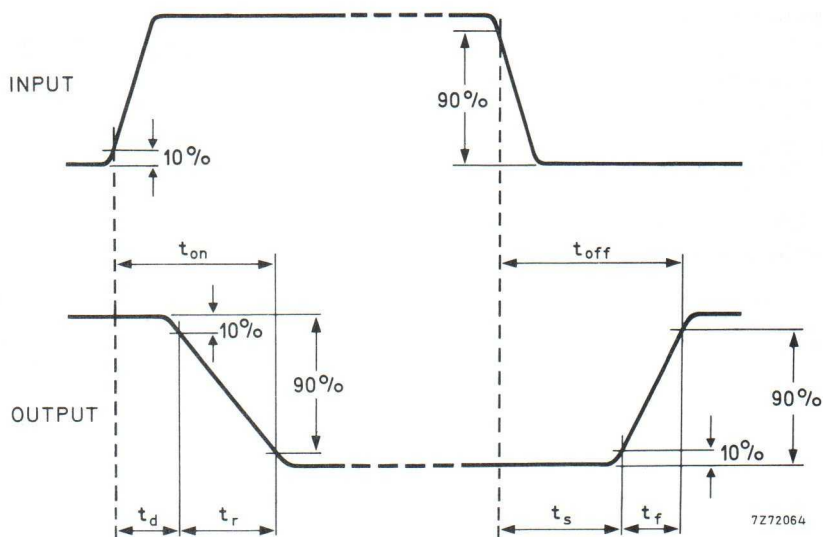


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

QUICK REFERENCE DATA

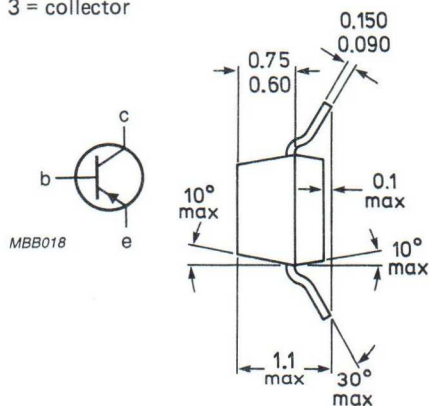
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Total power dissipation	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 °C
Transition frequency at $f = 100$ MHz $-V_{CE} = 5$ V; $-I_C = 10$ mA	f_T	typ.	180 MHz
Noise figure at $f = 1$ kHz $-V_{CE} = 5$ V; $-I_C = 200$ μ A	F	typ.	2 dB

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

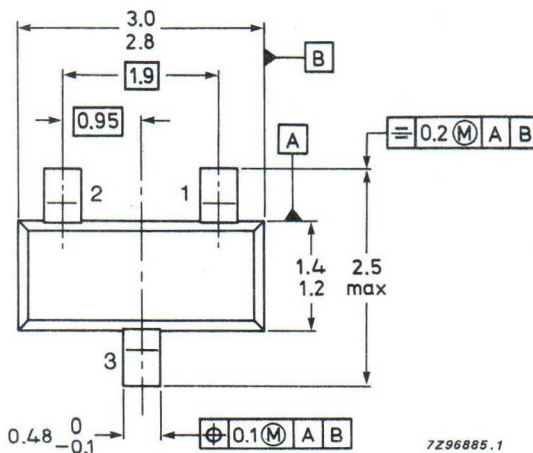
- 1 = base
2 = emitter
3 = collector



Dimensions in mm

Marking code

BCW61A = BA_p
BCW61B = BB_p
BCW61C = BC_p
BCW61D = BD_p



TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Base current	$-I_B$	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient *	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector-emitter cut-off current

 $V_{EB} = 0; -V_{CE} = 32\text{ V}$ $-I_{CES} < 20\text{ nA}$ $V_{EB} = 0; -V_{CE} = 32\text{ V}; T_{amb} = 150\text{ }^{\circ}\text{C}$ $-I_{CES} < 20\text{ }\mu\text{A}$

Emitter-base cut-off current

 $I_C = 0; -V_{EB} = 4\text{ V}$ $-I_{EBO} < 20\text{ nA}$

Saturation voltages

 $-I_C = 10\text{ mA}; -I_B = 0,25\text{ mA}$ $-V_{CEsat}$ 0,06 to 0,25 V $-V_{BEsat}$ 0,6 to 0,85 V $-I_C = 50\text{ mA}; -I_B = 1,25\text{ mA}$ $-V_{CEsat}$ 0,12 to 0,55 V $-V_{BEsat}$ 0,68 to 1,05 VTransition frequency at $f = 100\text{ MHz}$ ▲ $-V_{CE} = 5\text{ V}; -I_C = 10\text{ mA}$ f_T typ. 180 MHzCollector capacitance at $f = 1\text{ MHz}$ $-V_{CB} = 10\text{ V}; I_E = I_C = 0$ C_C typ. 4,5 pFEmitter capacitance at $f = 1\text{ MHz}$ $-V_{EB} = 0,5\text{ V}; I_C = I_C = 0$ C_e typ. 11 pFNoise figure at $R_S = 2\text{ k}\Omega$ $-V_{CE} = 5\text{ V}; -I_C = 200\text{ }\mu\text{A}; B = 200\text{ Hz}$ F typ. 2 dB
< 6 dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

		BCW61A	61B	61C	61D
D.C. current gain					
$-V_{CE} = 5 \text{ V}; -I_C = 10 \mu\text{A}$	$h_{FE} >$	—	30	40	100
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}$	$h_{FE} >$	120	180	250	380
	$h_{FE} <$	220	310	460	630
$-V_{CE} = 1 \text{ V}; -I_C = 50 \text{ mA}$	$h_{FE} >$	60	80	100	110
Input impedance					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{ie} typ.	2,7	3,6	4,5	7,5 $k\Omega$
Reverse voltage transfer ratio					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{re} typ.	1,5	2	2	3 10^{-4}
Small-signal current gain					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{fe} typ.	200	260	330	520
Output admittance					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{oe} typ.	18	24	30	50 μS
Base-emitter voltage					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}$	V_{BE} typ.	0,6 to 0,75			V
		0,65			V
$-V_{CE} = 5 \text{ V}; -I_C = 10 \mu\text{A}$	V_{BE} typ.	0,55			V
$-V_{CE} = 1 \text{ V}; -I_C = 50 \text{ mA}$	V_{BE} typ.	0,72			V

Switching times

 $-I_{Con} = 10 \text{ mA}; -I_{Bon} = I_{Boff} = 1 \text{ mA}$
 $-V_{CC} = 10 \text{ V}; R_L = 990 \Omega$
turn-on time ($t_d + t_r$)turn-off time ($t_s + t_f$)

t_{on}	typ.	85 ns
	<	150 ns
t_{off}	typ.	480 ns
	<	800 ns

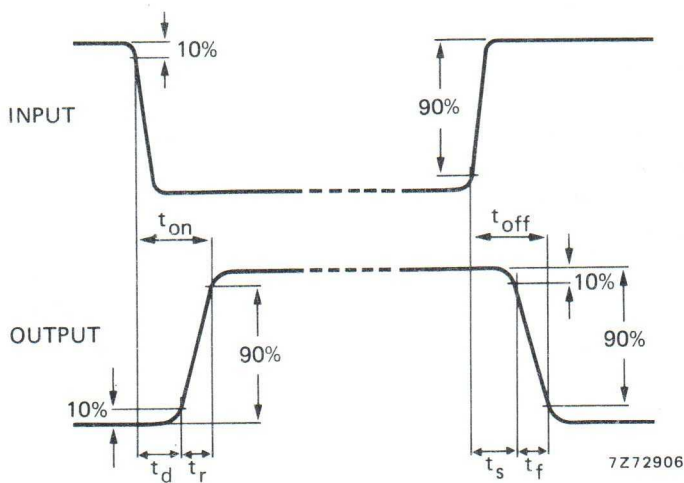


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

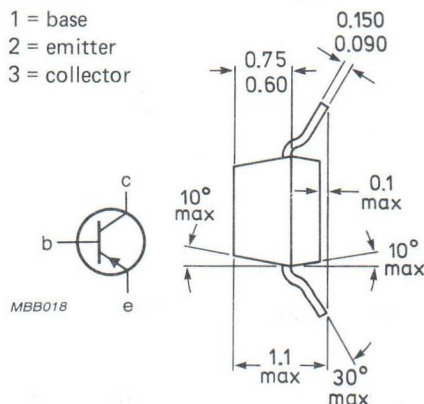
		BCW69	BCW70
D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$ $-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	120 260	215 500
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	50	V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	45	V
Collector current (peak value)	$-I_{CM}$ max.	200	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot} max.	250	mW
Junction temperature	T_j max.	150	$^{\circ}\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T typ.	150	MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V};$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	F	10	dB

MECHANICAL DATA

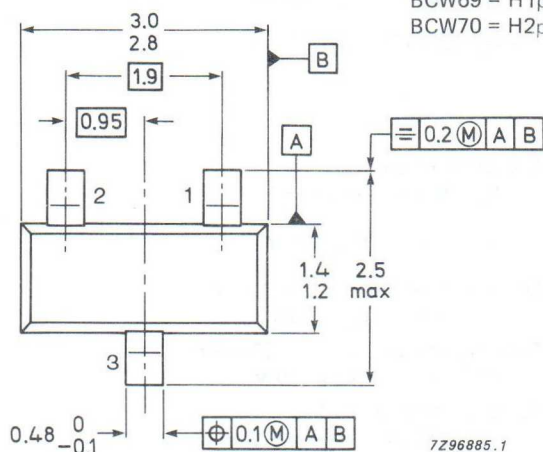
Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm



Marking code

BCW69 = H1p
BCW70 = H2p

Reverse pinning types are available on request.

TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	50 V
Collector-emitter voltage (open base) $-I_C = 2 \text{ mA}$	$-V_{CEO}$	max.	45 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	$-65 \text{ to } +150 \text{ }^{\circ}\text{C}$	
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th j-a}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 20 \text{ V}$

$-I_{CBO} < 100 \text{ nA}$

$I_E = 0; -V_{CB} = 20 \text{ V}; T_j = 100 \text{ }^{\circ}\text{C}$

$-I_{CBO} < 10 \text{ } \mu\text{A}$

Base-emitter voltage

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

$-V_{BE} \text{ 600 to 750 mV}$

Saturation voltages

$-V_{CEsat} \text{ typ. 80 mV}$

$< 300 \text{ mV}$

$-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$

$-V_{BEsat} \text{ typ. 720 mV}$

$-I_C = 50 \text{ mA}; -I_B = 2,5 \text{ mA}$

$-V_{CEsat} \text{ typ. 150 mV}$

$-V_{BEsat} \text{ typ. 810 mV}$

D.C. current gain

$-I_C = 10 \text{ } \mu\text{A}; -V_{CE} = 5 \text{ V}$

		BCW69	BCW70
h_{FE}	typ.	90	150
	$>$	120	215
	$<$	260	500
C_c	typ.	4,5	pF
f_T	typ.	150	MHz
F	$<$	10	dB

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

Collector capacitance at $f = 1 \text{ MHz}$

$I_E = I_c = 0; -V_{CB} = 10 \text{ V}$

Transition frequency at $f = 35 \text{ MHz}$

$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$

Noise figure at $R_S = 2 \text{ k}\Omega$

$-I_C = 200 \text{ } \mu\text{A}; -V_{CE} = 5 \text{ V}$

$f = 1 \text{ kHz}; B = 200 \text{ Hz}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

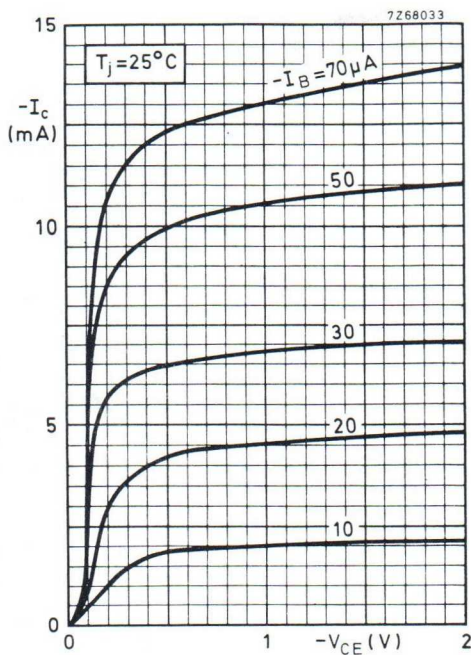


Fig. 2.

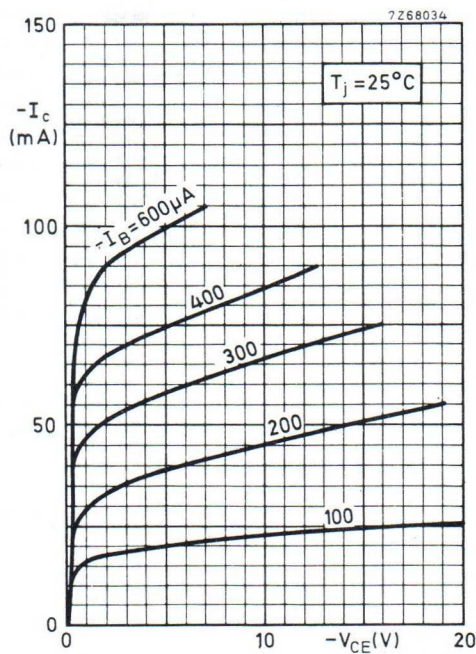


Fig. 3.

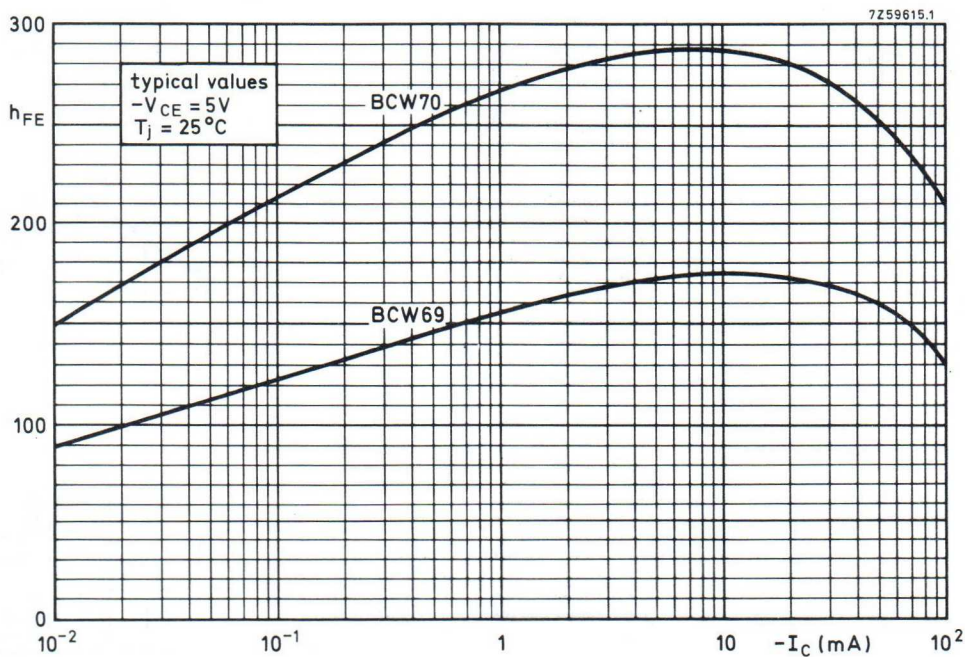


Fig. 4 D.C. current gain.

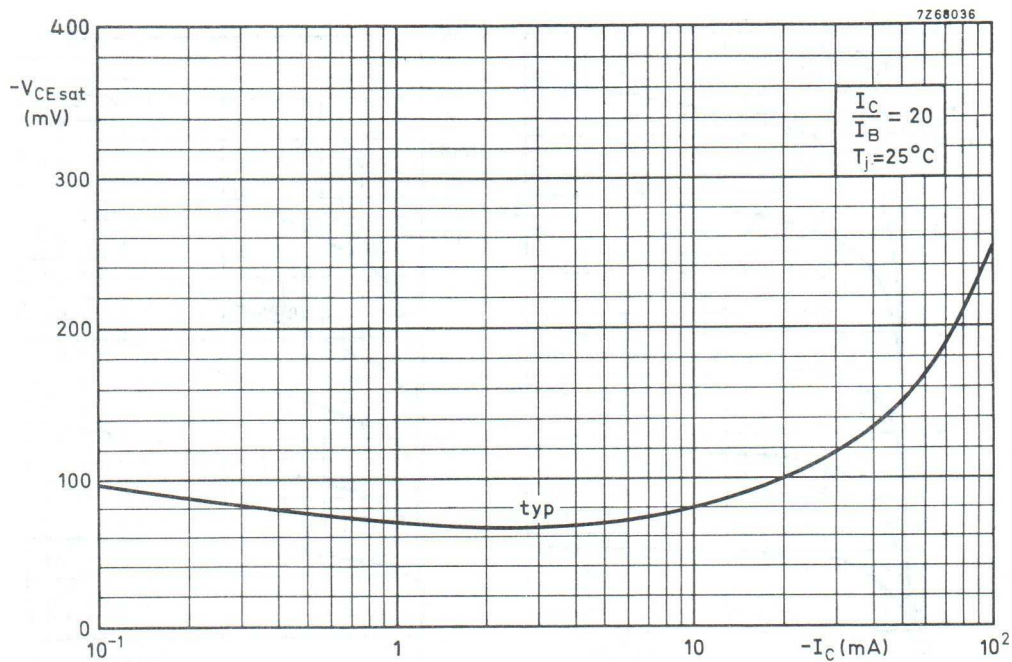


Fig. 5.

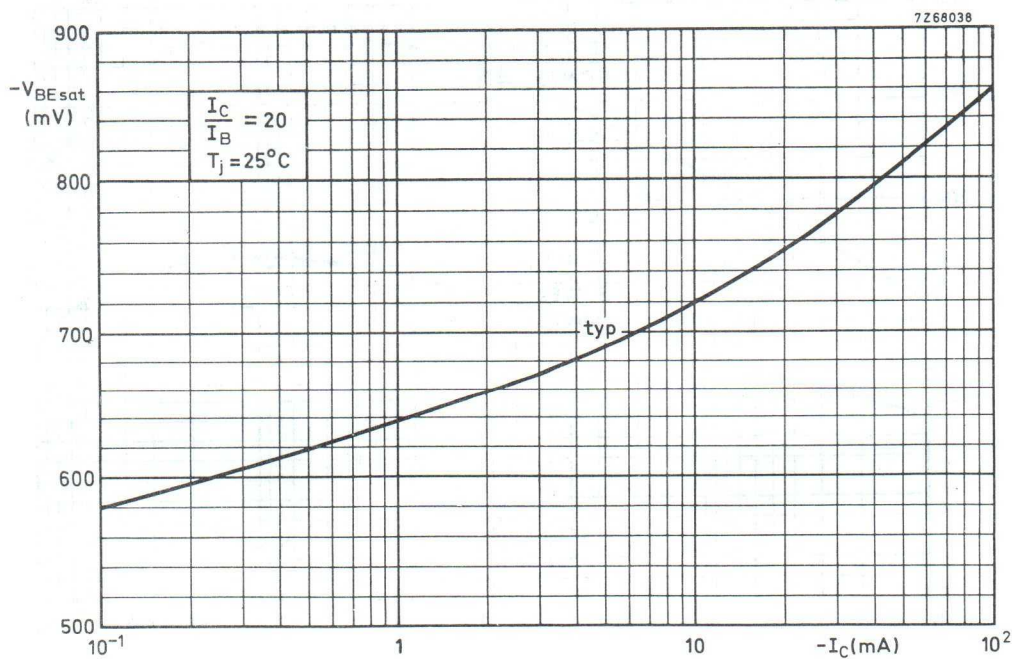


Fig. 6.

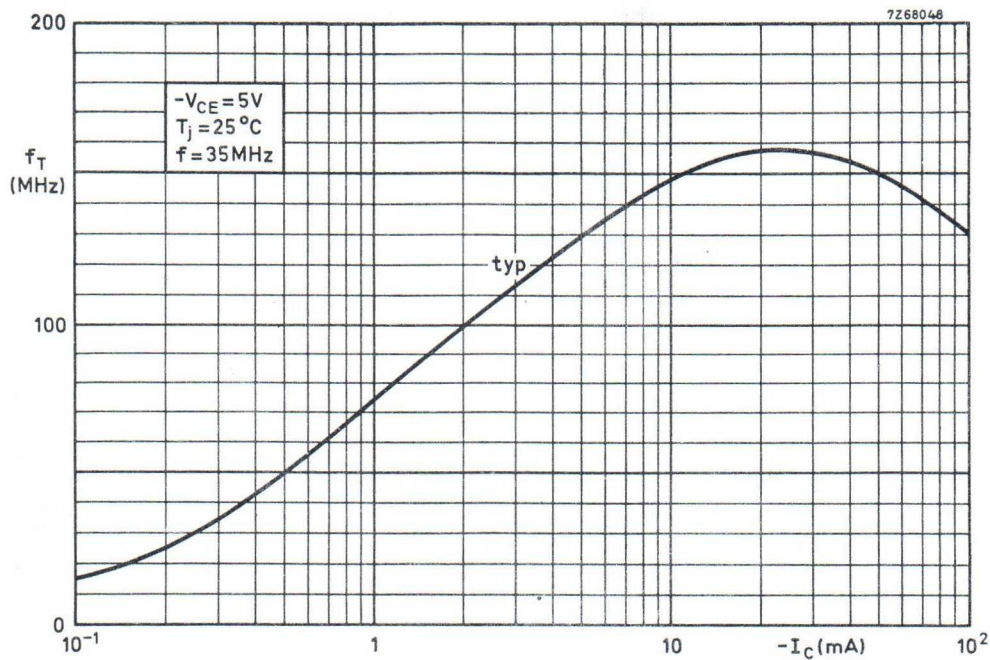
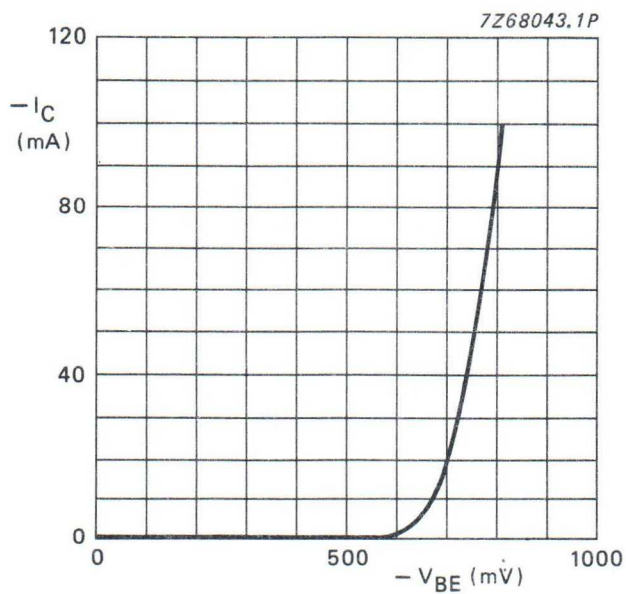


Fig. 7.

Fig. 8.; $-V_{CE} = 5V$; $T_j = 25^\circ C$; typical values.

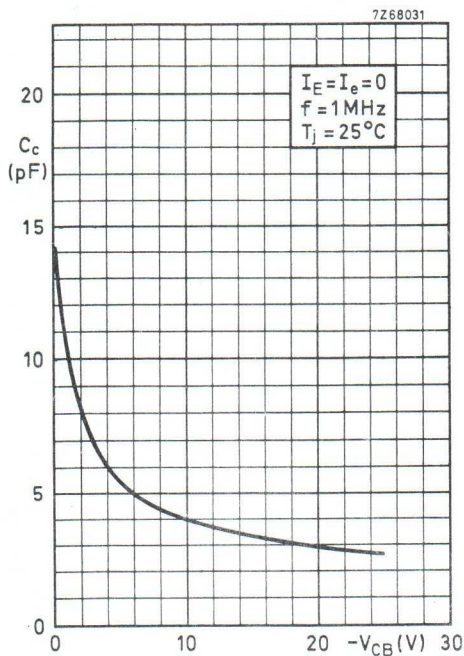


Fig. 9.

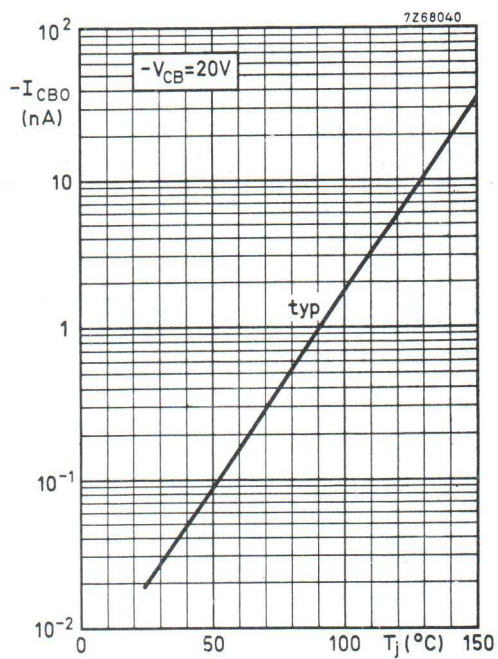


Fig. 10.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

D.C. current gain at $T_j = 25^\circ\text{C}$
 $I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$

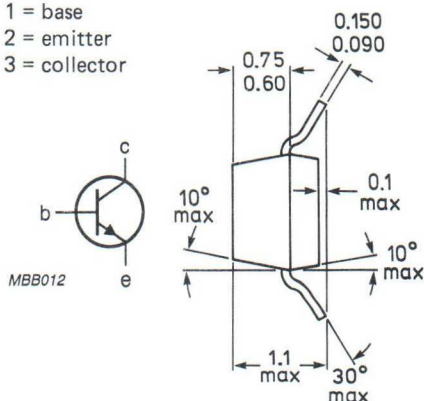
		BCW71	BCW72
h_{FE}	$>$	110	200
	$<$	220	450
Collector-base voltage (open emitter)	V_{CBO}	max. 50	V
Collector-emitter voltage (open base)	V_{CEO}	max. 45	V
Collector current (peak value)	I_{CM}	max. 200	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max. 250	mW
Junction temperature	T_j	max. 150	$^\circ\text{C}$
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ. 300	MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$	F	$<$ 10	dB

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

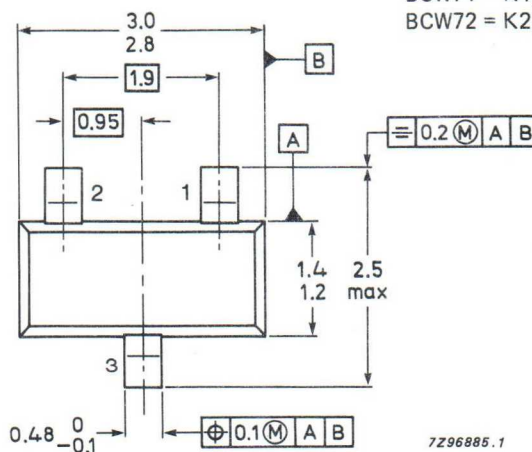
- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm

Marking code

BCW71 = K1p
 BCW72 = K2p



Reverse pinning types are available on request.

TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	45 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		$-65 \text{ to } +150^\circ\text{C}$
Junction temperature	T_j	max.	150°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 20 \text{ V}$

$I_{CBO} < 100 \text{ nA}$

$I_E = 0; V_{CB} = 20 \text{ V}; T_j = 100^\circ\text{C}$

$I_{CBO} < 10 \mu\text{A}$

Base emitter voltage

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

$V_{BE} \quad 550 \text{ to } 700 \text{ mV}$

Saturation voltages

$I_C = 10 \text{ mA}; I_B = 0,5 \text{ mA}$

$V_{CEsat} \quad \text{typ. } 120 \text{ mV}$
 $< 250 \text{ mV}$

$I_C = 50 \text{ mA}; I_B = 2,5 \text{ mA}$

$V_{BEsat} \quad \text{typ. } 750 \text{ mV}$
 $V_{CEsat} \quad \text{typ. } 210 \text{ mV}$
 $V_{BEsat} \quad \text{typ. } 850 \text{ mV}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

$$I_C = 10 \mu\text{A}; V_{CE} = 5 \text{ V}$$

$$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_C = 0; V_{CB} = 10 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$$

Noise figure at $R_S = 2 \text{ k}\Omega$

$$I_C = 200 \mu\text{A}; V_{CE} = 5 \text{ V}$$

$$f = 1 \text{ kHz}; B = 200 \text{ Hz}$$

		BCW71	BCW72
h_{FE}	typ.	90	150
h_{FE}	$>$	110	200
h_{FE}	$<$	220	450
C_C	typ.	2,5	pF
f_T	typ.	300	MHz
F	$<$	10	dB

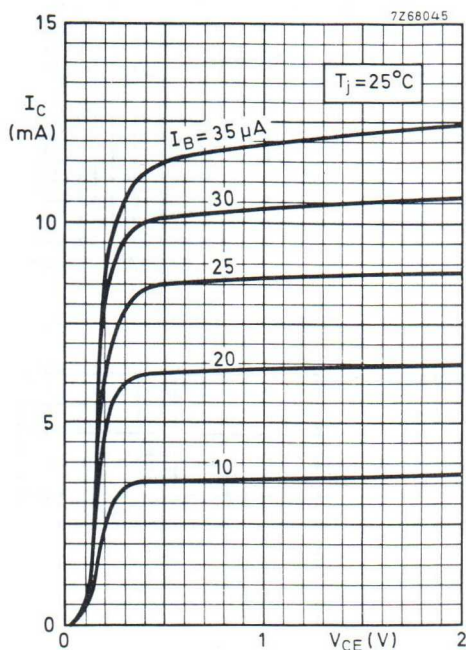


Fig. 2

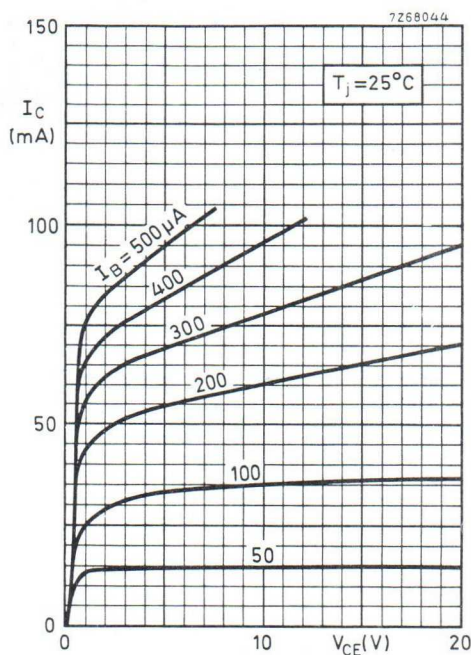


Fig. 3

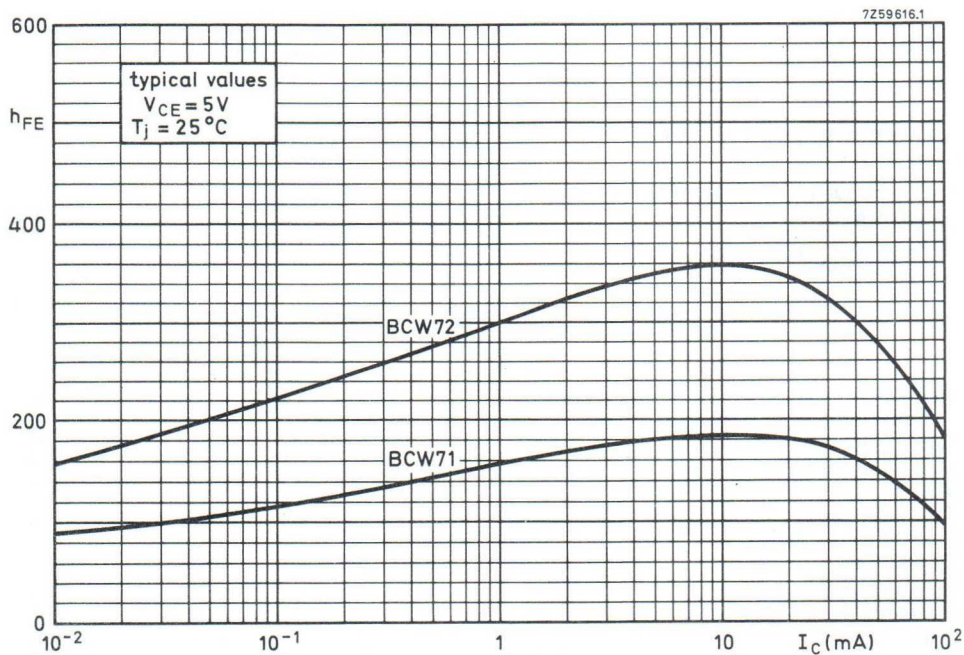


Fig. 4 D.C. current gain.

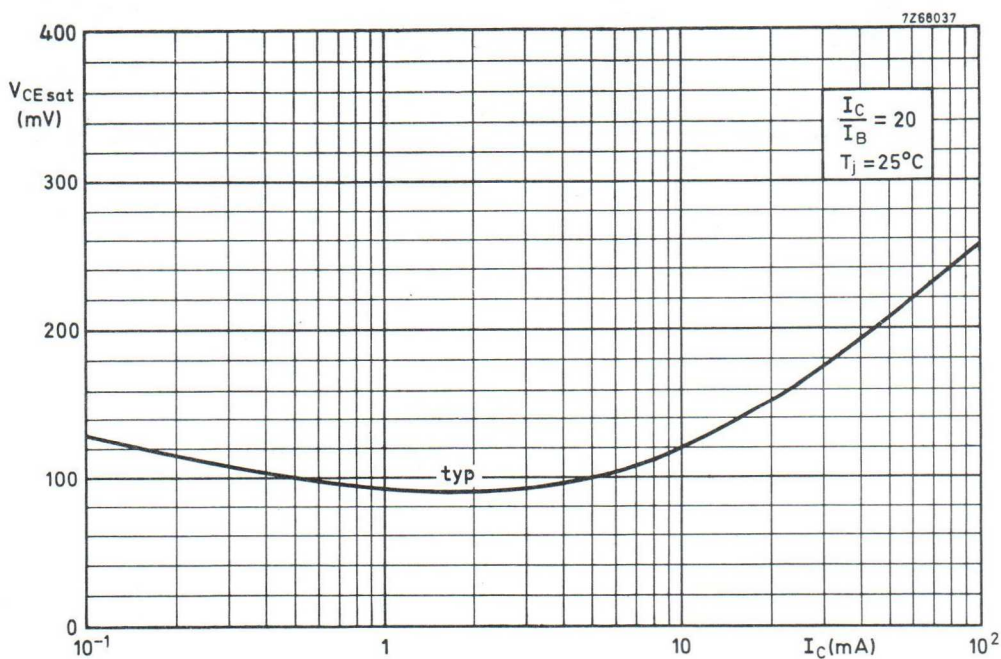


Fig. 5

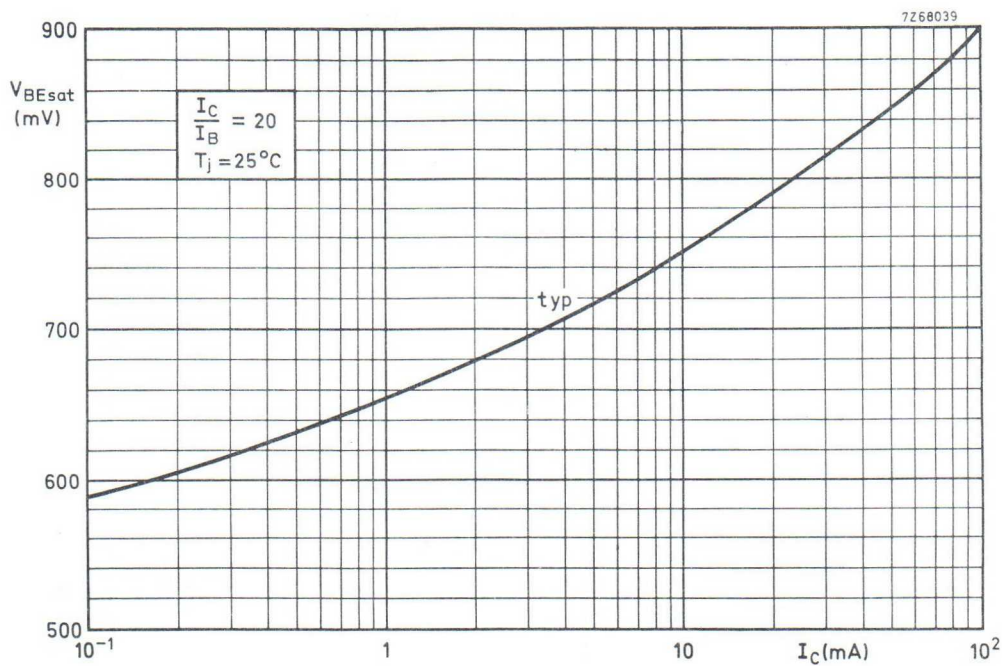


Fig. 6

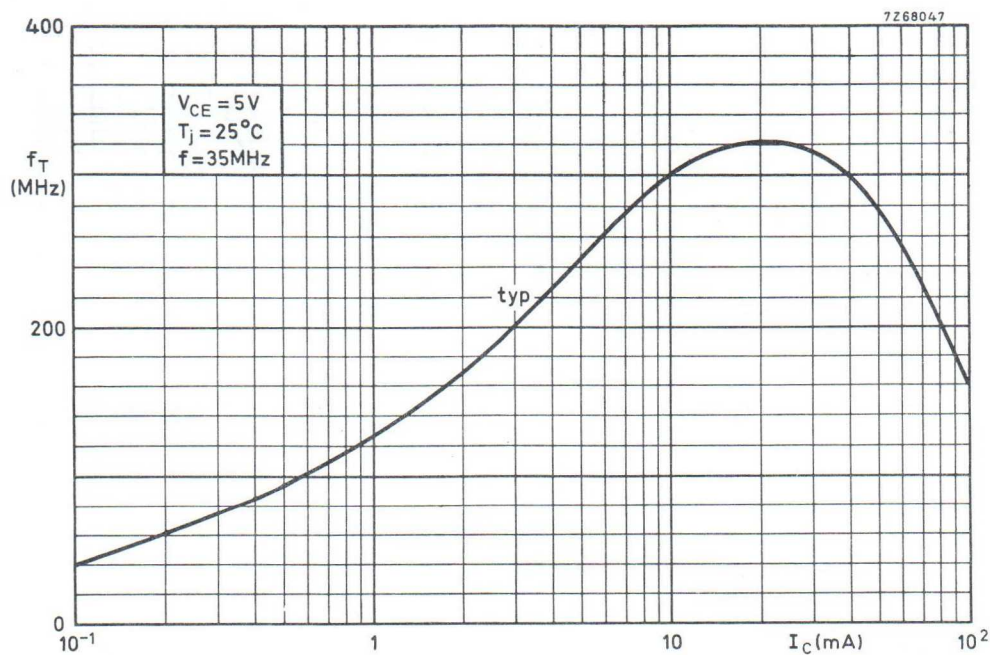


Fig. 7

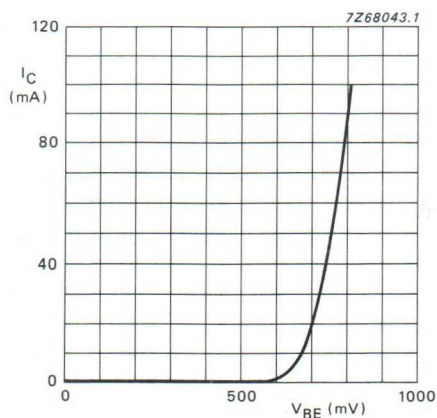


Fig. 8 $V_{CE} = 5 \text{ V}$; $T_j = 25^\circ\text{C}$; typical values.

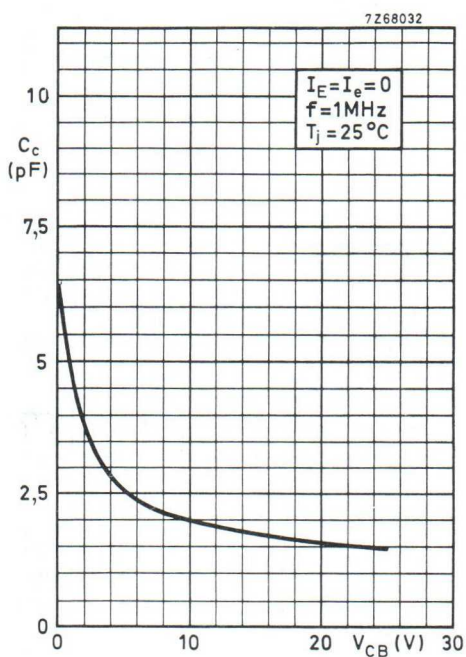


Fig. 9

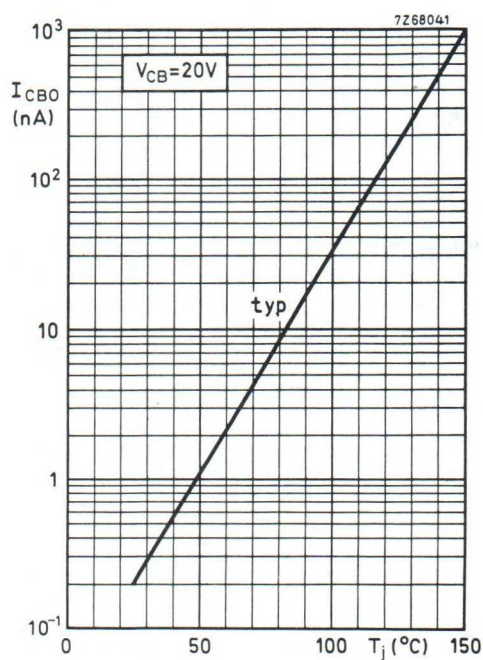


Fig. 10

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

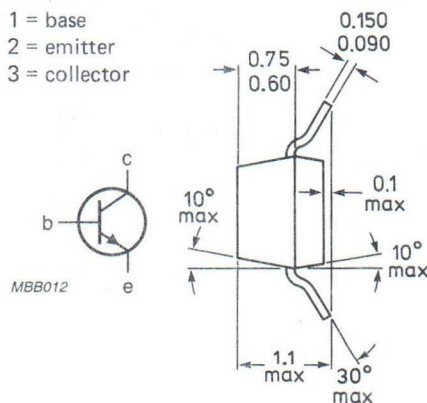
Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45 V
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$ $I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	$>$ $<$	420 800
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	300 MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	F	$<$	10 dB

MECHANICAL DATA

Fig. 1 SOT-23.

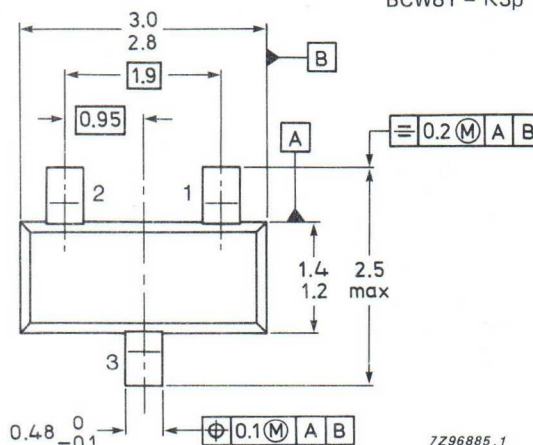
Pinning:

- 1 = base
2 = emitter
3 = collector



Dimensions in mm

Marking code

$$BCW81 = K3p$$


TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base) $I_C = 2 \text{ mA}$	V_{CEO}	max.	45 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	—65 to + 150	$^\circ\text{C}$
Junction temperature	T_j	max.	150 $^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th \text{ j-a}} = 500 \text{ K/W}$$

CHARACTERISTICS

 $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 20 \text{ V}$

$I_{CBO} < 100 \text{ nA}$

$I_E = 0; V_{CB} = 20 \text{ V}; T_j = 100 \text{ }^\circ\text{C}$

$I_{CBO} < 10 \text{ } \mu\text{A}$

Base emitter voltage

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

$V_{BE} \quad 550 \text{ to } 700 \text{ mV}$

Saturation voltages

$I_C = 10 \text{ mA}; I_B = 0,5 \text{ mA}$

$$V_{CEsat} \quad \begin{matrix} \text{typ.} & 120 \text{ mV} \\ < & 250 \text{ mV} \end{matrix}$$

$I_C = 50 \text{ mA}; I_B = 2,5 \text{ mA}$

$$\begin{matrix} V_{BEsat} & \text{typ.} & 750 \text{ mV} \\ V_{CEsat} & \text{typ.} & 210 \text{ mV} \\ V_{BEsat} & \text{typ.} & 850 \text{ mV} \end{matrix}$$

D.C. current gain

$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$

$$h_{FE} \quad \begin{matrix} > & 420 \\ < & 800 \end{matrix}$$

Collector capacitance at $f = 1 \text{ MHz}$

$I_E = I_e = 0; V_{CB} = 10 \text{ V}$

$C_c \quad \text{typ.} \quad 2,5 \text{ pF}$

Transition frequency at $f = 35 \text{ MHz}$

$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$

$f_T \quad \text{typ.} \quad 300 \text{ MHz}$

Noise figure at $R_S = 2 \text{ k}\Omega$

$I_C = 200 \text{ } \mu\text{A}; V_{CE} = 5 \text{ V}$

$f = 1 \text{ kHz}; B = 200 \text{ Hz}$

$F < 10 \text{ dB}$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

QUICK REFERENCE DATA

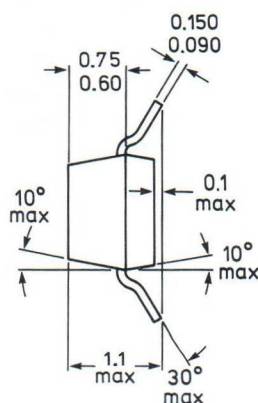
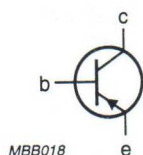
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60 V
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$ $-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$	h_{FE}	$>$ $<$	120 260
Transition frequency at $f = 35\text{ MHz}$ $-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$	f_T	typ.	150 MHz
Noise figure at $R_S = 2\text{ k}\Omega$ $-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V};$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	F	$<$	10 dB

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

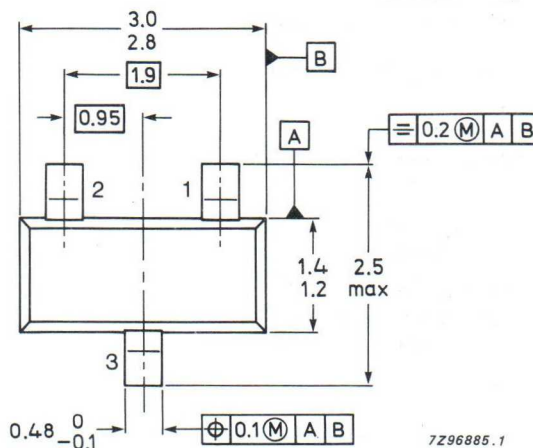
- 1 = base
- 2 = emitter
- 3 = collector



Dimensions in mm

Marking code

BCW89 = H3p



TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	60 V
Collector-emitter voltage (open base) $-I_C = 2 \text{ mA}$	$-V_{CEO}$	max.	60 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	$-65 \text{ to } +150 \text{ }^\circ\text{C}$	
Junction temperature	T_j	max.	150 $^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th \text{ j-a}} = 500 \text{ K/W}$$

CHARACTERISTICS $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 20 \text{ V}$

$-I_{CBO} < 100 \text{ nA}$

$I_E = 0; -V_{CB} = 20 \text{ V}; T_j = 100 \text{ }^\circ\text{C}$

$-I_{CBO} < 10 \text{ } \mu\text{A}$

Base-emitter voltage

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$

$-V_{BE} \quad 600 \text{ to } 750 \text{ mV}$

Saturation voltages

$-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$

$$\begin{array}{ll} -V_{CEsat} & \text{typ. } 80 \text{ mV} \\ & < 300 \text{ mV} \end{array}$$

$-I_C = 50 \text{ mA}; -I_B = 2,5 \text{ mA}$

$$\begin{array}{ll} -V_{BEsat} & \text{typ. } 720 \text{ mV} \\ -V_{CEsat} & \text{typ. } 150 \text{ mV} \\ -V_{BEsat} & \text{typ. } 810 \text{ mV} \end{array}$$

D.C. current gain

$-I_C = 10 \text{ } \mu\text{A}; -V_{CE} = 5 \text{ V}$

$h_{FE} \quad \text{typ. } 90$

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$

$$\begin{array}{ll} h_{FE} & > 120 \\ & < 260 \end{array}$$

Collector capacitance at $f = 1 \text{ MHz}$

$I_E = I_C = 0; -V_{CB} = 10 \text{ V}$

$C_C \quad \text{typ. } 4,5 \text{ pF}$

Transition frequency at $f = 35 \text{ MHz}$

$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$

$f_T \quad \text{typ. } 150 \text{ MHz}$

Noise figure at $R_S = 2 \text{ k}\Omega$

$-I_C = 200 \text{ } \mu\text{A}; -V_{CE} = 5 \text{ V}$

$f = 1 \text{ kHz}; B = 200 \text{ Hz}$

$F < 10 \text{ dB}$

* Mounted on a ceramic substrate of $8 \text{ mm} \times 10 \text{ mm} \times 0,7 \text{ mm}$.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a SOT-23 plastic envelope, intended for application in thick and thin-film circuits. These transistors are intended for general purposes as well as saturated switching and driver applications for industrial service.

N-P-N complements are BCX19 and BCX20 respectively.

QUICK REFERENCE DATA

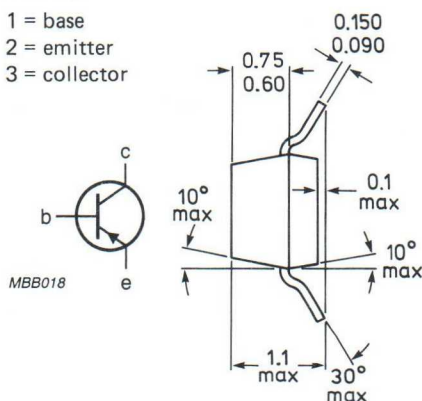
		BCX17	BCX18	
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$ max.	50	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	45	25	V
Collector current (peak value)	$-I_{CM}$ max.	1000		mA
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	P_{tot} max.	250		mW
Junction temperature	T_j max.	150		$^{\circ}\text{C}$
D.C. current gain	h_{FE}	100 to 600		
Transition frequency	f_T typ.	100		MHz
$-I_C = 100\text{ mA}; -V_{CE} = 1\text{ V}$				
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}; f = 35\text{ MHz}$				

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

- 1 = base
2 = emitter
3 = collector

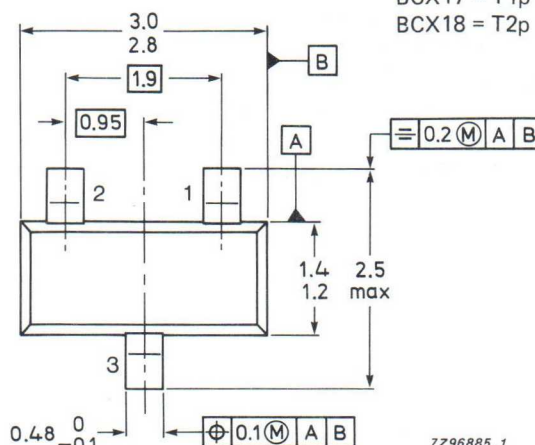


MBB018

Dimensions in mm

Marking code

BCX17 = T1p
BCX18 = T2p



7Z96885.1

TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX17	BCX18	
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	50	30	V
Collector-emitter voltage $-I_C = 10$ mA (see Fig. 2)	$-V_{CEO}$	max.	45	25	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	500		mA
Collector current (peak value)	$-I_{CM}$	max.	1000		mA
Emitter current (peak value)	I_{EM}	max.	1000		mA
Base current (d.c.)	$-I_B$	max.	100		mA
Base current (peak value)	$-I_{BM}$	max.	200		mA
Total power dissipation up to $T_{amb} = 25$ °C*	P_{tot}	max.	250		mW
Storage temperature	T_{stg}		-65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient $R_{th\ j-a} = 500$ K/W

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Collector cut-off current $I_E = 0$; $-V_{CB} = 20$ V	$-I_{CBO}$	<	100	nA
$I_E = 0$; $-V_{CB} = 20$ V; $T_j = 150$ °C	$-I_{CBO}$	<	5	μA
Emitter cut-off current $I_C = 0$; $-V_{EB} = 5$ V	$-I_{EBO}$	<	10	μA
Base-emitter voltage ▲ $-I_C = 500$ mA; $-V_{CE} = 1$ V	$-V_{BE}$	<	1,2	V
Saturation voltage $-I_C = 500$ mA; $-I_B = 50$ mA	$-V_{CEsat}$	<	620	mV

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ $-V_{BE}$ decreases by about 2 mV/°C with increasing temperature.

D.C. current gain

$$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$$

$$-I_C = 300 \text{ mA}; -V_{CE} = 1 \text{ V}$$

$$-I_C = 500 \text{ mA}; -V_{CE} = 1 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$$

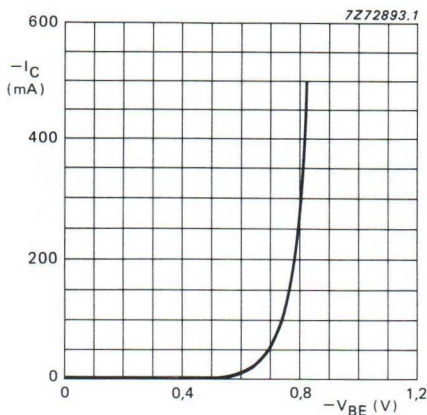
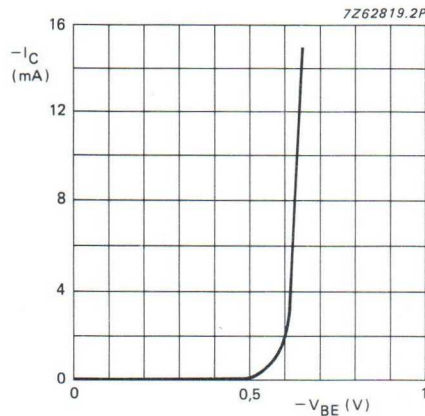
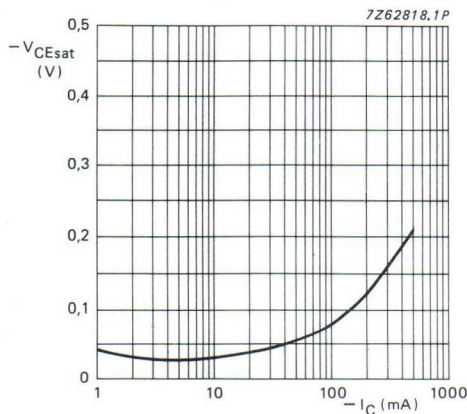
$$h_{FE} \quad 100 \text{ to } 600$$

$$h_{FE} > 70$$

$$h_{FE} > 40$$

$$f_T \quad \text{typ.} \quad 100 \text{ MHz}$$

$$C_C \quad \text{typ.} \quad 8 \text{ pF}$$

Fig. 2 $-V_{CE} = 1 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; typical values.Fig. 3 $V_{CE} = 5 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; typical values.Fig. 4 $I_C/I_B = 10$; $T_j = 25 \text{ }^\circ\text{C}$; typical values.

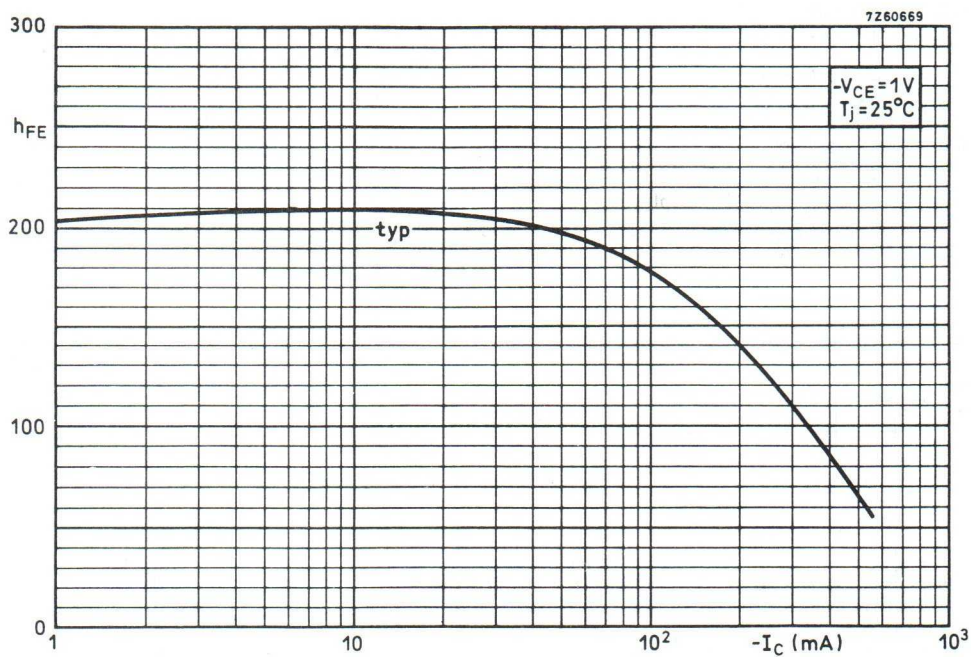


Fig. 5

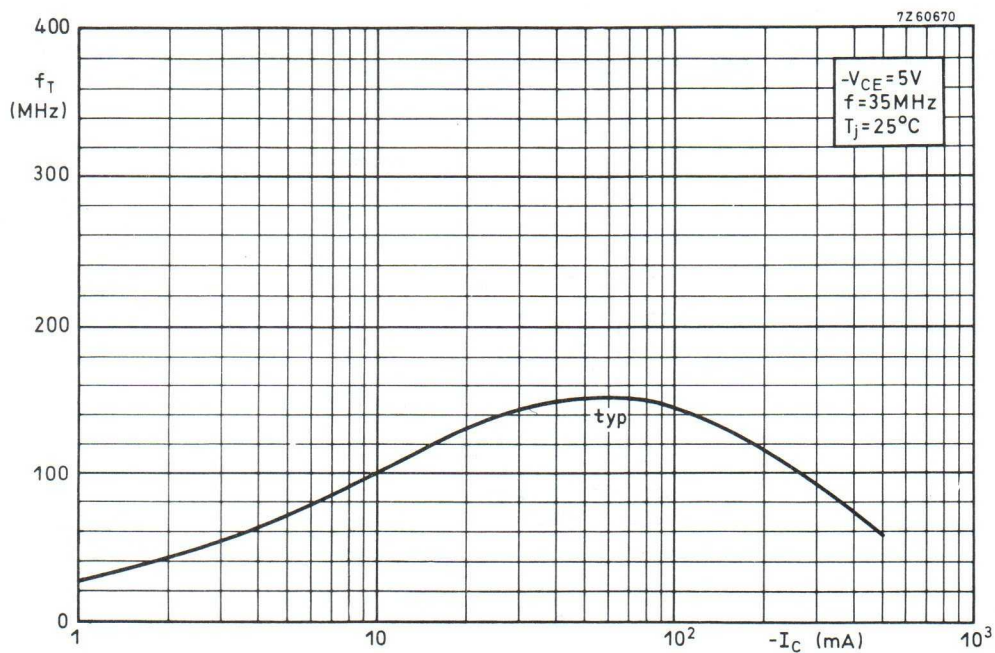


Fig. 6

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a SOT-23 plastic envelope, intended for application in thick and thin-film circuits. These transistors are intended for general purposes as well as saturated switching and driver applications for industrial service.

P-N-P complements are BCX17 and BCX18 respectively.

QUICK REFERENCE DATA

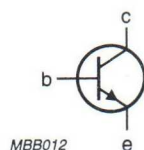
			BCX19	BCX20	
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	25	V
Collector current (peak value)	I_{CM}	max.	1000		mA
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	P_{tot}	max.	250		mW
Junction temperature	T_j	max.	150		$^{\circ}\text{C}$
D.C. current gain $I_C = 100\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}		100 to 600		
Transition frequency $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 35\text{ MHz}$	f_T	typ.	200		MHz

MECHANICAL DATA

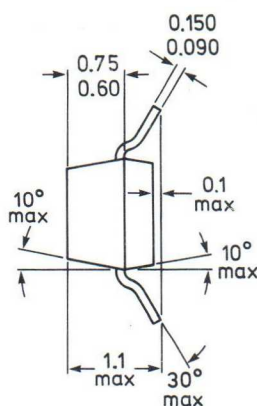
Fig. 1 SOT-23.

Pinning:

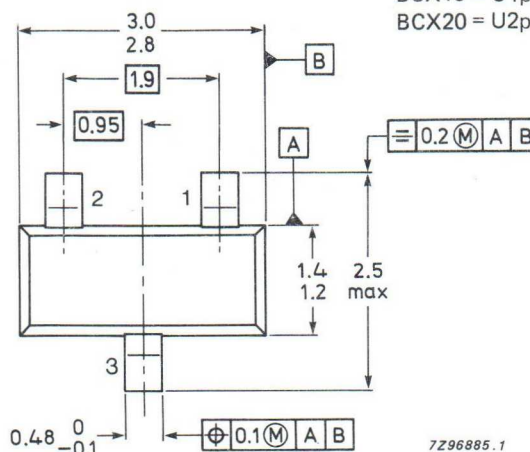
- 1 = base
- 2 = emitter
- 3 = collector



MBB012



Dimensions in mm



TOP VIEW

Reverse pinning types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX19	BCX20	
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base) $I_C = 10 \text{ mA}$	V_{CEO}	max.	45	25	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	V
Collector current (d.c.)	I_C	max.	500		mA
Collector current (peak value)	I_{CM}	max.	1000		mA
Emitter current (peak value)	$-I_{EM}$	max.	1000		mA
Base current (d.c.)	I_B	max.	100		mA
Base current (peak value)	I_{BM}	max.	200		mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}^*$	P_{tot}	max.	250		mW
Storage temperature	T_{stg}		$-65 \text{ to } +150$		$^\circ\text{C}$
Junction temperature	T_j	max.	150		$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$$R_{th \text{ j-a}} = 500 \text{ K/W}$$

CHARACTERISTICS

$T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current $I_E = 0; V_{CB} = 20 \text{ V}$	I_{CBO}	<	100	nA
$I_E = 0; V_{CB} = 20 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$	I_{CBO}	<	5	μA
Emitter cut-off current $I_C = 0; V_{EB} = 5 \text{ V}$	I_{EBO}	<	10	μA
Base emitter voltage ▲ $I_C = 500 \text{ mA}; V_{CE} = 1 \text{ V}$	V_{BE}	<	1,2	V
Saturation voltage $I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	V_{CEsat}	<	620	mV

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ V_{BE} decreases by about 2 mV/ $^\circ\text{C}$ with increasing temperature.

D.C. current gain

$$I_C = 100 \text{ mA}; V_{CE} = 1 \text{ V}$$

$$I_C = 300 \text{ mA}; V_{CE} = 1 \text{ V}$$

$$I_C = 500 \text{ mA}; V_{CE} = 1 \text{ V}$$

Transition frequency at $f = 35 \text{ MHz}$

$$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$$

Collector capacitance at $f = 1 \text{ MHz}$

$$I_E = I_e = 0; V_{CB} = 10 \text{ V}$$

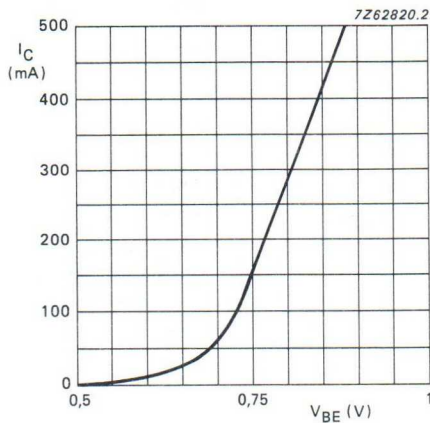
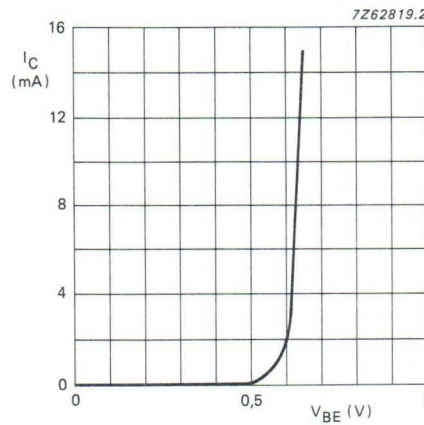
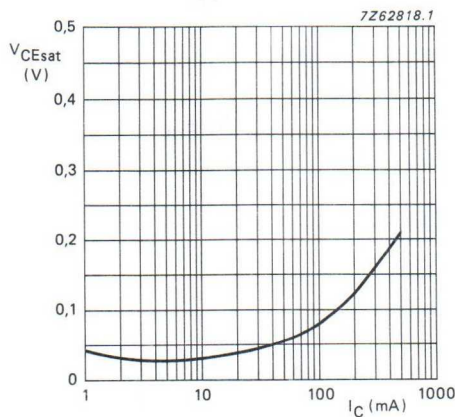
$$h_{FE} \quad 100 \text{ to } 600$$

$$h_{FE} > 70$$

$$h_{FE} > 40$$

$$f_T \quad \text{typ.} \quad 200 \text{ MHz}$$

$$C_c \quad \text{typ.} \quad 5 \text{ pF}$$

Fig. 2 $V_{CE} = 1 \text{ V}$; $T_j = 25^\circ\text{C}$; typical values.Fig. 3 $V_{CE} = 5 \text{ V}$; $T_j = 25^\circ\text{C}$; typical values.Fig. 4 $I_C/I_B = 10$; $T_j = 25^\circ\text{C}$; typical values.

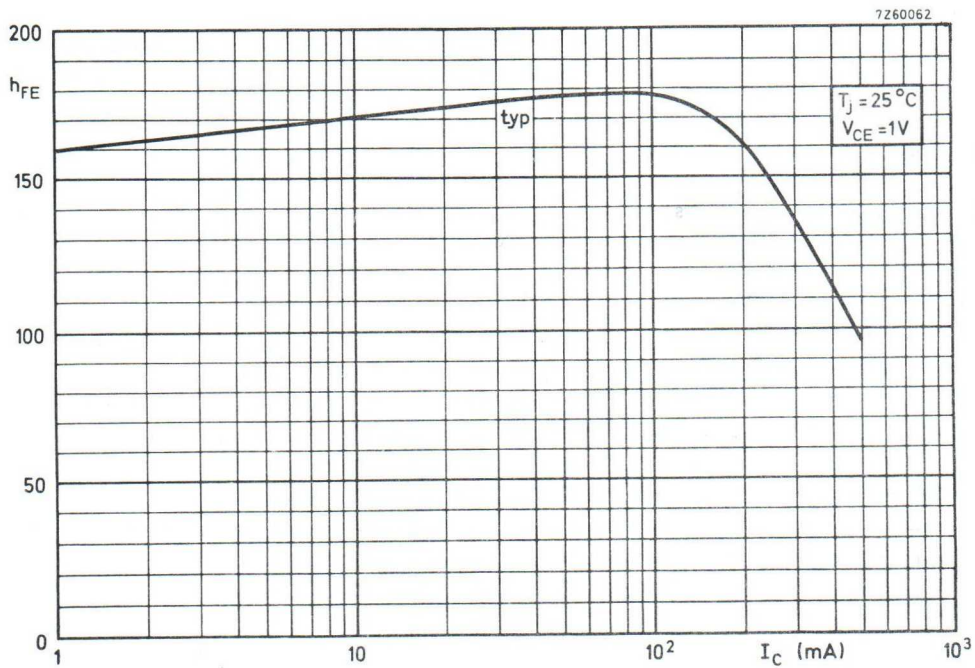


Fig. 5

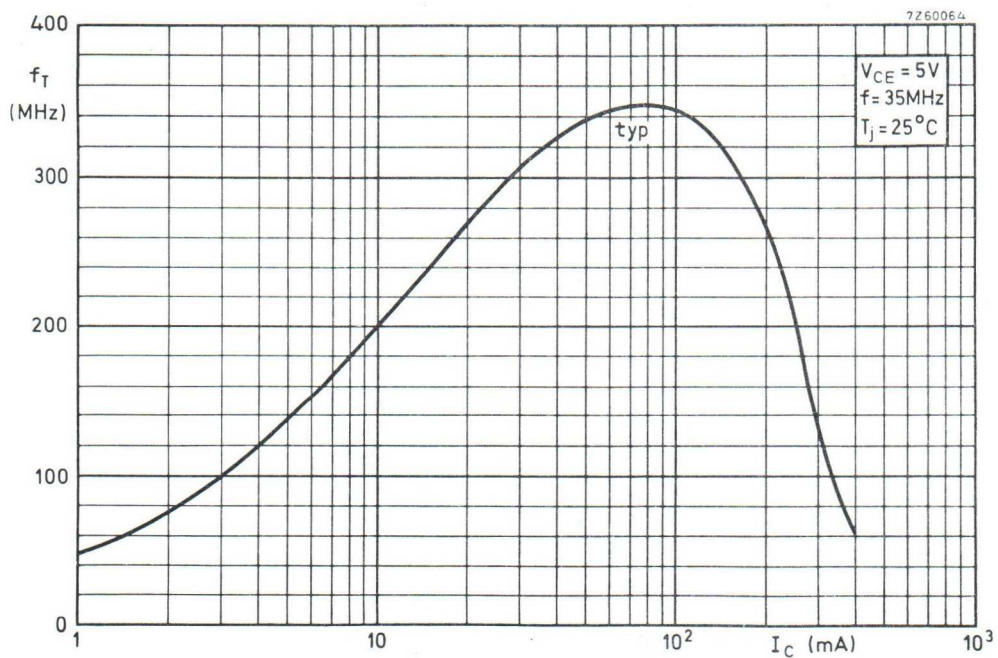


Fig. 6

SILICON PLANAR EPITAXIAL TRANSISTORS

Medium power p-n-p transistors in a miniature plastic envelope intended for applications in thick and thin-film circuits. These transistors are intended for general purposes as well as for use in driver stages of audio amplifiers.

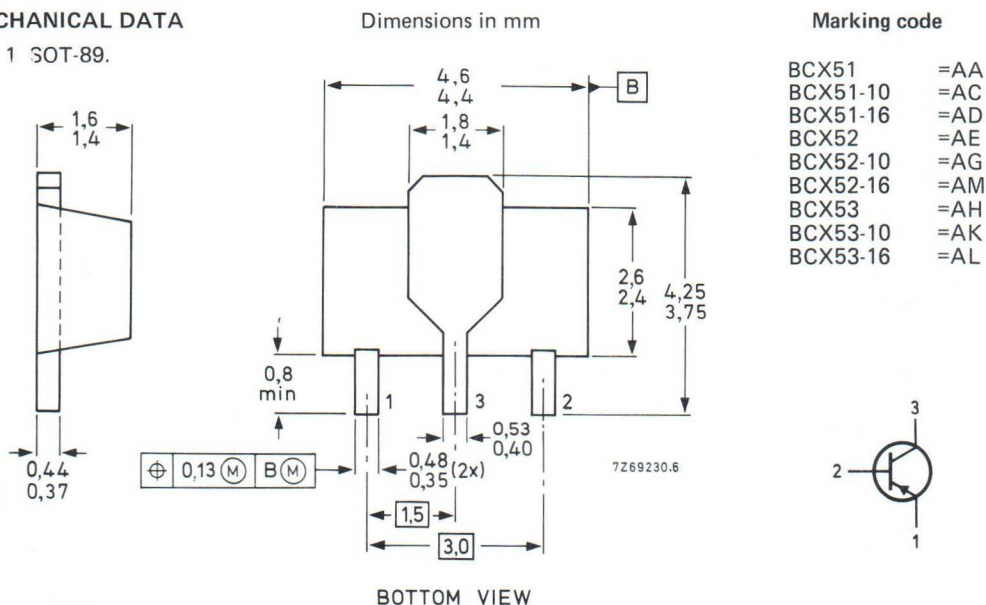
N-P-N complements are BCX54, BCX55 and BCX56 respectively.

QUICK REFERENCE DATA

		BCX51	BCX52	BCX53
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	45	60	100 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	45	60	80 V
Collector-emitter voltage ($R_{BE} = 1 \text{ k}\Omega$)	$-V_{CER}$ max.	45	60	100 V
Collector current (peak value)	$-I_{CM}$ max.		1,5	A
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot} max.		1	W
Junction temperature	T_j max.		150	$^\circ\text{C}$
D.C. current gain				
$-I_C = 150 \text{ mA}; -V_{CE} = 2 \text{ V}$	h_{FE}		40 to 250	
Transition frequency at $f = 35 \text{ MHz}$				
$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	f_T typ.		50	MHz

MECHANICAL DATA

Fig. 1 SOT-89.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX51	BCX52	BCX53
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	45	60	100 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	60	80 V
Collector-emitter voltage ($R_{BE} = 1 \text{ k}\Omega$)	$-V_{CER}$	max.	45	60	100 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5 V
Collector current (d.c.)	$-I_C$	max.		1,0	A
Collector current (peak value)	$-I_{CM}$	max.		1,5	A
Base current (d.c.)	$-I_B$	max.		0,1	A
Base current (peak value)	$-I_{BM}$	max.		0,2	A
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$ mounted on a ceramic substrate area = 2,5 cm ² ; thickness = 0,7 mm	P_{tot}	max.		1,0	W
Storage temperature	T_{stg}			-65 to + 150	$^\circ\text{C}$
Junction temperature	T_j	max.		150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to collector tab	$R_{th \text{ j-tab}}$	=		10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm ² ; thickness = 0,7 mm	$R_{th \text{ j-a}}$	=		125	K/W

CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0$; $-V_{CB} = 30 \text{ V}$

$-I_{CBO} < 100 \text{ nA}$

$I_E = 0$; $-V_{CB} = 30 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$

$-I_{CBO} < 10 \text{ } \mu\text{A}$

Emitter cut-off current

$I_C = 0$; $-V_{EB} = 5 \text{ V}$

$-I_{EBO} < 10 \text{ } \mu\text{A}$

Base-emitter voltage

$-I_C = 500 \text{ mA}$; $-V_{CE} = 2 \text{ V}$

$-V_{BE} < 1 \text{ V}$

Saturation voltage

$-I_C = 500 \text{ mA}$; $-I_B = 50 \text{ mA}$

$-V_{CEsat} < 0,5 \text{ V}$

D.C. current gain

$-I_C = 5 \text{ mA}$; $-V_{CE} = 2 \text{ V}$

$h_{FE} > 25$

$-I_C = 150 \text{ mA}$; $-V_{CE} = 2 \text{ V}$

$h_{FE} 40 \text{ to } 250$

$-I_C = 500 \text{ mA}$; $-V_{CE} = 2 \text{ V}$

$h_{FE} > 25$

Transition frequency at $f = 35 \text{ MHz}$

$-I_C = 10 \text{ mA}$; $-V_{CE} = 5 \text{ V}$

$f_T \text{ typ. } 50 \text{ MHz}$

CHARACTERISTICS (continued)

D.C. current gain

 $-I_C = 150 \text{ mA}; -V_{CE} = 2 \text{ V}$ $h_{FE} \begin{matrix} > \\ < \end{matrix}$

BCX51-10	BCX51-16
52-10	52-16
53-10	53-16
63	100
160	250

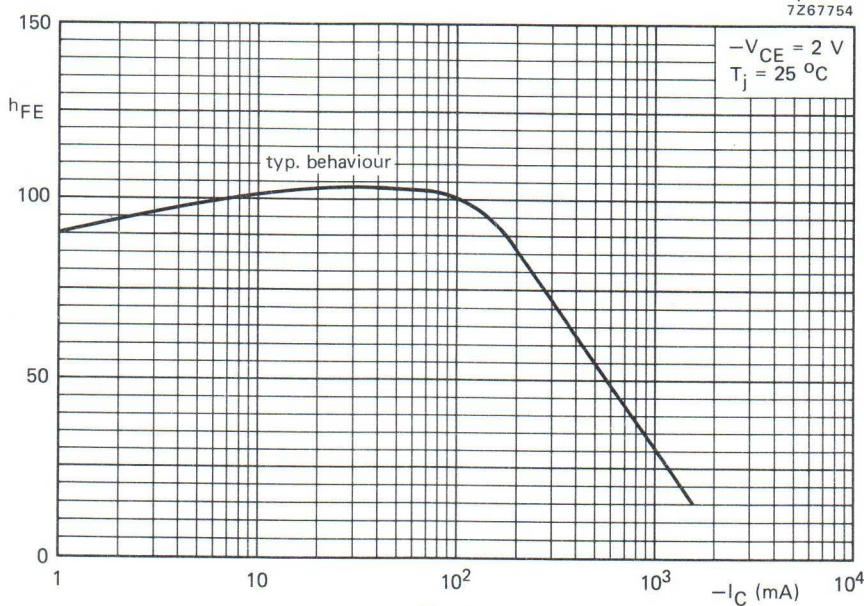
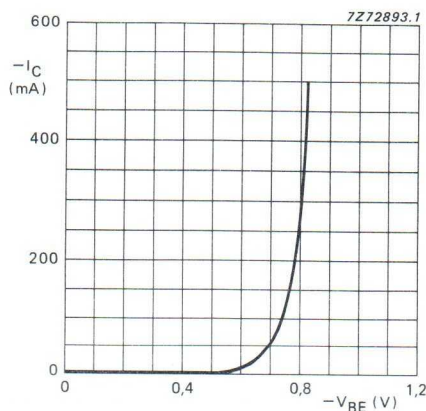


Fig. 2.

Fig. 3 $-V_{CE} = 2 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; typical values.

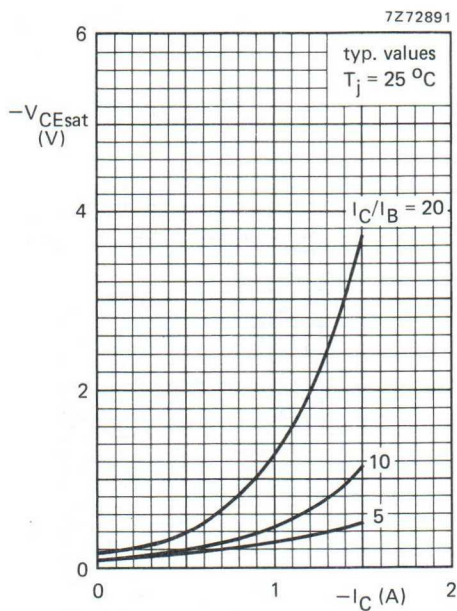


Fig. 4.

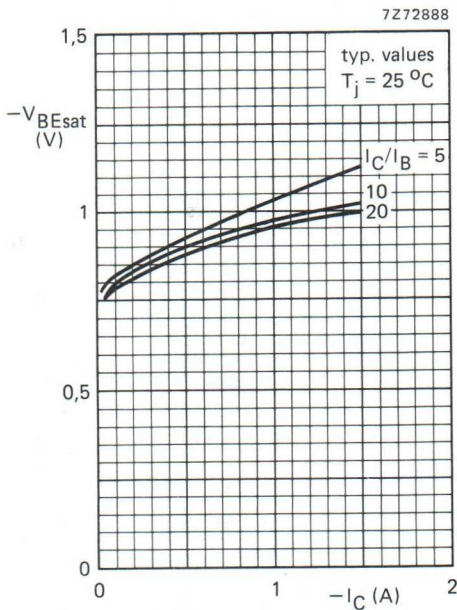


Fig. 5.

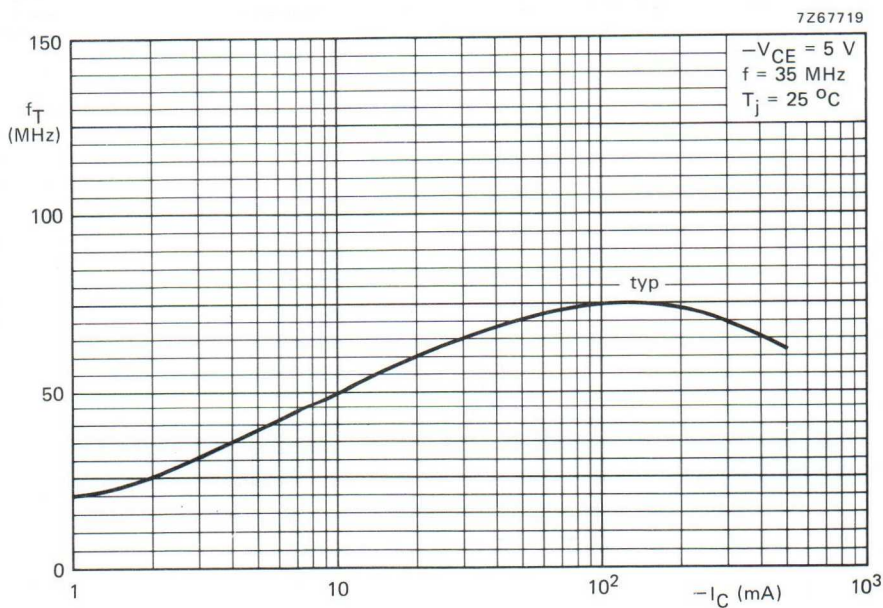


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTORS

Medium power n-p-n transistors in a miniature plastic envelope intended for applications in thick and thin-film circuits. These transistors are intended for general purposes as well as for use in driver stages of audio amplifiers.

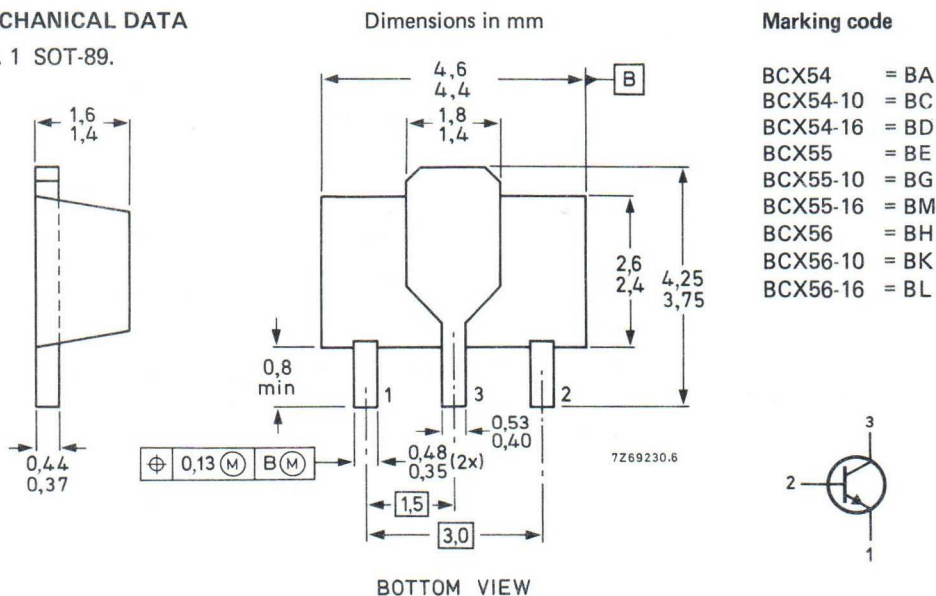
P-N-P complements are BCX51, BCX52 and BCX53 respectively.

QUICK REFERENCE DATA

	BCX54	BCX55	BCX56
Collector-base voltage (open emitter)	V_{CBO} max. 45	60	100 V
Collector-emitter voltage (open base)	V_{CEO} max. 45	60	80 V
Collector-emitter voltage ($R_{BE} = 1\text{ k}\Omega$)	V_{CER} max. 45	60	100 V
Collector current (peak value)	I_{CM} max.	1,5	A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot} max.	1	W
Junction temperature	T_j max.	150	$^{\circ}\text{C}$
D.C. current gain	h_{FE}	40 to 250	
$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$			
Transition frequency at $f = 35\text{ MHz}$	f_T typ.	130	MHz
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$			

MECHANICAL DATA

Fig. 1 SOT-89.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX54	BCX55	BCX56
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	100 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	60	80 V
Collector-emitter voltage ($R_{BE} = 1\text{ k}\Omega$)	V_{CER}	max.	45	60	100 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	5 V
Collector current (d.c.)	I_C	max.		1,0	A
Collector current (peak value)	I_{CM}	max.		1,5	A
Base current (d.c.)	I_B	max.		0,1	A
Base current (peak value)	I_{BM}	max.		0,2	A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ mounted on a ceramic substrate area = $2,5\text{ cm}^2$; thickness = $0,7\text{ mm}$	P_{tot}	max.		1,0	W
Storage temperature	T_{stg}			-65 to +150	$^{\circ}\text{C}$
Junction temperature	T_j	max.		150	$^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to collector tab	$R_{th\text{ j-tab}}$	=		10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = $2,5\text{ cm}^2$; thickness = $0,7\text{ mm}$	$R_{th\text{ j-a}}$	=		125	K/W

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current $I_E = 0$; $V_{CB} = 30\text{ V}$	I_{CBO}	<		100	nA
$I_E = 0$; $V_{CB} = 30\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$	I_{CBO}	<		10	μA
Emitter cut-off current $I_C = 0$; $V_{EB} = 5\text{ V}$	I_{EBO}	<		10	μA
Base-emitter voltage $I_C = 500\text{ mA}$; $V_{CE} = 2\text{ V}$	V_{BE}	<		1	V
Saturation voltage $I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$	V_{CEsat}	<		0,5	V
D.C. current gain $I_C = 5\text{ mA}$; $V_{CE} = 2\text{ V}$	h_{FE}	>		25	
$I_C = 150\text{ mA}$; $V_{CE} = 2\text{ V}$	h_{FE}			40 to 250	
$I_C = 500\text{ mA}$; $V_{CE} = 2\text{ V}$	h_{FE}	>		25	
Transition frequency at $f = 35\text{ MHz}$ $I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ.		130	MHz

CHARACTERISTICS (continued)

D.C. current gain

 $I_C = 150 \text{ mA}$; $V_{CE} = 2 \text{ V}$ $h_{FE} >$
 $h_{FE} <$

BCX54-10	BCX54-16
55-10	55-16
56-10	56-16
63	100
160	250

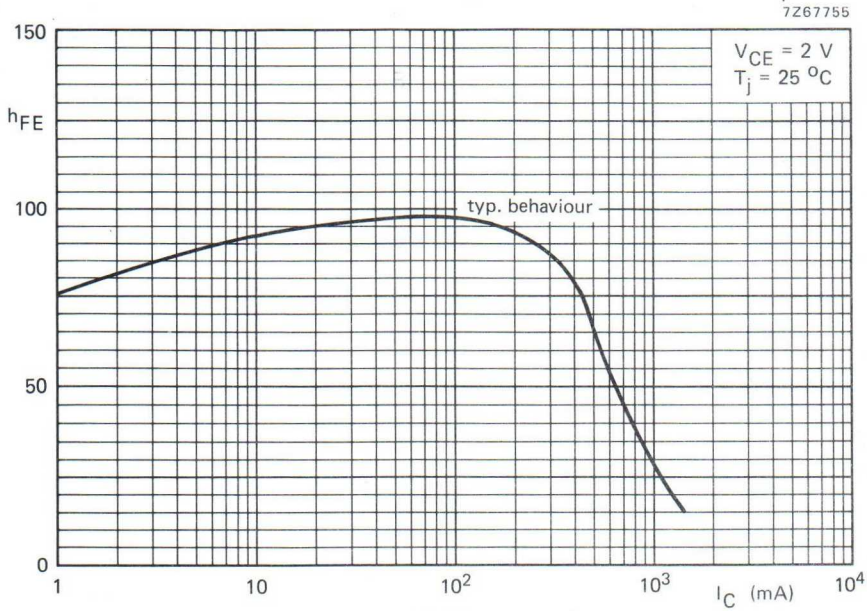
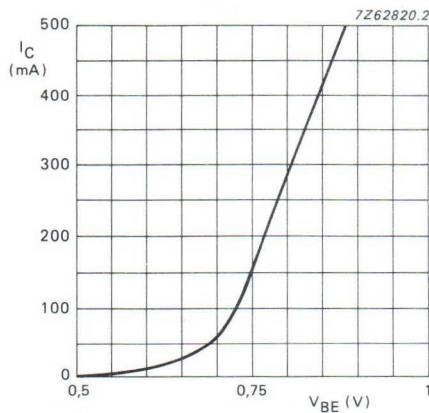


Fig. 2.

Fig. 3 $V_{CE} = 2 \text{ V}$; $T_j = 25^\circ \text{C}$; typical values.

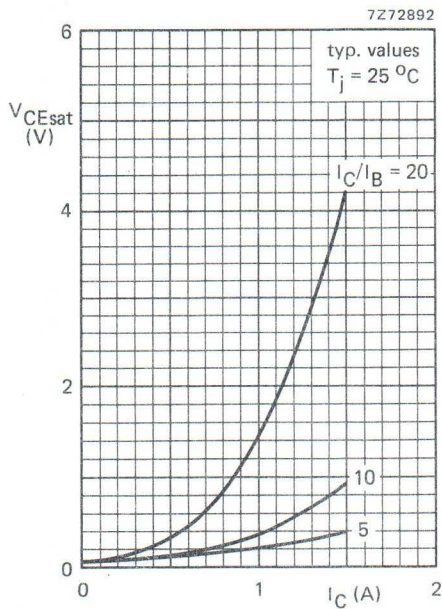


Fig. 4.

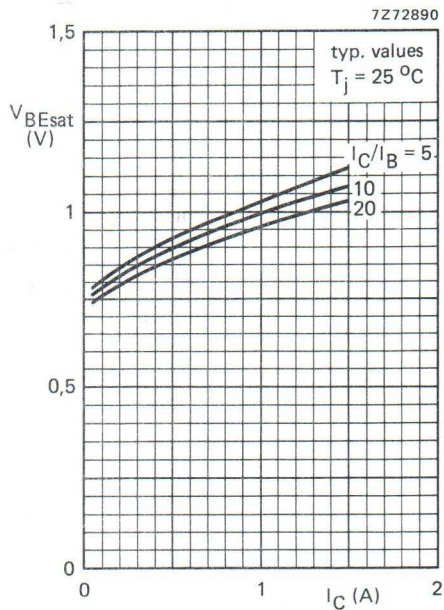


Fig. 5.

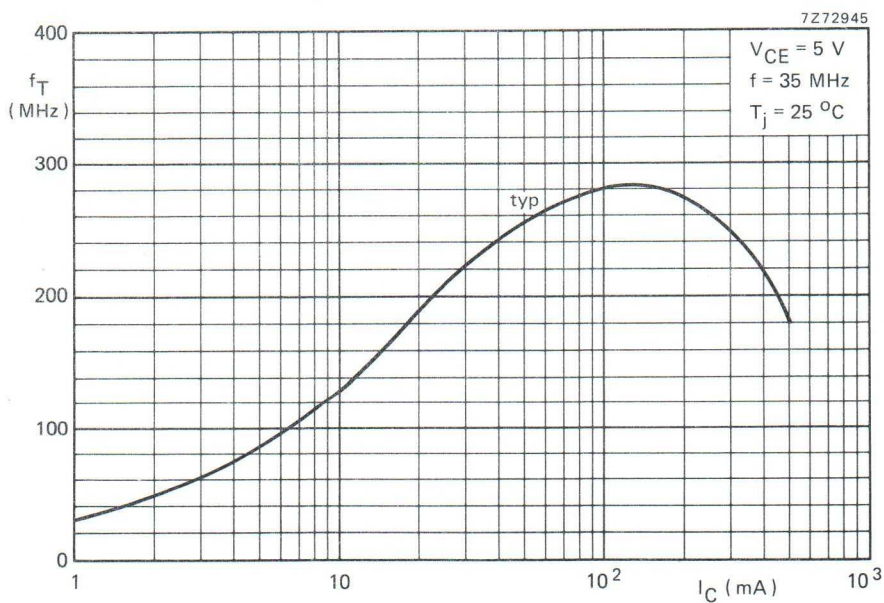


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	45 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45 V
Collector current (d.c.)	I_C	max.	200 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Transition frequency at $f = 100\text{ MHz}$ $V_{CE} = 5\text{ V}; I_C = 10\text{ mA}$	f_T	typ.	250 MHz
Noise figure at $f = 1\text{ kHz}$ $V_{CE} = 5\text{ V}; I_C = 200\text{ }\mu\text{A}; B = 200\text{ Hz}$	F	typ.	2 dB

MECHANICAL DATA

Dimensions in mm

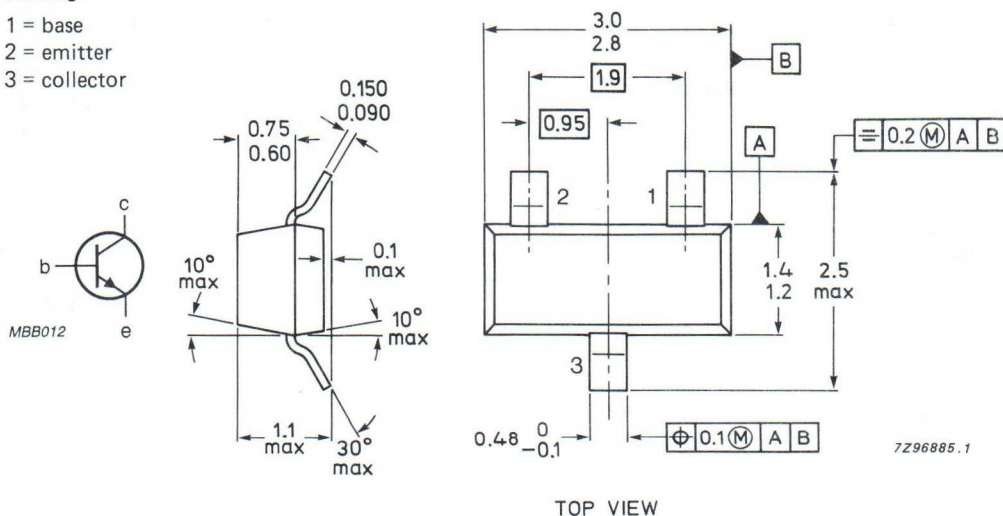
Marking code

Fig. 1 SOT-23.

BCX70G = AGp
BCX70H = AHp
BCX70J = AJp
BCX70K = AKp

Pinning:

- 1 = base
2 = emitter
3 = collector



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	45 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	200 mA
Base current	I_B	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector-emitter cut-off current

$V_{BE} = 0$; $V_{CE} = 45\text{ V}$

I_{CES}	<	20 nA
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$V_{BE} = 0$; $V_{CE} = 45\text{ V}$; $T_{amb} = 150\text{ }^{\circ}\text{C}$

I_{CES}	<	20 μA
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Emitter-base cut-off current

$I_C = 0$; $V_{EB} = 4\text{ V}$

I_{EBO}	<	20 nA
-----------	---	-------

Saturation voltages

at $I_C = 10\text{ mA}$; $I_B = 0,25\text{ mA}$

V_{CEsat}	0,05 to 0,35 V
-------------	----------------

V_{BEsat}	0,6 to 0,85 V
-------------	---------------

at $I_C = 50\text{ mA}$; $I_B = 1,25\text{ mA}$

V_{CEsat}	0,1 to 0,55 V
-------------	---------------

V_{BEsat}	0,7 to 1,05 V
-------------	---------------

Transition frequency at $f = 100\text{ MHz}$ ▲

$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$

f_T	>	125 MHz
	typ.	250 MHz

Collector capacitance at $f = 1\text{ MHz}$

$I_E = I_C = 0$; $V_{CB} = 10\text{ V}$

C_c	typ.	2,5 pF
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Emitter capacitance at $f = 1\text{ MHz}$

$I_C = I_E = 0$; $V_{EB} = 0,5\text{ V}$

C_e	typ.	8 pF
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Noise figure at $R_S = 2\text{ k}\Omega$

$I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$

F	typ.	2 dB
	<	6 dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

		BCX70G	70H	70J	70K
D.C. current gain					
$V_{CE} = 5 \text{ V}; I_C = 10 \mu\text{A}$	$h_{FE} >$	—	40	30	100
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}$	$h_{FE} >$	120	250	180	380
	$h_{FE} <$	220	460	310	630
$V_{CE} = 1 \text{ V}; I_C = 50 \text{ mA}$	$h_{FE} >$	50	70	90	100
Input impedance					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{ie} typ.	2,7	3,6	4,5	7,5 $k\Omega$
Reverse voltage transfer ratio					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{re} typ.	1,5	2	2	$3 \cdot 10^{-4}$
Small-signal current gain					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{fe} typ.	200	260	330	520
Output admittance					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{oe} typ.	18	24	30	50 μS
Base-emitter voltage					
$V_{CE} = 5 \text{ V}; I_C = 2 \text{ mA}$	V_{BE} typ.	0,55 to 0,75			V
			0,65		V
$V_{CE} = 5 \text{ V}; I_C = 10 \mu\text{A}$	V_{BE} typ.		0,52		V
$V_{CE} = 1 \text{ V}; I_C = 50 \text{ mA}$	V_{BE} typ.		0,78		V

Switching times

$I_{Con} = 10 \text{ mA}$; $I_{Bon} = -I_{Boff} = 1 \text{ mA}$

$V_{CC} = 10 \text{ V}$; $R_L = 990 \Omega$

turn-on time ($t_d + t_r$)

t_{on}	typ.	85 ns
	<	150 ns

turn-off time ($t_s + t_f$)

t_{off}	typ.	480 ns
	<	800 ns

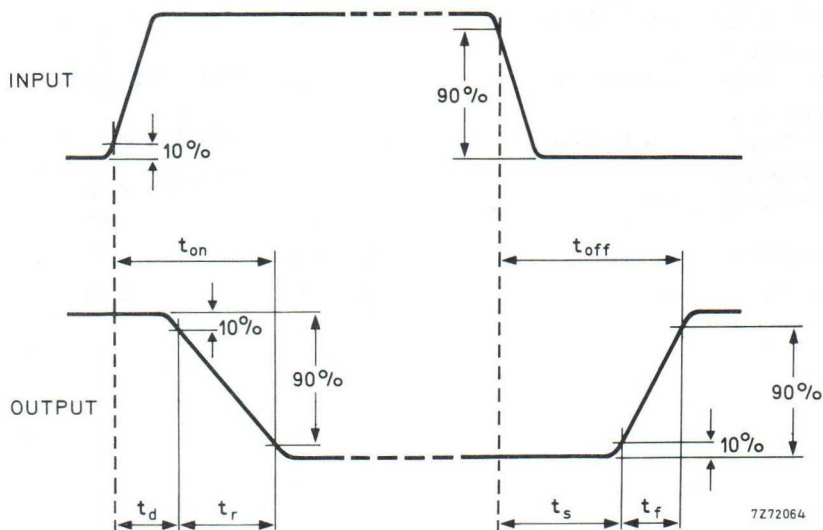


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	45 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Total power dissipation	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 °C
Transition frequency at $f = 100$ MHz $-V_{CE} = 5$ V; $-I_C = 10$ mA	f_T	typ.	180 MHz
Noise figure at $f = 1$ kHz $-V_{CE} = 5$ V; $-I_C = 200$ μ A	F	typ.	2 dB

MECHANICAL DATA

Dimensions in mm

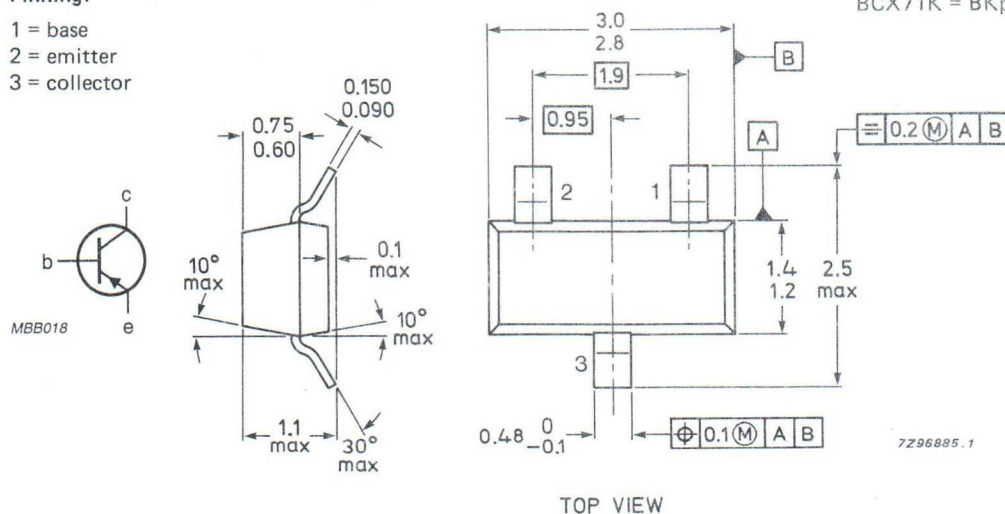
Marking code

Fig. 1 SOT-23.

BCX71G = BGp
BCX71H = BHp
BCX71J = BJp
BCX71K = BKp

Pinning:

- 1 = base
2 = emitter
3 = collector



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	45 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Base current	$-I_B$	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector-emitter cut-off current

$V_{EB} = 0$; $-V_{CE} = 45\text{ V}$

$-I_{CES}$	<	20 nA
------------	---	-------

$V_{EB} = 0$; $-V_{CE} = 45\text{ V}$; $T_{amb} = 150\text{ }^{\circ}\text{C}$

$-I_{CES}$	<	20 μA
------------	---	------------------

Emitter-base cut-off current

$I_C = 0$; $-V_{EB} = 4\text{ V}$

$-I_{EBO}$	<	20 nA
------------	---	-------

Saturation voltages

$-I_C = 10\text{ mA}$; $-I_B = 0,25\text{ mA}$

$-V_{CEsat}$	0,06 to 0,25 V
--------------	----------------

$-V_{BEsat}$	0,6 to 0,85 V
--------------	---------------

$-I_C = 50\text{ mA}$; $-I_B = 1,25\text{ mA}$

$-V_{CEsat}$	0,12 to 0,55 V
--------------	----------------

$-V_{BEsat}$	0,68 to 1,05 V
--------------	----------------

Transition frequency at $f = 100\text{ MHz}$ ▲

$-V_{CE} = 5\text{ V}$; $-I_C = 10\text{ mA}$

f_T	typ.	180 MHz
-------	------	---------

Collector capacitance at $f = 1\text{ MHz}$

$-V_{CB} = 10\text{ V}$; $I_E = I_e = 0$

C_C	typ.	4,5 pF
-------	------	--------

Emitter capacitance at $f = 1\text{ MHz}$

$-V_{EB} = 0,5\text{ V}$; $I_C = I_c = 0$

C_e	typ.	11 pF
-------	------	-------

Noise figure at $R_S = 2\text{ k}\Omega$

$-V_{CE} = 5\text{ V}$; $-I_C = 200\text{ }\mu\text{A}$; $B = 200\text{ Hz}$

F	typ.	2 dB
	<	6 dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

		BCX71G	71H	71J	71K
D.C. current gain					
$-V_{CE} = 5 \text{ V}; -I_C = 10 \mu\text{A}$	$h_{FE} >$	—	30	40	100
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}$	$h_{FE} >$	120	180	250	380
	$h_{FE} <$	220	310	460	630
$-V_{CE} = 1 \text{ V}; -I_C = 50 \text{ mA}$	$h_{FE} >$	60	80	100	110
Input impedance					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{ie} typ.	2,7	3,6	4,5	7,5 $k\Omega$
Reverse voltage transfer ratio					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{re} typ.	1,5	2	2	3 10^{-4}
Small-signal current gain					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{fe} typ.	200	260	330	520
Output admittance					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}; f = 1 \text{ kHz}$	h_{oe} typ.	18	24	30	50 μS
Base-emitter voltage					
$-V_{CE} = 5 \text{ V}; -I_C = 2 \text{ mA}$	V_{BE} typ.	0,6 to 0,75			V
			0,65		V
$-V_{CE} = 5 \text{ V}; -I_C = 10 \mu\text{A}$	V_{BE} typ.		0,55		V
$-V_{CE} = 1 \text{ V}; -I_C = 50 \text{ mA}$	V_{BE} typ.		0,72		V

Switching times

$-I_{Con} = 10 \text{ mA}$; $-I_{Bon} = I_{Boff} = 1 \text{ mA}$

$-V_{CC} = 10 \text{ V}$; $R_L = 990 \Omega$

turn-on time ($t_d + t_r$)

t_{on}	typ.	85 ns
	<	150 ns

turn-off time ($t_s + t_f$)

t_{off}	typ.	480 ns
	<	800 ns

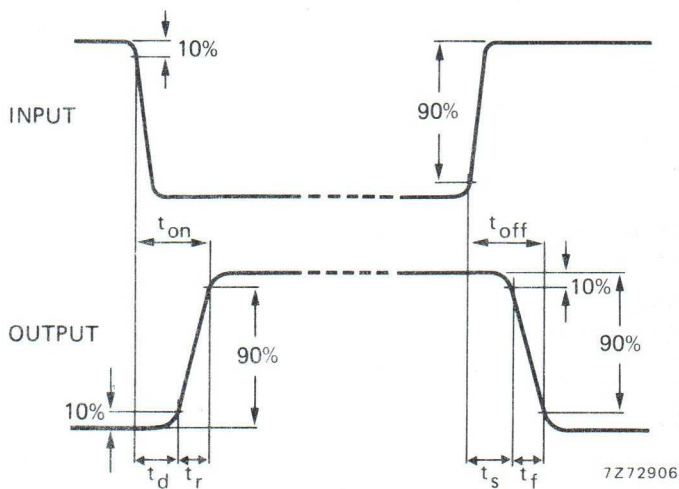


Fig. 2 Switching waveforms.

Data sheet	
status	Product specification
date of issue	April 1991

BDS60/60A/60B/60C

PNP silicon Darlington power transistors

DESCRIPTION

PNP silicon power transistors in a monolithic Darlington circuit in a miniature SMD envelope (SOT223) intended for switching applications. NPN complements are BDS61/61A/61B/61C.

QUICK REFERENCE DATA

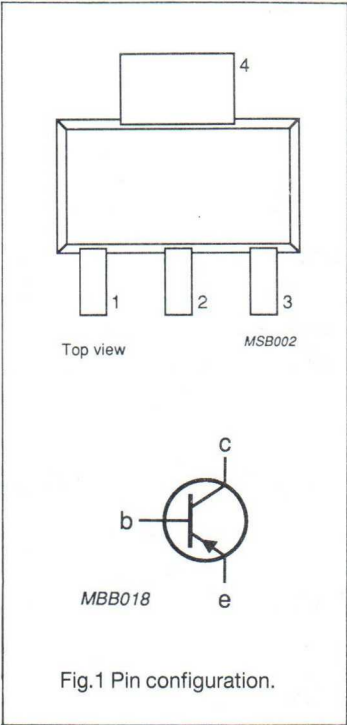
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	60	V
	BDS60		-	80	V
	BDS60A		-	100	V
	BDS60B		-	120	V
	BDS60C		-		
$-V_{CEO}$	collector-emitter voltage	open base	-	60	V
	BDS60		-	80	V
	BDS60A		-	100	V
	BDS60B		-	120	V
	BDS60C		-		
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	6	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 0.5\text{ V}$ $-V_{CE} = 3\text{ V};$	2200	-	

Note

1. Mounted on PCB.

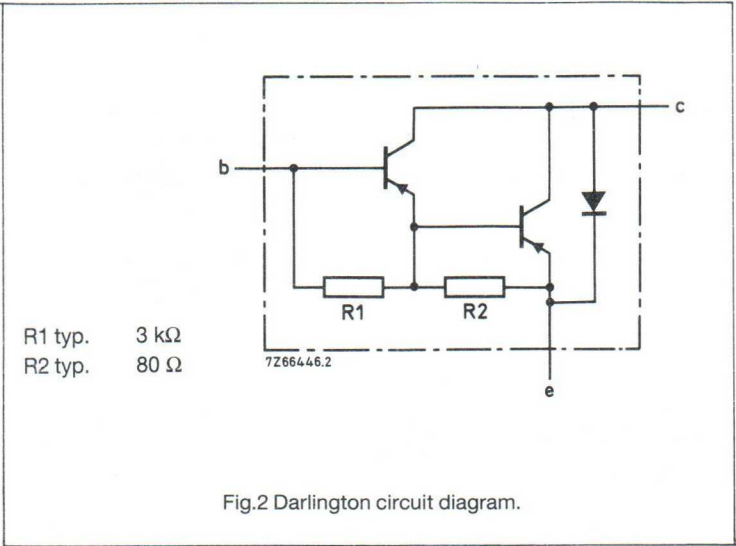
PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



PNP silicon Darlington power transistors

BDS60/60A/60B/60C



LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage BDS60 BDS60A BDS60B BDS60C	open emitter	-	60 80 100 120	V V V V
$-V_{CEO}$	collector-emitter voltage BDS60 BDS60A BDS60B BDS60C	open base	-	60 80 100 120	V V V V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	6	A
$-I_B$	base current		-	100	mA
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

PNP silicon Darlington power transistors**BDS60/60A/60B/60C****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

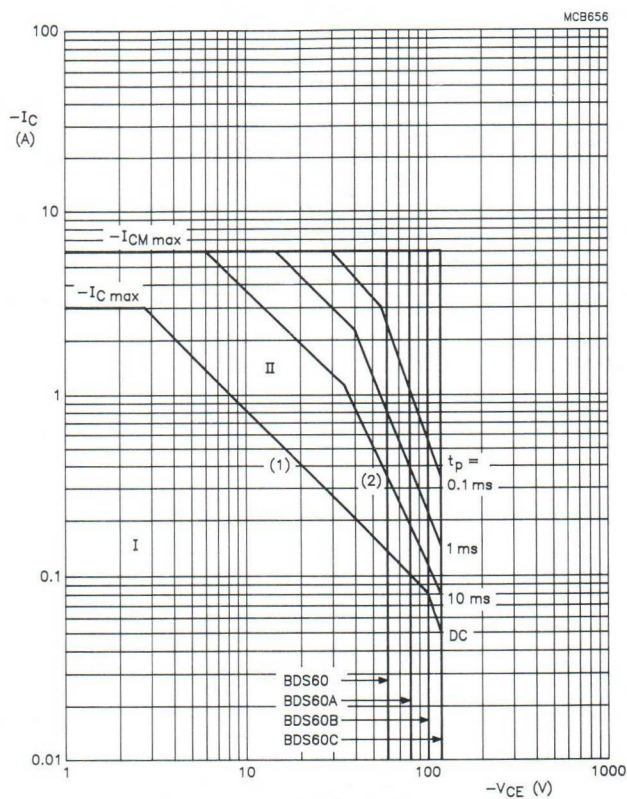
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-I_{CEO}$	collector cut-off current	$-I_B = 0$; $V_{CE} = 1/2 V_{CEO\text{ max}}$	-	-	0.2	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CEO\text{ max}}$	-	-	0.2	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $V_{CB} = 1/2 V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	0.5	mA
$-I_{EBO}$	emitter cut-off current	$-I_C = 0$; $-V_{EB} = 5\text{ V}$	-	-	5	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	-	2.5	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 1.5\text{ A}$; $-I_B = 6\text{ mA}$; note 1	-	-	2.5	V
h_{FE}	DC current gain	$-I_C = 0.5\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	2200	-	
h_{FE}	DC current gain	$-I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	750	-	-	
h_{FE}	DC current gain	$-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	500	-	
V_F	diode forward voltage	$I_F = 3\text{ A}$	-	2.1	-	V
f_{hfe}	cut-off frequency	$-I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$	-	25	-	kHz
h_{fe}	small signal current gain	$f = 1\text{ MHz}$; $-I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$	10	-	-	
t_{on}	switching times turn-on time	$-I_{C\text{ on}} = 1.5\text{ A}$; $-I_{B\text{ on}} = I_{B\text{ off}} = 6\text{ A}$; $-V_{CC} = 30\text{ V}$	-	0.3	1.5	μs
t_{off}	switching times turn-off time		-	1.5	5	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon Darlington power transistors

BDS60/60A/60B/60C



- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.
- (1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
- (2) Second breakdown limits.

Fig.3 Safe operating area; $T_{tab} = 25\ ^\circ\text{C}$.

PNP silicon Darlington power transistors

BDS60/60A/60B/60C

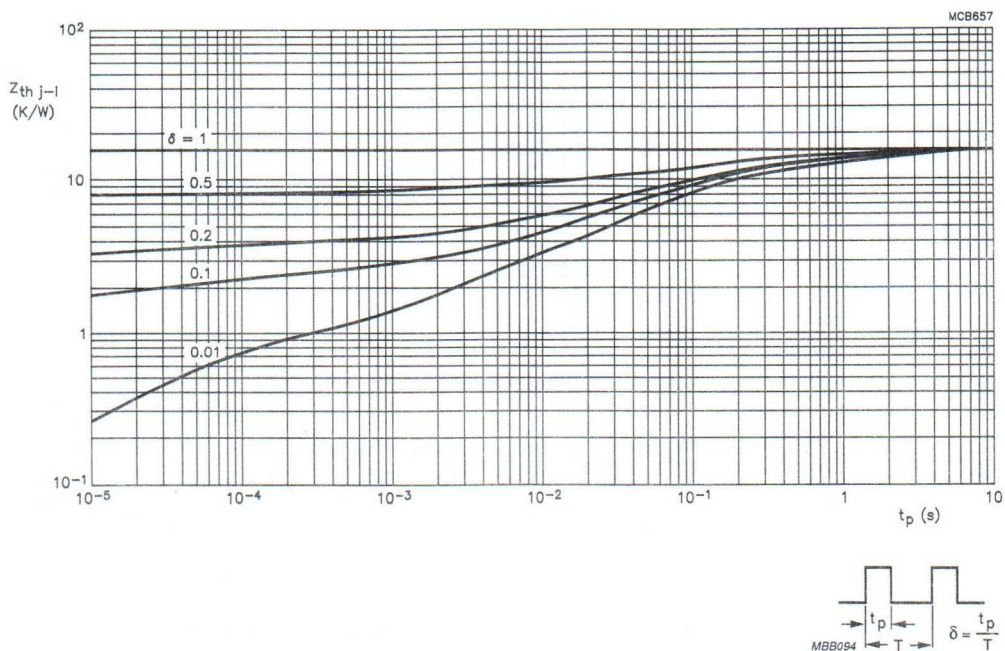


Fig.4 Pulse power rating chart.

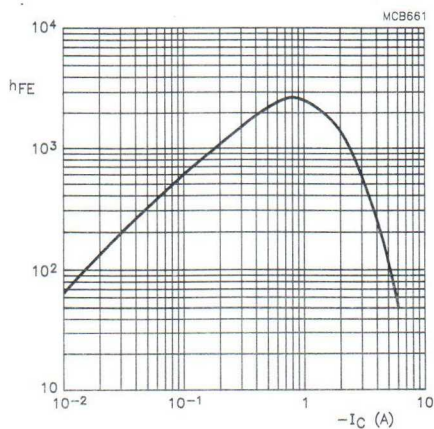
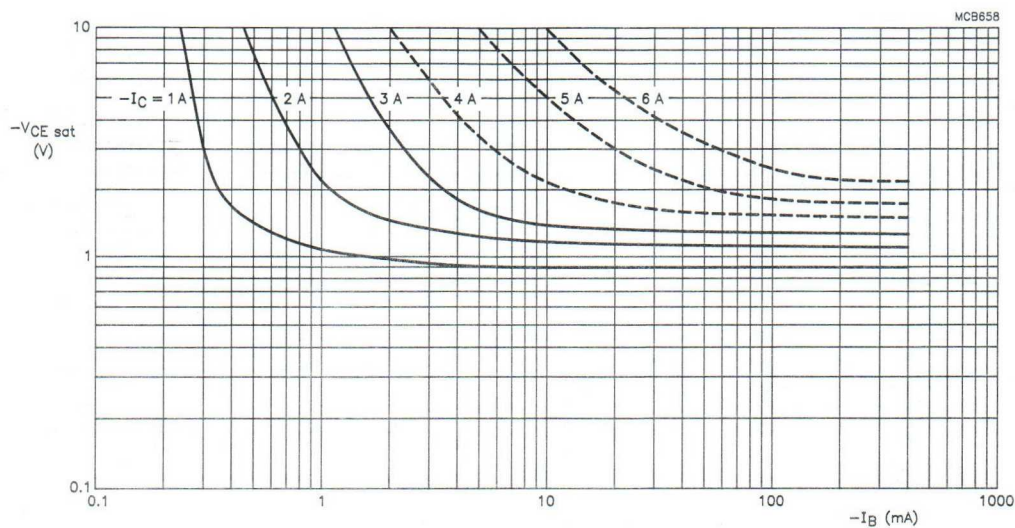


Fig.5 Typical DC current gain; $-V_{CE} = 3\text{ V}$;
 $T_{tab} = 25\text{ }^{\circ}\text{C}$.

PNP silicon Darlington power transistors

BDS60/60A/60B/60C

Fig.6 Typical values of collector-emitter saturation voltage at $T_{tab} = 25\text{ }^{\circ}\text{C}$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS61/61A/61B/61C

NPN silicon Darlington power transistors

DESCRIPTION

NPN silicon power transistors in a monolithic Darlington circuit in a miniature SMD envelope (SOT223) intended for switching applications. PNP complements are BDS60/60A/60B/60C.

PINNING - SOT223

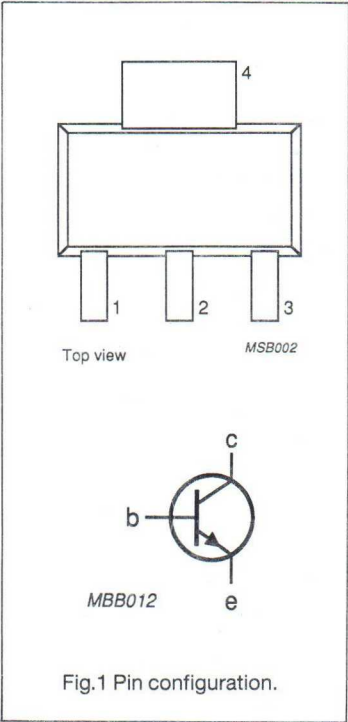
PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	60	V
	BDS61		-	80	V
	BDS61A		-	100	V
	BDS61B		-	120	V
	BDS61C		-		V
V _{CEO}	collector-emitter voltage	open base	-	60	V
	BDS61		-	80	V
	BDS61A		-	100	V
	BDS61B		-	120	V
	BDS61C		-		V
I _C	collector current	average value	-	3	A
I _{CM}	collector current	peak value	-	6	A
P _{tot}	total power dissipation	T _{tab} = 25 °C note 1	-	8 1.5	W W
T _J	junction temperature		-	150	°C
h _{FE}	DC current gain	-I _C = 0.5 V -V _{CE} = 3 V;	1150	-	

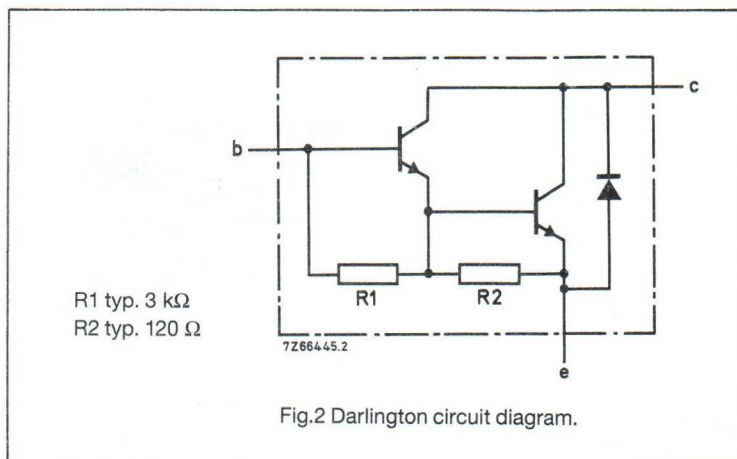
Note

- 1. Mounted on PCB.



NPN silicon Darlington power transistors

BDS61/61A/61B/61C



LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage BDS61 BDS61A BDS61B BDS61C	open emitter	-	60 80 100 120	V V V V
V_{CEO}	collector-emitter voltage BDS61 BDS61A BDS61B BDS61C	open base	-	60 80 100 120	V V V V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	6	A
I_B	base current		-	100	mA
P_{tot}	total power dissipation	$T_{tab} = 25\text{ °C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	°C
T_j	junction temperature		-	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

NPN silicon Darlington power transistors**BDS61/61A/61B/61C****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

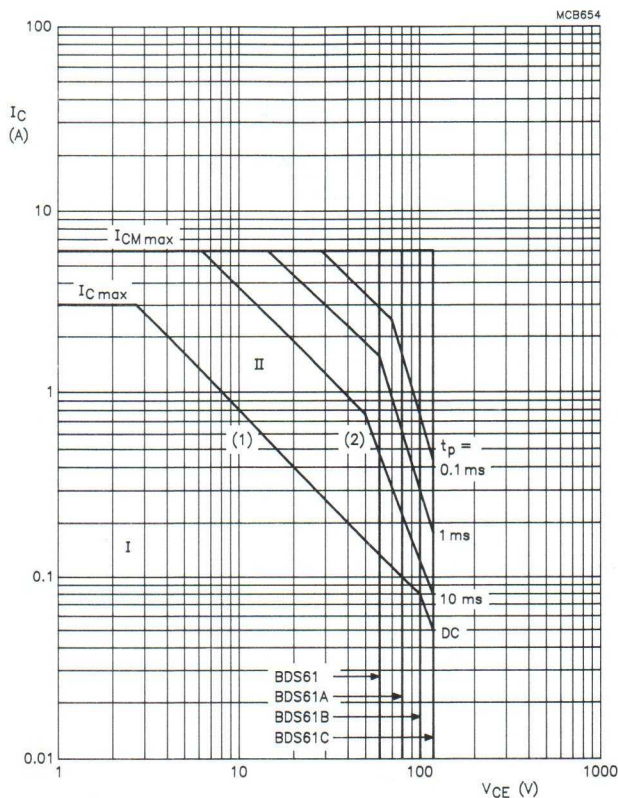
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 1/2 V_{CEO\text{ max}}$	-	-	0.2	mA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 1/2 V_{CBO\text{ max}}$ $T_j = 150\text{ }^{\circ}\text{C}$	-	-	0.5	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	-	5	mA
V_{BE}	base-emitter voltage	$I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	-	2.5	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 1.5\text{ A}$; $I_B = 6\text{ mA}$; note 1	-	-	2.5	V
h_{FE}	DC current gain	$I_C = 0.5\text{ A}$; $V_{CE} = 3\text{ V}$ note 1	-	1150	-	
h_{FE}	DC current gain	$I_C = 1.5\text{ A}$; $V_{CE} = 3\text{ V}$; note 1	750	-	-	
h_{FE}	DC current gain	$I_C = 3\text{ A}$; $V_{CE} = 3\text{ V}$; note 1	-	1800	-	
V_F	diode forward voltage	$I_F = 3\text{ A}$	-	2.6	-	V
f_{hfe}	cut-off frequency	$I_C = 1.5\text{ A}$; $-V_{CE} = 3\text{ V}$	-	25	-	kHz
h_{fe}	small signal current gain	$f = 1\text{ MHz}$; $I_C = 1.5\text{ A}$; $V_{CE} = 3\text{ V}$	10	-	-	
t_{on}	switching times turn-on time	$I_{C\text{ on}} = 1.5\text{ A}$; $I_{B\text{ on}} = -I_{B\text{ off}} = 6\text{ A}$; $V_{CC} = 30\text{ V}$	-	0.8	2	μs
t_{off}	switching times turn-off time		-	4.5	8	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon Darlington power transistors

BDS61/61A/61B/61C



- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.
- (1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
- (2) Second breakdown limits.

Fig.3 Safe operating area; $T_{tab} = 25\ ^\circ\text{C}$.

NPN silicon Darlington power transistors

BDS61/61A/61B/61C

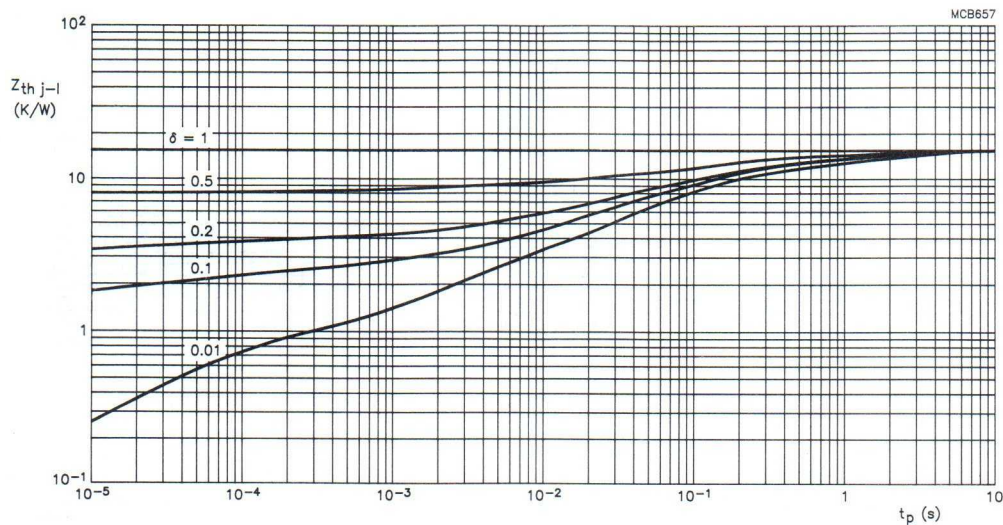
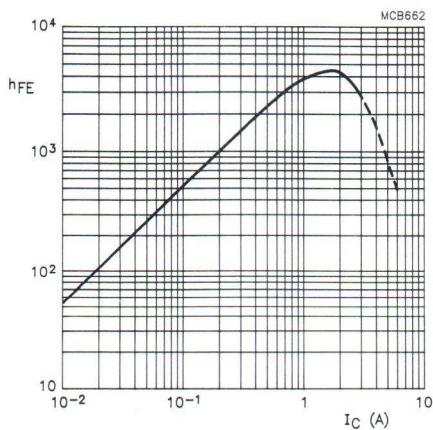
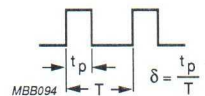
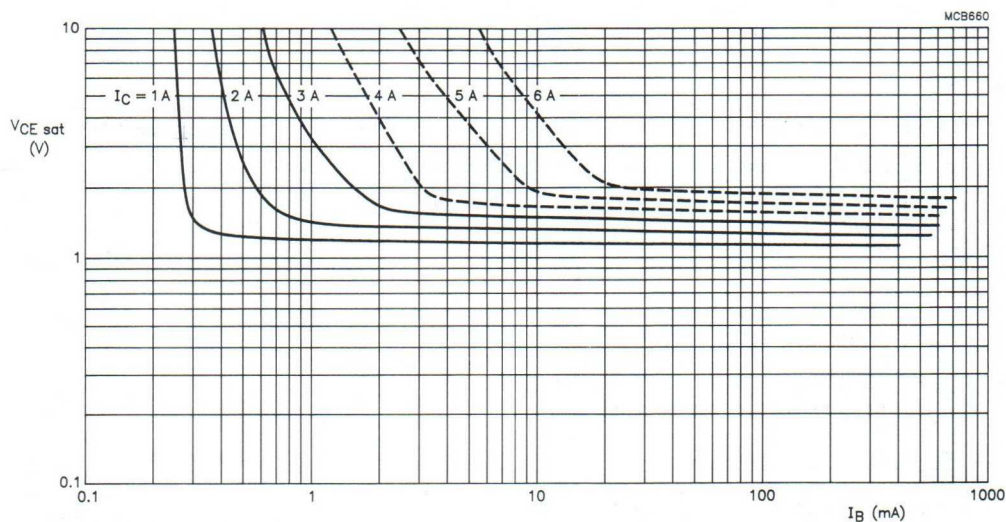


Fig.4 Pulse power rating chart.

Fig.5 Typical DC current gain; $V_{CE} = 3 \text{ V}$;
 $T_{\text{tab}} = 25 \text{ }^{\circ}\text{C}$.

NPN silicon Darlington power transistors

BDS61/61A/61B/61C

Fig.6 Typical values of collector-emitter saturation voltage at $T_{tab} = 25\ ^\circ\text{C}$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS201/203/77

NPN silicon epitaxial base power transistors

DESCRIPTION

NPN silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. PNP complements are BDS202/204/78.

QUICK REFERENCE DATA

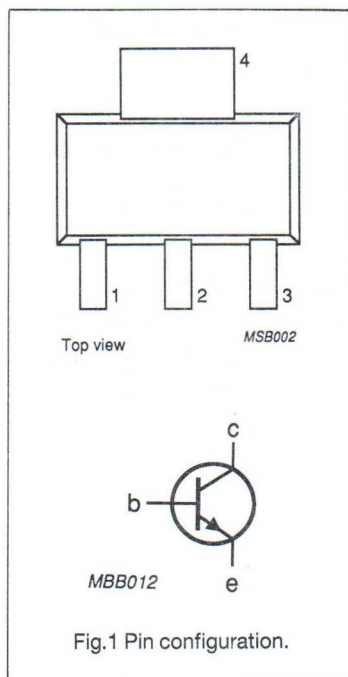
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	60	V
	BDS201		-	60	V
	BDS203		-	100	V
	BDS77		-	100	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
	BDS201		-	60	V
	BDS203		-	80	V
	BDS77		-	80	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
		note 1	-	1.5	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
f_{hfe}	cut-off frequency	$I_C = 0.3\text{ V}$ $V_{CE} = 3\text{ V};$	25	-	kHz

Note

1. Mounted on PCB

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



NPN silicon epitaxial base power transistors**BDS201/203/77****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage BDS201 BDS203 BDS77	open emitter	-	60	V
			-	60	V
			-	100	V
			-	100	V
V_{CEO}	collector-emitter voltage BDS201 BDS203 BDS77	open base	-	45	V
			-	60	V
			-	80	V
			-	80	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
I_B	base current		-	1	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

NPN silicon epitaxial base power transistors**BDS201/203/77****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

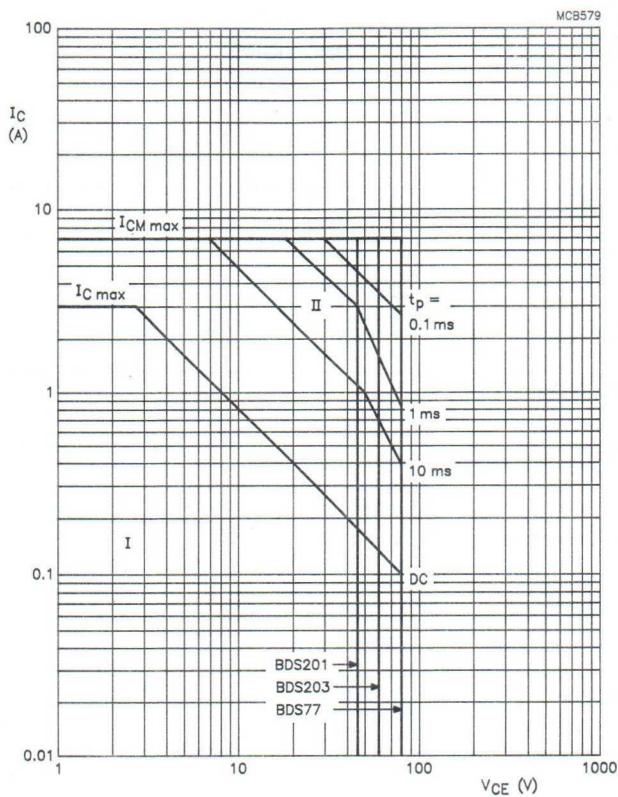
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CEO}$	collector-emitter breakdown voltage BDS201 BDS203 BDS77	$I_B = 0$; $I_C = 200\text{ mA}$	- - -	- - -	45 60 80	V V V
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 30\text{ V}$	-	-	0.2	mA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CE} = 40\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	-	0.5	mA
V_{BE}	base-emitter voltage	$I_C = 3\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	-	-	1.5	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 3\text{ A}$; $I_B = 0.3\text{ A}$; note 1	-	-	1	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 6\text{ A}$; $I_B = 0.6\text{ A}$; note 1	-	-	1.8	V
$V_{BE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 6\text{ A}$; $I_B = 0.6\text{ A}$; note 1	-	-	2.1	V
h_{FE}	DC current gain	$I_C = 3\text{ A}$; $V_{CE} = 2\text{ V}$; note 1 (BDS201)	30	-	-	
h_{FE}	DC current gain	$I_C = 2\text{ A}$; $V_{CE} = 2\text{ V}$; note 1 (BDS203/77)	30	-	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $I_C = 0.3\text{ A}$; $-V_{CE} = 3\text{ V}$	7	-	-	MHz
f_{hfe}	cut-off frequency	$I_C = 0.3\text{ A}$; $-V_{CE} = 3\text{ V}$	25	-	-	kHz
t_{on}	switching times turn-on time	$I_{C\text{ on}} = 2\text{ A}$; $I_{B\text{ on}} = -I_{B\text{ off}} = 0.2\text{ A}$; $V_{CC} = 20\text{ V}$	-	-	1	μs
t_{off}	switching times turn-off time		-	-	3	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon epitaxial base power transistors

BDS201/203/77



- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.

Fig.2 Safe operating area; $T_{\text{tab}} = 25\text{ }^{\circ}\text{C}$.

NPN silicon epitaxial base power transistors

BDS201/203/77

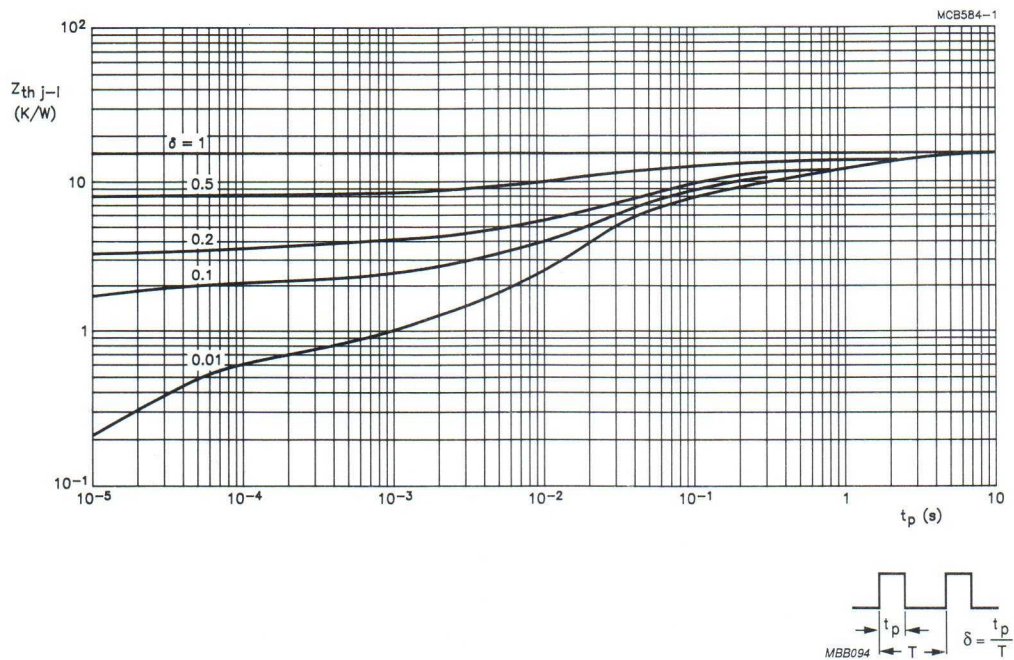
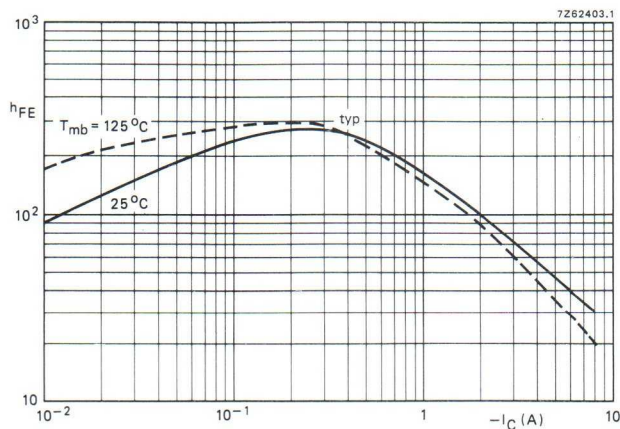


Fig.3 Pulse power rating chart.

Fig.4 DC current gain; $V_{CE} = 2$ V.



Data sheet	
status	Product specification
date of issue	April 1991

BDS202/204/78

PNP silicon epitaxial base power transistors

DESCRIPTION

PNP silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. NPN complements are BDS201/203/77.

QUICK REFERENCE DATA

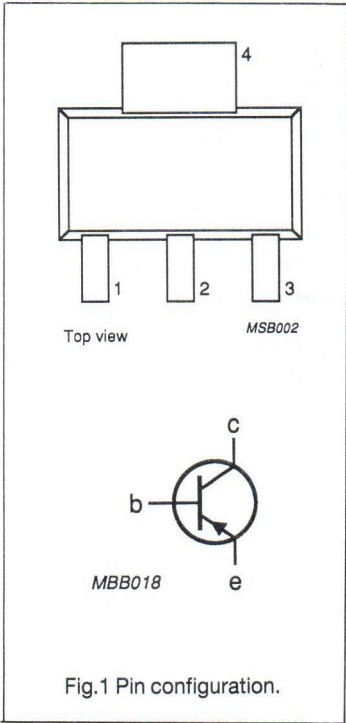
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage BDS202 BDS204 BDS78	open emitter	-	60	V
			-	60	V
			-	100	V
			-	100	V
$-V_{CEO}$	collector-emitter voltage BDS202 BDS204 BDS78	open base	-	45	V
			-	60	V
			-	80	V
			-	80	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8 1.5	W W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
f_{hfe}	cut-off frequency	$I_C = 0.3\text{ V}$ $V_{CE} = 3\text{ V};$	25	-	kHz

Note

1. Mounted on PCB

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



PNP silicon epitaxial base power transistors**BDS202/204/78****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage BDS202 BDS204 BDS78	open emitter	-	60	V
			-	60	V
			-	100	V
			-	100	V
$-V_{CEO}$	collector-emitter voltage BDS202 BDS204 BDS78	open base	-	45	V
			-	60	V
			-	80	V
			-	80	V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
$-I_B$	base current		-	1	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

PNP silicon epitaxial base power transistors**BDS202/204/78****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

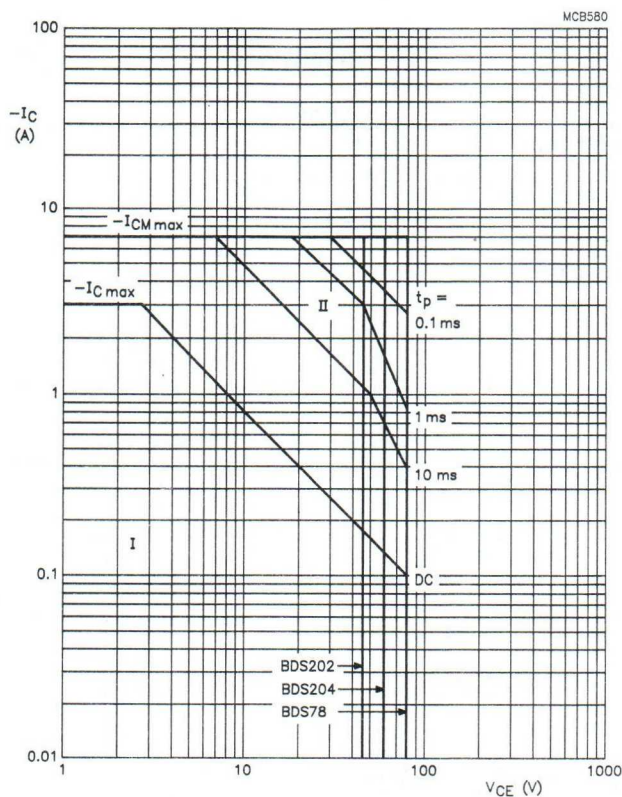
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_B = 0$; $-I_C = 200\text{ mA}$	45	-	60	V
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $-V_{CE} = 30\text{ V}$	-	-	0.2	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CE} = 40\text{ V}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
$-I_{EBO}$	emitter cut-off current	$I_C = 0$; $-V_{EB} = 5\text{ V}$	-	-	0.5	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 3\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	-	-	1.5	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 3\text{ A}$; $-I_B = 0.3\text{ A}$; note 1	-	-	1	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 6\text{ A}$; $-I_B = 0.6\text{ A}$; note 1	-	-	1.8	V
$-V_{BE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 6\text{ A}$; $-I_B = 0.6\text{ A}$; note 1	-	-	2.1	V
h_{FE}	DC current gain	$-I_C = 3\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	30	-	-	
h_{FE}	DC current gain	$-I_C = 2\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	30	-	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $-I_C = 0.3\text{ A}$; $-V_{CE} = 3\text{ V}$	7	-	-	MHz
f_{hfe}	cut-off frequency	$-I_C = 0.3\text{ A}$; $-V_{CE} = 3\text{ V}$	25	-	-	kHz
t_{on}	switching times turn-on time	$-I_{C\text{ on}} = 2\text{ A}$; $-I_{B\text{ on}} = I_{B\text{ off}} = 0.2\text{ A}$; $V_{CC} = 20\text{ V}$	-	-	1	μs
t_{off}	switching times turn-off time		-	-	3	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon epitaxial base power transistors

BDS202/204/78



- I. Region of permissible DC operation.
II. Permissible extension for repetitive pulse operation.

Fig.2 Safe operating area; $T_{\text{tab}} = 25^\circ\text{C}$.

PNP silicon epitaxial base power transistors

BDS202/204/78

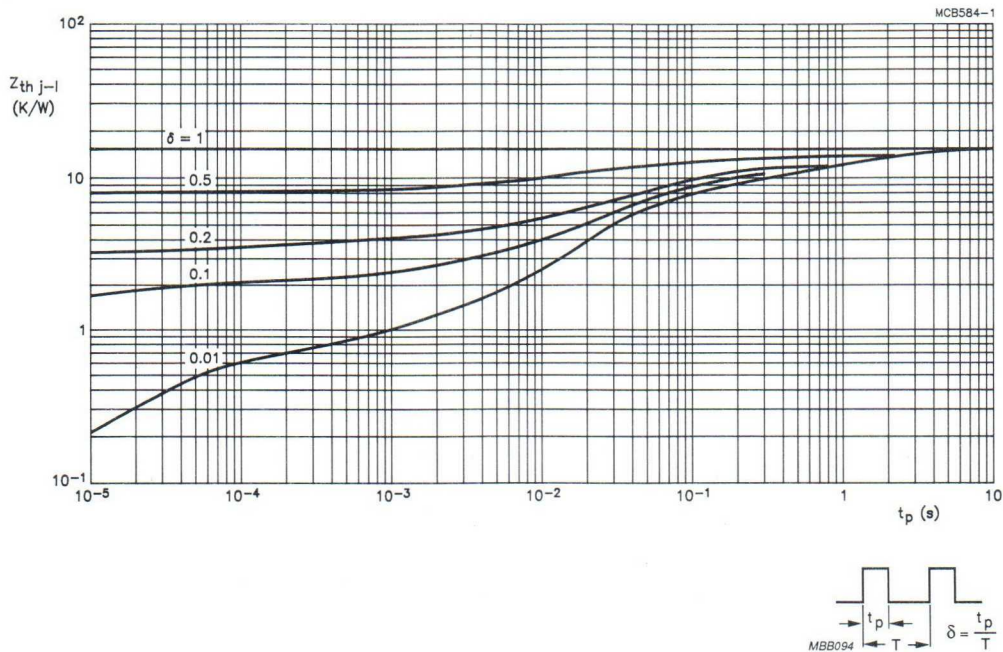
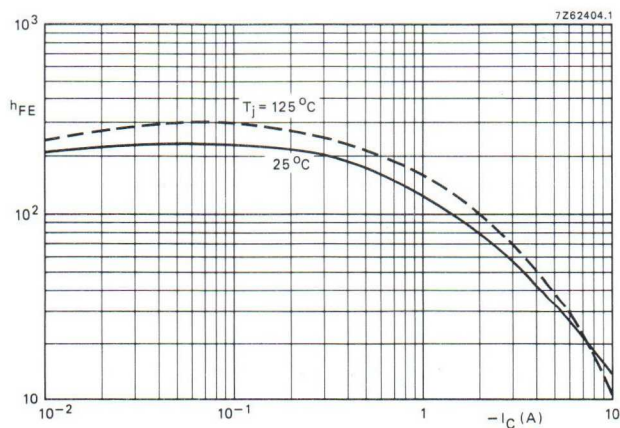


Fig.3 Pulse power rating chart.

Fig.4 DC current gain; $-V_{CE} = 2\text{ V}$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS643/645/647/649/651

NPN silicon Darlington power transistors

DESCRIPTION

NPN epitaxial base transistors in a monolithic Darlington circuit in SOT223, intended for general purpose and switching applications. PNP complements are BDS644/646/648/650/652.

PINNING - SOT223

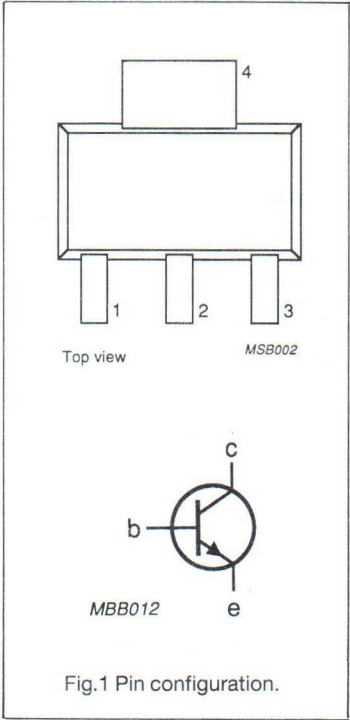
PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	60	V
	BDS643		-	80	V
	BDS645		-	100	V
	BDS647		-	120	V
	BDS649		-	140	V
V _{CEO}	collector-emitter voltage	open base	-	45	V
	BDS643		-	60	V
	BDS645		-	80	V
	BDS647		-	100	V
	BDS649		-	120	V
I _C	collector current	average value	-	3	A
I _{CM}	collector current	peak value	-	7	A
P _{tot}	total power dissipation	T _{tab} = 25 °C note 1	-	8 1.5	W W
T _j	junction temperature		-	150	°C
h _{FE}	DC current gain	I _C = 3 mA; V _{CE} = 3 V;	1000		

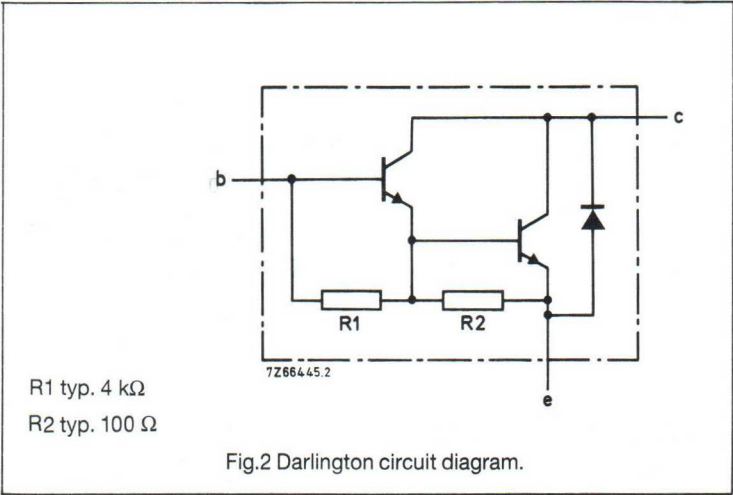
Note

- 1. Mounted on PCB



NPN silicon Darlington power transistors

BDS643/645/647/649/651



LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	60	V
	BDS643		-	80	V
	BDS645		-	100	V
	BDS647		-	120	V
	BDS649		-	140	V
	BDS651		-	140	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
	BDS643		-	60	V
	BDS645		-	80	V
	BDS647		-	100	V
	BDS649		-	120	V
	BDS651		-	120	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
I_B	base current		-	150	mA
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

NPN silicon Darlington power transistors**BDS643/645/647/649/651****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

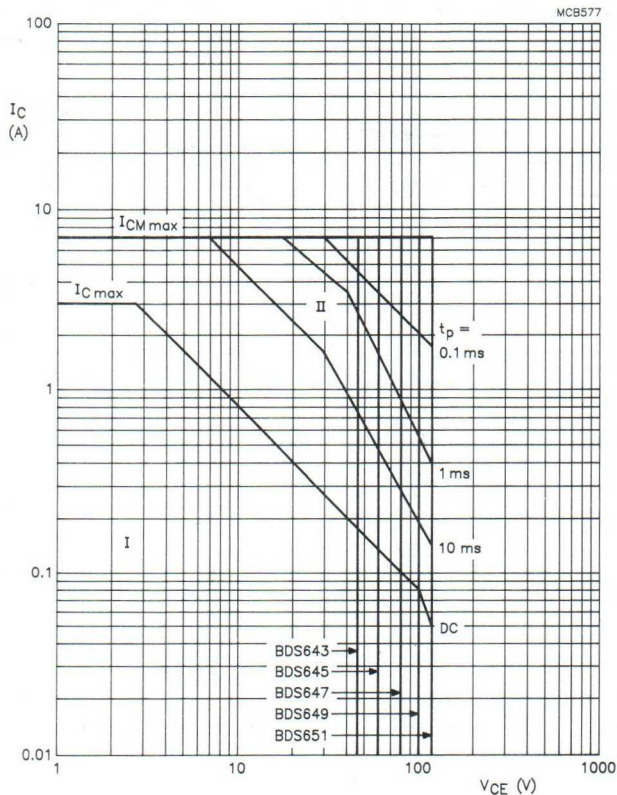
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 1/2 V_{CEO\text{ max}}$	-	-	0.2	mA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CEO\text{ max}}$	-	-	0.1	mA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 1/2 V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	-	5	mA
V_{BE}	base-emitter voltage	$I_C = 3\text{ A}$; $V_{CE} = 3\text{ V}$; note 1	-	-	2.5	V
$V_{CE\text{ sat}}$	saturation voltage	$I_C = 3\text{ A}$; $I_B = 12\text{ mA}$; note 1	-	-	2	V
$V_{CE\text{ sat}}$	saturation voltage	$I_C = 5\text{ A}$; $I_B = 50\text{ mA}$; note 1	-	-	2.5	V
$V_{BE\text{ sat}}$	saturation voltage	$I_C = 5\text{ A}$; $I_B = 50\text{ mA}$; note 1	-	-	3	V
h_{FE}	DC current gain	$I_C = 0.5\text{ A}$; $V_{CE} = 3\text{ V}$; note 1	-	2000	-	
h_{FE}	DC current gain	$I_C = 3\text{ A}$; $V_{CE} = 3\text{ V}$; note 1	1000	-	-	
V_F	diode forward voltage	$I_F = 3\text{ A}$	-	1.8	-	V
f_{hfe}	cut-off frequency	$I_C = 3\text{ A}$; $V_{CE} = 3\text{ V}$	-	50	-	kHz
h_{fe}	small signal current gain	$f = 1\text{ MHz}$; $I_C = 3\text{ A}$; $V_{CE} = 3\text{ V}$	10	-	-	
C_c	collector capacitance	$f = 1\text{ MHz}$; $V_{CB} = 10\text{ V}$	-	75	-	pF
t_{on}	switching times turn-on time	$I_{C\text{ on}} = 3\text{ A}$; $I_{B\text{ on}} = I_{B\text{ off}} = 12\text{ mA}$	-	-	2	μs
t_{off}	switching times turn-off time		-	-	10	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon Darlington power transistors

BDS643/645/647/649/651

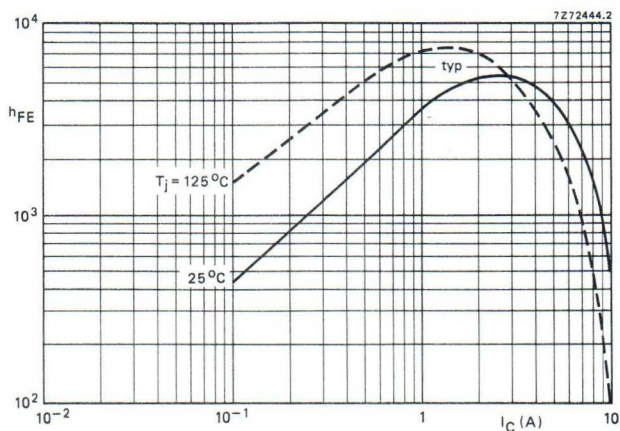
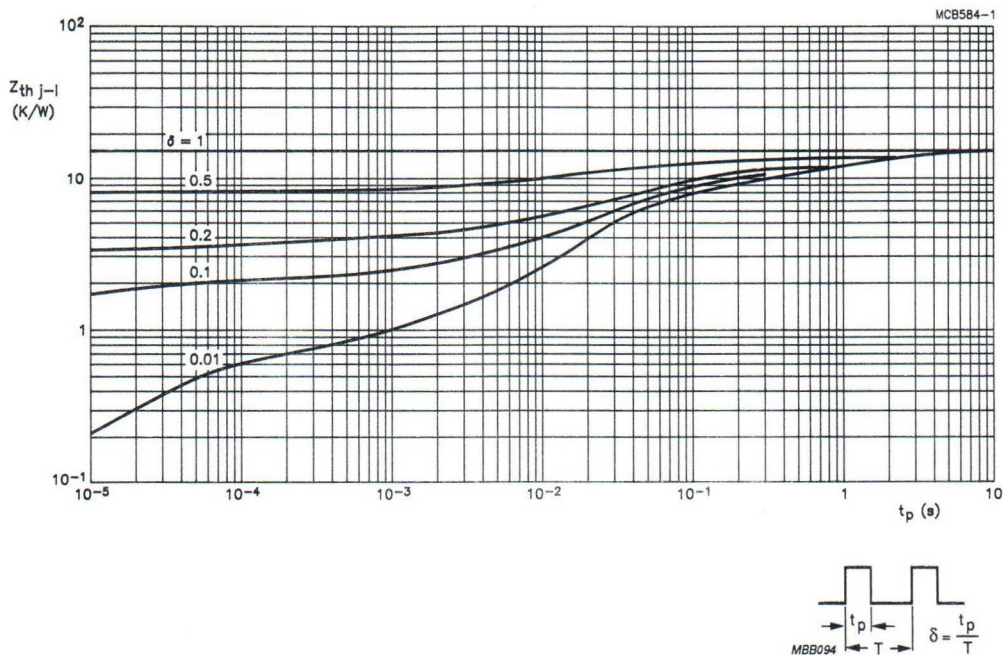


- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.

Fig. 3 Safe operating area; $T_{\text{tab}} = 25\ ^\circ\text{C}$.

NPN silicon Darlington power transistors

BDS643/645/647/649/651





Philips Components

Data sheet	
status	Product specification
date of issue	April 1991

BDS644/646/648/650/652

PNP silicon Darlington power transistors

DESCRIPTION

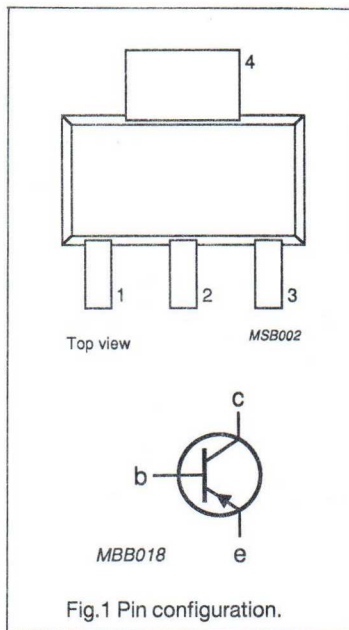
PNP silicon epitaxial base transistors in a monolithic Darlington circuit in a miniature SMD envelope (SOT223), intended for general purpose and switching applications. NPN complements are BDS643/645/647/649/651.

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

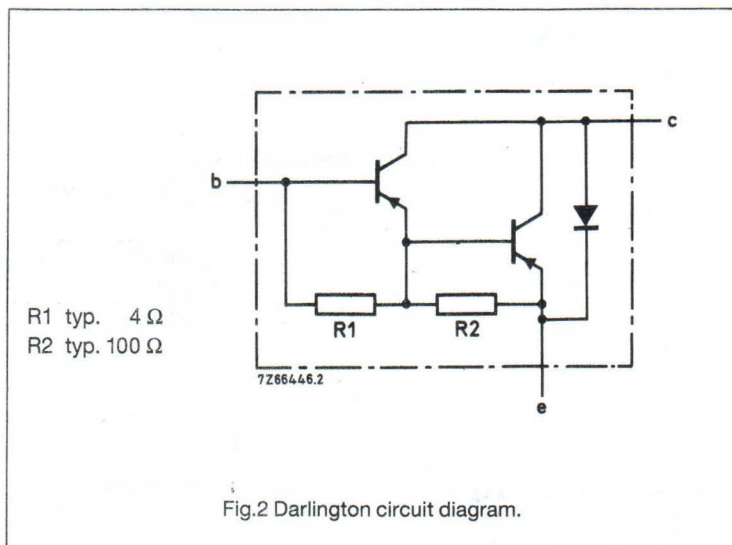
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	45	V
	BDS644		-	60	V
	BDS646		-	80	V
	BDS648		-	100	V
	BDS650		-	120	V
$-V_{CEO}$	collector-emitter voltage	open base	-	45	V
	BDS644		-	60	V
	BDS646		-	80	V
	BDS648		-	100	V
	BDS650		-	120	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 3\text{ mA}$; $-V_{CE} = 3\text{ V}$;	1000		



Note

1. Mounted on PCB

PNP silicon Darlington power transistors**BDS644/646/648/650/652****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	45	V
	BDS644		-	60	V
	BDS646		-	80	V
	BDS648		-	100	V
	BDS650		-	120	V
	BDS652		-	120	V
$-V_{CEO}$	collector-emitter voltage	open base	-	45	V
	BDS644		-	60	V
	BDS646		-	80	V
	BDS648		-	100	V
	BDS650		-	120	V
	BDS652		-	120	V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
$-I_B$	base current		-	150	mA
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

PNP silicon Darlington power transistors**BDS644/646/648/650/652****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

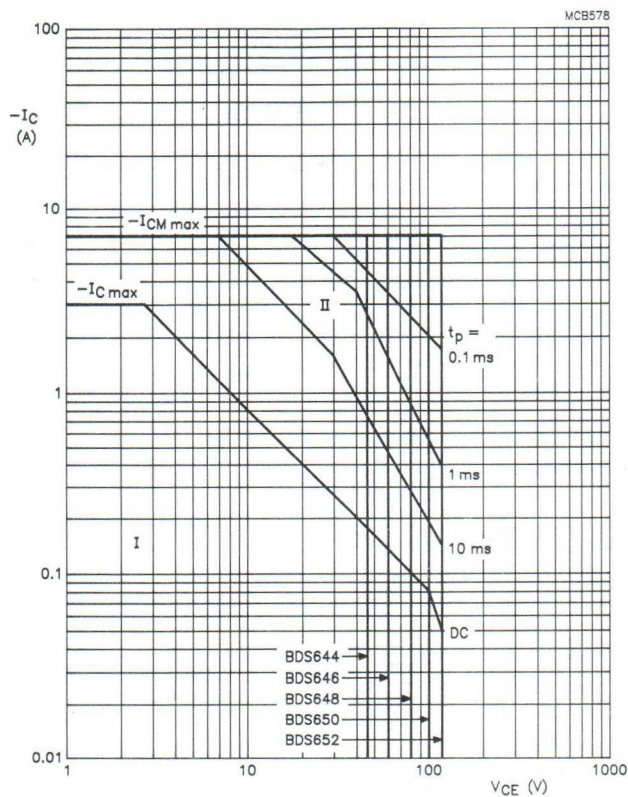
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-I_{CEO}$	collector cut-off current	$-I_B = 0$; $-V_{CE} = 1/2 V_{CEO\text{ max}}$	-	-	0.2	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CEO\text{ max}}$	-	-	0.1	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = 1/2 V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
$-I_{EBO}$	emitter cut-off current	$-I_C = 0$; $-V_{EB} = 5\text{ V}$	-	-	5	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	-	2.5	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 3\text{ A}$; $-I_B = 12\text{ mA}$; note 1	-	-	2	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 5\text{ A}$; $-I_B = 50\text{ mA}$; note 1	-	-	2.5	V
$-V_{BE\text{ sat}}$	base-emitter saturation voltage	$-I_C = 5\text{ A}$; $-I_B = 50\text{ mA}$; note 1	-	-	3	V
h_{FE}	DC current gain	$-I_C = 0.5\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	-	2000	-	
h_{FE}	DC current gain	$-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$; note 1	1000	-	-	
V_F	diode forward voltage	$I_F = 3\text{ A}$	-	1.2	-	V
f_{hfe}	cut-off frequency	$-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$	-	100	-	kHz
h_{fe}	small signal current gain	$f = 1\text{ MHz}$; $-I_C = 3\text{ A}$; $-V_{CE} = 3\text{ V}$;	10	-	-	
C_c	collector capacitance	$f = 1\text{ MHz}$; $-V_{CB} = 10\text{ V}$	-	75	-	pF
t_{on}	switching times turn-on time	$-I_{C\text{ on}} = 3\text{ A}$; $-I_{B\text{ on}} = I_{B\text{ off}} = 12\text{ mA}$; $-V_{CC} = 10\text{ V}$	-	-	2	μs
t_{off}	switching times turn-off time		-	-	10	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon Darlington power transistors

BDS644/646/648/650/652



- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.

Fig.3 Safe operating area; $T_{\text{tab}} = 25^\circ\text{C}$.

PNP silicon Darlington power transistors

BDS644/646/648/650/652

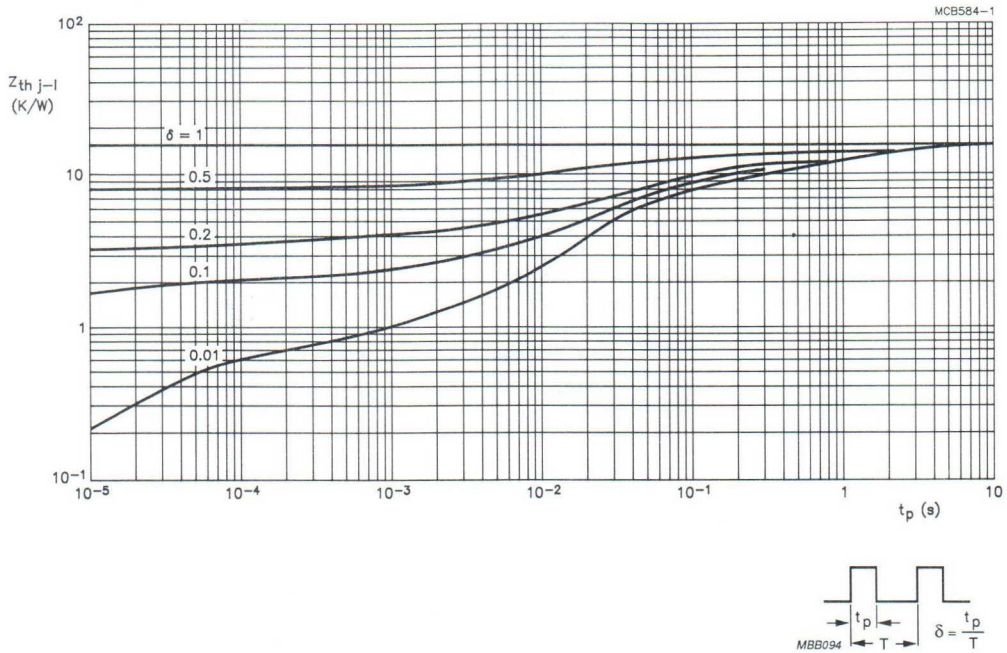


Fig.4 Pulse power rating chart.

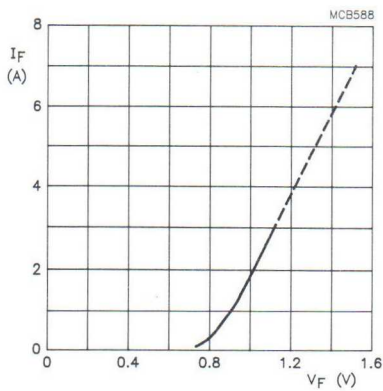
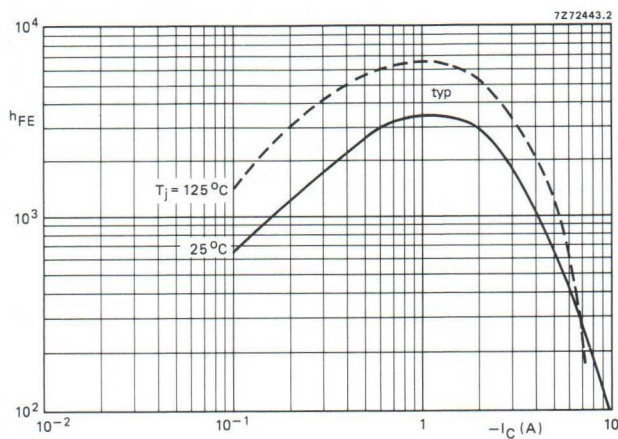


Fig.5 Diode forward current as a function of forward voltage; $T_{tab} = 25\text{ }^{\circ}\text{C}$; typical values.

PNP silicon Darlington power transistors

BDS644/646/648/650/652

Fig.6 DC current gain; $-V_{CE} = 3$ V; typical values.

Data sheet	
status	Product specification
date of issue	April 1991

BDS933/935/937/939/941

NPN silicon epitaxial base power transistors

DESCRIPTION

NPN silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. PNP complements are BDS934/936/938/940/942.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	45	V
	BDS933		-	60	V
	BDS935		-	100	V
	BDS937		-	120	V
	BDS939		-	140	V
	BDS941		-		
V_{CEO}	collector-emitter voltage	open base	-	45	V
	BDS933		-	60	V
	BDS935		-	80	V
	BDS937		-	100	V
	BDS939		-	120	V
	BDS941		-		
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	6	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8	W
			-	1.5	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$I_C = 150\text{ mA};$ $V_{CE} = 2\text{ V};$	40	250	
h_{FE}	DC current gain	$I_C = 1\text{ A};$ $V_{CE} = 2\text{ V};$	25	-	
f_T	transition frequency	$I_C = 250\text{ mA};$ $V_{CE} = 10\text{ V}$	3	-	MHz

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

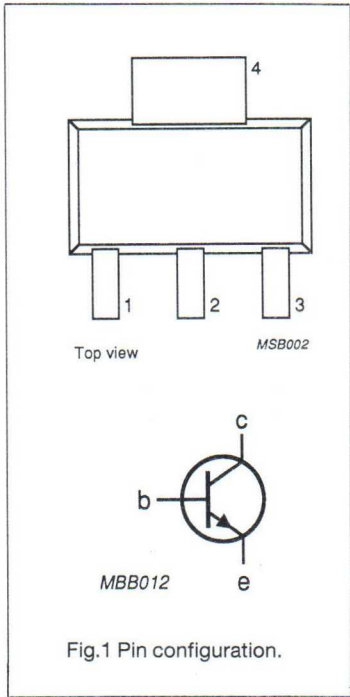


Fig.1 Pin configuration.

Note

1. Mounted on PCB

NPN silicon epitaxial base power transistors

BDS933/935/937/939/941

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BDS933		-	45	V
	BDS935		-	60	V
	BDS937		-	100	V
	BDS939		-	120	V
	BDS941		-	140	V
V _{CEO}	collector-emitter voltage	open base			
	BDS933		-	45	V
	BDS935		-	60	V
	BDS937		-	80	V
	BDS939		-	100	V
	BDS941		-	120	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current	average value	-	3	A
I _{CM}	collector current	peak value	-	6	A
I _B	base current		-	0.5	A
P _{tot}	total power dissipation	T _{tab} = 25 °C	-	8	W
T _{stg}	storage temperature range		-65	+150	°C
T _j	junction temperature		-	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
R _{th j-t}	from junction to tab		15.5	K/W
R _{th j-a}	from junction to ambient	on PCB	83.3	K/W

NPN silicon epitaxial base power transistors

BDS933/935/937/939/941

CHARACTERISTICS

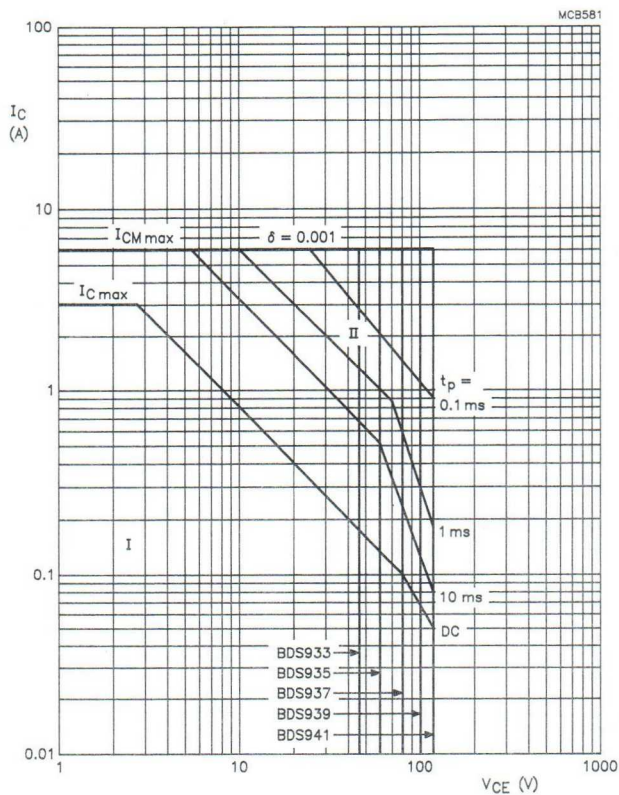
 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CBO\text{ max}}$	-	-	50	μA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = V_{CEO\text{ max}}$	-	-	0.1	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	-	0.2	mA
V_{BE}	base-emitter voltage	$I_C = 1\text{ A}$; $V_{CE} = 2\text{ V}$; note 1	-	-	1.3	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 1\text{ A}$; $I_B = 0.1\text{ A}$	-	-	0.6	V
h_{FE}	DC current gain	$I_C = 150\text{ mA}$; $V_{CE} = 2\text{ V}$; note 1	40	-	250	
h_{FE}	DC current gain	$I_C = 1\text{ A}$; $V_{CE} = 2\text{ V}$; note 1	25	-	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $I_C = 250\text{ mA}$; $V_{CE} = 10\text{ V}$	3	-	-	MHz
t_{on}	switching times turn-on time	$I_{C\text{ on}} = 1\text{ A}$; $I_{B\text{ on}} = -I_{B\text{ off}} = 0.1\text{ A}$	-	0.4	1	μs
t_{off}	switching times turn-off time		-	1.5	3	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon epitaxial base power transistors

BDS933/935/937/939/941


- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.

Fig.2 Safe operating area; $T_{tab} = 25\ ^\circ C$.

**NPN silicon epitaxial base
power transistors**

BDS933/935/937/939/941

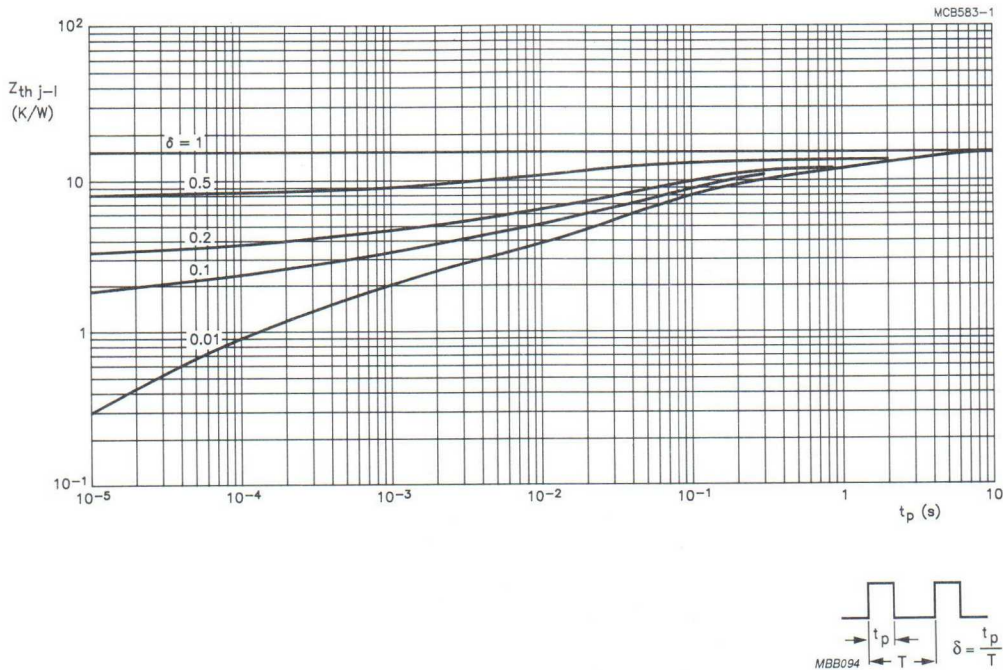


Fig.3 Pulse power rating chart.

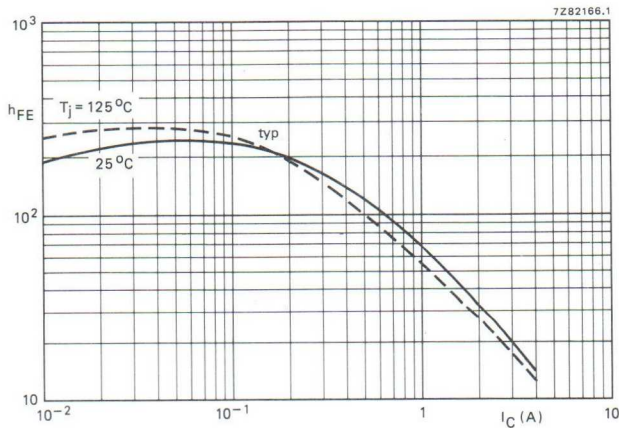


Fig.4 Typical DC current gain; $V_{CE} = 2$ V.

Data sheet	
status	Product specification
date of issue	April 1991

BDS934/936/938/940/942

PNP silicon epitaxial base power transistors

DESCRIPTION

PNP silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. NPN complements are BDS933/935/937/939/941.

QUICK REFERENCE DATA

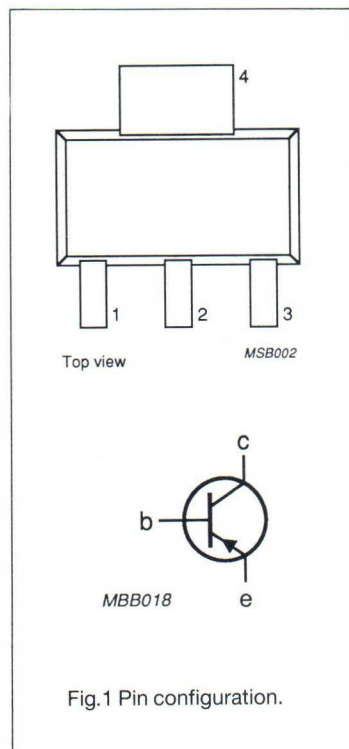
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-		
	BDS934		-	45	V
	BDS936		-	60	V
	BDS938		-	100	V
	BDS940		-	120	V
	BDS942		-	140	V
$-V_{CEO}$	collector-emitter voltage	open base	-		
	BDS934		-	45	V
	BDS936		-	60	V
	BDS938		-	80	V
	BDS940		-	100	V
	BDS942		-	120	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	6	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8 1.5	W W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 150\text{ mA};$ $-V_{CE} = 2\text{ V}$	40	250	
h_{FE}	DC current gain	$-I_C = 1\text{ A};$ $-V_{CE} = 2\text{ V}$	25	-	
f_T	transition frequency	$-I_C = 250\text{ mA};$ $-V_{CE} = 10\text{ V}$	3	-	MHz

Note

1. When mounted on PCB

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



PNP silicon epitaxial base power transistors

BDS934/936/938/940/942

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter			
	BDS934		-	45	V
	BDS936		-	60	V
	BDS938		-	100	V
	BDS940		-	120	V
	BDS942		-	140	V
$-V_{CEO}$	collector-emitter voltage	open base			
	BDS934		-	45	V
	BDS936		-	60	V
	BDS938		-	80	V
	BDS940		-	100	V
	BDS942		-	120	V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	6	A
$-I_B$	base current		-	0.5	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

PNP silicon epitaxial base power transistors

BDS934/936/938/940/942

CHARACTERISTICS

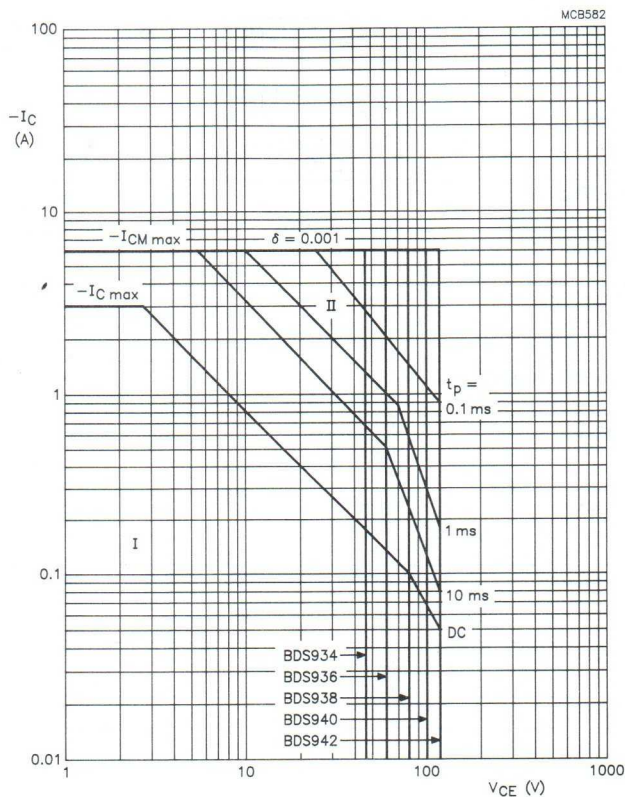
 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CBO\text{ max}}$	-	-	50	μA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	-	1	mA
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $-V_{CE} = -V_{CEO\text{ max}}$	-	-	0.1	mA
$-I_{EBO}$	emitter cut-off current	$-I_C = 0$; $-V_{EB} = 5\text{ V}$	-	-	0.2	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 1\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	-	-	1.3	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 1\text{ A}$; $-I_B = 0.1\text{ A}$	-	-	0.6	V
h_{FE}	DC current gain	$-I_C = 150\text{ mA}$; $-V_{CE} = 2\text{ V}$; note 1	40	-	250	
h_{FE}	DC current gain	$-I_C = 1\text{ A}$; $-V_{CE} = 2\text{ V}$; note 1	25	-	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $-I_C = 250\text{ mA}$; $-V_{CE} = 10\text{ V}$	3	-	-	MHz
t_{on}	switching times turn-on time	$-I_{C\text{ on}} = 1\text{ A}$; $I_{B\text{ on}} = I_{B\text{ off}} = 0.1\text{ A}$	-	0.2	0.6	μs
t_{off}	switching times	turn-off time	-	0.7	2.4	μs

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon epitaxial base power transistors

BDS934/936/938/940/942


- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.

Fig.2 Safe operating area; $T_{tab} = 25\ ^\circ\text{C}$.

PNP silicon epitaxial base power transistors

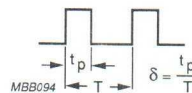
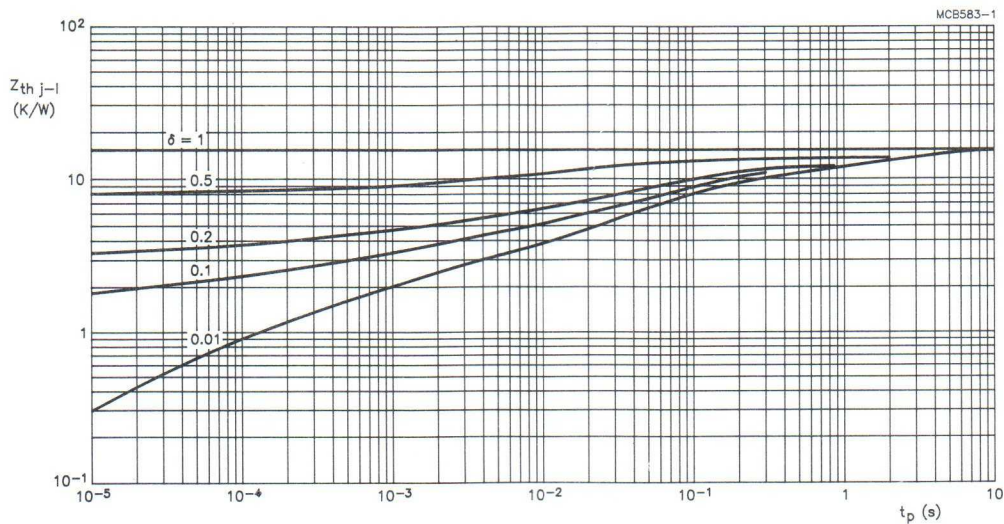
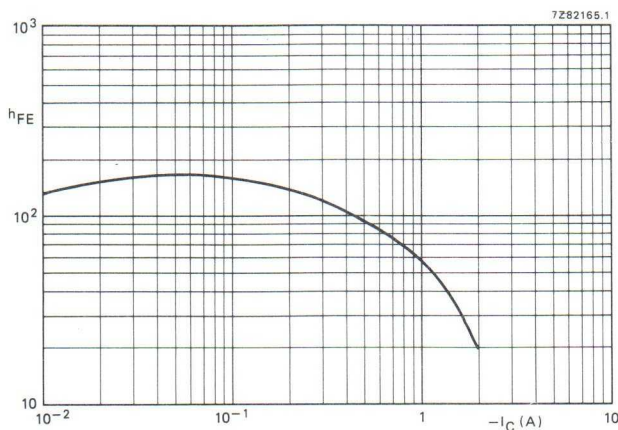
BDS934/936/938/940/942


Fig.3 Pulse power rating chart.


 Fig.4 Typical static forward current transfer ratio as
a function of the collector current; $-V_{CE} = 2$ V; $T_j \leq 25^\circ\text{C}$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS943/945/947

NPN silicon epitaxial base power transistors

DESCRIPTION

NPN silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. PNP complements are BDS944/946/948.

QUICK REFERENCE DATA

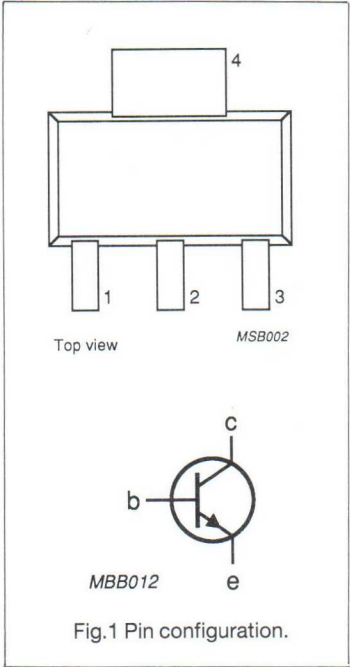
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	22	V
	BDS943		-	32	V
	BDS945		-	45	V
	BDS947		-	45	V
V_{CEO}	collector-emitter voltage	open base	-	22	V
	BDS943		-	32	V
	BDS945		-	45	V
	BDS947		-	45	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
		note 1	-	1.5	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	25	-	
h_{FE}	DC current gain	$I_C = 500\text{ mA}; V_{CE} = 1\text{ V}$	85	475	
h_{FE}	DC current gain	$I_C = 2\text{ A}; V_{CE} = 1\text{ V}$	50	-	
	BDS943		50	-	
	BDS945		40	-	
	BDS947		40	-	

Note

1. Mounted on PCB.

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



NPN silicon epitaxial base power transistors**BDS943/945/947****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BDS943		-	22	V
	BDS945		-	32	V
	BDS947		-	45	V
V_{CEO}	collector-emitter voltage	open base			
	BDS943		-	22	V
	BDS945		-	32	V
	BDS947		-	45	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
I_B	base current		-	1	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

NPN silicon epitaxial base power transistors**BDS943/945/947****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

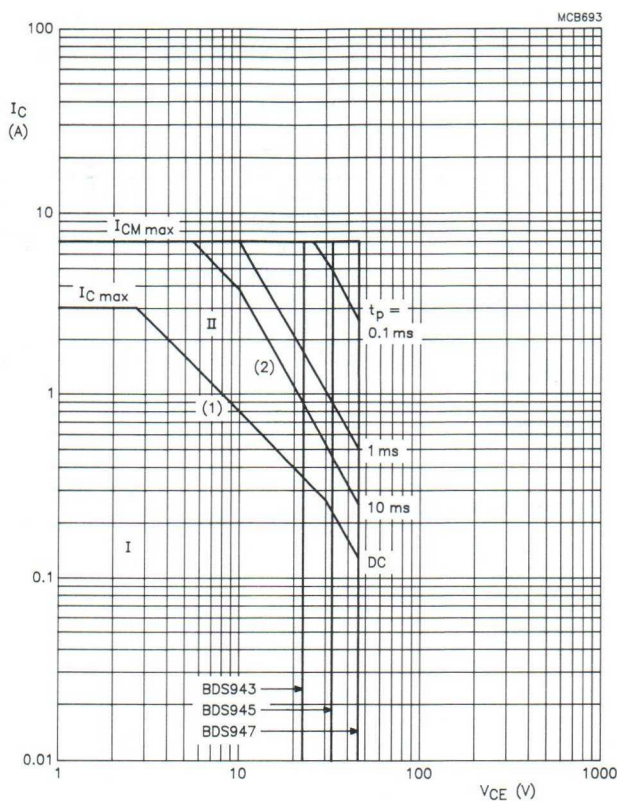
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CBO\text{ max}}$	-	50	μA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 15\text{ V}$ (BDS943)	-	0.1	mA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 20\text{ V}$ (BDS945)	-	0.1	mA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 25\text{ V}$ (BDS947)	-	0.1	mA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	1	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	0.2	mA
V_{BE}	base-emitter voltage	$I_C = 2\text{ A}$; $V_{CE} = 1\text{ V}$; note 1	-	1.2	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 2\text{ A}$; $I_B = 0.2\text{ A}$; note 1	-	0.5	V
h_{FE}	DC current gain	$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$; note 1	25	-	
h_{FE}	DC current gain	$I_C = 500\text{ mA}$; $V_{CE} = 1\text{ V}$; note 1	85	475	
h_{FE}	DC current gain	$I_C = 2\text{ A}$; $V_{CE} = 1\text{ V}$; note 1 (BDS943/945)	50	-	
h_{FE}	DC current gain	$I_C = 250\text{ mA}$; $V_{CE} = 1\text{ V}$; note 1 (BDS947)	40	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $I_C = 250\text{ mA}$; $V_{CE} = 1\text{ V}$	3	-	MHz

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon epitaxial base power transistors

BDS943/945/947

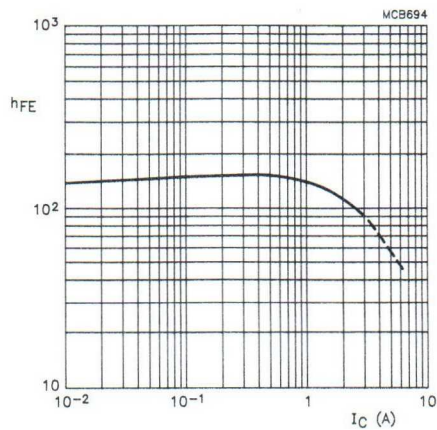
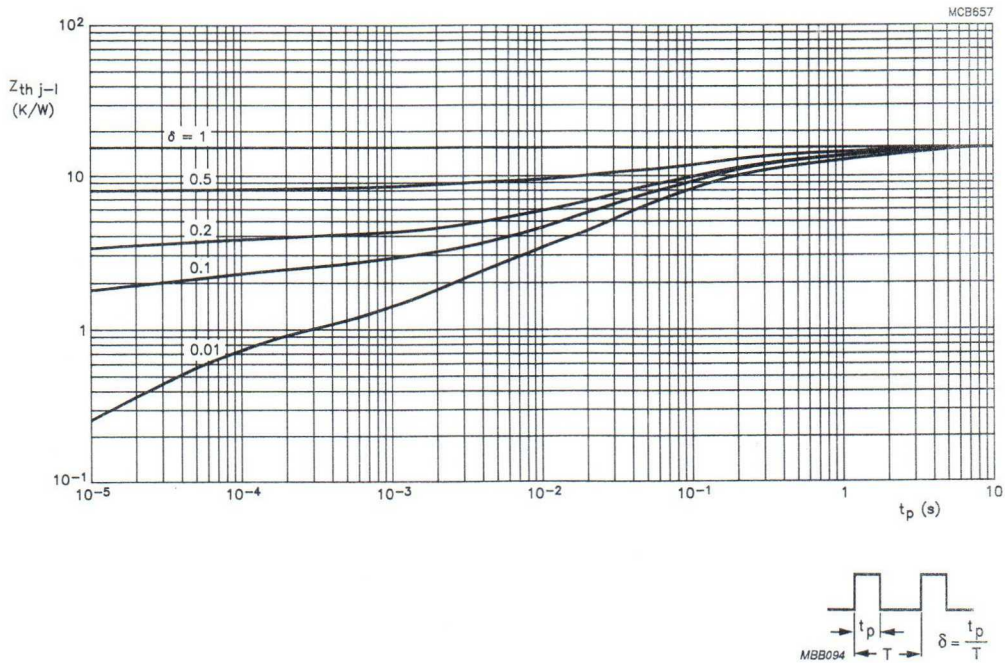


1. Region of permissible DC operation.
2. Permissible extension for repetitive pulse operation.
- (1) $P_{tot} \max$ and $P_{peak} \max$ lines.
- (2) Second breakdown limits.

Fig.2 Safe operating area; $T_{tab} = 25^\circ \text{C}$.

NPN silicon epitaxial base power transistors

BDS943/945/947



NPN silicon epitaxial base power transistors

BDS943/945/947

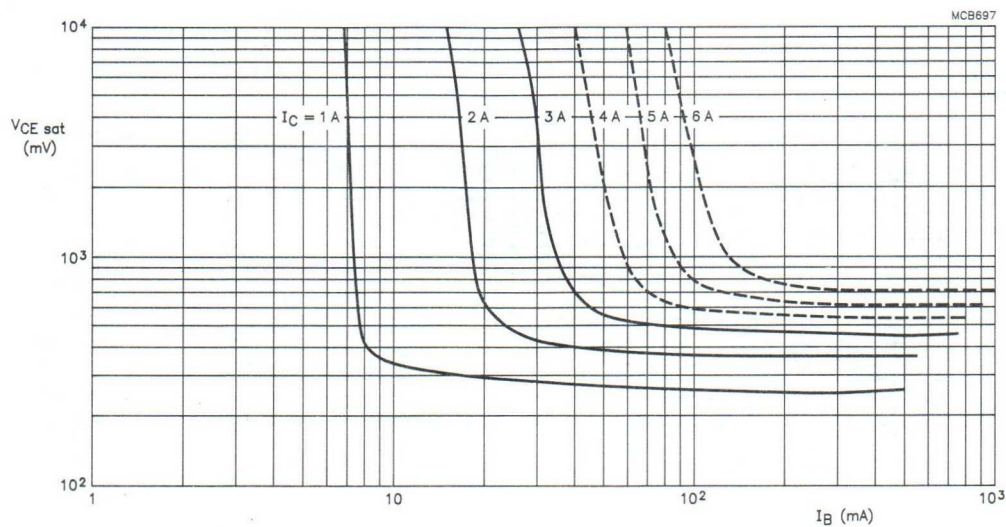


Fig.5 Typical values of collector-emitter saturation voltage at $T_{tab} = 25\ ^\circ C$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS944/946/948

PNP silicon epitaxial base power transistors

DESCRIPTION

PNP silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. NPN complements are BDS943/945/947.

QUICK REFERENCE DATA

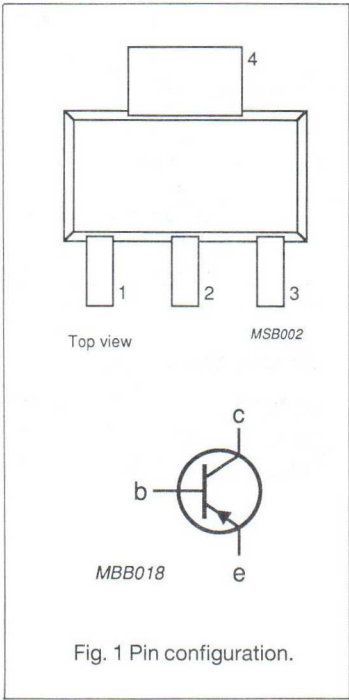
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter			
			-	22	V
			-	32	V
			-	45	V
$-V_{CEO}$	collector-emitter voltage	open base			
			-	22	V
			-	32	V
			-	45	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$ note 1	-	8	W
			-	1.5	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 10\text{ mA};$ $-V_{CE} = 5\text{ V}$	25	-	
h_{FE}	DC current gain	$-I_C = 500\text{ mA};$ $-V_{CE} = 1\text{ V}$	85	475	
h_{FE}	DC current gain	$-I_C = 2\text{ A};$ $-V_{CE} = 1\text{ V}$			
			50	-	
			50	-	
			40	-	

Note

1. Mounted on PCB.

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



PNP silicon epitaxial base power transistors**BDS944/946/948****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter			
	BDS944		-	22	V
	BDS946		-	32	V
	BDS948		-	45	V
$-V_{CEO}$	collector-emitter voltage	open base			
	BDS944		-	22	V
	BDS946		-	32	V
	BDS948		-	45	V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
$-I_B$	base current		-	1	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

PNP silicon epitaxial base power transistors**BDS944/946/948****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

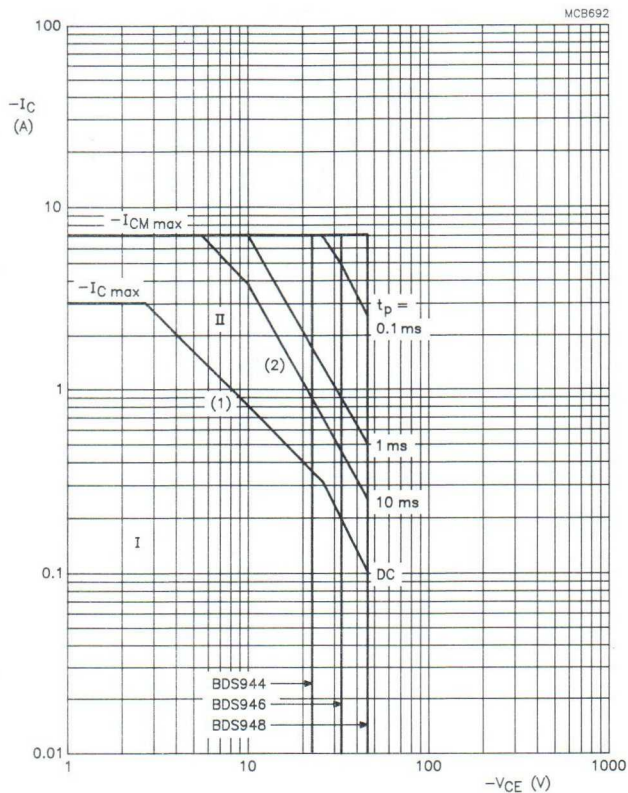
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CBO\text{ max}}$	-	50	μA
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $-V_{CE} = 15\text{ V}$ (BDS944)	-	0.1	mA
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $-V_{CE} = 20\text{ V}$ (BDS946)	-	0.1	mA
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $-V_{CE} = 25\text{ V}$ (BDS948)	-	0.1	mA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	1	mA
$-I_{EBO}$	emitter cut-off current	$I_C = 0$; $-V_{EB} = 5\text{ V}$	-	0.2	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 2\text{ A}$; $-V_{CE} = 1\text{ V}$; note 1	-	1.2	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 2\text{ A}$; $-I_B = 0.2\text{ A}$; note 1	-	0.5	V
h_{FE}	DC current gain	$-I_C = 10\text{ mA}$; $-V_{CE} = 5\text{ V}$; note 1	25	-	
h_{FE}	DC current gain	$-I_C = 500\text{ mA}$; $-V_{CE} = 1\text{ V}$; note 1	85	475	
h_{FE}	DC current gain	$-I_C = 2\text{ A}$; $-V_{CE} = 1\text{ V}$; note 1 (BDS944/946)	50	-	
h_{FE}	DC current gain	$-I_C = 2\text{ A}$; $-V_{CE} = 1\text{ V}$; note 1 (BDS948)	40	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $-I_C = 250\text{ mA}$; $-V_{CE} = 1\text{ V}$	3	-	MHz

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon epitaxial base power transistors

BDS944/946/948



1. Region of permissible DC operation.
2. Permissible extension for repetitive pulse operation.
 - (1) $P_{tot\ max}$ and $P_{peak\ max}$ lines.
 - (2) Second breakdown limits.

Fig.2 Safe operating area; $T_{\text{tab}} = 25\text{ }^{\circ}\text{C}$.

PNP silicon epitaxial base power transistors

BDS944/946/948

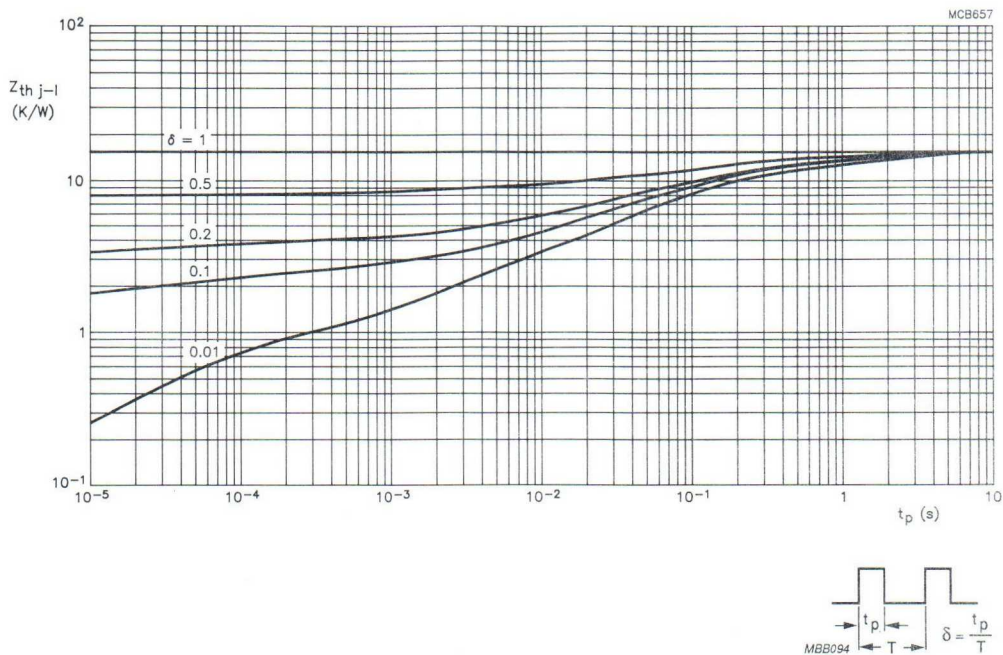
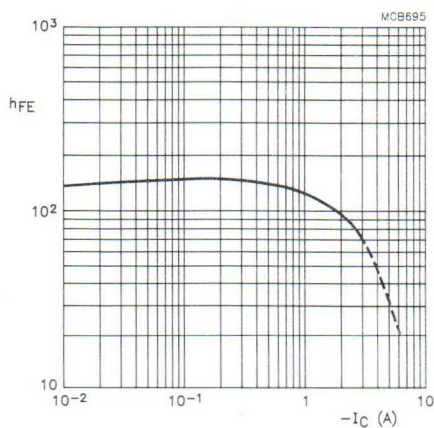
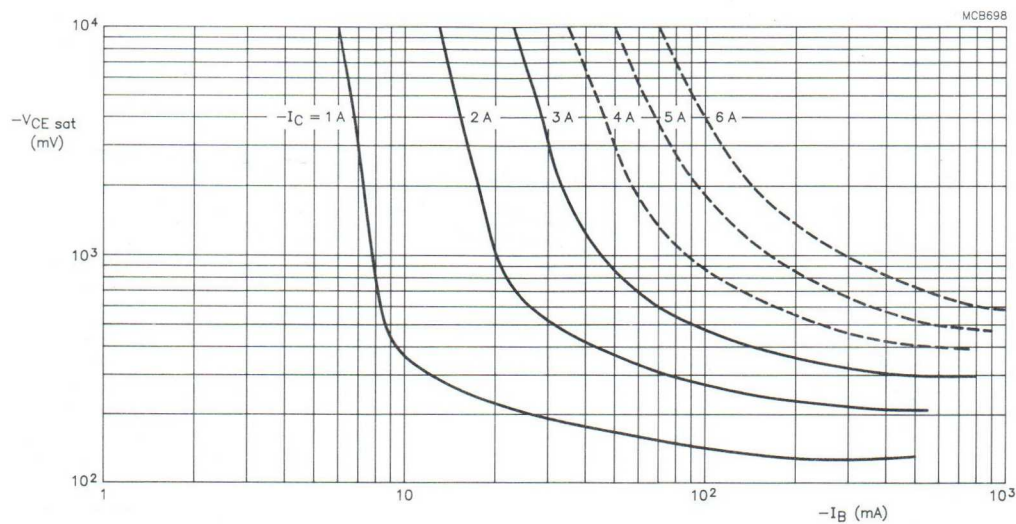


Fig.3 Pulse power rating chart.

Fig.4 Typical DC current gain; $V_{CE} = 1$ V;
 $T_{tab} = 25$ °C.

PNP silicon epitaxial base power transistors

BDS944/946/948

Fig.5 Typical values of collector-emitter saturation voltage at $T_{\text{tab}} = 25^\circ\text{C}$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS949/951/953/955

NPN silicon epitaxial base power transistors

DESCRIPTION

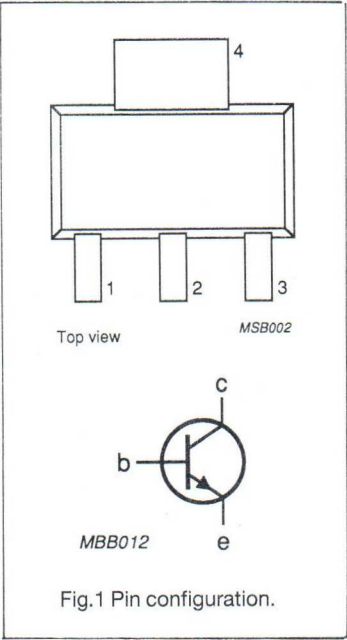
NPN silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. PNP complements are BDS950/952/954/956.

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
			-	60	V
			-	80	V
			-	100	V
			-	120	V
V _{CEO}	collector-emitter voltage	open base			
			-	60	V
			-	80	V
			-	100	V
			-	120	V
I _C	collector current	average value	-	3	A
I _{CM}	collector current	peak value	-	7	A
P _{tot}	total power dissipation	T _{tab} = 25 °C note 1	-	8 1.5	W W
T _j	junction temperature		-	150	°C
h _{FE}	DC current gain	I _C = 0.5 A; V _{CE} = 4 V	40	-	
h _{FE}	DC current gain	I _C = 2 A; V _{CE} = 4 V	20	-	



Note

1. Mounted on PCB.

NPN silicon epitaxial base power transistors**BDS949/951/953/955****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BDS949		-	60	V
	BDS951		-	80	V
	BDS953		-	100	V
	BDS955		-	120	V
V_{CEO}	collector-emitter voltage	open base			
	BDS949		-	60	V
	BDS951		-	80	V
	BDS953		-	100	V
	BDS955		-	120	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current	average value	-	3	A
I_{CM}	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-t}$	from junction to tab		15.5	K/W
$R_{th\ j-a}$	from junction to ambient	on PCB	83.3	K/W

NPN silicon epitaxial base power transistors**BDS949/951/953/955****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

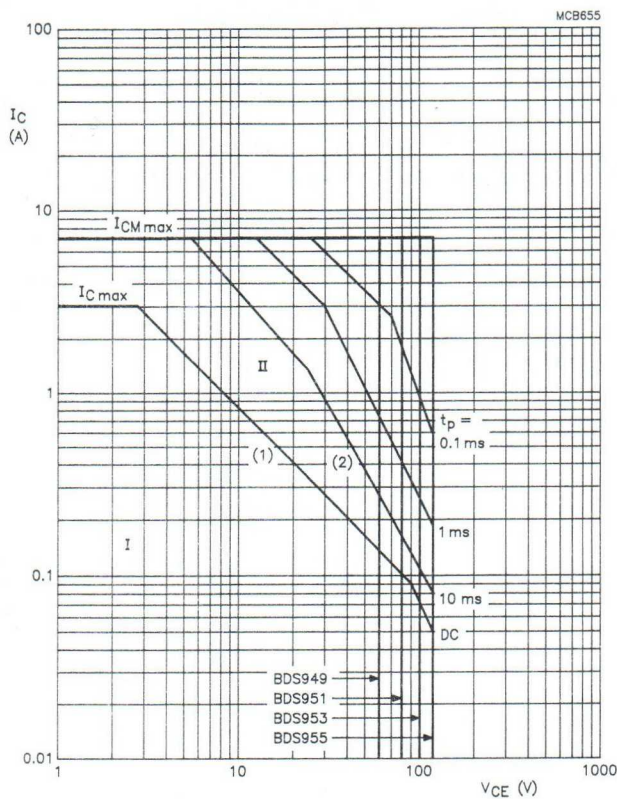
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = V_{CBO\text{ max}}$	-	50	μA
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 1/2 V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	1	mA
I_{CEO}	collector cut-off current	$I_B = 0$; $V_{CE} = 1/2 V_{CEO\text{ max}}$	-	0.1	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	-	0.2	mA
V_{BE}	base-emitter voltage	$I_C = 2\text{ A}$; $V_{CE} = 4\text{ V}$; note 1	-	1.4	V
$V_{CE\text{ sat}}$	collector-emitter saturation voltage	$I_C = 2\text{ A}$; $I_B = 0.2\text{ A}$; note 1	-	1	V
h_{FE}	DC current gain	$I_C = 500\text{ mA}$; $V_{CE} = 4\text{ V}$; note 1	40	-	
h_{FE}	DC current gain	$I_C = 2\text{ A}$; $V_{CE} = 4\text{ V}$; note 1	20	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $I_C = 500\text{ mA}$; $V_{CE} = 4\text{ V}$	3	-	MHz

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

NPN silicon epitaxial base power transistors

BDS949/951/953/955

Fig.2 Safe operating area; $T_{tab} = 25\ ^\circ\text{C}$.

NPN silicon epitaxial base power transistors

BDS949/951/953/955

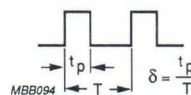
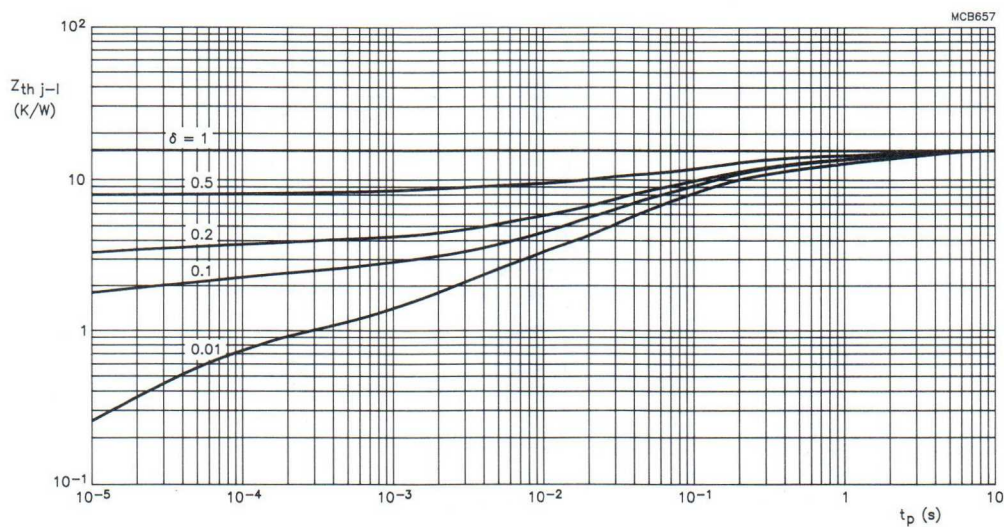
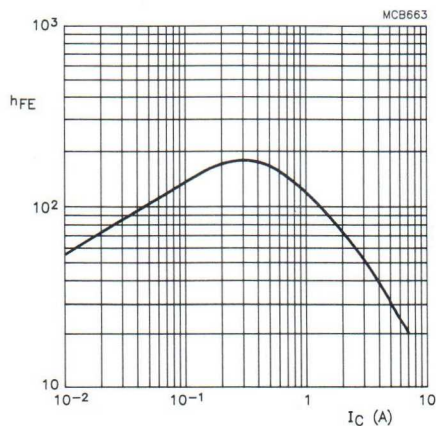


Fig.3 Pulse power rating chart.

Fig.4 Typical DC current gain; $V_{CE} = 4 V$; $T_{tab} = 25^\circ C$.

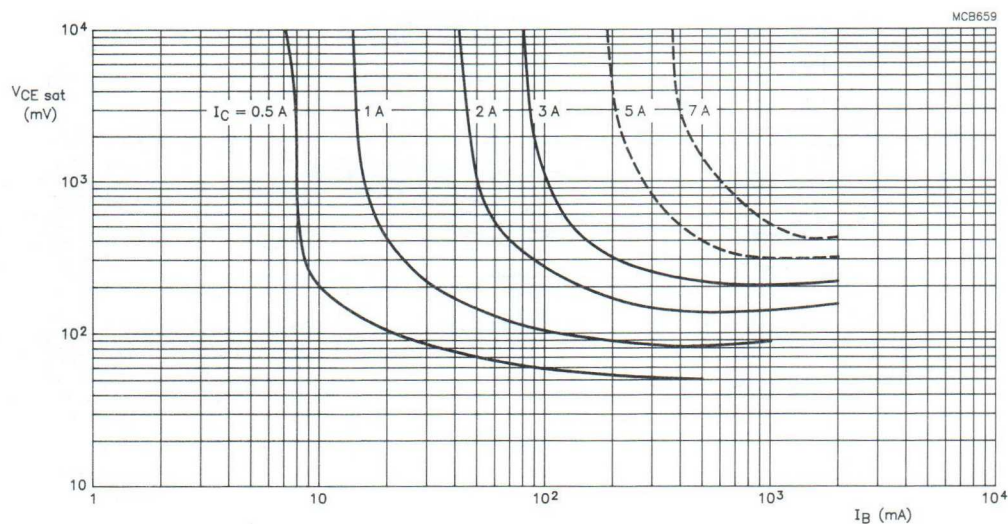
NPN silicon epitaxial base power transistors**BDS949/951/953/955**

Fig.5 Typical values of collector-emitter saturation voltage at $T_{tab} = 25\ ^\circ C$.

Data sheet	
status	Product specification
date of issue	April 1991

BDS950/952/954/956

PNP silicon epitaxial base power transistors

DESCRIPTION

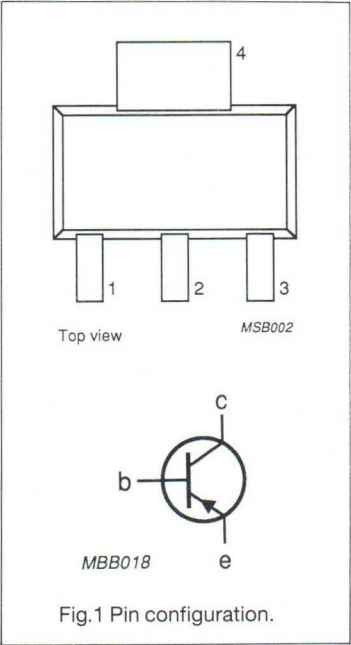
PNP silicon epitaxial base transistors in a miniature SMD envelope (SOT223) intended for general purpose and switching applications. NPN complements are BDS949/951/953/955.

PINNING - SOT223

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter			
	BDS950		-	60	V
	BDS952		-	80	V
	BDS954		-	100	V
	BDS956		-	120	V
$-V_{CEO}$	collector-emitter voltage	open base			
	BDS950		-	60	V
	BDS952		-	80	V
	BDS954		-	100	V
	BDS956		-	120	V
$-I_C$	collector current	average value	-	3	A
$-I_{CM}$	collector current	peak value	-	7	A
P_{tot}	total power dissipation	$T_{tab} = 25\text{ }^{\circ}\text{C}$	-	8	W
		note 1	-	1.5	W
T_j	junction temperature		-	150	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 0.5\text{ A};$ $-V_{CE} = 4\text{ V}$	40	-	
h_{FE}	DC current gain	$-I_C = 2\text{ A};$ $-V_{CE} = 4\text{ V}$	20	-	



Note

- 1. Mounted on PCB.

PNP silicon epitaxial base power transistors**BDS950/952/954/956****LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
-V _{CBO}	collector-base voltage	open emitter			
	BDS950		-	60	V
	BDS952		-	80	V
	BDS954		-	100	V
	BDS956		-	120	V
-V _{CEO}	collector-emitter voltage	open base			
	BDS950		-	60	V
	BDS952		-	80	V
	BDS954		-	100	V
	BDS956		-	120	V
-V _{EBO}	emitter-base voltage	open collector	-	5	V
-I _C	collector current	average value	-	3	A
-I _{CM}	collector current	peak value	-	7	A
P _{tot}	total power dissipation	T _{tab} = 25 °C	-	8	W
T _{stg}	storage temperature range		-65	+150	°C
T _j	junction temperature		-	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
R _{th j-t}	from junction to tab		15.5	K/W
R _{th j-a}	from junction to ambient	on PCB	83.3	K/W

PNP silicon epitaxial base power transistors**BDS950/952/954/956****CHARACTERISTICS**

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

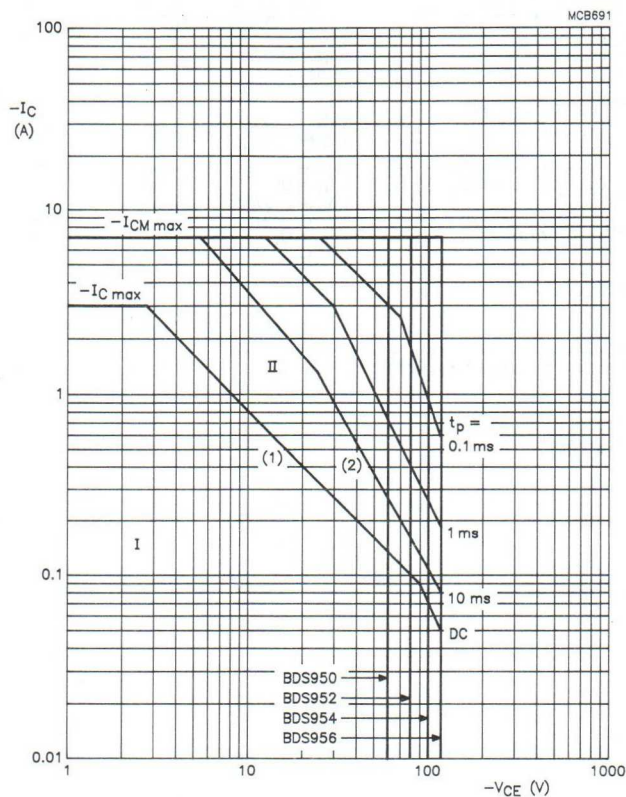
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $-V_{CB} = -V_{CBO\text{ max}}$	-	50	μA
$-I_{CBO}$	collector cut-off current	$I_E = 0$; $V_{CB} = 1/2 V_{CBO\text{ max}}$; $T_j = 150\text{ }^{\circ}\text{C}$	-	1	mA
$-I_{CEO}$	collector cut-off current	$I_B = 0$; $V_{CE} = 1/2 V_{CEO\text{ max}}$	-	0.1	mA
$-I_{EBO}$	emitter cut-off current	$I_C = 0$; $-V_{EB} = 5\text{ V}$	-	0.2	mA
$-V_{BE}$	base-emitter voltage	$-I_C = 2\text{ A}$; $-V_{CE} = 4\text{ V}$; note 1	-	1.4	V
$-V_{CE\text{ sat}}$	collector-emitter saturation voltage	$-I_C = 2\text{ A}$; $-I_B = 0.2\text{ A}$; note 1	-	1	V
h_{FE}	DC current gain	$-I_C = 500\text{ mA}$; $-V_{CE} = 4\text{ V}$; note 1	40	-	
h_{FE}	DC current gain	$-I_C = 2\text{ A}$; $-V_{CE} = 4\text{ V}$; note 1	20	-	
f_T	transition frequency	$f = 1\text{ MHz}$; $-I_C = 500\text{ mA}$; $-V_{CE} = 4\text{ V}$	3	-	MHz

Note

1. Measured under pulse conditions: $t_p < 300\text{ }\mu\text{s}$, duty cycle $< 2\%$.

PNP silicon epitaxial base power transistors

BDS950/952/954/956

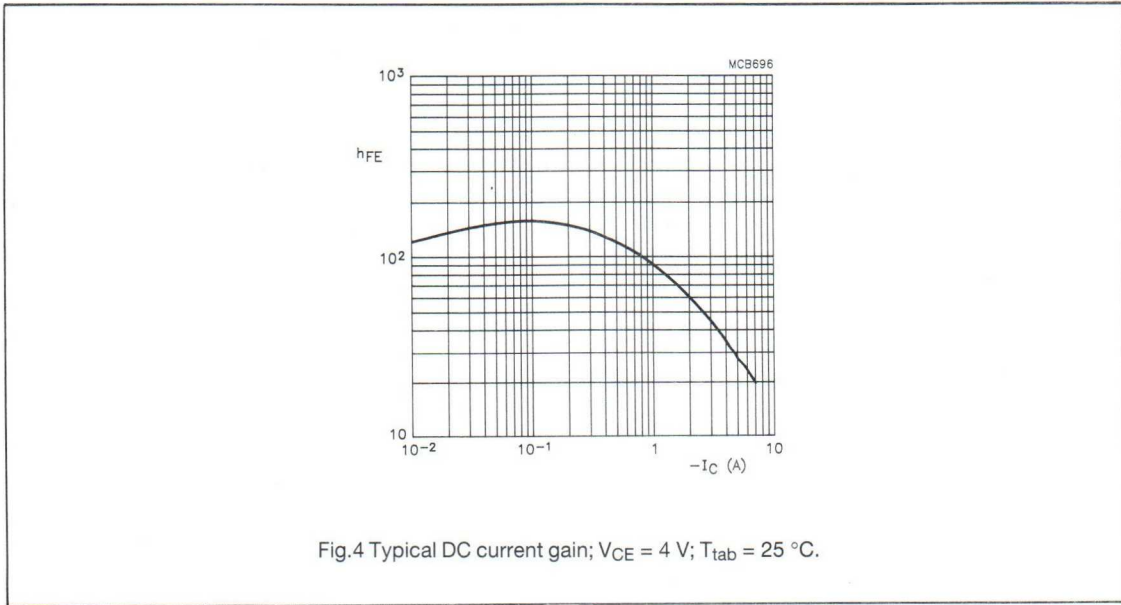
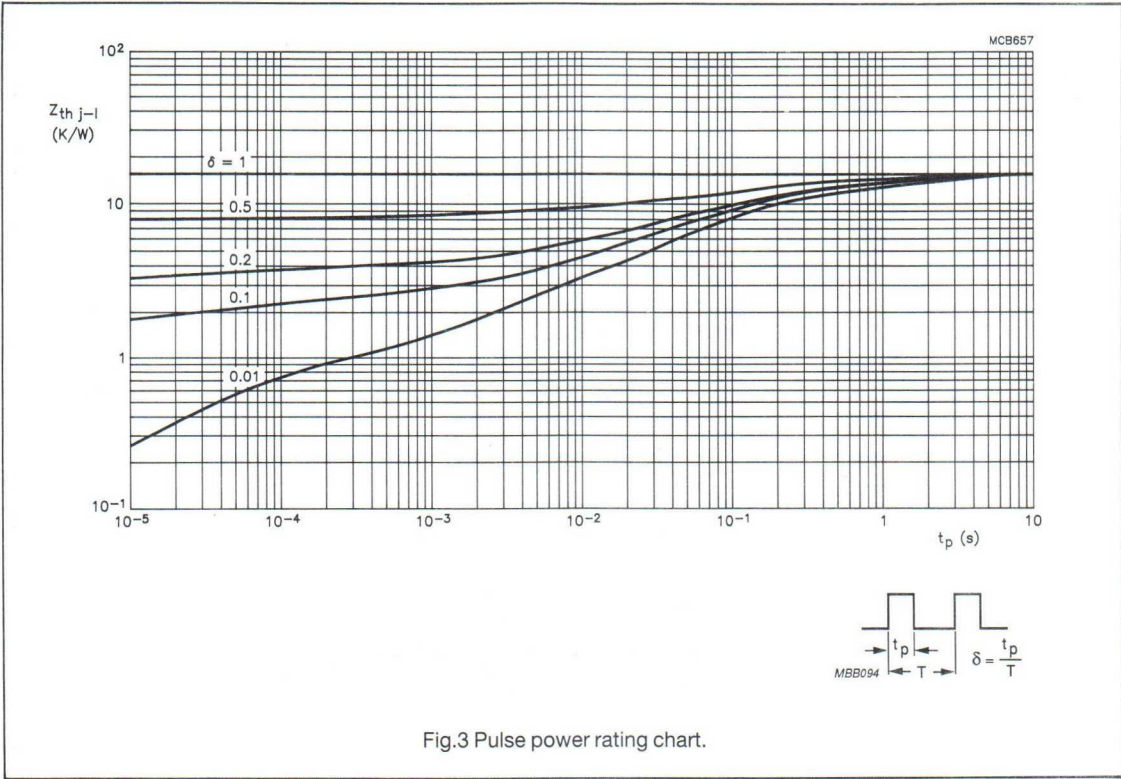


- I. Region of permissible DC operation.
- II. Permissible extension for repetitive pulse operation.
- (1) $P_{tot} \max$ and $P_{peak} \max$ lines.
- (2) Second breakdown limits.

Fig.2 Safe operating area; $T_{tab} = 25^\circ \text{C}$.

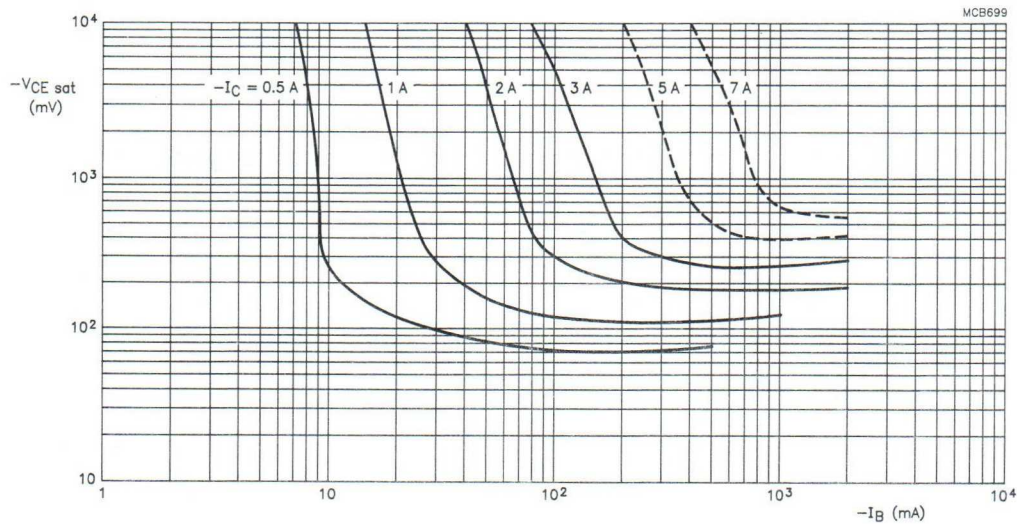
PNP silicon epitaxial base power transistors

BDS950/952/954/956



PNP silicon epitaxial base power transistors

BDS950/952/954/956

Fig.5 Typical values of collector-emitter saturation voltage at $T_{tab} = 25\text{ }^{\circ}\text{C}$.

N-CHANNEL SILICON FIELD-EFFECT TRANSISTORS

Asymmetrical N-channel planar epitaxial junction field-effect transistors in the miniature plastic envelope intended for applications up to the v.h.f. range in hybrid thick and thin-film circuits. Special features are the low feedback capacitance and the low noise figure. These features make the product very suitable for applications such as the r.f. stages in f.m. portables (BF510), car radios (BF511) and mains radios (BF512) or the mixer stage (BF513).

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V		
Drain current (DC or average)	I_D	max.	30	mA		
Total power dissipation up to $T_{amb} = 40\text{ }^{\circ}\text{C}$	P_{tot}	max.	250	mW		
			BF510	511	512	513
Drain current $V_{DS} = 10\text{ V}; V_{GS} = 0$	I_{DSS}	>	0.7	2.5	6	10 mA
		<	3.0	7.0	12	18 mA
Transfer admittance (common source) $V_{DS} = 10\text{ V}; V_{GS} = 0; f = 1\text{ kHz}$	$ y_{fs} $	>	2.5	4	6	7 mS
Feedback capacitance $V_{DS} = 10\text{ V}; V_{GS} = 0$	C_{rs}	typ.	0.3	0.3	—	— pF
$V_{DS} = 10\text{ V}; I_D = 5\text{ mA}$	C_{rs}	typ.	—	—	0.3	0.3 pF
Noise figure at optimum source admittance $G_S = 1\text{ mS}; -B_S = 3\text{ mS}; f = 100\text{ MHz}$	F	typ.	1.5	1.5	—	— dB
$V_{DS} = 10\text{ V}; I_D = 5\text{ mA}$		typ.	—	—	1.5	1.5 dB

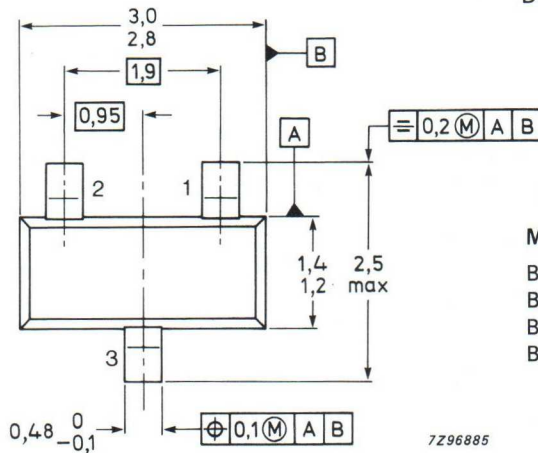
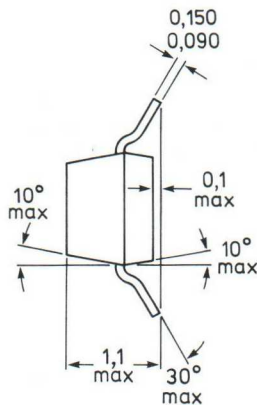
MECHANICAL DATA

SOT23.

See also *Soldering recommendations*.

MECHANICAL DATA

Fig. 1 SOT23.



TOP VIEW

Dimensions in mm

Pinning

1 = gate

2 = drain

3 = source

**Marking code**

BF510 = S6p

BF511 = S7p

BF512 = S8p

BF513 = S9p

7296885

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain-gate voltage (open source)	V_{DGO}	max.	20 V
Drain current (DC or average)	I_D	max.	30 mA
Gate current	$\pm I_G$	max.	10 mA
Total power dissipation up to $T_{amb} = 40^\circ\text{C}$ (note 1)	P_{tot}	max.	250 mW
Storage temperature range	T_{stg}	-65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient (note 1)

$$R_{th\ j-a} = 430\ \text{K/W}$$

Note

1. Mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$

			BF510	511	512	513
Gate cut-off current						
$-V_{GS} = 0.2\text{ V}; V_{DS} = 0$	$-I_{GSS}$	<	10	10	10	10 nA
Gate-drain breakdown voltage						
$I_S = 0; -I_D = 10\text{ }\mu\text{A}$	$-V_{(BR)GDO}$	>	20	20	20	20 V
Drain current						
$V_{DS} = 10\text{ V}; V_{GS} = 0$	I_{DSS}	>	0.7	2.5	6	10 mA
		<	3.0	7.0	12	18 mA
Gate-source cut-off voltage						
$I_D = 10\text{ }\mu\text{A}; V_{DS} = 10\text{ V}$	$-V_{(P)GS}$	typ.	0.8	1.5	2.2	3 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $V_{DS} = 10\text{ V}; V_{GS} = 0; T_{amb} = 25\text{ }^{\circ}\text{C}$ for BF510 and BF511 $V_{DS} = 10\text{ V}; I_D = 5\text{ mA}; T_{amb} = 25\text{ }^{\circ}\text{C}$ for BF512 and BF513

y-parameters (common source)			BF510	511	512	513
Input capacitance at $f = 1\text{ MHz}$	C_{is}	<	5	5	5	5 pF
Input conductance at $f = 100\text{ MHz}$	g_{is}	typ.	100	90	60	50 μS
Feedback capacitance at $f = 1\text{ MHz}$	C_{rs}	typ.	0.3	0.3	0.3	0.3 pF
		<	0.4	0.4	0.4	0.4 pF
Transfer admittance at $f = 1\text{ kHz}$	$ y_{fs} $	>	2.5	4.0	4.0	3.5 mS
$V_{GS} = 0$ instead of $I_D = 5\text{ mA}$	$ y_{fs} $	>	—	—	6.0	7.0 mS
Transfer admittance at $f = 100\text{ MHz}$	$ y_{fs} $	typ.	3.5	5.5	5.0	5.0 mS
Output capacitance at $f = 1\text{ MHz}$	C_{os}	<	3	3	3	3 pF
Output conductance at $f = 1\text{ MHz}$	g_{os}	<	60	80	100	120 μS
Output conductance at $f = 100\text{ MHz}$	g_{os}	typ.	35	55	70	90 μS
Noise figure at optimum source admittance						
$G_S = 1\text{ mS}; -B_S = 3\text{ mS};$						
$f = 100\text{ MHz}$	F	typ.	1.5	1.5	1.5	1.5 dB

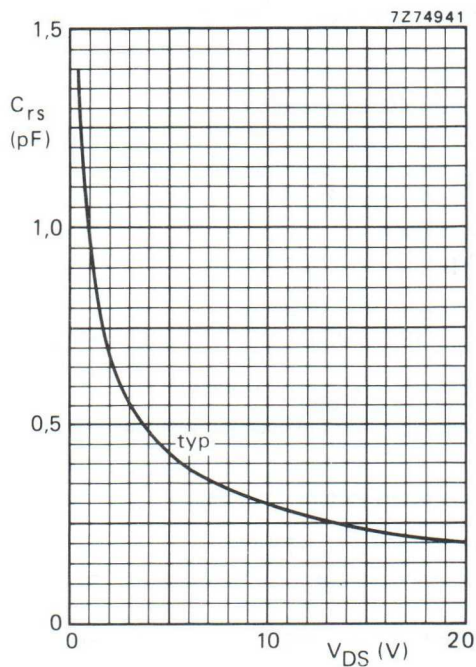


Fig. 2 $V_{GS} = 0$ for BF510 and BF511;
 $I_D = 5$ mA for BF512 and BF513;
 $f = 1$ MHz; $T_{amb} = 25$ °C.

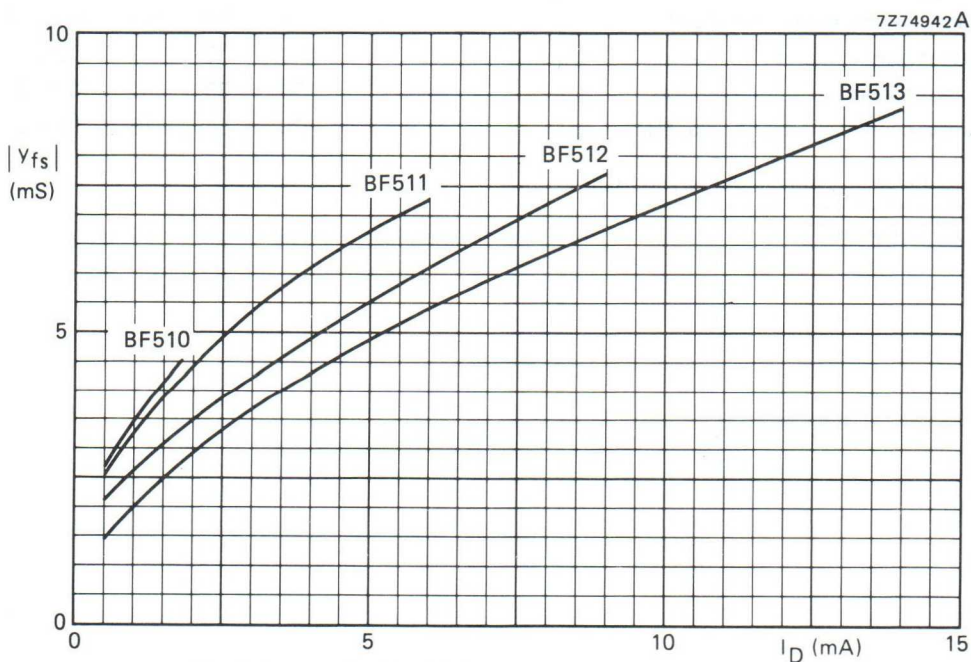


Fig. 3 $V_{DS} = 10$ V; $f = 1$ kHz; $T_{amb} = 25$ °C; typical values.

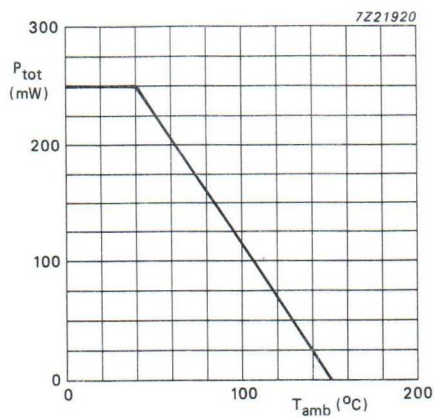


Fig.4 Power derating curve.



SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor, in a microminiature plastic envelope, intended for applications in thick and thin-film circuits. This transistor is primarily intended for use in i.f. detection applications.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40 V
Collector current (d.c.)	$-I_C$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	h_{FE}	>	50
Transition frequency at $f = 100\text{ MHz}$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	f_T	typ.	325 MHz
Noise figure at $R_S = 300\text{ }\Omega$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}; f = 100\text{ kHz}$	F	typ.	2 dB

MECHANICAL DATA

Dimensions in mm

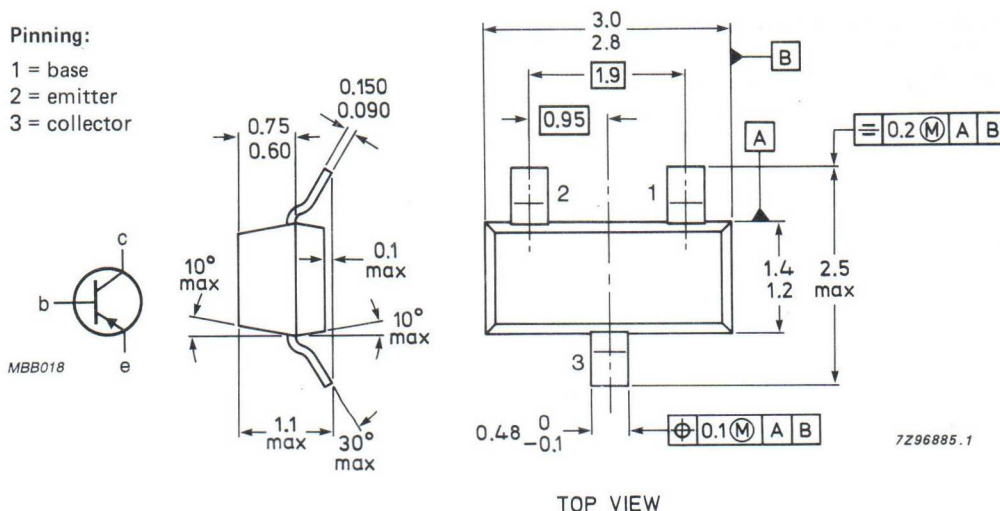
Marking code

Fig. 1 SOT-23

BF550 = LAP

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



See also *Soldering Recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4 V
Collector current (d.c.)	$-I_C$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current $I_E = 0; -V_{CB} = 30\text{ V}$	$-I_{CBO}$	<	50 nA
Emitter cut-off current $I_C = 0; -V_{EB} = 3\text{ V}$	$-I_{EBO}$	<	100 μA
Base-emitter voltage $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	$-V_{BE}$	typ.	750 mV
D.C. current gain $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	h_{FE}	>	50
Transition frequency at $f = 100\text{ MHz}$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	f_T	typ.	325 MHz
Feedback capacitance at $f = 1\text{ MHz}$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$	C_{re}	typ.	0,5 pF
Noise figure at $R_S = 300\text{ }\Omega$ $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}; f = 100\text{ kHz}$	F	typ.	2 dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a microminiature plastic envelope, intended for applications in thick and thin-film circuits such as self-oscillating mixer in u.h.f. tuners in conjunction with bipolar transistors or with MOS fets.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	35 V
Collector current (d.c.)	$-I_C$	max.	30 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transition frequency at $f = 100\text{ MHz}$ $I_F = 3\text{ mA}; -V_{CB} = 10\text{ V}$	f_T	typ.	900 MHz

MECHANICAL DATA

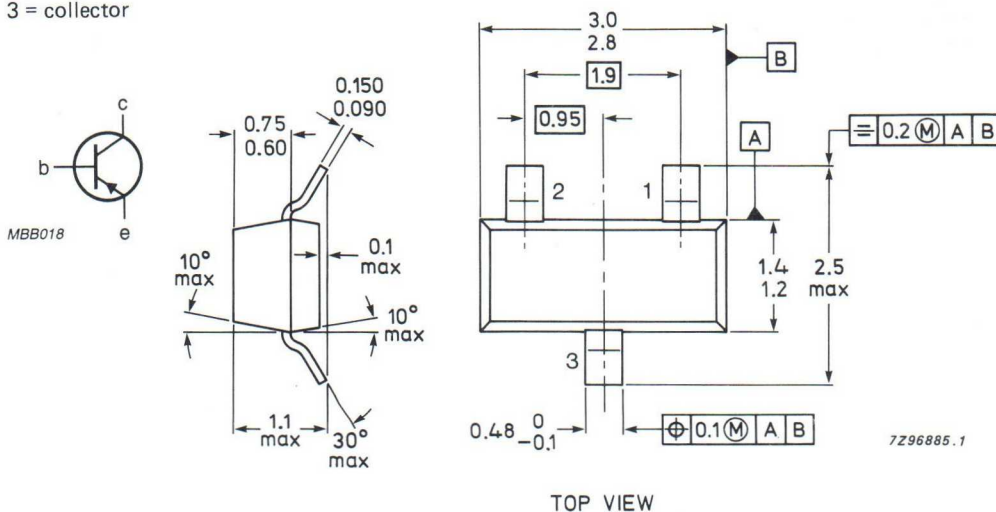
Dimensions in mm

Fig. 1 SOT-23

Pinning:

1 = base
2 = emitter
3 = collector

Marking code

$$\text{BF569} = \text{LH}_p$$


See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	35 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3 V
Collector current (d.c.)	$-I_C$	max.	30 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Collector cut-off current

$I_E = 0; -V_{CB} = 20\text{ V}$	$-I_{CBO}$	<	100 nA
----------------------------------	------------	---	--------

D.C. current gain

$I_E = 3\text{ mA}; -V_{CB} = 10\text{ V}$	h_{FE}	> typ.	25 50
--	----------	-----------	----------

Transition frequency at $f = 100\text{ MHz}$

$I_E = 3\text{ mA}; -V_{CB} = 10\text{ V}$	f_T	typ.	900 MHz
--	-------	------	---------

Feedback capacitance at $f = 1\text{ MHz}$

$I_E = 1\text{ mA}; -V_{CB} = 10\text{ V}$	C_{re}	typ.	0,33 pF
--	----------	------	---------

Noise figure at $f = 800\text{ MHz}$

$I_E = 3\text{ mA}; -V_{CB} = 10\text{ V}; R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega$	F	typ.	4,5 dB
---	-----	------	--------

Power gain at $f = 800\text{ MHz}$

$I_E = 3\text{ mA}; -V_{CB} = 10\text{ V}; R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega$	G_{pb}	typ.	14,5 dB
---	----------	------	---------

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor in a plastic SOT-23 variant envelope, intended for use in large-signal handling i.f. pre-amplifiers of TV receivers in combination with surface acoustic wave filters.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	40 V
Collector-emitter voltage (open base)	V_{CEO}	max.	15 V
Collector current (d.c.)	I_C	max.	100 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
D.C. current gain $I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$	h_{FE}	>	40
Transition frequency at $f = 100\text{ MHz}$ $I_C = 40\text{ mA}; V_{CE} = 10\text{ V}$	f_T	>	490 MHz
Voltage gain at $f = 36\text{ MHz}$ (see Fig. 4) $I_C = 20\text{ mA}; V_{CE} \approx 10,4\text{ V}$	G_v	typ.	24 dB
Interference voltage for $K = 1\%$ (see Fig. 3)	$V_{(int)rms}$	typ.	120 mV

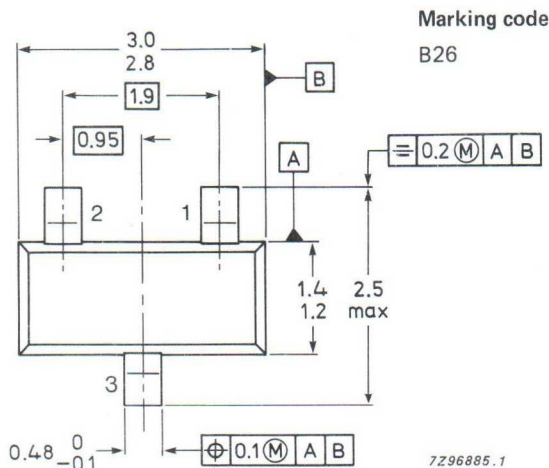
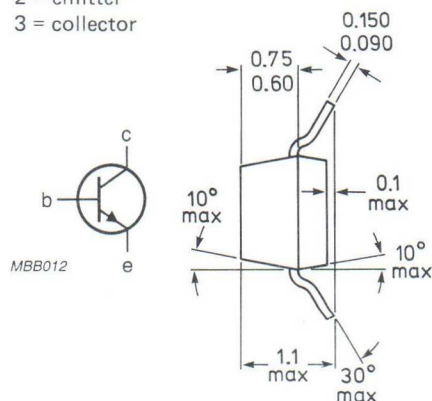
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	40 V
Collector-emitter voltage (open base)	V_{CEO}	max.	15 V
Emitter-base voltage (open collector)	V_{EBO}	max.	4,5 V
Collector current (d.c.)	I_C	max.	100 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		$-65\text{ to }+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to tab	$R_{th\ j-t}$	=	500 K/W
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CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

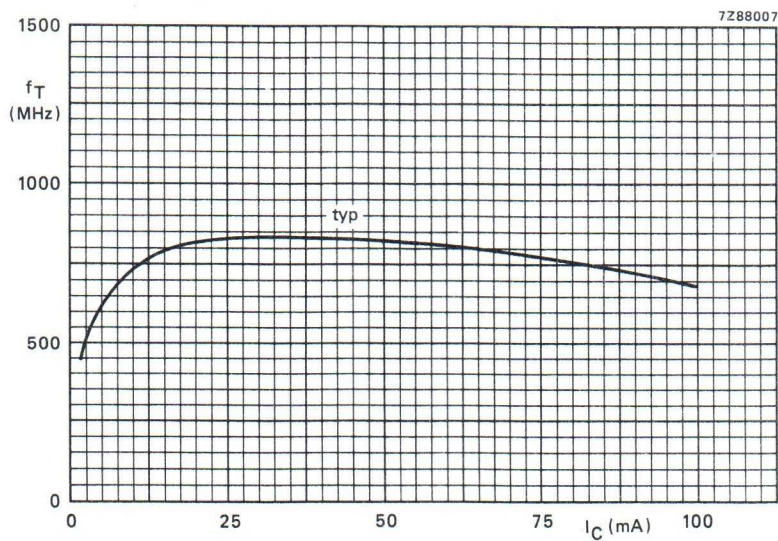
 $I_E = 0; V_{CB} = 20\text{ V}$ $I_{CBO} < 400\text{ nA}$ $I_E = 0; V_{CB} = 20\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$ $I_{CBO} < 30\text{ }\mu\text{A}$

Emitter cut-off current

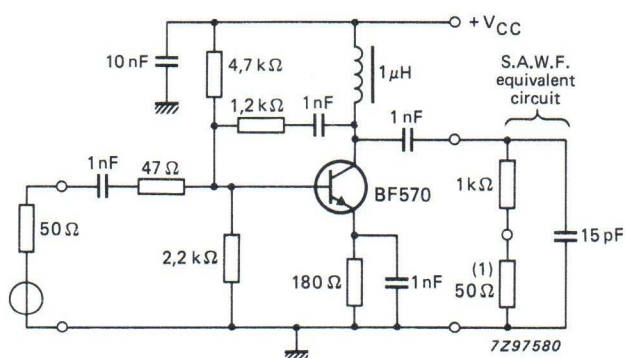
 $I_C = 0; V_{EB} = 2\text{ V}$ $I_{EBO} < 100\text{ nA}$

D.C. current gain

 $I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$ $h_{FE} > 40$ Transition frequency at $f = 100\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$ $f_T > 500\text{ MHz}$ $I_C = 40\text{ mA}; V_{CE} = 10\text{ V}$ $f_T > 490\text{ MHz}$ Collector capacitance at $f = 1\text{ MHz}$ $I_E = I_C = 0; V_{CB} = 10\text{ V}$ C_c typ. 2,2 pF
< 3,5 pFEmitter capacitance at $f = 1\text{ MHz}$ $I_C = I_E = 0; V_{EB} = 1\text{ V}$ $C_e < 4,5\text{ pF}$ Feedback capacitance at $f = 1\text{ MHz}$ $I_C = 0; V_{CE} = 10\text{ V}$ C_{re} typ. 1,6 pF
< 2,2 pF

Fig. 2 $V_{CE} = 10$ V; $T_j = 25$ °C.

APPLICATION INFORMATION



(1) Test instrument load.

Fig. 3 Large-signal handling i.f. preamplifier for surface acoustic wave filter.

Performance

Supply voltage

 $V_{CC} = 12 \text{ V}$

Collector current

 $I_C = 20 \text{ mA}$

Measuring frequency

 $f_i = 36 \text{ MHz}$

Input impedance

 $Z_i \text{ typ. } 50 \Omega // 1 \text{ pF}$

Output impedance

 $Z_o < 100 \Omega$

Voltage gain

$$G_V \text{ (in dB)} = 20 \log \frac{V_o}{V_i}$$

 $G_V \text{ typ. } 24 \text{ dB}$ Interference voltage for $K = 1\%^*$ $V_{(int)rms} \text{ typ. } 120 \text{ mV}$

* Input terminal voltage at 50Ω internal resistance of signal generator, interference frequency 40 MHz, 80% modulated with 1 kHz.

SILICON PLANAR TRANSISTOR

P-N-P transistor in a microminiature envelope primarily intended for u.h.f. applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	20 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20 V
Collector current	$-I_C$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transition frequency at $f = 100\text{ MHz}$ $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}$	f_T	typ.	1350 MHz
Transducer gain (common base) $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}; f = 800\text{ MHz}$ $R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega; T_{amb} = 25\text{ }^{\circ}\text{C}$	G_{tr}	typ.	16 dB
Noise figure (common base) $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}; f = 800\text{ MHz}$ $R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega$	F	typ.	4,5 dB

MECHANICAL DATA

Dimensions in mm

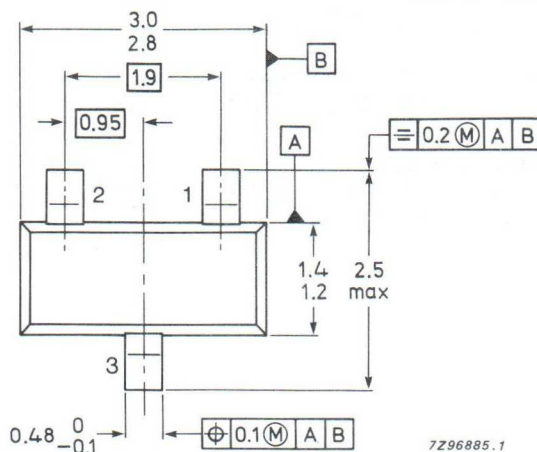
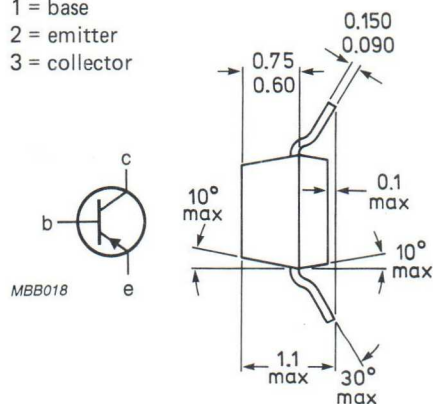
Marking code

Fig. 1 SOT-23.

BF579 = LJp

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	$-V_{CBO}$	max.	20 V
Collector-emitter voltage (open base) see Fig. 2	$-V_{CEO}$	max.	20 V
Emitter-base voltage (open collector) see Fig. 2	$-V_{EBO}$	max.	3 V
Collector current	$-I_C$	max.	25 mA
Base current (d.c.)	$-I_B$	max.	10 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$

Collector cut-off current

 $I_E = 0; -V_{CB} = 15\text{ V}$

$$-I_{CBO} < 100\text{ nA}$$

Emitter cut-off current

 $I_C = 0; -V_{EB} = 1\text{ V}$

$$-I_{EBO} < 100\text{ nA}$$

D.C. current gain

 $I_C = 10\text{ mA}; -V_{CE} = 10\text{ V}$

$$h_{FE} > 20$$

Transition frequency at $f = 100\text{ MHz}$ $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}$

$$f_T \text{ typ. } 1350\text{ MHz}$$

Feedback capacitance at $f = 500\text{ kHz}$ $I_E = 7\text{ mA}; -V_{CB} = 10\text{ V}$

$$C_{re} \text{ typ. } 0,46\text{ pF}$$

 $I_E = 0; -V_{CB} = 10\text{ V}$

$$C_{rb} \text{ typ. } 160\text{ fF}$$

Transducer gain (common base)

 $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}; f = 800\text{ MHz}$ $R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega$

$$G_{tr} \text{ typ. } 16\text{ dB}$$

Noise figure (common base)

 $I_E = 10\text{ mA}; -V_{CB} = 10\text{ V}; f = 800\text{ MHz}$ $R_S = 60\text{ }\Omega; R_L = 500\text{ }\Omega$

$$F \text{ typ. } 4,5\text{ dB}$$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

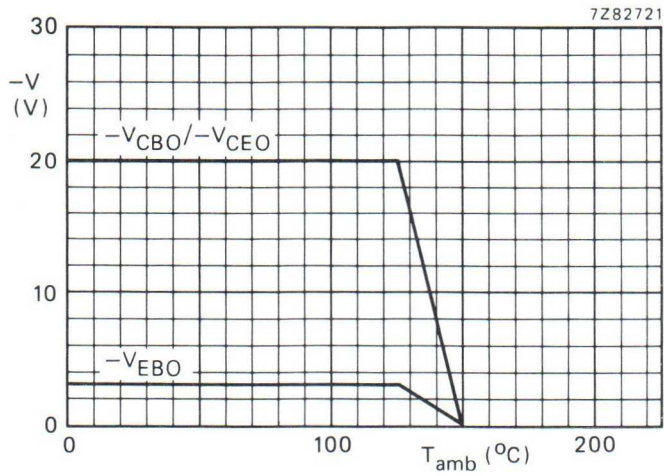


Fig. 2 Voltage derating curves.

SILICON EPITAXIAL TRANSISTORS

● For video output stages

N-P-N transistors in a microminiature plastic envelope intended for class-B video output stages in colour television receivers.

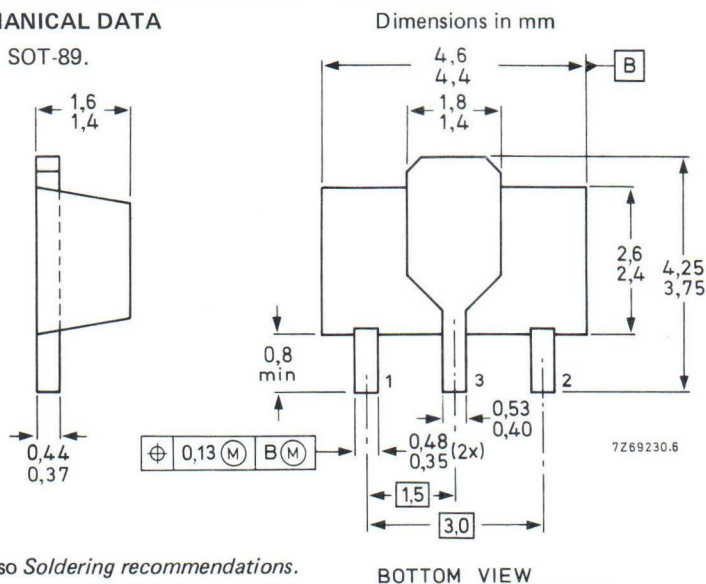
P-N-P complements are BF621 and BF623 respectively.

QUICK REFERENCE DATA

		BF620	BF622
Collector-base voltage (open emitter)	V_{CBO} max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO} max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER} max.	300	— V
Collector current (peak value)	I_{CM} max.	100	mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot} max.	1	W
Junction temperature	T_j max.	150	$^\circ\text{C}$
D.C. current gain $I_C = 25 \text{ mA}; V_{CE} = 20 \text{ V}$	$h_{FE} >$	50	
Transition frequency at $f = 35 \text{ MHz}$ $I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$	$f_T >$	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$ $I_C = 0; V_{CE} = 30 \text{ V}$	$C_{re} <$	1,6	pF

MECHANICAL DATA

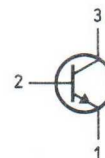
Fig. 1 SOT-89.



Marking code

BF620 = DC

BF622 = DA



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF620	BF622
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO}	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER}	max.	300	— V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	50	mA
Collector current (peak value)	I_{CM}	max.	100	mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$ mounted on a ceramic substrate area = $2,5 \text{ cm}^2$; thickness = $0,7 \text{ mm}$	P_{tot}	max.	1	W
Storage temperature	T_{stg}		-65 to + 150	$^\circ\text{C}$
Junction temperature	T_j	max.	150	$^\circ\text{C}$

THERMAL RESISTANCE*

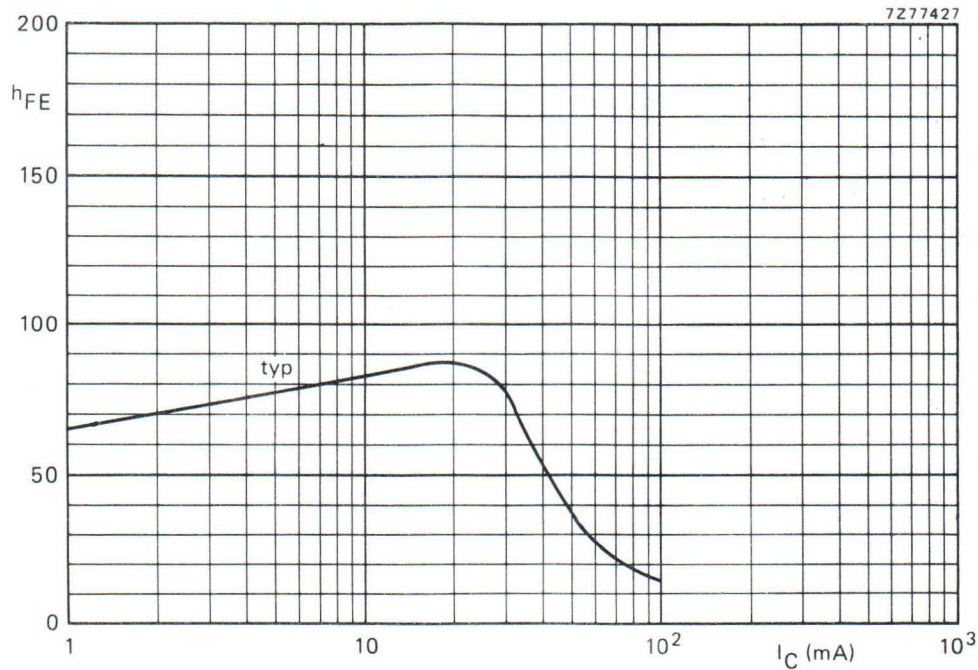
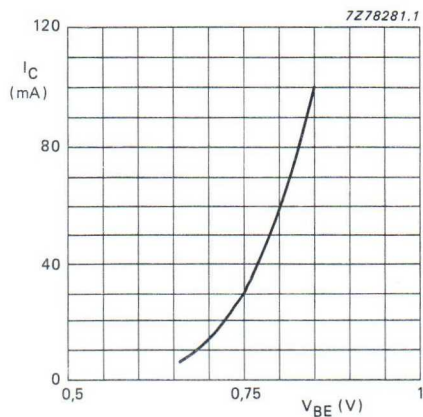
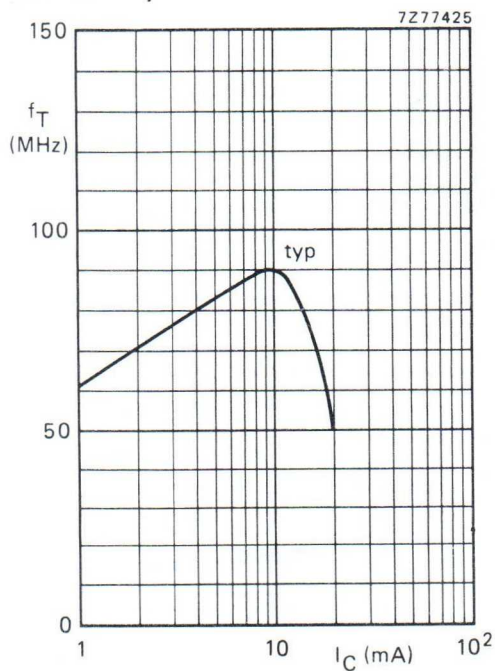
From junction to collector tab	$R_{thj-tab}$	=	25	K/W
From junction to ambient in free air mounted on a ceramic substrate area = $2,5 \text{ cm}^2$; thickness = $0,7 \text{ mm}$	R_{thj-a}	=	125	K/W

CHARACTERISTICS

$T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

			BF620	BF622
Collector cut-off current $I_E = 0$; $V_{CB} = 200 \text{ V}$	I_{CBO}	<	10	10 nA
Collector-emitter voltage $R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 250 \text{ V}$	I_{CER}	<	50	— nA
$R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 200 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$	I_{CER}	<	10	10 μA
Saturation voltage $I_C = 30 \text{ mA}$; $I_B = 5 \text{ mA}$	$V_{CE sat}$	<	0,6	V
D.C. current gain $I_C = 25 \text{ mA}$; $V_{CE} = 20 \text{ V}$	h_{FE}	>	50	
Transition frequency at $f = 35 \text{ MHz}$ $I_C = 10 \text{ mA}$; $V_{CE} = 10 \text{ V}$	f_T	>	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$ $I_C = 0$; $V_{CE} = 30 \text{ V}$	C_{re}	<	1,6	pF

* See Thermal characteristics.

Fig. 2 Typical values at $V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 3 $V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 4 $V_{CE} = 10$ V; $T_j = 25$ °C; $f = 35$ MHz.

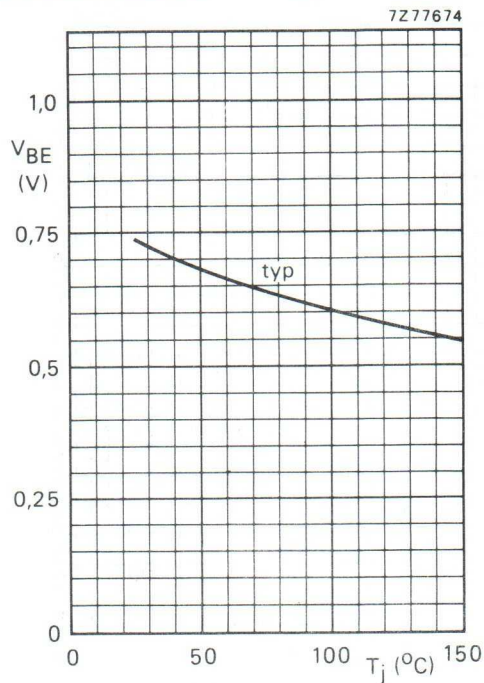


Fig. 5 $I_C = 25$ mA; $V_{CE} = 20$ V.

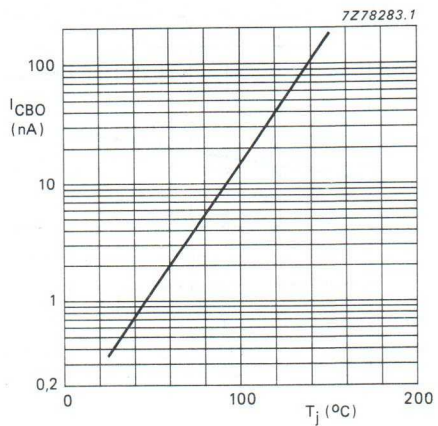


Fig. 6 $V_{CB} = 200$ V; typical values.

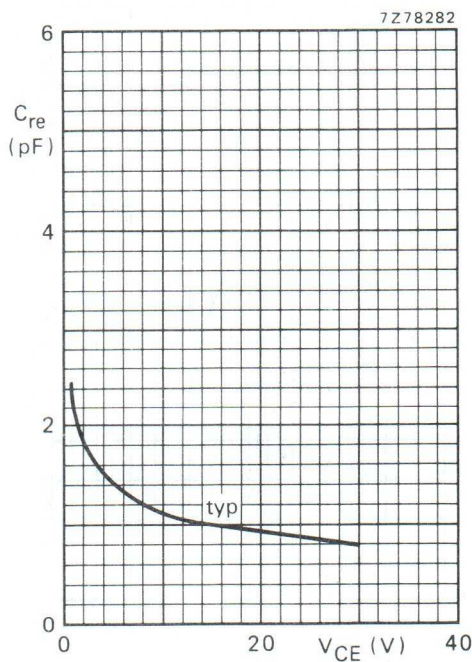


Fig. 7 $I_C = 0$; $f = 1$ MHz; $T_j = 25$ °C.

SILICON EPITAXIAL TRANSISTORS

● For video output stages

P-N-P transistors in a microminiature plastic envelope intended for application in class-B video output stages in colour television receivers.

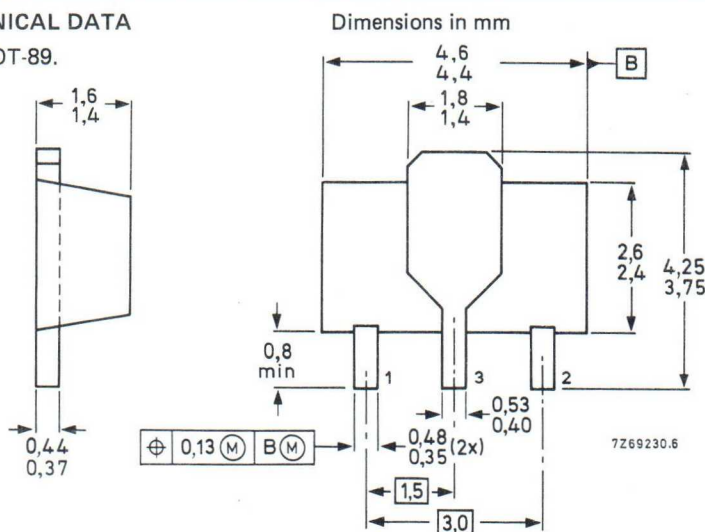
N-P-N complements are BF620 and BF622 respectively.

QUICK REFERENCE DATA

			BF621	BF623
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$	max.	300	— V
Collector current (peak value)	$-I_{CM}$	max.	100	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	$^\circ\text{C}$
D.C. current gain				
$-I_C = 25 \text{ mA}; -V_{CE} = 20 \text{ V}$	h_{FE}	>	50	
Transition frequency at $f = 35 \text{ MHz}$				
$-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$	f_T	>	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$				
$I_C = 0; -V_{CE} = 30 \text{ V}$	C_{re}	<	1,6	pF

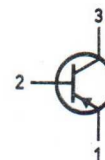
MECHANICAL DATA

Fig. 1 SOT-89.



Marking code

BF621 = DF
BF623 = DB



See also *Soldering recommendations*.

BOTTOM VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF621	BF623
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$	max.	300	— V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	50	mA
Collector current (peak value)	$-I_{CM}$	max.	100	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$ mounted on a ceramic substrate area = $2,5 \text{ cm}^2$; thickness = $0,7 \text{ mm}$	P_{tot}	max.	1	W
Storage temperature	T_{stg}		-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.	150	$^\circ\text{C}$

THERMAL RESISTANCE *

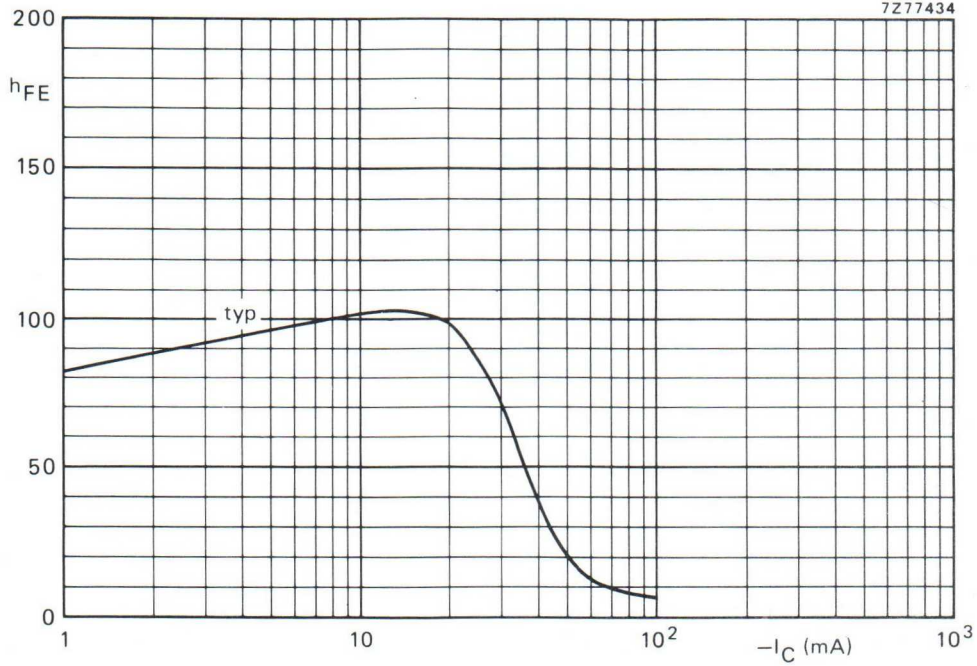
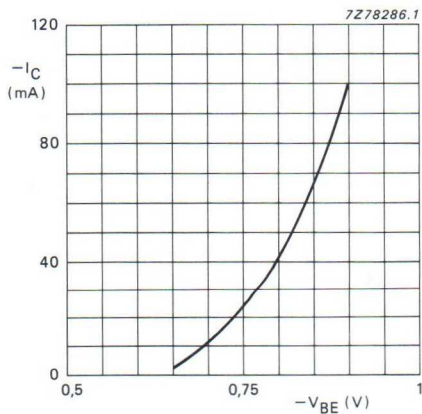
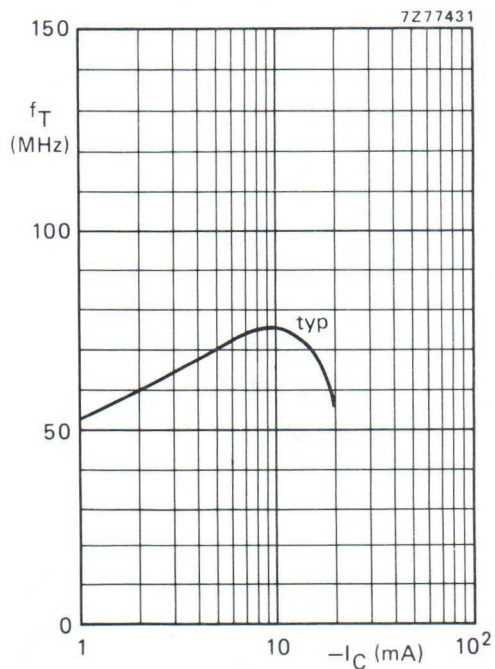
From junction to collector tab	$R_{th \text{ j-tab}}$	=	25	K/W
From junction to ambient in free air mounted on a ceramic substrate area = $2,5 \text{ cm}^2$; thickness = $0,7 \text{ mm}$	$R_{th \text{ j-a}}$	=	125	K/W

CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

			BF621	BF623
Collector cut-off current $I_E = 0$; $-V_{CB} = 200 \text{ V}$	$-I_{CBO}$	<	10	10 nA
Collector-emitter voltage $R_{BE} = 2,7 \text{ k}\Omega$; $-V_{CE} = 250 \text{ V}$	$-I_{CER}$	<	50	— nA
$R_{BE} = 2,7 \text{ k}\Omega$; $-V_{CE} = 200 \text{ V}$; $T_j = 150^\circ\text{C}$	$-I_{CER}$	<	10	10 μA
Saturation voltage $-I_C = 30 \text{ mA}$; $-I_B = 5 \text{ mA}$	$-V_{CEsat}$	<	0,8	V
D.C. current gain $-I_C = 25 \text{ mA}$; $-V_{CE} = 20 \text{ V}$	h_{FE}	>	50	
Transition frequency at $f = 35 \text{ MHz}$ $-I_C = 10 \text{ mA}$; $-V_{CE} = 10 \text{ V}$	f_T	>	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$ $I_C = 0$; $-V_{CE} = 30 \text{ V}$	C_{re}	<	1,6	pF

* See *Thermal characteristics*.

Fig. 2 Typical values at $-V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 3 $-V_{CE} = 20$ V; $T_j = 25$ °C; typical values.Fig. 4 $-V_{CE} = 10$ V; $T_j = 25$ °C; $f = 35$ MHz.

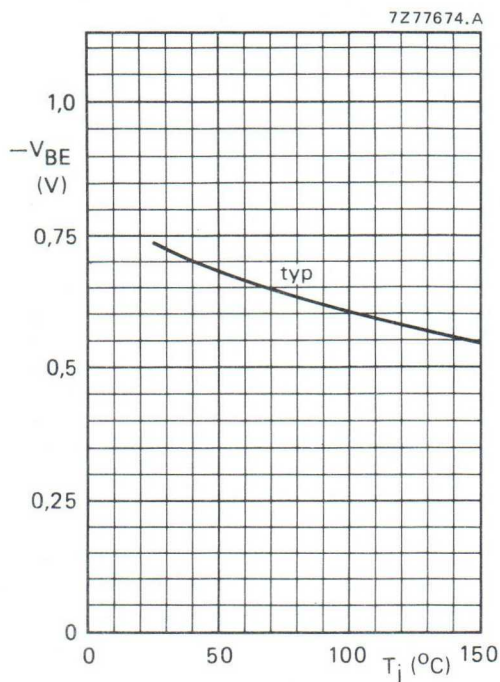


Fig. 5 $-I_C = 25$ mA; $-V_{CE} = 20$ V.

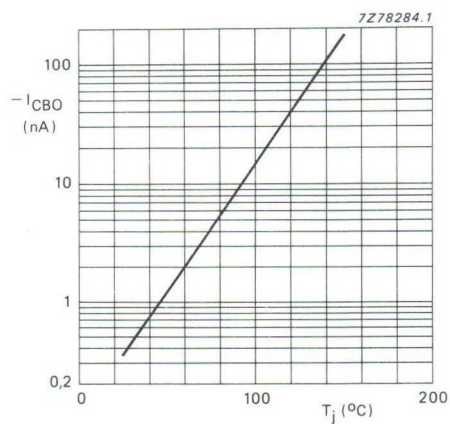


Fig. 6 $-V_{CB} = 200$ V; typical values.

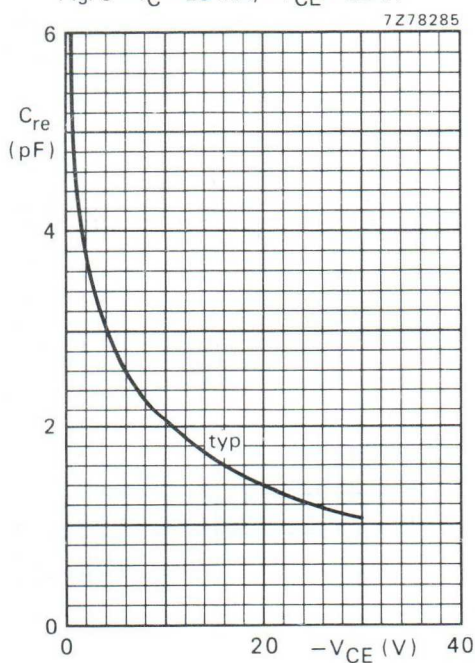


Fig. 7 $I_C = 0$; $f = 1$ MHz; $T_j = 25$ °C.

SILICON PLANAR TRANSISTOR

P-N-P transistor, in a microminiature plastic envelope; intended for use as oscillator in v.h.f. tuners with extended frequency range and/or in conjunction with MOS-FETs in thick and thin-film circuits.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Collector current (peak value)	$-I_{CM}$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transition frequency at $f = 100\text{ MHz}$ $I_E = 5\text{ mA}; -V_{CB} = 10\text{ V}$	f_T	typ.	650 MHz

MECHANICAL DATA

Dimensions in mm

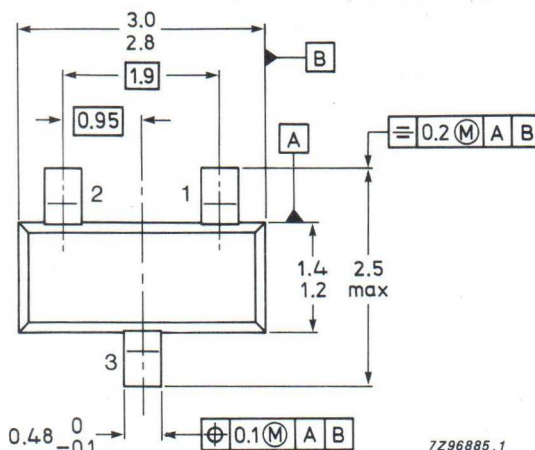
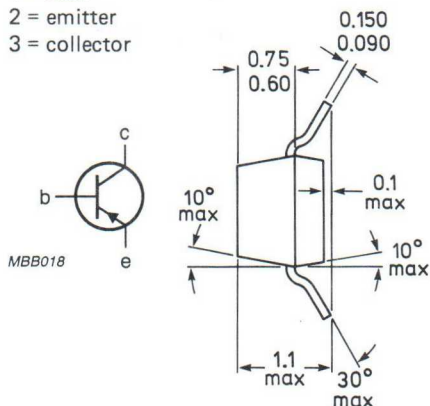
Marking code

Fig. 1 SOT-23.

BF660 = LEp

Pinning:

- 1 = base
2 = emitter
3 = collector



TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4 V
Collector current (peak value)	$-I_{CM}$	max.	25 mA
Base current (d.c.)	$-I_B$	max.	10 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$

Collector cut-off current

 $I_E = 0; -V_{CB} = 20\text{ V}$

$-I_{CBO}$	<	50 nA
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D.C. current gain

 $I_E = 3\text{ mA}; -V_{CE} = 10\text{ V}$

h_{FE}	>	30
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Transition frequency at $f = 100\text{ MHz}$ $I_E = 5\text{ mA}; -V_{CB} = 10\text{ V}$

f_T	typ.	650 MHz
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Feedback capacitance at $f = 1\text{ MHz}$ $I_E = 1\text{ mA}; -V_{CB} = 10\text{ V}$

C_{re}	typ.	0,65 pF
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* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON EPITAXIAL TRANSISTORS

NPN transistors in a microminiature plastic envelope intended for class-B video output stages in colour television receivers, and general purpose high voltage circuits.

PNP complements are BF721 and BF723 respectively.

QUICK REFERENCE DATA

		BF720	BF722
Collector-base voltage (open emitter)	V_{CBO} max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO} max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER} max.	300	— V
Collector current (peak value)	I_{CM} max.	100	mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot} max.	1,5	W
Junction temperature	T_j max.	150	$^\circ\text{C}$
DC current gain	h_{FE}	50	
$I_C = 25 \text{ mA}; V_{CE} = 20 \text{ V}$			
Transition frequency at $f = 35 \text{ MHz}$	f_T	60	
$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$		MHz	
Feedback capacitance at $f = 1 \text{ MHz}$	C_{re}	1,6	
$I_C = 0; V_{CE} = 30 \text{ V}$		pF	

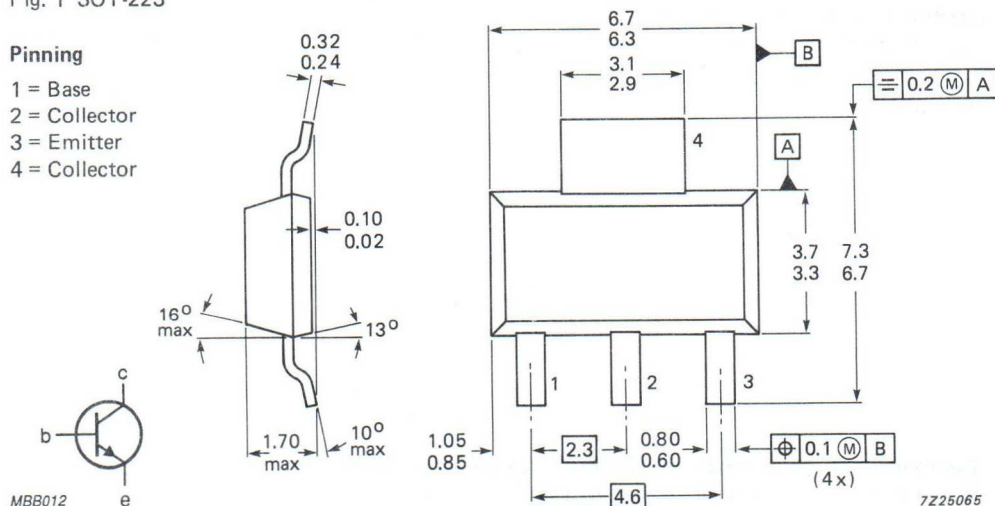
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter
- 4 = Collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF720	BF722
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO}	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER}	max.	300	— V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (DC)	I_C	max.	50	mA
Collector current (peak value)	I_{CM}	max.	100	mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$ *	P_{tot}	max.	1,5	W
Storage temperature range	T_{stg}		—65 to + 150	$^\circ\text{C}$
Junction temperature	T_j	max.	150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$R_{th \text{ j-a}}$	=	83,3	K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0$; $V_{CB} = 200 \text{ V}$

			BF720	BF722
I_{CBO}	<	10	10	nA
I_{CER}	<	50	—	nA
I_{CER}	<	10	10	μA

Collector-emitter voltage

$R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 250 \text{ V}$

$R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 200 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$

Saturation voltage

$I_C = 30 \text{ mA}$; $I_B = 5 \text{ mA}$

$V_{CE \text{ sat}}$	<	0,6	V
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DC current gain

$I_C = 25 \text{ mA}$; $V_{CE} = 20 \text{ V}$

h_{FE}	>	50	
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Transition frequency at $f = 35 \text{ MHz}$

$I_C = 10 \text{ mA}$; $V_{CE} = 10 \text{ V}$

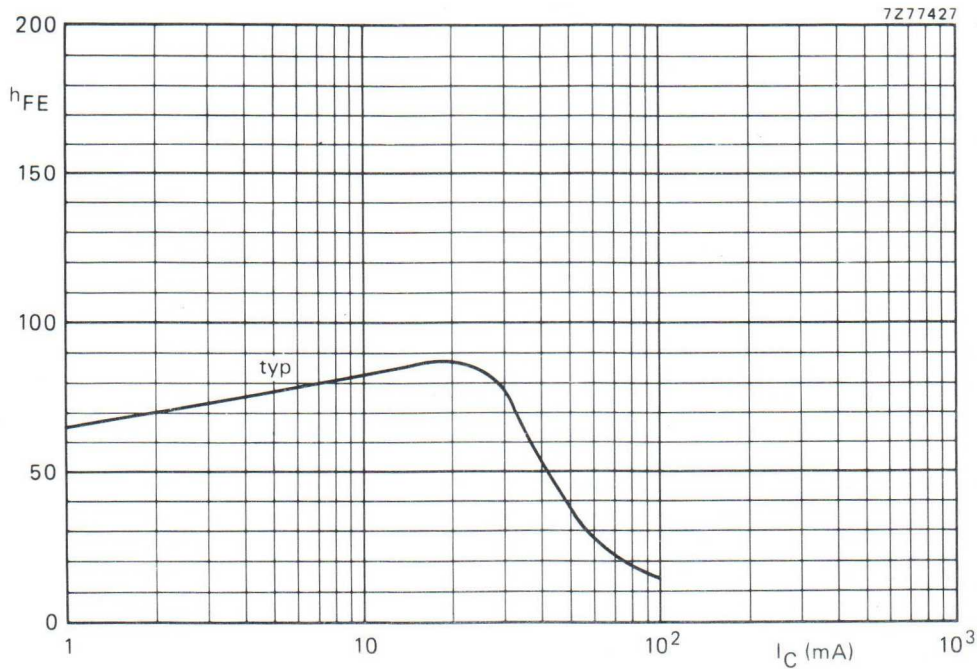
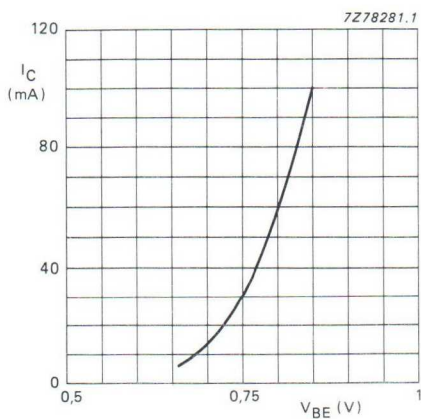
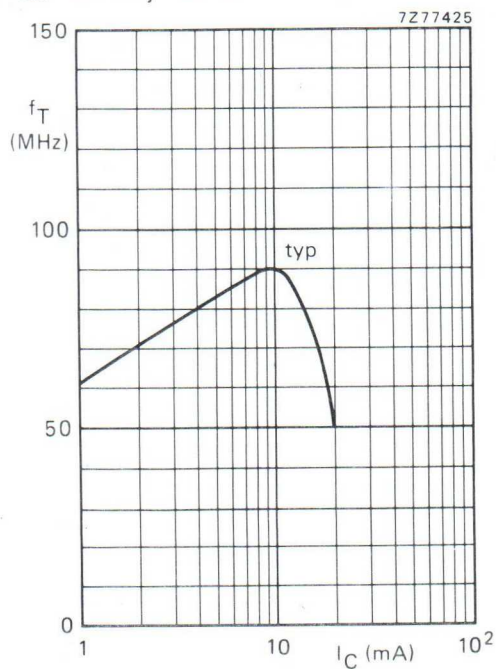
f_T	>	60	MHz
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Feedback capacitance at $f = 1 \text{ MHz}$

$I_C = 0$; $V_{CE} = 30 \text{ V}$

C_{re}	<	1,6	pF
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* Device mounted on an epoxy printed circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

Fig. 2 Typical values at $V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 3 $V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 4 $V_{CE} = 10$ V; $T_j = 25$ °C; $f = 35$ MHz.

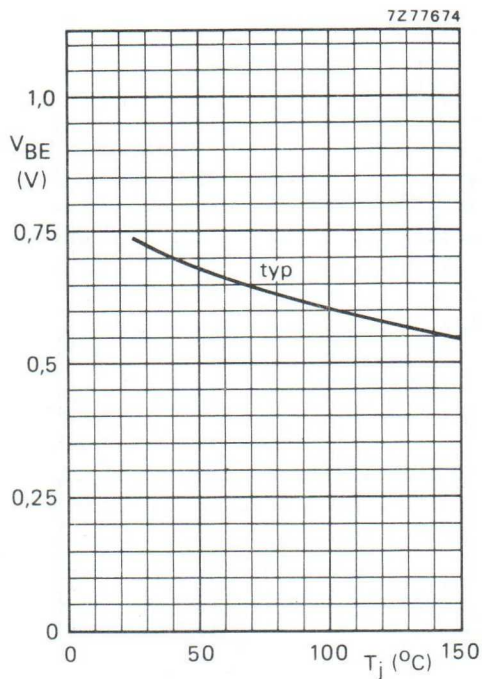


Fig. 5 $I_C = 25$ mA; $V_{CE} = 20$ V.

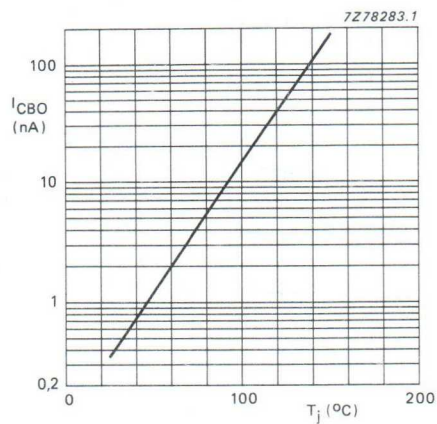


Fig. 6 $V_{CB} = 200$ V; typical values.

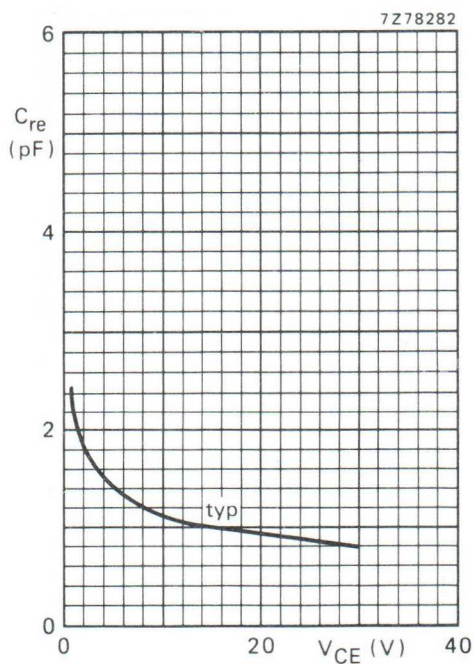


Fig. 7 $I_C = 0$; $f = 1$ MHz; $T_j = 25$ °C.

SILICON EPITAXIAL TRANSISTORS

PNP transistors in a microminiature plastic envelope intended for application in class-B video output stages in colour television receivers, and general purpose high voltage circuits.

NPN complements are BF720 and BF722 respectively.

QUICK REFERENCE DATA

			BF721	BF723
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$	max.	300	— V
Collector current (peak value)	$-I_{CM}$	max.	100	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	1,5	W
Junction temperature	T_j	max.	150	$^\circ\text{C}$
DC current gain				
$-I_C = 25 \text{ mA}; -V_{CE} = 20 \text{ V}$	h_{FE}	>	50	
Transition frequency at $f = 35 \text{ MHz}$				
$-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$	f_T	>	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$				
$I_C = 0; -V_{CE} = 30 \text{ V}$	C_{re}	<	1,6	pF

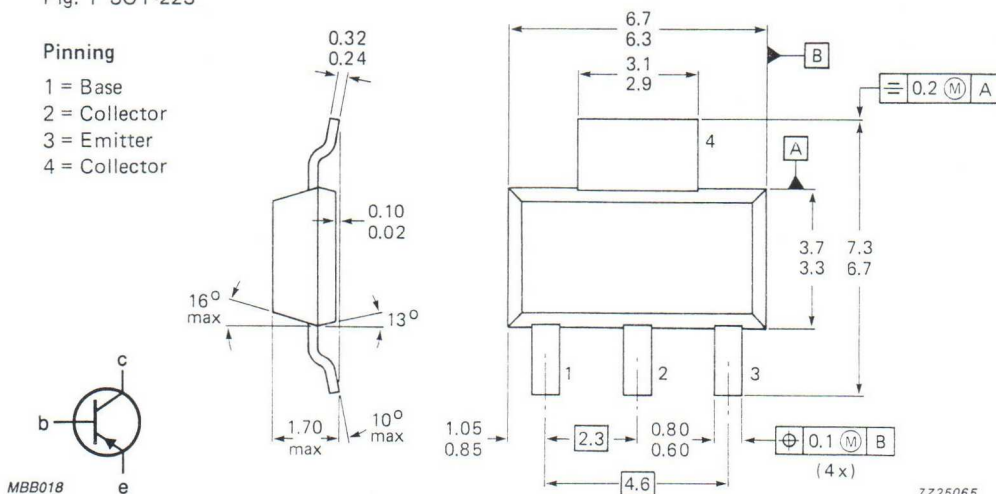
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-223

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter
- 4 = Collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF721	BF723
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$	max.	300	— V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	—	5 V
Collector current (DC)	$-I_C$	max.	—	50 mA
Collector current (peak value)	$-I_{CM}$	max.	—	100 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	—	1,5 W
Storage temperature range	T_{stg}		—65 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.	—	150 $^\circ\text{C}$

THERMAL RESISTANCE

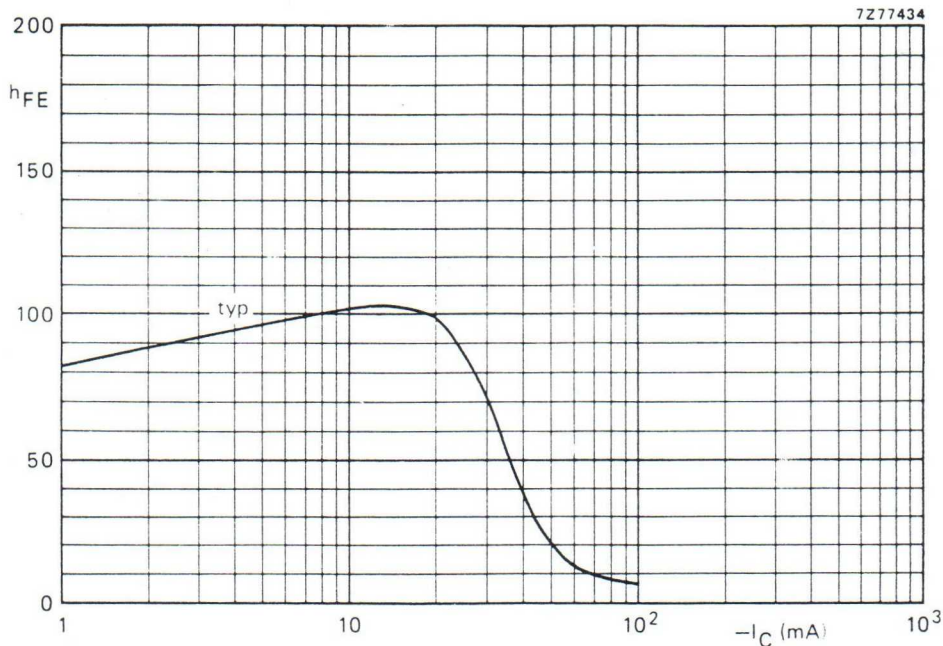
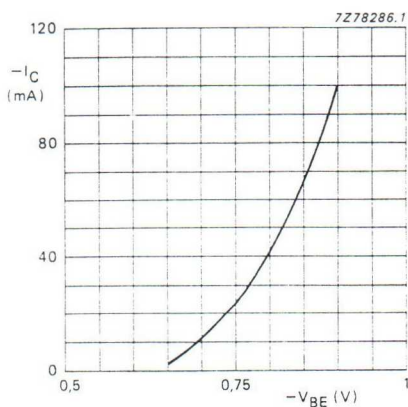
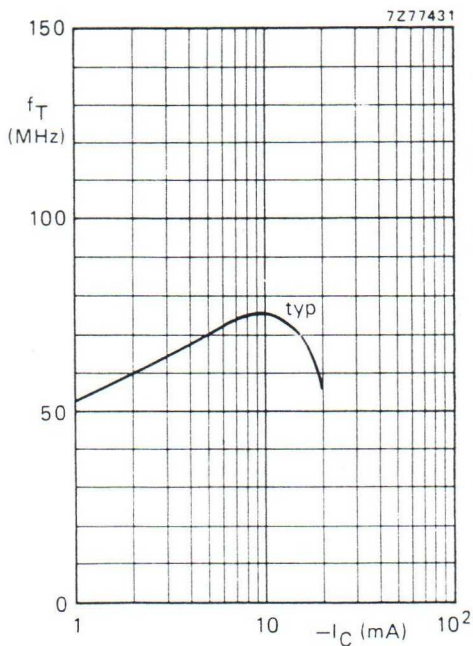
From junction to ambient*	$R_{th \text{ j-a}}$	=	83,3	K/W
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CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

			BF721	BF723
Collector cut-off current $I_E = 0; -V_{CB} = 200 \text{ V}$	$-I_{CBO}$	<	10	10 nA
Collector-emitter voltage $R_{BE} = 2,7 \text{ k}\Omega; -V_{CE} = 250 \text{ V}$ $R_{BE} = 2,7 \text{ k}\Omega; -V_{CE} = 200 \text{ V}; T_j = 150^\circ\text{C}$	$-I_{CER}$ $-I_{CER}$	< <	50 10	— nA 10 μA
Saturation voltage $-I_C = 30 \text{ mA}; -I_B = 5 \text{ mA}$	$-V_{CEsat}$	<	—	0,8 V
DC current gain $-I_C = 25 \text{ mA}; -V_{CE} = 20 \text{ V}$	h_{FE}	>	50	—
Transition frequency at $f = 35 \text{ MHz}$ $-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$	f_T	>	60	MHz
Feedback capacitance at $f = 1 \text{ MHz}$ $I_C = 0; -V_{CE} = 30 \text{ V}$	C_{re}	<	—	1,6 pF

* Device mounted on an epoxy printed circuit board 40 mm x 40 mm x 1,5 mm;
mounting pad for the collector lead min. 6 cm².

Fig. 2 Typical values at $-V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 3 $-V_{CE} = 20$ V; $T_j = 25$ °C; typical values.Fig. 4 $-V_{CE} = 10$ V; $T_j = 25$ °C; $f = 35$ MHz.

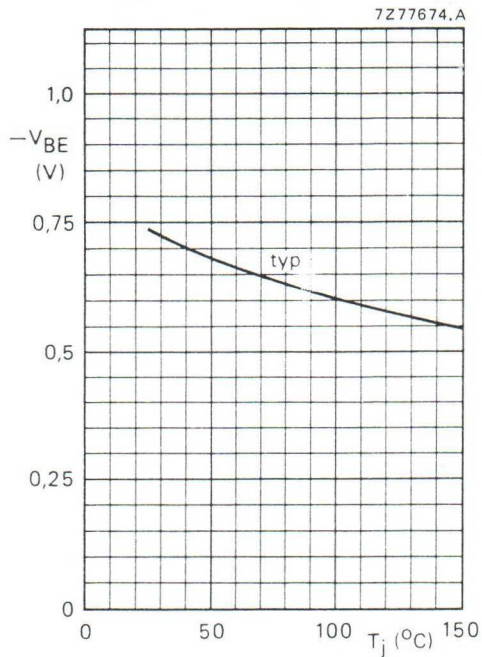


Fig. 5 $-I_C = 25$ mA; $-V_{CE} = 20$ V.

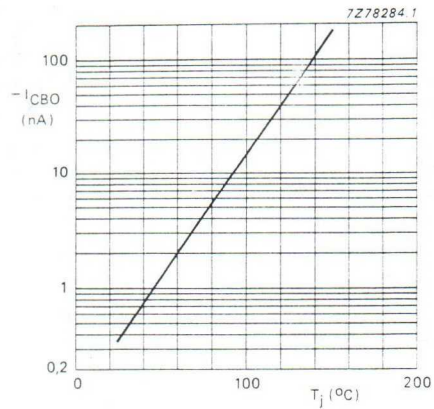


Fig. 6 $-V_{CB} = 200$ V; typical values.

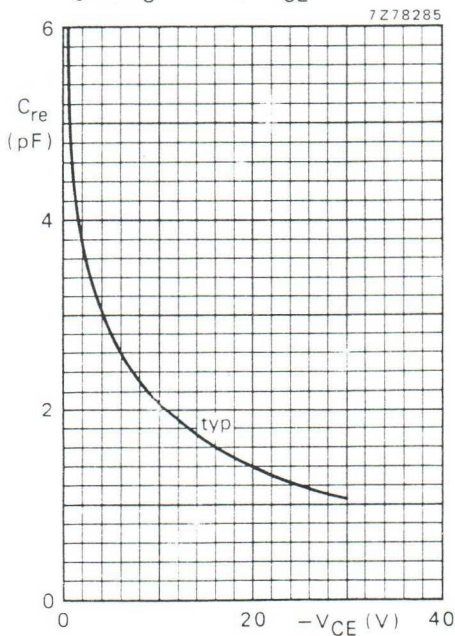


Fig. 7 $I_C = 0$; $f = 1$ MHz; $T_j = 25$ °C.

Philips Components

Data sheet	
status	Product specification
date of issue	April 1991

BF747

NPN 1 GHz wideband transistor

FEATURES

- Stable oscillator operation
- High current gain
- Good thermal stability.

DESCRIPTION

The BF747 is a low cost NPN transistor in a plastic SOT23 envelope. It is intended for VHF and UHF TV-tuner applications and can be used as a mixer and/or oscillator.

MECHANICAL DATA

Plastic SOT23.

PIN	DESCRIPTION
1	base
2	emitter
3	collector

Marking code : E15

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CEO}	collector-emitter voltage		-	20	V
V_{CBO}	collector-base voltage		-	30	V
V_{EBO}	emitter-base voltage		-	3	V
I_{CM}	collector current (DC)	peak value	-	50	mA
P_{tot}	total power dissipation	up to $T_s = 100^\circ\text{C}$ note 1	-	150	mW
T_{stg}	storage temperature range		-55	+150	$^\circ\text{C}$
T_j	junction temperature		-	+150	$^\circ\text{C}$

Note

1. T_s temperature measured on soldering point of collector tab.

ORDERING AND PACKAGE INFORMATION

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BF747	SOT23	12 mm reel	3000

NPN 1 GHz wideband transistor**BF747****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CE0}	collector-emitter voltage		-	20	V
V_{EBO}	emitter-base voltage		-	3	V
V_{CBO}	collector-base voltage		-	30	V
I_{CM}	collector current (DC)	peak value	-	50	mA
P_{tot}	total power dissipation	up to $T_s = 100\text{ }^{\circ}\text{C}$	-	150	mW
T_{stg}	storage temperature range		-55	+150	$^{\circ}\text{C}$
T_j	operating junction temperature		-	+150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-s}$	from junction to soldering point	320	K/W

CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 10\text{ V}$	-	-	100	nA
h_{FE}	DC current gain	$I_C = 2\text{ mA}$; $V_{CE} = 10\text{ V}$	40	-	250	
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 15\text{ mA}$; $V_{CE} = 10\text{ V}$	0.8	1.2	1.6	GHz
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_E = I_e = 0$; $V_{CB} = 10\text{ V}$	-	0.5	-	pF
G_{UM}	maximum unilateral power gain	$f = 100\text{ MHz}$; $I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$ note 1	-	20	-	dB

Note1. Maximum Unilateral Gain (G_{UM}) is defined as:

$$G_{UM} = \frac{1}{1 - |S_{11}|^2} |S_{21}|^2 \frac{1}{1 - |S_{22}|^2}$$

NPN 1 GHz wideband transistor

BF747

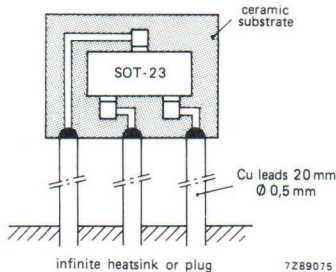


Fig.1 Test circuit for SOT23 $R_{th\ j-s}$ measurement; ceramic substrate 8 x 10 x 0.7 mm.

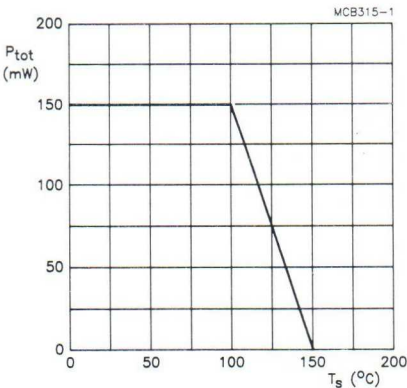


Fig.2 Power derating curve, junction to case.

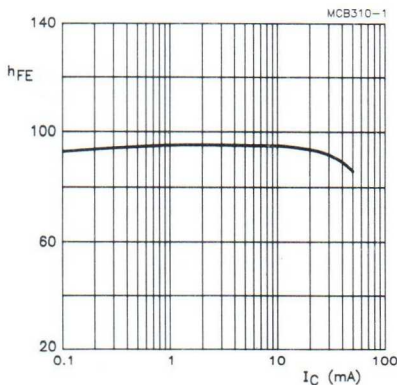


Fig.3 Current gain as a function of collector current; $V_{CE} = 10$ V.

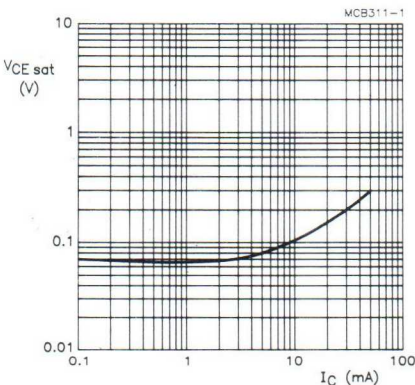


Fig.4 Collector-emitter saturation voltage as a function of collector current; $I_C/I_B = 10$.

NPN 1 GHz wideband transistor

BF747

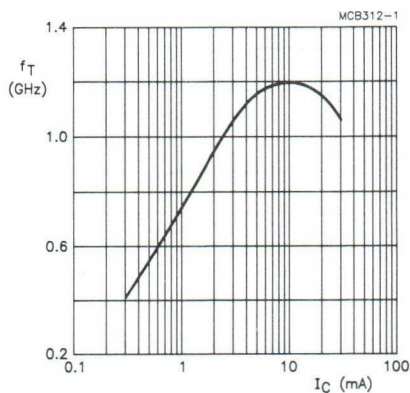


Fig.5 Transition frequency as a function of collector current; $V_{CE} = 10$ V; $f = 500$ MHz.

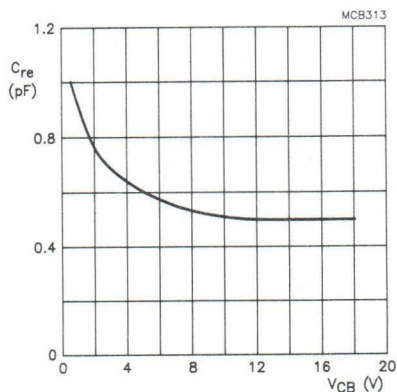


Fig.6 Feedback capacitance as a function of voltage; $I_E = I_B = 0$; $f = 1$ MHz.

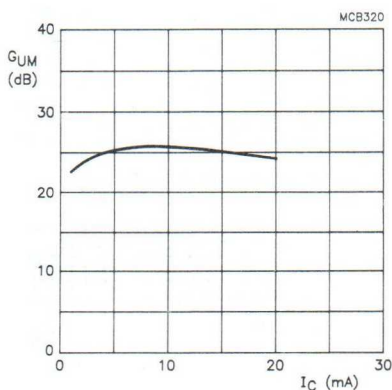


Fig.7 Common-emitter G_{UM} as a function of collector current; $V_{CE} = 10$ V; $f = 100$ MHz.

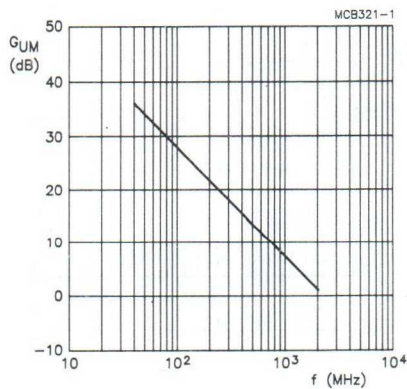


Fig.8 Common-emitter G_{UM} as a function of frequency; $V_{CE} = 10$ V; $I_C = 15$ mA.

NPN 1 GHz wideband transistor

BF747

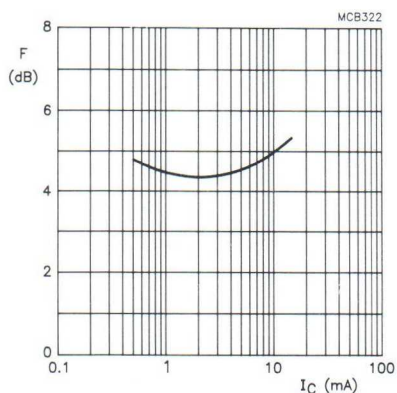


Fig.9 Common-emitter noise figure as a function of collector current; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$; $Z_S = Z_L = 50\ \Omega$.

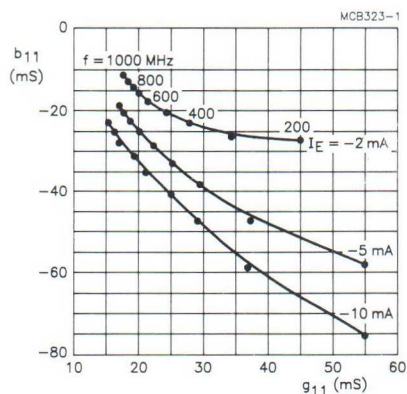


Fig.10 Common-base input admittance, Y_{11} ; $V_{CB} = 10\text{ V}$.

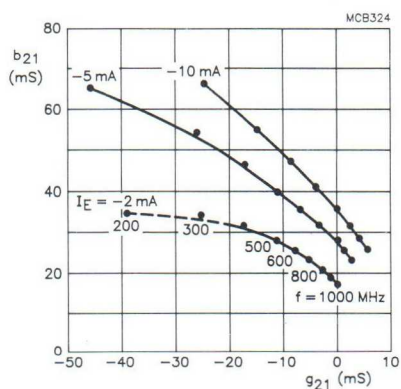


Fig.11 Common-base forward admittance, Y_{21} ; $V_{CB} = 10\text{ V}$.

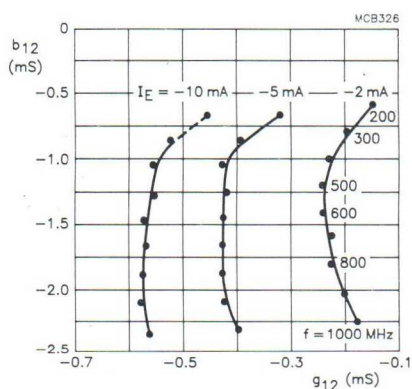


Fig.12 Common-base reverse admittance, Y_{12} ; $V_{CB} = 10\text{ V}$.

NPN 1 GHz wideband transistor

BF747

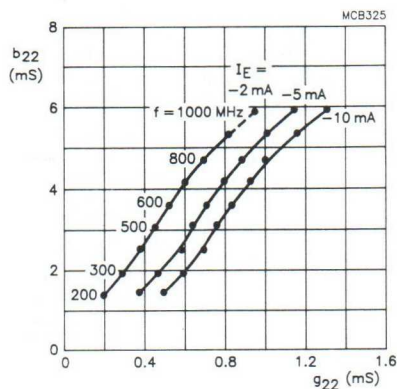


Fig.13 Common-base output admittance, Y_{22} ;
 $V_{CB} = 10$ V.

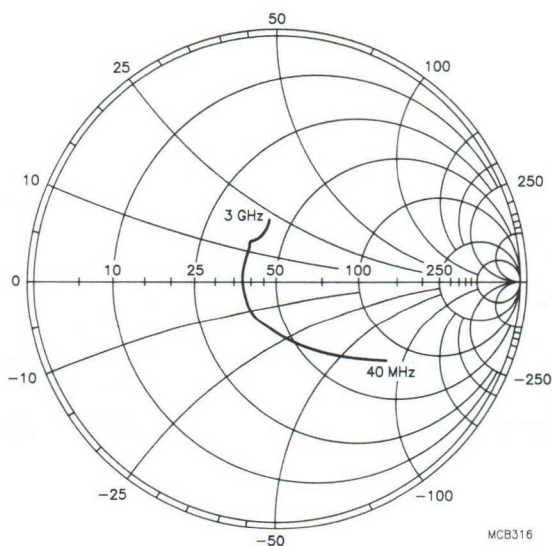
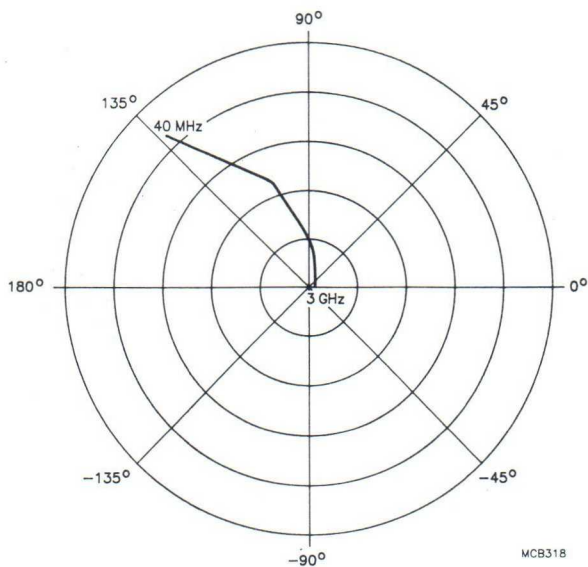
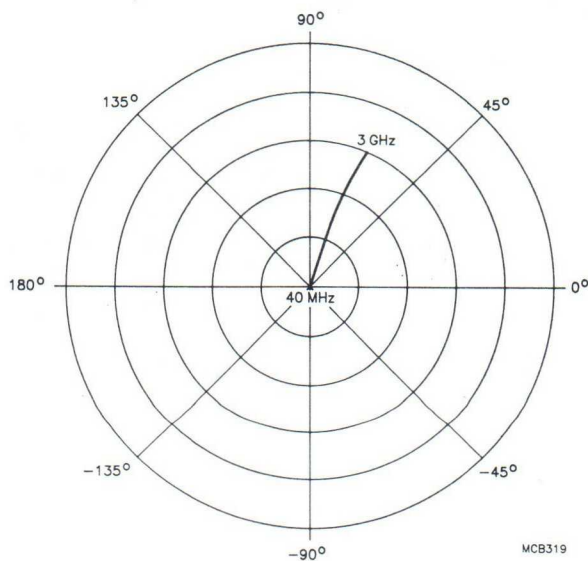


Fig.14 Common-emitter input reflection coefficient, S_{11} ; $V_{CE} = 10$ V; $I_C = 15$ mA.

NPN 1 GHz wideband transistor

BF747

Fig.15 Common-emitter forward transmission coefficient, S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.Fig.16 Common-emitter reverse transmission coefficient, S_{12} ; $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.

NPN 1 GHz wideband transistor

BF747

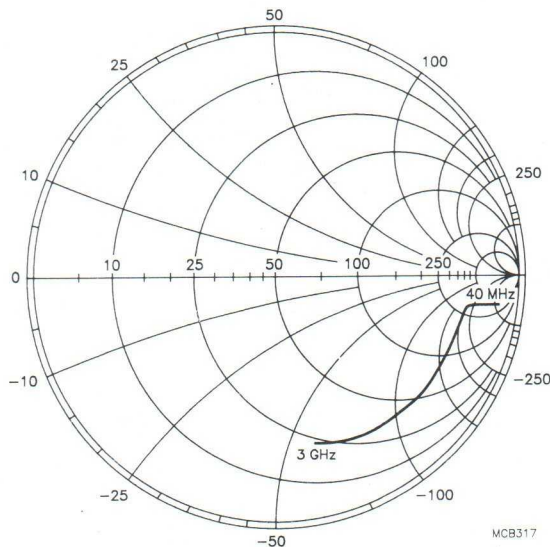


Fig.17 Common-emitter output transmission coefficient, S_{22} ; $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.

Y-Parameters (common-base) at $V_{CB} = 10\text{ V}$; $I_E = -2\text{ mA}$; typical values.

FREQUENCY (MHz)	Y ₁₁		Y ₂₁		Y ₁₂		Y ₂₂	
	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)
40.00	68.9746	-10.271	-67.9160	12.3298	-.0200	-.1000	-.0130	.29080
100.00	60.4233	-20.585	-57.9200	25.6144	-.0600	-.3000	-.0840	.70980
200.00	45.0125	-27.430	-39.0830	34.4796	-.1000	-.6000	.1943	1.35389
300.00	34.2639	-26.441	-25.4210	33.9009	-.2000	-.8000	.2948	1.91811
400.00	27.6753	-23.366	-17.2450	31.1112	-.2000	-1.0036	.3728	2.50881
500.00	23.9258	-20.416	-11.6530	27.6373	-.2000	-1.2020	.4471	3.04457
600.00	21.4986	-17.909	- 7.8471	25.0050	-.2000	-1.4026	.5253	3.59467
700.00	20.0348	-15.630	- 5.3109	22.6341	-.2000	-1.5963	.5974	4.17222
800.00	18.6263	-14.039	- 2.9007	20.1675	-.2000	-1.8013	.6929	4.70894
900.00	18.2579	-12.788	- 1.3647	18.7133	-.2000	-2.0306	.8206	5.29419
1000.00	17.8426	-11.684	- .0660	17.1226	-.2000	-2.2498	.9520	5.88614

NPN 1 GHz wideband transistor**BF747**Y-Parameters (common-base) at $V_{CB} = 10\text{ V}$; $I_E = -5\text{ mA}$; typical values.

FREQUENCY (MHz)	Y ₁₁		Y ₂₁		Y ₁₂		Y ₂₂	
	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)
40.00	132.6450	-35.658	-130.47000	38.7532	-.060	-.2000	-.05600	.36870
100.00	96.3278	-62.045	-91.06400	67.9477	-.200	-.5000	.20970	.83980
200.00	54.7356	-57.831	-45.98500	64.7007	-.300	-.7000	.37680	1.42279
300.00	37.5006	-46.867	-26.38900	53.7615	-.400	-.8000	.46800	1.95355
400.00	29.1994	-38.645	-16.63700	45.7605	-.400	-1.0430	.58050	2.52321
500.00	25.2687	-32.798	-11.03600	39.7522	-.400	-1.2500	.63100	3.09770
600.00	22.0303	-28.445	-6.27570	34.9583	-.400	-1.4469	.70520	3.63913
700.00	20.2654	-25.198	-3.34920	31.4025	-.400	-1.6459	.80310	4.21016
800.00	18.6656	-22.649	-.60000	27.6064	-.400	-1.8593	.87660	4.73938
900.00	17.8189	-20.746	1.38032	25.2334	-.400	-2.0839	1.00727	5.31269
1000.00	17.2772	-19.065	2.92948	23.0084	-.400	-2.3053	1.15011	5.92755

Y-Parameters (common-base) at $V_{CB} = 10\text{ V}$; $I_E = -10\text{ mA}$; typical values.

FREQUENCY (MHz)	Y ₁₁		Y ₂₁		Y ₁₂		Y ₂₂	
	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)
40.00	189.0470	-79.568	-185.47000	82.9150	-.090	-.3000	-.08600	.43550
100.00	108.5130	-99.005	-101.43000	105.3800	-.300	-.5000	.32930	.87400
200.00	55.2449	-76.232	-44.63200	82.8056	-.500	-.7000	.49110	1.40994
300.00	37.1349	-59.012	-24.28100	65.6604	-.500	-.9000	.60430	1.96058
400.00	28.8268	-47.567	-14.57300	54.4220	-.600	-1.0467	.68940	2.52179
500.00	24.6784	-40.178	-8.56610	46.6501	-.600	-1.2644	.75390	3.09189
600.00	21.2460	-35.017	-3.39520	40.7817	-.600	-1.4688	.84080	3.63543
700.00	19.2824	-30.939	-.20000	36.2027	-.600	-1.6715	.93220	4.20978
800.00	17.1543	-27.470	2.55300	31.1491	-.600	-1.8634	.99920	4.71616
900.00	16.4469	-25.237	4.57622	28.3362	-.600	-2.1025	1.15185	5.31337
1000.00	15.8137	-23.001	6.03713	25.4579	-.600	-2.3336	1.31127	5.90833

Y-Parameters (common-base) at $V_{CB} = 10\text{ V}$; $I_E = -15\text{ mA}$; typical values.

FREQUENCY (MHz)	Y ₁₁		Y ₂₁		Y ₁₂		Y ₂₂	
	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)	Real (mS)	Imag (mS)
40.00	206.4780	-113.760	-202.64000	118.0530	-.200	-.3000	.18780	.47790
100.00	104.3290	-113.970	-96.42500	120.0870	-.400	-.5000	.41900	.87720
200.00	53.0622	-81.120	-41.70000	87.7035	-.500	-.7000	.57550	1.41575
300.00	35.9283	-62.076	-21.91000	68.6039	-.600	-.8000	.65550	1.93670
400.00	28.0704	-50.027	-12.48400	56.9216	-.600	-1.0609	.75580	2.52909
500.00	23.4107	-42.306	-6.08020	48.2499	-.600	-1.2607	.81790	3.07778
600.00	20.1019	-36.373	-1.22150	41.5856	-.600	-1.4610	.89420	3.61247
700.00	18.1804	-32.035	2.01096	36.6737	-.600	-1.6677	.99970	4.18590
800.00	16.1524	-28.238	4.48487	31.3273	-.600	-1.8612	1.09358	4.71538
900.00	15.4557	-25.677	6.45024	28.0793	-.600	-2.1019	1.26238	5.28396
1000.00	14.6838	-23.452	7.89223	24.8572	-.600	-2.3163	1.39668	5.87286

NPN 1 GHz wideband transistor**BF747****S-Parameters (common-base) at $V_{CE} = 10\text{ V}$; $I_C = 2\text{ mA}$; typical values.**

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} (dB)
	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	
40	.891	-17.1	5.90	160.4	.013	79.3	.986	-4.0	37.7
100	.741	-37.1	4.89	137.9	.027	69.4	.936	-7.8	26.2
200	.522	-55.9	3.38	115.3	.044	64.0	.882	-10.6	18.4
300	.404	-65.8	2.48	103.2	.057	63.2	.857	-12.6	14.4
400	.332	-73.3	1.97	94.4	.070	63.0	.847	-14.6	11.8
500	.288	-78.7	1.62	88.0	.081	63.2	.839	-16.9	9.8
600	.258	-84.7	1.39	82.5	.092	63.1	.835	-19.3	8.3
700	.233	-89.2	1.23	77.9	.102	62.7	.833	-21.7	7.1
800	.213	-95.0	1.10	73.8	.112	62.5	.829	-24.0	6.0
900	.199	-100.3	1.00	70.0	.122	62.0	.827	-26.4	5.1
1000	.184	-106.5	.93	66.6	.131	61.9	.822	-28.8	4.4
1200	.154	-120.2	.82	59.6	.148	61.1	.812	-33.5	3.0
1400	.142	-134.3	.74	53.9	.164	60.8	.807	-38.5	2.0
1600	.131	-146.0	.68	50.0	.178	60.9	.799	-43.2	1.1
1800	.121	-161.9	.64	45.9	.194	60.9	.792	-47.6	.4
2000	.117	-179.8	.60	41.0	.207	60.4	.771	-52.2	-.3

S-Parameters (common-base) at $V_{CE} = 10\text{ V}$; $I_C = 5\text{ mA}$; typical values.

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} (dB)
	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	
40	.767	-26.3	11.30	149.3	.011	75.8	.956	-6.0	35.6
100	.542	-49.1	7.60	123.2	.022	67.6	.875	-8.8	25.4
200	.359	-65.2	4.49	104.5	.036	66.7	.827	-10.1	18.6
300	.283	-75.2	3.14	95.4	.049	66.7	.811	-11.8	14.9
400	.244	-84.2	2.45	88.6	.061	66.5	.804	-13.9	12.5
500	.214	-92.4	1.99	83.5	.073	66.5	.798	-16.0	10.5
600	.196	-100.7	1.69	78.7	.083	66.6	.797	-18.5	9.1
700	.180	-108.6	1.48	74.7	.093	66.6	.797	-20.8	7.9
800	.170	-115.6	1.31	71.2	.102	66.5	.796	-23.1	6.8
900	.156	-123.6	1.19	67.7	.112	66.1	.792	-25.4	5.9
1000	.146	-131.7	1.10	64.4	.121	66.0	.790	-27.8	5.2
1200	.132	-150.4	.96	57.6	.138	65.9	.783	-32.5	3.9
1400	.132	-164.8	.85	52.4	.155	65.9	.778	-37.4	2.7
1600	.133	-176.8	.78	48.4	.172	66.2	.776	-42.1	1.9
1800	.132	169.3	.72	44.4	.189	66.3	.770	-46.5	1.2
2000	.140	152.4	.67	39.3	.205	65.5	.752	-50.9	.3

NPN 1 GHz wideband transistor

BF747

S-Parameters (common-base) at $V_{CE} = 10\text{ V}$; $I_C = 10\text{ mA}$; typical values.

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} (dB)
	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	
40	.637	- 34.1	15.48	139.4	.010	72.6	.921	- 7.3	34.2
100	.416	- 54.7	8.90	114.2	.020	68.9	.837	- 8.5	25.0
200	.283	- 71.9	4.95	99.1	.033	68.5	.802	- 9.4	18.7
300	.236	- 84.8	3.42	91.6	.046	68.3	.790	-11.1	15.1
400	.204	- 97.7	2.64	85.3	.057	68.0	.785	-13.2	12.7
500	.186	-108.3	2.14	80.6	.068	68.5	.781	-15.5	10.8
600	.173	-117.8	1.81	76.1	.077	68.8	.780	-17.7	9.4
700	.155	-127.4	1.58	72.3	.087	69.2	.781	-20.1	8.2
800	.151	-134.7	1.40	68.8	.097	69.4	.781	-22.5	7.1
900	.143	-143.3	1.26	65.3	.106	69.3	.778	-24.7	6.1
1000	.139	-152.2	1.16	62.3	.115	69.4	.779	-27.0	5.4
1200	.135	-170.8	1.01	55.5	.134	69.4	.773	-31.7	4.1
1400	.139	177.6	.89	50.3	.152	69.2	.768	-36.7	2.9
1600	.143	167.4	.80	46.4	.170	69.4	.766	-41.4	2.0
1800	.146	152.2	.74	42.6	.188	69.4	.762	-45.9	1.3
2000	.161	140.1	.69	37.5	.205	68.3	.746	-50.4	.4

S-Parameters (common-base) at $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; typical values.

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} (dB)
	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	Mag (rat)	Ang (deg)	
40	.564	- 37.9	16.88	133.4	.009	73.0	.901	- 7.4	33.4
100	.365	- 57.3	8.99	110.3	.019	69.4	.826	- 7.9	24.7
200	.260	- 75.7	4.93	96.9	.032	69.3	.797	- 8.9	18.5
300	.216	- 91.4	3.41	89.8	.044	69.2	.786	-10.8	15.0
400	.187	-105.1	2.63	83.7	.055	69.3	.781	-12.9	12.6
500	.174	-116.4	2.12	79.0	.066	69.9	.779	-15.1	10.7
600	.160	-126.6	1.80	74.4	.075	70.1	.778	-17.4	9.2
700	.152	-136.3	1.56	70.5	.085	70.7	.781	-19.8	8.1
800	.143	-145.0	1.38	67.0	.095	71.0	.780	-22.1	6.9
900	.138	-152.1	1.24	63.7	.104	70.9	.780	-24.4	6.0
1000	.136	-161.8	1.14	60.5	.113	71.0	.778	-26.7	5.3
1200	.137	-178.2	.99	53.9	.132	70.9	.774	-31.5	3.9
1400	.144	168.8	.87	48.6	.151	70.6	.770	-36.4	2.8
1600	.145	159.4	.78	44.6	.169	70.9	.768	-41.2	1.9
1800	.150	146.2	.73	41.0	.188	70.8	.764	-45.7	1.1
2000	.167	134.2	.67	35.9	.206	69.5	.748	-50.3	.3

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope intended for application in thick and thin-film circuits. Primarily intended for use in telephony and professional communication equipment. P-N-P components are BF821, BF823 respectively.

QUICK REFERENCE DATA

		BF820	BF822
Collector-base voltage (open emitter)	V_{CBO} max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO} max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER} max.	300	— V
Collector current (peak value)	I_{CM} max.	100	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot} max.	250	mW
Junction temperature	T_j max.	150	$^\circ\text{C}$
D.C. current gain	h_{FE}	> 50	
$I_C = 25 \text{ mA}; V_{CE} = 20 \text{ V}$			
Feedback capacitance at $f = 1 \text{ MHz}$	C_{re}	< 1,6 pF	
$I_C = 0; V_{CE} = 30 \text{ V}$			
Transition frequency at $f = 35 \text{ MHz}$	f_T	> 60 MHz	
$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$			

MECHANICAL DATA

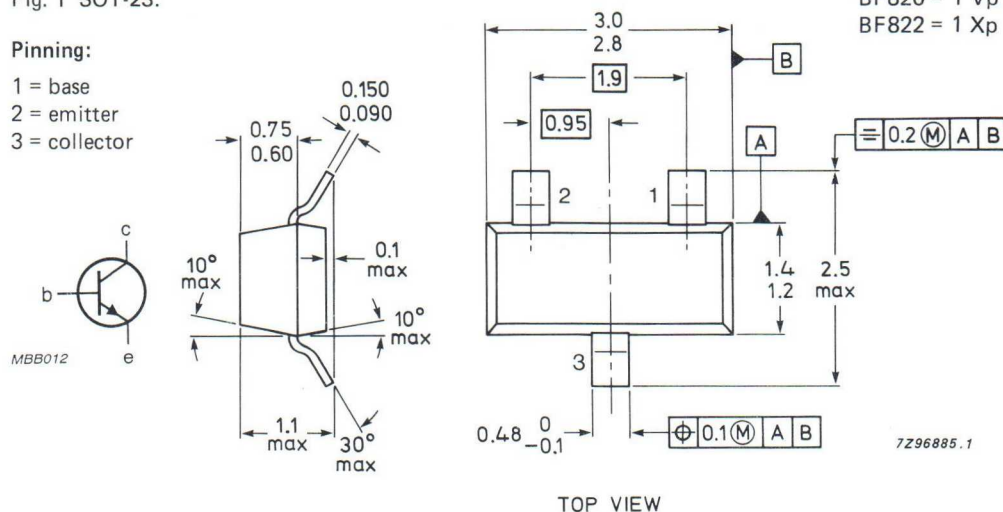
Dimensions in mm

Marking code

Fig. 1 SOT-23.

Pinning:

- 1 = base
2 = emitter
3 = collector



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BF820	BF822
Collector-base voltage (open emitter)	V_{CBO} max.	300	250 V
Collector-emitter voltage (open base)	V_{CEO} max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	V_{CER} max.	300	— V
Emitter-base voltage (open collector)	V_{EBO} max.	5	V
Collector current (d.c.)	I_C max.	50	mA
Collector current (peak value)	I_{CM} max.	100	mA
Total power dissipation* up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot} max.	250	mW
Storage temperature	T_{stg}	-65 to +150 $^\circ\text{C}$	
Junction temperature	T_j max.	150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th \text{ j-a}}$ =	500	K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0$; $V_{CB} = 200 \text{ V}$

	BF820	BF822
I_{CBO}	< 10	10 nA
I_{CER}	< 50	50 nA
I_{CER}	< 10	10 μA
$V_{CE \text{ sat}}$	< 0,6	V

Collector-emitter voltage

$R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 250 \text{ V}$

$R_{BE} = 2,7 \text{ k}\Omega$; $V_{CE} = 200 \text{ V}$; $T_j = 150 \text{ }^\circ\text{C}$

Saturation voltage

$I_C = 30 \text{ mA}$; $I_B = 5 \text{ mA}$

D.C. current gain

$I_C = 25 \text{ mA}$; $V_{CE} = 20 \text{ V}$

Transition frequency at $f = 35 \text{ MHz}$

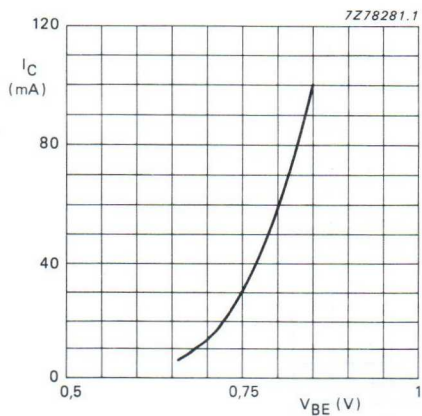
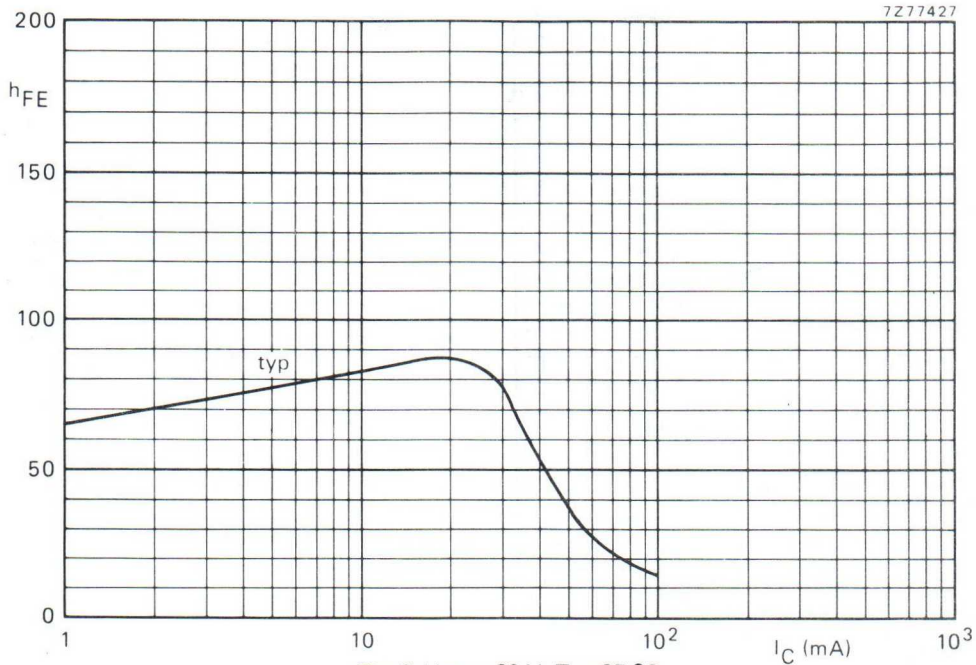
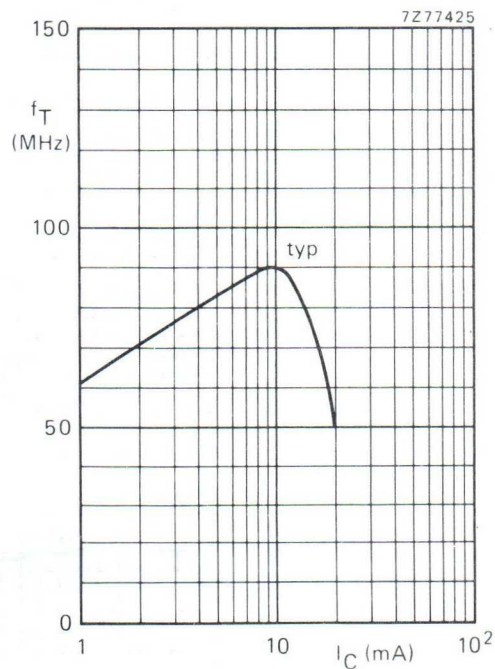
$I_C = 10 \text{ mA}$; $V_{CE} = 10 \text{ V}$

Feedback capacitance at $f = 1 \text{ MHz}$

$I_C = 0$; $V_{CE} = 30 \text{ V}$

h_{FE}	> 50	
f_T	> 60	MHz
C_{re}	< 1,6	pF

* Mounted on a ceramic substrate: area = $2,5 \text{ cm}^2$; thickness = 0,7 mm.

Fig. 3 $V_{CE} = 20 \text{ V}$; $T_j = 25^\circ\text{C}$; typical values.Fig. 4 $V_{CE} = 10 \text{ V}$; $T_j = 25^\circ\text{C}$, $f = 35 \text{ MHz}$.

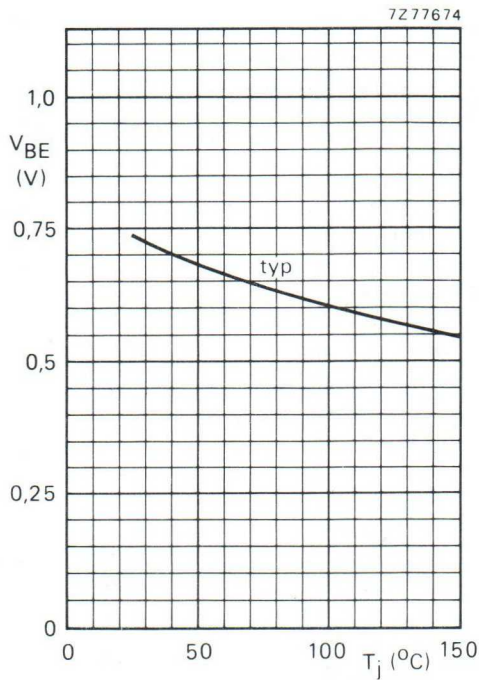


Fig. 5 $I_C = 25 \text{ mA}$; $V_{CE} = 20 \text{ V}$.

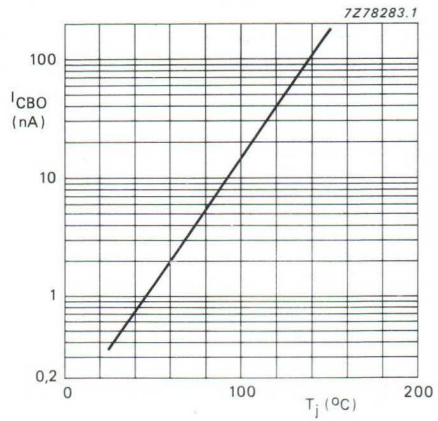


Fig. 6 $V_{CB} = 200 \text{ V}$; typical values.

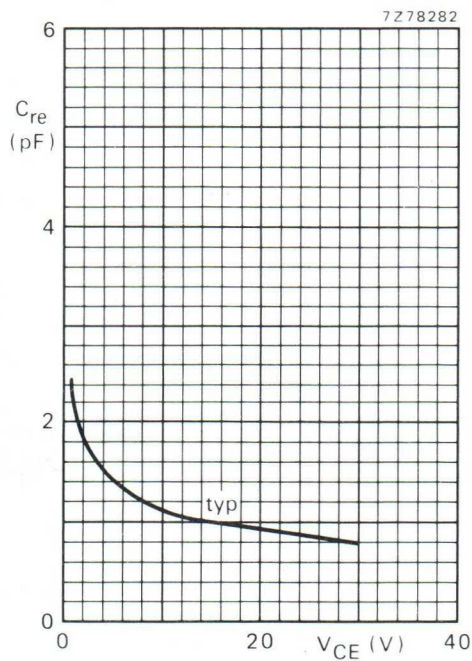


Fig. 7 $I_C = 0$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^{\circ}\text{C}$.

SILICON EPITAXIAL TRANSISTORS

P-N-P transistors in a microminiature plastic envelope intended for application in thick and thin-film circuits. Primarily intended for use in telephony and professional communication equipment. N-P-N complements are BF820, BF822 respectively.

QUICK REFERENCE DATA

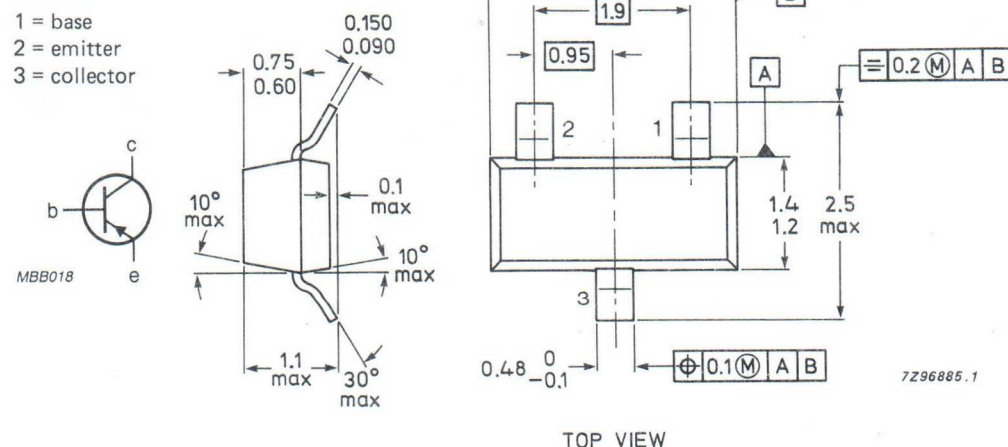
		BF821	BF823
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$ max.	300	— V
Collector current (peak value)	$-I_{CM}$ max.	100	mA
Total power dissipation up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot} max.	250	mW
Junction temperature	T_j max.	150	$^\circ\text{C}$
D.C. current gain	h_{FE}	>	50
Feedback capacitance at $f = 1 \text{ MHz}$	C_{re}	<	1,6 pF
Transition frequency at $f = 35 \text{ MHz}$	f_T	>	60 MHz
		$-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$	

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		BF821	BF823
Collector-base voltage (open emitter)	$-V_{CBO}$ max.	300	250 V
Collector-emitter voltage (open base)	$-V_{CEO}$ max.	—	250 V
Collector-emitter voltage ($R_{BE} = 2,7 \text{ k}\Omega$)	$-V_{CER}$ max.	300	— V
Emitter-base voltage (open collector)	$-V_{EBO}$ max.	5	V
Collector current (d.c.)	$-I_C$ max.	50	mA
Collector current (peak value)	$-I_{CM}$ max.	100	mA
Total power dissipation * up to $T_{amb} = 25 \text{ }^\circ\text{C}$	P_{tot} max.	250	mW
Storage temperature	T_{stg}	$-65 \text{ to } +150 \text{ }^\circ\text{C}$	
Junction temperature	T_j max.	150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient*

$R_{th \text{ j-a}}$	=	500	K/W
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CHARACTERISTICS

$T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 200 \text{ V}$

	BF821	BF823
$-I_{CBO}$	< 10	10 nA

Collector-emitter voltage

$R_{BE} = 2,7 \text{ k}\Omega; -V_{CE} = 250 \text{ V}$

$R_{BE} = 2,7 \text{ k}\Omega; -V_{CE} = 200 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$

$-I_{CER}$	< 50	50 nA
$-I_{CER}$	< 10	10 μA

Saturation voltage

$-I_C = 30 \text{ mA}; -I_B = 5 \text{ mA}$

$-V_{CEsat}$	< 0,8	V
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D.C. current gain

$-I_C = 25 \text{ mA}; -V_{CE} = 20 \text{ V}$

h_{FE}	> 50	
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Transition frequency at $f = 35 \text{ MHz}$

$-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$

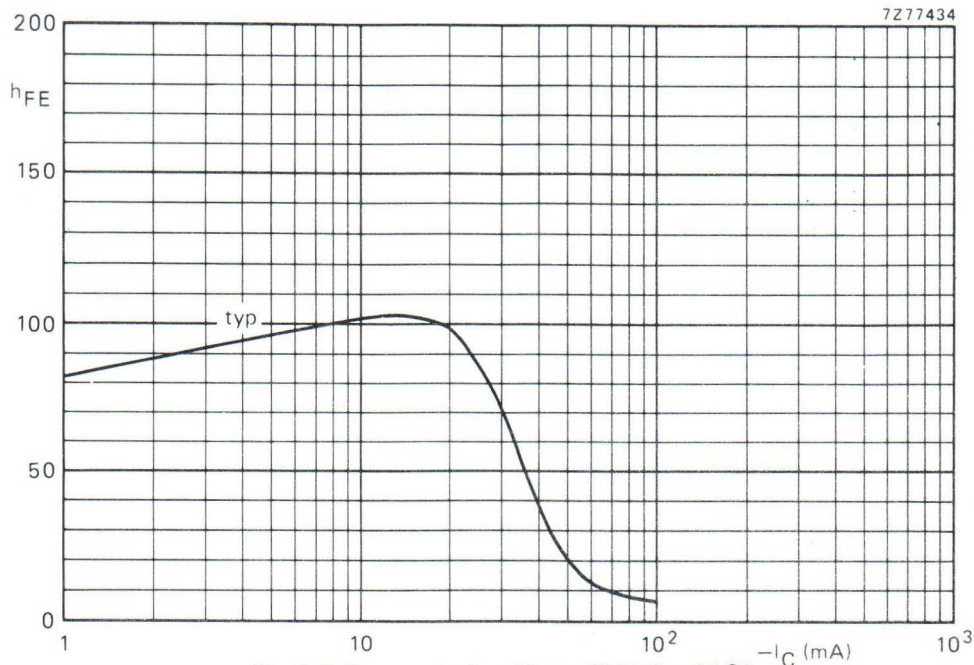
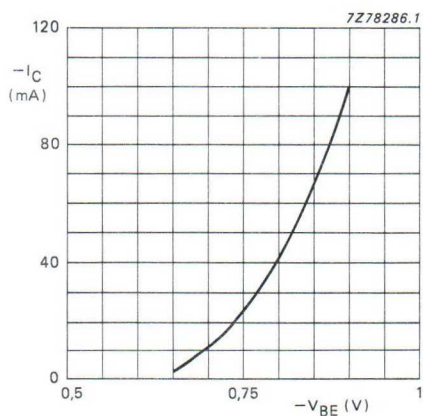
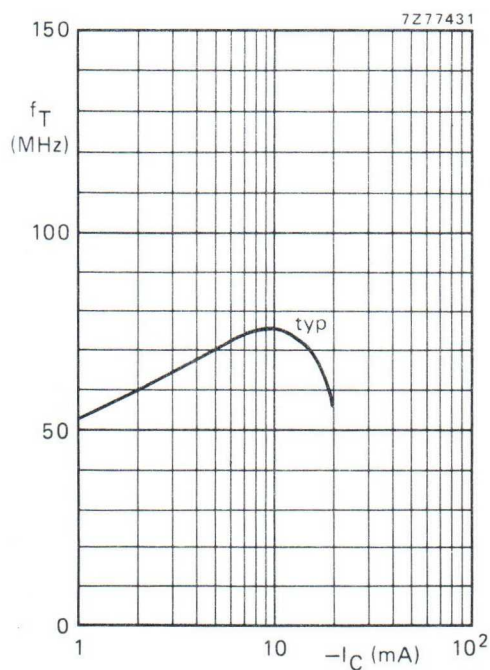
f_T	> 60	MHz
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Feedback capacitance at $f = 1 \text{ MHz}$

$I_C = 0; -V_{CE} = 30 \text{ V}$

C_{re}	< 1,6	pF
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* Mounted on a ceramic substrate: area = $2,5 \text{ cm}^2$; thickness = $0,7 \text{ mm}$.

Fig. 2 D.C. current gain. $-V_{CE} = 20$ V; $T_j = 25$ °C.Fig. 3 $-V_{CE} = 20$ V; $T_j = 25$ °C; typical values.Fig. 4 $-V_{CE} = 10$ V; $T_j = 25$ °C; $f = 35$ MHz.

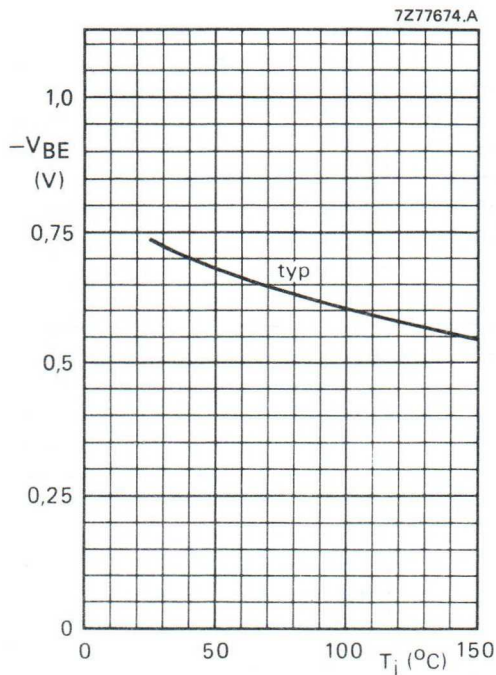


Fig. 5 $-I_C = 25$ mA; $-V_{CE} = 20$ V.

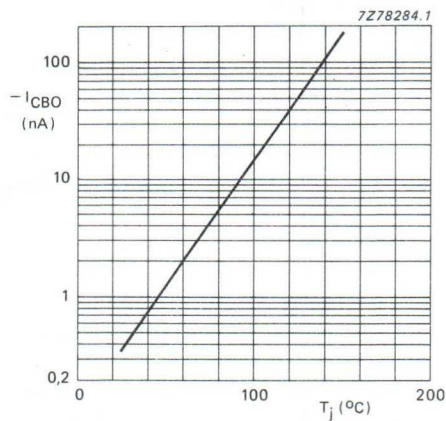


Fig. 6 $-V_{CB} = 200$ V; typical values.

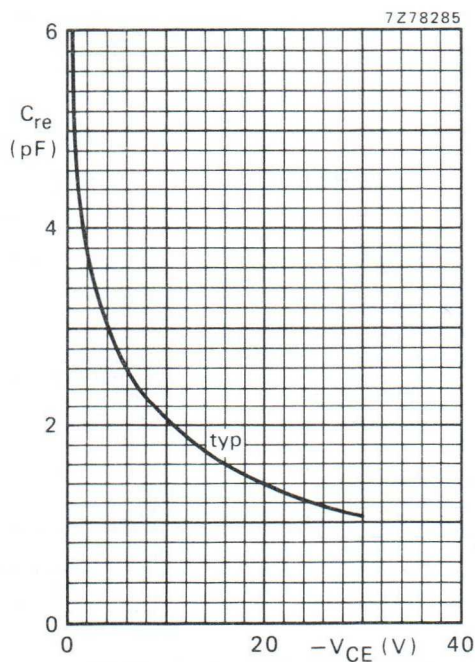


Fig. 7 $I_C = 0$; $f = 1$ MHz; $T_j = 25$ °C.

H.F. SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a plastic SOT-23 envelope especially intended for r.f. stages in f.m. front-ends in common base configuration for SMD applications.

QUICK REFERENCE DATA

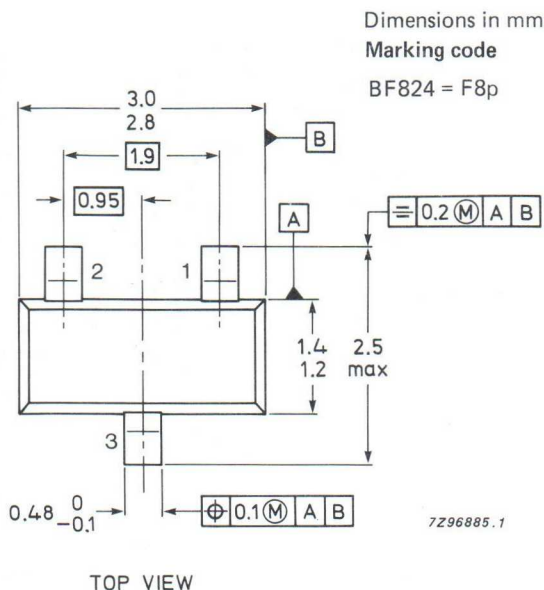
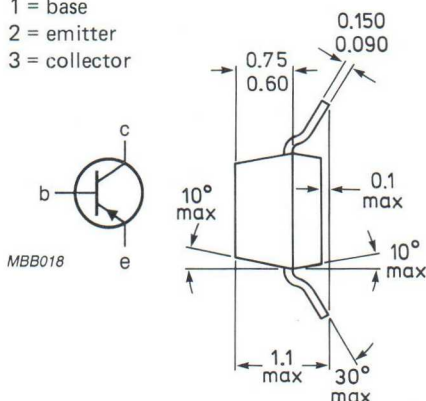
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Collector current (d.c.)	$-I_C$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Base current			
$-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$	$-I_B$	typ.	80 μA
		<	160 μA
Transition frequency	f_T	typ.	450 MHz
$-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$			
Noise figure at $f = 100\text{ MHz}$	F	typ.	3 dB
$-I_C = 2\text{ mA}; -V_{CE} = 10\text{ V}; G_S = 16,7\text{ mS}$			
Feedback capacitance at $f = 1\text{ MHz}$	C_{rb}	typ.	0,1 pF
$V_{EB} = 0; -V_{CB} = 10\text{ V}$			

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4 V
Collector current (d.c.)	$-I_C$	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ *	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air*

$$R_{th\ j-a} = 500\text{ K/W}$$

CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 30\text{ V}$

$-I_{CBO} < 50\text{ nA}$

Emitter cut-off current

$I_C = 0; -V_{EB} = 4\text{ V}$

$-I_{EBO} < 10\text{ }\mu\text{A}$

Base current

$-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$

$$-I_B \begin{matrix} \text{typ.} & 80\text{ }\mu\text{A} \\ < & 160\text{ }\mu\text{A} \end{matrix}$$

$-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$

$-I_B \text{ typ. } 22\text{ }\mu\text{A}$

Base-emitter voltage

$-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$

$-V_{BE} \text{ typ. } 0,76\text{ V}$

Transition frequency at $f = 100\text{ MHz}$

$-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$

$f_T \text{ typ. } 350\text{ MHz}$

$-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$

$f_T \text{ typ. } 450\text{ MHz}$

$-I_C = 8\text{ mA}; -V_{CE} = 10\text{ V}$

$f_T \text{ typ. } 440\text{ MHz}$

Feedback capacitance at $f = 1\text{ MHz}$

$V_{EB} = 0; -V_{CB} = 10\text{ V}$

$C_{rb} \text{ typ. } 0,1\text{ pF}$

Noise factor at $f = 100\text{ MHz}$

$-I_C = 2\text{ mA}; -V_{CE} = 10\text{ V};$

$G_s = 16,7\text{ mS}$

$F \text{ typ. } 3\text{ dB}$

$-I_C = 5\text{ mA}; -V_{CE} = 10\text{ V};$

$G_s = 6,7\text{ mS}; -jB_s = 5\text{ mS}$

$F \text{ typ. } 3,5\text{ dB}$

* Mounted on ceramic substrate of $8\text{ mm} \times 10\text{ mm} \times 0,7\text{ mm}$.

y-parameters (common base) at $f = 100 \text{ MHz}$ $-I_C = 4 \text{ mA}; -V_{CB} = 10 \text{ V}$

Input conductance

Input capacitance

Transfer admittance

Phase angle of transfer admittance

Output conductance

Output capacitance

Feedback admittance

Phase angle of feedback admittance

g_{ib}	typ.	125 mS
C_{ib}	typ.	64 pF
$ y_{fb} $	typ.	100 mS
φ_{fb}	typ.	147°
g_{ob}	typ.	$40 \mu\text{S}$
C_{ob}	typ.	1,25 pF
$ y_{rb} $	typ.	$220 \mu\text{S}$
φ_{rb}	typ.	85°

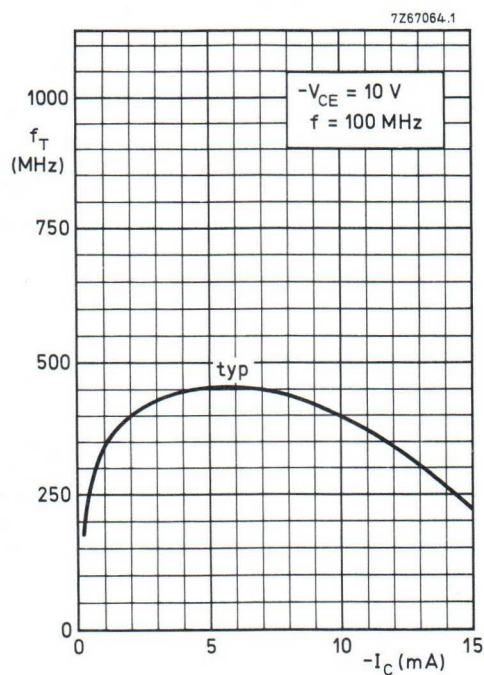


Fig. 2.

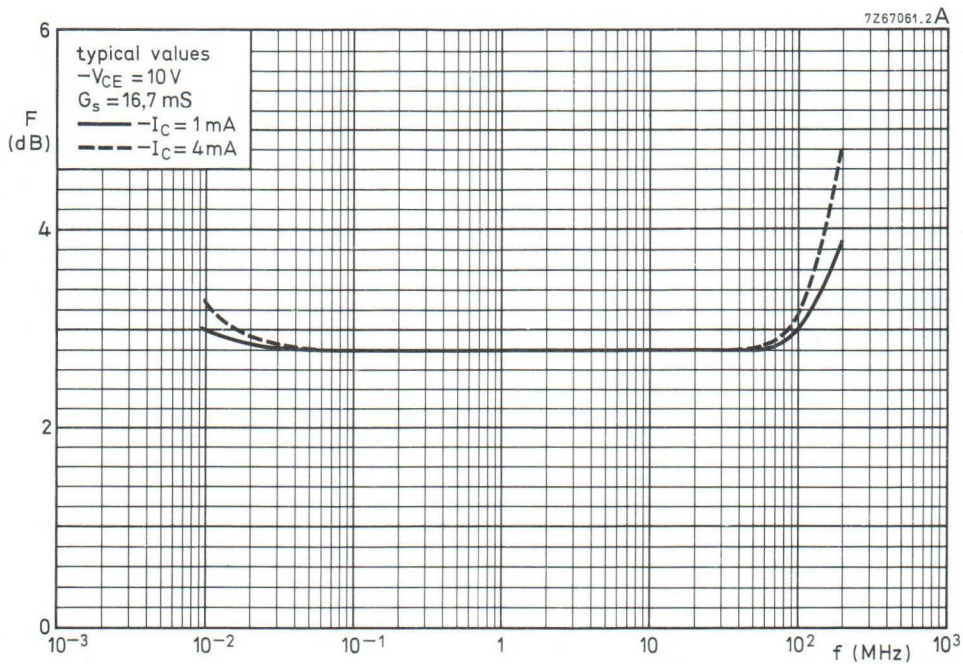


Fig. 3.

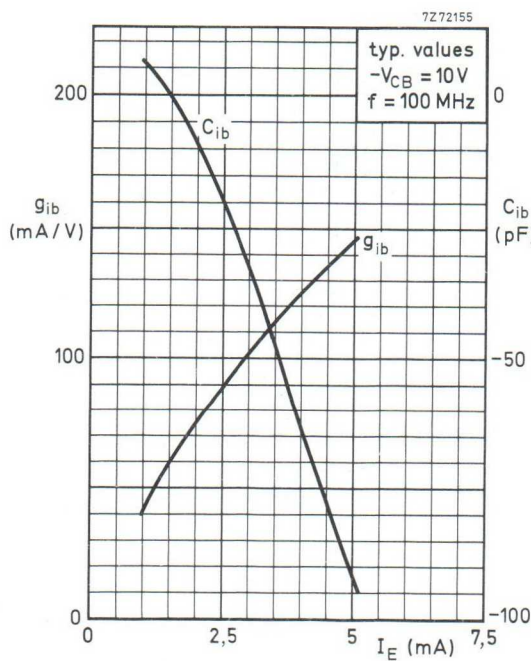


Fig. 4.

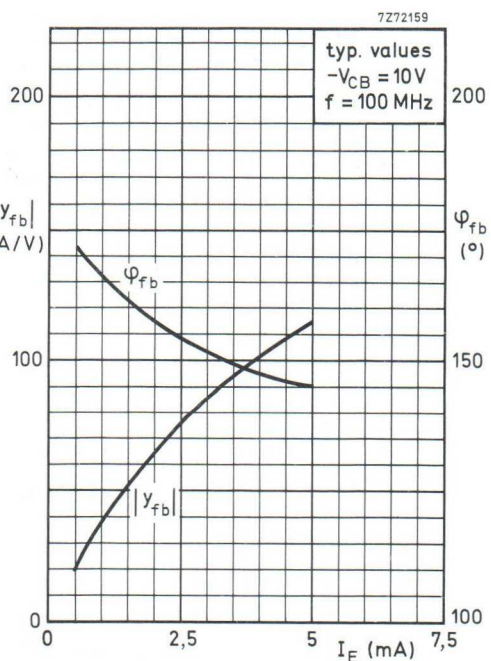


Fig. 5.

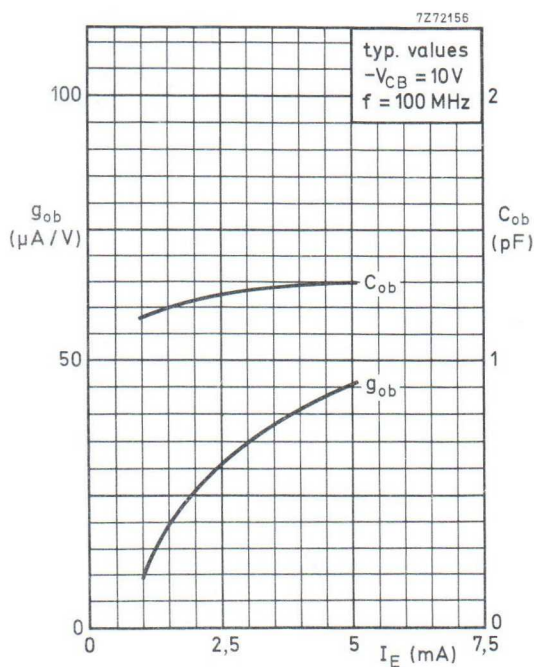


Fig. 6.

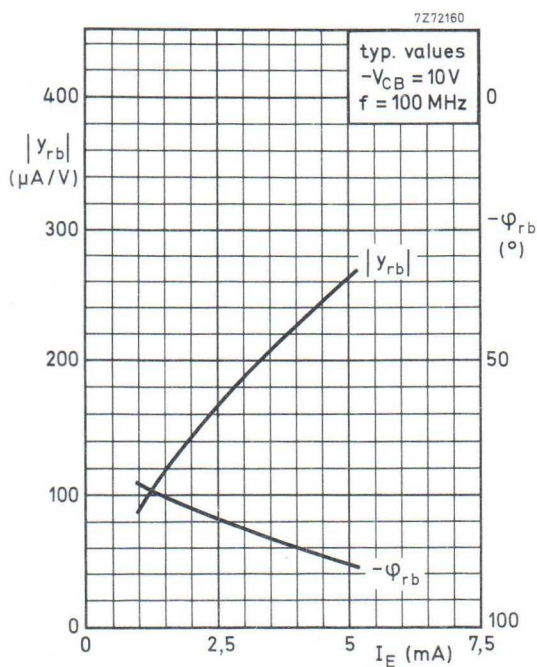


Fig. 7.

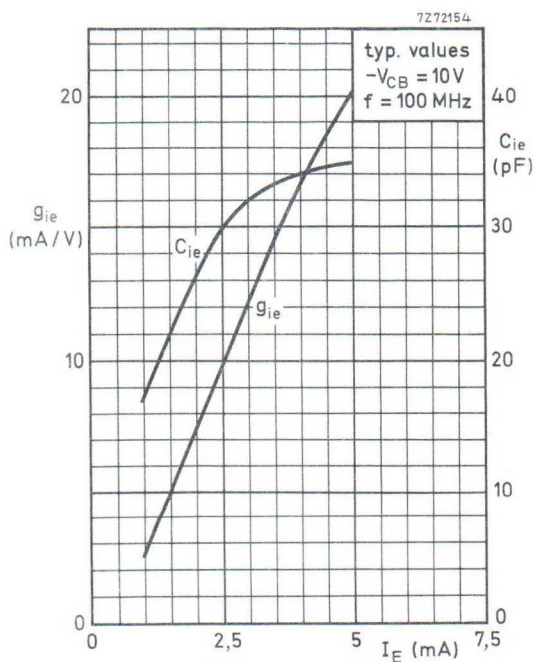


Fig. 8.

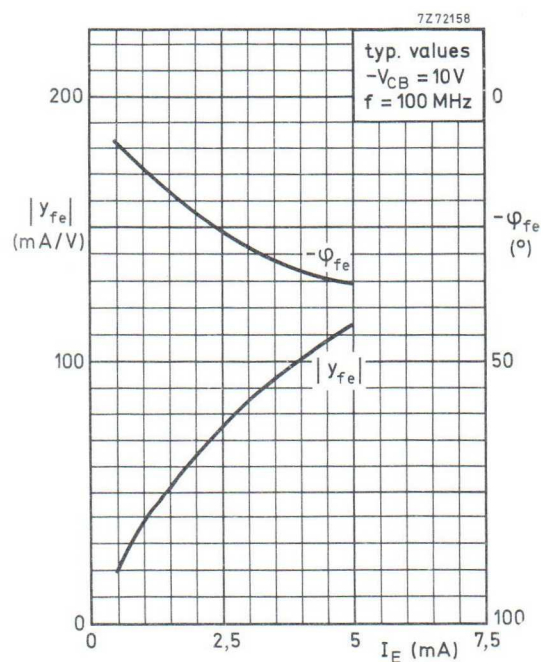


Fig. 9.

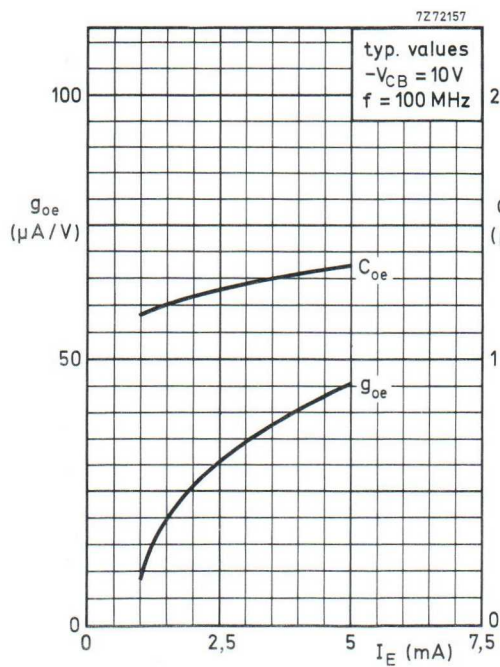


Fig. 10.

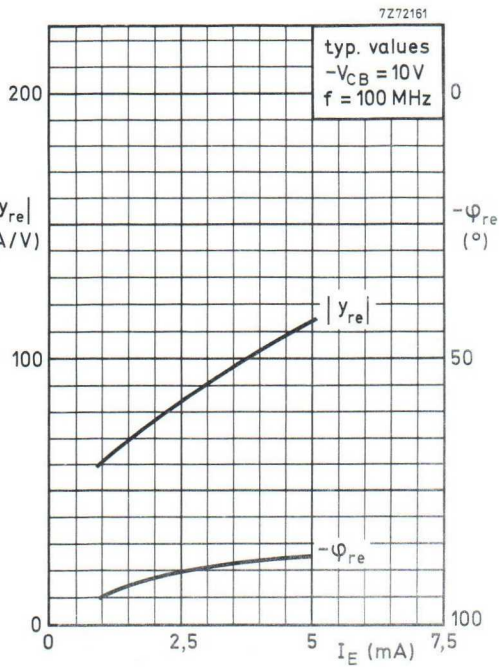


Fig. 11.

SILICON PLANAR TRANSISTORS

N-P-N transistors in a plastic SOT-23 envelope.

Primarily intended for a.m. mixers and i.f. amplifiers in a.m./f.m. receivers using SMD technology.

QUICK REFERENCE DATA

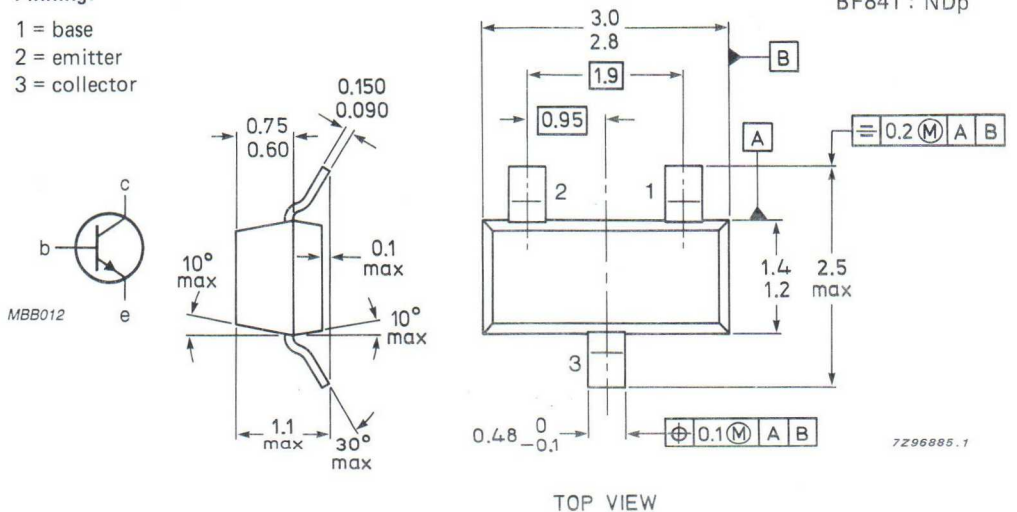
		BF840	BF841
Collector-base voltage (open emitter)	V_{CBO}	max. 40	V
Collector-emitter voltage (open base)	V_{CEO}	max. 40	V
Collector current (d.c.)	I_C	max. 25	mA
Base current	I_B	4,5–15	8–28 μ A
$I_C = 1$ mA; $V_{CE} = 10$ V			
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max. 250	mW
Junction temperature	T_j	max. 150	°C
Feedback capacitance at $f = 1$ MHz	C_{re}	typ. 0,3	pF
$I_C = 1$ mA; $V_{CE} = 10$ V			

MECHANICAL DATA

Fig. 1 SOT-23.

Pinning:

- 1 = base
- 2 = emitter
- 3 = collector



See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	40 V
Collector-emitter voltage (open base)	V_{CEO}	max.	40 V
Emitter-base voltage (open collector)	V_{EBO}	max.	4 V
Collector current (d.c.)	I_C	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}^*$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}		-65 to +150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	500 K/W
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CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0$; $V_{CB} = 20\text{ V}$

I_{CBO}	max.	100 nA
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Base-emitter voltage

$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$

V_{BE}	typ.	700 mV
		650 to 740 mV

Base current

$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$

		BF840	BF841
I_B		4,5-15	8-28 μA
f_T	typ.	380	380 MHz
C_{re}	typ.	0,3	0,3 pF
F	typ.	1,5	2,0 dB

Transition frequency at $f = 100\text{ MHz}$

$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$

Feedback capacitance at $f = 1\text{ MHz}$

$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$

Noise figure

$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$;

$f = 0,2\text{ MHz}$; $R_S = 200\text{ }\Omega$

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in u.h.f. applications in television tuners. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

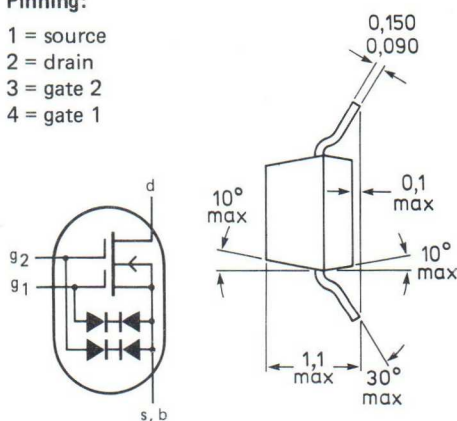
Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	20 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 7\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	12 mS
Input capacitance at gate 1; $f = 1\text{ MHz}$ $I_D = 7\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ.	1.8 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 7\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	25 fF
Noise figure at $G_S = 2\text{ mS}$; $B_S = B_S\text{ opt}$ $I_D = 7\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 800\text{ MHz}$	F	typ.	2.8 dB

MECHANICAL DATA

Fig.1 SOT143.

Pinning:

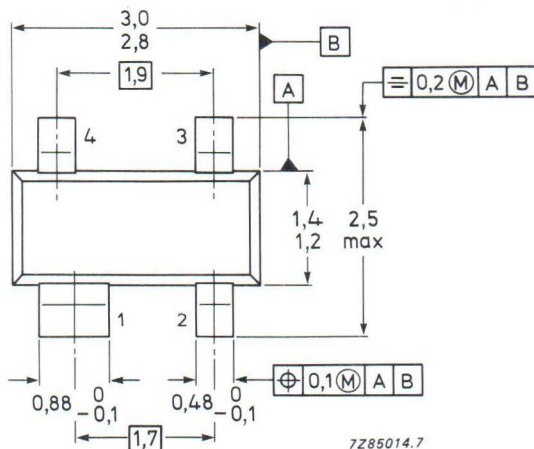
- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



Dimensions in mm

Marking code:

BF989 = MAp



7Z85014.7

TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	20 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}	—65 to + 150 $^{\circ}\text{C}$	
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)

$$R_{th\ j-a} = 460\text{ K/W}$$

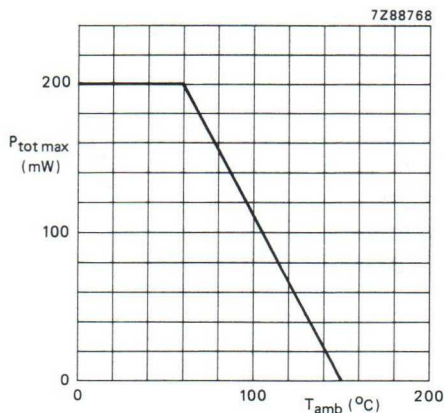


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

$\pm V_{G1-S} = 5\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS}$

max. 50 nA

$\pm V_{G2-S} = 5\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS}$

max. 50 nA

Drain current

$V_{DS} = 10\text{ V}; V_{G1-S} = 0; +V_{G2-S} = 4\text{ V}$

I_{DSS}

2 to 20 mA

Gate-source breakdown voltages

$\pm I_{G1-SS} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS}$

6 to 20 V

$\pm I_{G2-SS} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS}$

6 to 20 V

Gate-source cut-off voltages

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S}$

max. 2.7 V

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S}$

max. 2.7 V

DYNAMIC CHARACTERISTICSMeasuring conditions (common source): $I_D = 7\text{ mA}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$ Transfer admittance at $f = 1\text{ kHz}$

$|y_{fs}|$

min. 9.5 mS

typ. 12 mS

Input capacitance at gate 1; $f = 1\text{ MHz}$

C_{ig1-s}

typ. 1.8 pF

Input capacitance at gate 2; $f = 1\text{ MHz}$

C_{ig2-s}

typ. 1.0 pF

Feedback capacitance at $f = 1\text{ MHz}$

C_{rs}

typ. 25 fF

Output capacitance at $f = 1\text{ MHz}$

C_{os}

typ. 0.9 pF

Noise figure at $G_S = 2\text{ mS}; B_S = B_S\text{ opt}$

$f = 200\text{ MHz}$

F

typ. 1.6 dB

$f = 800\text{ MHz}$

F

typ. 2.8 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected, intended for UHF applications, such as UHF television tuners with 12 V supply voltage and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

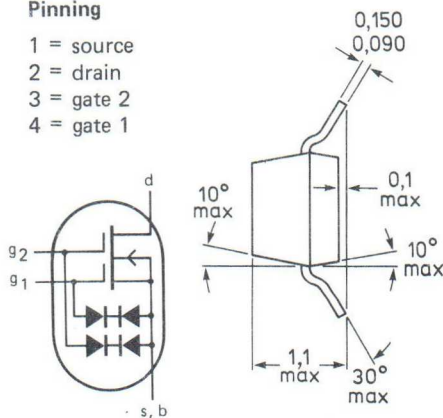
Drain-source voltage	V_{DS}	max.	18 V
Drain current	I_D	max.	30 mA
Total power dissipation up to $T_{amb} = 60^\circ\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^\circ\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	19 mS
Input capacitance at gate; $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ. max.	2.6 pF 3.0 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	25 fF
Noise figure at optimum source admittance $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 800\text{ MHz}$	F	typ. max.	2.0 dB 3.0 dB

MECHANICAL DATA

Fig.1 SOT143.

Pinning

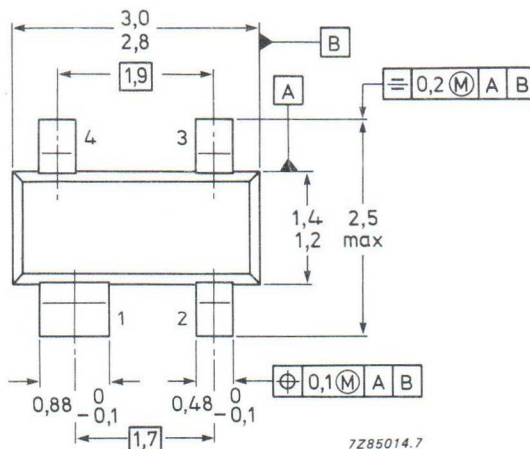
- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



Marking code

BF990A = M87

Dimensions in mm



See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	18 V
Drain current	I_D	max.	30 mA
Gate 1-source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2-source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}		-65 to +150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)	$R_{th\ j-a}$	=	460 K/W
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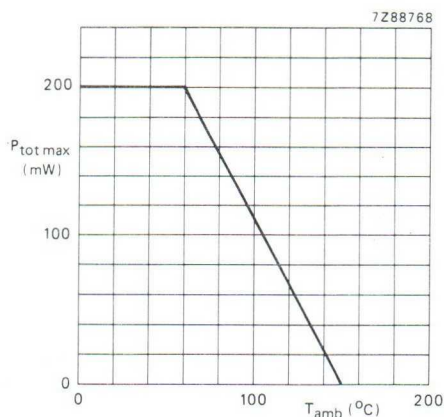


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

gate 1;

$\pm V_{G1-S} = 7\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS}$ max. 25 nA

gate 2;

$\pm V_{G2-S} = 7\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS}$ max. 25 nA

Gate-source breakdown voltages

gate 1;

$\pm I_{G1-SS} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS}$ 8 to 20 V

gate 2;

$\pm I_{G2-SS} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS}$ 8 to 20 V

Gate-source cut-off voltages

gate 1;

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S}$ max. 1.3 V

gate 2;

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S}$ max. 1.1 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 10\text{ mA}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$ Transfer admittance at $f = 1\text{ kHz}$

$|y_{fs}|$ min. 18 mS
typ. 19 mS

Input capacitance at gate 1; $f = 1\text{ MHz}$

C_{ig1-s} typ. 2.6 pF
max. 3.0 pF

Input capacitance at gate 2; $f = 1\text{ MHz}$

C_{ig2-s} typ. 1.4 pF

Feedback capacitance at $f = 1\text{ MHz}$

C_{rs} typ. 25 fF

Output capacitance at $f = 1\text{ MHz}$

C_{os} typ. 1.2 pF

Noise figure at $f = 800\text{ MHz}; G_S = 5\text{ mS}; B_S = B_S\text{ opt}$

F typ. 2.0 dB
max. 3.0 dB

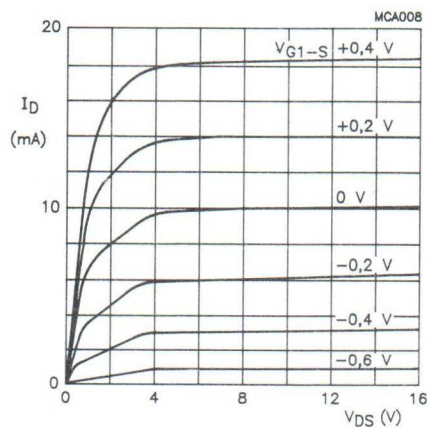


Fig.3 Output characteristics.
 $V_{G2-S} = 4 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$.

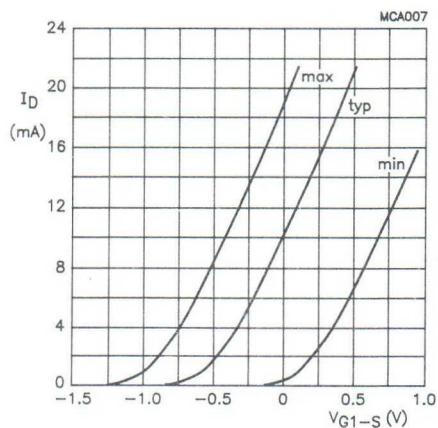


Fig.4 Transfer characteristics.
 $V_{DS} = 10 \text{ V}$; $V_{G2-S} = 4 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in v.h.f. applications, such as v.h.f. television tuners and f.m. tuners. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

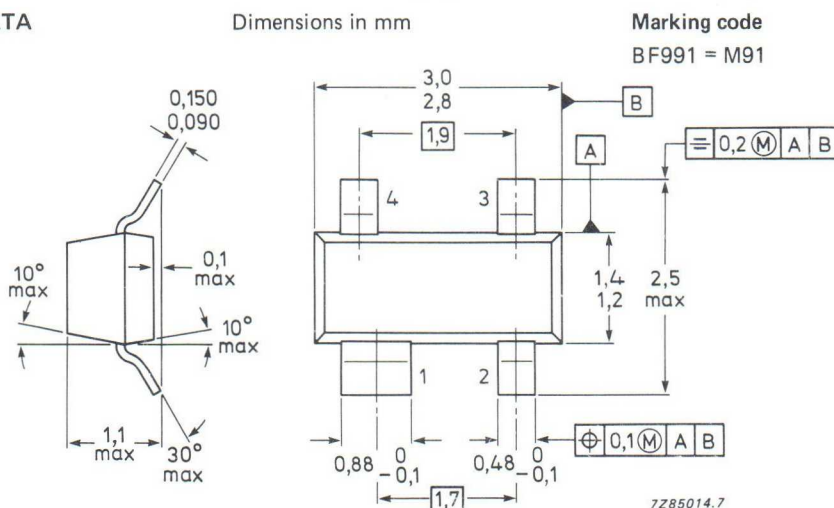
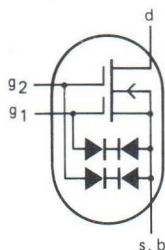
Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	20 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	14 mS
Input capacitance at gate 1; $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ.	2,1 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	20 fF
Noise figure at optimum source admittance $I_D = 10\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 200\text{ MHz}$	F	typ.	0,7 dB

MECHANICAL DATA

Fig.1 SOT143.

Pinning

- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	20 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature	T_{stg}		-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)	$R_{th\ j-a}$	=	460 K/W
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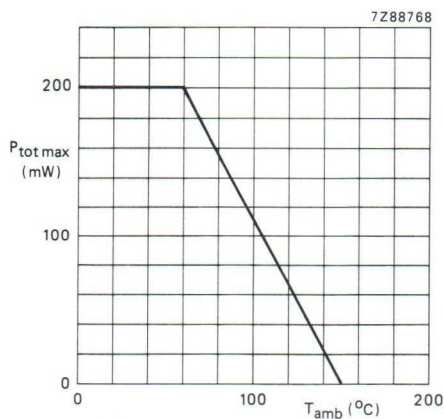


Fig.2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

$\pm V_{G1-S} = 5\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS} < 50\text{ nA}$

$\pm V_{G2-S} = 5\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS} < 50\text{ nA}$

Drain current

$V_{DS} = 10\text{ V}; V_{G1-S} = 0; +V_{G2-S} = 4\text{ V}$

$I_{DSS} \quad 4\text{ to }25\text{ mA}$

Gate-source breakdown voltages

$\pm I_{G1-SS} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS} \quad 6\text{ to }20\text{ V}$

$\pm I_{G2-SS} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS} \quad 6\text{ to }20\text{ V}$

Gate-source cut-off voltages

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S} < 2,5\text{ V}$

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S} < 2,5\text{ V}$

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 10\text{ mA}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$ Transfer admittance at $f = 1\text{ kHz}$

$|Y_{fs}| > 10\text{ mS}$

$\text{typ. } 14\text{ mS}$

Input capacitance at gate 1; $f = 1\text{ MHz}$

$C_{ig1-s} \text{ typ. } 2,1\text{ pF}$

Input capacitance at gate 2; $f = 1\text{ MHz}$

$C_{ig2-s} \text{ typ. } 1,0\text{ pF}$

Feedback capacitance at $f = 1\text{ MHz}$

$C_{rs} \text{ typ. } 20\text{ fF}$

Output capacitance at $f = 1\text{ MHz}$

$C_{os} \text{ typ. } 1,1\text{ pF}$

Noise figure

$f = 100\text{ MHz}; G_S = 1\text{ mS}; B_S = B_S \text{ opt}$

$F \text{ typ. } 0,7\text{ dB}$

$< 1,7\text{ dB}$

$f = 200\text{ MHz}; G_S = 2\text{ mS}; B_S = B_S \text{ opt}$

$F \text{ typ. } 1,0\text{ dB}$

$< 2,0\text{ dB}$

Transducer gain (note 1)

$f = 100\text{ MHz}; G_S = 1\text{ mS}; B_S = B_S \text{ opt};$

$G_L = 0,5\text{ mS}; B_L = B_L \text{ opt}$

$G_{tr} \text{ typ. } 29\text{ dB}$

$f = 200\text{ MHz}; G_S = 2\text{ mS}; B_S = B_S \text{ opt};$

$G_L = 0,5\text{ mS}; B_L = B_L \text{ opt}$

$G_{tr} \text{ typ. } 26\text{ dB}$

Note

1. Crystal mounted in a SOT103 envelope.



SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in v.h.f. applications, such as v.h.f. television tuners, FM tuners with a 12 volt supply voltage. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

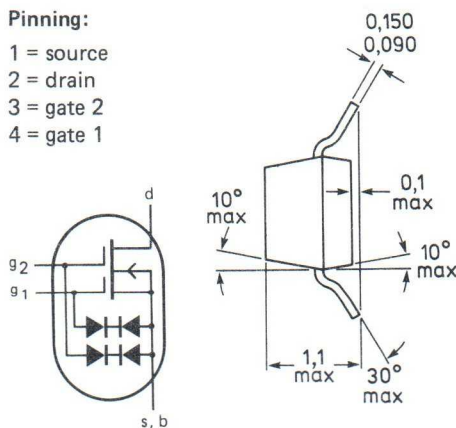
Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	40 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 15\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	25 mS
Input capacitance at gate 1; $f = 1\text{ MHz}$ $I_D = 15\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ.	4 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 15\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	30 fF
Noise figure at $G_S = 2\text{ mS}$ $I_D = 15\text{ mA}$; $V_{DS} = 10\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 200\text{ MHz}$	F	typ.	1.2 dB

MECHANICAL DATA

Fig.1 SOT143.

Pinning:

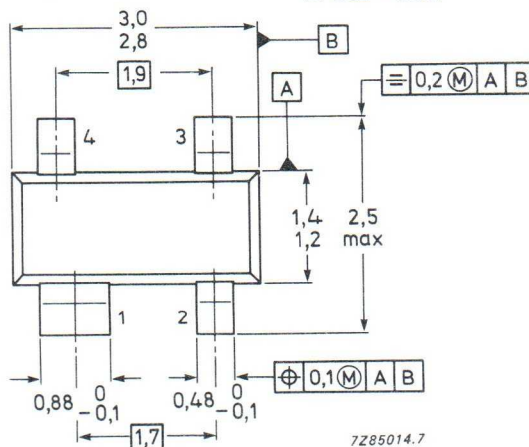
- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



Dimensions in mm

Marking code:

BF992 = M92



See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	40 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60^\circ\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}		-65 to $+150^\circ\text{C}$
Junction temperature	T_j	max.	150°C

THERMAL RESISTANCE

From junction to ambient in free air (note 1)

$$R_{th\ j-a} = 460\ \text{K/W}$$

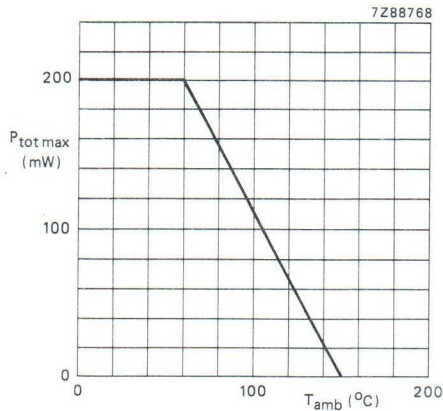


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

$\pm V_{G1-S} = 7\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS}$ max. 25 nA

$\pm V_{G2-S} = 7\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS}$ max. 25 nA

Gate-source breakdown voltages

$\pm I_{G1-SS} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS}$ 8 to 20 V

$\pm I_{G2-SS} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS}$ 8 to 20 V

Gate-source cut-off voltages

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S}$ 0.2 to 1.3 V

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 10\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S}$ 0.2 to 1.1 V

DYNAMIC CHARACTERISTICSMeasuring conditions (common source): $I_D = 15\text{ mA}; V_{DS} = 10\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$ Transfer admittance at $f = 1\text{ kHz}$

$|y_{fs}|$ min. 20 mS
typ. 25 mS

Input capacitance at gate 1; $f = 1\text{ MHz}$

C_{ig1-s} typ. 4 pF

Input capacitance at gate 2; $f = 1\text{ MHz}$

C_{ig2-s} typ. 1.7 pF

Feedback capacitance at $f = 1\text{ MHz}$

C_{rs} typ. 30 fF
max. 40 fF

Output capacitance at $f = 1\text{ MHz}$

C_{os} typ. 2 pF

Noise figure at $f = 200\text{ MHz}; G_S = 2\text{ mS}$

F typ. 1.2 dB

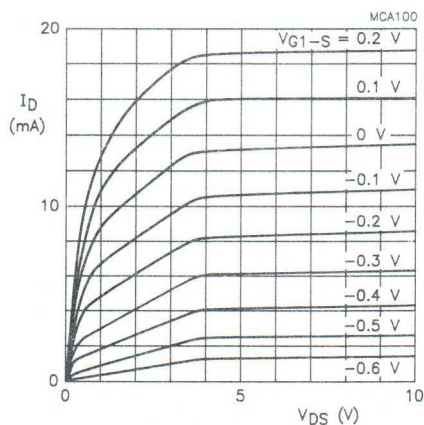


Fig.2 Output characteristics.

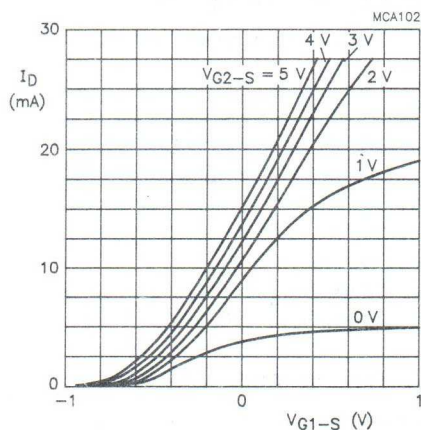


Fig.3 Transfer characteristics.

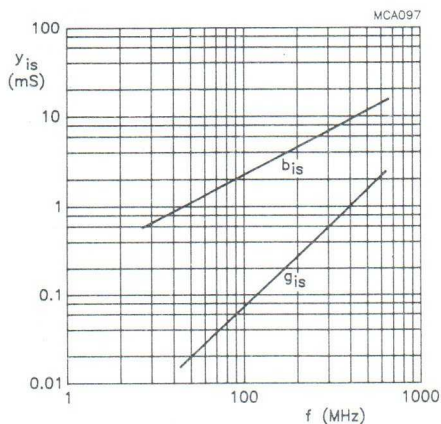


Fig.4 Input admittance as a function of frequency; $V_{DS} = 10 \text{ V}$; $V_{G2-S} = 4 \text{ V}$; $I_D = 15 \text{ mA}$; $T_{amb} = 25^\circ\text{C}$; typical values.

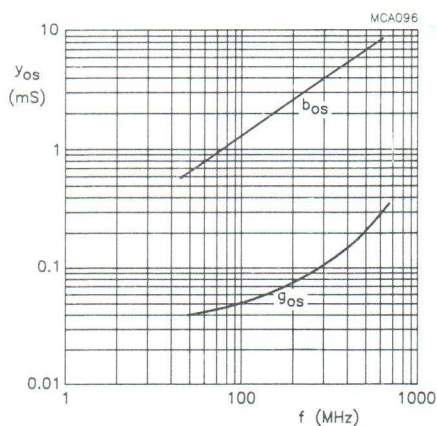


Fig.5 Output admittance as a function of frequency; $V_{DS} = 10 \text{ V}$; $V_{G2-S} = 4 \text{ V}$; $I_D = 15 \text{ mA}$; $T_{amb} = 25^\circ\text{C}$; typical values.

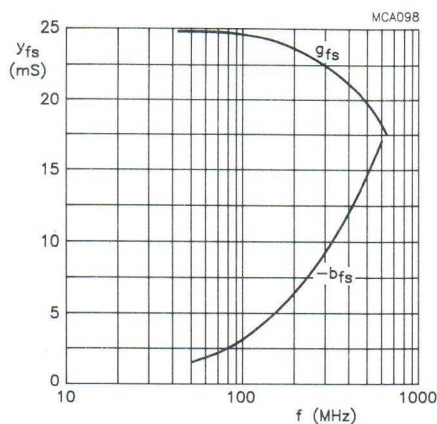


Fig.6 Transfer admittance as a function of frequency; $V_{DS} = 10$ V; $V_{G2-S} = 4$ V; $I_D = 15$ mA; $T_{amb} = 25$ °C; typical values.

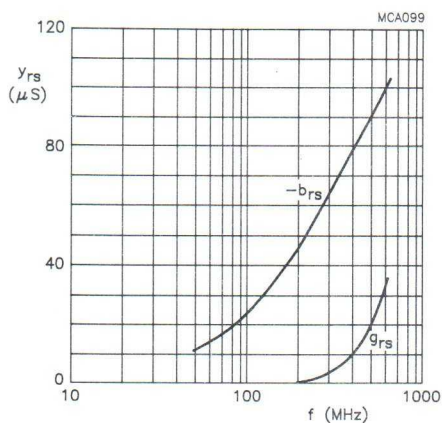


Fig.7 Feedback admittance as a function of frequency; $V_{DS} = 10$ V; $V_{G2-S} = 4$ V; $I_D = 15$ mA; $T_{amb} = 25$ °C; typical values.

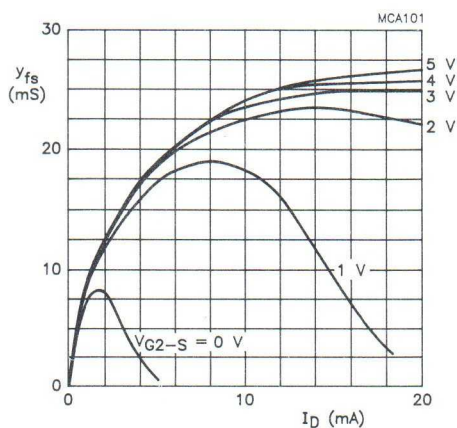


Fig.8 Transfer admittance as a function of drain current.

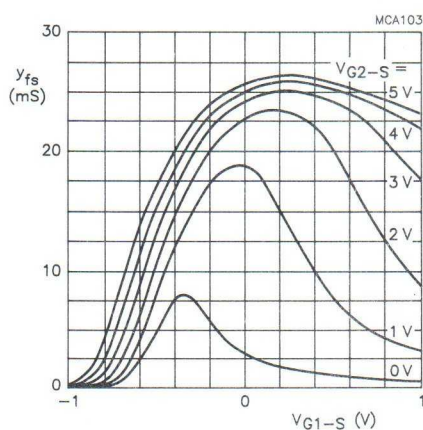


Fig.9 Transfer admittance as a function of gate 2 source voltage.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected and intended for VHF applications in television tuners.

The device is also suitable for use in professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	50 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	18 mS
Input capacitance at gate 1; $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ. max.	2.5 pF 3.0 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	25 fF
Noise figure at $G_S = 2\text{ mS}$; $B_S = B_{S\text{ opt}}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 200\text{ MHz}$	F	typ.	1.0 dB

MECHANICAL DATA

Fig.1 SOT143.

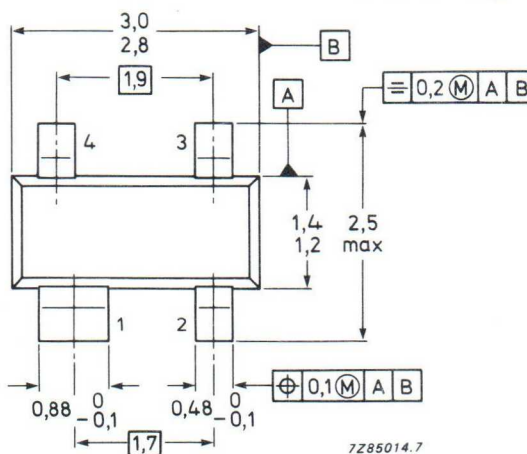
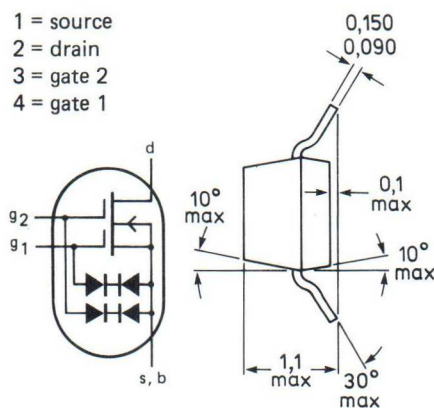
Dimensions in mm

Marking code

BF994S = MGp

Pinning

- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	50 mA
Gate 1-source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2-source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	-65 to +150 $^{\circ}\text{C}$	
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)

$$R_{th\ j-a} = 460\text{ K/W}$$

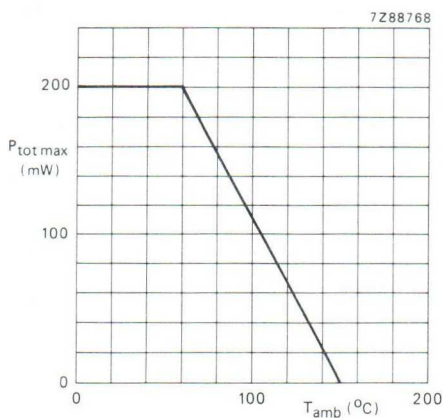


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

$\pm V_{G1-S} = 5\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS}$ max. 50 nA

$\pm V_{G2-S} = 5\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS}$ max. 50 nA

Gate-source breakdown voltages

$\pm I_{G1-S} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS}$ 6 to 20 V

$\pm I_{G2-S} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS}$ 6 to 20 V

Drain current

$V_{DS} = 15\text{ V}; V_{G1-S} = 0; V_{G2-S} = 4\text{ V}$

I_{DSS} 4 to 20 mA

Gate-source cut-off voltages

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S}$ max. 2.5 V

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S}$ max. 2.0 V

DYNAMIC CHARACTERISTICSMeasuring conditions (common source): $I_D = 10\text{ mA}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$.Transfer admittance at $f = 1\text{ kHz}$

$|y_{fs}|$ min. 15 mS
typ. 18 mS

Input capacitance at gate 1: $f = 1\text{ MHz}$

C_{ig1-s} typ. 2.5 pF
max. 3.0 pF

Input capacitance at gate 2: $f = 1\text{ MHz}$

C_{ig2-s} typ. 1.2 pF

Feedback capacitance at $f = 1\text{ MHz}$

C_{rs} typ. 25 fF

Output capacitance at $f = 1\text{ MHz}$

C_{os} typ. 1.0 pF

Noise figure at $G_S = 2\text{ mS}; B_S = B_S\text{ opt}; f = 200\text{ MHz}$

F typ. 1.0 dB

Power gain at $G_S = 2\text{ mS}; B_S = B_S\text{ opt}$

$G_L = 0.5\text{ mS}; B_L = B_L\text{ opt}; f = 200\text{ MHz}$

G_p typ. 25 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected and intended for UHF applications in television tuners.

The device is also suitable for use in professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	30 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	18 mS
Input capacitance at gate 1 : $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ. max.	2.3 pF 2.6 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	25 fF
Noise figure at $G_S = 2\text{ mS}$; $B_S = B_{S\text{ opt}}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 200\text{ MHz}$	F	typ.	1.8 dB

MECHANICAL DATA

Dimensions in mm

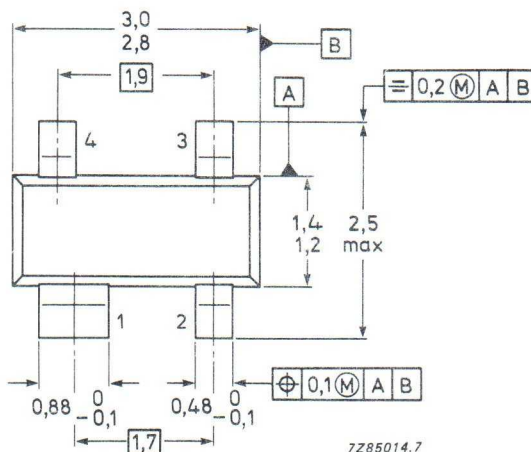
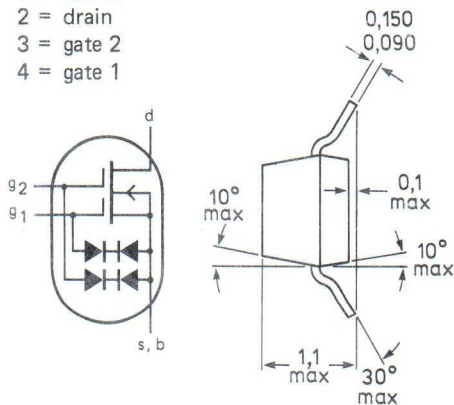
Fig.1 SOT143.

Pinning

- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1

Marking code

BF996S = MHP



See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	30 mA
Gate 1-source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2-source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}	max.	$-65\text{ to }+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)	R_{thj-a}	=	460 K/W
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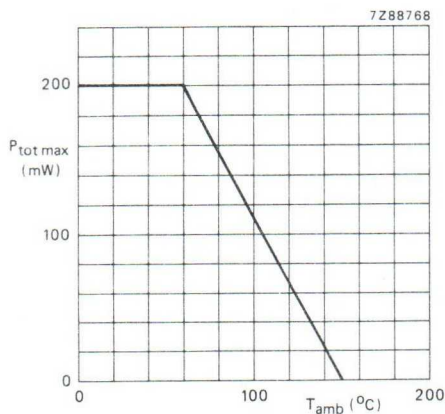


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

$\pm V_{G1-S} = 5\text{ V}; V_{G2-S} = V_{DS} = 0$

$\pm I_{G1-SS}$ max. 50 nA

$\pm V_{G2-S} = 5\text{ V}; V_{G1-S} = V_{DS} = 0$

$\pm I_{G2-SS}$ max. 50 nA

Gate-source breakdown voltages

$\pm I_{G1-S} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$

$\pm V_{(BR)G1-SS}$ 6 to 20 V

$\pm I_{G2-S} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$

$\pm V_{(BR)G2-SS}$ 6 to 20 V

Drain current

$V_{DS} = 15\text{ V}; V_{G1-S} = 0; V_{G2-S} = 4\text{ V}$

I_{DSS} 4 to 20 mA

Gate-source cut-off voltages

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}$

$-V_{(P)G1-S}$ max. 2.5 V

$I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; V_{G1-S} = 0$

$-V_{(P)G2-S}$ max. 2.0 V

DYNAMIC CHARACTERISTICSMeasuring conditions (common source): $I_D = 10\text{ mA}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$.Transfer admittance at $f = 1\text{ kHz}$

$|y_{fs}|$ min. 15 mS
typ. 18 mS

Input capacitance at gate 1: $f = 1\text{ MHz}$

C_{ig1-s} typ. 2.3 pF
max. 2.6 pF

Input capacitance at gate 2: $f = 1\text{ MHz}$

C_{ig2-s} typ. 1.2 pF

Feedback capacitance at $f = 1\text{ MHz}$

C_{rs} typ. 25 fF

Output capacitance at $f = 1\text{ MHz}$

C_{os} typ. 0.8 pF

Noise figure

$f = 200\text{ MHz}; G_S = 2\text{ mS}; B_S = B_S\text{ opt}$

F typ. 1.0 dB

$f = 800\text{ MHz}; G_S = 3.3\text{ mS}; B_S = B_S\text{ opt}$

typ. 1.8 dB

Power gain

$f = 200\text{ MHz}; G_S = 2\text{ mS}; B_S = B_S\text{ opt}; G_L = 0.5\text{ mS};$

$B_L = B_L\text{ opt}$

G_p typ. 25 dB

$f = 800\text{ MHz}; G_S = 3.3\text{ mS}; B_S = B_S\text{ opt}; G_L = 1.0\text{ mS};$

$B_L = B_L\text{ opt}$

typ. 18 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected, intended for u.h.f. and v.h.f. applications, such as u.h.f./v.h.f. television tuners and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source and has an integrated drain resistance to suppress oscillation in the frequency range higher than 1 GHz.

This device is especially intended for use in pre-amplifiers in CATV tuners with a large tuning range up to 500 MHz.

QUICK REFERENCE DATA

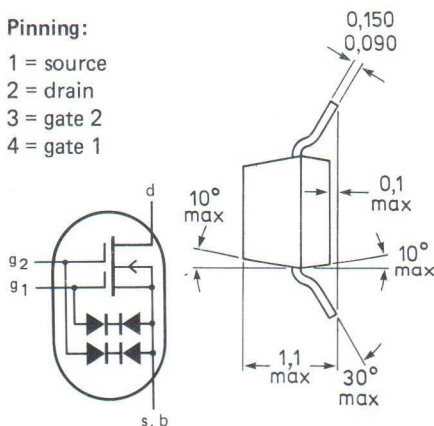
Drain-source voltage	V_{DS}	max.	20 V
Drain current	I_D	max.	30 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$	P_{tot}	max.	200 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transfer admittance at $f = 1\text{ kHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	$ y_{fs} $	typ.	18 mS
Input capacitance at gate 1; $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{ig1-s}	typ.	2.5 pF
Feedback capacitance at $f = 1\text{ MHz}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$	C_{rs}	typ.	25 fF
Noise figure at $G_S = 2\text{ mS}$; $B_S = B_S\text{ opt}$ $I_D = 10\text{ mA}$; $V_{DS} = 15\text{ V}$; $+V_{G2-S} = 4\text{ V}$; $f = 200\text{ MHz}$	F	typ.	1.0 dB

MECHANICAL DATA

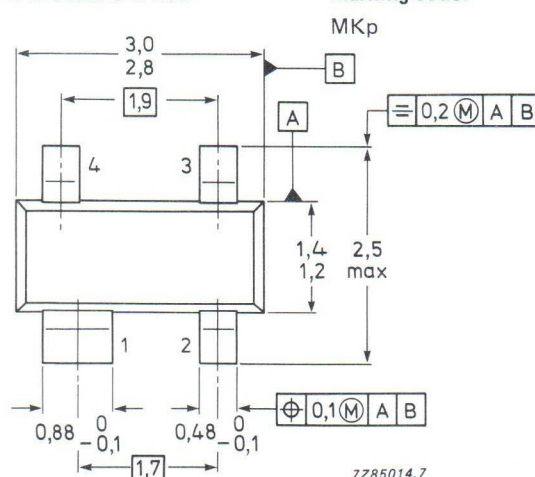
Fig.1 SOT143.

Pinning:

- 1 = source
- 2 = drain
- 3 = gate 2
- 4 = gate 1



Dimensions in mm



7Z85014.7

See also *Soldering recommendations*.

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (DC or average)	I_D	max.	30 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}	max.	-65 to $+150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient in free air (note 1)

$$R_{th\ j-a} = 460\text{ K/W}$$

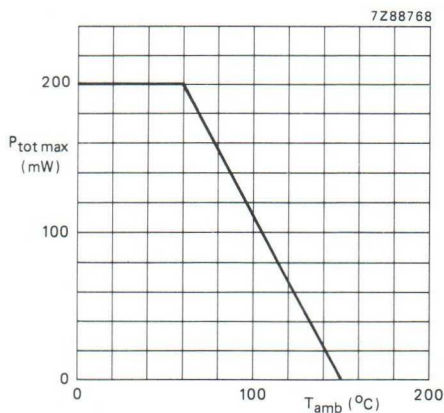


Fig. 2 Power derating curve.

Note

1. Device mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm.

STATIC CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Gate cut-off currents

gate 1;

 $\pm V_{G1-S} = 5\text{ V}; V_{G2-S} = V_{DS} = 0$ $\pm I_{G1-SS}$ max. 50 nA

gate 2;

 $\pm V_{G2-S} = 5\text{ V}; V_{G1-S} = V_{DS} = 0$ $\pm I_{G2-SS}$ max. 50 nA

Gate-source breakdown voltages

gate 1;

 $\pm I_{G1-SS} = 10\text{ mA}; V_{G2-S} = V_{DS} = 0$ $\pm V_{(BR)G1-SS}$ 6 to 20 V

gate 2;

 $\pm I_{G2-SS} = 10\text{ mA}; V_{G1-S} = V_{DS} = 0$ $\pm V_{(BR)G2-SS}$ 6 to 20 V

Gate-source cut-off voltages

gate 1;

 $I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}$ $-V_{(P)G1-S}$ max. 2.5 V

gate 2;

 $I_D = 20\text{ }\mu\text{A}; V_{DS} = 15\text{ V}; V_{G1-S} = 0$ $-V_{(P)G2-S}$ max. 2.0 V

Drain-source cut-off voltage

 $V_{DS} = 15\text{ V}; V_{G2-S} = 4\text{ V}; V_{G1-S} = 0$ I_{DSS} 2 to 20 mA**DYNAMIC CHARACTERISTICS**Measuring conditions (common source): $I_D = 10\text{ mA}; V_{DS} = 15\text{ V}; +V_{G2-S} = 4\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$ Transfer admittance at $f = 1\text{ kHz}$ $|y_{fs}|$ min. 15 mS
typ. 18 mSInput capacitance at gate 1; $f = 1\text{ MHz}$ C_{ig1-s} typ. 2.5 pFInput capacitance at gate 2; $f = 1\text{ MHz}$ C_{ig2-s} typ. 1.2 pFFeedback capacitance at $f = 1\text{ MHz}$ C_{rs} typ. 25 fFOutput capacitance at $f = 1\text{ MHz}$ C_{os} typ. 1.0 pFNoise figure at $f = 200\text{ MHz}; G_S = 2\text{ mS}; B_S = B_S\text{ opt}$ F typ. 1.0 dBPower gain at $G_S = 2\text{ mS}; B_S = B_S\text{ opt}$ $G_L = 0.5\text{ mS}; B_L = B_L\text{ opt}; f = 200\text{ MHz}$ G_p typ. 25 dB

Data sheet	
status	Preliminary specification
date of issue	April 1991

BF998

Silicon n-channel dual gate MOS-FET

FEATURES

- Short channel transistor with high ratio $|Y_{fs}|/C_{is}$.
- Low noise gain controlled amplifier to 1 GHz.

DESCRIPTION

Depletion type field-effect transistor in a plastic SOT143 microminiature envelope with source and substrate interconnected, intended for VHF and UHF applications, such as television tuners, with 12 V supply voltage and professional communication equipment. This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage	-	12	V
I_D	drain current	-	30	mA
P_{tot}	total power dissipation	-	200	mW
T_j	junction temperature	-	150	°C
$ Y_{fs} $	transfer admittance	24	-	mS
C_{ig1-s}	input capacitance at gate 1	2.1	-	pF
C_{rs}	feedback capacitance	25	-	fF
F	noise figure at 800 MHz	1	-	dB

Silicon n-channel dual gate MOS-FET

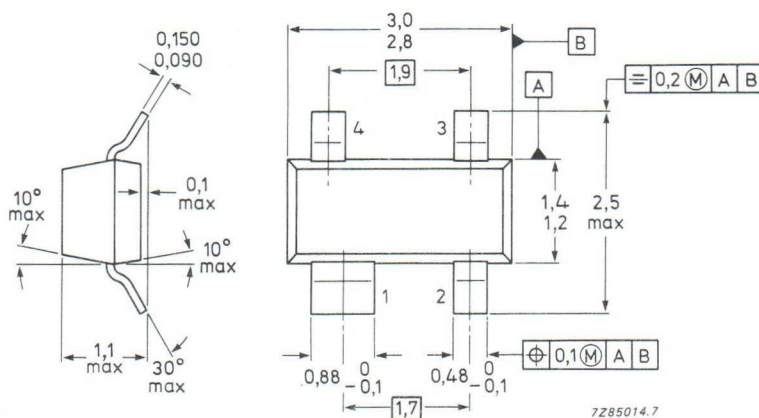
BF998

MECHANICAL DATA

Dimensions in mm

Marking code

BF998 = MOp



TOP VIEW

See also soldering recommendations.

Fig.1 SOT143.

PIN CONFIGURATION

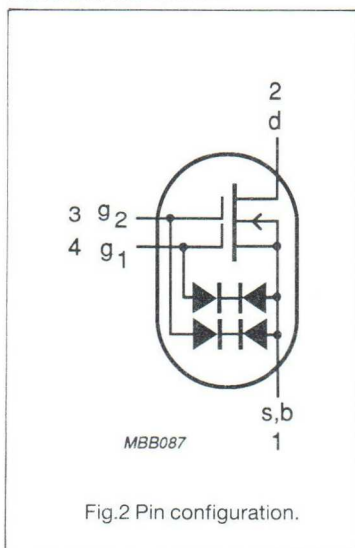


Fig.2 Pin configuration.

PINNING

PIN	DESCRIPTION
1	source
2	drain
3	gate 2
4	gate 1

Silicon n-channel dual gate MOS-FET

BF998

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

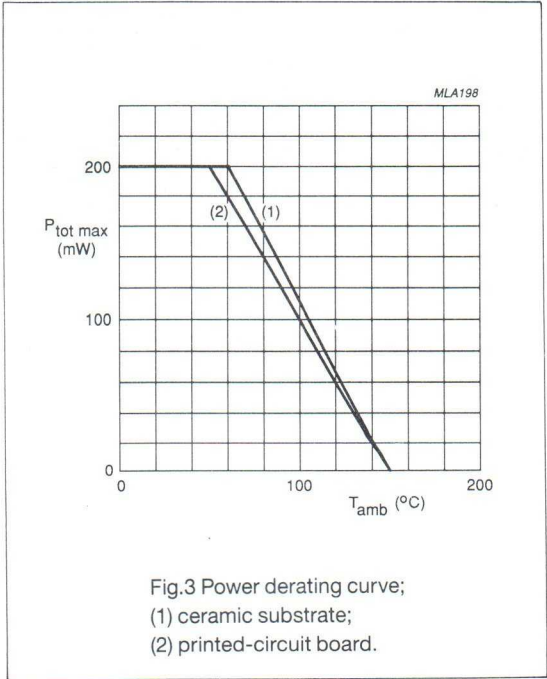
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		-	12	V
I_D	drain current (DC or average)		-	30	mA
$\pm I_{G1-S}$	gate 1-source current		-	10	mA
$\pm I_{G2-S}$	gate 2-source current		-	10	mA
P_{tot}	total power dissipation	$T_{amb} = 60\text{ }^{\circ}\text{C}$ (note 1)	-	200	mW
P_{tot}	total power dissipation	$T_{amb} = 50\text{ }^{\circ}\text{C}$ (note 2)	-	200	mW
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	from junction to ambient in free air (note 1)	460	K/W
$R_{th\ j-a}$	from junction to ambient in free air (note 2)	500	K/W

Notes

- 1. Device mounted on a ceramic substrate, 8 mm x 10 mm x 0.7 mm.
- 2. Device mounted on printed circuit board.



Silicon n-channel dual gate MOS-FET**BF998****STATIC CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$\pm I_{G1-SS}$	gate 1 cut-off current	$\pm V_{G1-S} = 5\text{ V}$ $V_{G2-S} = V_{DS} = 0$	-	50	nA
$\pm I_{G2-SS}$	gate 2 cut-off current	$\pm V_{G2-S} = 5\text{ V}$ $V_{G1-S} = V_{DS} = 0$	-	50	nA
$\pm V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$\pm I_{G1-SS} = 10\text{ mA}$ $V_{G2-S} = V_{DS} = 0$	6	20	V
$\pm V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$\pm I_{G2-SS} = 10\text{ mA}$ $V_{G1-S} = V_{DS} = 0$	6	20	V
$-V_{(P)G1-S}$	gate 1-source cut-off voltage	$I_D = 20\text{ }\mu\text{A}$ $V_{DS} = 8\text{ V}$ $+V_{G2-S} = 4\text{ V}$	-	2.5	V
$-V_{(P)G2-S}$	gate 2-source cut-off voltage	$I_D = 20\text{ }\mu\text{A}$ $V_{DS} = 8\text{ V}$ $V_{G1-S} = 0$	-	2.0	V
I_{DSS}	drain current (measured under pulse condition)	$V_{DS} = 8\text{ V}$ $V_{G1-S} = 0$ $+V_{G2-S} = 4\text{ V}$	2	18	mA

DYNAMIC CHARACTERISTICSMeasuring conditions (common source) $I_D = 10\text{ mA}$; $V_{DS} = 8\text{ V}$; $V_{G2-S} = 4\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ Y_{fs} $	transfer admittance	$f = 1\text{ kHz}$	21	24	-	mS
C_{ig1-s}	input capacitance at gate 1	$f = 1\text{ MHz}$	-	2.1	2.5	pF
C_{os}	output capacitance	$f = 1\text{ MHz}$	-	1.05	-	pF
C_{rs}	feedback capacitance	$f = 1\text{ MHz}$	-	25	-	fF
C_{ig2-s}	input capacitance at gate 2	$f = 1\text{ MHz}$	-	1.2	-	pF
F	noise figure	$f = 200\text{ MHz}$ $G_s = 2\text{ mS}$ $B_s = B_{s\text{opt}}$	-	0.6	-	dB
F	noise figure	$f = 800\text{ MHz}$ $G_s = 3.3\text{ mS}$ $B_s = B_{s\text{opt}}$	-	1	-	dB

Silicon n-channel dual gate MOS-FET

BF998

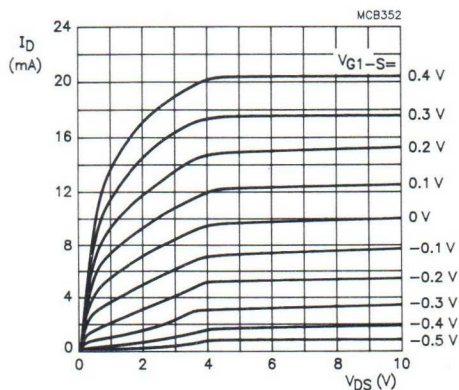


Fig.4 Output characteristics; $V_{G2-S} = 4$ V;
 $T_{amb} = 25$ °C.

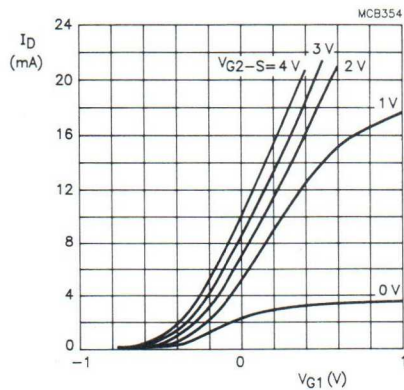


Fig.5 Transfer characteristics; $V_{DS} = 8$ V;
 $T_{amb} = 25$ °C.

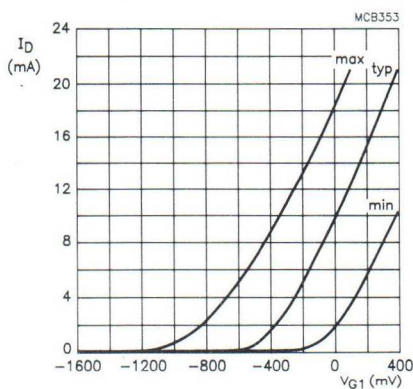


Fig.6 Drain current as a function of gate 1 voltage;
 $V_{DS} = 8$ V; $V_{G2-S} = 4$ V; $T_{amb} = 25$ °C.

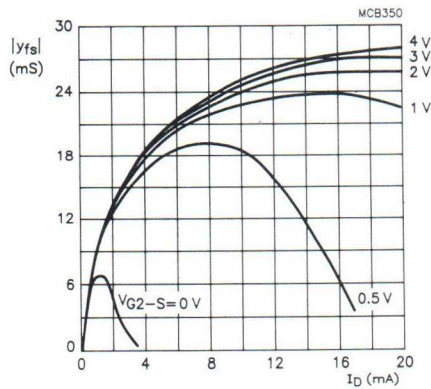


Fig.7 Transfer admittance as a function of drain
current; $V_{DS} = 8$ V; $T_{amb} = 25$ °C.

Silicon n-channel dual gate MOS-FET

BF998

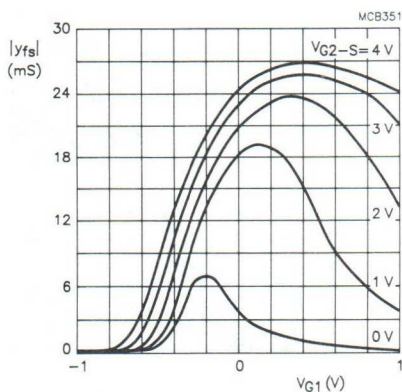


Fig.8 Transfer admittance as a function of gate 1 voltage; $V_{DS} = 8$ V; $T_{amb} = 25$ °C.

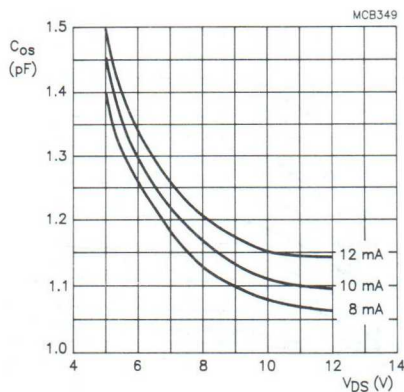


Fig.9 Output capacitance as a function of drain-source voltage; $V_{G2-S} = 4$ V; $f = 1$ MHz; $T_{amb} = 25$ °C.

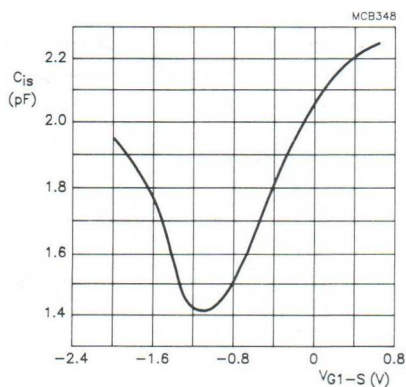


Fig.10 Gate 1 input capacitance as a function of gate 1-source voltage; $V_{DS} = 8$ V; $V_{G2-S} = 4$ V; $f = 1$ MHz; $T_{amb} = 25$ °C.

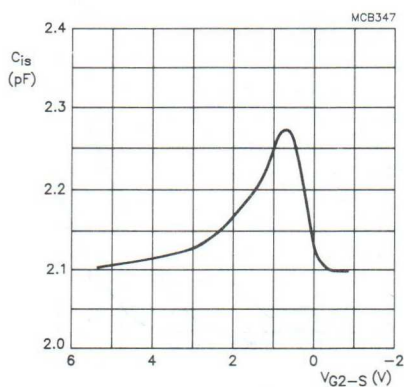


Fig.11 Gate 1 input capacitance as a function of gate 2-source voltage; $V_{DS} = 8$ V; $V_{G1-S} = 0$; $f = 1$ MHz; $T_{amb} = 25$ °C.

Silicon n-channel dual gate MOS-FET

BF998

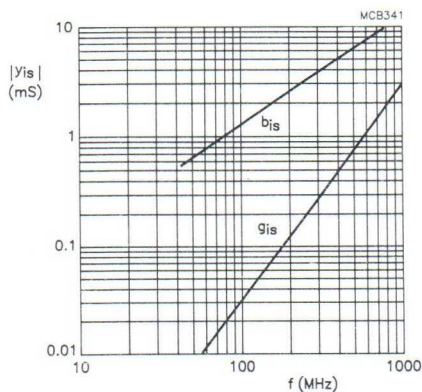


Fig. 12 Input admittance as a function of frequency; $V_{DS} = 8\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

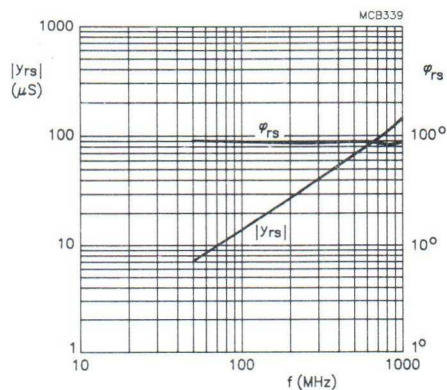


Fig. 13 Feedback admittance as a function of frequency; $V_{DS} = 8\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

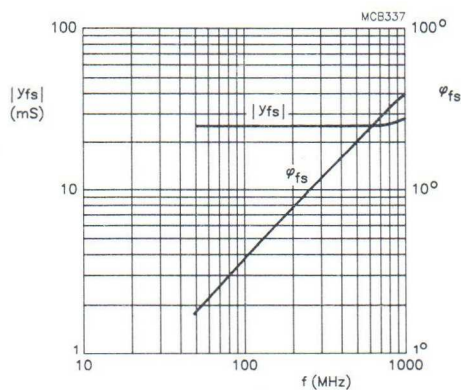


Fig. 14 Transfer admittance as a function of frequency; $V_{DS} = 8\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

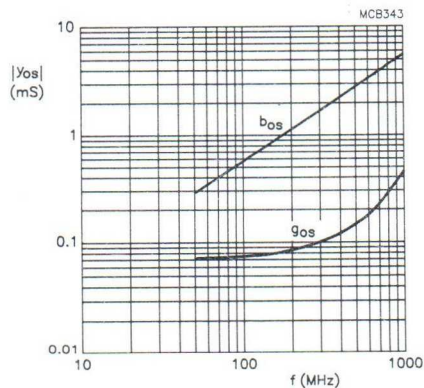
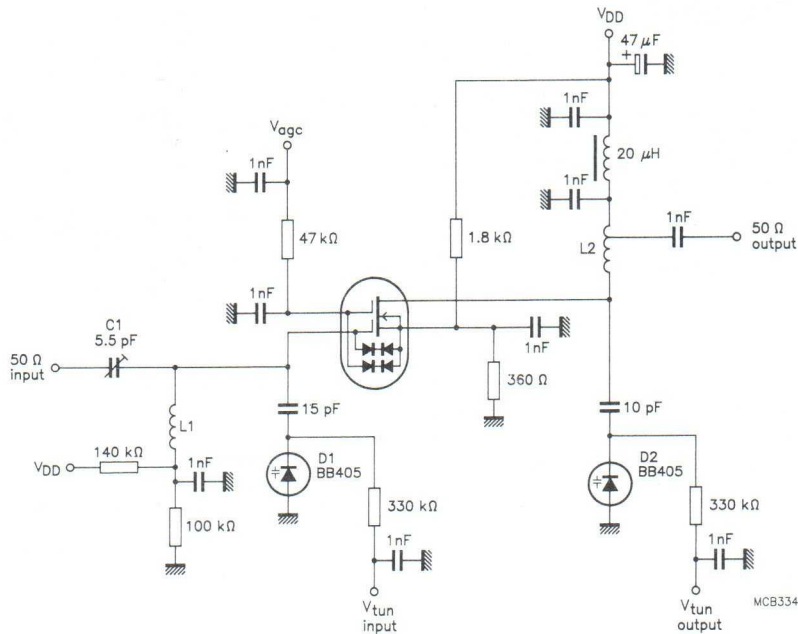


Fig. 15 Output admittance as a function of frequency; $V_{DS} = 8\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 10\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Silicon n-channel dual gate MOS-FET

BF998



$L1 = 45 \text{ nH}$, 4 turns, internal diameter 4 mm, 0.8 mm copper wire.

$L2 = 160 \text{ nH}$, 3 turns, internal diameter 8 mm, 0.8 mm copper wire.

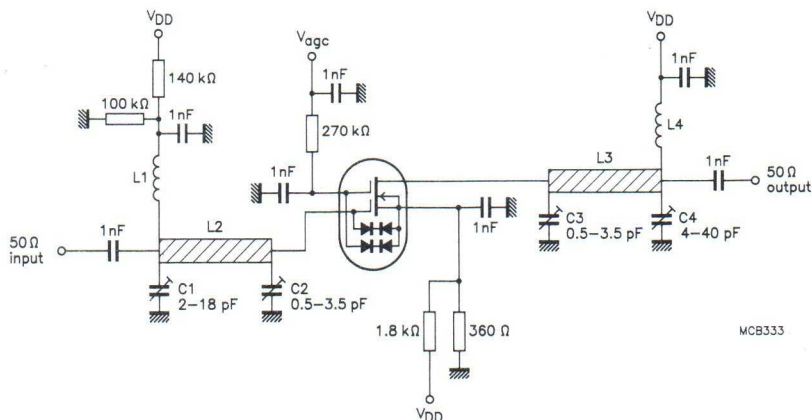
Tapped at approximately half a turn from the cold side, to adjust $G_L = 0.5 \text{ mS}$.

$C1$ adjusted for $G_S = 2 \text{ mS}$.

Fig.16 Gain control test circuit at $f = 200 \text{ MHz}$; $V_{DD} = 12 \text{ V}$; $G_S = 2 \text{ mS}$; $G_L = 0.5 \text{ mS}$.

Silicon n-channel dual gate MOS-FET

BF998



$L1 = L4 = 11$ turns, internal diameter 3 mm, 0.5 mm copper wire, without spacing; ≈ 200 nH.

$L2 = 2$ cm, silvered 0.8 mm copper wire, 4 mm above ground plane.

$L3 = 2$ cm, silvered 0.5 mm copper wire, 4 mm above ground plane.

Fig.17 Gain control test circuit at $f = 800$ MHz; $V_{DD} = 12$ V; $G_S = 3.3$ mS; $G_L = 1$ mS.

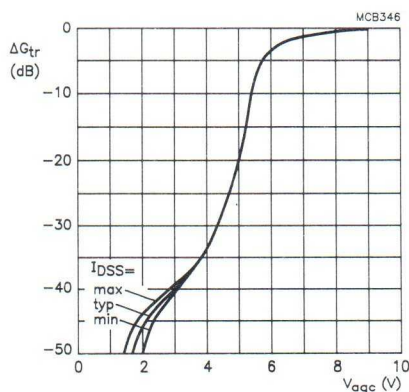


Fig.18 Automatic gain control characteristics measured in circuit of Fig.16; $V_{DD} = 12$ V; $f = 200$ MHz; $T_{amb} = 25$ °C.

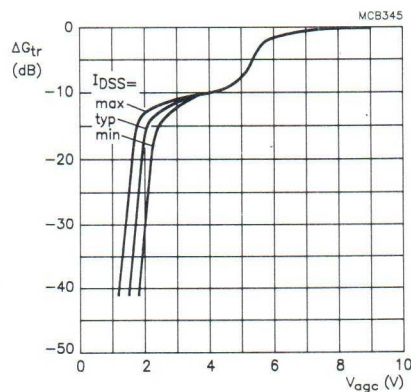
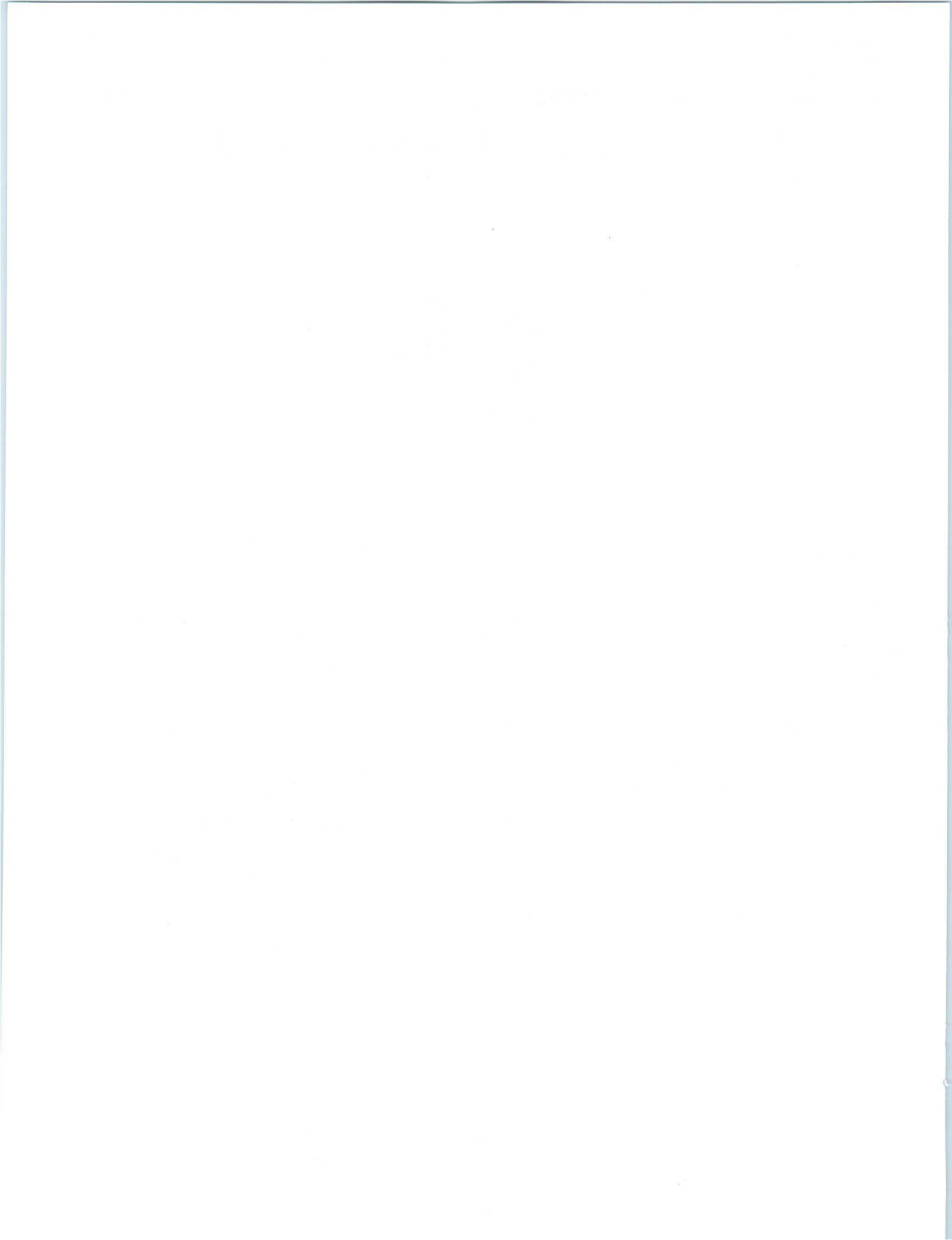


Fig.19 Automatic gain control characteristics measured in circuit of Fig.17; $V_{DD} = 12$ V; $f = 800$ MHz; $T_{amb} = 25$ °C.



Philips Components

Data sheet	
status	Product specification
date of issue	April 1991

BFG16A

NPN 1 GHz wideband transistor

DESCRIPTION

NPN transistor primarily intended for wideband amplifier, aerial amplifiers and vertical amplifiers in high speed oscilloscopes.

The BFG16A is mounted in a SOT223 plastic envelope.

FEATURES

- High power gain
- Good thermal stability
- Gold metallization ensures excellent reliability.

MECHANICAL DATA

Plastic SOT223 envelope

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-	40	V
V_{CEO}	collector-emitter voltage	open base	-	-	25	V
I_C	collector current (DC)		-	-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$; (note 1)	-	-	1	W
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
h_{FE}	DC current gain	$I_C = 150\text{ mA}$; $V_{CE} = 5\text{ V}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	1.5	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	-	10	-	dB

Note

1. T_{case} temperature measured on soldering point of collector tab.

ORDERING AND PACKAGE INFORMATION

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG16A	SOT223	bulk	500
BFG16A	SOT223	12 mm REEL	1000

NPN 1 GHz wideband transistor**BFG16A****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CB0}	collector-base voltage	open emitter	-	40	V
V_{CE0}	collector-emitter voltage	open base	-	25	V
V_{EB0}	emitter-base voltage	open collector	-	2	V
I_C	collector current (DC)		-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	MAX.	UNIT
$R_{th\ j-c}$	from junction to case.	40	K/W

CHARACTERISTICS $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter $I_C = 0.1\text{ mA}$	25	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base $I_C = 10\text{ mA}$	18	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector $I_E = 0.1\text{ mA}$	3	-	-	V
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 28\text{ V}$	-	-	20	μA
h_{FE}	DC current gain	$I_C = 50\text{ mA}$ / 150 mA; $V_{CE} = 5\text{ V}$	25	-	-	
C_c	collector capacitance	$f = 1\text{ MHz}$; $I_E = i_e = 0$; $V_{CB} = 10\text{ V}$	-	2.5	-	pF
C_e	emitter capacitance	$f = 1\text{ MHz}$; $I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$	-	10.0	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0\text{ mA}$; $V_{CB} = 10\text{ V}$	-	1.8	-	pF
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	1.5	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	10	-	dB

NPN 1 GHz wideband transistor

BFG16A

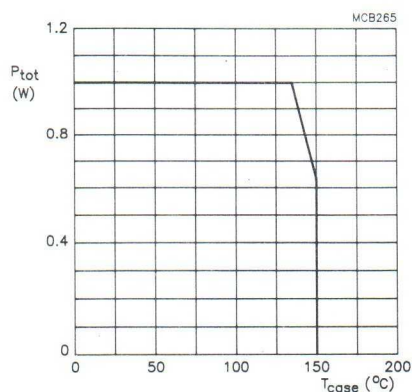
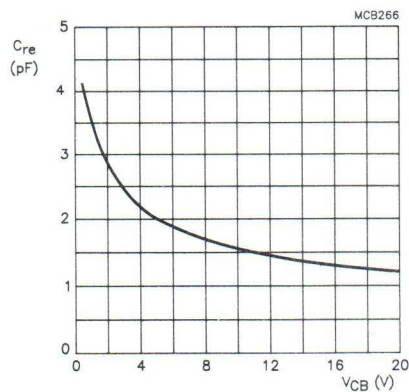
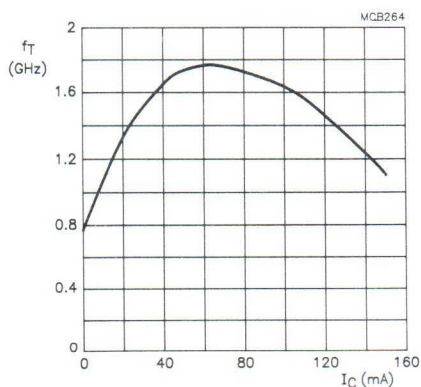
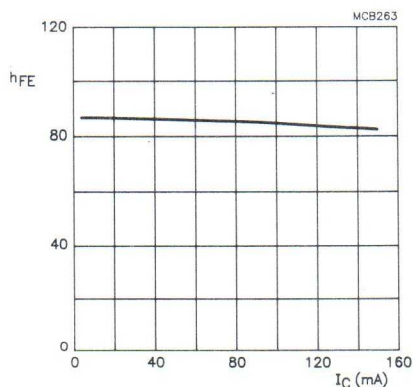


Fig.1 Power derating curve.

Fig.2 Feedback capacitance as function of collector-base voltage; $I_C = I_C = 0$; $f = 1$ MHz.Fig.3 Transition frequency as function of collector current; $V_{CE} = 10$ V; $f = 500$ MHz.Fig.4 Current gain as function of collector current; $V_{CE} = 10$ V.

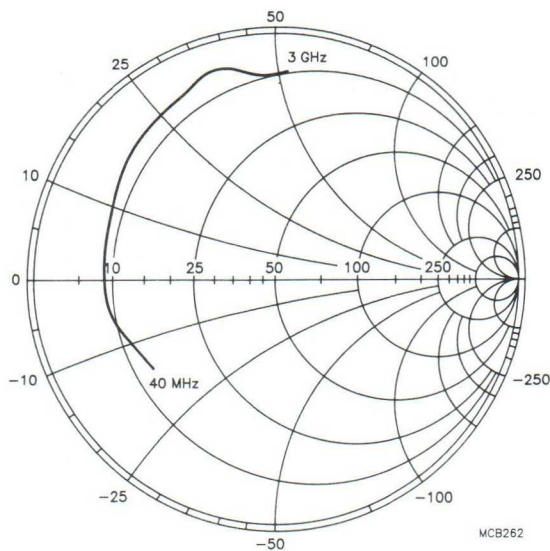
NPN 1 GHz wideband transistor**BFG16A**

Fig.5 Common emitter input reflection coefficient, S_{11} ; $V_{CE} = 15$ V; $I_C = 70$ mA.

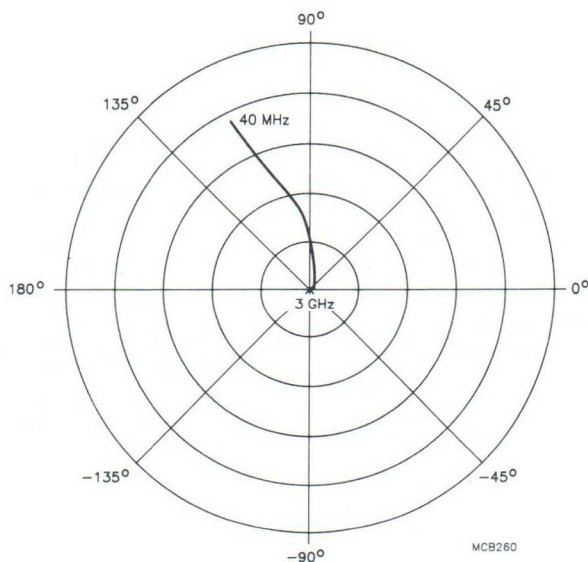


Fig.6 Common emitter forward transmission coefficient, S_{21} ; $V_{CE} = 15$ V; $I_C = 70$ mA.

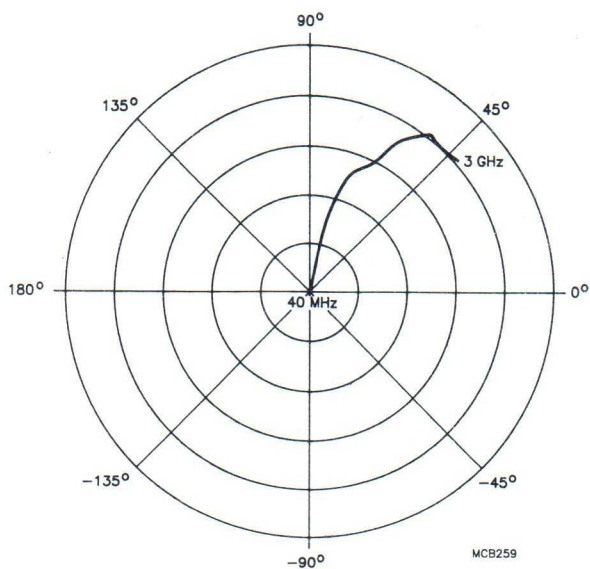
NPN 1 GHz wideband transistor**BFG16A**

Fig.7 Common emitter reverse transmission coefficient, S_{12} ; $V_{CE} = 15$ V; $I_C = 70$ mA.

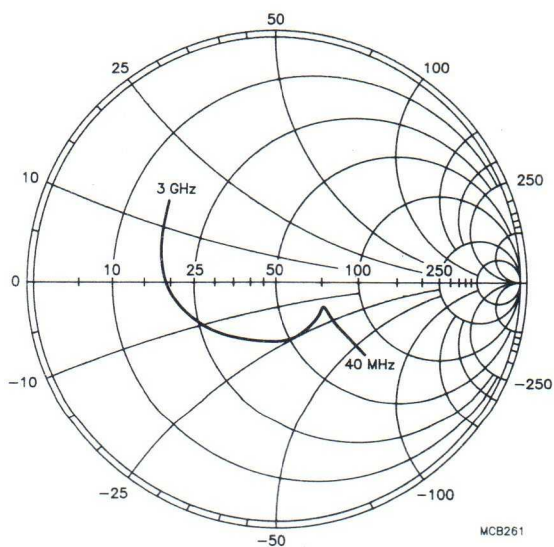


Fig.8 Common emitter output transmission coefficient, S_{22} ; $V_{CE} = 15$ V; $I_C = 70$ mA.

NPN 1 GHz wideband transistor**BFG16A****S-Parameters (common-emitter) at $V_{CE} = 15\text{ V}$; $I_C = 70\text{ mA}$; typical values.**

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{UM} (dB)
	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	
40	.622	-144.5	36.80	113.9	.011	50.6	.465	- 41.8	34.51
100	.679	-167.0	16.10	96.5	.016	57.8	.278	- 36.4	27.23
200	.694	-177.9	8.24	85.9	.026	67.8	.230	- 29.4	21.42
300	.699	176.7	5.54	79.1	.038	71.3	.220	- 29.1	18.01
400	.707	172.6	4.15	73.1	.049	73.4	.218	- 31.4	15.60
500	.710	168.6	3.32	67.9	.060	74.2	.218	- 35.0	13.69
600	.714	164.9	2.79	62.8	.071	75.8	.219	- 39.8	12.23
700	.721	161.5	2.39	58.0	.082	76.0	.221	- 45.2	10.98
800	.726	157.9	2.10	53.5	.093	76.1	.222	- 51.8	9.95
900	.733	154.2	1.88	49.1	.105	76.0	.226	- 58.6	9.08
1000	.740	150.6	1.70	44.9	.116	75.9	.229	- 66.0	8.34
1200	.760	144.2	1.42	36.6	.140	76.9	.240	- 81.7	7.06
1400	.778	137.8	1.20	29.2	.171	75.7	.258	- 98.1	5.97
1600	.786	132.2	1.04	21.7	.199	74.0	.281	-115.1	4.88
1800	.795	124.4	.92	15.1	.230	72.4	.309	-132.0	4.11
2000	.820	118.0	.82	9.5	.270	69.0	.346	-148.4	3.67

S-Parameters (common-emitter) at $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; typical values.

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{UM} (dB)
	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	
40	.656	-157.2	34.60	109.7	.009	52.0	.376	- 51.1	33.90
100	.709	-172.5	14.80	94.4	.016	63.2	.201	- 46.9	26.64
200	.718	179.3	7.49	84.6	.028	71.6	.154	- 39.2	20.76
300	.729	174.6	5.03	77.9	.041	73.9	.145	- 38.3	17.43
400	.733	170.7	3.78	71.9	.053	75.2	.143	- 41.0	14.99
500	.736	167.4	3.01	66.6	.065	75.5	.144	- 45.3	13.08
600	.742	163.6	2.52	61.7	.077	76.1	.146	- 51.2	11.63
700	.745	160.1	2.18	56.5	.089	75.9	.150	- 58.3	10.40
800	.751	156.7	1.91	52.1	.101	75.7	.154	- 66.4	9.35
900	.757	152.8	1.71	47.7	.114	75.3	.161	- 74.8	8.51
1000	.764	149.5	1.55	43.3	.126	75.0	.169	- 83.9	7.77
1200	.781	142.8	1.28	35.3	.152	75.2	.190	-101.6	6.46
1400	.798	136.7	1.09	28.2	.184	73.4	.219	-118.9	5.43
1600	.804	130.6	.94	21.4	.213	71.1	.252	-135.6	4.34
1800	.809	123.4	.83	14.8	.244	69.1	.291	-151.4	3.48
2000	.832	116.7	.74	9.6	.284	65.4	.340	-166.2	3.05

NPN 1 GHz wideband transistor

BFG16A

S-Parameters (common-emitter) at $V_{CE} = 10\text{ V}$; $I_C = 70\text{ mA}$; typical values.

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{um} (dB)
	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	
40	.644	-150.5	35.00	112.5	.011	50.8	.417	- 51.5	34.06
100	.700	-169.8	15.20	95.7	.017	58.0	.218	- 50.4	26.81
200	.715	-179.5	7.75	85.5	.028	68.1	.157	- 43.2	21.01
300	.721	175.4	5.21	78.6	.041	71.7	.145	- 41.7	17.62
400	.725	171.5	3.91	72.7	.053	73.7	.141	- 43.9	15.17
500	.731	167.8	3.12	67.4	.065	74.2	.141	- 47.9	13.31
600	.734	163.9	2.62	62.2	.077	75.0	.143	- 53.6	11.83
700	.740	160.6	2.25	57.3	.090	75.1	.146	- 60.4	10.61
800	.743	157.2	1.98	52.8	.101	74.7	.152	- 68.0	9.57
900	.748	153.4	1.78	48.5	.114	74.5	.158	- 76.2	8.69
1000	.758	149.9	1.61	44.2	.126	74.2	.166	- 85.0	7.96
1200	.776	143.2	1.34	35.9	.151	74.5	.188	-102.5	6.73
1400	.791	137.2	1.13	28.6	.183	72.8	.218	-119.2	5.61
1600	.794	131.0	.98	21.7	.213	70.7	.253	-135.7	4.51
1800	.804	123.8	.87	15.1	.243	68.9	.293	-151.2	3.72
2000	.827	117.0	.76	10.1	.282	65.2	.342	-166.0	3.26

S-Parameters (common-emitter) at $V_{CE} = 5\text{ V}$; $I_C = 150\text{ mA}$; typical values.

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{um} (dB)
	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	M (rat)	ϕ (deg)	
40	.791	-172.2	16.70	104.0	.009	53.8	.178	- 80.7	28.87
100	.810	-179.6	7.15	94.4	.017	67.4	.100	- 99.1	21.78
200	.815	175.1	3.77	86.1	.031	75.1	.088	-114.9	16.32
300	.818	171.1	2.62	78.8	.047	76.2	.094	-123.8	13.23
400	.824	167.7	2.00	72.3	.061	77.0	.105	-130.3	11.02
500	.821	164.1	1.62	66.4	.076	76.8	.117	-135.8	9.14
600	.826	160.1	1.37	61.0	.091	76.9	.132	-141.0	7.85
700	.826	156.5	1.20	55.5	.106	76.2	.149	-145.8	6.68
800	.828	153.0	1.06	50.9	.122	75.0	.167	-150.6	5.72
900	.833	149.2	.96	46.4	.138	74.0	.186	-155.2	5.02
1000	.840	145.6	.88	42.2	.151	72.7	.207	-159.9	4.41
1200	.845	138.7	.74	35.4	.183	71.1	.248	-169.2	3.17
1400	.853	132.5	.64	29.9	.219	67.6	.293	-178.4	2.25
1600	.845	126.1	.56	25.3	.249	63.8	.339	171.9	1.08
1800	.844	119.2	.51	20.8	.278	60.6	.382	162.6	.30
2000	.856	112.5	.47	18.7	.315	56.2	.429	153.4	.21

NPN 2 GHz WIDEBAND TRANSISTOR

BFG17A is a npn wideband transistor in a microminature SOT143 envelope with double emitter bonding. The device contains a BFW92A crystal. This transistor is intended for use in wideband (40 to 860 MHz) aerial amplifiers using SMD technology.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	15 V
Collector current (DC)	I_C	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
DC current gain	h_{FE}	min. max.	20 150
Transition frequency at $f = 500\text{ MHz}$ $I_C = 25\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T	typ.	2.8 GHz
Feedback capacitance at $f = 1\text{ MHz}$ $I_C = 0$; $V_{CE} = 5\text{ V}$	C_{re}	typ.	0.06 pF
Noise figure $I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$; $f = 800\text{ MHz}$; $Z_s = 600\text{ }\Omega$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	F	typ.	2.5 dB
Maximum unilateral power gain at $f = 800\text{ MHz}$; $I_C = 14\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	G_{UM}	typ.	15 dB

MECHANICAL DATA

SOT143

Pinning

- 1 = collector
- 2 = base
- 3,4 = emitter

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Collector-base voltage (open emitter)	V_{CBO}	max.	25 V
Collector-emitter voltage (open base)	V_{CEO}	max.	15 V
Emitter-base voltage (open collector)	V_{EB0}	max.	2.5 V
Collector current (DC)	I_C	max.	25 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ mounted on a ceramic substrate $8 \times 10 \times 0.7\text{ mm}$	P_{tot}	max.	300 mW
Storage temperature range	T_{stg}		$-65\text{ to }150\text{ }^{\circ}\text{C}$
Junction temperature	T_j	max.	$150\text{ }^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient mounted on ceramic
substrate $8 \times 10 \times 0.7\text{ mm}$

R_{thj-a}	=	430 K/W
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CHARACTERISTICS

 $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 10\text{ V}$

I_{CBO}	max.	50 nA
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DC current gain

$I_C = 2\text{ mA}; V_{CE} = 1\text{ V}$

$I_C = 25\text{ mA}; V_{CE} = 1\text{ V}$

h_{FE}	min.	20
h_{FE}	max.	150

Transition frequency at $f = 500\text{ MHz}$

$I_C = 25\text{ mA}; V_{CE} = 5\text{ V}$

f_T	typ.	2.8 GHz
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Noise figure

$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; f = 800\text{ MHz}$

$Z_s = 60\text{ }\Omega; T_{amb} = 25\text{ }^{\circ}\text{C}$

F	typ.	2.5 dB
-----	------	--------

Collector capacitance at $f = 1\text{ MHz}$

$I_E = 0; V_{CB} = 10\text{ V}$

C_C	typ.	0.7 pF
-------	------	--------

Emitter capacitance at $f = 1\text{ MHz}$

$I_C = 0; V_{EB} = 0.5\text{ V}$

C_e	typ.	1.25 pF
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Feedback capacitance at $f = 1\text{ MHz}$

$I_C = 0; V_{CE} = 5\text{ V}$

C_{re}	typ.	0.6 pF
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Maximum unilateral power gain at $f = 800\text{ MHz}$

$I_C = 14\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; S_{12} = 0$

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$$

G_{UM}	typ.	15 dB
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Output voltage at $d_{im} = -60$ dB

(DIN 45004B, para. 6,3: 3-tone)

$I_C = 14$ mA; $V_{CE} = 10$ V; $Z_L = 75 \Omega$

$V_p = V_O$; $f_p = 795.25$ MHz

$V_q = V_O - 6$ dB; $f_q = 803.25$ MHz

$V_r = V_O - 6$ dB; $f_r = 805.25$ MHz

Measured at $f_{(p+q-r)} = 793.25$ MHz

V_O typ. 150 mV

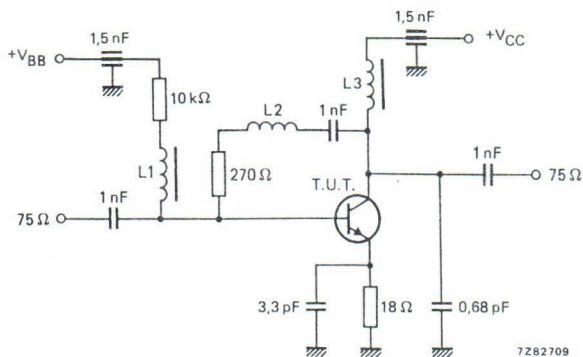


Fig.1 Intermodulation distortion and second harmonic distortion MATV test circuit.

$L1 = L3 = 5 \mu\text{H}$ Ferroxcube choke.

$L2 = 3$ turns Copper wire (0.4 mm), internal diameter 3 mm, winding pitch 1 mm.

Table 1 S-parameters (common emitter)Conditions: $T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_{CE} = 10\text{ V}$; typical values.

I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		GUM (dB)
		M	Φ	M	Φ	M	Φ	M	Φ	
5	40	0.84/-19.4		14.3/168.2		0.02/67.7		0.98/-5.1		41.9
	100	0.77/-50.0		12.83/147.8		0.02/65.6		0.95/-13.0		35.7
	200	0.61/-84.3		9.31/128.7		0.03/54.4		0.80/-19.3		25.9
	500	0.51/-136.7		5.21/99.3		0.05/47.0		0.69/-26.2		18.5
	800	0.47/-157.4		3.51/84.6		0.06/50.3		0.63/-32.0		14.2
	1000	0.46/-168.7		2.86/75.4		0.07/51.4		0.64/-34.2		12.5
	1200	0.47/179.8		2.36/68.1		0.07/53.5		0.63/-38.9		10.7
	1500	0.46/173.4		1.96/60.2		0.09/56.8		0.57/-42.7		8.6
	2000	0.47/157.3		1.44/45.6		0.11/59.8		0.56/-55.6		5.9
10	40	0.75/-27.9		24.57/163.4		0.02/67.9		0.96/-8.1		42.8
	100	0.65/-68.5		19.95/138.6		0.02/58.9		0.86/-17.9		34.3
	200	0.52/-107.8		13.04/118.2		0.03/51.3		0.70/-22.3		26.6
	500	0.48/-152.8		6.31/91.7		0.04/54.2		0.59/-25.4		19.0
	800	0.45/-170.1		4.11/79.0		0.06/59.1		0.56/-30.5		14.9
	1000	0.46/-178.9		3.30/71.0		0.06/60.4		0.57/-32.2		13.1
	1200	0.47/171.4		2.72/64.6		0.07/62.0		0.56/-36.5		11.4
	1500	0.46/167.3		2.22/57.0		0.09/63.6		0.51/-40.8		9.3
	2000	0.47/152.7		1.63/43.4		0.11/64.3		0.51/-53.7		6.7
15	40	0.69/-34.4		31.29/159.8		0.02/62.6		0.94/-10.2		42.3
	100	0.59/-80.7		23.65/132.7		0.02/55.5		0.81/-20.2		34.0
	200	0.49/-120.7		14.46/112.6		0.02/52.5		0.64/-22.6		26.7
	500	0.47/-160.1		6.61/88.3		0.04/58.2		0.55/-23.7		19.1
	800	0.45/-174.7		4.25/76.3		0.05/63.3		0.53/-28.8		15.0
	1000	0.46/177.6		3.39/68.7		0.06/64.0		0.55/-30.6		13.2
	1200	0.47/168.6		2.79/62.6		0.07/65.0		0.54/-34.8		11.5
	1500	0.47/165.2		2.27/55.2		0.09/65.7		0.50/-39.6		9.4
	2000	0.48/151.1		1.65/42.0		0.11/66.0		0.51/-52.8		6.8
20	40	0.65/-39.4		35.51/157.2		0.02/54.5		0.93/-11.4		42.3
	100	0.56/-89.4		25.64/128.6		0.02/57.3		0.77/-20.9		33.7
	200	0.47/-128.5		14.99/109.0		0.02/53.5		0.61/-21.7		26.6
	500	0.47/-163.8		6.62/86.0		0.04/61.0		0.54/-22.0		19.0
	800	0.45/-176.8		4.21/74.5		0.05/66.0		0.52/-27.4		14.9
	1000	0.46/175.9		3.35/67.1		0.06/65.9		0.55/-29.4		13.1
	1200	0.47/167.4		2.75/61.2		0.07/66.7		0.55/-33.8		11.4
	1500	0.47/164.2		2.23/53.8		0.09/67.3		0.50/-38.8		9.3
	2000	0.48/150.4		1.62/40.9		0.11/67.1		0.51/-52.5		6.6
30	40	0.58/-51.2		39.39/150.7		0.01/57.5		0.89/-13.0		40.6
	100	0.50/-105.8		25.05/121.1		0.02/54.2		0.72/-19.3		32.3
	200	0.45/-141.0		13.65/103.2		0.02/55.2		0.60/-17.9		25.6
	500	0.46/-169.0		5.79/82.5		0.03/64.8		0.57/-19.0		18.0
	800	0.45/179.7		3.65/71.7		0.05/67.9		0.56/-25.7		13.8
	1000	0.46/173.1		2.89/64.5		0.06/67.9		0.58/-28.6		12.1
	1200	0.48/165.1		2.37/58.9		0.07/68.4		0.58/-33.9		10.4
	1500	0.48/161.8		1.91/51.9		0.09/69.2		0.53/-39.1		8.2
	2000	0.49/148.0		1.40/39.3		0.11/69.0		0.54/-53.8		5.6

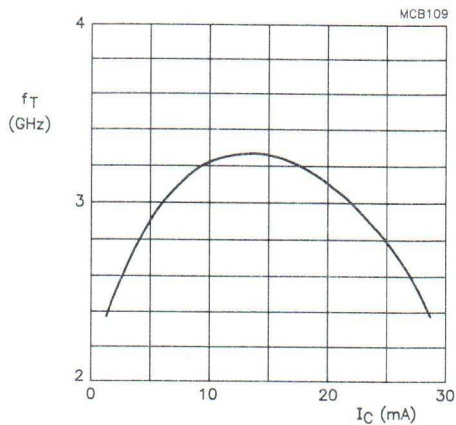


Fig.2 Transition frequency as a function of collector current; $V_{CE} = 5$ V; $f = 500$ MHz; $T_{amb} = 25$ °C.

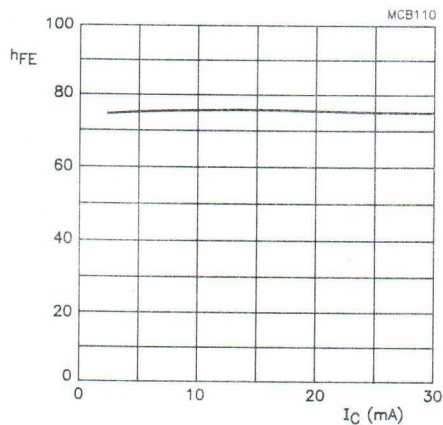


Fig.3 Current gain as a function of collector current; $V_{CE} = 1$ V; $T_{amb} = 25$ °C.

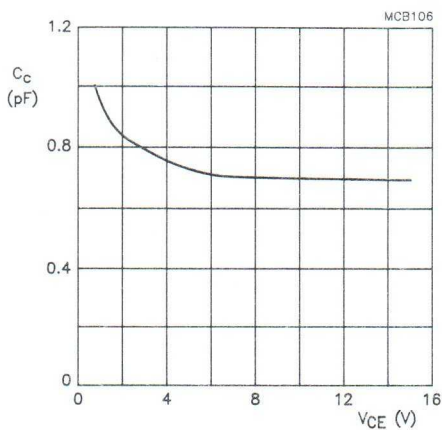


Fig.4 Collector capacitance as a function of collector-emitter voltage; $f = 1$ MHz; $I_E = 0$; $T_{amb} = 25$ °C.

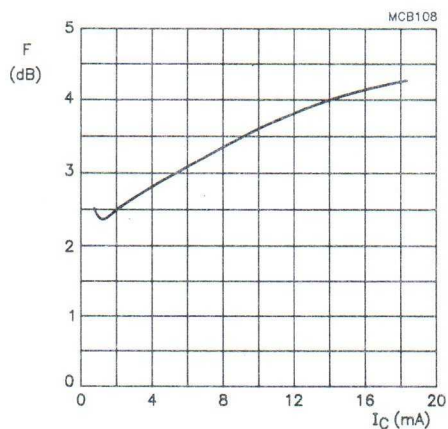


Fig.5 Noise figure as a function of collector current; $V_{CE} = 5$ V; $f = 800$ MHz; $R_S = 60$ Ω ; $b_S = \text{opt.}$; $T_{amb} = 25$ °C.

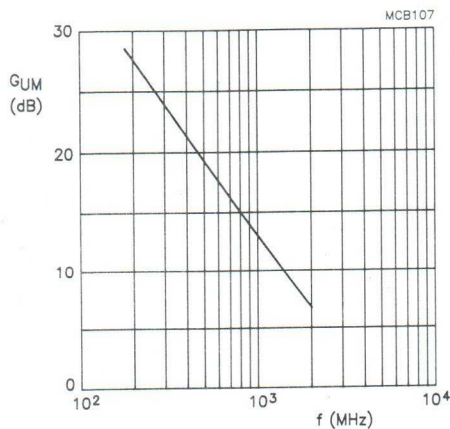


Fig.6 Maximum power gain as a function of frequency; $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

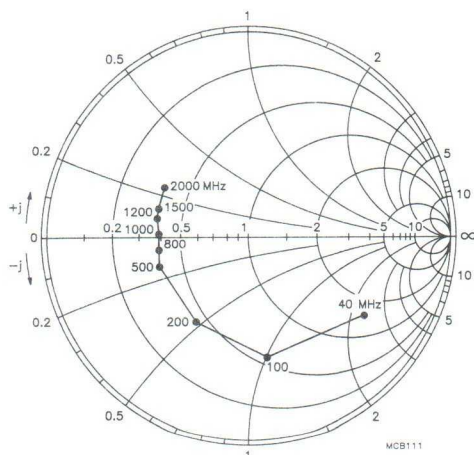


Fig.7 Input impedance derived from S_{11} (in $\Omega \times 50$); $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

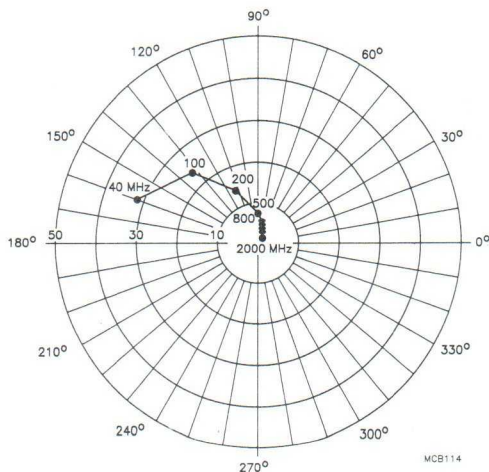


Fig.8 Forward transmission coefficient S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

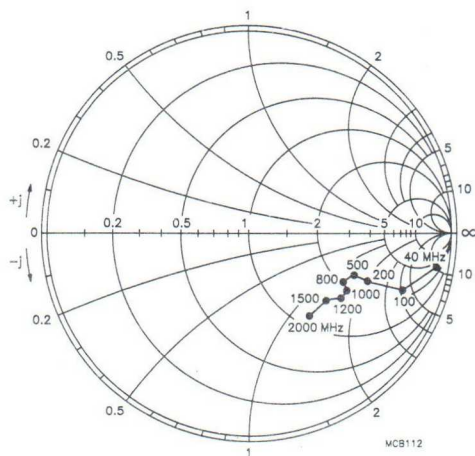


Fig.9 Output impedance derived from S_{22}
(in Ohm $\times 50$); $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$;
 $T_{amb} = 25\text{ }^{\circ}\text{C}$.

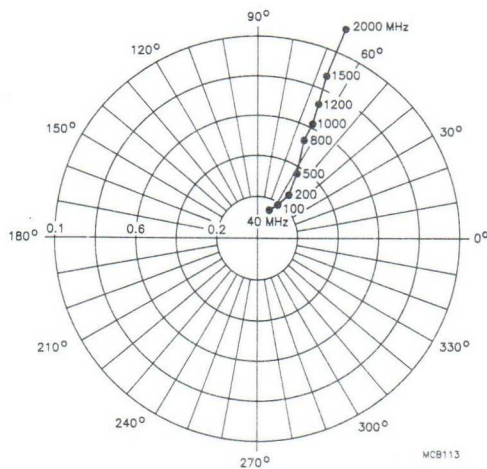


Fig.10 Reverse transmission coefficient S_{12} ;
 $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Data sheet	
status	Preliminary specification
date of issue	April 1991

BFG25AX

NPN HF wideband transistor

DESCRIPTION

NPN transistor in a plastic SOT143 envelope, primarily for use on low power amplifiers. Ideal for pagers and other battery operated systems where low power consumption is critical.

MECHANICAL DATA

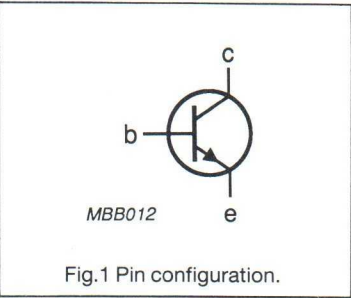
Plastic SOT143 envelope.

Marking code: V11

PINNING

PIN	DESCRIPTION
1	collector
2,4	emitter
3	base

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-	8	V
V_{CEO}	collector-emitter voltage	open base	-	-	5	V
I_C	collector current		-	-	6.5	mA
P_{tot}	total power dissipation (DC)	note 1	-	-	32	mW
T_j	junction temperature		-	-	150	°C
h_{FE}	DC current gain	$I_C = 0.5\text{ mA};$ $V_{CE} = 1\text{ V}$	50	80	200	
f_T	transition frequency	$f = 500\text{ MHz};$ $I_C = 1\text{ mA};$ $V_{CE} = 1\text{ V}$	3.5	5	-	GHz

Note

- Up to $T_s = 140\text{ °C}$; T_s = temperature measured on soldering point of collector tab.

NPN HF wideband transistor**BFG25AX****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	8	V
V_{CEO}	collector-emitter voltage	open base	-	5	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I_C	collector current		-	6.5	mA
P_{tot}	total power dissipation (DC)	note 1	-	32	mW
T_{stg}	storage temperature range		-65	+150	°C
T_j	junction temperature		-	150	°C

Note

1. Up to $T_s = 140\text{ °C}$; T_s = temperature measured on soldering point of collector tab.

THERMAL RESISTANCE

SYMBOL	PARAMETER	MAX.	UNIT
$R_{th\ j-s}$	from junction to soldering point	320	K/W

NPN HF wideband transistor**BFG25AX****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR) CBO}$	collector-base breakdown voltage	open emitter $I_C = 10\text{ }\mu\text{A}$	8	-	-	V
$V_{(BR) CEO}$	collector-emitter breakdown voltage	open base $I_C = 100\text{ }\mu\text{A}$	5	-	-	V
$V_{(BR) EBO}$	emitter-base breakdown voltage	open collector $I_E = 10\text{ }\mu\text{A}$	2	-	-	V
h_{FE}	DC current gain	$I_C = 0.5\text{ mA}$; $V_{CE} = 1\text{ V}$	50	80	200	
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CE} = 1\text{ V}$	-	0.22	0.3	pF
G_{UM}	unilateral gain	$f = 500\text{ MHz}$; $I_C = 0.5\text{ mA}$; $V_{CE} = 1\text{ V}$	-	30	-	dB
G_{UM}	unilateral gain	$f = 1\text{ GHz}$; $I_C = 0.5\text{ mA}$; $V_{CE} = 1\text{ V}$	-	18	-	dB
F	noise figure	$f = 500\text{ MHz}$; $I_C = 0.5\text{ mA}$; $V_{CE} = 1\text{ V}$	-	1.6	2.0	dB
F	noise figure	$f = 1\text{ GHz}$; $I_C = 1.0\text{ mA}$; $V_{CE} = 1\text{ V}$	-	1.8	2.5	dB
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 1\text{ mA}$; $V_{CE} = 1\text{ V}$	3.5	5		GHz

Data sheet	
status	Product specification
date of issue	April 1991

BFG31

PNP 5 GHz wideband transistor

FEATURES

- High output voltage capability
- High gain bandwidth product
- Good thermal stability
- Gold metallization ensures excellent reliability
- Complementary npn type BFG97.

DESCRIPTION

PNP planar epitaxial transistor intended for wideband amplifier applications.

The BFG31 is mounted in a SOT223 plastic envelope.

MECHANICAL DATA

Plastic SOT223 envelope.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	-	20	V
$-V_{CEO}$	collector-emitter voltage	open base	-	-	15	V
$-I_C$	collector current (DC)		-	-	100	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$; note 1	-	-	1	W
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	5.0	-	-	GHz
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	12	-	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $f_{(p+q-r)} = 848.25\text{ MHz}$	-	600	-	mV

Note

1. T_{case} temperature measured on soldering point of collector tab.

PNP 5 GHz wideband transistor**BFG31****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG31	SOT223	bulk	500
BFG31	SOT223	12 mm tape	1000

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CB0}$	collector-base voltage	open emitter	-	20	V
$-V_{CE0}$	collector-emitter voltage	open base	-	15	V
$-V_{EB0}$	emitter-base voltage	open collector	-	3	V
$-I_C$	collector current (DC)		-	100	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-c}$	from junction to case.	40	K/W

PNP 5 GHz wideband transistor

BFG31

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{(BR)CBO}$	collector-base breakdown voltage	open emitter $-I_C = 10\text{ mA}$	20	-	-	V
$-V_{(BR)CEO}$	collector-emitter breakdown voltage	open base $-I_C = 10\text{ mA}$	18	-	-	V
$-V_{(BR)EBO}$	emitter-base breakdown voltage	open collector $-I_E = 0.1\text{ mA}$	3	-	-	V
$-I_{CBO}$	collector cut-off current	$-I_E = 0$; $-V_{CB} = 10\text{ V}$	-	-	1	μA
h_{FE}	DC current gain	$-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$	25	-	-	
C_{cb}	collector-base capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{CB} = 10\text{ V}$	-	1.8	-	pF
C_{eb}	emitter-base capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{EB} = 10\text{ V}$	-	5	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{CE} = 10\text{ V}$	-	1.6	-	pF
f_T	transition frequency	$f = 500\text{ MHz}$; $-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	5	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	16	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $-I_C = 70\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	12	-	dB
V_o	output voltage	note 1	-	600	-	mV
V_o	output voltage	note 2	-	650	-	mV

Note

1. $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $-I_C = 100\text{ mA}$;
 $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $f_p = 850.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_q = 858.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
 $f_r = 860.25\text{ MHz}$; Measured at $f_{(p+q+r)} = 848.25\text{ MHz}$.
2. $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $-I_C = 100\text{ mA}$;
 $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $f_p = 445.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_q = 453.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
 $f_r = 455.25\text{ MHz}$; Measured at $f_{(p+q+r)} = 443.25\text{ MHz}$.

PNP 5 GHz wideband transistor

BFG31

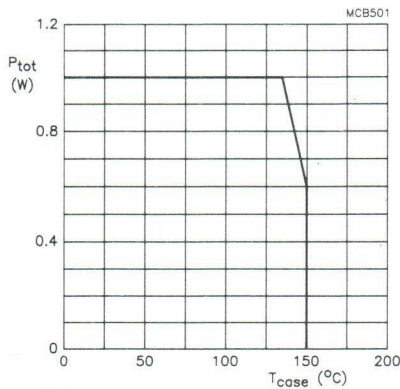
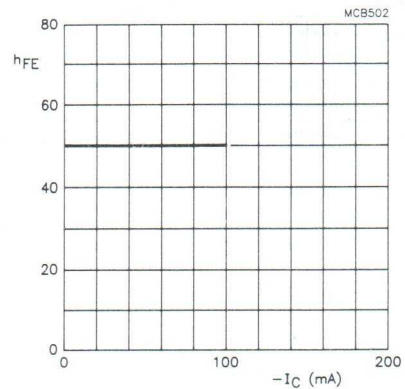
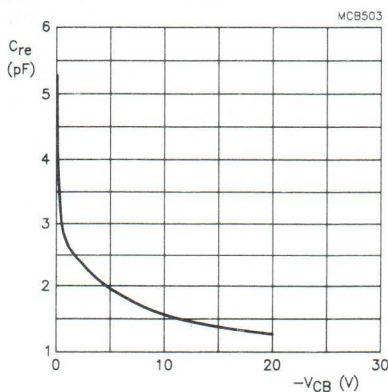
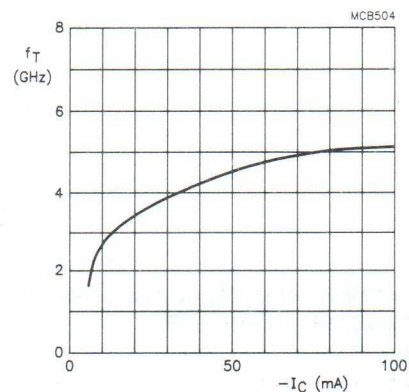


Fig.1 Power derating curve.

Fig.2 DC current gain as a function of collector current; $-V_{CE} = 10 V$; $T_{amb} = 25^{\circ}C$.Fig.3 Feedback capacitance as a function of collector-base voltage; $f = 1 MHz$; $T_{amb} = 25^{\circ}C$; typical values.Fig.4 Transition frequency as a function of collector current; $-V_{CE} = 10 V$; $T_{amb} = 25^{\circ}C$; typical values.

PNP 5 GHz wideband transistor

BFG31

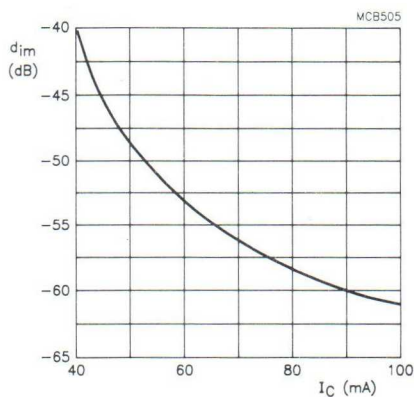


Fig.5 Intermodulation distortion as a function of collector current; $-V_{CE} = 10$ V; $V_o = 650$ mV; $T_{amb} = 25$ °C; $f_{(p+q-r)} = 443.25$ MHz.

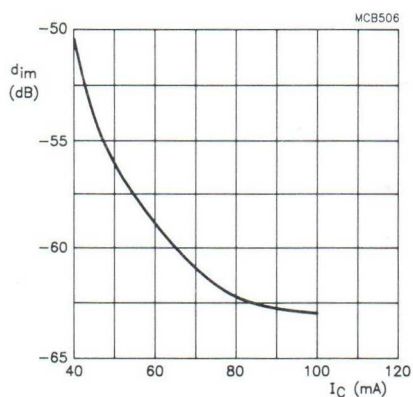


Fig.6 Intermodulation distortion as a function of collector current; $-V_{CE} = 10$ V; $V_o = 600$ mV; $T_{amb} = 25$ °C; $f_{(p+q-r)} = 848.25$ MHz.

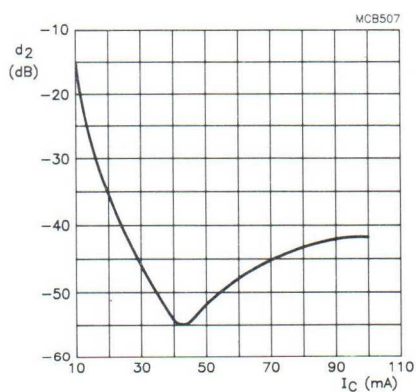


Fig.7 Second order beat as a function of collector current; $-V_{CE} = 10$ V; $V_o = 50$ dBmV; $T_{amb} = 25$ °C; $f_{(p+q)} = 450$ MHz.

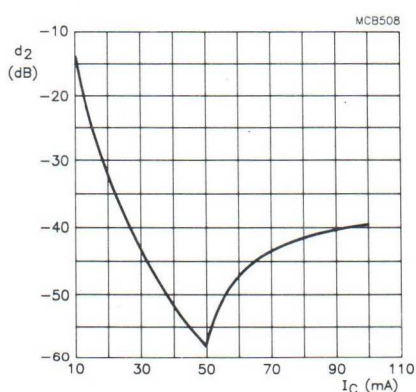


Fig.8 Second order beat as a function of collector current; $-V_{CE} = 10$ V; $V_o = 50$ dBmV; $T_{amb} = 25$ °C; $f_{(p+q)} = 810$ MHz.

NPN 12 GHz WIDEBAND TRANSISTOR

BFG33 is an npn transistor in a microminiature SOT143 envelope with double emitter bonding. The device contains a BFQ33 crystal and is for use in circuits using SMD technology.

Features

- Extremely high transition frequency
- Very low noise at high frequencies.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	9.0 V
Collector-emitter voltage (open base)	V_{CEO}	max.	7.0 V
Collector current (DC)	I_C	max.	20 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ mounted on a ceramic substrate $8 \times 10 \times 0.7\text{ mm}$	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
Transition frequency at $f = 1.5\text{ GHz}$ $I_C = 14\text{ mA}$; $V_{CE} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	f_T	typ.	12 GHz
Noise figure at optimum source impedance $I_C = 5\text{ mA}$; $V_{CE} = 5\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	F	typ.	2.5 dB

MECHANICAL DATA

SOT143.

BFG33 Marking code: V6
BFG33X Marking code: V16

Pinning

BFG33

1 = collector
2 = base
3, 4 = emitter

BFG33X

1 = collector
2, 4 = emitter
3 = base

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Collector-base voltage (open emitter)	V_{CB0}	max.	9.0 V
Collector-emitter voltage (open base)	V_{CEO}	max.	7.0 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2.0 V
Collector current (DC)	I_C	max.	20 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$ mounted on a ceramic substrate $8 \times 10 \times 0.7$ mm	P_{tot}	max.	300 mW
Storage temperature range	T_{stg}		-65 to 150°C
Junction temperature	T_j	max.	150°C

THERMAL RESISTANCE

From junction to ambient mounted on ceramic
substrate $8 \times 10 \times 0.7$ mm

$$R_{th\ j-a} = 430 \text{ K/W}$$

CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$$I_E = 0; V_{CB} = 5 \text{ V}$$

$$I_{CBO} \text{ max. } 50 \text{ nA}$$

DC current gain

$$I_C = 14 \text{ mA}; V_{CE} = 5 \text{ V}$$

$$h_{FE} \text{ min. } 50$$

Transition frequency at $f = 1.5 \text{ GHz}$

$$I_C = 14 \text{ mA}; V_{CE} = 5 \text{ V}; T_{amb} = 25^\circ\text{C}$$

$$f_T \text{ typ. } 12 \text{ GHz}$$

Noise figure at optimum source impedance

$$I_C = 5 \text{ mA}; V_{CE} = 5 \text{ V}; f = 2 \text{ GHz}; T_{amb} = 25^\circ\text{C}$$

$$F \text{ typ. } 2.5 \text{ dB}$$

Maximum unilateral power gain

$$I_C = 14 \text{ mA}; V_{CE} = 5 \text{ V}; f = 2 \text{ GHz};$$

$$T_{amb} = 25^\circ\text{C}; S_{12} = 0$$

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$$

$$G_{UM} \text{ typ. } 10.5 \text{ dB}$$

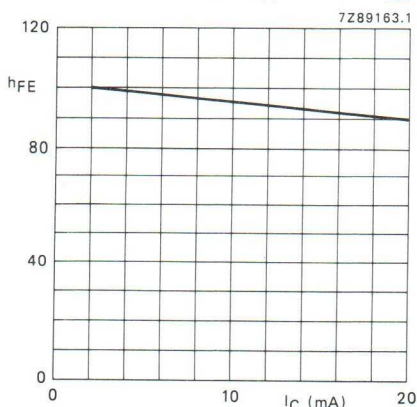


Fig.1 Gain as a function of collector current.

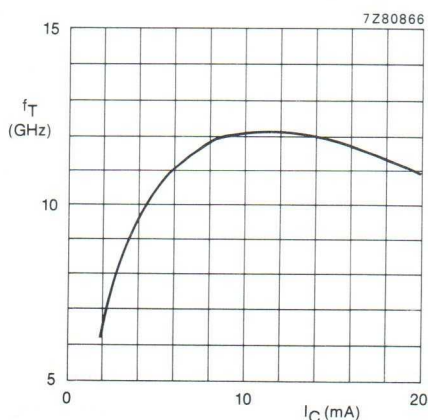


Fig.2 Transitional frequency as a function of collector current.

Data sheet	
status	Product specification
date of issue	April 1991

BFG35

NPN 4 GHz wideband transistor

DESCRIPTION

NPN planar epitaxial transistor in a plastic SOT223 envelope, intended for wideband amplifier applications. The device features high output voltage capabilities. Its pnp complement is the BFG55.

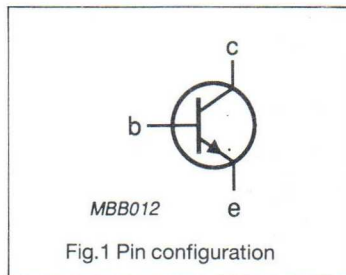
MECHANICAL DATA

Plastic SOT223 envelope.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-	25	V
V_{CEO}	collector-emitter voltage	open base	-	-	18	V
I_C	collector current (DC)		-	-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$; note 1	-	-	1	W
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
h_{FE}	DC current gain	$I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	4.0	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	-	15	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	-	11	-	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $f_{(p+q-r)} = 793.25\text{ MHz}$	-	750	-	mV

Note

1. T_{case} temperature measured on soldering point of collector tab.

NPN 4 GHz wideband transistor**BFG35****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG35	SOT223	bulk	500
BFG35	SOT223	12 mm reel	1000

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	25	V
V_{CEO}	collector-emitter voltage	open base	-	18	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I_C	collector current (DC)		-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

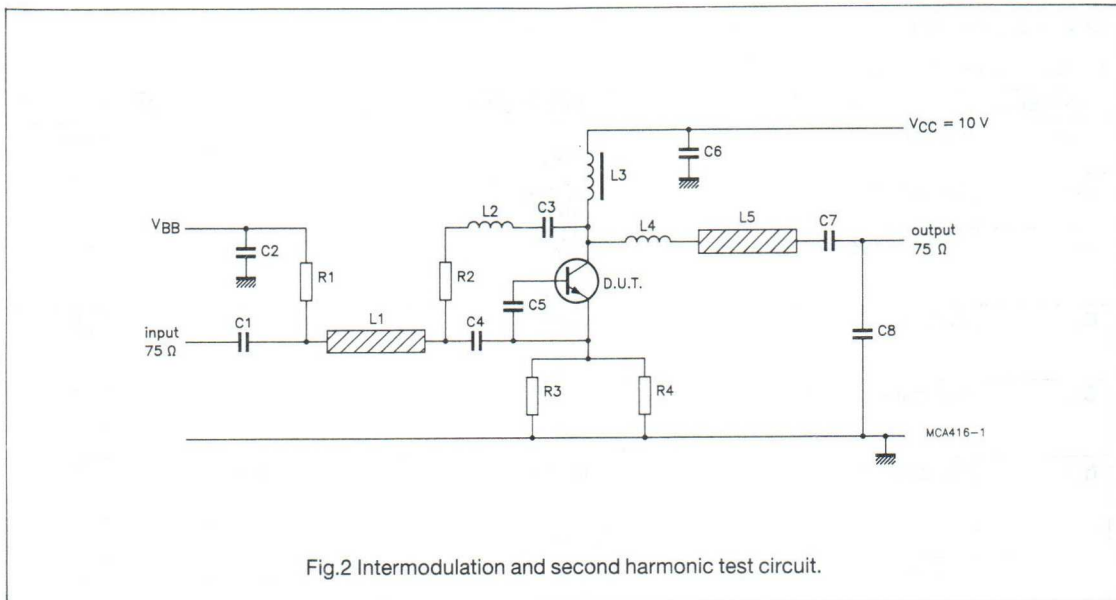
SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-c}$	from junction to case	40	K/W

NPN 4 GHz wideband transistor**BFG35****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 10\text{ V}$	-	-	1	μA
h_{FE}	DC current gain	$I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	25	-	-	
C_c	collector capacitance	$f = 1\text{ MHz}$; $I_E = I_E = 0$; $V_{CB} = 10\text{ V}$	-	2.0	-	pF
C_e	emitter capacitance	$f = 1\text{ MHz}$; $I_C = I_C = 0$; $V_{EB} = 0.5\text{ V}$	-	10.0	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CE} = 10\text{ V}$	-	1.2	-	pF
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	4.0	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	15	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	11	-	dB
V_o	output voltage	see note 1	-	750	-	mV
V_o	output voltage	see note 2	-	800	-	mV

Note

- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$;
 $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $f_p = 795.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_q = 803.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
 $f_r = 805.25\text{ MHz}$; Measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$;
 $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $f_p = 445.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_q = 453.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
 $f_r = 455.25\text{ MHz}$; Measured at $f_{(p+q-r)} = 443.25\text{ MHz}$.

NPN 4 GHz wideband transistor**BFG35****List of components:**

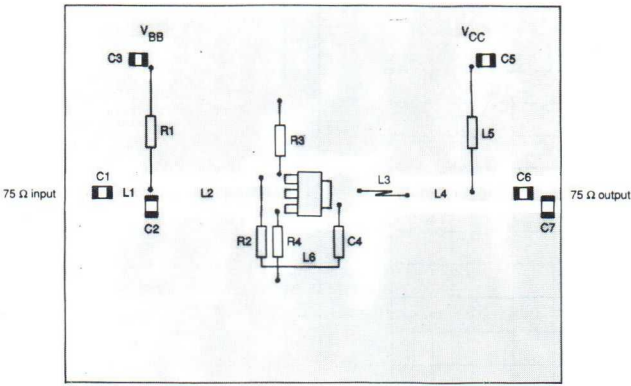
R1 = 10 k Ω metal film resistor	(cat. no. 2322 180 73103)
R2 = 200 Ω metal film resistor	(cat. no. 2322 180 73201)
R3 = R4 = 27 Ω metal film resistor	(cat. no. 2322 180 73279)
C1 = C3 = C5 = C6 = 10 nF ceramic multilayer capacitor	(cat. no. 2222 590 08627)
C2 = C7 = 1 pF ceramic multilayer capacitor	(cat. no. 2222 851 12108)
C4 = 10 nF miniature ceramic plate capacitor	(cat. no. 2222 629 08103)
L1 = 75 Ω microstripline	(L = 7 mm; W = 2.5 mm)
L2 = 75 Ω microstripline	(L = 22 mm; W = 2.5 mm)
L3 = 1.5 turn Cu wire (0.4 mm), internal diameter 3 mm, winding pitch 1 mm	
L4 = 75 Ω microstripline	(L = 19 mm; W = 2.5 mm)
L5 = 5 μ H Ferroxcube choke	(cat. no. 3122 108 20153)
L6 = 30 mm Cu-wire (0.4 mm; L $\approx$ 24 nH)	

The circuit has been built on a double Cu clad printed circuit board with PTFE dielectric ($\epsilon_r = 2.2$); thickness 1/16 inch; thickness of copper-sheet 2 x 35 μ m; see Figs 3a, 3b and 3c.

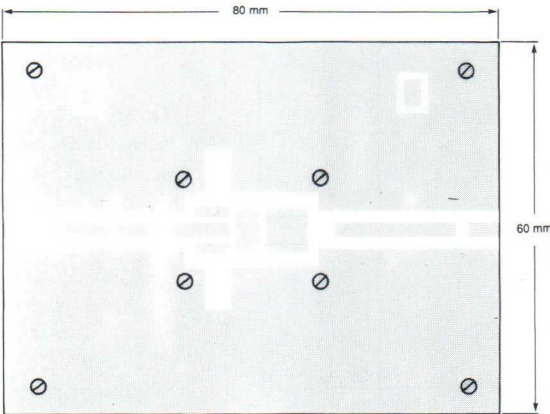
The components R2, L6, C5 and L3 are mounted on the underside of the PCB.

NPN 4 GHz wideband transistor

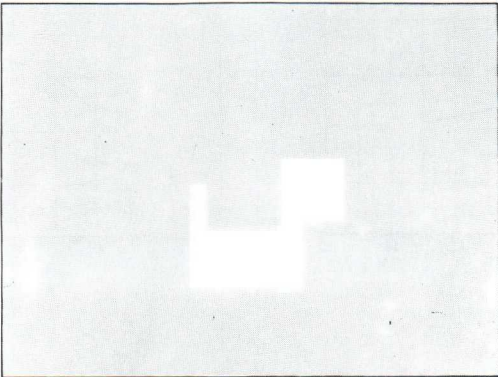
BFG35



7Z26284



7Z26285



7Z26286

Fig.3 Intermodulation test circuit printed circuit board.

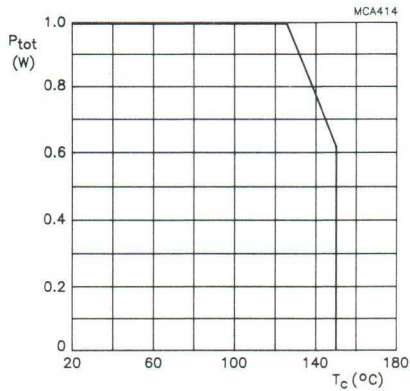
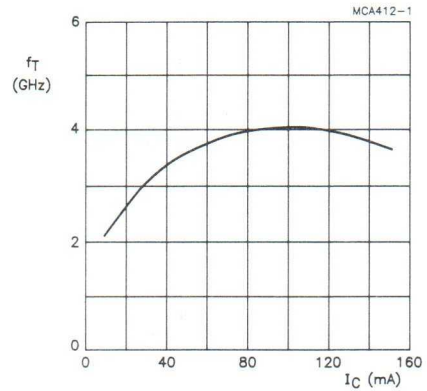
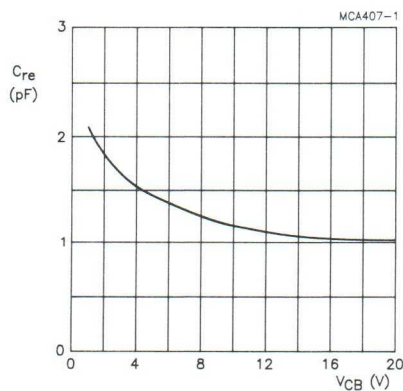
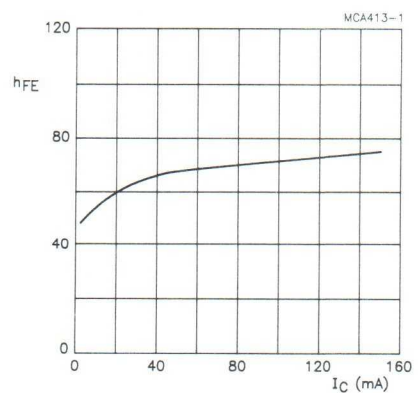
NPN 4 GHz wideband transistor**BFG35**

Fig.4 Power derating curve.

Fig.5 Transition frequency as a function of collector current; $V_{CE} = 10$ V; $f = 500$ MHz; $T_j = 25$ °C; typical values.Fig.6 Feedback capacitance as a function of collector-base voltage; $I_E = 0$; $f = 1$ MHz; $T_j = 25$ °C.Fig.7 DC current gain as a function of collector current; $V_{CE} = 10$ V; $T_j = 25$ °C.

NPN 4 GHz wideband transistor

BFG35

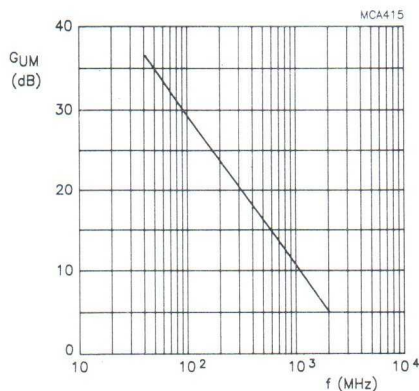


Fig.8 Maximum gain as a function of frequency;
 $V_{CE} = 10$ V; $I_C = 100$ mA; $T_{amb} = 25$ °C; typical values.

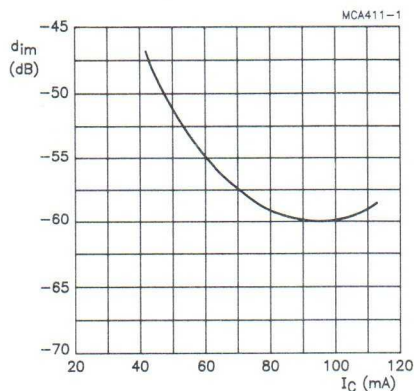


Fig.9 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 800$ mV;
 $f_{(p+q-r)} = 443.25$ MHz; $T_{amb} = 25$ °C; typical values.

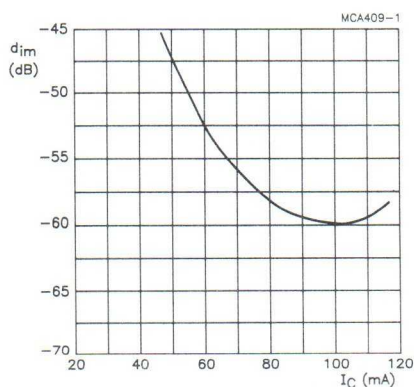


Fig.10 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 750$ mV;
 $f_{(p+q-r)} = 793.25$ MHz; $T_{amb} = 25$ °C; typical values.

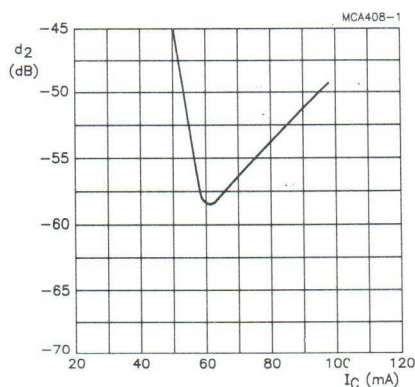


Fig.11 Second order beat as a function of collector current; $V_{CE} = 10$ V; $V_o = 50$ dBmV;
 $f_{(p+q)} = 450$ MHz; $T_{amb} = 25$ °C; typical values.

NPN 4 GHz wideband transistor

BFG35

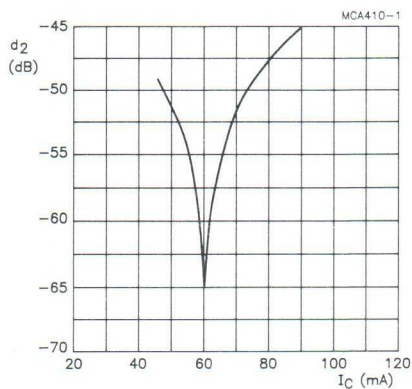


Fig.12 Second order beat as a function of collector current; $V_{CE} = 10$ V; $V_o = 50$ dBmV; $f_{(p+q)} = 810$ MHz; $T_{amb} = 25$ °C; typical values.

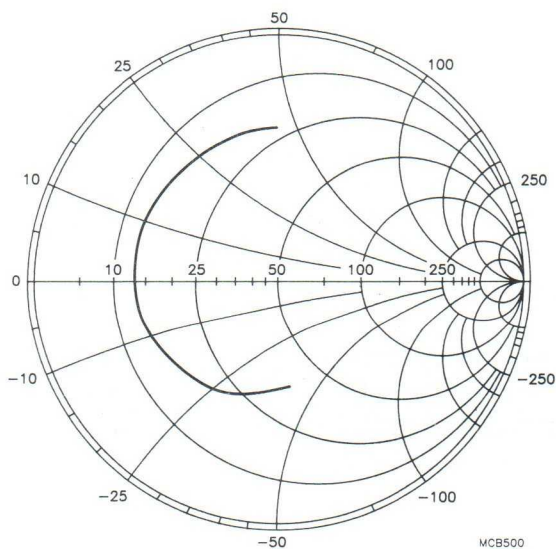


Fig.13 Input reflection coefficient, S_{11} ; $V_{CE} = 10$ V; $I_C = 100$ mA; $T_{amb} = 25$ °C; typical values.

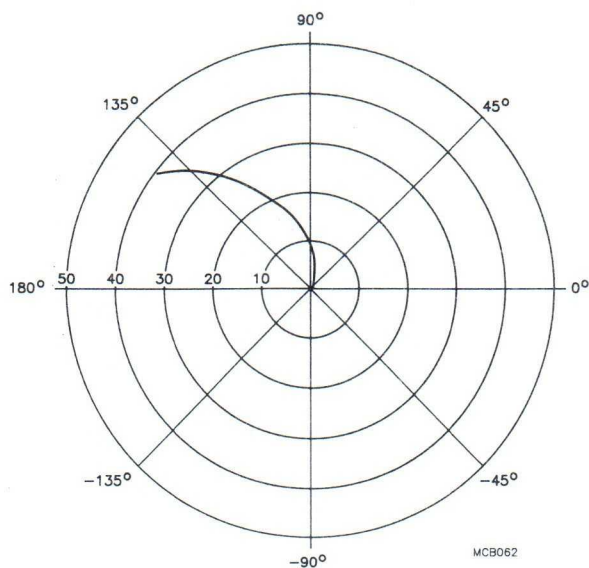
NPN 4 GHz wideband transistor**BFG35**

Fig.14 Forward transmission coefficient, S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ °C}$; typical values.

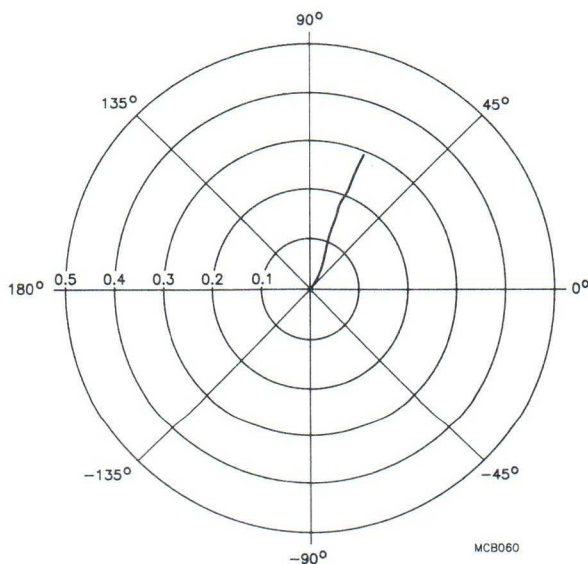


Fig.15 Reverse transmission coefficient, S_{12} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ °C}$; typical values.

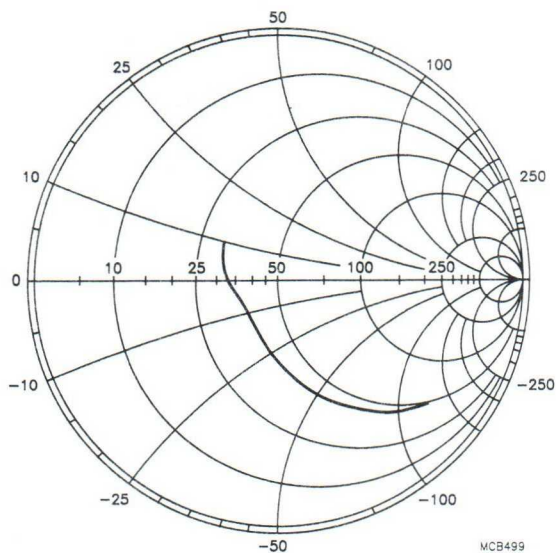
NPN 4 GHz wideband transistor**BFG35**

Fig.16 Output reflection coefficient, S_{22} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

NPN 4 GHz wideband transistor

BFG35

S-Parameters (common emitter) at $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{UM} (dB)
		M	Φ	M	Φ	M	Φ	M	Φ	
10	40	0.60/-	53.6	17.3/153.9		0.02/71.2		0.91/-	20.3	34.4
	100	0.63/-	104.6	12.6/127.3		0.04/49.2		0.70/-	38.4	27.0
	200	0.66/-	144.8	7.7/105.2		0.05/39.5		0.48/-	50.4	21.4
	500	0.68/-	174.0	3.4/ 77.4		0.06/48.9		0.34/-	65.4	13.8
	800	0.68/	151.8	2.1/ 61.1		0.09/64.5		0.33/-	84.2	9.7
	1000	0.68/	139.9	1.7/ 51.0		0.11/71.0		0.33/-	99.4	7.8
	1200	0.68/	128.8	1.4/ 42.6		0.13/77.8		0.34/-	115.2	5.9
	1500	0.67/	112.8	1.1/ 33.5		0.18/78.3		0.36/-	138.8	3.5
20	2000	0.66/	89.5	0.7/ 22.0		0.28/77.1		0.42/-	175.3	0.5
	40	0.49/-	66.9	24.3/150.1		0.02/68.7		0.87/-	27.3	35.0
	100	0.56/-	119.1	16.5/123.2		0.04/52.2		0.60/-	50.5	28.0
	200	0.61/-	153.9	9.7/102.7		0.05/46.3		0.38/-	65.8	22.5
	500	0.63/	170.6	4.1/ 78.3		0.07/59.9		0.22/-	85.3	14.8
	800	0.63/	150.4	2.6/ 63.7		0.10/68.2		0.21/-	103.9	10.8
	1000	0.64/	139.2	2.1/ 54.5		0.12/70.3		0.21/-	118.3	8.9
	1200	0.64/	128.5	1.7/ 47.0		0.15/72.7		0.22/-	132.5	7.0
50	1500	0.63/	113.7	1.4/ 37.7		0.19/73.7		0.26/-	153.5	5.2
	2000	0.63/	91.0	0.9/ 25.1		0.28/72.6		0.33/	173.4	2.1
	40	0.43/-	80.9	31.7/145.8		0.02/62.5		0.82/-	35.3	35.7
	100	0.53/-	130.9	20.0/118.8		0.03/51.7		0.52/-	64.5	28.8
	200	0.59/-	160.8	11.3/100.3		0.04/53.5		0.31/-	86.6	23.3
	500	0.60/	168.2	4.7/ 78.8		0.08/64.3		0.18/-	119.6	15.6
	800	0.61/	149.2	3.0/ 65.5		0.11/69.3		0.17/-	139.1	11.6
	1000	0.61/	138.6	2.4/ 57.4		0.14/69.8		0.17/-	155.0	9.6
70	1200	0.61/	128.5	1.9/ 50.6		0.16/70.7		0.19/-	165.9	7.9
	1500	0.61/	114.1	1.6/ 41.6		0.21/68.9		0.22/	179.2	6.2
	2000	0.61/	91.9	1.1/ 29.7		0.28/67.3		0.29/	154.6	3.2
	40	0.44/-	83.3	33.6/144.3		0.02/65.8		0.80/-	37.8	35.9
	100	0.53/-	132.9	20.7/117.5		0.03/53.1		0.50/-	68.4	29.0
	200	0.58/-	162.0	11.6/ 99.5		0.04/55.3		0.30/-	92.3	23.5
	500	0.59/	167.7	4.8/ 78.7		0.08/66.2		0.18/-	127.6	15.7
	800	0.60/	149.2	3.0/ 65.7		0.12/67.6		0.16/-	148.8	11.7
100	1000	0.60/	138.6	2.4/ 57.1		0.14/68.7		0.17/-	160.7	9.8
	1200	0.60/	128.4	2.0/ 51.2		0.17/70.6		0.19/-	172.3	8.0
	1500	0.60/	114.2	1.6/ 42.0		0.21/68.2		0.23/	172.8	6.3
	2000	0.61/	92.1	1.1/ 30.7		0.29/67.0		0.29/	149.1	3.4
	40	0.45/-	85.7	35.2/142.8		0.02/65.1		0.78/-	40.4	36.0
	100	0.53/-	134.7	21.2/116.1		0.03/51.6		0.48/-	71.7	29.1
	200	0.58/-	163.0	11.8/ 98.6		0.04/54.1		0.29/-	97.7	23.5
	500	0.59/	167.1	4.9/ 78.6		0.08/65.5		0.17/-	134.9	15.8
100	800	0.60/	148.8	3.0/ 65.4		0.12/67.7		0.17/-	154.8	11.8
	1000	0.60/	138.2	2.4/ 57.7		0.14/68.3		0.18/-	167.5	9.8
	1200	0.60/	128.4	2.0/ 51.2		0.17/69.9		0.19/-	178.9	8.1
	1500	0.60/	113.8	1.6/ 42.3		0.21/67.7		0.22/	168.5	6.3
	2000	0.61/	92.0	1.1/ 31.1		0.29/65.7		0.29/	146.1	3.4

Data sheet	
status	Product specification
date of issue	April 1991

BFG55

PNP 4 GHz wideband transistor

FEATURES

- High output voltage capability
- High gain bandwidth product
- Good thermal stability
- Gold metallization ensures excellent reliability
- Complementary npn type BFG35.

DESCRIPTION

PNP planar epitaxial transistor intended for wideband amplifier applications.

The BFG55 is mounted in a SOT223 plastic envelope.

MECHANICAL DATA

Plastic SOT223 envelope.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	-	25	V
$-V_{CEO}$	collector-emitter voltage	open base	-	-	18	V
$-I_C$	collector current (DC)		-	-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$; note 1	-	-	1	W
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
h_{FE}	DC current gain	$-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	4	-	GHz
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	11	-	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $f_{(p+q-r)} = 848.25\text{ MHz}$	-	750	-	mV

Note

1. T_{case} temperature measured on soldering point of collector tab.

PNP 4 GHz wideband transistor**BFG55****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG55	SOT223	bulk	500
BFG55	SOT223	12 mm reel	1000

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CB0}$	collector-base voltage	open emitter	-	25	V
$-V_{CE0}$	collector-emitter voltage	open base	-	18	V
$-V_{EB0}$	emitter-base voltage	open collector	-	2	V
$-I_C$	collector current (DC)		-	150	mA
P_{tot}	total power dissipation	$T_{case} = 135\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-c}$	from junction to case	35	K/W

PNP 4 GHz wideband transistor**BFG55****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{(BR)CBO}$	collector-base breakdown voltage	open emitter $-I_C = 0.1\text{ mA}$	25	-	-	V
$-V_{(BR)CEO}$	collector-emitter breakdown voltage	open base $-I_C = 10\text{ mA}$	18	-	-	V
$-V_{(BR)EBO}$	emitter-base breakdown voltage	open collector $-I_E = 0.1\text{ mA}$	3	-	-	V
$-I_{CBO}$	collector cut-off current	$-I_E = 0$; $-V_{CB} = 10\text{ V}$	-	-	1	μA
h_{FE}	DC current gain	$-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$	-	25	-	
C_C	collector-base capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{CB} = 10\text{ V}$	-	2.3	-	pF
C_e	emitter-base capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{EB} = 10\text{ V}$	-	8	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $-I_C = 0$; $-V_{CE} = 10\text{ V}$	-	1.7	-	pF
f_T	transition frequency	$f = 500\text{ MHz}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	4	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	15	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $-I_C = 100\text{ mA}$; $-V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	11	-	dB
V_o	output voltage	see note 1	-	750	-	mV
V_o	output voltage	see note 2	-	800	-	mV

Note

1. $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $-I_C = 100\text{ mA}$;
 $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 850.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 858.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 860.25\text{ MHz}$;
Measured at $f_{(p+q+r)} = 848.25\text{ MHz}$.
2. $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $-I_C = 100\text{ mA}$;
 $-V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 445.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 453.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 455.25\text{ MHz}$;
Measured at $f_{(p+q-r)} = 443.25\text{ MHz}$.

PNP 4 GHz wideband transistor

BFG55

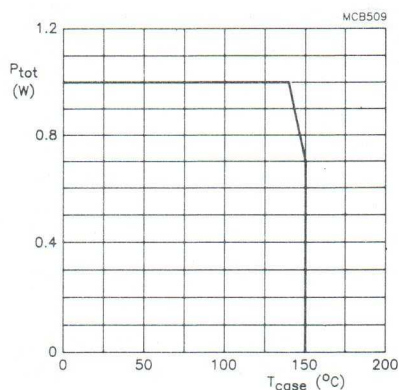
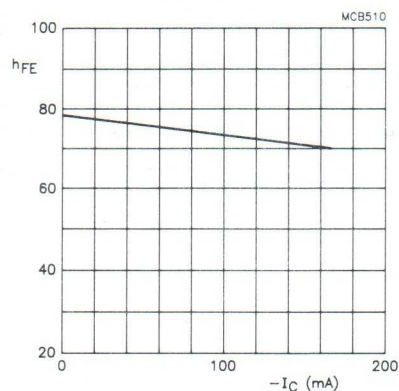
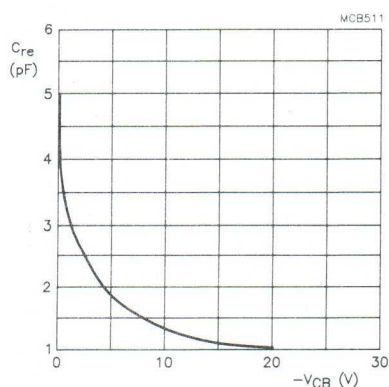
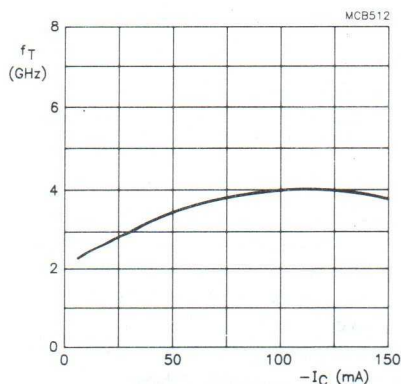


Fig.1 Power derating curve.

Fig.2 DC current gain as a function of collector current; $-V_{CE} = 10$ V; $T_{amb} = 25$ °C.Fig.3 Feedback capacitance as a function of collector-base voltage; $f = 1$ MHz; $T_{amb} = 25$ °C; typical values.Fig.4 Transition frequency as a function of collector current; $-V_{CE} = 10$ V; $T_{amb} = 25$ °C; typical values.

PNP 4 GHz wideband transistor

BFG55

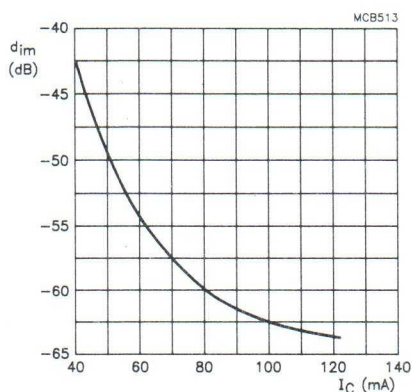


Fig.5 Intermodulation distortion as a function of collector current; $-V_{CE} = 10$ V; $V_o = 650$ mV; $T_{amb} = 25$ °C; $f_{(p+q-r)} = 443.25$ MHz.

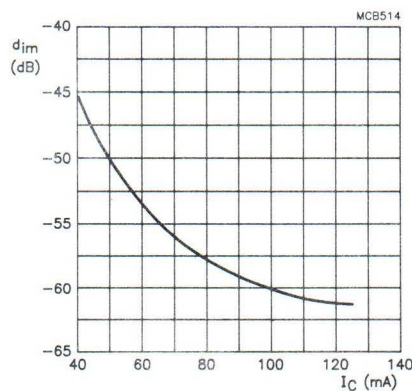


Fig.6 Intermodulation distortion as a function of collector current; $-V_{CE} = 10$ V; $V_o = 600$ mV; $T_{amb} = 25$ °C; $f_{(p+q-r)} = 848.25$ MHz.

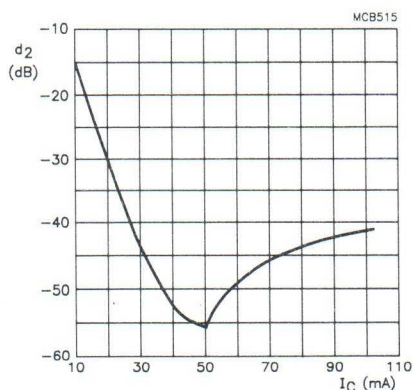


Fig.7 Second order beat as a function of collector current; $-V_{CE} = 10$ V; $V_o = 50$ dBmV; $T_{amb} = 25$ °C; $f_{(p+q)} = 450$ MHz.

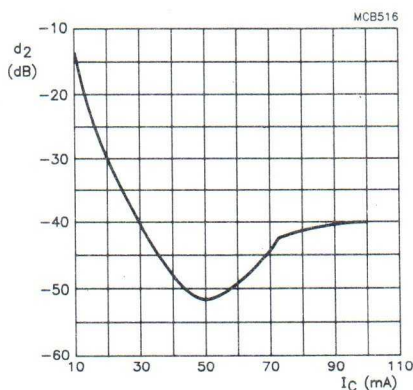


Fig.8 Second order beat as a function of collector current; $-V_{CE} = 10$ V; $V_o = 50$ dBmV; $T_{amb} = 25$ °C; $f_{(p+q)} = 810$ MHz.

NPN 7 GHz WIDEBAND TRANSISTOR

NPN transistor in a four-lead dual emitter plastic envelope (SOT143). A version with reverse pinning is available on request. It is designed for wideband application in the GHz range, such as satellite TV systems (SATV) and repeater amplifiers in fibre-optical systems. The device features a very high transition frequency, high gain and a very low noise figure up to high frequencies.

QUICK REFERENCE DATA

Collector-base voltage	V_{CBO}	max.	20 V
Collector-emitter voltage	V_{CEO}	max.	10 V
Collector current (DC)	I_C	max.	50 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$
DC current gain $I_C = 15\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min. typ.	60 100
Transition frequency at $f = 500\text{ MHz}$ $I_C = 15\text{ mA}; V_{CE} = 8\text{ V}$	f_T	typ.	7.5 GHz
Maximum unilateral power gain at $f = 2\text{ GHz}$ $I_C = 15\text{ mA}; V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	G_{UM}	typ.	10.0 dB
Noise figure at $f = 2\text{ GHz}$ $Z_S = 60\text{ }\Omega; T_{amb} = 25\text{ }^{\circ}\text{C}$ $I_C = 5\text{ mA}; V_{CE} = 8\text{ V}$	F	typ.	2.5 dB
$I_C = 15\text{ mA}; V_{CE} = 8\text{ V}$	F	typ.	3.0 dB

MECHANICAL DATA

SOT143

Marking code:

BFG67 : V3

BFG67X: V12

Pinning:

BFG67

1 = collector

2 = base

3,4 = emitter

BFG67X

1 = collector

2,4 = emitter

3 = base

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20 V
Collector-emitter voltage (open base)	V_{CEO}	max.	10 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2.5 V
Collector current (DC)	I_C	max.	50 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$ mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm	P_{tot}	max.	300 mW
Storage temperature range	T_{stg}		-65 to $+150^\circ\text{C}$
Junction temperature	T_j	max.	150°C

THERMAL RESISTANCE

From junction to ambient

mounted on a ceramic substrate of
8 mm x 10 mm x 0.7 mm

$$R_{th\ j-a} = 430\ \text{K/W}$$

CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$$I_E = 0; V_{CB} = 10\ \text{V}$$

$$I_{CBO} \text{ max. } 50\ \text{nA}$$

DC current gain

$$I_C = 15\ \text{mA}; V_{CE} = 5\ \text{V}$$

$$h_{FE} \text{ min. } 60 \\ \text{typ. } 100$$

Transition frequency at $f = 500\ \text{MHz}$

$$I_C = 15\ \text{mA}; V_{CE} = 8\ \text{V}$$

$$f_T \text{ typ. } 7.5\ \text{GHz}$$

Collector capacitance at $f = 1\ \text{MHz}$

$$I_E = I_c = 0; V_{CB} = 8\ \text{V}$$

$$C_c \text{ typ. } 0.7\ \text{pF}$$

Emitter capacitance at $f = 1\ \text{MHz}$

$$I_C = I_c = 0; V_{EB} = 0.5\ \text{V}$$

$$C_e \text{ typ. } 1.3\ \text{pF}$$

Feedback capacitance at $f = 1\ \text{MHz}$

$$I_C = 0; V_{CE} = 8\ \text{V}$$

$$C_{re} \text{ typ. } 0.5\ \text{pF}$$

Maximum unilateral power gain (S_{12} assumed to be zero)

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{[1 - |S_{11}|^2][1 - |S_{22}|^2]}$$

$$\text{at } I_C = 15\ \text{mA}; V_{CE} = 8\ \text{V};$$

$$f = 2\ \text{GHz}; T_{amb} = 25^\circ\text{C}$$

$$G_{UM} \text{ typ. } 10.0\ \text{dB}$$

Noise figures at $f = 800\ \text{MHz}$; $Z_S = \text{opt.}$;

$$T_{amb} = 25^\circ\text{C}; V_{CE} = 8\ \text{V}$$

$$I_C = 5\ \text{mA}$$

$$I_C = 15\ \text{mA}$$

$$F \text{ typ. } 0.8\ \text{dB}$$

$$F \text{ typ. } 1.5\ \text{dB}$$

Noise figures at $f = 2\ \text{GHz}$; $Z_S = 60\ \Omega$

$$T_{amb} = 25^\circ\text{C}; V_{CE} = 8\ \text{V}$$

$$I_C = 5\ \text{mA}$$

$$I_C = 15\ \text{mA}$$

$$F \text{ typ. } 2.5\ \text{dB}$$

$$F \text{ typ. } 3.0\ \text{dB}$$

s-parameters (common emitter) at $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

I_C mA	f MHz	S_{11} Φ		S_{21} Φ		S_{12} Φ		S_{22} Φ		G_{UM} dB
		M	Φ	M	Φ	M	Φ	M	Φ	
2	40	0,96/	-6,8°	5,8/177,8°		0,01/	84,5°	0,99/	-3,2°	44,1
	100	0,98/	-20,8°	5,6/165,8°		0,03/	77,5°	1,01/	-10,0°	46,5
	200	0,89/	-40,1°	5,1/153,2°		0,05/	66,8°	0,91/	-19,0°	28,7
	500	0,81/	-89,3°	4,3/121,5°		0,09/	43,4°	0,79/	-38,5°	21,5
	800	0,68/	-123,0°	3,3/102,0°		0,11/	33,8°	0,67/	-50,0°	15,7
	1000	0,64/	-139,9°	2,8/ 89,8°		0,11/	28,0°	0,65/	-54,5°	13,7
	1200	0,60/	-157,3°	2,3/ 81,1°		0,11/	25,8°	0,62/	-61,7°	11,5
	1500	0,59/	-173,3°	2,0/ 71,8°		0,11/	27,4°	0,55/	-69,3°	9,5
	2000	0,57/	+161,7°	1,5/ 56,3°		0,10/	32,2°	0,54/	-85,8°	6,7
5	40	0,91/	-10,9°	13,5/174,8°		0,01/	83,3°	0,98/	-5,9°	44,2
	100	0,91/	-30,3°	12,6/159,5°		0,03/	72,2°	0,96/	-17,0°	40,9
	200	0,79/	-56,3°	10,6/143,5°		0,04/	60,3°	0,81/	-29,5°	29,3
	500	0,64/	-115,9°	7,4/109,8°		0,07/	41,4°	0,58/	-50,8°	21,5
	800	0,55/	-145,5°	5,2/ 93,5°		0,08/	39,9°	0,48/	-59,5°	17,1
	1000	0,53/	-161,4°	4,2/ 84,0°		0,08/	39,1°	0,44/	-62,2°	15,0
	1200	0,52/	-176,5°	3,5/ 77,8°		0,08/	41,2°	0,42/	-67,1°	13,1
	1500	0,51/	+172,2°	2,9/ 69,1°		0,09/	44,6°	0,38/	-75,7°	11,3
	2000	0,50/	+149,8°	2,2/ 56,7°		0,11/	49,8°	0,38/	-89,5°	8,7
10	40	0,85/	-16,1°	23,5/170,6°		0,01/	80,1°	0,96/	-9,7°	43,8
	100	0,81/	-42,6°	21,3/151,8°		0,02/	67,2°	0,89/	-25,2°	38,0
	200	0,67/	-76,3°	16,6/133,0°		0,04/	55,5°	0,68/	-40,0°	29,6
	500	0,54/	-137,5°	9,5/101,5°		0,05/	45,7°	0,42/	-60,2°	21,9
	800	0,49/	-161,8°	6,3/ 88,5°		0,07/	49,2°	0,35/	-67,0°	17,7
	1000	0,49/	-175,2°	5,1/ 80,5°		0,07/	50,6°	0,32/	-68,9°	15,8
	1200	0,49/	+171,5°	4,2/ 75,8°		0,08/	53,4°	0,29/	-72,5°	13,9
	1500	0,47/	+163,5°	3,5/ 67,5°		0,09/	55,3°	0,28/	-82,1°	12,3
	2000	0,47/	+142,5°	2,6/ 56,8°		0,12/	57,7°	0,29/	-94,5°	9,6
15	40	0,80/	-20,1°	31,0/167,8°		0,01/	76,4°	0,94/	-12,2°	43,5
	100	0,74/	-51,8°	26,9/146,8°		0,02/	64,1°	0,83/	-30,3°	37,2
	200	0,60/	-89,4°	19,9/126,7°		0,03/	54,0°	0,60/	-45,5°	29,8
	500	0,51/	-147,5°	10,3/ 98,0°		0,05/	49,7°	0,35/	-64,9°	22,1
	800	0,47/	-168,5°	6,7/ 86,5°		0,06/	54,6°	0,29/	-70,8°	18,1
	1000	0,47/	+179,2°	5,4/ 79,3°		0,07/	55,9°	0,27/	-72,8°	16,1
	1200	0,48/	+166,5°	4,4/ 75,0°		0,08/	58,4°	0,24/	-75,8°	14,3
	1500	0,46/	+160,0°	3,7/ 67,0°		0,10/	59,2°	0,24/	-86,0°	12,5
	2000	0,45/	+139,5°	2,7/ 56,8°		0,12/	60,2°	0,25/	-97,8°	10,0
20	40	0,76/	-23,8°	37,2/165,4°		0,01/	75,6°	0,92/	-14,3°	43,3
	100	0,69/	-60,0°	31,2/142,6°		0,02/	61,7°	0,78/	-34,3°	36,8
	200	0,55/	-99,6°	21,8/122,5°		0,03/	53,6°	0,54/	-49,5°	29,8
	500	0,49/	-152,5°	10,6/ 96,0°		0,04/	53,0°	0,31/	-68,0°	22,2
	800	0,46/	-172,9°	7,0/ 85,0°		0,06/	58,1°	0,26/	-73,3°	18,2
	1000	0,46/	+175,9°	5,5/ 78,3°		0,07/	59,3°	0,24/	-75,3°	16,1
	1200	0,47/	+163,5°	4,6/ 74,3°		0,08/	61,5°	0,21/	-78,3°	14,5
	1500	0,45/	+157,9°	3,8/ 66,4°		0,10/	61,4°	0,22/	-88,9°	12,8
	2000	0,45/	+137,8°	2,8/ 56,7°		0,12/	61,7°	0,22/	-100,2°	10,2

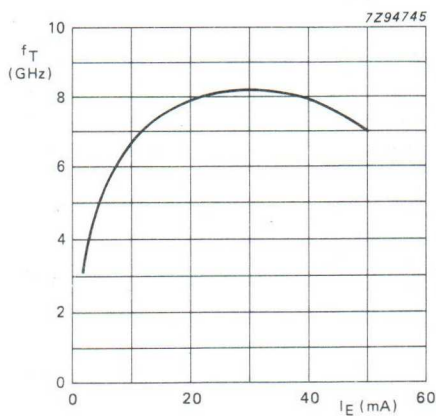


Fig.1 $V_{CE} = 8$ V; $f = 500$ MHz;
 $T_{amb} = 25$ °C; typical values.

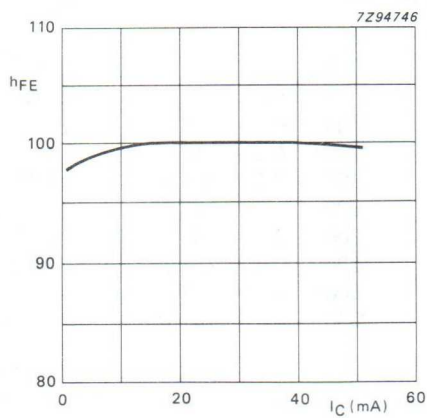


Fig.2 $V_{CE} = 5$ V; $T_{amb} = 25$ °C;
typical values.

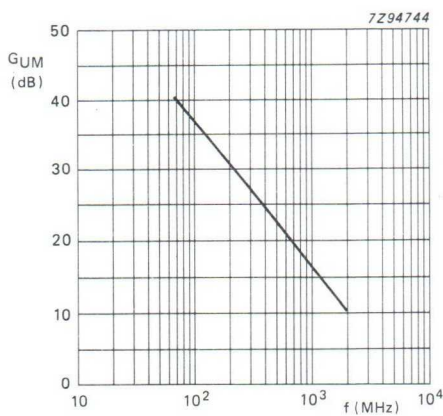


Fig.3 $V_{CE} = 8$ V; $I_C = 15$ mA;
 $T_{amb} = 25$ °C; typical values.

NPN 5 GHz WIDEBAND TRANSISTOR

NPN transistor in a four-lead dual-emitter SOT143 envelope. The device is primarily intended for use in vhf and uhf wideband amplifiers and features low noise and high power gain.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	20 V
Collector-emitter voltage (open base)	V_{CEO}	max.	15 V
Collector current (DC)	I_C	max.	25 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 $^\circ\text{C}$
DC current gain $I_C = 14\text{ mA}; V_{CE} = 10\text{ V}$	h_{FE}	min. typ.	40 90
Transition frequency at $f = 500\text{ MHz}$ $I_C = 14\text{ mA}; V_{CE} = 10\text{ V}$	f_T	typ.	5.0 GHz
Feedback capacitance at $f = 1\text{ MHz}$ $I_C = 0; V_{CE} = 10\text{ V}$	C_{re}	typ.	0.35 pF
Noise figure at $f = 800\text{ MHz}$ $I_C = 4\text{ mA}; V_{CE} = 10\text{ V}; Z_S = \text{opt.}$	F	typ.	1.8 dB
Maximum unilateral power gain $I_C = 14\text{ mA}; V_{CE} = 10\text{ V}$ $f = 800\text{ MHz}$ $f = 2\text{ GHz}$	G_{UM}	typ. typ.	17.5 dB 9.5 dB

MECHANICAL DATA

SOT143

Marking code:

BFG92A: P8

BFG92AX: V14

Pinning

BFG92A

1 = collector
2 = base
3, 4 = emitter

BFG92AX

1 = collector
2, 4 = emitter
3 = base

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V _{CBO}	max.	20 V
Collector-emitter voltage (open base)	V _{CEO}	max.	15 V
Emitter-base voltage (open collector)	V _{EBO}	max.	2 V
Collector current (DC)	I _C	max.	25 mA
Total power dissipation up to T _{amb} = 25 °C and mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm	P _{tot}	max.	300 mW
Storage temperature range	T _{stg}		−65 to +150 °C
Junction temperature	T _j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient
and mounted on a ceramic substrate
of 8 mm x 10 mm x 0.7 mm

R _{th j-a}	=	430 K/W
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CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current

I_E = 0; V_{CB} = 10 V

I _{CBO}	max.	50 nA
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DC current gain

I_C = 14 mA; V_{CE} = 10 V

h _{FE}	min.	40
	typ.	90

Transition frequency at f = 500 MHz

I_C = 14 mA; V_{CE} = 10 V

f _T	typ.	5.0 GHz
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Collector capacitance at f = 1 MHz

I_E = I_e = 0; V_{CB} = 10 V

C _c	typ.	0.6 pF
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Emitter capacitance at f = 1 MHz

I_C = I_c = 0; V_{EB} = 0.5 V

C _e	typ.	1.2 pF
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Feedback capacitance at f = 1 MHz

I_C = 0; V_{CE} = 10 V

C _{re}	typ.	0.35 pF
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Maximum unilateral power gain (S₁₂ assumed to be zero)

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{[1 - |S_{11}|^2][1 - |S_{22}|^2]}$$

I_C = 14 mA; V_{CE} = 10 V; T_{amb} = 25 °C;

f = 800 MHz

f = 2 GHz

G _{UM}	typ.	17.5 dB
	typ.	9.5 dB

Noise figure at f = 800 MHz and T_{amb} = 25 °C

I_C = 4 mA; V_{CE} = 10 V; Z_S = opt.

F	typ.	1.8 dB
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s-parameters (common emitter) at $V_{CE} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values

I _C mA	f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂		GUM dB
		M	Φ	M	Φ	M	Φ	M	Φ	
2	40	0,87/	-9,1°	7,0/174,7°		0,01/	82,1°	1,00/	-2,8°	50,0
	100	0,88/	-26,2°	6,9/162,5°		0,02/	75,2°	1,01/	-9,0°	39,6
	200	0,79/	-49,8°	6,1/148,0°		0,04/	65,0°	0,92/	-16,6°	28,2
	500	0,68/	-102,5°	4,6/115,2°		0,07/	44,4°	0,81/	-30,0°	20,6
	800	0,59/	-153,5°	3,2/ 97,7°		0,07/	39,3°	0,73/	-39,7°	15,3
	1000	0,56/	-149,0°	2,7/ 86,8°		0,08/	36,6°	0,73/	-44,0°	13,6
	1200	0,54/	-164,7°	2,2/ 78,4°		0,08/	36,1°	0,72/	-50,8°	11,5
	1500	0,53/	-178,6°	1,9/ 70,8°		0,08/	40,6°	0,63/	-57,9°	9,0
	2000	0,51/	158,1°	1,4/ 55,7°		0,08/	46,3°	0,63/	-76,2°	6,3
5	40	0,74/	-14,0°	14,4/172,1°		0,01/	80,4°	0,99/	-4,8°	45,2
	100	0,73/	-37,7°	13,8/156,7°		0,02/	71,0°	0,98/	-13,8°	39,6
	200	0,64/	-68,7°	11,4/138,8°		0,03/	60,1°	0,84/	-22,8°	28,7
	500	0,55/	-126,5°	7,0/106,5°		0,05/	46,3°	0,66/	-35,0°	21,0
	800	0,50/	-152,7°	4,7/ 91,5°		0,06/	47,4°	0,59/	-42,8°	16,6
	1000	0,49/	-166,7°	3,9/ 82,7°		0,06/	47,8°	0,59/	-45,9°	14,8
	1200	0,48/	179,7°	3,2/ 76,1°		0,07/	49,8°	0,58/	-51,3°	12,9
	1500	0,48/	169,9°	2,6/ 69,0°		0,08/	54,2°	0,51/	-58,7°	10,8
	2000	0,48/	148,9°	1,9/ 56,0°		0,09/	57,5°	0,51/	-75,9°	8,2
10	40	0,59/	-21,1°	23,6/168,8°		0,01/	73,4°	0,98/	-7,3°	44,3
	100	0,57/	-53,7°	21,6/149,8°		0,02/	67,1°	0,92/	-19,0°	36,7
	200	0,50/	-92,0°	16,2/129,8°		0,02/	56,9°	0,74/	-28,5°	28,9
	500	0,48/	-146,3°	8,7/100,2°		0,04/	52,2°	0,54/	-37,6°	21,4
	800	0,46/	-167,6°	5,7/ 87,5°		0,05/	56,9°	0,49/	-44,1°	17,3
	1000	0,46/	-179,1°	4,6/ 80,0°		0,06/	57,9°	0,50/	-46,6°	15,5
	1200	0,47/	169,1°	3,8/ 74,6°		0,06/	60,0°	0,48/	-51,1°	13,7
	1500	0,46/	162,3°	3,1/ 67,9°		0,08/	62,4°	0,44/	-59,1°	11,7
	2000	0,46/	142,8°	2,3/ 56,3°		0,09/	63,8°	0,44/	-75,9°	9,2
14	40	0,50/	-26,3°	28,8/166,7°		0,01/	74,4°	0,98/	-8,8°	43,9
	100	0,49/	-64,6°	25,4/145,8°		0,02/	66,4°	0,89/	-21,5°	36,2
	200	0,46/	-105,3°	18,2/125,5°		0,02/	57,5°	0,68/	-30,6°	29,0
	500	0,47/	-154,3°	9,2/ 97,9°		0,03/	56,7°	0,50/	-37,8°	21,6
	800	0,45/	-173,4°	6,0/ 86,0°		0,05/	61,1°	0,46/	-44,0°	17,5
	1000	0,46/	176,3°	4,8/ 78,8°		0,05/	52,2°	0,46/	-46,4°	15,7
	1200	0,47/	165,3°	3,9/ 73,9°		0,06/	63,8°	0,45/	-50,7°	13,9
	1500	0,46/	159,5°	3,2/ 67,3°		0,08/	65,4°	0,41/	-59,1°	12,0
	2000	0,46/	140,6°	2,4/ 56,1°		0,10/	65,9°	0,41/	-75,8°	9,5
20	40	0,42/	-33,9°	34,3/164,1°		0,01/	73,6°	0,97/	-10,4°	43,3
	100	0,43/	-79,0°	28,8/141,3°		0,01/	63,1°	0,84/	-24,0°	35,4
	200	0,42/	-120,1°	19,7/121,0°		0,02/	58,1°	0,63/	-31,3°	29,0
	500	0,46/	-162,0°	9,4/ 95,5°		0,03/	60,6°	0,46/	-37,1°	21,6
	800	0,45/	-178,4°	6,1/ 84,5°		0,05/	65,0°	0,43/	-43,5°	17,6
	1000	0,46/	172,4°	4,9/ 77,8°		0,05/	65,6°	0,44/	-45,9°	15,7
	1200	0,48/	162,3°	4,0/ 73,1°		0,06/	66,9°	0,43/	-50,1°	14,0
	1500	0,46/	157,2°	3,3/ 66,7°		0,08/	67,3°	0,39/	-58,9°	12,1
	2000	0,47/	138,9°	2,5/ 55,8°		0,10/	67,6°	0,39/	-75,9°	9,5

s-parameters (common-emitter) at $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

I_C mA	f MHz	S_{11}		S_{21}		S_{12}		S_{22}		G_{UM} dB
		M	Φ	M	Φ	M	Φ	M	Φ	
2	40	0,87/	-8,9°	6,8/174,8°		0,01/	80,8°	1,00/	-2,5°	49,9
	100	0,88/	-25,8°	6,8/162,8°		0,02/	76,3°	1,01/	-8,8°	39,5
	200	0,79/	-49,3°	6,0/148,3°		0,04/	64,8°	0,92/	-16,3°	28,2
	500	0,69/	-101,8°	4,5/115,5°		0,07/	44,9°	0,82/	-29,8°	20,6
	800	0,59/	-131,9°	3,2/ 98,0°		0,08/	39,1°	0,73/	-39,6°	15,2
	1000	0,56/	-148,5°	2,7/ 87,0°		0,08/	36,3°	0,73/	-43,8°	13,5
	1200	0,54/	-164,1°	2,2/ 78,6°		0,08/	36,3°	0,72/	-50,7°	11,5
	1500	0,53/	-178,2°	1,8/ 71,0°		0,08/	40,5°	0,64/	-57,8°	9,0
	2000	0,52/	158,5°	1,4/ 55,8°		0,08/	46,3°	0,63/	-76,2°	6,3
5	40	0,73/	-14,1°	14,6/172,2°		0,01/	77,9°	0,99/	-4,8°	44,6
	100	0,72/	-37,9°	14,1/156,6°		0,02/	71,0°	0,98/	-13,8°	39,7
	200	0,63/	-69,2°	11,6/138,7°		0,03/	60,3°	0,83/	-22,9°	28,6
	500	0,55/	-127,0°	7,1/106,4°		0,05/	46,4°	0,66/	-35,0°	21,1
	800	0,50/	-153,1°	4,8/ 91,5°		0,06/	48,0°	0,58/	-42,7°	16,6
	1000	0,49/	-167,1°	3,9/ 82,8°		0,06/	48,6°	0,59/	-45,8°	14,8
	1200	0,48/	179,5°	3,2/ 76,2°		0,07/	50,2°	0,58/	-51,1°	12,9
	1500	0,48/	169,8°	2,6/ 69,2°		0,08/	54,7°	0,51/	-58,6°	10,8
	2000	0,47/	148,7°	2,0/ 56,3°		0,09/	58,0°	0,51/	-75,8°	8,2
10	40	0,59/	-20,9°	23,7/168,9°		0,01/	76,7°	0,98/	-7,2°	43,5
	100	0,57/	-53,5°	21,6/149,9°		0,02/	67,5°	0,92/	-18,8°	36,7
	200	0,50/	-91,7°	16,2/130,0°		0,02/	58,0°	0,74/	-28,3°	28,9
	500	0,48/	-146,0°	8,7/100,5°		0,04/	52,4°	0,55/	-37,3°	21,5
	800	0,46/	-167,3°	5,7/ 87,7°		0,05/	57,2°	0,49/	-43,7°	17,3
	1000	0,46/	-178,8°	4,6/ 80,3°		0,06/	58,3°	0,50/	-46,3°	15,5
	1200	0,47/	169,4°	3,8/ 74,8°		0,06/	60,2°	0,48/	-50,9°	13,7
	1500	0,46/	162,5°	3,1/ 68,0°		0,08/	62,7°	0,44/	-58,9°	11,7
	2000	0,46/	143,1°	2,3/ 56,5°		0,09/	64,0°	0,44/	-75,6°	9,2
14	40	0,51/	-25,9°	28,5/166,9°		0,01/	72,3°	0,98/	-8,5°	43,9
	100	0,50/	-63,8°	25,4/146,1°		0,02/	65,3°	0,89/	-21,3°	36,2
	200	0,46/	-104,5°	18,2/125,8°		0,02/	57,6°	0,69/	-30,3°	29,0
	500	0,47/	-153,6°	9,2/ 98,2°		0,03/	55,7°	0,50/	-37,5°	21,6
	800	0,45/	-172,9°	6,0/ 86,2°		0,05/	61,3°	0,46/	-43,7°	17,5
	1000	0,46/	176,8°	4,8/ 79,0°		0,05/	62,6°	0,46/	-46,2°	15,7
	1200	0,47/	165,8°	3,9/ 74,1°		0,06/	63,7°	0,45/	-50,4°	14,0
	1500	0,46/	159,9°	3,2/ 67,5°		0,08/	65,3°	0,41/	-58,9°	12,0
	2000	0,46/	140,9°	2,4/ 56,4°		0,09/	65,9°	0,41/	-75,6°	9,5
20	40	0,42/	-32,2°	34,3/165,3°		0,01/	72,8°	0,97/	-9,3°	43,3
	100	0,43/	-77,0°	28,8/142,5°		0,01/	65,2°	0,85/	-22,9°	35,7
	200	0,43/	-118,2°	19,7/122,1°		0,02/	58,3°	0,64/	-30,8°	29,0
	500	0,46/	-160,6°	9,5/ 96,5°		0,03/	61,6°	0,47/	-36,0°	21,7
	800	0,45/	-177,2°	6,1/ 85,5°		0,05/	65,4°	0,43/	-42,3°	17,6
	1000	0,46/	173,6°	4,9/ 78,8°		0,05/	66,7°	0,44/	-44,8°	15,8
	1200	0,48/	163,5°	4,0/ 74,1°		0,06/	68,0°	0,43/	-49,1°	14,1
	1500	0,46/	158,3°	3,3/ 67,5°		0,08/	68,9°	0,39/	-57,7°	12,1
	2000	0,47/	139,9°	2,5/ 56,7°		0,10/	68,4°	0,40/	-74,7°	9,6

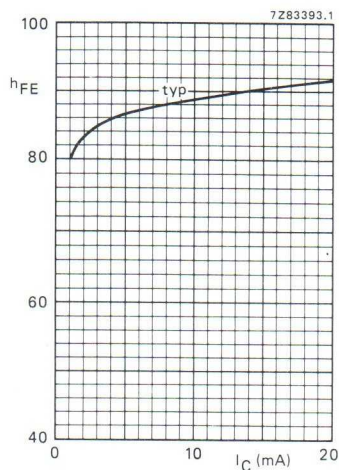


Fig.1 Gain as a function of collector current.
 $V_{CE} = 10\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$;
 typical values.

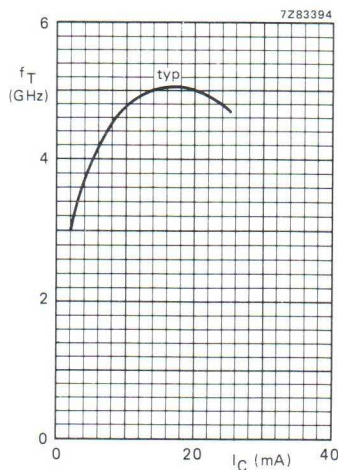


Fig.2 Transition frequency as a function of collector current.
 $V_{CE} = 10\text{ V}$; $f = 500\text{ MHz}$;
 $T_j = 25\text{ }^{\circ}\text{C}$; typical values.

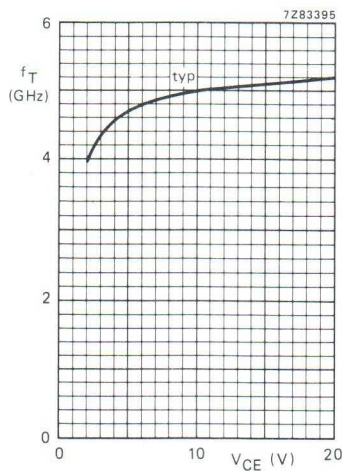


Fig.3 Transition frequency as a function of V_{CE} .
 $I_C = 14\text{ mA}$; $f = 500\text{ MHz}$; $T_j = 25\text{ }^{\circ}\text{C}$; typical values.

NPN 5 GHz WIDEBAND TRANSISTOR

NPN transistor in a four-lead dual-emitter SOT143 envelope. The device is primarily intended for use in UHF and microwave amplifiers and features low noise and high power gain.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CB0}	max.	15 V
Collector-emitter voltage (open base)	V_{CEO}	max.	12 V
Collector current (DC)	I_C	max.	35 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150°C
DC current gain $I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min. typ.	40 90
Transition frequency at $f = 500\text{ MHz}$ $I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$	f_T	typ.	6.0 GHz
Feedback capacitance at $f = 1\text{ MHz}$ $I_C = 0; V_{CE} = 5\text{ V}$	C_{re}	typ.	0.6 pF
Noise figure at $f = 800\text{ MHz}$ $I_C = 4\text{ mA}; V_{CE} = 8\text{ V}; Z_S = \text{opt.}$	F	typ.	1.6 dB
Maximum unilateral power gain $I_C = 30\text{ mA}; V_{CE} = 8\text{ V}$ $f = 800\text{ MHz}$ $f = 2\text{ GHz}$	GUM	typ. typ.	17.0 dB 9.0 dB

MECHANICAL DATA

Dimensions in mm

SOT143

Pinning

BFG93A	BFG93AX
1 = collector	1 = collector
3,4 = emitter	2,4 = emitter
2 = base	3 = base

Marking code:

BFG93A : R8
BFG93AX: V15

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CB0}	max.	15 V
Collector-emitter voltage (open base)	V_{CEO}	max.	12 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2 V
Collector current (DC)	I_C	max.	35 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ and mounted on a ceramic substrate of 8 mm x 10 mm x 0.7 mm	P_{tot}	max.	300 mW
Storage temperature range	T_{stg}		-65 to +150 $^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient

and mounted on a ceramic substrate
of 8 mm x 10 mm x 0.7 mm

$R_{th\ j-a}$	=	430 K/W
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CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; V_{CB} = 5\text{ V}$

I_{CBO}	max.	50 nA
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DC current gain

$I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$

h_{FE}	min.	40
	typ.	90

Transition frequency at $f = 500\text{ MHz}$

$I_C = 30\text{ mA}; V_{CE} = 5\text{ V}$

f_T	typ.	6.0 GHz
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Collector capacitance at $f = 1\text{ MHz}$

$I_E = I_e = 0; V_{CB} = 5\text{ V}$

C_c	typ.	0.9 pF
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Emitter capacitance at $f = 1\text{ MHz}$

$I_C = I_c = 0; V_{EB} = 0.5\text{ V}$

C_e	typ.	2.5 pF
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Feedback capacitance at $f = 1\text{ MHz}$

$I_C = 0; V_{CE} = 5\text{ V}$

C_{re}	typ.	0.6 pF
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Maximum unilateral power gain (S_{12} assumed to be zero)

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{[1 - |S_{11}|^2][1 - |S_{22}|^2]}$$

$I_C = 30\text{ mA}; V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C};$

$f = 800\text{ MHz}$

$f = 2\text{ GHz}$

G_{UM}	typ.	17.0 dB
	typ.	9.0 dB

Noise figure at $f = 800\text{ MHz}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$

$I_C = 4\text{ mA}; V_{CE} = 8\text{ V}; Z_S = \text{opt.}$

F	typ.	1.6 dB
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s-parameters (common emitter) at $V_{CE} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values

I _C mA	f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} dB
		M	Φ	M	Φ	M	Φ	M	Φ	
2	40	0,93/	-10,4°	7,1/174,6°	0,02/	84,9°	1,00/	-3,3°	52,9	
	100	0,93/	-30,9°	7,0/160,6°	0,03/	73,5°	1,00/	-11,9°	52,8	
	200	0,83/	-58,3°	6,0/144,6°	0,06/	60,4°	0,88/	-22,1°	27,2	
	500	0,74/	-115,5°	4,2/110,2°	0,10/	36,5°	0,71/	-40,3°	18,9	
	800	0,67/	-144,9°	2,9/ 92,5°	0,11/	29,0°	0,61/	-51,6°	13,9	
	1000	0,65/	-161,0°	2,4/ 81,5°	0,11/	25,2°	0,60/	-55,8°	12,0	
	1200	0,64/	-175,0°	2,0/ 73,9°	0,10/	25,2°	0,58/	-62,7°	9,9	
	1500	0,64/	+171,3°	1,7/ 64,5°	0,11/	28,1°	0,52/	-72,1°	8,1	
2000	0,63/	+148,8°	1,2/ 49,6°	0,10/	35,4°	0,52/	-90,7°	5,5		
5	40	0,86/	-17,1°	16,2/171,0°	0,01/	81,2°	0,99/	-7,5°	46,5	
	100	0,83/	-46,6°	15,2/152,3°	0,03/	66,6°	0,92/	-21,4°	36,9	
	200	0,72/	-82,0°	11,6/133,0°	0,05/	53,3°	0,73/	-34,7°	27,8	
	500	0,63/	-140,5°	6,5/101,0°	0,07/	38,0°	0,48/	-52,8°	19,6	
	800	0,60/	-164,4°	4,3/ 87,0°	0,08/	39,2°	0,41/	-61,7°	15,4	
	1000	0,59/	-177,4°	3,5/ 78,3°	0,08/	39,9°	0,39/	-64,2°	13,4	
	1200	0,59/	+170,7°	2,9/ 72,9°	0,09/	43,3°	0,37/	-69,0°	11,6	
	1500	0,58/	+160,8°	2,4/ 64,2°	0,10/	46,6°	0,34/	-79,5°	9,9	
2000	0,58/	+140,3°	1,8/ 51,8°	0,11/	51,4°	0,35/	-95,8°	7,4		
10	40	0,78/	-25,7°	27,2/166,2°	0,01/	78,4°	0,97/	-12,5°	44,5	
	100	0,72/	-64,9°	23,2/143,3°	0,03/	61,1°	0,83/	-31,4°	35,5	
	200	0,62/	-105,0°	16,2/123,2°	0,04/	50,0°	0,59/	-45,9°	28,1	
	500	0,59/	-155,7°	7,9/ 95,5°	0,05/	44,9°	0,34/	-63,2°	20,3	
	800	0,56/	-175,9°	5,1/ 83,5°	0,07/	50,4°	0,29/	-70,7°	16,2	
	1000	0,57/	+173,2°	4,1/ 76,3°	0,07/	52,3°	0,27/	-72,7°	14,3	
	1200	0,58/	+162,5°	3,4/ 72,1°	0,08/	55,6°	0,25/	-76,2°	12,5	
	1500	0,56/	+154,8°	2,8/ 63,8°	0,10/	56,6°	0,25/	-88,2°	10,8	
2000	0,56/	+135,3°	2,1/ 52,8°	0,13/	58,5°	0,26/	-102,7°	8,4		
20	40	0,65/	-39,4°	42,2/159,3°	0,01/	72,3°	0,91/	-19,7°	42,7	
	100	0,60/	-89,5°	31,6/132,8°	0,02/	55,5°	0,69/	-42,9°	34,8	
	200	0,55/	-129,0°	19,7/114,0°	0,02/	50,4°	0,44/	-57,0°	28,4	
	500	0,57/	-168,3°	8,8/ 91,5°	0,04/	54,8°	0,24/	-74,1°	20,8	
	800	0,55/	+175,7°	5,6/ 81,0°	0,06/	60,5°	0,21/	-80,3°	16,8	
	1000	0,55/	+166,5°	4,5/ 74,8°	0,07/	61,7°	0,19/	-82,5°	14,8	
	1200	0,57/	+156,9°	3,7/ 71,1°	0,08/	64,0°	0,17/	-85,5°	13,2	
	1500	0,54/	+150,5°	3,1/ 63,0°	0,10/	63,0°	0,18/	-130,7°	11,4	
2000	0,55/	+131,8°	2,3/ 53,3°	0,13/	62,3°	0,20/	-111,3°	9,0		
30	40	0,58/	-50,3°	50,7/154,7°	0,01/	69,7°	0,87/	-24,2°	42,2	
	100	0,56/	-104,9°	35,1/127,1°	0,02/	53,8°	0,61/	-48,7°	34,5	
	200	0,54/	-141,0°	20,7/109,8°	0,02/	52,4°	0,37/	-61,2°	28,4	
	500	0,56/	-173,6°	8,9/ 89,5°	0,04/	60,0°	0,20/	-77,6°	20,8	
	800	0,55/	+172,3°	5,7/ 79,7°	0,06/	64,8°	0,18/	-83,1°	16,9	
	1000	0,56/	+164,0°	4,5/ 73,8°	0,07/	65,3°	0,17/	-85,3°	14,9	
	1200	0,58/	+154,8°	3,7/ 70,6°	0,08/	67,1°	0,15/	-88,3°	13,3	
	1500	0,55/	+148,9°	3,1/ 62,5°	0,10/	65,2°	0,16/	-100,8°	11,5	
2000	0,55/	+130,5°	2,3/ 53,0°	0,13/	63,7°	0,18/	-114,1°	9,1		

s-parameters (common-emitter) at $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values

I_C mA	f MHz	S_{11}		S_{21}		S_{12}		S_{22}		GUM dB
		M	Φ	M	Φ	M	Φ	M	Φ	
2	40	0,94/	-9,9 $^{\circ}$	7,1/174,8 $^{\circ}$		0,01/	84,5 $^{\circ}$	1,00/	-2,8 $^{\circ}$	53,5
	100	0,94/	-30,0 $^{\circ}$	7,0/161,3 $^{\circ}$		0,03/	73,7 $^{\circ}$	1,00/	-11,0 $^{\circ}$	53,4
	200	0,83/	-56,5 $^{\circ}$	6,1/145,5 $^{\circ}$		0,05/	61,5 $^{\circ}$	0,89/	-20,5 $^{\circ}$	27,7
	500	0,74/	-113,2 $^{\circ}$	4,3/111,4 $^{\circ}$		0,09/	37,8 $^{\circ}$	0,73/	-37,8 $^{\circ}$	19,4
	800	0,66/	-142,9 $^{\circ}$	3,0/ 93,7 $^{\circ}$		0,10/	30,8 $^{\circ}$	0,63/	-48,7 $^{\circ}$	14,3
	1000	0,64/	-159,0 $^{\circ}$	2,5/ 82,5 $^{\circ}$		0,10/	27,0 $^{\circ}$	0,62/	-52,8 $^{\circ}$	12,4
	1200	0,63/	-173,3 $^{\circ}$	2,0/ 74,6 $^{\circ}$		0,10/	26,9 $^{\circ}$	0,61/	-59,6 $^{\circ}$	10,3
	1500	0,62/	+172,7 $^{\circ}$	1,7/ 65,5 $^{\circ}$		0,10/	29,8 $^{\circ}$	0,54/	-68,5 $^{\circ}$	8,3
5	2000	0,63/	+149,9 $^{\circ}$	1,3/ 50,5 $^{\circ}$		0,10/	37,8 $^{\circ}$	0,54/	-87,0 $^{\circ}$	5,7
	40	0,87/	-15,9 $^{\circ}$	15,9/171,6 $^{\circ}$		0,01/	81,6 $^{\circ}$	0,99/	-6,5 $^{\circ}$	46,7
	100	0,84/	-43,8 $^{\circ}$	14,8/153,5 $^{\circ}$		0,03/	68,2 $^{\circ}$	0,93/	-19,3 $^{\circ}$	37,7
	200	0,72/	-78,0 $^{\circ}$	11,6/134,5 $^{\circ}$		0,05/	54,8 $^{\circ}$	0,76/	-31,6 $^{\circ}$	28,3
	500	0,63/	-136,7 $^{\circ}$	6,7/102,2 $^{\circ}$		0,07/	38,8 $^{\circ}$	0,52/	-48,3 $^{\circ}$	20,0
	800	0,59/	-161,4 $^{\circ}$	4,4/ 87,9 $^{\circ}$		0,08/	40,0 $^{\circ}$	0,44/	-56,7 $^{\circ}$	15,7
	1000	0,58/	-174,8 $^{\circ}$	3,6/ 79,0 $^{\circ}$		0,08/	40,8 $^{\circ}$	0,43/	-59,3 $^{\circ}$	13,7
	1200	0,58/	+172,8 $^{\circ}$	2,9/ 73,4 $^{\circ}$		0,08/	44,0 $^{\circ}$	0,41/	-63,9 $^{\circ}$	11,9
10	1500	0,57/	+162,6 $^{\circ}$	2,5/ 64,9 $^{\circ}$		0,09/	47,2 $^{\circ}$	0,37/	-73,9 $^{\circ}$	10,1
	2000	0,57/	+141,9 $^{\circ}$	1,8/ 52,3 $^{\circ}$		0,11/	52,4 $^{\circ}$	0,38/	-90,2 $^{\circ}$	7,6
	40	0,80/	-23,3 $^{\circ}$	26,3/167,2 $^{\circ}$		0,01/	78,3 $^{\circ}$	0,97/	-11,0 $^{\circ}$	44,6
	100	0,74/	-60,0 $^{\circ}$	22,9/145,1 $^{\circ}$		0,03/	62,7 $^{\circ}$	0,85/	-28,1 $^{\circ}$	36,3
	200	0,62/	-99,1 $^{\circ}$	16,2/125,0 $^{\circ}$		0,04/	50,9 $^{\circ}$	0,62/	-41,6 $^{\circ}$	28,4
	500	0,58/	-151,7 $^{\circ}$	8,1/ 96,7 $^{\circ}$		0,05/	45,4 $^{\circ}$	0,38/	-56,3 $^{\circ}$	20,6
	800	0,55/	-172,9 $^{\circ}$	5,3/ 84,4 $^{\circ}$		0,06/	50,5 $^{\circ}$	0,32/	-63,4 $^{\circ}$	16,5
	1000	0,55/	+175,8 $^{\circ}$	4,2/ 77,0 $^{\circ}$		0,07/	52,3 $^{\circ}$	0,31/	-64,9 $^{\circ}$	14,5
20	1200	0,56/	+164,5 $^{\circ}$	3,5/ 72,4 $^{\circ}$		0,08/	55,1 $^{\circ}$	0,29/	-68,2 $^{\circ}$	12,8
	1500	0,54/	+156,7 $^{\circ}$	2,9/ 64,3 $^{\circ}$		0,10/	56,6 $^{\circ}$	0,28/	-79,7 $^{\circ}$	11,1
	2000	0,54/	+136,8 $^{\circ}$	2,1/ 53,1 $^{\circ}$		0,12/	58,5 $^{\circ}$	0,28/	-94,3 $^{\circ}$	8,6
	40	0,70/	-35,0 $^{\circ}$	41,2/160,7 $^{\circ}$		0,01/	75,1 $^{\circ}$	0,92/	-17,3 $^{\circ}$	43,5
	100	0,63/	-82,0 $^{\circ}$	31,7/134,8 $^{\circ}$		0,02/	57,6 $^{\circ}$	0,72/	-38,6 $^{\circ}$	35,4
	200	0,55/	-122,2 $^{\circ}$	20,2/115,6 $^{\circ}$		0,03/	50,9 $^{\circ}$	0,47/	-51,0 $^{\circ}$	28,7
	500	0,55/	-164,6 $^{\circ}$	9,1/ 92,2 $^{\circ}$		0,04/	54,4 $^{\circ}$	0,27/	-63,8 $^{\circ}$	21,0
	800	0,53/	+178,4 $^{\circ}$	5,8/ 81,6 $^{\circ}$		0,06/	60,2 $^{\circ}$	0,24/	-69,5 $^{\circ}$	17,0
30	1000	0,54/	+168,8 $^{\circ}$	4,6/ 75,3 $^{\circ}$		0,07/	61,3 $^{\circ}$	0,22/	-70,7 $^{\circ}$	15,0
	1200	0,55/	+158,7 $^{\circ}$	3,8/ 71,4 $^{\circ}$		0,08/	63,4 $^{\circ}$	0,20/	-72,9 $^{\circ}$	13,4
	1500	0,52/	+152,5 $^{\circ}$	3,2/ 63,5 $^{\circ}$		0,10/	63,0 $^{\circ}$	0,21/	-85,9 $^{\circ}$	11,6
	2000	0,53/	+133,3 $^{\circ}$	2,4/ 53,4 $^{\circ}$		0,13/	62,3 $^{\circ}$	0,22/	-99,5 $^{\circ}$	9,2
	40	0,65/	-42,9 $^{\circ}$	49,0/156,7 $^{\circ}$		0,01/	72,7 $^{\circ}$	0,89/	-20,9 $^{\circ}$	43,0
	100	0,58/	-94,4 $^{\circ}$	35,1/129,5 $^{\circ}$		0,02/	54,7 $^{\circ}$	0,65/	-43,2 $^{\circ}$	35,0
	200	0,53/	-132,8 $^{\circ}$	21,1/111,5 $^{\circ}$		0,03/	51,8 $^{\circ}$	0,40/	-53,7 $^{\circ}$	28,7
	500	0,54/	-169,5 $^{\circ}$	9,2/ 90,5 $^{\circ}$		0,04/	58,8 $^{\circ}$	0,23/	-64,8 $^{\circ}$	21,1
30	800	0,52/	+175,3 $^{\circ}$	5,9/ 80,5 $^{\circ}$		0,06/	63,6 $^{\circ}$	0,21/	-70,2 $^{\circ}$	17,0
	1000	0,53/	+166,4 $^{\circ}$	4,7/ 74,3 $^{\circ}$		0,07/	64,6 $^{\circ}$	0,20/	-71,4 $^{\circ}$	15,1
	1200	0,55/	+156,8 $^{\circ}$	3,9/ 70,8 $^{\circ}$		0,08/	66,1 $^{\circ}$	0,18/	-73,2 $^{\circ}$	13,4
	1500	0,52/	+150,9 $^{\circ}$	3,2/ 63,0 $^{\circ}$		0,10/	64,8 $^{\circ}$	0,19/	-87,3 $^{\circ}$	11,7
	2000	0,53/	+132,2 $^{\circ}$	2,4/ 53,0 $^{\circ}$		0,13/	63,5 $^{\circ}$	0,20/	-100,8 $^{\circ}$	9,0

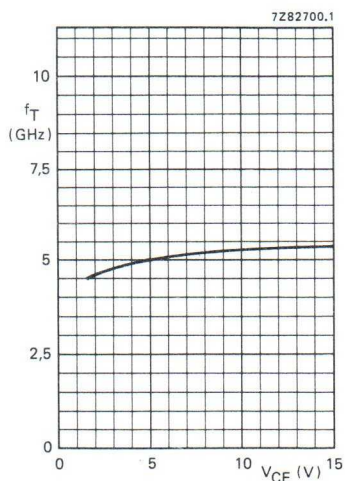


Fig.1 Transition frequency as a function of collector-emitter voltage.

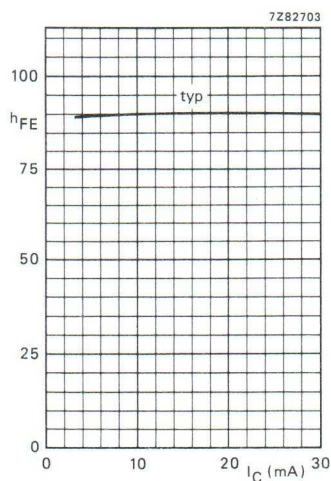


Fig.2 Current gain as a function of collector current.

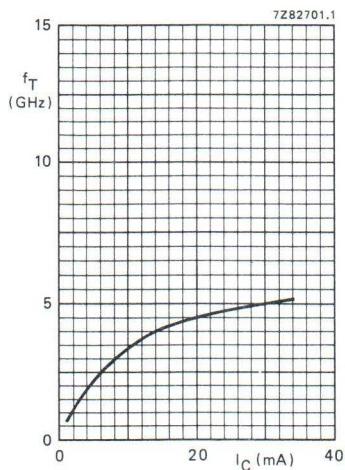


Fig.3 Transition frequency as a function of collector current.

Data sheet	
status	Product specification
date of issue	April 1991

BFG94

NPN 6 GHz wideband transistor

FEATURES

- High power gain.
- Low noise figure.
- Low intermodulation distortion.
- Gold metallization ensures excellent reliability.

DESCRIPTION

The BFG94 is a npn transistor primarily intended for use in communication and instrumentation systems.

The BFG94 is mounted in a SOT223 plastic envelope.

MECHANICAL DATA

Plastic SOT223 envelope.

PINNING

PIN	DESCRIPTION
1,3	emitter
2	base
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-	15	V
V_{CEO}	collector-emitter voltage	open base	-	-	12	V
I_C	collector current (DC)		-	-	60	mA
P_{tot}	total power dissipation	$T_{case} = 140\text{ }^{\circ}\text{C}$; note 1	-	-	700	mW
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CB} = 10\text{ V}$	-	-	0.8	pF
f_T	transition frequency	$f = 1\text{ GHz}$; $I_C = 45\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	4	-	-	GHz
G_{UM}	maximum power gain	$f = 1\text{ GHz}$; $I_C = 45\text{ mA}$; $V_{CE} = 10\text{ V}$; note 2	11.5	13.5	-	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $I_C = 45\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $f = 800\text{ MHz}$	-	500	-	mV
P_{L1}	output power at 1 dB gain compression	$I_C = 45\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 1\text{ GHz}$	-	21.5	-	dBm

NPN 6 GHz wideband transistor**BFG94****Notes to the Quick Reference Data**1. T_{case} temperature measured on soldering point of collector tab.

$$2. G_{\text{UM}} = 10 \text{ LOG} \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ [dB]}$$

 $(S_{12} \text{ assumed to be zero})$ **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	15	V
V_{CEO}	collector-emitter voltage	open base	-	12	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I_{C}	collector current (DC)		-	60	mA
P_{tot}	total power dissipation	$T_{\text{case}} = 140^\circ\text{C}$ note 1	-	700	mW
T_{stg}	storage temperature range		-65	+150	$^\circ\text{C}$
T_{j}	junction temperature		-	175	$^\circ\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{\text{th j-s}}$	from junction to soldering point	50	K/W

CHARACTERISTICS $T_{\text{j}} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_{\text{E}} = 0$; $V_{\text{CB}} = 10 \text{ V}$	-	-	100	nA
h_{FE}	DC current gain	$I_{\text{C}} = 30 \text{ mA}$; $V_{\text{CE}} = 5 \text{ V}$	45	-	-	
		$I_{\text{C}} = 45 \text{ mA}$; $V_{\text{CE}} = 10 \text{ V}$	-	100	-	
C_{c}	collector capacitance	$f = 1 \text{ MHz}$; $I_{\text{E}} = i_{\text{e}} = 0$; $V_{\text{CB}} = 10 \text{ V}$	-	0.9	2.0	pF
C_{e}	emitter capacitance	$f = 1 \text{ MHz}$; $I_{\text{C}} = i_{\text{e}} = 0$; $V_{\text{EB}} = 0.5 \text{ V}$	-	2.9	4.5	pF
C_{re}	feedback capacitance	$f = 1 \text{ MHz}$; $I_{\text{C}} = i_{\text{c}} = 0$; $V_{\text{CB}} = 10 \text{ V}$	-	0.5	0.8	pF
f_{T}	transition frequency	$f = 1 \text{ GHz}$; $I_{\text{C}} = 45 \text{ mA}$; $V_{\text{CE}} = 10 \text{ V}$; $T_{\text{amb}} = 25^\circ\text{C}$	4	-	-	GHz
		$f = 1 \text{ GHz}$; $I_{\text{C}} = 30 \text{ mA}$; $V_{\text{CE}} = 5 \text{ V}$; $T_{\text{amb}} = 25^\circ\text{C}$	-	6	-	GHz

NPN 6 GHz wideband transistor**BFG94**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _{UM}	maximum power gain	f = 1 GHz; T _{amb} = 25 °C; I _C = 45 mA; V _{CE} = 10 V; note 2	11.5	13.5	-	dB
F _{min}	noise figure	Γ _s = Γ _{opt} ; I _C = 45 mA; V _{CE} = 10 V; f = 500 MHz	-	2.7	-	dB
		Γ _s = Γ _{opt} ; I _C = 45 mA; V _{CE} = 10 V; f = 1000 MHz	-	3	-	dB
V _o	output voltage	note 3	-	500	-	mV
V _o	output voltage	note 4	-	280	-	mV
P _{L1}	output power at 1 dB gain compression	I _C = 45 mA; V _{CE} = 10 V; R _L = 50 Ω; T _{amb} = 25 °C; measured at f = 1 GHz	-	21.5	-	dBm
ITO	third order intercept point	note 5	-	34	-	dBm

Notes

1. T_{case} temperature measured on soldering point of collector tab.

$$2. G_{UM} = 10 \text{ LOG} \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ [dB]}$$

(S₁₂ assumed to be zero)

3. d_{im} = -60 dB (DIN 45004B, par.6.3 : 3-tone); T_{amb} = 25 °C;

I_C = 45 mA; V_{CE} = 10 V; R_L = 75 Ω; V_p = V_o at d_{im} = -60 dB;

f_p = 795.25 MHz; V_q = V_o -6 dB; V_r = V_o -6 dB;

f_q = 803.25 MHz; f_r = 805.25 MHz; measured at

f_(p+q-r) = 793.25 MHz.

4. d₂ = -50 dB; T_{amb} = 25 °C; I_C = 45 mA; V_{CE} = 10 V;

R_L = 75 Ω; V_p = V_o at d₂ = -50 dB; V_q = V_o at d₂ = -50 dB;

f_p = 250 MHz; f_q = 560 MHz;

measured at f_(p+q) = 810 MHz.

5. I_C = 45 mA; V_{CE} = 10 V; R_L = 50 Ω; T_{amb} = 25 °C;

P_p = ITO = -6 dB; f_p = 1000 MHz;

P_q = ITO = -6 dB; f_q = 1001 MHz;

measured at f_(2p-q) and f_(2q-p).

NPN 6 GHz wideband transistor

BFG94

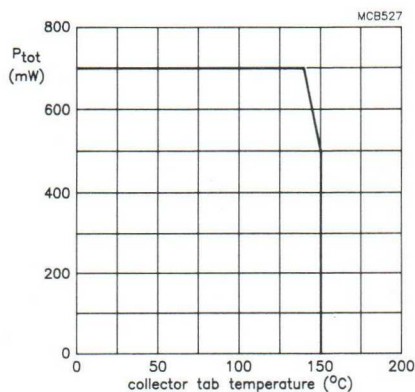


Fig.1 Power derating curve as a function of collector tab temperature.

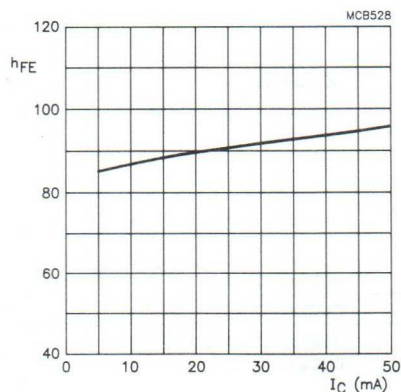


Fig.2 DC current gain as a function of collector current; $V_{CE} = 10$ V.

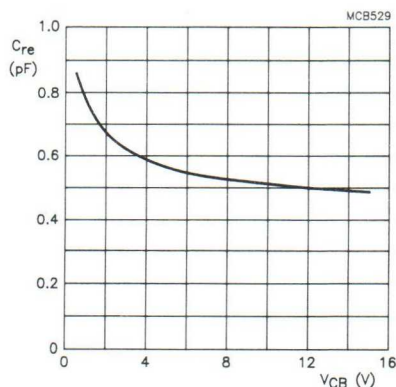


Fig.3 Feedback capacitance as a function of collector voltage; $I_C = I_c = 0$; $f = 1$ MHz.

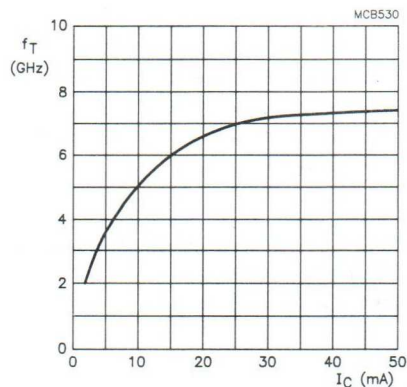


Fig.4 Transition frequency as a function of collector current; $V_{CE} = 10$ V; $f = 1$ GHz.

NPN 6 GHz wideband transistor

BFG94

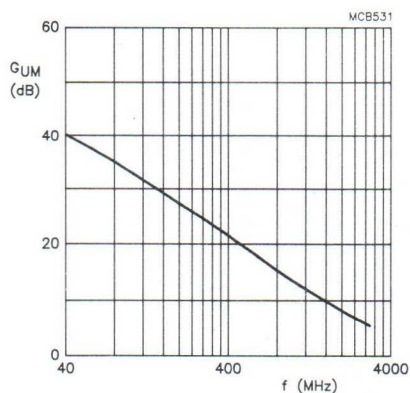


Fig.5 Maximum unilateral power gain as a function of frequency; $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$.

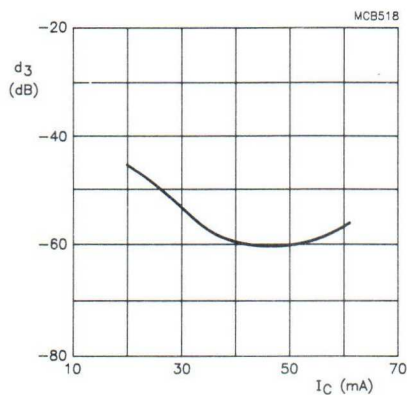


Fig.6 Third order intermodulation distortion. See test circuit (Fig.14); $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$; $f_m = 793.25\text{ MHz}$.

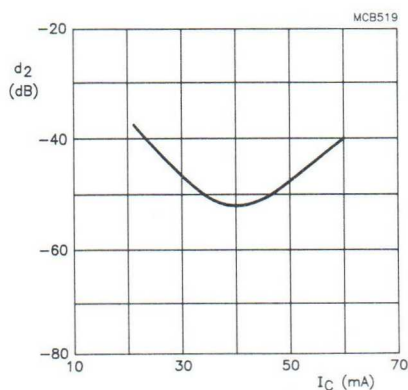
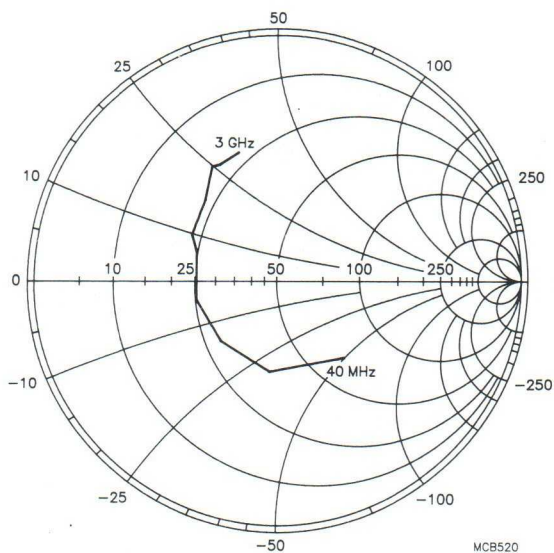
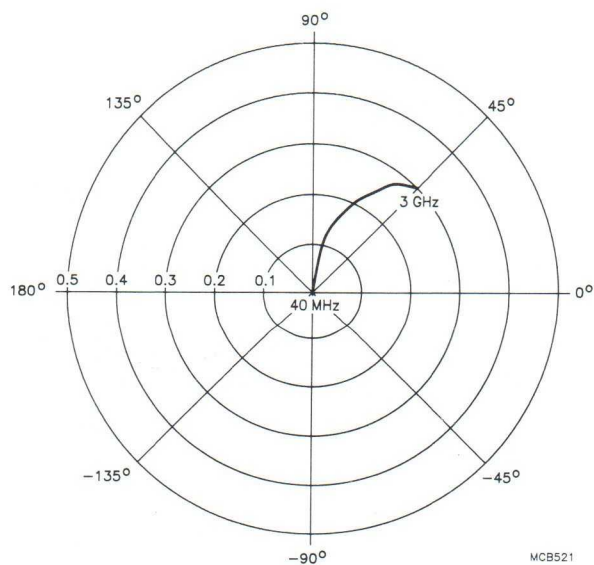


Fig.7 Second order distortion. See test circuit (Fig.14); $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$; $f_m = 810\text{ MHz}$.

NPN 6 GHz wideband transistor**BFG94**Fig.8 Common emitter input reflection coefficient S_{11} ; $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$.Fig.9 Common emitter forward transmission coefficient S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$.

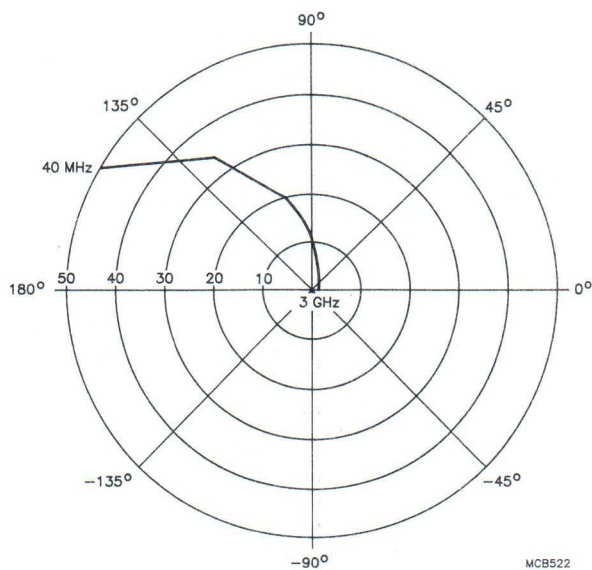
NPN 6 GHz wideband transistor**BFG94**

Fig.10 Common emitter reverse transmission coefficient S_{12} ; $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$.

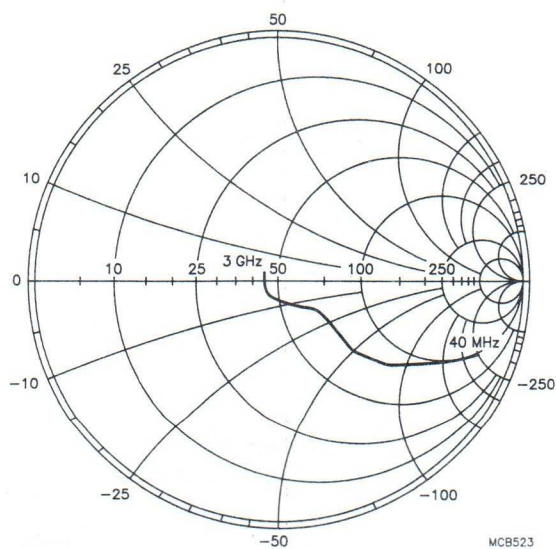


Fig.11 Common emitter output reflection coefficient S_{22} ; $V_{CE} = 10\text{ V}$; $I_C = 45\text{ mA}$.

NPN 6 GHz wideband transistor

BFG94

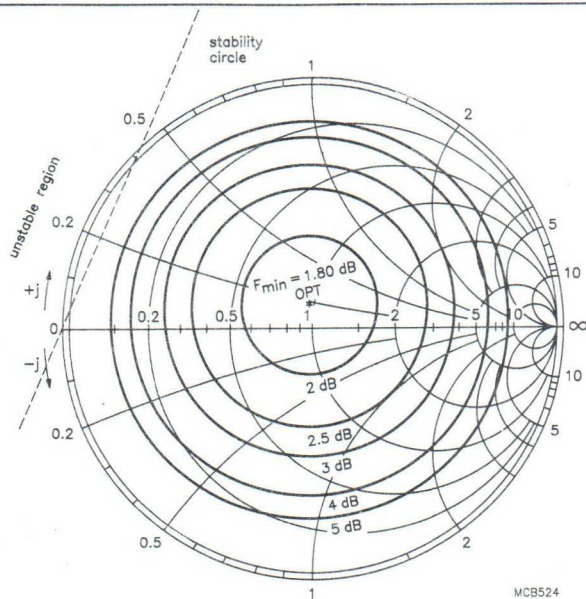


Fig.12 Location of optimum source reflection coefficient for minimum noise figure;
 $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $f = 500\text{ MHz}$.

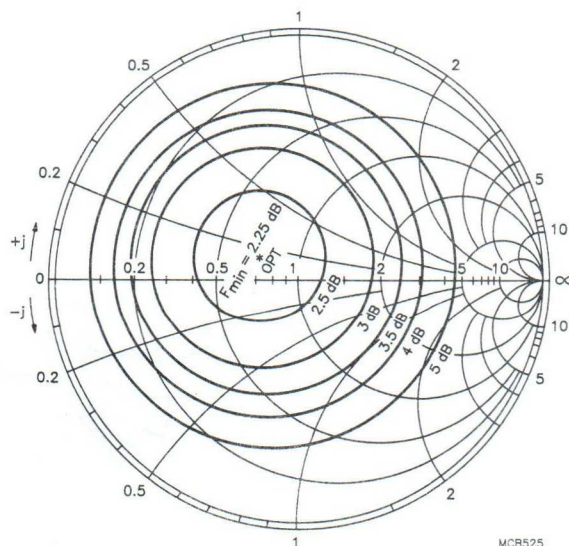


Fig.13 Location of optimum source reflection coefficient for minimum noise figure;
 $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$; $f = 1\text{ GHz}$.

NPN 6 GHz wideband transistor

BFG94

Common emitter S and noise parameters at $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		GUM (dB)
	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	
40	.404	- 48.4	50.03	150.0	.009	74.3	.836	- 22.0	40.0
100	.347	- 97.6	33.55	124.0	.017	66.9	.587	- 38.4	32.9
200	.319	-134.5	19.73	105.9	.027	67.6	.385	- 43.0	27.1
300	.316	-152.0	13.62	97.2	.037	70.5	.304	- 41.8	23.6
400	.320	-162.4	10.46	91.3	.048	71.4	.262	- 40.1	21.2
500	.325	-169.4	8.42	86.8	.058	72.1	.239	- 39.2	19.3
600	.328	-175.0	7.07	83.3	.068	72.3	.222	- 38.5	17.7
700	.321	179.8	6.10	80.1	.078	72.2	.210	- 38.6	16.4
800	.325	175.1	5.37	77.0	.089	71.4	.199	- 38.8	15.3
900	.329	170.0	4.81	74.2	.099	70.8	.189	- 39.4	14.3
1000	.336	164.9	4.37	71.2	.108	69.9	.178	- 40.1	13.5
1200	.364	157.5	3.65	65.7	.129	68.8	.158	- 43.1	12.0
1400	.392	152.6	3.15	60.9	.149	66.8	.139	- 48.2	10.8
1600	.391	147.8	2.79	55.6	.168	64.9	.120	- 54.1	9.7
1800	.407	140.5	2.51	50.4	.186	63.0	.099	- 60.5	8.8
2000	.426	133.4	2.31	45.9	.207	60.7	.078	- 70.5	8.2
2200	.465	127.8	2.11	41.8	.224	57.7	.057	- 92.9	7.6
2400	.491	124.8	1.95	37.8	.238	56.1	.050	-125.7	7.0
2600	.511	121.6	1.79	33.0	.255	54.6	.052	-155.3	6.4
2800	.506	115.7	1.68	27.9	.279	52.0	.054	179.9	5.8
3000	.527	108.7	1.61	23.7	.290	46.8	.066	154.9	5.6

FREQUENCY (MHz)	F_{min} (dB)	Γ_{opt}		R_n (Ω)	$r_n (= R_n/50)$ (Ω)
		M (rat)	Φ (deg)		
500	2.70	.168	159.1	12.1	.241
1000	3.00	.295	-177.3	10.2	.204

NPN 6 GHz wideband transistor**BFG94**Common emitter S and noise parameters at $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.

FREQUENCY (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		GUM (dB)
	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	
40	.438	- 41.5	44.41	153.0	.009	74.6	.865	- 19.7	39.9
100	.374	- 87.1	31.75	128.2	.018	66.3	.641	- 36.3	33.0
200	.320	-126.9	19.27	108.7	.028	66.9	.429	- 43.2	27.1
300	.314	-147.0	13.58	99.2	.038	68.6	.338	- 43.0	23.6
400	.315	-158.3	10.38	92.9	.048	69.9	.291	- 41.7	21.2
500	.314	-166.3	8.38	88.3	.058	70.6	.263	- 40.5	19.2
600	.315	-174.1	7.05	84.3	.068	71.6	.245	- 40.1	17.7
700	.316	-178.9	6.08	80.8	.078	71.3	.230	- 40.4	16.4
800	.316	175.3	5.35	77.7	.088	70.7	.217	- 40.8	15.2
900	.318	170.3	4.79	74.8	.099	70.1	.206	- 41.6	14.3
1000	.325	165.1	4.36	71.9	.108	69.3	.196	- 43.1	13.5
1200	.348	157.1	3.66	66.2	.128	68.4	.176	- 46.7	12.0
1400	.372	150.9	3.14	61.1	.149	66.6	.160	- 51.8	10.7
1600	.386	146.8	2.79	56.0	.168	64.5	.144	- 57.8	9.7
1800	.389	139.1	2.52	51.4	.186	62.8	.124	- 63.8	8.8
2000	.413	132.5	2.29	46.2	.206	60.7	.103	- 73.7	8.1
2200	.455	126.1	2.12	42.3	.223	57.6	.084	- 92.2	7.6
2400	.481	122.7	1.96	38.2	.238	55.7	.079	-113.2	7.0
2600	.489	118.3	1.81	33.0	.256	54.4	.075	-130.0	6.4
2800	.496	113.4	1.67	29.1	.279	51.8	.065	-149.4	5.8
3000	.514	106.1	1.60	24.3	.287	46.7	.064	-179.0	5.5

FREQUENCY (MHz)	F_{min} (dB)	Γ_{opt}		R_n (Ω)	$r_n (= R_n/50)$ (Ω)
		M (rat)	Φ (deg)		
500	2.30	.134	155.2	11.00	.222
1000	2.70	.253	175.6	10.80	.216

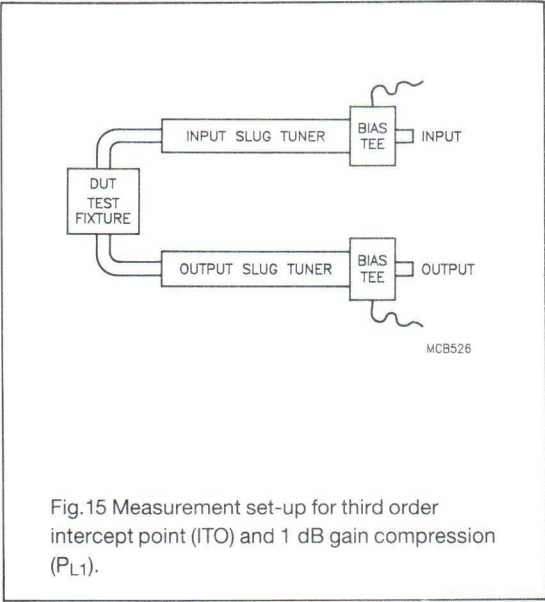
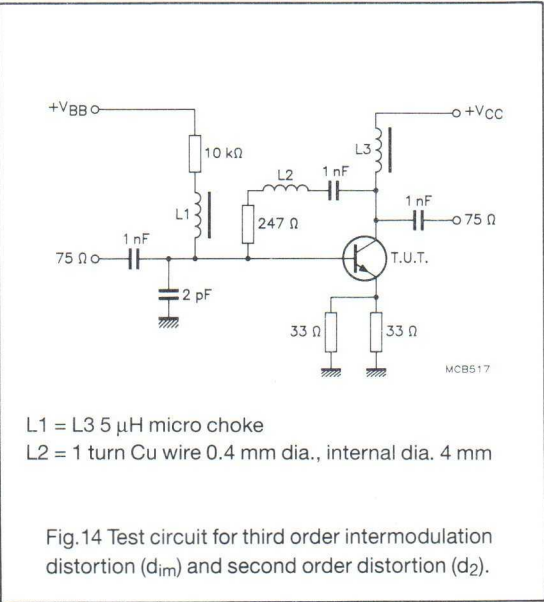
NPN 6 GHz wideband transistor

BFG94

Common emitter S and noise parameters at $V_{CE} = 10\text{ V}$; $I_C = 15\text{ mA}$.

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		G _{UM} (dB)
	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	M (rat)	Φ (deg)	
40	.609	− 29.1	32.10	159.5	.010	76.7	.925	− 14.6	40.6
100	.526	− 65.4	25.66	136.9	.022	65.5	.758	− 30.1	33.3
200	.427	−104.2	17.25	115.9	.033	59.5	.539	− 40.5	27.1
300	.385	−128.2	12.43	104.5	.042	60.7	.425	− 43.1	23.5
400	.367	−143.8	9.72	96.9	.051	62.2	.360	− 43.4	21.0
500	.361	−154.5	7.91	91.4	.059	63.6	.323	− 43.7	19.1
600	.359	−163.1	6.66	87.0	.068	64.7	.297	− 43.6	17.5
700	.346	−169.8	5.78	83.1	.077	65.6	.280	− 43.5	16.2
800	.350	−176.3	5.08	79.8	.087	65.6	.266	− 44.1	15.0
900	.348	−177.6	4.55	76.4	.096	66.0	.253	− 44.7	14.0
1000	.355	171.6	4.13	73.3	.104	65.5	.240	− 45.8	13.2
1200	.374	162.4	3.48	67.2	.122	65.6	.219	− 49.3	11.7
1400	.394	155.5	2.99	61.7	.142	64.2	.199	− 54.9	10.4
1600	.395	150.1	2.65	56.6	.159	63.0	.183	− 61.1	9.4
1800	.414	143.3	2.40	51.3	.176	61.8	.166	− 66.8	8.6
2000	.430	135.8	2.21	46.5	.197	60.2	.146	− 73.9	7.9
2200	.466	130.3	2.03	42.4	.214	57.4	.127	− 86.9	7.3
2400	.486	125.5	1.87	37.8	.227	56.1	.117	−104.2	6.7
2600	.508	121.9	1.73	32.9	.245	55.0	.110	−119.0	6.1
2800	.505	117.2	1.61	28.3	.270	52.5	.100	−129.7	5.5
3000	.527	109.4	1.55	24.0	.281	47.7	.090	−144.9	5.3

FREQUENCY (MHz)	F _{min} (dB)	Γ _{opt}		R _n (Ω)	r _n (= R _n /50) (Ω)
		M (rat)	Φ (deg)		
500	1.80	.112	98.1	10.55	.211
1000	2.25	.203	152.1	10.50	.210



Philips Components

Data sheet	
status	Product specification
date of issue	April 1991

BFG97

NPN 5 GHz wideband transistor

NPN planar epitaxial transistor in a plastic SOT223 envelope, primarily intended for MATV applications.

The device features excellent output voltage capabilities.
Its pnp complement is the BFG31.

MECHANICAL DATA

SOT223.

PINNING

PIN	DESCRIPTION
1,3	emitter
2	base
4	collector

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	-	15	V
I_C	collector current (DC)		-	-	100	mA
P_{tot}	total power dissipation	$T_{case} = 125\text{ }^{\circ}\text{C}$; note 1	-	-	1	W
T_j	junction temperature		-	-	175	$^{\circ}\text{C}$
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	5.5	-	GHz
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	-	16	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	-	12	-	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $f_{(p+q-r)} = 793.25\text{ MHz}$	-	700	-	mV

Note

1. T_{case} temperature measured on soldering point of collector tab.

NPN 5 GHz wideband transistor**BFG97****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG97	SOT223	bulk	500
BFG97	SOT223	12 mm reel	1000

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	15	V
V_{EBO}	emitter-base voltage	open collector	-	3	V
I_C	collector current (DC)		-	100	mA
P_{tot}	total power dissipation	$T_{case} = 125\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-c}$	from junction to case	50	K/W

NPN 5 GHz wideband transistor**BFG97****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 10\text{ V}$	-	-	100	nA
h_{FE}	DC current gain	$I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	25	-	-	
f_T	transition frequency	$f = 500\text{ MHz}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	5.5	-	GHz
C_c	collector capacitance	$f = 1\text{ MHz}$; $I_E = I_E = 0$; $V_{CB} = 10\text{ V}$	-	1.5	-	pF
C_e	emitter capacitance	$f = 1\text{ MHz}$; $I_C = I_C = 0$; $V_{EB} = 0.5\text{ V}$	-	6.5	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CE} = 10\text{ V}$	-	1.0	-	pF
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	-	16	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$	-	12	-	dB
V_o	output voltage	note 1	-	750	-	mV
V_o	output voltage	note 2	-	700	-	mV

Notes

- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $V_q = V_o - 6\text{ dB}$; $f_p = 445.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$; $f_q = 453.25\text{ MHz}$; $f_r = 445.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 443.25\text{ MHz}$.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 70\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $V_q = V_o - 6\text{ dB}$; $f_p = 795.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$; $f_q = 803.25\text{ MHz}$; $f_r = 805.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.

NPN 5 GHz wideband transistor**BFG97****List of components:**

R1 = 10 k Ω metal film resistor	(cat. no. 2322 180 73103)
R2 = 220 Ω metal film resistor	(cat. no. 2322 180 73221)
R3 = R4 = 30 Ω metal film resistor	(cat. no. 2322 180 73309)
C2 = C3 = C7 = C8 = 10 nF ceramic multilayer capacitor	(cat. no. 2222 590 08627)
C1 = C4 = C6 = 1.2 pF ceramic multilayer capacitor	(cat. no. 2222 851 12128)
C5 = 10 nF miniature ceramic plate capacitor	(cat. no. 2222 629 08103)
L1 = 0.5 turn Cu wire (0.4 mm), internal diameter 3 mm	
L2 = 75 Ω microstripline	(L = 14 mm; W = 2.5 mm)
L3 = 75 Ω microstripline	(L = 8 mm; W = 2.5 mm)
L4 = L5 = 1.5 turns Cu wire (0.4 mm), internal diameter 3 mm, winding pitch 1 mm	
L6 = 75 Ω microstripline	(L = 19 mm; W = 2.5 mm)
L7 = 5 μ H Ferroxcube choke	(cat. no. 3122 108 20153)

The circuit has been built on a double Cu clad printed circuit board with PTFE dielectric ($\epsilon_r = 2.2$); thickness 1/16 inch; thickness of copper-sheet 2 x 35 μ m.

The components L1, R2, L4, C5 and L5 are mounted on the underside of the PCB.

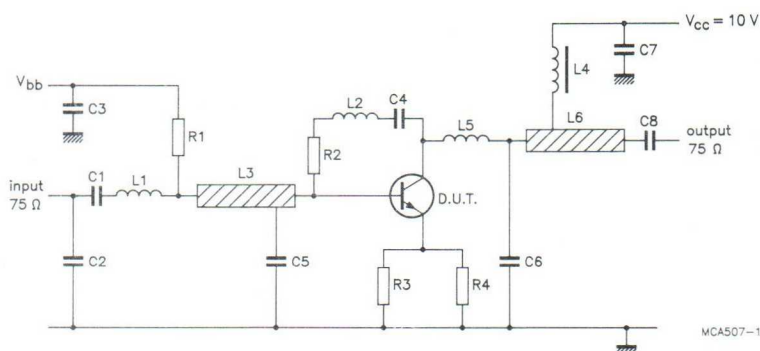


Fig.1 Intermodulation and second harmonic test circuit.

NPN 5 GHz wideband transistor

BFG97

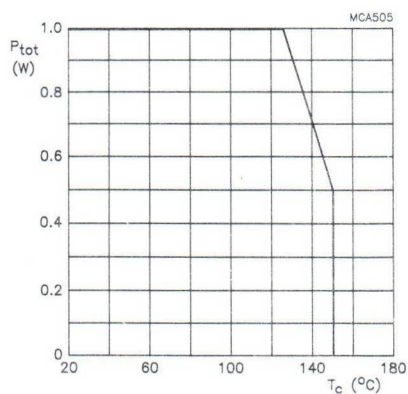


Fig.2 Power derating curve as a function of case temperature.

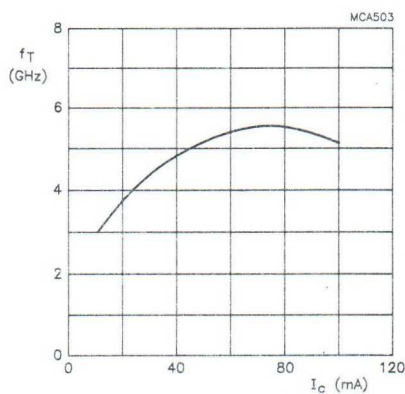


Fig.3 Transition frequency as a function of collector current; $V_{CE} = 10$ V; $f = 500$ MHz; $T_j = 25$ °C; typical values.

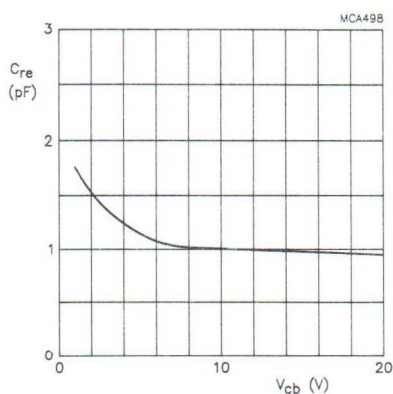


Fig.4 Feedback capacitance as a function of collector-base voltage; $I_E = 0$; $f = 1$ MHz; $T_j = 25$ °C; typical values.

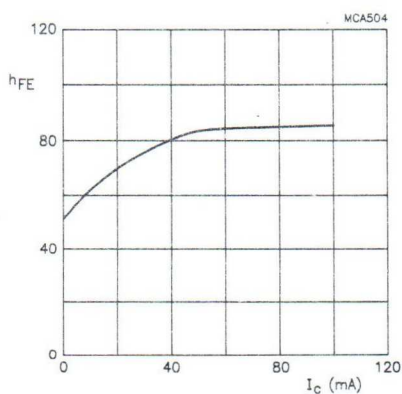


Fig.5 DC current gain as a function of collector current; $V_{CE} = 10$ V; $T_j = 25$ °C; typical values.

NPN 5 GHz wideband transistor

BFG97

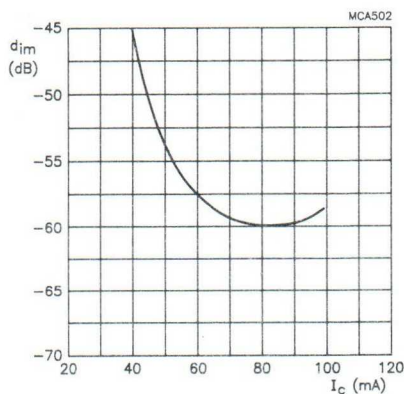


Fig.6 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 750$ mV; $f_{(p+q-r)} = 443.25$ MHz; $T_{amb} = 25$ °C; typical values.

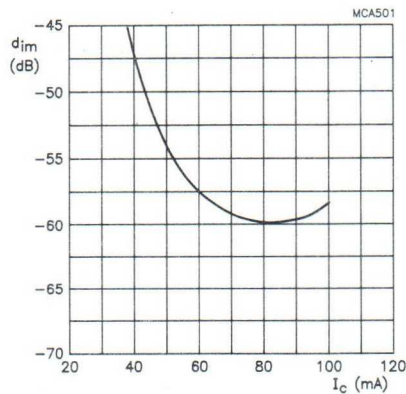


Fig.7 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 700$ mV; $f_{(p+q-r)} = 793.25$ MHz; $T_{amb} = 25$ °C; typical values.

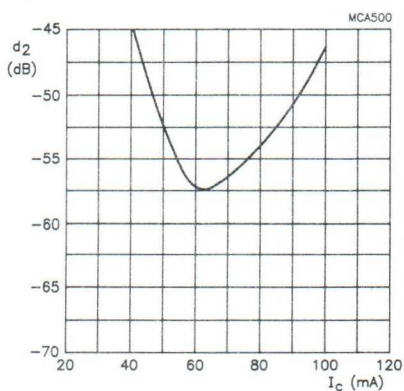


Fig.8 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 50$ dBmV; $f_{(p+q)} = 450$ MHz; $T_{amb} = 25$ °C; typical values.

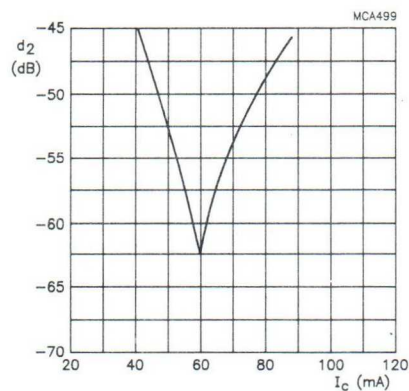


Fig.9 Intermodulation distortion as a function of collector current; $V_{CE} = 10$ V; $V_o = 50$ dBmV; $f_{(p+q)} = 810$ MHz; $T_{amb} = 25$ °C; typical values.

NPN 5 GHz wideband transistor

BFG97

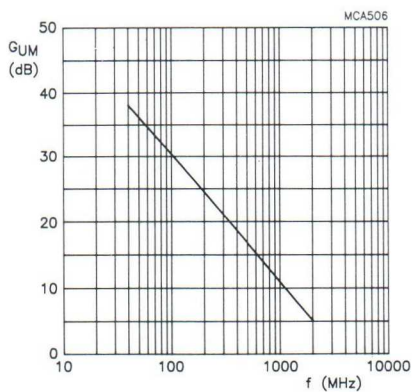


Fig.10 Gain as a function of frequency; $V_{CE} = 10\text{ V}$;
 $I_C = 70\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

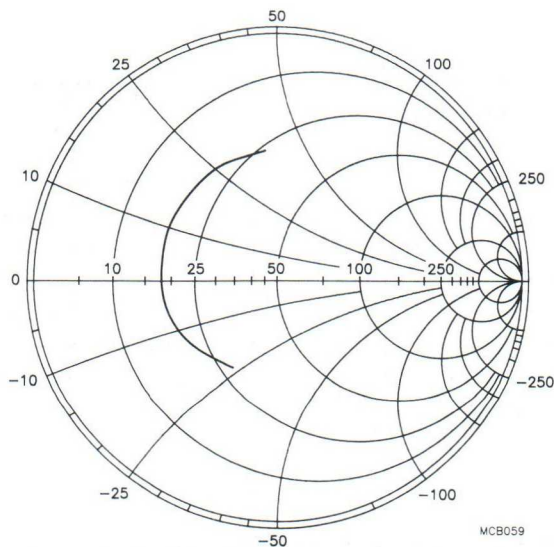


Fig.11 Input reflection coefficient S_{11} ; $V_{CE} = 10\text{ V}$; $I_C = 70\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

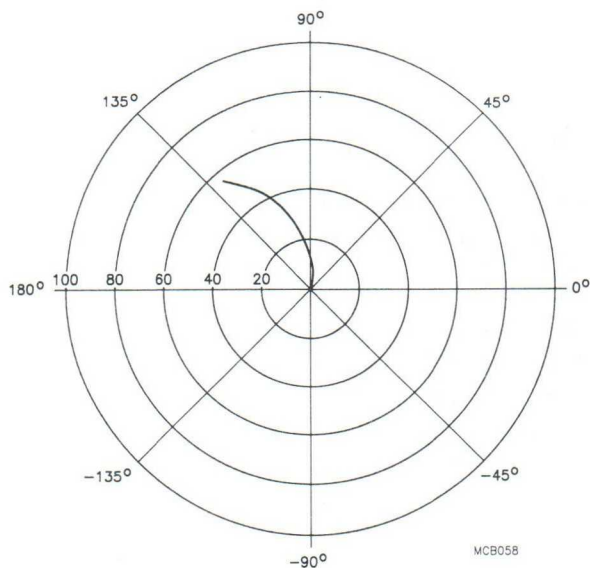
NPN 5 GHz wideband transistor**BFG97**

Fig.12 Forward transmission coefficient S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 70\text{ mA}$; $T_{amb} = 25\text{ °C}$; typical values.

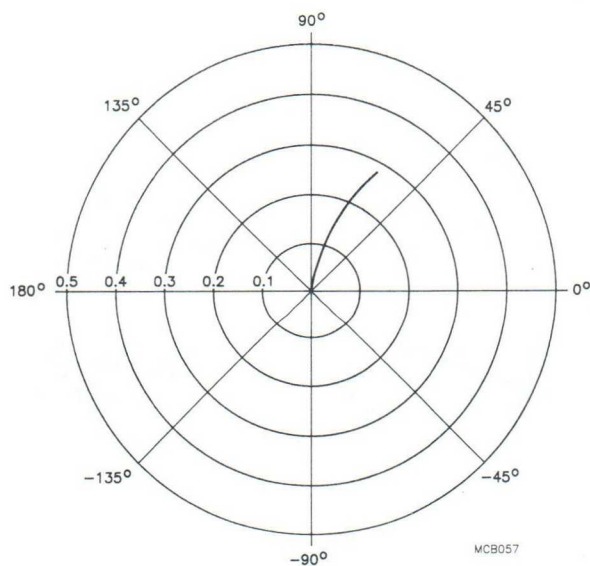


Fig.13 Reverse transmission coefficient S_{12} ; $V_{CE} = 10\text{ V}$; $I_C = 70\text{ mA}$; $T_{amb} = 25\text{ °C}$; typical values.

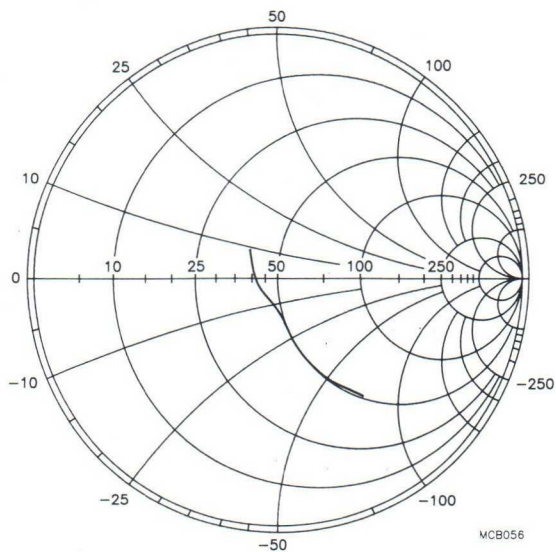
NPN 5 GHz wideband transistor**BFG97**

Fig.14 Output reflection coefficient S_{22} ; $V_{CE} = 10\text{ V}$; $I_C = 70\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

NPN 5 GHz wideband transistor

BFG97

S-Parameters (common emitter) at $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

I_C (mA)	f (MHz)	S_{11} M Φ	S_{21} M Φ	S_{12} M Φ	S_{22} M Φ	G_{um} (dB)
5	40	0.84/- 32.9	13.1/160.1	0.02/74.0	0.95/- 12.8	37.8
	100	0.76/- 73.1	10.2/138.1	0.04/56.3	0.79/- 27.3	28.2
	200	0.69/-117.6	7.4/114.1	0.06/43.1	0.62/- 35.4	22.2
	500	0.63/-171.8	3.4/ 84.6	0.07/41.3	0.45/- 44.7	13.8
	800	0.61/ 159.8	2.2/ 69.3	0.09/48.3	0.42/- 55.8	9.6
	1000	0.61/ 146.0	1.8/ 60.5	0.10/55.1	0.40/- 65.1	7.7
	1200	0.61/ 133.8	1.5/ 52.2	0.11/63.4	0.37/- 75.8	6.1
	1500	0.59/ 117.1	1.2/ 43.9	0.14/67.2	0.36/- 93.4	4.0
10	2000	0.59/ 82.8	0.8/ 30.6	0.21/72.5	0.33/-126.2	0.6
	40	0.71/- 46.9	24.2/152.2	0.02/66.8	0.89/- 21.4	37.5
	100	0.63/- 95.9	17.0/126.6	0.04/52.3	0.65/- 38.7	29.2
	200	0.59/-137.8	10.3/106.0	0.05/47.2	0.44/- 46.9	23.0
	500	0.56/ 177.7	4.5/ 82.6	0.07/56.0	0.29/- 51.3	15.0
	800	0.56/ 154.7	2.8/ 69.5	0.10/61.6	0.25/- 61.1	11.0
	1000	0.56/ 142.8	2.3/ 61.6	0.11/63.7	0.23/- 69.4	9.0
	1200	0.56/ 131.6	1.9/ 54.7	0.14/66.6	0.22/- 80.2	7.3
30	1500	0.56/ 116.3	1.5/ 46.4	0.17/67.9	0.21/- 99.1	5.3
	2000	0.56/ 93.2	1.1/ 34.1	0.23/68.8	0.19/-136.7	2.4
	40	0.47/- 85.5	44.5/137.3	0.02/65.4	0.73/- 39.1	37.3
	100	0.48/-135.9	24.8/112.1	0.02/58.7	0.41/- 60.0	29.8
	200	0.50/-163.5	13.4/ 97.2	0.04/65.9	0.24/- 69.3	24.0
	500	0.50/ 167.5	5.5/ 80.5	0.07/70.5	0.12/- 80.5	16.2
	800	0.51/ 149.5	3.5/ 69.4	0.11/70.7	0.09/- 91.9	12.2
	1000	0.52/ 139.2	2.8/ 62.8	0.13/70.7	0.08/-106.3	10.2
50	1200	0.52/ 129.5	2.3/ 57.3	0.16/71.5	0.07/-126.8	8.5
	1500	0.52/ 115.2	1.8/ 49.2	0.19/67.0	0.08/-154.7	6.7
	2000	0.53/ 93.7	1.3/ 39.0	0.25/65.6	0.10/ 158.6	4.0
	40	0.42/-105.0	51.8/131.1	0.01/63.4	0.65/- 46.5	37.5
	100	0.46/-148.6	26.6/107.7	0.02/64.8	0.34/- 68.4	30.1
	200	0.48/-170.0	14.0/ 94.9	0.03/64.4	0.19/- 80.7	24.3
	500	0.49/ 165.2	5.7/ 79.7	0.07/73.8	0.09/-100.5	16.4
	800	0.50/ 148.5	3.6/ 69.2	0.11/71.4	0.07/-119.4	12.4
70	1000	0.51/ 138.5	2.9/ 63.1	0.14/71.9	0.07/-140.3	10.5
	1200	0.51/ 128.9	2.4/ 57.5	0.16/71.8	0.07/-157.3	8.8
	1500	0.52/ 114.9	1.9/ 49.9	0.20/67.6	0.09/ 174.1	7.0
	2000	0.53/ 93.6	1.4/ 40.2	0.26/65.7	0.13/ 141.3	4.2
	40	0.40/-117.5	55.2/127.4	0.01/64.0	0.60/- 51.0	37.5
	100	0.46/-154.5	27.2/105.3	0.02/62.6	0.30/- 72.6	30.1
	200	0.48/-173.1	14.2/ 93.6	0.03/70.8	0.16/- 86.1	24.3
	500	0.49/ 164.1	5.8/ 79.3	0.07/75.0	0.08/-109.8	16.4
	800	0.51/ 148.0	3.6/ 69.1	0.11/73.1	0.06/-131.5	12.5
	1000	0.51/ 138.3	2.9/ 62.8	0.14/70.8	0.06/-155.7	10.5
	1200	0.51/ 128.7	2.4/ 57.8	0.16/70.9	0.07/-172.6	8.8
	1500	0.51/ 114.7	1.9/ 49.9	0.20/68.1	0.10/ 165.6	7.0
	2000	0.53/ 93.5	1.4/ 40.6	0.27/64.4	0.14/ 136.3	4.3

Data sheet	
status	Product specification
date of issue	April 1991

BFG135

NPN 7 GHz wideband transistor

NPN planar epitaxial transistor in a plastic SOT223 envelope, intended for wideband amplifier applications. The small emitter structures ensure high output voltage capabilities at a low distortion level. The distribution of the active areas across the surface of the device, gives an excellent temperature profile.

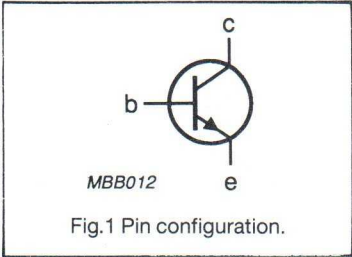
MECHANICAL DATA

SOT223.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	-	25	V
V _{CE0}	collector-emitter voltage	open base	-	-	15	V
I _C	collector current (DC)		-	-	150	mA
P _{tot}	total power dissipation	T _{case} = 145 °C note 1	-	-	1	W
T _j	junction temperature		-	-	175	°C
h _{FE}	DC current gain	I _C = 100 mA; V _{CE} = 10 V	80	-	-	
f _T	transition frequency	f = 1 GHz; I _C = 100 mA; V _{CE} = 10 V; T _{amb} = 25 °C	-	7.0	-	GHz
G _{UM}	maximum power gain	f = 500 MHz; I _C = 100 mA; V _{CE} = 10 V	-	16	-	dB
G _{UM}	maximum power gain	f = 800 MHz; I _C = 100 mA; V _{CE} = 10 V	-	12	-	dB
V _O	output voltage	d _{im} = -60 dB; I _C = 100 mA; V _{CE} = 10 V; R _L = 75 Ω; f _(p+q-r) = 793.25 MHz	-	850	-	mV

Note

1. T_{case} temperature measured on soldering point of collector tab.

NPN 7 GHz wideband transistor**BFG135****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG135	SOT223	bulk	500
BFG135	SOT223	12 mm reel	1000

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	25	V
V_{CEO}	collector-emitter voltage	open base	-	15	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I_C	collector current (DC)		-	150	mA
P_{tot}	total power dissipation	$T_{case} = 145\text{ }^{\circ}\text{C}$	-	1	W
T_{stg}	storage temperature range		-65	+150	$^{\circ}\text{C}$
T_j	junction temperature		-	175	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	NOM.	UNIT
$R_{th\ j-c}$	from junction to case	30	K/W

NPN 7 GHz wideband transistor**BFG135****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 10\text{ V}$	-	-	1	μA
h_{FE}	DC current gain	$I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	80	-	-	
f_T	transition frequency	$f = 1\text{ GHz}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	7.0	-	GHz
C_c	collector capacitance	$f = 1\text{ MHz}$; $I_E = I_C = 0$; $V_{CB} = 10\text{ V}$	-	2.0	-	pF
C_e	emitter capacitance	$f = 1\text{ MHz}$; $I_C = I_E = 0$; $V_{EB} = 0.5\text{ V}$	-	7.0	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CE} = 10\text{ V}$	-	1.2	-	pF
G_{UM}	maximum power gain	$f = 500\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	-	16	-	dB
G_{UM}	maximum power gain	$f = 800\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$	-	12	-	dB
V_o	output voltage	note 1	-	900	-	mV
V_o	output voltage	note 2	-	850	-	mV

Notes

- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$;
 $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $V_q = V_o - 6\text{ dB}$; $f_p = 445.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_q = 453.25\text{ MHz}$; $f_r = 455.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 443.25\text{ MHz}$
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_C = 100\text{ mA}$;
 $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $V_q = V_o - 6\text{ dB}$; $f_p = 795.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_q = 803.25\text{ MHz}$; $f_r = 805.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$

NPN 7 GHz wideband transistor**BFG135****S-Parameters (common emitter) at $V_{CE} = 10\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.**

I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G_{UM} (dB)
		M	Φ	M	Φ	M	Φ	M	Φ	
10	40	0.79/-	25.3	12.7/165.9		0.02/75.7		0.97/-	11.1	38.3
	100	0.70/-	57.4	12.1/146.9		0.04/62.4		0.87/-	25.4	31.7
	200	0.64/-	100.7	9.0/125.7		0.06/46.1		0.69/-	41.2	25.3
	500	0.60/-	162.7	4.6/ 92.7		0.08/32.6		0.44/-	60.4	17.0
	800	0.60/	168.5	2.9/ 75.6		0.08/34.3		0.35/-	73.9	12.7
	1000	0.60/	154.0	2.4/ 65.9		0.08/41.3		0.34/-	82.6	10.8
	1200	0.60/	141.4	1.9/ 57.5		0.08/50.5		0.33/-	93.4	8.9
	1500	0.60/	124.7	1.5/ 48.5		0.09/61.3		0.32/-	111.5	6.7
	2000	0.61/	100.0	1.1/ 34.3		0.41/76.3		0.32/-	144.0	3.2
20	40	0.69/-	38.7	24.8/159.3		0.02/72.6		0.93/-	17.4	38.7
	100	0.62/-	81.3	18.7/138.5		0.04/57.9		0.74/-	39.9	31.0
	200	0.58/-	127.1	13.1/115.7		0.05/45.3		0.53/-	56.9	25.9
	500	0.56/	174.8	6.0/ 88.8		0.06/44.4		0.32/-	72.4	18.3
	800	0.56/	159.5	3.7/ 74.8		0.07/54.9		0.22/-	91.6	13.9
	1000	0.56/	148.2	3.0/ 66.5		0.08/58.2		0.20/-	103.6	11.9
	1200	0.57/	136.6	2.5/ 59.8		0.10/63.9		0.19/-	114.9	10.2
	1500	0.57/	121.5	1.9/ 51.4		0.12/67.9		0.20/-	135.1	8.0
	2000	0.58/	99.8	1.4/ 39.3		0.17/73.3		0.22/-	167.3	5.1
50	40	0.60/-	83.2	44.8/148.9		0.01/69.2		0.82/-	33.1	38.4
	100	0.55/-	131.0	29.7/123.0		0.02/52.4		0.55/-	62.4	32.2
	200	0.54/-	159.8	17.3/104.4		0.03/55.6		0.33/-	86.9	26.9
	500	0.54/	169.9	7.3/ 84.9		0.05/68.7		0.18/-	124.2	19.2
	800	0.54/	152.0	4.6/ 73.7		0.08/71.1		0.15/-	147.1	15.2
	1000	0.54/	142.0	3.6/ 67.0		0.09/71.1		0.15/-	160.5	13.1
	1200	0.54/	132.6	3.0/ 61.8		0.12/72.1		0.15/-	174.7	11.4
	1500	0.54/	119.1	2.4/ 54.2		0.15/72.3		0.18/-	170.8	9.4
	2000	0.56/	98.3	1.6/ 44.2		0.20/71.1		0.22/	148.3	6.4
70	40	0.33/-	117.0	53.4/143.7		0.01/73.3		0.76/-	39.7	38.8
	100	0.49/-	147.8	32.6/117.1		0.02/65.0		0.46/-	74.6	32.5
	200	0.56/-	169.3	18.2/101.0		0.03/66.7		0.28/-	102.7	27.2
	500	0.58/	166.0	7.5/ 83.9		0.05/72.8		0.17/-	141.6	19.4
	800	0.59/	149.8	4.7/ 73.2		0.08/73.2		0.16/-	164.9	15.4
	1000	0.59/	140.1	3.7/ 66.8		0.10/72.2		0.17/-	177.0	13.4
	1200	0.58/	131.1	3.0/ 61.9		0.12/73.9		0.17/-	173.4	11.6
	1500	0.58/	117.9	2.4/ 54.5		0.15/71.8		0.20/	161.2	9.7
	2000	0.58/	97.8	1.7/ 45.3		0.20/70.6		0.25/	138.5	6.7
100	40	0.35/-	130.4	58.2/140.3		0.01/59.3		0.70/-	44.7	38.8
	100	0.50/-	156.7	33.7/114.7		0.02/64.8		0.42/-	79.1	32.7
	200	0.56/-	173.5	18.4/ 99.3		0.03/67.8		0.26/-	108.5	27.2
	500	0.58/	164.4	7.6/ 82.9		0.05/75.5		0.18/-	150.7	19.5
	800	0.59/	148.8	4.7/ 72.7		0.08/74.8		0.17/-	169.5	15.5
	1000	0.59/	139.4	3.7/ 66.3		0.10/75.8		0.18/-	177.7	13.4
	1200	0.58/	130.5	3.0/ 61.7		0.12/74.6		0.18/-	166.9	11.6
	1500	0.58/	117.5	2.4/ 54.4		0.16/73.2		0.21/	156.6	9.8
	2000	0.59/	97.7	1.7/ 45.1		0.20/70.6		0.26/	135.2	6.7

NPN 7 GHz wideband transistor

BFG135

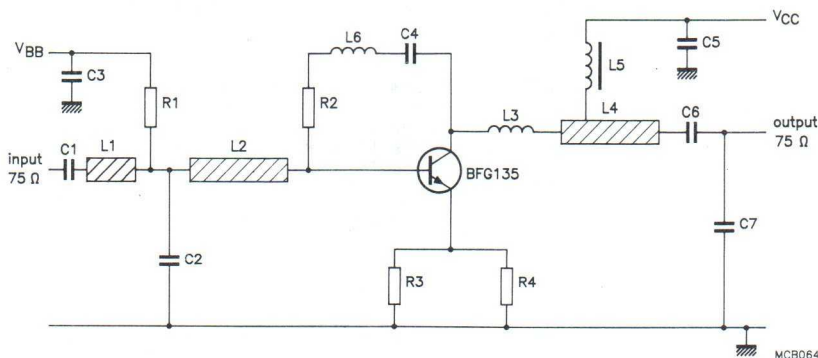


Fig.2 Intermodulation and second harmonic test circuit.

List of components:

R1 = 10 k Ω metalfilm resistor

(cat. no. 2322 180 73103)

R2 = 200 Ω metalfilm resistor

(cat. no. 2322 180 73201)

R3 = R4 = 27 Ω metalfilm resistor

(cat. no. 2322 180 73279)

C1 = C3 = C5 = C6 = 10 nF ceramic multilayer capacitor

(cat. no. 2222 590 08627)

C2 = C7 = 1 pF ceramic multilayer capacitor

(cat. no. 2222 851 12108)

C4 = 10 nF miniature ceramic plate capacitor

(cat. no. 2222 629 08103)

L1 = 75 Ω microstripline

(L = 7 mm; W = 2.5 mm)

L2 = 75 Ω microstripline

(L = 22 mm; W = 2.5 mm)

L3 = 1.5 turn Cu wire (0.4 mm), internal diameter 3 mm, winding pitch 1 mm

(L = 19 mm; W = 2.5 mm)

L4 = 75 Ω microstripline

(L = 19 mm; W = 2.5 mm)

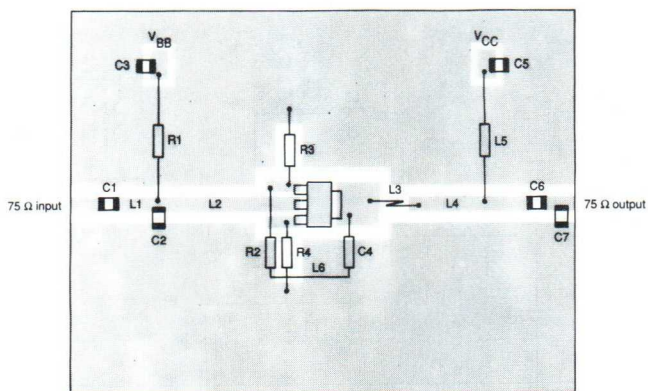
L5 = 5 μ H Ferroxcube choke

(cat. no. 3122 108 20153)

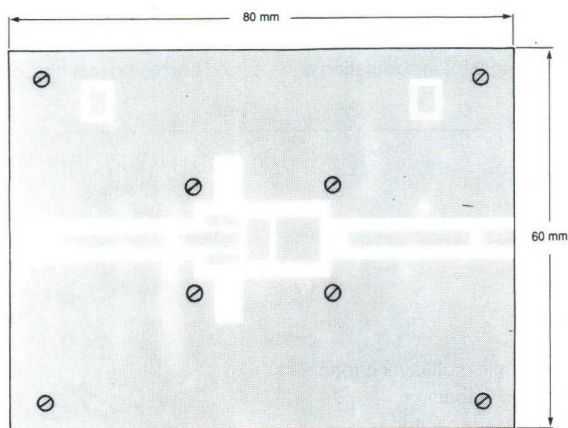
L6 = 30 mm Cu wire (0.4 mm; L $\approx$ 24 nH)

The circuit has been build on a double Cu clad printed circuit board with P.T.F.E. dielectric ($\epsilon_r = 2.2$); thickness 1/16 inch; thickness of copper-sheet 2 x 35 μ m; see Fig 3.

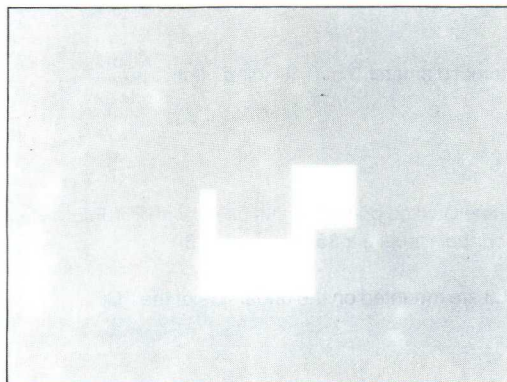
The components R2, L6, C4 and L3 are mounted on the underside of the PCB

NPN 7 GHz wideband transistor**BFG135**

7Z26284



7Z26285



7Z26286

Fig.3 Intermodulation test circuit printed circuit board.

NPN 7 GHz wideband transistor

BFG135

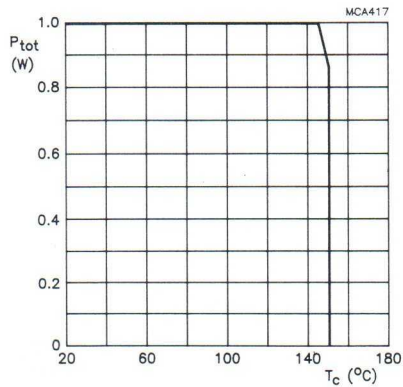
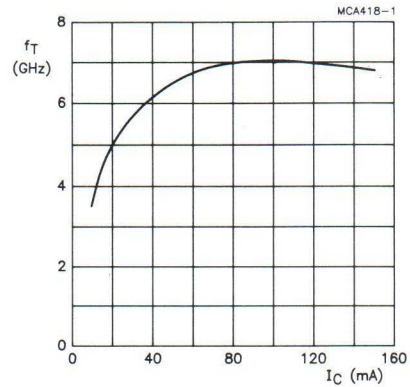
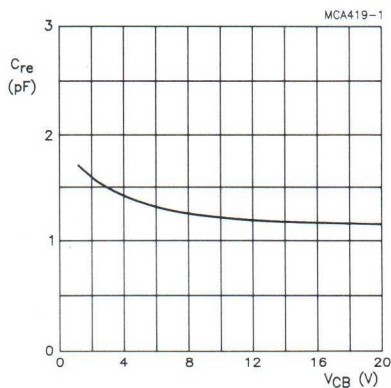
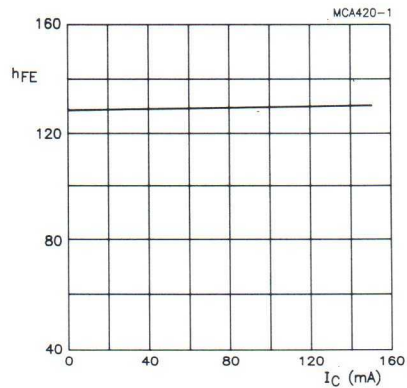


Fig.4 Power derating curve.

Fig.5 Transition frequency as a function of collector current; $V_{CE} = 10$ V; $f = 1$ GHz; $T_j = 25$ °C; typical values.Fig.6 Feedback capacitance as a function of collector-base voltage; $I_E = 0$; $f = 1$ MHz; $T_j = 25$ °C; typical values.Fig.7 DC current gain as a function of collector current; $V_{CE} = 10$ V; $T_j = 25$ °C; typical values.

NPN 7 GHz wideband transistor

BFG135

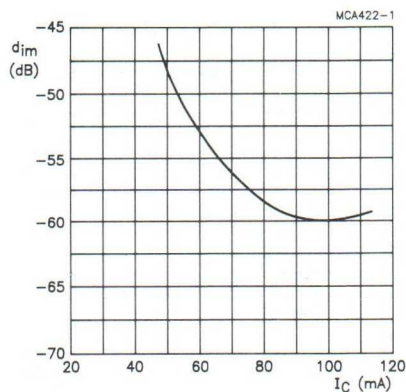


Fig.8 Intermodulation distortion; $V_{CE} = 10$ V;
 $V_o = 900$ mV; $f_{(p+q-r)} = 443.25$ MHz; $T_{amb} = 25$ °C;
 typical values.

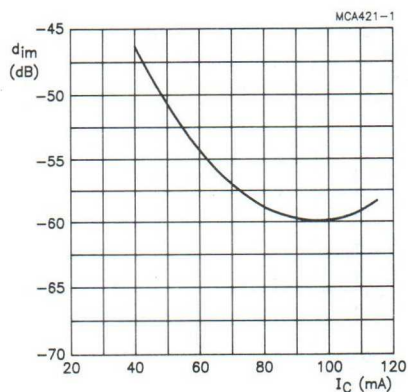


Fig.9 Intermodulation distortion; $V_{CE} = 10$ V;
 $V_o = 850$ mV; $f_{(p+q-r)} = 793.25$ MHz; $T_{amb} = 25$ °C;
 typical values.

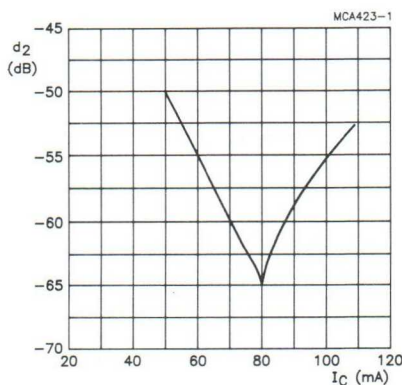


Fig.10 Second order beat; $V_{CE} = 10$ V;
 $V_o = 50$ dBmV; $f_{(p+q)} = 450$ MHz; $T_{amb} = 25$ °C;
 typical values.

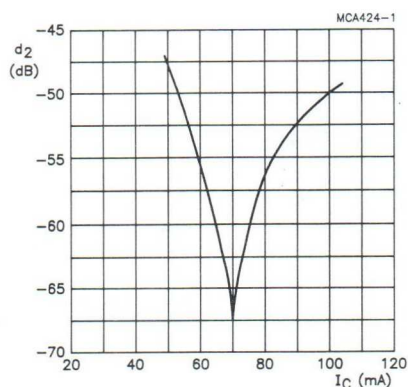


Fig.11 Second order beat; $V_{CE} = 10$ V;
 $V_o = 50$ dBmV; $f_{(p+q)} = 810$ MHz; $T_{amb} = 25$ °C;
 typical values.

NPN 7 GHz wideband transistor

BFG135

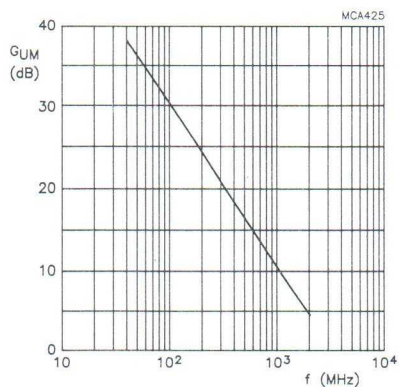


Fig.12 Maximum unilateral gain as a function of frequency; $V_{CE} = 10$ V; $I_C = 100$ mA; $T_{amb} = 25$ °C; typical values.

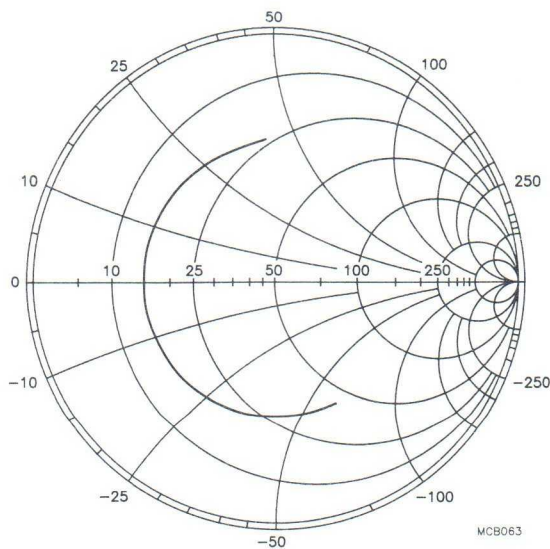


Fig.13 Input reflection coefficient S_{11} ; $V_{CE} = 10$ V; $I_C = 100$ mA; $T_{amb} = 25$ °C; typical values.

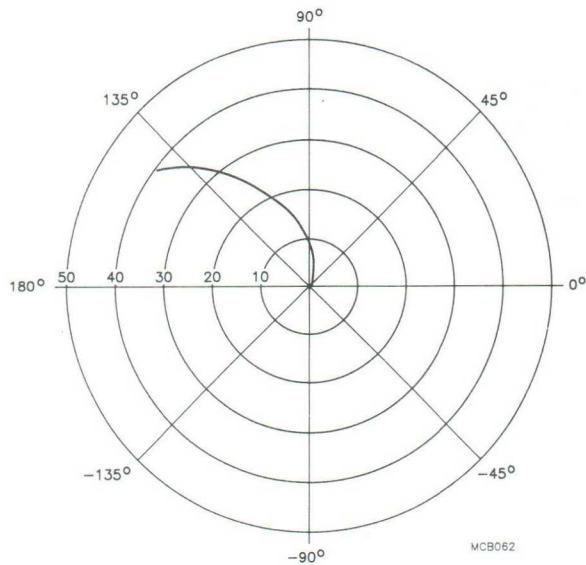
NPN 7 GHz wideband transistor**BFG135**

Fig.14 Forward transmission coefficient S_{21} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

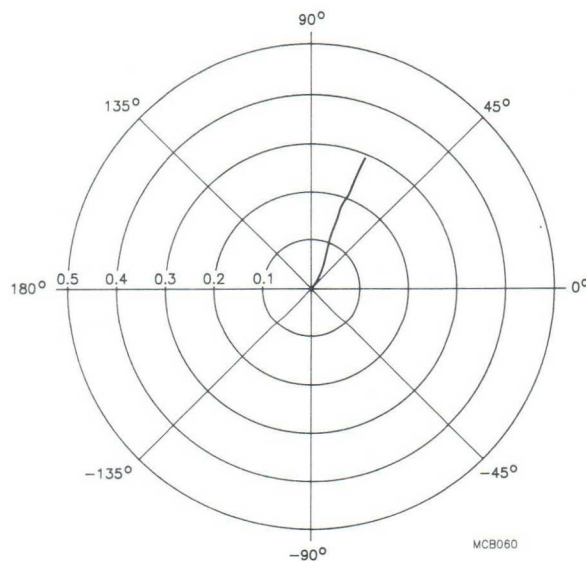


Fig.15 Reverse transmission coefficient S_{12} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.

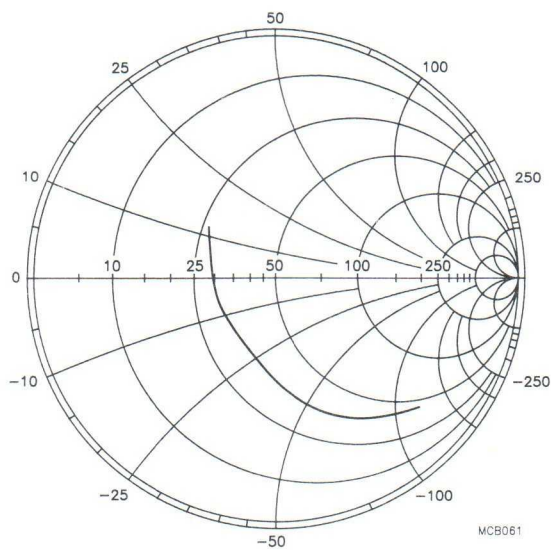
NPN 7 GHz wideband transistor**BFG135**

Fig.16 Output reflection coefficient S_{22} ; $V_{CE} = 10\text{ V}$; $I_C = 100\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; typical values.



Data sheet	
status	Product specification
date of issue	April 1991

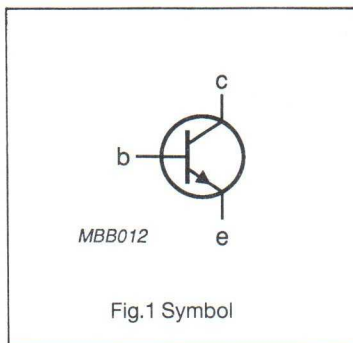
BFG197/197X

NPN 7 GHz wideband transistor

DESCRIPTION

NPN transistor in a microminiature SOT143 envelope. It is designed for wideband application in the 7 GHz range, such as satellite TV systems (SATV) and repeater amplifiers in fibre-optical systems. The device features a very high transition frequency, high gain and a very low noise figure up to high frequencies.

PIN CONFIGURATION



PINNING

BFG 197

PIN	DESCRIPTION
1	collector
2	base
3	emitter
4	emitter

BFG197X

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	10	V
I_C	collector current (DC)		-	100	mA
P_{tot}	total power dissipation	$T_s = 80^\circ\text{C}$	-	300	W
T_j	junction temperature		-	150	$^\circ\text{C}$
f_T	transition frequency	$f = 2\text{ GHz};$ $I_C = 50\text{ mA};$ $V_{CE} = 4\text{ V};$ $T_{amb} = 25^\circ\text{C}$	7.5	-	GHz
C_{re}	feedback capacitance	$f = 1\text{ MHz};$ $I_C = 0;$ $V_{CE} = 8\text{ V}$	0.85	-	pF
G_{UM}	maximum power gain	$f = 2\text{ GHz};$ $I_C = 50\text{ mA};$ $T_{amb} = 25^\circ\text{C};$ $V_{CE} = 4\text{ V};$ $V_{CE} = 6\text{ V};$	-	11	dB
			-	11	dB

NPN 7 GHz wideband transistor**BFG197/197X****ORDERING AND PACKAGE INFORMATION**

EXTENDED TYPE NUMBER	PACKAGE		
	CODE	PACKING METHOD	PACKING QUANTITY
BFG197	SOT143	bulk	500
BFG197	SOT143	12 mm tape	3000
BFG197X	SOT143 note 1	bulk	500
BFG197X	SOT143 note 1	12 mm tape	3000

Note

1. Cross emitter pinning.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	20	V
V_{CEO}	collector-emitter voltage	open base	-	10	V
V_{EBO}	emitter-base voltage	open collector	-	2.5	V
I_C	collector current (DC)		-	100	mA
P_{tot}	total power dissipation	$T_s = 80\text{ }^{\circ}\text{C}$ note 1	-	300	mW
T_{stg}	storage temperature range		-65	150	$^{\circ}\text{C}$
T_j	junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th\ j-s}$	from junction to soldering point	note 1	320	K/W

Note

1. Mounted on a ceramic substrate measuring $8 \times 10 \times 0.7$ mm.
 T_s = temperature measured at soldering point of collector tab.

NPN 7 GHz wideband transistor**BFG197/197X****CHARACTERISTICS** $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 5\text{ V}$	-	-	100	nA
h_{FE}	DC current gain	$I_C = 50\text{ mA}$; $V_{CE} = 5\text{ V}$	40	90	-	
f_T	transition frequency	$f = 2\text{ GHz}$; $I_C = 50\text{ mA}$; $V_{CE} = 4\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	7.5	-	GHz
F	noise figure at optimum source impedance	$I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	1.7	-	dB
F	noise figure at optimum source impedance	$I_C = 50\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$	-	2.3	-	dB
C_C	collector capacitance	$I_E = I_C = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	-	1.5	-	pF
C_e	emitter capacitance	$f = 1\text{ MHz}$; $I_C = I_E = 0$; $V_{EB} = 0.5\text{ V}$	-	3.3	-	pF
C_{re}	feedback capacitance	$f = 1\text{ MHz}$; $I_C = 0$; $V_{CE} = 8\text{ V}$	-	0.85	-	pF
G_{UM}	maximum unilateral power gain	note 1 $f = 2\text{ GHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_E = 50\text{ mA}$; $V_{CE} = 4\text{ V}$	-	11	-	dB
G_{UM}	maximum unilateral power gain	note 1 $f = 2\text{ GHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_E = 50\text{ mA}$; $V_{CE} = 6\text{ V}$	-	11	-	dB

Note

$$1. G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$$

NPN 7 GHz wideband transistor**BFG197/197X**S-parameters (common emitter) at $V_{CE} = 4.00$ V

I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		GUM (dB)
		M	Φ	M	Φ	M	Φ	M	Φ	
10	40	0.36/-	49.6	20.42/165.1		0.02/69.8		1.08/-	14.9	34.7
	100	0.54/-	100.4	17.36/141.8		0.03/57.2		0.94/-	38.0	35.7
	200	0.69/-	134.8	11.94/120.5		0.04/43.6		0.65/-	59.6	26.7
	500	0.82/-	166.8	5.61/ 91.2		0.05/34.6		0.40/-	89.5	20.6
	800	0.84/-	178.7	3.68/ 78.0		0.06/40.2		0.37/-	99.9	17.1
	1000	0.85/	175.2	2.89/ 70.1		0.06/44.3		0.35/-	103.5	15.2
	1200	0.86/	169.3	2.37/ 66.2		0.07/50.9		0.34/-	109.2	13.8
	1500	0.84/	164.4	2.02/ 56.5		0.08/54.9		0.37/-	113.9	12.0
	2000	0.84/	153.5	1.49/ 46.1		0.11/62.6		0.40/-	123.6	9.7
15	40	0.29/-	72.8	26.00/162.3		0.02/66.9		1.06/-	18.9	37.6
	100	0.55/-	119.0	20.87/137.3		0.03/55.1		0.88/-	46.2	34.4
	200	0.70/-	146.8	13.71/116.5		0.04/44.0		0.58/-	70.3	27.5
	500	0.83/-	172.1	6.12/ 89.5		0.04/41.6		0.36/-	104.2	21.5
	800	0.84/	177.8	4.00/ 77.5		0.06/49.0		0.34/-	113.8	17.7
	1000	0.85/	172.4	3.14/ 70.3		0.06/52.8		0.32/-	117.5	15.9
	1200	0.86/	166.8	2.58/ 66.9		0.07/58.0		0.31/-	123.5	14.5
	1500	0.84/	162.5	2.20/ 57.3		0.09/59.9		0.34/-	125.7	12.6
	2000	0.83/	151.9	1.64/ 47.8		0.12/64.6		0.37/-	133.1	10.1
20	40	0.28/-	93.5	30.55/160.2		0.02/65.4		1.05/-	22.1	40.3
	100	0.57/-	130.7	23.42/133.8		0.02/54.4		0.83/-	52.5	34.2
	200	0.72/-	153.7	14.69/113.8		0.03/45.8		0.54/-	78.4	28.0
	500	0.83/-	175.1	6.43/ 88.5		0.04/47.4		0.35/-	114.5	21.8
	800	0.83/	175.8	4.19/ 77.2		0.06/54.6		0.33/-	137.8	18.1
	1000	0.85/	170.8	3.28/ 70.3		0.06/57.8		0.32/-	126.9	16.2
	1200	0.86/	165.3	2.71/ 67.4		0.07/62.2		0.31/-	133.5	14.9
	1500	0.83/	161.4	2.31/ 57.8		0.09/62.6		0.33/-	133.8	12.8
	2000	0.83/	151.0	1.73/ 48.7		0.12/65.2		0.36/-	139.9	10.3
30	40	0.31/-	119.7	36.73/157.0		0.02/62.3		1.01/-	26.9	47.3
	100	0.62/-	143.8	26.39/129.3		0.02/52.4		0.76/-	61.3	34.3
	200	0.75/-	161.8	15.92/110.3		0.03/47.9		0.48/-	89.9	28.7
	500	0.83/-	178.4	6.74/ 87.3		0.04/54.9		0.34/-	126.7	22.2
	800	0.83/	173.6	4.38/ 76.7		0.05/61.5		0.33/-	133.6	18.5
	1000	0.85/	169.0	3.43/ 70.3		0.06/63.0		0.32/-	138.0	16.6
	1200	0.86/	163.8	2.84/ 67.8		0.07/66.9		0.32/-	144.6	15.3
	1500	0.83/	160.2	2.42/ 58.3		0.10/65.1		0.34/-	143.1	13.2
	2000	0.83/	149.8	1.82/ 49.6		0.13/66.4		0.35/-	148.1	10.8
50	40	0.40/-	140.6	44.62/152.6		0.02/54.8		0.96/-	33.5	45.4
	100	0.68/-	155.5	29.14/124.0		0.02/51.8		0.68/-	72.5	34.6
	200	0.77/-	167.8	16.87/106.6		0.02/53.7		0.44/-	103.1	29.4
	500	0.84/	178.7	6.92/ 86.0		0.04/62.3		0.35/-	112.1	22.7
	800	0.84/	171.7	4.49/ 75.8		0.06/66.2		0.34/-	143.8	18.8
	1000	0.85/	167.5	3.51/ 70.0		0.07/67.5		0.33/-	147.8	16.9
	1200	0.86/	162.5	2.91/ 67.8		0.08/70.2		0.33/-	154.4	15.6
	1500	0.83/	159.0	2.48/ 58.3		0.10/67.2		0.34/-	151.3	13.4
	2000	0.82/	148.8	1.88/ 50.0		0.13/66.9		0.36/-	155.2	11.0

NPN 7 GHz wideband transistor

BFG197/197X

S-parameters (common emitter) at $V_{CE} = 8.00$ V

I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}		G _{UM} (dB)
		M	Φ	M	Φ	M	Φ	M	Φ	
5	40	0.57/-	25.7	12.45/169.2		0.02/74.6		1.10/-	9.0	30.5
	100	0.63/-	66.0	11.47/149.8		0.04/62.3		1.03/-	24.9	35.1
	200	0.70/-	106.1	8.71/129.0		0.06/46.8		0.80/-	41.5	26.2
	500	0.83/-	152.5	4.63/ 95.3		0.07/25.7		0.54/-	64.8	19.9
	800	0.84/-	169.0	3.08/ 79.8		0.07/24.3		0.48/-	75.6	16.3
	1000	0.86/-	177.1	2.43/ 70.3		0.07/25.2		0.47/-	79.4	14.5
	1200	0.86/	175.9	1.98/ 65.2		0.07/31.4		0.46/-	86.3	12.8
	1500	0.86/	169.5	1.68/ 55.3		0.07/40.1		0.47/-	93.2	11.3
	2000	0.86/	157.5	1.22/ 43.6		0.09/57.2		0.50/-	107.6	9.0
10	40	0.41/-	42.3	20.42/165.6		0.02/69.2		1.08/-	14.1	34.9
	100	0.56/-	92.9	17.56/142.8		0.03/58.8		0.95/-	36.5	36.6
	200	0.68/-	129.6	12.22/121.8		0.04/44.1		0.66/-	57.3	27.0
	500	0.81/-	164.6	5.83/ 92.0		0.05/33.9		0.41/-	86.5	20.8
	800	0.83/-	177.1	3.82/ 78.8		0.06/39.0		0.37/-	96.7	17.2
	1000	0.84/	176.5	3.01/ 70.8		0.06/43.0		0.35/-	100.4	15.4
	1200	0.85/	170.3	2.47/ 66.9		0.07/49.0		0.34/-	105.8	13.9
	1500	0.83/	165.3	2.10/ 57.3		0.08/53.8		0.36/-	110.9	12.1
	2000	0.83/	154.3	1.55/ 47.0		0.11/61.8		0.40/-	121.0	9.7
15	40	0.34/-	59.1	26.30/163.0		0.02/66.9		1.06/-	18.1	37.9
	100	0.55/-	110.2	21.36/138.3		0.03/55.3		0.89/-	44.6	34.9
	200	0.69/-	141.8	14.19/117.5		0.04/44.4		0.59/-	68.1	27.7
	500	0.81/-	170.0	6.40/ 90.3		0.05/40.1		0.36/-	101.5	21.4
	800	0.82/	179.3	4.18/ 78.3		0.06/47.2		0.33/-	111.1	17.7
	1000	0.83/	173.6	3.28/ 71.0		0.06/51.4		0.32/-	114.4	15.9
	1200	0.84/	167.7	2.70/ 67.7		0.07/56.7		0.31/-	120.9	14.3
	1500	0.82/	163.5	2.30/ 58.2		0.09/58.9		0.33/-	123.3	12.6
	2000	0.82/	152.6	1.71/ 48.5		0.12/63.6		0.36/-	130.8	10.1
20	40	0.31/-	74.2	30.90/160.9		0.02/66.7		1.04/-	21.2	41.3
	100	0.57/-	121.5	24.24/134.8		0.02/53.8		0.83/-	50.9	34.5
	200	0.70/-	148.9	15.38/114.7		0.03/44.9		0.54/-	76.3	28.2
	500	0.81/-	173.1	6.75/ 89.3		0.04/45.5		0.35/-	112.2	21.8
	800	0.82/	177.2	4.39/ 77.8		0.06/53.0		0.32/-	44.9	18.1
	1000	0.83/	171.9	3.45/ 71.0		0.06/55.9		0.31/-	124.9	16.2
	1200	0.84/	166.3	2.84/ 68.1		0.07/61.1		0.30/-	131.5	14.7
	1500	0.82/	162.3	2.42/ 58.7		0.09/61.2		0.33/-	131.9	13.0
	2000	0.81/	151.7	1.81/ 49.5		0.12/64.5		0.35/-	138.1	10.3
30	40	0.31/-	95.5	37.63/157.6		0.02/63.8		1.01/-	26.0	47.5
	100	0.60/-	134.2	27.51/130.3		0.02/53.1		0.77/-	59.7	34.6
	200	0.72/-	156.5	16.67/111.1		0.03/46.6		0.49/-	87.7	28.8
	500	0.82/-	176.4	7.10/ 87.8		0.04/51.9		0.34/-	125.0	22.3
	800	0.82/	175.0	4.62/ 77.3		0.06/59.4		0.32/-	132.0	18.5
	1000	0.83/	170.2	3.62/ 71.0		0.06/61.4		0.31/-	136.5	16.6
	1200	0.84/	164.6	2.99/ 68.4		0.07/64.7		0.30/-	143.4	15.2
	1500	0.81/	161.1	2.54/ 59.0		0.10/63.6		0.32/-	141.8	13.2
	2000	0.81/	150.6	1.92/ 50.4		0.13/65.1		0.34/-	146.6	10.7

NPN 7 GHz wideband transistor

BFG197/197X

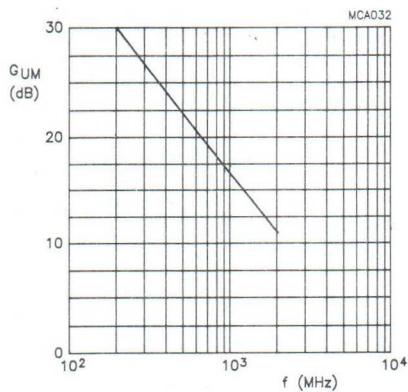


Fig.2 Gain as a function of frequency; $V_{CE} = 8$ V;
 $I_C = 50$ mA; $T_{amb} = 25$ °C; typical values.

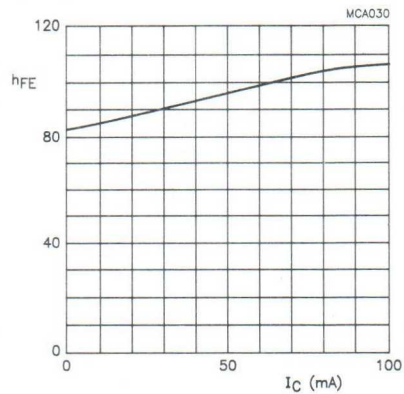


Fig.3 DC current gain; typical values.

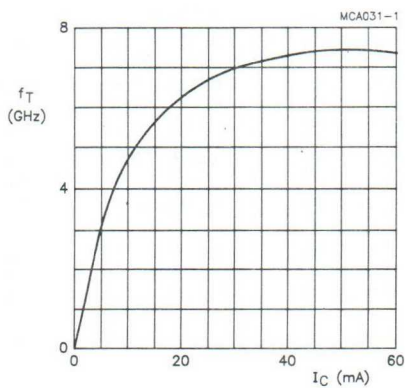


Fig.4 Transition frequency; $V_{CE} = 4$ V; $f = 2$ GHz;
 $T_{amb} = 25$ °C; typical values.

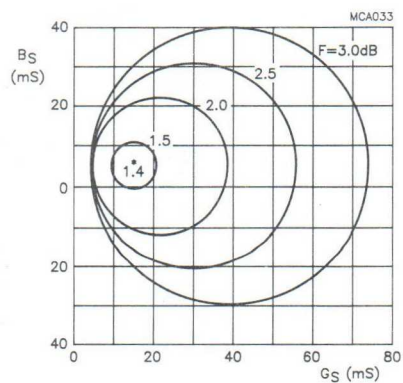


Fig.5 Circles of constant noise; $V_{CE} = 8$ V;
 $I_C = 15$ mA; $f = 800$ MHz; typical values.

NPN 7 GHz wideband transistor

BFG197/197X

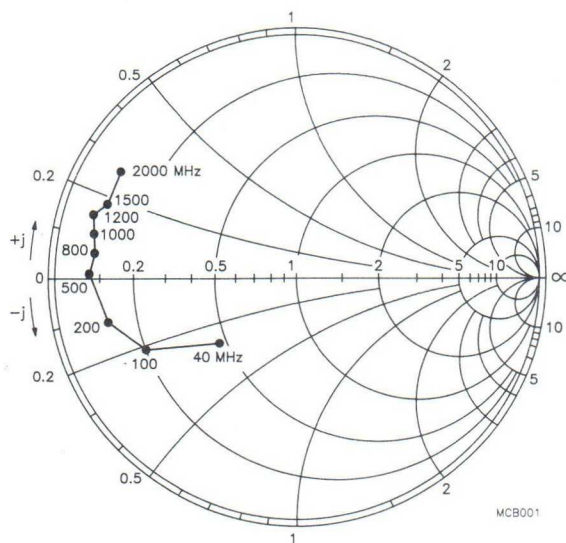


Fig.6 Input impedance derived from S_{11} ($\Omega \times 50$); $V_{CE} = 4$ V; $I_C = 50$ mA; $T_{amb} = 25$ °C.

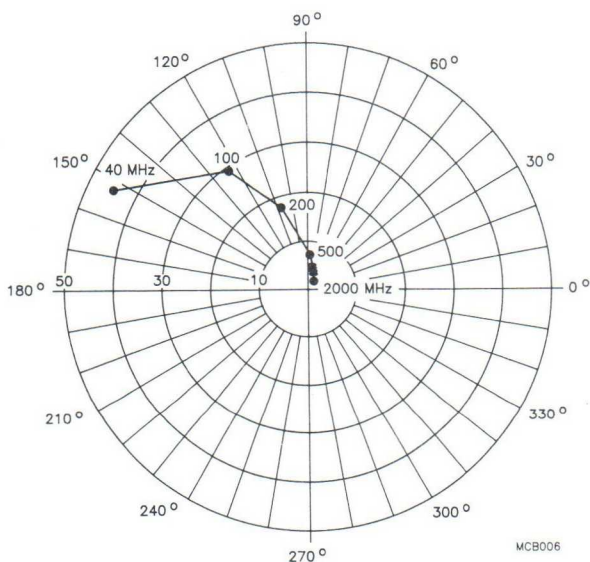


Fig.7 Forward transmission coefficient S_{21} ; $V_{CE} = 4$ V; $I_C = 50$ mA; $T_{amb} = 25$ °C.

NPN 7 GHz wideband transistor

BFG197/197X

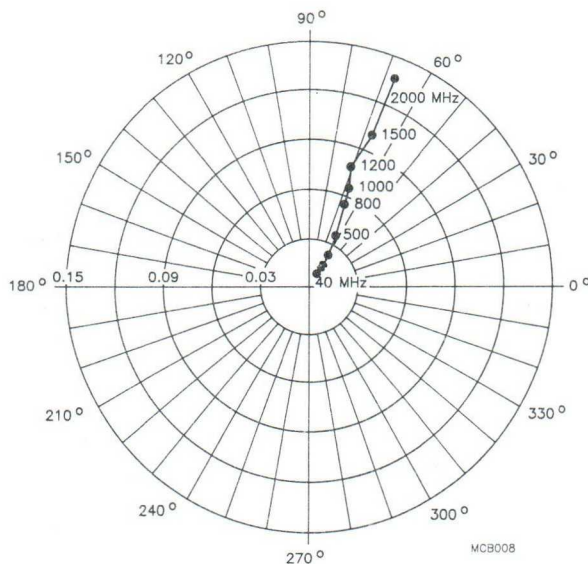


Fig.8 Reverse transmission coefficient S_{12} ; $V_{CE} = 4\text{ V}$; $I_C = 50\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

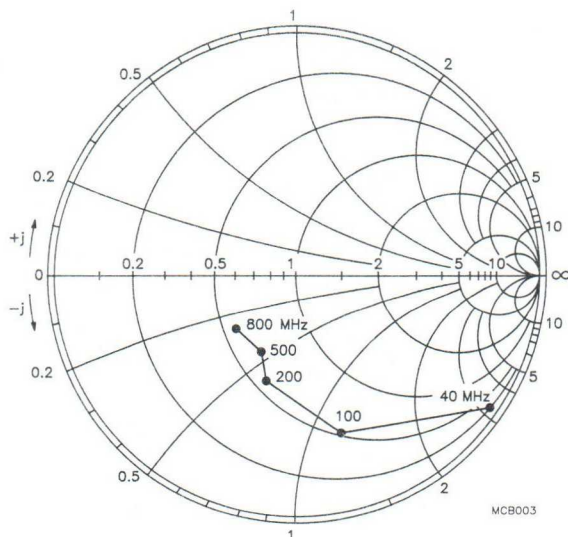


Fig.9 Output impedance derived from S_{22} ($\Omega \times 50$); $V_{CE} = 4\text{ V}$; $I_C = 50\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

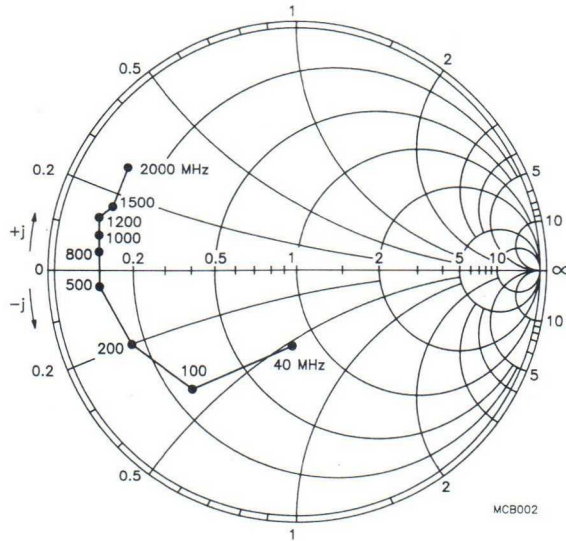
NPN 7 GHz wideband transistor**BFG197/197X**

Fig.10 Input impedance derived from S_{11} ($\Omega \times 50$); $V_{CE} = 8\text{ V}$; $I_C = 30\text{ mA}$; $T_{amb} = 25\text{ }^\circ\text{C}$.

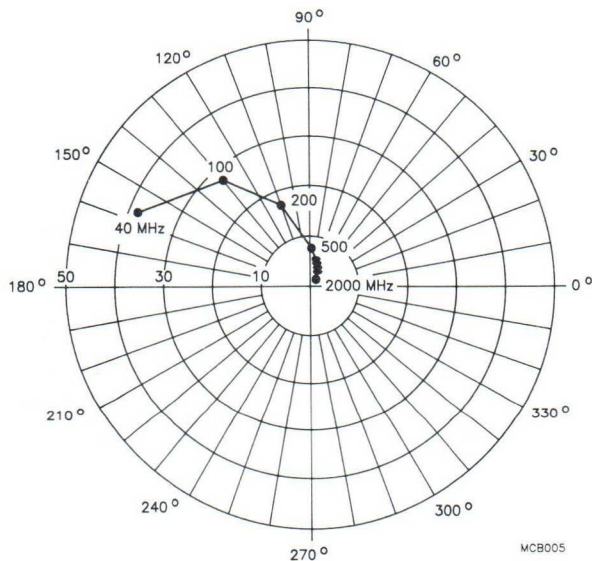


Fig.11 Forward transmission coefficient S_{21} ; $V_{CE} = 8\text{ V}$; $I_C = 30\text{ mA}$; $T_{amb} = 25\text{ }^\circ\text{C}$.

NPN 7 GHz wideband transistor

BFG197/197X

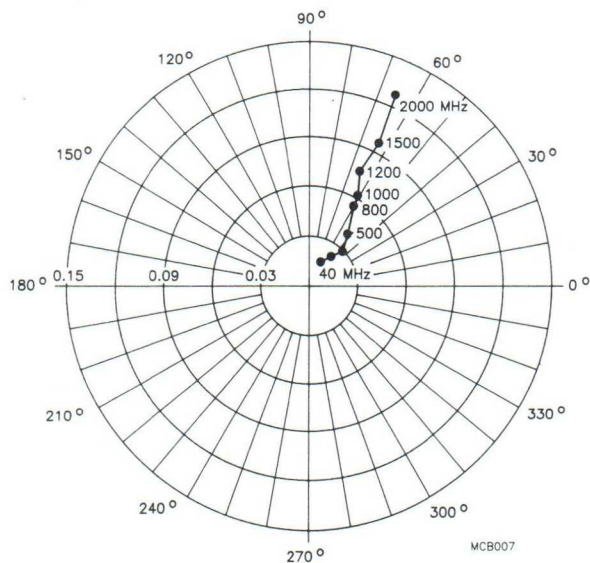


Fig.12 Reverse transmission coefficient S_{12} ; $V_{CE} = 8\text{ V}$; $I_C = 30\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

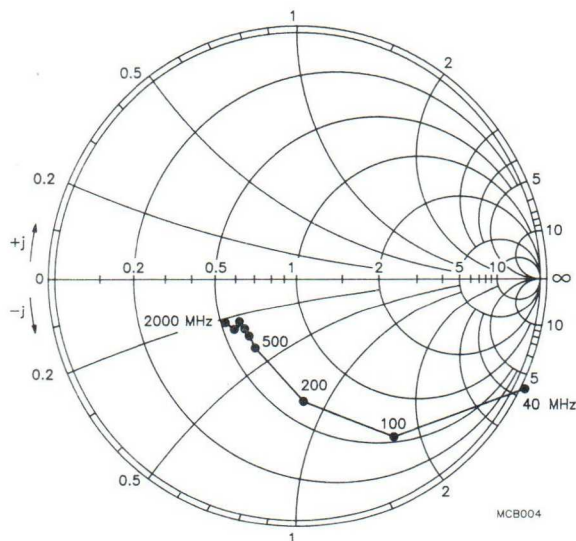


Fig.13 Output impedance derived from S_{22} ($\Omega \times 50$); $V_{CE} = 8\text{ V}$; $I_C = 30\text{ mA}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

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ADS86

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